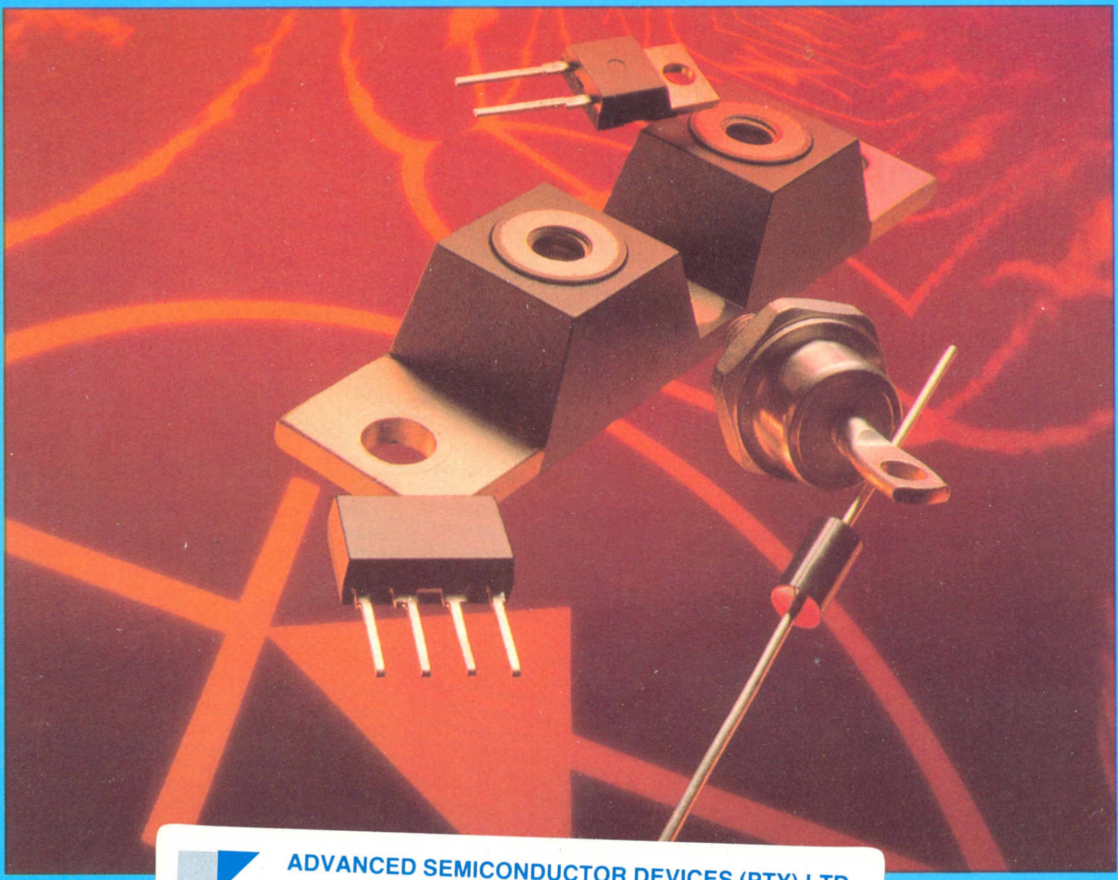
DLE125R3/D

MOTOROLA Semiconductors



RECTIFIERS AND ZENER DIODES DATA

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MOTOROLA

RECTIFIERS AND ZENER DIODES DATA

This book presents technical data for the broad line of Motorola Silicon Rectifiers and Zener Diodes. Complete specifications for the individual devices are provided in the form of data sheets. In addition, a comprehensive selector guide and industry cross-reference guide are included to simplify the task of choosing the best set of components required for a specific application.

The information in this book has been carefully checked and is believed to be accurate; however, no responsibility is assumed for inaccuracies.

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MDA920A8	MDA920A8		—
MDA920A9	MDA920A9		—
MDA970A1	MDA970A1		—
MDA970A2	MDA970A2		—
MDA970A3	MDA970A3		—
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MDA970A6	MDA970A6		—
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*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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.4T6.8,A,B	.5M6.8Z,10,5		—
THRU	THRU		
.4T110,A,B	.5M110Z,10,5		—
.4Z6.8D,10,5	.5M6.8Z,10,5		—
THRU	THRU		
.4Z110D,10,5	.5M110Z,10,5		—
.5M2.4ZS10,5	.5M2.4AZ,10,5		—
THRU	THRU		
.5M110ZS10,5	.5M110Z,10,5		—
.7JZ6.8,A,B,C,D	1M6.8ZS,10,5,1,2		—
THRU	THRU		
.7JZ200,A,B,C,D	1M200ZS,10,5,1,2		—
.7ZM6.8,A,B,C,D	1M6.8ZS,10,5,1,2		—
THRU	THRU		
.7ZM200,A,B,C,D	1M200ZS,10,5,1,2		—
.25T5.6,A		.5M5.6Z10,5	—
THRU		THRU	
.25T110,A		.5M110Z10,5	—
1.5JZ6.8,A,B,C,D		MZG41-6.8A,B	—
THRU		THRU	
1.5JZ200,A,B,C,D		MZG41-200A,B	—
1.5KE6.8,A	1.5KE6.8,A		—
1.5KE7.5,A	1.5KE7.5,A		—
1.5KE8.2,A	1.5KE8.2,A		—
1.5KE9.1,A	1.5KE9.1,A		—
1.5KE10,A	1.5KE10,A		—
1.5KE11,A	1.5KE11,A		—
1.5KE12,A	1.5KE12,A		—
1.5KE13,A	1.5KE13,A		—
1.5KE15,A	1.5KE15,A		—
1.5KE16,A	1.5KE16,A		—
1.5KE18,A	1.5KE18,A		—
1.5KE20,A	1.5KE20,A		—
1.5KE22,A	1.5KE22,A		—
1.5KE24,A	1.5KE24,A		—
1.5KE27,A	1.5KE27,A		—
1.5KE30,A	1.5KE30,A		—
1.5KE33,A	1.5KE33,A		—
1.5KE36,A	1.5KE36,A		—
1.5KE39,A	1.5KE39,A		—
1.5KE43,A	1.5KE43,A		—
1.5KE47,A	1.5KE47,A		—
1.5KE51,A	1.5KE51,A		—
1.5KE56,A	1.5KE56,A		—
1.5KE62,A	1.5KE62,A		—
1.5KE68,A	1.5KE68,A		—
1.5KE75,A	1.5KE75,A		—
1.5KE82,A	1.5KE82,A		—
1.5KE91,A	1.5KE91,A		—
1.5KE100,A	1.5KE100,A		—
1.5KE110,A	1.5KE110,A		—
1.5KE120,A	1.5KE120,A		—
1.5KE130,A	1.5KE130,A		—
1.5KE150,A	1.5KE150,A		—
1.5KE160,A	1.5KE160,A		—
1.5KE170,A	1.5KE170,A		—
1.5KE180,A	1.5KE180,A		—
1.5KE200,A	1.5KE200,A		—
1.5KE220	1.5KE220		—
1.5KE250	1.5KE250		—
1.5R6.8,A,B		MZG41-6.8A,B	—
THRU		THRU	
1.5R200,A,B		MZG41-200A,B	—
1.5Z6.8,A,B,C,D		MZG41-6.8A,B	—
THRU		THRU	
1.5Z200,A,B,C,D		MZG41-200A,B	—
1.5Z6.8D,10,5	1.5M6.8Z,10,5		—
THRU	THRU		
1.5Z200D,10,5	1.5M200Z,10,5		—
1/2R6.8,A,B	.5M6.8Z,10,5		—
THRU	THRU		
1/2R110,A,B	.5M110Z,10,5		
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1/4LZ6.8D,10,5		.5M6.8AZ10,5	—
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1/4M3.0AZ10	1/4M3.0AZ10		2-4
1/4M3.3AZ10	1/4M3.3AZ10		2-4
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1/4M56AZ10	1/4M56AZ10		2-4
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THRU		THRU	
1/4Z110D,10,5		.5M110Z10,5	—
1D3.3,A,B		1M3.3ZS,10,5	—
THRU		THRU	
1D6.2,A,B		1M6.2ZS,10,5	—
1D6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
1D200,A,B		1M200ZS,10,5	—
1EZ110D5	1M110ZS5		—
1EZ120D5	1M120ZS5		—
1EZ130D5	1M130ZS5		—
1EZ140D5	1M140ZS5		—
1EZ150D5	1M150ZS5		—
1EZ160D5	1M160ZS5		—
1EZ170D5	1M170ZS5		—
1EZ180D5	1M180ZS5		—
1EZ190D5	1M190ZS5		—
1EZ200D5	1M200ZS5		—
1M110ZS10	1M110ZS10		—
1M120ZS10	1M120ZS10		—
1M130ZS10	1M130ZS10		—
1M150ZS10	1M150ZS10		—
1M160ZS10	1M160ZS10		—
1M170ZS10	1M170ZS10		—
1M180ZS10	1M180ZS10		—
1M200ZS10	1M200ZS10		—
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THRU	THRU		
1N745	1N745		—
1N702A-0*	1N702A-0		—
THRU	THRU		
1N702A-9	1N702A-9		—
1N703A-0*	1N703A-0		—
THRU	THRU		
1N703A-6	1N703A-6		—
1N704A-0*	1N704A-0		—
THRU	THRU		
1N704A-5	1N704A-5		—
1N705A-0*	1N705A-0		—
THRU	THRU		
1N705A-8	1N705A-8		—
1N706A-0*	1N706A-0		—
THRU	THRU		
1N706A-9	1N706A-9		—
1N707A-0*	1N707A-0		—
THRU	THRU		
1N707A-7	1N707A-7		—
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1N755	1N755		4-4
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1N757	1N757		4-4
1N758	1N758		4-4
1N759	1N759		4-4
1N761,-1,-2*	1N761,-1,-2		—
1N761-69*	1N761-69		—
1N762,-1,-2*	1N762,-1,-2		—
1N763,-1,-2,-3*	1N763,-1,-2,-3		—
1N764,-1*	1N764,-1		—
THRU	THRU		
1N764,-4	1N764,-4		—
1N765,-1,-2*	1N765,-1,-2		—
1N766,-1,-2,-3*	1N766,-1,-2,-3		—
1N767,-1,-2,-3*	1N767,-1,-2,-3		—

*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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1N825A	1N825A		4-10
1N826		1N825	4-10
1N827	1N827		4-10
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1N963A	1N963A		4-4
1N964A	1N964A		4-4
1N965A	1N965A		4-4
1N966A	1N966A		4-4
1N967A	1N967A		4-4
THRU	THRU		
1N975A	1N975A		4-4
1N976A	1N976A		4-4
1N977A	1N977A		4-4
1N978A	1N978A		4-4
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1N989A	1N989A		4-21
1N990A	1N990A		4-21
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1N1351A		1N2974B	—
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1N1352A		1N2975B	—
1N1353		1N2976A	—
1N1353A		1N2976B	—
1N1354		1N2977A	—
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*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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1N2790		1N3156	—
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1N2841A	1N2841A		—
1N2841RA	1N2841RA		—
1N2842A	1N2842A		—
1N2842RA	1N2842RA		—
1N2843A	1N2843A		—
1N2843RA	1N2843RA		—
1N2844A	1N2844A		—
1N2844RA	1N2844RA		—
1N2845A	1N2845A		—
1N2845RA	1N2845RA		—
1N2846A	1N2846A		—
1N2846RA	1N2846RA		—
1N2937			—
1N2970A	1N2970A		—
1N2970RA	1N2970RA		—
1N2971A	1N2971A		—
1N2971RA	1N2971RA		—
1N2972A	1N2972A		—
1N2972RA	1N2972RA		—
1N2973A	1N2973A		—
1N2973RA	1N2973RA		—
1N2974A	1N2974A		—
1N2974RA	1N2974RA		—
1N2975A	1N2975A		—
1N2975RA	1N2975RA		—
1N2976A	1N2976A		—
1N2976RA	1N2976RA		—
1N2977A	1N2977A		—
1N2977RA	1N2977RA		—
1N2978A	1N2978A		—
1N2978RA	1N2978RA		—
1N2979A	1N2979A		—
1N2979RA	1N2979RA		—
1N2980A	1N2980A		—
1N2980RA	1N2980RA		—
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*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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1N2983RA	1N2983RA		—
1N2984A	1N2984A		—
1N2984RA	1N2984RA		—
1N2985A	1N2985A		—
1N2985RA	1N2985RA		—
1N2986A	1N2986A		—
1N2986RA	1N2986RA		—
1N2987A*	1N2987A		—
1N2987RA*	1N2987RA		—
1N2988A	1N2988A		—
1N2988RA	1N2988RA		—
1N2989A	1N2989A		—
1N2989RA	1N2989RA		—
1N2990A	1N2990A		—
1N2990RA	1N2990RA		—
1N2991A	1N2991A		—
1N2991RA	1N2991RA		—
1N2992A	1N2992A		—
1N2992RA	1N2992RA		—
1N2993A	1N2993A		—
1N2993RA	1N2993RA		—
1N2994A*	1N2994A		—
1N2994RA*	1N2994RA		—
1N2995A*	1N2995A		—
1N2995RA*	1N2995RA		—
1N2996A	1N2996A		—
1N2996RA	1N2996RA		—
1N2997A	1N2997A		—
1N2997RA	1N2997RA		—
1N2998A	1N2998A		—
1N2998RA	1N2998RA		—
1N2999A*	1N2999A		—
1N2999RA*	1N2999RA		—
1N3000A	1N3000A		—
1N3000RA	1N3000RA		—
1N3001A	1N3001A		—
1N3001RA	1N3001RA		—
1N3002A	1N3002A		—
1N3002RA	1N3002RA		—
1N3003A	1N3003A		—
1N3003RA	1N3003RA		—
1N3004A	1N3004A		—
1N3004RA	1N3004RA		—
1N3005A	1N3005A		—
1N3005RA	1N3005RA		—
1N3006A	1N3006A		—
1N3006RA	1N3006RA		—
1N3007A	1N3007A		—
1N3007RA	1N3007RA		—
1N3008A	1N3008A		—
1N3008RA	1N3008RA		—
1N3009A	1N3009A		—
1N3009RA	1N3009RA		—
1N3010A	1N3010A		—
1N3010RA	1N3010RA		—
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1N3013RA*	1N3013RA		—
1N3014A	1N3014A		—
1N3014RA	1N3014RA		—
1N3015A	1N3015A		—
1N3015RA	1N3015RA		—
1N3016A	1N3016A		—
1N3017A	1N3017A		—
1N3018A	1N3018A		—
1N3019A	1N3019A		—
1N3020A	1N3020A		—
1N3021A	1N3021A		—
1N3022A	1N3022A		—
1N3023A	1N3023A		—
1N3024A	1N3024A		—
1N3025A	1N3025A		—
1N3026A	1N3026A		—
1N3027A	1N3027A		—
1N3028A	1N3028A		—
1N3029A	1N3029A		—
1N3030A	1N3030A		—
1N3031A	1N3031A		—
1N3032A	1N3032A		—
1N3033A	1N3033A		—
1N3034A	1N3034A		—
1N3035A	1N3035A		—
1N3036A	1N3036A		—
1N3037A	1N3037A		—
1N3038A	1N3038A		—
1N3039A	1N3039A		—
1N3040A	1N3040A		—
1N3041A	1N3041A		—
1N3042A	1N3042A		—
1N3043A	1N3043A		—
1N3044A	1N3044A		—
1N3045A	1N3045A		—
1N3046A	1N3046A		—
1N3047A	1N3047A		—
1N3048A	1N3048A		—
1N3049A	1N3049A		—
1N3050A	1N3050A		—
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*These devices are manufactured by Motorola but no data sheet available — Consult Factory

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1N3222RA	1N3222RA		—
1N3223A	1N3223A		—
1N3223RA	1N3223RA		—
1N3224A	1N3224A		—
1N3224RA	1N3224RA		—
1N3225A	1N3225A		—
1N3225RA	1N3225RA		—
1N3226A	1N3226A		—
1N3226RA	1N3226RA		—
1N3227A	1N3227A		—
1N3227RA	1N3227RA		—
1N3228A	1N3228A		—
1N3228RA	1N3228RA		—
1N3305A	1N3305A		—
1N3305RA	1N3305RA		—
1N3306A	1N3306A		—
1N3306RA	1N3306RA		—
1N3307A	1N3307A		—
1N3307RA	1N3307RA		—
1N3308A	1N3308A		—
1N3308RA	1N3308RA		—
1N3309A	1N3309A		—
1N3309RA	1N3309RA		—
1N3310A	1N3310A		—
1N3310RA	1N3310RA		—
1N3311A	1N3311A		—
1N3311RA	1N3311RA		—
1N3312A	1N3312A		—
1N3312RA	1N3312RA		—
1N3313A	1N3313A		—
1N3313RA	1N3313RA		—
1N3314A	1N3314A		—
1N3314RA	1N3314RA		—
1N3315A	1N3315A		—
1N3315RA	1N3315RA		—
1N3316A	1N3316A		—
1N3316RA	1N3316RA		—
1N3317A	1N3317A		—
1N3317RA	1N3317RA		—
1N3318A	1N3318A		—
1N3318RA	1N3318RA		—
1N3319A	1N3319A		—
1N3319RA	1N3319RA		—
1N3320A	1N3320A		—
1N3320RA	1N3320RA		—
1N3321A	1N3321A		—
1N3321RA	1N3321RA		—
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1N3322RA	1N332RA		—
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1N3325A	1N3325A		—
1N3325RA	1N3325RA		—
1N3326A	1N3326A		—
1N3326RA	1N3326RA		—
1N3327A	1N3327A		—
1N3327RA	1N3327RA		—
1N3328A	1N3328A		—
1N3328RA	1N3328RA		—
1N3329A	1N3329A		—
1N3329RA	1N3329RA		—
1N3330A	1N3330A		—
1N3330RA	1N3330RA		—
1N3331A	1N3331A		—
1N3331RA	1N3331RA		—
1N3332A	1N3332A		—
1N3332RA	1N3332RA		—
1N3333A	1N3333A		—
1N3333RA	1N3333RA		—
1N3334A	1N3334A		—
1N3334RA	1N3334RA		—
1N3335A	1N3335A		—
1N3335RA	1N3335RA		—
1N3336A	1N3336A		—
1N3336RA	1N3336RA		—
1N3337A	1N3337A		—
1N3337RA	1N3337RA		—
1N3338A	1N3338A		—
1N3338RA	1N3338RA		—
1N3339A	1N3339A		—
1N3339RA	1N3339RA		—
1N3340A	1N3340A		—
1N3340RA	1N3340RA		—
1N3341A	1N3341A		—
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1N3342A	1N3342A		—
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1N3346RA	1N3346RA		—
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1N3348RA	1N3348RA		—
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1N3349RA	1N3349RA		—
1N3350A	1N3350A		—
1N3350RA	1N3350RA		—
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1N3520		1N5242B	—
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1N3531		1N5258B	—
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*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

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1N3704A	1M110ZS10		—
1N3704B	1M110ZS5		—
1N3705	1M120ZS10		—
1N3705A	1M120ZS10		—
1N3705B	1M120ZS5		—
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1N3707A	1M150ZS10		—
1N3707B	1M150ZS5		—
1N3708	1M160ZS10		—
1N3708A	1M160ZS10		—
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1N3709	1M180ZS10		—
1N3709A	1M180ZS10		—
1N3709B	1M180ZS5		—
1N3710	1M200ZS10		—
1N3710A	1M200ZS10		—
1N3710B	1M200ZS5		—
1N3779		1N821A	4-10
1N3780		1N821A	4-10
1N3781		1N823A	4-10
1N3782		1N825A	4-10
1N3783		1N827A	4-10
1N3784		1N829A	4-10
1N3785A	1N3785A		—
1N3786A	1N3786A		—
1N3787A	1N3787A		—
1N3788A	1N3788A		—
1N3789A	1N3789A		—
1N3790A	1N3790A		—
1N3791A	1N3791A		—
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1N3793A	1N3793A		—
1N3794A	1N3794A		—
1N3795A	1N3795A		—
1N3796A	1N3796A		—
1N3797A	1N3797A		—
1N3798A	1N3798A		—
1N3799A	1N3799A		—
1N3800A	1N3800A		—
1N3801A	1N3801A		—
1N3802A	1N3802A		—
1N3803A	1N3803A		—
1N3804A	1N3804A		—
1N3805A	1N3805A		—
1N3806A	1N3806A		—
1N3807A	1N3807A		—

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1N3810A	1N3810A		—
1N3811A	1N3811A		—
1N3812A	1N3812A		—
1N3813A	1N3813A		—
1N3814A	1N3814A		—
1N3815A	1N3815A		—
1N3816A	1N3816A		—
1N3817A	1N3817A		—
1N3818A	1N3818A		—
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1N3820A	1N3820A		—
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1N3828	1N3828		4-32
1N3829	1N3829		4-32
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1N3949		1N2984B	—
1N3950		1N3796B	—
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1N3984		1N3997A	—
1N3985		1N3998A	—
1N3986		1N3998A	—
1N3993	1N3993		4-38
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1N3994	1N3994		4-38
1N3994R	1N3994R		—
1N3995	1N3995		4-38
1N3995R	1N3995R		—
1N3996	1N3996		4-38
1N3996R	1N3996R		—
1N3997	1N3997		4-38
1N3997R	1N3997R		—
1N3998	1N3998		4-38
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1N4016B		1N2972B	—
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1N4017A		1N2973A	—
1N4017B		1N2973B	—
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1N4018B		1N2974B	—
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1N4019A		1N2975A	—
1N4019B		1N2975B	—
1N4020		1N2976A	—
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1N4021B		1N2977B	—
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1N4022A		1N2979A	—
1N4022B		1N2979B	—
1N4023		1N2980A	—
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1N4023B		1N2980B	—
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1N4024A		1N2982A	—
1N4024B		1N2982B	—
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1N4025B		1N2984B	—
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1N4026B		1N2985B	—
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1N4027A		1N2986A	—
1N4027B		1N2986B	—
1N4028		1N2988A	—
1N4028A		1N2988A	—
1N4028B		1N2988B	—
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1N4030B		1N2990B	—
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1N4031B		1N2991B	—
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1N4032A		1N2992A	—
1N4032B		1N2992B	—
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1N4035B		1N2997B	—
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1N4036B		1N2999B	—
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1N4037A		1N3000A	—
1N4037B		1N3000B	—
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1N4038A		1N3001A	—
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1N4039A		1N3002A	—
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1N4040A		1N3003A	—

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1N4194A		1N2970A	—
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1N4195B		1N2971B	—
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1N4197B		1N2973B	—
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1N4198A		1N2974A	—
1N4198B		1N2974B	—
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1N4210B		1N2986B	—
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1N4211A		1N2987A	—
1N4211B		1N2987B	—
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1N4212B		1N2988B	—
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1N4214B		1N2990B	—
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1N4215B		1N2991B	—
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1N4216B		1N2992B	—
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1N4226B		1N3002B	—
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1N4235B		1N3011B	—
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1N4278B		1N2995B	—
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THRU		THRU	
BZY88-C30		.5M30Z5	—
BZY91-C7V5		50M7.5ZS5	—
THRU		THRU	
BZY91-C75		50M75ZS5	—
BZY93-C7V5		10M7.5Z5	—
THRU		THRU	
BZY93-C75		10M75Z5	—
BZY96-C4V7		1M4.7AZ5	—
THRU		THRU	
BZY96-C75		1M75Z5	—
C0DI6041		MZ2360	4-115
C0DI6045		MZ2360	4-115
C0DI6042		MZ2361	4-115
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C0DI6049		MZ2360	4-115
C0DI6050		MZ2361	4-115
C4011		1N746-1N759	4-4
THRU		THRU	
C4029		1N957-1N973	—
C6012		MZC2.7A10	—
THRU		THRU	
C6032		MZC47A10	—
CD3168	1N5262		—
THRU	THRU		
CD3174	1N5268		—
CD4112	1N3154		4-29
THRU	THRU		
CD4115	1N3157		4-29
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THRU		THRU	
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THRU		THRU	
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CD3212048		1M8.2ZS	—
THRU		THRU	
CD3212062		1M33ZS	—
CD3214738		1M8.2ZS	—
THRU		THRU	
CD3214752		1M33ZS	—
CD3907562	.4M8.2Z		—
THRU	THRU		
CD3909732	.4M33Z		—
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THRU	THRU		
CZ200,A,B,C,D	1M200ZS,10,5,1,2		
DI-746	1N746		4-4
DI-759	1N759		4-4
DI-957	1N957A		4-4
DI-976	1N976A		4-4
DSZ3006	5M6.0ZS5		
THRU	THRU		
DSZ3100	5M100ZS5		—
EVR6,A		1M6.8ZS10,5	—
THRU		THRU	
EVR150,A		1M150ZS10,5	
G4Z7.5		.5M7.5Z10	—
THRU		THRU	
G4Z110		.5M110Z10	—
GA4Z2.4		.5M2.4AZ	—
THRU		THRU	
GA4Z12.0		.5M12AZ	—
GARE SERIES		1N821 SERIES	4-10
GLAZ2.6A		1N702A	—
THRU		THRU	
GLAZ6.8A		1N710A	—
GLZ7.0A		1N763A	—
THRU		THRU	
GLZ24A		1N769A	—
GLZ7.5A		1N711A	—
THRU		THRU	
GLZ100A		1N738A	—
GRE11.7 SERIES		1N941 SERIES	4-17
GRE SERIES		1N935 SERIES	4-13
GW6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
GW200,A,B		1M200ZS,10,5	
HM6.8	1N746-1N759		4-4
THRU	THRU		
HM200	1N957-1N992		
HW6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
HW200,A,B		1M200ZS,10,5	
ICT-5		ICTE-5	—
ICT-8		ICTE-8	—
ICT-10		ICTE-10	—
ICT-12		ICTE-12	—
ICT-15		ICTE-15	—
ICT-18		ICTE-18	—
ICT-22		ICTE-22	—
ICT-36		ICTE-36	—
ICT-45		ICTE-45	—
ICTE-5	ICTE-5		—
ICTE-5C	ICTE-5C		—
ICTE-8	ICTE-8		—
ICTE-10	ICTE-10		—
ICTE-12	ICTE-12		—
ICTE-15	ICTE-15		—
ICTE-18	ICTE-18		—
ICTE-22	ICTE-22		—
ICTE-36	ICTE-36		—
ICTE-45	ICTE-45		—
JZ3.9,A,B,C,D	1M3.9ZS,10,5,1,2		—

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THRU	THRU		
LMZ200,A	1M200ZS10,5		—
LPM7.5,A	1M7.5ZS10,5		—
THRU	THRU		
LPM200,A	1M200ZS10,5		—
LPZ7.5,A	1M7.5ZS10,5		—
THRU	THRU		
LPZ200,A	1M200ZS10,5		—
LPZT8.2	1M8.2ZZ10		—
THRU	THRU		
LPZT33	1M33ZZ10		—
LVA43,A,B,C		1N5521A,B,C,D	—
THRU		THRU	
LVA100,A,B,C		1N5530A,B,C,D	—
LVA343,A,B,C		1N5521A,B,C,D	—
THRU		THRU	
LVA3100,A,B,C		1N5530A,B,C,D	—
M4Z7.5,A		.5M7.5Z10,5	—
THRU		THRU	
M4Z110,A		.5M110Z10,5	—
MC6007,A		1N746-1N759	4-4
THRU		THRU	
MC6030,A		1N957A-1N977A	4-4
MC6107,A		1M6.8ZS10,5	—
THRU		THRU	
MC6130,A		1M47ZS10,5	—
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MC6418		1N936	4-13
MC6419		1N936A	4-13
MC6420		1N937	4-13
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MC6422		1N938	4-13
MC6423		1N939A	4-13
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MC6428		1N937	4-13
MC6429		1N939A	4-13
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MCL1302	MCL1302		4-87
MCL1303	MCL1303		4-87
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(M)GLA100		1N5518 SERIES	4-16
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(M)HLA3100		1N5518 SERIES	4-16
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THRU		THRU	
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THRU	THRU		

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THRU	THRU		
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MLL4099	MLL4099		4-93
THRU	THRU		
MLL4135	MLL4135		4-93
MLL4370	MLL4370		4-88
THRU	THRU		
MLL4372	MLL4372		4-88
MLL4614	MLL4614		4-93
THRU	THRU		
MLL4627	MLL4627		4-93
MLL4678	MLL4678		4-97
THRU	THRU		
MLL4717	MLL4717		4-97
MLL4728	MLL4728		4-99
THRU	THRU		
MLL4764	MLL4764		4-99
MLL5221	MLL5221		—
THRU	THRU		
MLL5270	MLL5270		—
MLV746A		1N746A	—
THRU		THRU	
MLV759A		1N759A	—
MLV4370A		1N4370A	—
THRU		THRU	
MLV4372A		1N4372A	—
MMZ7.5,A	1M7.5ZS10,5		—
THRU	THRU		
MMZ200,A	1M200ZS10,5		—
MPT-5		MPTE-5	—
MPT-8		MPTE-8	—
MPT-10		MPTE-10	—
MPT-12		MPTE-12	—
MPT-15		MPTE-15	—
MPT-18		MPTE-18	—
MPT-22		MPTE-22	—
MPT-36		MPTE-36	—
MPT-45		MPTE-45	—
MPTE-5	MPTE-5		—
MPTE-8	MPTE-8		—
MPTE-10	MPTE-10		—
MPTE-12	MPTE-12		—
MPTE-15	MPTE-15		—
MPTE-18	MPTE-18		—
MPTE-22	MPTE-22		—
MPTE-36	MPTE-36		—
MPTE-45	MPTE-45		—
MPZ5-16A	MPZ5-16A		4-110
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MPZ5-180B	MPZ5-180B		4-110
MPZ5-180C	MPZ5-180C		4-110
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MTZ630,A	1N957-1N977		—
MZ7.5,A	10M7.5,10,5		—
THRU	THRU		
MZ92-2.4	1N4370		4-4
MZ92-2.5		.5M2.5AZ10	—
MZ92-2.7		1N4371	4-4
MZ92-2.8		.5M2.8AZ10	—
MZ92-3.0		1N4372	4-4
MZ92-3.3		1N746	4-4
MZ92-3.6		1N747	4-4
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MZ92-5.1		1N751	4-4
MZ92-5.6		1N752	4-4
MZ92-6.0		.5M6.0AZ10	—
MZ92-6.2		1N753	4-4
MZ92-6.8		1N754	4-4
MZ92-7.5		1N755	4-4
MZ92-8.2		1N756	4-4
MZ92-8.7		.5M8.7AZ10	—
MZ92-9.1		1N757	4-4
MZ92-10		1N758	4-4
MZ92-11		.5M11AZ10	—
MZ92-12		1N759	4-4
MZ92-13		1N964A	4-4
MZ92-14		.5M14Z10	—
MZ92-15		1N965A	4-4
MZ92-16		1N966A	4-4
MZ92-17		.5M17Z10	—
MZ92-18		1N967A	4-4
MZ92-19		.5M19Z10	—
MZ92-20		1N968A	4-4
MZ92-22		1N969A	4-4
MZ92-24		1N970A	4-4
MZ92-25		.5M25Z10	—
MZ92-27		1N971A	4-4
MZ92-28		.5M28Z10	—
MZ92-30		1N972A	4-4
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MZ92-60		.5M60Z10	—
MZ92-62		1N980A	4-4
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MZ92-87		.5M87Z10	—
MZ92-91		1N984A	4-4
MZ92-100		1N985A	4-4
MZ92-110		1N986A	4-4
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THRU		THRU	
MZ122		5M110ZSB5	—
MZ200,A	10M200Z10,5		—
MZ220		5M200ZS10	—
THRU		THRU	
MZ222		5M110ZSB10	—
MZ240		5M200ZSB10	—
THRU		THRU	
MZ322		5M110ZSB20	—
MZ320		5M200ZS20	—
THRU		THRU	
MZ340		5M200ZSB20	—
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MZ500-12		1N5235A	4-51
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THRU		THRU	
MZ806		5M6.8ZS10	—
MZ906		5M6.8ZS20	—
MZ1000-1		1N4728	4-47
MZ1000-2		1N4729	4-47
MZ1000-3		1N4730	4-47
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THRU		THRU	
MZ5220		5M200ZS10	—
MZ5222		5M110ZSB10	—
THRU		THRU	
MZ5240		5M200ZSB10	—
MZ5555		1N6283A	—
MZ5556		1N6287A	—
MZ5557		1N6289A	—
MZ5558		1N6303A	—
MZ5806		5M6.8ZS10	—
THRU		THRU	
MZ5890		5M90ZS10	—
MZP5221,A,B	1N5221,A,B		—
MZP5270,A,B	1N5270,A,B		—
MZT2970	MZT2970		—
THRU	THRU		
MZT3015	MZT3015		—
MZT3305	MZT3305		—
THRU	THRU		
MZT3350	MZT3350		—
MZT4549	MZT4549		—
THRU	THRU		
MZT4554	MZT4554		—
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P6KE22	P6KE22		4-117
P6KE24	P6KE24		4-117
P6KE27	P6KE27		4-117
P6KE30	P6KE30		4-117
P6KE33	P6KE33		4-117
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P6KE39	P6KE39		4-117
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THRU		THRU	
PD6061,A		1N957A-1N968A	4-4
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THRU		THRU	
PD6210,A,B,C		1N5530A,B,C,D	—
PR6105-PR6450	1N825		4-10
PR6105A-PR6450A	1N827		4-10
PR9110-PR9450	1N937		4-10
PR9110A-PR9450A	1N938		4-10
PRD105	MZ605		4-112
PRD110	MZ610		4-112
PRD120	MZ620		4-112
PRD140	MZ640		4-112
PRD160	MZ640		4-112
PS3535	1N4570A		—
THRU	THRU		
PS3539	1N4573A		—
PS3546	1N4565A		—
THRU	THRU		
PS3549	1N4568A		—
SG1910		MZ2360	4-115
THRU		THRU	
SG1912		MZ2360	4-115
SG1920		MZ2361	4-115
SG1922		MZ2361	4-115
SS1		MZ2360	4-115
SS1-2		MZ2361	4-115
STB567		MZ2361	4-115
SV7401		MZ605	4-112
SVR4732,A		1M4.7ZS10,5	—
THRU		THRU	
SVR4764,A		1M100ZS10,5	—
SX30	1M2.4ZS10,5	1M30ZS5	—
THRU	THRU	THRU	
SX120	1M16ZS10,5	1M120ZS5	—
SZ2.4,A	1M3.9ZS,10,5,1,2		—
THRU	THRU		
SZ16.0,A	1M200ZS,10,5,1,2		—
TZ3.9,A,B,C,D			—
THRU			
TZ200,A,B,C,D			—
UZ120		5M200ZS5	—
THRU		THRU	
UZ220		5M200ZS10	—
UZ122		5M110ZSB5	—
THRU		THRU	
UZ222		5M100ZSB10	—
UZ140		5M200ZSB5	—
THRU		THRU	
UZ240		5M200ZSB10	—
UZ706		5M6.8ZS5	—
UZ806		5M6.8ZS10	—
UZ3016,A,B		1N3016A,B	—

*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

ZENER INDEX CROSS-REFERENCE (Continued)

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page #
UZ3051,A,B		1N3051A,B	—
UZ3235,A,B		1N5235,A,B	—
THRU		THRU	
UZ3281,A,B		1N5281,A,B	—
UZ3470,A,B		1N2970A,B	—
UZ3515,A,B		1N3015A,B	—
UZ4116,A,B		1N5384A,B	4-63
UZ4706,A,B		1N5342A,B	4-63
UZ4736,A		1N4736,A	4-47
THRU		THRU	
UZ4764,A		1N4764,A	4-47
UZ5120		5M200ZS5	—
THRU		THRU	
UZ5220		5M200ZS10	—
UZ5122		5M110ZSB5	—
THRU		THRU	
UZ5222		5M110ZSB10	—
UZ5140		5M200ZSB5	—
THRU		THRU	
UZ5240		5M200ZSB10	—
UZ5706		5M6.8ZS5	—
THRU		THRU	
UZ5806		5M6.8ZS10	—
UZ7110		10M100Z5	—
THRU		THRU	
UZ7210		10M100Z10	—
UZ7706		10M6.8Z5	—
THRU		THRU	
UZ7806		10M6.8Z10	—
UZ8120		1M200ZS5	—
THRU		THRU	
UZ8220		1M200ZS10	—
UZ8706		1M6.8ZS5	—
THRU		THRU	
UZ8806		1M6.8ZS10	—
VR6.2	1M6.2ZS10		—
THRU	THRU		
VR200	1M200ZS10		—
Z4X5.1B,A	1M5.1AZ10,5		—
THRU	THRU		
Z4X14B,A	1M14Z10,5		—
ZA6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
ZA82,A,B		1M82ZS,10,5	—
ZAC6.8,A,B		5M6.8ZS,10,5	—
THRU		THRU	
ZAC200,A,B		5M200ZS,10,5	—
ZB6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
ZB200,A,B		1M200ZS,10,5	—
ZBC6.8,A,B,C,D,E		1M6.8,10,5,1,2,3	—
THRU		THRU	
ZBC200,A,B,C,D,E		1M200,10,5,1,2,3	—
ZC6.8,A,B,C,D,E		5M6.8ZS,10,5,1,2	—
THRU		THRU	
ZC200,A,B,C,D,E		5M200ZS,10,5,1,2	—
ZCC6.8,A,B,C,D,E		5M6.8ZS,10,5,1,2	—
THRU		THRU	
ZCC200,A,B,C,D,E		5M200ZS,10,5,1,2	—
ZD3.3,A,B		1M3.3ZS,10,5	—
THRU		THRU	
ZD6.2,A,B		1M6.2ZS,10,5	—
ZD3.9	1M3.9ZS,10,5		—
THRU	THRU		
ZD200	1M200ZS,10,5		—
ZD6.8,A,B		1M6.8ZS,10,5	—
THRU		THRU	
ZD200,A,B		1M200ZS,10,5	—
ZM3.9,A,B,C,D	1M3.9ZS,10,5,1,2		—
THRU	THRU		
ZM200,A,B,C,D	1M200ZS,10,5,1,2		—
ZS4.7,A,B		1M4.7ZS,10,5	—
THRU		THRU	
ZS36,A,B		1M36ZS,10,5	—

*These devices are manufactured by Motorola but no data sheet available — Consult Factory.

1

1

RECTIFIERS

Motorola is the world's leading supplier of rectifiers, including those for use in switching power supplies. Wafer fabrication technology has constantly improved, leading to the product offering outlined in this selector guide. Today's Motorola rectifiers embody the same precision technology as the most advanced ICs, and are capable of passing stringent environmental testing, including under the hood of an automobile.

In addition to improved quality, rectifier product trends are toward higher operating temperature, faster switching times, plastic packages (translate lower cost) and use of dual rectifier modules.

ZENER DIODES

Motorola's standard Zeners and Avalanche Regulator diodes comprise the largest inventoried line in the industry. Continuous development of improved manufacturing techniques have resulted in computerized diffusion and test, as well as critical process controls learned from surface-sensitive MOS fabrication. Resultant high yields lower factory costs. Check the following features for application to your specific requirements:

- Wide selection of package materials and styles:
  - Plastic (Surmetic) for low cost, mechanical ruggedness
  - Glass for highest reliability, lowest cost
  - Metal for highest power
- Power ratings from 0.25 to 50 Watts
- Breakdown voltages from 1.8 to 200 V in approximately 10% steps
- Available tolerances from 10% (low cost) to a tight as 1% (critical applications) with off-the-shelf delivery
- Special selection of electrical characteristics available at low cost due to high-volume lines (check your Motorola sales representative for special quotations)
- JAN/JANTX(V) availability
- Special glass now used in DO-35 type packages is compatible with low temperature alloy processes, yielding sharper breakdown and low leakage.

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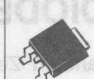
Schottky Rectifiers

SWITCHMODE Schottky Power Rectifiers with the high speed and low forward voltage drop characteristic of Schottky's metal/silicon junctions are produced with ruggedness and temperature performance comparable to silicon-junction rectifiers. Ideal for use in low voltage, high frequency power supplies and as very fast clamping diodes, these devices feature switching times less than 10 ns, and are offered in current ranges from 0.5 to 300 amperes, and reverse voltages to 60 volts.

In some current ranges, devices are available with junction temperature specifications of 125°C, 150°C, 175°C. Devices with higher T_J ratings can have significantly lower leakage currents, but higher forward-voltage specifications. These parameter tradeoffs should be considered when selecting devices for applications that can be satisfied by more than one device type number.

All devices are connected cathode to case or cathode to heatsink, where applicable. Reverse polarity may be available on some devices upon special request. Contact your Motorola representative for more information.

	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)							
	0.5		1.0		3.0			5.0
	362-01 MLL34 Glass Leadless	299-02 (DO-204AH) Glass	59-04 Plastic	362B-01 MLL41 Glass Leadless	267-02 Plastic		369A-04 Plastic	60-01 Metal
V_{RRM} (Volts)								
15								
20			1N5817	MBRL120	1N5820	MBR320	MBRD320	1N5823
25								
30	MBRL030	MBR030	1N5818	MBRL130	1N5821	MBR330	MBRD330	1N5824
35								
40	MBRL040	MBR040	1N5819	MBRL140	1N5822	MBR340	MBRD340	1N5825
45								
50			MBR150††			MBR350	MBRD350	
60			MBR160††			MBR360	MBRD360	
70								
80								
90								
100								
I_{FSM} (Amps)	5.0	5.0	25	20	80	80	75	500
†T_C @ Rated I_O (°C)							125	
†T_L @ Rated I_O (°C)	75	75	90	75	95			80
T_J (Max) (°C)	150	150	125	150	125	150	150	125
Max V_F @ $I_{FM} = I_O$	0.65 T_L = 25°C	0.65 T_L = 25°C	*0.60 T_L = 25°C	*0.69 T_L = 25°C	*0.525 T_L = 25°C	***0.740 T_L = 25°C	0.45 T_C = 125°C	*0.38 T_C = 25°C

☐ TX versions available.

* Values are for the 40-Volt units. The lower voltage parts provide lower limits and higher voltage units provide slightly higher limits.

** I_O is total device output.

*** Values are for 60 volt units. The lower voltages parts ≤40 volts provide lower limits.

† Must be derated for reverse power dissipation. See Data Sheet.

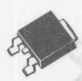
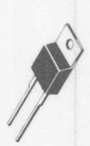
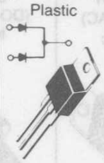
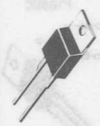
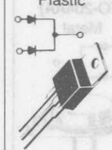
†† T_J (Max) = 150°C

There are many other standard features in Motorola Schottky rectifiers that give added performance and reliability.

1. GUARDRINGS are included in all Schottky die for reverse voltage stress protection from high rates of dv/dt to virtually eliminate the need for snubber networks. The guardring also operates like a zener and avalanches when subjected to voltage transients.

2. MOLYBDENUM DISCS on both sides of the die minimize fatigue from power cycling in all metal product. The plastic TO-220 devices have a special solder formulation for the same purpose.

3. QUALITY CONTROL monitors all critical fabrication operations and performs selected stress tests to assure constant processes.

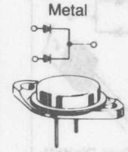
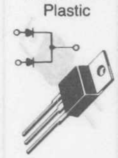
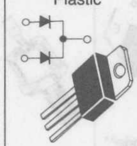
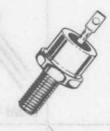
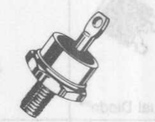
I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)								
6.0	7.5	10	15		16	20	25	
369A-04 Plastic  Dual Diode**	221B-01 (TO-220AC) Plastic 		221A-04 (TO-220AB) Plastic  Dual Diode**	56-03 (DO-203AA) (DO-4) Metal 	221B-01 (TO-220AC) Plastic 	221A-04 (TO-220AB) Plastic  Dual Diode**	56-03 (DO-203AA) (DO-4) Metal 	
MBRD620CT				1N5826			1N5829	
MBRD630CT				1N5827			1N5830	1N6095
	MBR735	MBR1035	MBR1535CT		MBR1635	MBR2035CT		
MBRD640CT	MBR740	MBR1040	MBR1540CT	1N5828	MBR1640	MBR2040CT	1N5831	1N6096
	MBR745	MBR1045	MBR1545CT		MBR1645	MBR2045CT		
MBRD650CT								
MBRD660CT		MBR1060				MBR2060CT		
		MBR1070				MBR2070CT		
		MBR1080				MBR2080CT		
		MBR1090				MBR2090CT		
		MBR10100				MBR20100CT		
	150	150	150	500	150	150	800	400
	105	135	105	85	125	135	85	70
	150	150	150	125	150	150	125	125
	0.57 T_C = 125°C	0.57 T_C = 125°C	0.72 @ 15 A T_C = 125°C	*0.50 T_C = 25°C	0.57 T_C = 125°C	0.72 @ 20 A T_C = 125°C	*0.48 T_C = 25°C	0.86 @ 78.5 A T_C = 70°C

* Values are for the 40-Volt units. The lower voltage parts provide lower limits.

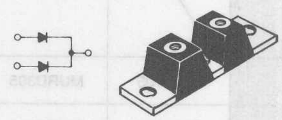
** I_O is total device output.

SCHOTTKY RECTIFIERS (continued)

2

VRRM (Volts)	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)					
	30			35	40	50
	11-03 (TO-204AA) Metal  Dual Diode** (40 Mil Pins)	221A-04 (TO-220AB) Plastic  Dual Diode**	340D-01 (TO-218AC) Plastic  Dual Diode **	56-03 (DO-203AA) Metal 	257-01 (DO-203AB) Metal 	
15						
20					1N5832	
25						
30					1N5833	1N6097
35	MBR3035CT	MBR2535CT	MBR3035PT	MBR3535		
40	MBR3040CT	MBR2540CT	MBR3040PT	MBR3540	1N5834	1N6098
45	SD241 MBR3045CT	MBR2545CT	MBR3045PT	SD41 MBR3545,H,H1***		
50						
60						
I_{FSM} (Amps)	400	300	400	600	800	800
†T_C @ Rated I_O (°C)	105	125	105	90	75	70
†T_L @ Rated I_O (°C)						
T_J (Max) (°C)	150	150	150	150	125	125
Max V_F @ $I_{FM} = I_O$	0.72 @ 30 A T_C = 125°C	0.73 @ 30 A T_C = 125°C	0.72 @ 30 A T_C = 125°C	0.55 T_C = 25°C	*0.59 T_C = 25°C	0.86 @ 157 A T_C = 70°C

* Values are for the 40-Volt units. The lower voltage parts provide lower limits.
** I_O is total device output.
*** H & H1 versions are Hi-Rel Processed Parts (Non JAN, JTX).
† Must be derated for reverse power dissipation. See Data Sheet.

I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)								
60		65	75	80	120	200		300
		257-01 DO-203AB Metal 					357C-01 Plastic POWER TAP Dual Diode**	
	MBR6015L						MBR20015CTL	
	MBR6020L						MBR20020CTL	
	MBR6025L						MBR20025CTL	
	MBR6030L						MBR20030CTL	
MBR6035		MBR6535	MBR7535	MBR8035	MBR12035CT	MBR20035CT		MBR30035CT
MBR6040		MBR6540	MBR7540					MBR30040CT
SD51 MBR6045,H,H1***		MBR6545	MBR7545	MBR8045	MBR12045CT	MBR20045CT		MBR30045CT
					MBR12050CT	MBR20050CT		MBR30050CT
					MBR12060CT	MBR20060CT		MBR30060CT
800	1000	800	1000	1000	1500	1500	1500	2500
90	120	120	90	120	140	140	140	140
150	150	175	150	175	175	175	175	175
*0.6 T_C = 125°C	0.38 @ T_C = 150°C	0.62 T_C = 150°C	0.60 T_C = 125°C	0.59 T_C = 150°C	0.68 T_C = 125°C	0.71 T_C = 125°C	0.48 @ T_C = 150°C	0.64 T_C = 125°C

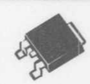
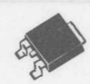
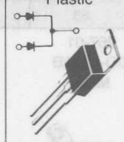
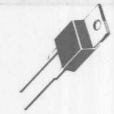
** I_O is total device output.

*** H & H1 versions are Hi-Rel Processed Parts (Non JAN, JTX).

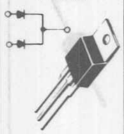
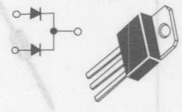
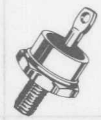
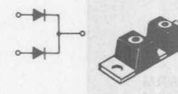
Ultrafast Recovery Rectifiers

EXPANDING the SWITCHMODE Rectifier family are these ultrafast devices with reverse recovery times of 25 to 100 nanoseconds. They complement the broad Schottky offering for use in the higher voltage outputs and internal circuitry of switching power supplies as operating frequencies increase from 20 kHz to 250 kHz. Additional package styles and operating current levels are planned.

All devices are connected cathode to case or cathode to heatsink, where applicable. Reverse polarity may be available on some devices upon special request. Contact your Motorola representative for more information.

	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)						
	1.0	3.0	4.0	6.0		8.0	15
	59-04 (DO-41) Plastic	369A-04 Plastic	267-02 Plastic	369A-04 Plastic	221A-04 (TO-220AB) Plastic	221B-01 (TO-220AC) Plastic	
V_{RRM} (Volts)				 Dual Diode**	 Dual Diode**		
50	MUR105	MURD305	MUR405	MURD605CT	MUR605CT	MUR805	MUR1505
100	MUR110	MURD310	MUR410	MURD610CT	MUR610CT	MUR810	MUR1510
150	MUR115	MURD315	MUR415	MURD615CT	MUR615CT	MUR815	MUR1515
200	MUR120	MURD320	MUR420	MURD620CT	MUR620CT	MUR820	MUR1520
300	MUR130		MUR430			MUR830	MUR1530
400	MUR140		MUR440			MUR840	MUR1540
500	MUR150		MUR450			MUR850	MUR1550
600	MUR160		MUR460			MUR860	MUR1560
700	MUR170		MUR470			MUR870	
800	MUR180		MUR480			MUR880	
900	MUR190		MUR490			MUR890	
1000	MUR1100		MUR4100			MUR8100	
I_{FSM} (Amps)	35	75	125	63	75	100	200
T_A @ Rated I_O (°C)	50		80				
T_C @ Rated I_O (°C)		158		145	130	150	150
T_J (Max) (°C)	175	175	175	175	175	175	175
t_{rr} ns	25/50/75	35	25/50/75	35	35	35/60/100	35/60

** I_O is total device output.

I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)							
16	25	30		50	70	100	200
221A-04 (TO-220AB) Plastic  Dual Diode**	56-03 (DO-203AA) 	340D-01 (TO-218AC) Plastic  Dual Diode **		257-01 (DO-203AB) Metal 		357C-01 Plastic POWER TAP  Dual Diode**	
MUR1605CT	MUR2505	R710XPT	MUR3005PT	MUR5005	MUR7005	MUR10005CT	MUR20005CT
MUR1610CT	MUR2510	R711XPT	MUR3010PT	MUR5010	MUR7010	MUR10010CT	MUR20010CT
MUR1615CT	MUR2515		MUR3015PT	MUR5015	MUR7015	MUR10015CT	MUR20015CT
MUR1620CT	MUR2520	R712XPT	MUR3020PT	MUR5020	MUR7020	MUR10020CT	MUR20020CT
MUR1630CT			MUR3030PT				MUR20030CT
MUR1640CT		R714XPT	MUR3040PT				MUR20040CT
MUR1650CT			MUR3050PT				
MUR1660CT			MUR3060PT				
100	500	150	400	600	1000	400	800
150	145	100	150	125	125	140	95
175	175	150	175	175	175	175	175
35	50	100	35	50	50	50	50

** I_O is total device output.

Fast Recovery Rectifiers

. . . available for designs requiring a power rectifier having maximum switching times ranging from 200 ns to 750 ns. These devices are offered in current ranges of 1.0 to 50 amperes and in voltages to 1000 volts.

All devices are connected cathode to case or cathode to heatsink, where applicable. Reverse polarity may be available on some devices upon special request. Contact your Motorola representative for more information.

	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)					
	1.0		3.0			5.0
V_{RRM} (Volts)	59-04 Plastic 		60-01 Metal 	267-02 Plastic 		194-04 Plastic 
50	†1N4933	MR810	MR830	MR850	MR910	MR820
100	†1N4934	MR811	MR831	MR851	MR911	MR821
200	†1N4935	MR812	MR832	MR852	MR912	MR822
400	†1N4936	MR814	MR834	MR854	MR914	MR824
600	†1N4937	MR816	MR836	MR856	MR916	MR826
800		MR817			MR917	
1000		MR818			MR918	
I_{FSM} (Amps)	30	30	100	100	100	300
T_A @ Rated I_O (°C)	75	75		*90	*90	*55
T_C @ Rated I_O (°C)		100	100			
T_J (Max) (°C)	150	150	150	175	175	175
t_{rr} (μs)	0.2	0.75	0.2	0.2	0.75	0.2

* Must be derated for reverse power dissipation. See Data Sheet.

† Package Size: 0.120" Max Diameter by 0.260" Max Length.

V_{RRM} (Volts)	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)						
	6.0	12	20	24	30	40	50
	245A-02 (DO-203AA) Metal 		42A-01 (DO-203AB) Metal 	339-02 Plastic Note 1 	42A-01 (DO-203AB) Metal 	257-01 (DO-203AB) Metal 	
50	1N3879	1N3889	1N3899	MR2400F	1N3909	MR860	MR870
100	1N3880	1N3890	1N3900	MR2401F	1N3910	MR861	MR871
200	1N3881	1N3891	1N3901	MR2402F	1N3911	MR862	MR872
400	1N3883	1N3893	1N3903	MR2404F	1N3913	MR864	MR874
600	MR1366	MR1376	MR1386	MR2406F	MR1396	MR866	MR876
800							
1000							
I_{FSM} (Amps)	150	200	250	300	300	350	400
T_A @ Rated I_O (°C)							
T_C @ Rated I_O (°C)	100	100	100	125	100	100	100
T_J (max) (°C)	150	150	150	175	150	160	160
t_{rr} μs	0.2	0.2	0.2	0.2	0.2	0.2	0.2

☐ TX versions available.

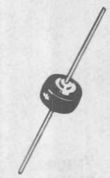
Note 1. Meets mounting configuration of TO-220 outline.

2

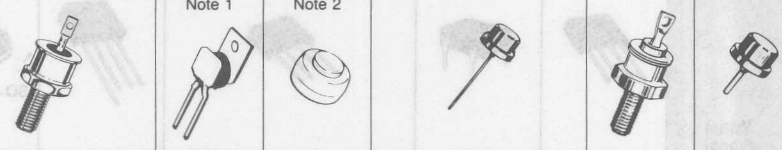
General-Purpose Rectifiers

Motorola offers a wide variety of low-cost devices, packaged to meet diverse mounting requirements. Avalanche capability is available in the axial lead 1.5, 3 and 6 amp packages shown below to provide protection from transients.

All devices are connected cathode to case or cathode to heatsink, where applicable. Reverse polarity may be available on some devices upon special request. Contact your Motorola representative for more information.

V_{RRM} (Volts)	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)					
	1.0	1.5	3.0			6.0
	59-03 (DO-41) Plastic 	59-04 Plastic 	60-01 Metal 	267-02 Plastic 		194-04 Plastic 
50	†1N4001	**1N5391	1N4719	**MR500	1N5400	MR750
100	†1N4002	**1N5392	1N4720	**MR501	1N5401	MR751
200	†1N4003	1N5393 *MR5059	1N4721	**MR502	1N5402	MR752
400	†1N4004	1N5395 *MR5060	1N4722	**MR504	1N5404	MR754
600	†1N4005	1N5397 *MR5061	1N4723	**MR506	1N5406	MR756
800	†1N4006	1N5398	1N4724	MR508		MR758
1000	†1N4007	1N5399	1N4725	MR510		MR760
I_{FSM} (Amps)	30	50	300	100	200	400
T_A @ Rated I_O (°C)	75	T_L = 70	75	95	T_L = 105	60
T_C @ Rated I_O (°C)						
T_J (Max) (°C)	175	175	175	175	175	175

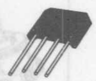
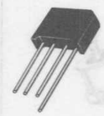
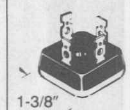
† Package Size: 0.120" Max Diameter by 0.260" Max Length.
* 1N5059 series equivalent Avalanche Rectifiers.
** Avalanche versions available, consult factory.

V_{RRM} (Volts)	I_O, AVERAGE RECTIFIED FORWARD CURRENT (Amperes)							
	12	20	24	25	30		40	50
	245A-02 (DO-203AA) Metal		339-02 Plastic Note 1	193-03 Plastic Note 2	43-02 (DO-21) Metal		42A-01 (DO-203AB) Metal	43-04 Metal
								
50	MR1120 1N1199,A,B	MR2000	MR2400	MR2500	1N3491	1N3659	1N1183A	MR5005
100	MR1121 1N1200,A,B	MR2001	MR2401	MR2501	1N3492	1N3660	1N1184A	MR5010
200	MR1122 1N1202,A,B	MR2002	MR2402	MR2502	1N3493	1N3661	1N1186A	MR5020
400	MR1124 1N1204,A,B	MR2004	MR2404	MR2504	1N3495	1N3663	1N1188A	MR5040
600	MR1126 1N1206,A,B	MR2006	MR2406	MR2506	MR328	Note 3	1N1190A	Note 3
800	MR1128 1N3988	MR2008		MR2508	MR330	Note 3	Note 3	Note 3
1000	MR1130 1N3990	MR2010		MR2510	MR331	Note 3	Note 3	Note 3
I_{FSM} (Amps)	300	400	400	400	300	400	800	600
T_A @ Rated I_O (°C)								
T_C @ Rated I_O (°C)	150	150	125	150	130	100	150	150
T_J (Max) (°C)	190	175	175	175	175	175	190	195

Note 1. Meets mounting configuration of TO-220 outline.
Note 2. Request Data Sheet for Mounting Information.
Note 3. Available on special order.

Rectifier Bridges

Motorola SUPERBRIDGES offer cost effectiveness and reliability in single phase applications. Assemblies combine pretested "button" rectifier cells for low assembly cost and high yields. Performance of four individual diodes is achieved with reliability of the whole assembly comparable to that of a single unit. Assemblies feature versatile slip-on/solder/wire wrap terminals.

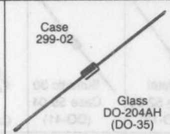
	I_O, DC OUTPUT CURRENT (Amperes)						
	1.0		2.0		4.0	25	35
V_{RRM} (Volts)	377A-01 	379-01 	377A-01 		377-01 	309A-03 	309A-02 
50	MDA100G	DF005M	MDA200G	2KBP005	MDA970G1	MDA2500	MDA3500
100	MDA101G	DF01M	MDA201G	2KBP01	MDA970G2	MDA2501	MDA3501
200	MDA102G	DF02M	MDA202G	2KBP02	MDA970G3	MDA2502	MDA3502
400	MDA104G	DF04M	MDA204G	2KBP04	MDA970G5	MDA2504	MDA3504
600	MDA106G	DF06M	MDA206G	2KBP06	MDA970G6	MDA2506	MDA3506
800							MDA3508
1000							MDA3510
I_{FSM} (Amps)						400	400
T_A @ Rated I_O (°C)							
T_C @ Rated I_O (°C)						55	55
T_J (Max) (°C)						175	175

UL RECOGNIZED E61980

Dimensions given are nominal

Zener and Avalanche Regulator Diodes

General-Purpose Regulator Diodes

Nominal Zener Voltage	250 mW Low Level Cathode = Polarity Mark	250 mW Low Noise Cathode = Polarity Mark	250 mW Low Level Cathode = Polarity Mark	250 mW Low Noise Cathode = Polarity Mark	350 mW Cathode = Polarity Mark		400 mW Low Noise Low Leakage Cathode = Polarity Mark	500 mW Cathode = Polarity Mark		
(*Note 1)	(*Notes 2,11)		(*Note 2)	(*Note 2)	(*Notes 5,13)		(*Note 3)	(*Note 4)	(*Note 8)	(*Note 9)
	 Glass Case 362-01		Case 299-02  Glass DO-204AH (DO-35)		 Case 318-02,-03 Style 8 SOT-23 (TO-236AA/AB)			Case 299-02  Glass DO-204AH (DO-35)		
1.8	MLL4678	MLL4614	1N4678	1N4614						
2.0	MLL4679	MLL4615	1N4679	1N4615						
2.2	MLL4680	MLL4616	1N4680	1N4616						
2.4	MLL4681	MLL4617	1N4681	1N4617				1N4370	1N5221A	1N5985A
2.5										
2.7	MLL4682	MLL4618	1N4682	1N4618				1N4371	1N5223A	
2.8										1N5986A
3.0	MLL4683	MLL4619	1N4683	1N4619				1N4372	1N5225A	1N5987A
3.3	MLL4684	MLL4620	1N4684	1N4620	MMBZ5226		1N5518A	1N746	1N5226A	1N5988A
3.6	MLL4685	MLL4621	1N4685	1N4621	MMBZ5227		1N5519A	1N747	1N5227A	1N5989A
3.9	MLL4686	MLL4622	1N4686	1N4622	MMBZ5228		1N5520A	1N748	1N5228A	1N5990A
4.3	MLL4687	MLL4623	1N4687	1N4623	MMBZ5229		1N5221A	1N749	1N5229A	1N5991A
4.7	MLL4688	MLL4624	1N4688	1N4624	MMBZ5230	BZX84C4V7	1N5522A	1N750	1N5230A	1N5992A
5.1	MLL4689	MLL4625	1N4689	1N4625	MMBZ5231	BZX84C5V1	1N5523A	1N751	1N5231A	1N5993A
5.6	MLL4690	MLL4626	1N4690	1N4626	MMBZ5232	BZX84C5V6	1N5524A	1N752	1N5232A	1N5994A
6.0					MMBZ5233					
6.2	MLL4691	MLL4627	1N4691	1N4627	MMBZ5234	BZX84C6V2	1N5525A	1N753	1N5234A	1N5995A
6.8	MLL4692	MLL4099	1N4692	1N4099	MMBZ5235	BZX84C6V8	1N5526A	1N754 1N957A	1N5235A	1N5996A
7.5	MLL4693	MLL4100	1N4693	1N4100	MMBZ5236	BZX84C7V5	1N5527A	1N755 1N958A	1N5236A	1N5997A
8.2	MLL4694	MLL4101	1N4694	1N4101	MMBZ5237	BZX84C8V2	1N5228A	1N756 1N959A	1N5237A	1N5998A
8.7	MLL4695	MLL4102	1N4695	1N4102	MMBZ5238				1N5238A	
9.1	MLL4696	MLL4103	1N4696	1N4103	MMBZ5239	BZX84C9V1	1N5529A	1N757 1N960A	1N5239A	1N5999A
10	MLL4697	MLL4104	1N4697	1N4104	MMBZ5240	BZX84C10	1N5530A	1N758 1N961A	1N5240A	1N6000A
11	MLL4698	MLL4105	1N4698	1N4105	MMBZ5241	BZX84C11	1N5531A	1N962A	1N5241A	1N6001A
12	MLL4699	MLL4106	1N4699	1N4106	MMBZ5242	BZX84C12	1N5532A	1N759 1N963A	1N5242A	1N6002A
13	MLL4700	MLL4107	1N4700	1N4107	MMBZ5243	BZX84C13	1N5533A	1N964A	1N5243A	1N6003A
14	MLL4701	MLL4108	1N4701	1N4108	MMBZ5244		1N5334A		1N5244A	
15	MLL4702	MLL4109	1N4702	1N4109	MMBZ5245	BZX84C15	1N5335A	1N965A	1N5245A	1N6004A
16	MLL4703	MLL4110	1N4703	1N4110	MMBZ5246	BZX84C16	1N5336A	1N966A	1N5246A	1N6005A
17	MLL4704	MLL4111	1N4704	1N4111	MMBZ5247		1N5337A		1N5247A	
18	MLL4705	MLL4112	1N4705	1N4112	MMBZ5248	BZX84C18	1N5338A	1N967A	1N5248A	1N6006A
19	MLL4706	MLL4113	1N4706	1N4113	MMBZ5249		1N5539A		1N5249A	
20	MLL4707	MLL4114	1N4707	1N4114	MMBZ5250	BZX84C20	1N5540A	1N968A	1N5250A	1N6007A
22	MLL4708	MLL4115	1N4708	1N4115	MMBZ5251	BZX84C22	1N5541A	1N969A	1N5251A	1N6008A
24	MLL4709	MLL4116	1N4709	1N4116	MMBZ5252	BZX84C24	1N5542A	1N970A	1N5252A	1N6009A
25	MLL4710	MLL4117	1N4710	1N4117	MMBZ5253		1N5543A		1N5253A	
27	MLL4711	MLL4118	1N4711	1N4118	MMBZ5254	BZX84C27		1N971A	1N5254A	1N6010A
28	MLL4712	MLL4119	1N4712	1N4119	MMBZ5255		1N5544A		1N5255A	
30	MLL4713	MLL4120	1N4713	1N4120	MMBZ5256	BZX84C30	1N5545A	1N972A	1N5256A	1N6011A
33	MLL4714	MLL4121	1N4714	1N4121	MMBZ5257	BZX84C33	1N5546A	1N973A	1N5257A	1N6012A
36	MLL4715	MLL4122	1N4715	1N4122				1N974A	1N5258A	1N6013A
39	MLL4716	MLL4123	1N4716	1N4123				1N975A	1N5259A	1N6014A
43	MLL4717	MLL4124	1N4717	1N4124				1N976A	1N5260A	1N6015A
47		MLL4125		1N4125				1N977A	1N5261A	1N6016A
51		MLL4126		1N4126				1N978A	1N5262A	1N6017A
56		MLL4127		1N4127				1N979A	1N5263A	1N6018A
60		MLL4128		1N4128					1N5264A	
62		MLL4129		1N4129				1N980A	1N5265A	1N6019A
68		MLL4130		1N4130				1N981A	1N5266A	1N6020A
75		MLL4131		1N4131				1N982A	1N5267A	1N6021A
82		MLL4132		1N4132				1N983A	1N5268A	1N6022A
87		MLL4133		1N4133					1N5269A	
91		MLL4134		1N4134				1N984A	1N5270A	1N6023A
100		MLL4135		1N4135				1N985A	1N5271A	1N6024A
110								1N986A	1N5272A	1N6025A
120								†1N987A	†1N5273A	
130								†1N988A	†1N5274A	
140									†1N5275A	
150								†1N989A	†1N5276A	
160								†1N990A	†1N5277A	
170									†1N5278A	
180								†1N991A	†1N5279A	
200								†1N992A	†1N5281A	

□ JAN JANTX(V) available, ±5% only.

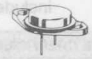
† 1N987A–1N992A & 1N5273A–1N5281A supplied in DO-7 glass package. *See Notes.

2

Nominal Zener Voltage	500 mW Cathode = Polarity Mark		1 Watt Cathode = Polarity Mark		1 Watt Cathode to Case	1.5 Watt Cathode = Polarity Mark	1.5 Watt Cathode to Case	5 Watt Cathode = Polarity Mark
(*Note 1)	(*Notes 4,11)	(*Notes 9,11)	(*Note 6)	(*Notes 6,12)	(*Note 7)	(*Note 8)	(*Note 9)	(*Note 8)
	 Glass Case 362-01		 Glass Case 59-04 (DO-41)	 Glass Case 362B-01	 Metal Case 52-03 (DO-13)	 Sumetic 30 Case 59-04 (DO-41)	 Metal Case 55-01	 Sumetic 40 Case 17-02
1.8								
2.0								
2.2								
2.4	MLL4370	MLL5221A						
2.5		MLL5222A						
2.7	MLL4371	MLL5223A						
2.8		MLL5224A						
3.0	MLL4372	MLL4225A						
3.3	MLL746	MLL5226A	1N4728	MLL4728	1N3821	1N5913A		1N5333A
3.6	MLL747	MLL5227A	1N4729	MLL4729	1N3822	1N5914A		1N5334A
3.9	MLL748	MLL5228A	1N4730	MLL4730	1N3823	1N5915A		1N5335A
4.3	MLL749	MLL5229A	1N4731	MLL4731	1N3824	1N5916A		1N5336A
4.7	MLL750	MLL5230A	1N4732	MLL4732	1N3825	1N5917A		1N5337A
5.1	MLL751	MLL5231A	1N4733	MLL4733	1N3826	1N5918A		1N5338A
5.6	MLL752	MLL5232A	1N4734	MLL4734	1N3827	1N5919A		1N5339A
6.0		MLL5233A						
6.2	MLL753	MLL5234A	1N4735	MLL4735	1N3828	1N5920A		1N5341A
6.8	MLL754 MLL957A	MLL5235A	1N4736	MLL4736	1N3829 1N3016A	1N5921A	1N3785A	1N5342A
7.5	MLL755 MLL958A	MLL5236A	1N4737	MLL4737	1N3830 1N3017A	1N5922A	1N3786A	1N5343A
8.2	MLL756 MLL959A	MLL5237A	1N4738	MLL4738	1N3018A	1N5923A	1N3787A	1N5344A
8.7		MLL5238A						1N5345A
9.1	MLL757 MLL960A	MLL5239A	1N4739	MLL4739	1N3019A	1N5924A	1N3788A	1N5346A
10	MLL758 MLL961A	MLL5240A	1N4740	MLL4740	1N3020A	1N5925A	1N3789A	1N5347A
11	MLL962A	MLL5241A	1N4741	MLL4741	1N3021A	1N5926A	1N3790A	1N5348A
12	MLL759 MLL963A	MLL5242A	1N4742	MLL4742	1N3022A	1N5927A	1N3791A	1N5349A
13	MLL964A	MLL5243A	1N4743	MLL4743	1N3023A	1N5928A	1N3792A	1N5350A
14		MLL5244A						1N5351A
15	MLL965A	MLL5245A	1N4744	MLL4744	1N3024A	1N5929A	1N3793A	1N5352A
16	MLL966A	MLL5246A	1N4745	MLL4745	1N3025A	1N5930A	1N3794A	1N5353A
17		MLL5247A						1N5354A
18	MLL967A	MLL5248A	1N4746	MLL4746	1N3026A	1N5931A	1N3795A	1N5355A
19		MLL5249A						1N5356A
20	MLL968A	MLL5250A	1N4747	MLL4747	1N3027A	1N5932A	1N3796A	1N5357A
22	MLL969A	MLL5251A	1N4748	MLL4748	1N3028A	1N5933A	1N3797A	1N5358A
24	MLL970A	MLL5252A	1N4749	MLL4749	1N3029A	1N5934A	1N3798A	1N5359A
25		MLL5253A						1N5360A
27	MLL971A	MLL5254A	1N4750	MLL4750	1N3030A	1N5935A	1N3799A	1N5361A
28		MLL5255A						1N5362A
30	MLL972A	MLL5256A	1N4751	MLL4751	1N3031A	1N5936A	1N3800A	1N5363A
33	MLL973A	MLL5257A	1N4752	MLL4752	1N3032A	1N5937A	1N3801A	1N5364A
36	MLL974A	MLL5258A	1N4753	MLL4753	1N3033A	1N5938A	1N3802A	1N5365A
39	MLL975A	MLL5259A	1N4754	MLL4754	1N3034A	1N5939A	1N3803A	1N5366A
43	MLL976A	MLL5260A	1N4755	MLL4755	1N3035A	1N5940A	1N3804A	1N5367A
47	MLL977A	MLL5261A	1N4756	MLL4756	1N3036A	1N5941A	1N3805A	1N5368A
51	MLL978A	MLL5262A	1N4757	MLL4751	1N3037A	1N5942A	1N3806A	1N5369A
56	MLL979A	MLL5263A	1N4758	MLL4758	1N3038A	1N5943A	1N3807A	1N5370A
60		MLL5264A						1N5371A
62	MLL980A	MLL5265A	1N4759	MLL4759	1N3039A	1N5944A	1N3808A	1N5372A
68	MLL981A	MLL5266A	1N4760	MLL4760	1N3040A	1N5945A	1N3809A	1N5373A
75	MLL982A	MLL5267A	1N4761	MLL4761	1N3041A	1N5946A	1N3810A	1N5374A
82	MLL983A	MLL5268A	1N4762	MLL4762	1N3042A	1N5947A	1N3811A	1N5375A
87		MLL5269A						1N5376A
91	MLL984A	MLL5270A	1N4763	MLL4763	1N3043A	1N5958A	1N3812A	1N5377A
100	MLL985A		1N4764	MLL4764	1N3044A	1N5949A	1N3813A	1N5378A
110	MLL986A		◆1M110ZS10		1N3045A	1N5950A	1N3814A	1N5379A
120			◆1M120ZS10		1N3046A	1N5951A	1N3815A	1N5380A
130			◆1M130ZS10		1N3047A	1N5952A	1N3816A	1N5831A
150			◆1M150ZS10		1N3048A	1N5953A	1N3817A	1N5383A
160			◆1M160ZS10		1N3049A	1N5954A	1N3818A	1N5384A
170			◆1M170ZS10					1N5385A
175								
180			◆1M180ZS10		1N3050A	1N5955A	1N3819A	1N5386A
200			◆1M200ZS10		1N3051A	1N5956A	1N3820A	1N5388A

◆ 1M110ZS10 Series supplied in Surmetic (Plastic) DO-41 package.

General-Purpose Regulator Diodes (continued)

Nominal Zener Voltage	10 Watt Cathode to Case = 1N3993 & MZT2970 Series Anode to Case = 1N2970 Series		50 Watt Cathode to Case = MZT4549 Series Anode to Case = 1N4557A Series		
(*Note 1)	(*Notes 9,10)	(*Note 9)	(*Note 9)	(*Notes 9,10)	(*Notes 9,10)
	 Metal Case 56-03 DO-203AA	 221B-01 (TO-220AC) Plastic		 Metal Case 54-05 (TO-3)	 Metal Case 58-01 (DO-5 Type)
1.8					
2.0					
2.2					
2.4					
2.5					
2.7					
2.8					
3.0					
3.3					
3.6					
3.9	1N3993&R		MZT4549A	1N4557A&RA	1N4549A&RA
4.3	1N3994&R		MZT4550A	1N4558A&RA	1N4550A&RA
4.7	1N3995&R		MZT4551A	1N4559A&RA	1N4551A&RA
5.1	1N3996&R		MZT4552A	1N4560A&RA	1N4552A&RA
5.6	1N3997&R		MZT4553A	1N4561A&RA	1N4553A&RA
6.0					
6.2	1N3998&R		MZT4554A	1N4562A&RA	1N4554A&RA
6.8	1N3999&R 1N2970A&RA	MZT2970A	MZT3305A	1N4563A&RA 1N2804A&RA	1N4555A&RA 1N3305A&RA
7.5	1N4000&R 1N2971A&RA	MZT2971A	MZT3306A	1N4564A&RA 1N2805A&RA	1N4556A&RA 1N3306A&RA
8.2	1N2972A&RA	MZT2972A	MZT3307A	1N2806A&RA	1N3307A&RA
8.7					
9.1	1N2973A&RA	MZT2973A	MZT3308A	1N2807A&RA	1N3308A&RA
10	1N2974A&RA	MZT2974A	MZT3309A	1N2808A&RA	1N3309A&RA
11	1N2975A&RA	MZT2975A	MZT3310A	1N2809A&RA	1N3310A&RA
12	1N2976A&RA	MZT2976A	MZT3311A	1N2810A&RA	1N3311A&RA
13	1N2977A&RA	MZT2977A	MZT3312A	1N2811A&RA	1N3312A&RA
14	1N2878A&RA	MZT2978A	MZT3313A	1N2812A&RA	1N3313A&RA
15	1N2979A&RA	MZT2979A	MZT3314A	1N2813A&RA	1N3314A&RA
16	1N2980A&RA	MZT2980A	MZT3315A	1N2814A&RA	1N3315A&RA
17			MZT3316A	1N2815A&RA	1N3316A&RA
18	1N2982A&RA	MZT2981A	MZT3317A	1N2816A&RA	1N3317A&RA
19	1N2983A&RA	MZT2982A	MZT3318A	1N2817A&RA	1N3318A&RA
20	1N2984A&RA	MZT2983A	MZT3319A	1N2818A&RA	1N3319A&RA
22	1N2985A&RA	MZT2984A	MZT3320A	1N2819A&RA	1N3320A&RA
24	1N2986A&RA	MZT2986A	MZT3321A	1N2820A&RA	1N3321A&RA
25			MZT3322A	1N2821A&RA	1N3322A&RA
27	1N2988A&RA	MZT2987A	MZT3323A	1N2822A&RA	1N3323A&RA
28					
30	1N2989A&RA	MZT2988A	MZT3324A	1N2823A&RA	1N3324A&RA
33	1N2990A&RA	MZT2989A	MZT3325A	1N2824A&RA	1N3325A&RA
36	1N2991A&RA	MZT2990A	MZT3326A	1N2825A&RA	1N3326A&RA
39	1N2992A&RA	MZT2992A	MZT3327A	1N2826A&RA	1N3327A&RA
43	1N2993A&RA	MZT2993A	MZT3328A	1N2827A&RA	1N3328A&RA
47	1N2996A&RA	MZT2995A	MZT3330A	1N2829A&RA	1N33330A&RA
50		MZT2996A	MZT3331A		
51	1N2997A&RA	MZT2997A	MZT3332A	1N2831A&RA	1N3332A&RA
52		MZT2998A	MZT3333A		1N3334A&RA
56	1N2999A&RA	MZT2999A	MZT3334A	1N2832A&RA	
60					1N3335A&RA
62	1N3000A&RA	MZT3000A	MZT3335A	1N2833A&RA	1N3336A&RA
68	1N3001A&RA	MZT3001A	MZT3336A	1N2834A&RA	
75	1N3002A&RA	MZT3002A	MZT3337A	1N2835A&RA	1N3337A&RA
82	1N3003A&RA	MZT3003A	MZT3338A	1N2836A&RA	1N3338A&RA
87					
91	1N3004A&RA	MZT3004A	MZT3339A	1N2837A&RA	1N3339A&RA
100	1N3005A&RA	MZT3005A	MZT3340A	1N2838A&RA	1N3340A&RA
105		MZT3006A	MZT3341A		
110	1N3007A&RA	MZT3007A	MZT3342A	1N2840A&RA	1N3342A&RA
120	1N3008A&RA	MZT3008A	MZT3343A	1N2841A&RA	1N3343A&RA
130	1N3009A&RA	MZT3009A	MZT3344A	1N2842A&RA	1N3344A&RA
140					1N3345A&RA
150	1N3011A&RA	MZT3010A	MZT3345A	1N2843A&RA	1N3346A&RA
160	1N3012A&RA	MZT3011A	MZT3347A	1N2844A&RA	1N3347A&RA
170					
175		MZT3012A	MZT3348A		
180	1N3014A&RA	MZT3014A	MZT3349A	1N2845A&RA	1N3349A&RA
200	1N3015A&RA	MZT3015A	MZT3350A	1N2846A&RA	1N3350A&RA

☐ JAN JANTX (V) available, ±5% only. * See Notes

NOTES

1. The Zener Voltage is measured at approximately 1/4 the rated power, with the following exceptions: the 1N4678–4717 is measured with I_{ZT} = 50 μAdc; the 1N4614/1N4099 is measured with I_{ZT} = 250 μAdc; the 1N4370/1N746 and the 1N5221–5242 are measured with I_{ZT} = 20 mAdc; the 1N5985A–6012A is measured with I_{ZT} = 5.0 mA; 1N6013A–6023A is measured with I_{ZT} = 2.0 mA; 1N6024–6025 is measured with I_{ZT} = 1.0 mA.

Tolerances

2. No suffix = ±5%
   C suffix = 2%
   D suffix = 1%
3. A Suffix = ±10% with guaranteed limits on V_Z, V_F, and I_R only
   B suffix = ±5%
   C suffix = ±2%
   D suffix = ±1%
4. MLL4370/1N4370/1N746 series:
   No suffix = ±10%
   A suffix = ±5%
   C suffix = 2%
   D suffix = 1%
   MLL957/1N957 series:
   A suffix = ±10%
   B suffix = ±5%
   C suffix = 2%
   D suffix = 1%

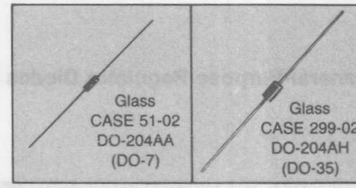
Military parts in 1N4370/746/962/4099/4614/5518 series supplied in DO-7. Military parts in 1N4370/746/962/4099/4614/5518 are also available in the cost effective DO-204AH (DO-35) package as the -1 version. This version can be ordered by inserting a 1 between the part number and the JAN, JTX or JTXV suffix, i.e. 1N746A1JAN. MIL-STD 19500/117 and 127 state the -1 version is a direct substitute for the non -1 version. The -1 versions appear on MIL-STD 701 as the preferred parts for new designs.

5. No suffix = ±10% with guaranteed limits on V_Z, V_F and I_R only.
   A suffix = ±10%
   B suffix = ±5%
6. No suffix = ±10%
   A suffix = ±5%
   C suffix = 2%
   D suffix = 1%
7. 1N3821 series: No suffix = ±10%
   A suffix = ±5%
   1N3016 series: A suffix = ±10%
   B suffix = ±5%
8. A suffix = ±10% C suffix = ±2%
   B suffix = ±5% D suffix = ±1%
9. A suffix = ±10%
   B suffix = ±5%

   Exception:
   1N3993–1N4000: No suffix = ±10%
   A suffix = ±5%
10. RA and RB = Reverse Polarity Types Available
11. Available in 8 mm Tape and Reel
    T1 Cathode Facing Sprocket Holes
    T2 Anode Facing Sprocket Holes
12. Available in 12 mm Tape and Reel
    T1 Cathode Facing Sprocket Holes
    T2 Anode Facing Sprocket Holes
13. Available in 8 mm tape and reel, both T1 and T2 options.

Voltage Reference Diodes

Temperature Compensated Reference Devices



For applications where output voltage must remain within narrow limits during changes in input voltage, load resistance and temperature. Motorola guarantees all References Devices to fall within the specified maximum voltage variations, ΔV_Z, at the specifically indicated test temperatures and test current (JEDEC Standard #5). Temperature Coefficient is also specified but should be considered as a reference only — not a maximum rating.

Devices in this table are hermetically sealed structures. Includes JAN, JANTX and JTXV Devices.

V_Z Volts	Test Current mAdc	Test* Temp Points	AVERAGE TEMPERATURE COEFFICIENT OVER THE OPERATING RANGE										Case
			0.01 %/°C		0.005 %/°C		0.002 %/°C		0.001 %/°C		0.0005 %/°C		
			Device Type	ΔV_Z Max Volts	Device Type	ΔV_Z Max Volts	Device Type	ΔV_Z Max Volts	Device Type	ΔV_Z Max Volts	Device Type	ΔV_Z Max Volts	
6.2 △1	7.5	A	1N821	0.096	1N823	0.048	1N825	0.019	1N827	0.009	1N829	0.005	299-02
6.2 △1	7.5	A	1N821A	0.096	1N823A	0.048	1N825A	0.019	1N827A	0.009	1N829A	0.005	
6.4	0.5	B	1N4565	0.018	1N4566	0.024	1N4567	0.010	1N4568	0.005	1N4569	0.002	DO-204AH (DO-35)
	0.5	A	1N4565A	0.099	1N4566A	0.050	1N4567A	0.020	1N4568A	0.010	1N4569A	0.005	
	1.0	B	1N4570	0.048	1N4571	0.024	1N4572	0.010	1N4573	0.005	1N4574	0.002	
	1.0	A	1N4570A	0.099	1N4571A	0.050	1N4572A	0.020	1N4573A	0.010	1N4574A	0.005	
	2.0	B	1N4575	0.048	1N4576	0.024	1N4577	0.010	1N4578	0.005	1N4579	0.002	
	2.0	A	1N4575A	0.099	1N4576A	0.025	1N4577A	0.020	1N4578A	0.010	1N4579A	0.005	
	4.0	B	1N4580	0.048	1N4581	0.024	1N4582	0.010	1N4583	0.005	1N4584	0.002	
	4.0	A	1N4580A	0.099	1N4581A	0.050	1N4582A	0.020	1N4583A	0.010	1N4584A	0.005	
8.4	10	A	1N3154	0.130	1N3155	0.065	1N3156	0.026	1N3157	0.013			51-02
	10	C	1N3154A	0.072	1N3155A	0.085	1N3156A	0.034	1N3157A	0.017			
8.5	0.5	B	1N4775	0.064	1N4776	0.032	1N4777	0.013	1N4778	0.006	1N4779	0.003	DO-204AA (DO-7)
	0.5	A	1N4775A	0.132	1N4776A	0.066	1N4777A	0.026	1N4778A	0.013	1N4779A	0.007	
	1.0	B	1N4780	0.064	1N4781	0.032	1N4782	0.013	1N4783	0.006	1N4784	0.003	
	1.0	A	1N4780A	0.132	1N4781A	0.066	1N4782A	0.026	1N4783A	0.013	1N4784A	0.007	
9.0	7.5	B	1N935	0.067	1N936	0.033	1N937	0.013	1N938	0.006	1N939	0.003	
	7.5	A	1N935A	0.139	1N936A	0.069	1N937A	0.027	1N938A	0.013	1N939A	0.007	
	7.5	C	1N935B	0.184	1N936B	0.092	1N937B	0.037	1N938B	0.018	1N939B	0.009	
9.1	0.5	B	1N4765	0.068	1N4766	0.034	1N4767	0.014	1N4768	0.007	1N4769	0.003	
	0.5	A	1N4765A	0.141	1N4766A	0.070	1N4767A	0.028	1N4768A	0.014	1N4769A	0.007	
	1.0	B	1N4770	0.068	1N4771	0.034	1N4772	0.014	1N4773	0.007	1N4774	0.003	
	1.0	A	1N4770A	0.141	1N4771A	0.070	1N4772A	0.028	1N4773A	0.014	1N4774A	0.007	
11.7	7.5	B	1N941	0.088	1N942	0.044	1N943	0.018	1N944	0.009	1N945	0.004	51-02 DO-204AA (DO-7)
	7.5	A	1N941A	0.081	1N942A	0.090	1N943A	0.036	1N944A	0.018	1N945A	0.009	
	7.5	C	1N941B	0.239	1N942B	0.120	1N943B	0.047	1N944B	0.024	1N945B	0.012	

△1 Non-suffix — Z_{ZT} = 15, "A" Suffix — Z_{ZT} = 10

☐ -1 and non-1 JAN/JANTX(V) available, ±5% only, Military parts in the 1N821, -1 and 1N4565, -1 series and supplied in the DO-7 package.

***Test Temperature Points °C: A** = −55, 0, +25, +75, +100 **B** = 0, +25, +75 **C** = −55, 0, +25, +75, +100, +150

Precision Reference Diodes (CASE 51-02, DO-204AA)

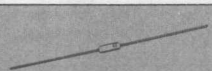
Designed, manufactured and tested for ultra-high stability of voltage with time and temperature change. Use of special measurement equipment and voltage standards provide calibration directly traceable to the National Bureau of Standards.

Reference Voltage Volts	Test Current mA	Temperature Stability		CERTIFIED VOLTAGE TIME STABILITY OVER 1000 HOURS OF OPERATION (Parts/Million Change)							
				<5 PPM/1000 HR		<10 PPM/1000 HR		<20 PPM/1000 HR		<40 PPM/1000 HR	
		ΔV_Z (mV)	OP Temp Range °C	Device Type	Change µV Max	Device Type	Change µV Max	Device Type	Change µV Max	Device Type	Change µV Max
6.2±5%	7.5	2.5	25,75,100	MZ605	30	MZ610	60	MZ620	120	MZ640	240

Special Purpose Regulators

Field-Effect Current Regulator Diodes

High impedance diodes whose "constant current source" characteristic complements the "constant voltage" of the zener line. Currents are available from 0.22 to 4.7 mA, with usable voltage range from a minimum limit of 1.0 to 2.5 V, up to a voltage compliance of 100 V, for the 1N5283 series, or 70 V, for the MCL1300 series.



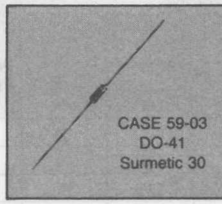
Glass
Case 51-02
DO-204AA
(DO-7)

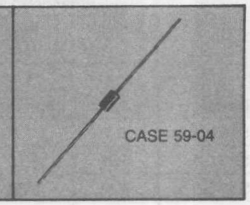
Reg. Current I_P @V_T = 25 V mA Nom	Device Type	Knee Imp Z_K @V_K = 6.0 V MΩ Min	Limiting Voltage @I_L = 0.8 I_P Volts Max
0.22	1N5283	2.75	1.00
0.24	1N5284	2.35	1.00
0.27	1N5285	1.95	1.00
0.30	1N5286	1.60	1.00
0.33	1N5287	1.35	1.00
0.39	1N5288	1.00	1.05
0.43	1N5289	0.870	1.05
0.47	1N5290	0.750	1.05
0.56	1N5291	0.560	1.10
0.62	1N5292	0.470	1.13
0.68	1N5293	0.400	1.15
0.75	1N5294	0.335	1.20
0.82	1N5295	0.290	1.25
0.91	1N5296	0.240	1.29
1.00	1N5297	0.205	1.35
1.10	1N5298	0.180	1.40
1.20	1N5299	0.155	1.45
1.30	1N5300	0.135	1.50
1.40	1N5301	0.115	1.55
1.50	1N5302	0.105	1.60
1.60	1N5303	0.092	1.65
1.80	1N5304	0.074	1.75
2.00	1N5305	0.061	1.85
2.20	1N5306	0.052	1.95
2.40	1N5307	0.044	2.00
2.70	1N5308	0.035	2.15
3.00	1N5309	0.029	2.25
3.30	1N5310	0.024	3.35
3.60	1N5311	0.020	2.50
3.90	1N5312	0.017	2.60
4.30	1N5313	0.014	2.75
4.70	1N5314	0.012	2.90
0.5±.03	MCL1300	0.500	1.00
1.0±0.6	MCL1301	0.200	1.50
2.0±0.6	MCL1302	0.100	2.00
3.0±0.6	MCL1303	0.050	2.00
4.0±0.6	MCL1304	0.025	2.50

☐ JAN/JANTX (V) availability

Low-Voltage Regulators

High-conductance silicon diodes designed as stable forward-reference sources for transistor amplifier biasing and similar applications. Available in high reliability glass construction or economic plastic packaging.





ELECTRICAL CHARACTERISTICS

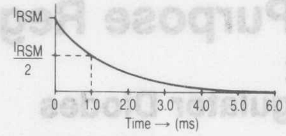
(T_A = 25°C unless otherwise noted).

Forward Reference Voltage Min	Forward Reference Voltage Max	I_F Test Current mA	Leakage Current I_R @ V_R µA	Leakage Current I_R @ V_R Volts	Device Type	Case
0.63	0.71	10	10	5.0	MZ2360	59-04 Surmetic
1.24	1.38	10	10	5.0	MZ2361	59-03 Surmetic

2

Transient Suppressors

General-Purpose



Surge Current Characteristics


CASE 59-04

Transient suppressors are designed for applications requiring protection of voltage sensitive electronic devices in danger of destruction by high energy voltage transients. Select from standard factory available types or design the suppressor to meet specific needs by paralleling cells. For specific options, i.e., non-standard voltage, higher power capacity, and package configurations, consult factory.

PEAK POWER DISSIPATION @ 1.0 ms = 500 WATTS — CASE 59-04

Device	Breakdown Voltage V_{BR} Volts Min	Max Non "A"	Max "A"	@ I_T mA	V_{RWM} Peak Rev. Voltage Volts	I_R Max. Rev. Leakage µA	I_{RSM} Max Reverse Surge Current Amps Non "A"	I_{RSM} "A"	V_{RSM} Max Reverse Voltage @ I_{RSM} Volts Non "A"	V_{RSM} "A"
SA5.0,A	6.4	7.3	7	10	5	600	52	54.3	9.6	9.2
SA6.0,A	6.67	8.15	7.37	10	6	600	43.9	48.5	11.4	10.3
SA6.5,A	7.22	8.82	7.98	10	6.5	400	40.7	44.7	12.3	11.2
SA7.0,A	7.78	9.51	8.6	10	7	150	37.8	41.7	13.3	12
SA7.5,A	8.33	10.2	9.21	1	7.5	50	35	38.8	14.3	12.9
SA8.0,A	8.89	10.9	9.3	1	8	25	33.3	36.7	15	13.6
SA8.5,A	9.44	11.5	10.4	1	8.5	5	31.4	34.7	15.9	14.4
SA9.0,A	10	12.2	11.1	1	9	1	29.5	32.5	16.9	15.4
SA10,A	11.1	13.6	12.3	1	10	1	26.6	29.4	18.8	17
SA11,A	12.2	14.9	13.5	1	11	1	24.9	27.4	20.1	18.2
SA12,A	13.3	16.3	14.7	1	12	1	22.7	25.1	22	19.9
SA13,A	14.4	17.6	15.9	1	13	1	21	23.2	23.8	21.5
SA14,A	15.6	19.1	17.2	1	14	1	19.4	21.5	25.8	23.2
SA15,A	16.7	20.4	18.5	1	15	1	18.8	20.6	26.9	24.4
SA16,A	17.8	21.8	19.7	1	16	1	17.6	19.2	28.8	26
SA17,A	18.9	23.1	20.9	1	17	1	16.4	18.1	30.5	27.6
SA18,A	20	24.4	22.1	1	18	1	15.5	17.2	32.2	29.2
SA20,A	22.2	27.1	24.5	1	20	1	13.9	15.4	35.8	32.4
SA22,A	24.4	29.8	26.9	1	22	1	12.7	14.1	39.4	35.5
SA24,A	26.7	32.6	29.5	1	24	1	11.6	12.8	43	38.9
SA26,A	28.9	35.3	31.9	1	26	1	10.7	11.9	26.6	42.1
SA28,A	31.1	38	34.4	1	28	1	9.9	11	50	45.4
SA30,A	33.3	40.7	36.8	1	30	1	9.3	10.3	53.5	48.4
SA33,A	36.7	44.9	40.6	1	33	1	8.5	9.4	59	53.3
SA36,A	40	48.9	44.2	1	36	1	7.8	8.6	64.3	58.1
SA40,A	44.4	54.3	49.1	1	40	1	7	7.8	71.4	64.5
SA43,A	47.8	58.4	52.8	1	43	1	6.5	7.2	76.7	69.4
SA45,A	50	61.1	55.3	1	45	1	6.2	6.9	80.3	72.7
SA48,A	53.3	65.1	58.9	1	48	1	5.8	6.5	85.5	77.4
SA51,A	56.7	69.3	62.7	1	51	1	5.5	6.1	91.1	82.4
SA54,A	60	73.3	66.3	1	54	1	5.2	5.7	96.3	87.1
SA60,A	66.7	81.5	73.7	1	60	1	4.7	5.2	107	96.8
SA64,A	71.1	86.9	78.6	1	64	1	4.4	4.9	114	103

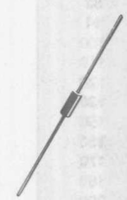
(continued)

PEAK POWER DISSIPATION @ 1.0 ms = 500 WATTS — CASE 59-04 — continued

Device	Breakdown Voltage V_{BR} Volts Min	Max Non "A"	Max "A"	@ I_T mA	V_{RWM} Peak Rev. Voltage Volts	I_R Max. Rev. Leakage μA	I_{RSM} Max Reverse Surge Current Amps Non "A"	I_{RSM} "A"	V_{RSM} Max Reverse Voltage @ I_{RSM} Volts Non "A"	V_{RSM} "A"
SA70,A	77.8	95.1	86	1	70	1	4	4.4	125	113
SA75,A	83.3	102	92.1	1	75	1	3.7	4.1	134	121
SA78,A	86.7	106	95.8	1	78	1	3.6	4	139	126
SA85,A	94.4	115	104	1	85	1	3.3	3.6	151	137
SA90,A	100	122	111	1	90	1	3.1	3.4	160	146
SA100,A	111	136	123	1	100	1	2.8	3.1	179	162
SA110,A	122	149	135	1	110	1	2.6	2.8	196	177
SA120,A	133	163	147	1	120	1	2.3	2.6	214	193
SA130,A	144	176	159	1	130	1	2.2	2.4	231	209
SA150,A	167	204	185	1	150	1	1.9	2.1	268	243
SA160,A	178	218	197	1	160	1	1.7	1.9	287	259
SA170,A	189	231	209	1	170	1	1.6	1.8	304	275

PEAK POWER DISSIPATION @ 1.0 ms = 600 WATTS

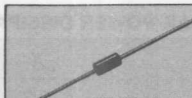
Breakdown Voltage $V_{(BR)}$ Volts Nom	@I_T mA	Device Type	I_{RSM} Maximum Reverse Surge Current Amp	V_{RSM} Maximum Reverse Voltage @ I_{RSM} Volts
6.8	10	P6KE6.8	56	10.8
7.5	10	P6KE7.5	51	11.7
8.2	10	P6KE8.2	48	12.5
9.1	1.0	P6KE9.1	44	13.8
10	1.0	P6KE10	40	15
11	1.0	P6KE11	37	16.2
12	1.0	P6KE12	35	17.3
13	1.0	P6KE13	32	19
15	1.0	P6KE15	27	22
16	1.0	P6KE16	26	23.5
18	1.0	P6KE18	23	26.5
20	1.0	P6KE20	21	29.1
22	1.0	P6KE22	19	31.9
24	1.0	P6KE24	17	34.7
27	1.0	P6KE27	15	39.1
30	1.0	P6KE30	14	43.5
33	1.0	P6KE33	12.6	47.7
36	1.0	P6KE36	11.6	52
39	1.0	P6KE39	10.6	56.4
43	1.0	P6KE43	9.6	61.9
47	1.0	P6KE47	8.9	67.8
51	1.0	P6KE51	8.2	73.5
56	1.0	P6KE56	7.4	80.5
62	1.0	P6KE62	6.8	89
68	1.0	P6KE68	6.1	98
75	1.0	P6KE75	5.5	108
82	1.0	P6KE82	5.1	118
91	1.0	P6KE91	4.8	131
100	1.0	P6KE100	4.2	144
110	1.0	P6KE110	3.8	158
120	1.0	P6KE120	3.5	173
130	1.0	P6KE130	3.2	187
150	1.0	P6KE150	2.8	215
160	1.0	P6KE160	2.6	230
170	1.0	P6KE170	2.5	244
180	1.0	P6KE180	2.3	258
200	1.0	P6KE200	2.1	287



CASE 17-02

Breakdown Voltage for Standard is ±10% Tolerance; ±5% version is available by adding "A", i.e., P6KE6.8A. Clipper (back to back) versions are available by ordering with a "C" or "CA" suffix, i.e., P6KE6.8C or P6KE6.8CA.

TRANSIENT SUPPRESSORS (continued)

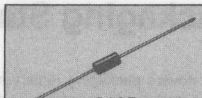


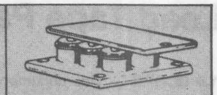
CASE 41-11

PEAK POWER DISSIPATION @ 1.0 ms = 1500 WATTS

Breakdown Voltage $V_{(BR)}$ Volts Nom	Breakdown Voltage $@I_T$ mA	Device Type	Device Type	I_{RSM} Maximum Reverse Surge Current Amp	V_{RSM} Maximum Reverse Voltage @ I_{RSM} Volts	Case
6.0	1.0	1N5908		120	8.5	41-11
6.8	10	1N6267	1.5KE6.8	139	10.8	
7.5	10	1N6268	1.5KE7.5	128	11.7	
8.2	10	1N6269	1.5KE8.2	120	12.5	
9.1	1.0	1N6270	1.5KE9.1	109	13.8	
10	1.0	1N6271	1.5KE10	100	15.0	
11	1.0	1N6272	1.5KE11	93	16.2	
12	1.0	1N6273	1.5KE12	87	17.3	
13	1.0	1N6274	1.5KE13	79	19.0	
15	1.0	1N6275	1.5KE15	68	22.0	
16	1.0	1N6276	1.5KE16	64	23.5	
18	1.0	1N6277	1.5KE18	56.5	26.5	
20	1.0	1N6278	1.5KE20	51.5	29.1	
22	1.0	1N6279	1.5KE22	47.0	31.9	
24	1.0	1N6280	1.5KE24	43.0	34.7	
27	1.0	1N6281	1.5KE27	38.5	39.1	
30	1.0	1N6282	1.5KE30	34.5	43.5	
33	1.0	1N6283	1.5KE33	31.5	47.7	
36	1.0	1N6284	1.5KE36	29.0	52	
39	1.0	1N6285	1.5KE39	26.5	56.4	
43	1.0	1N6286	1.5KE43	24	61.9	
47	1.0	1N6287	1.5KE47	22.2	67.8	
51	1.0	1N6288	1.5KE51	20.4	73.5	
56	1.0	1N6289	1.5KE56	18.6	80.5	
62	1.0	1N6290	1.5KE62	16.9	89	
68	1.0	1N6291	1.5KE68	15.3	98	
75	1.0	1N6292	1.5KE75	13.9	108	
82	1.0	1N6293	1.5KE82	12.7	118	
91	1.0	1N6294	1.5KE91	11.4	131	
100	1.0	1N6295	1.5KE100	10.4	144	
110	1.0	1N6296	1.5KE110	9.5	158	
120	1.0	1N6297	1.5KE120	8.7	173	
130	1.0	1N6298	1.5KE130	8.0	187	
150	1.0	1N6299	1.5KE150	7.0	215	
160	1.0	1N6300	1.5KE160	6.5	230	
170	1.0	1N6301	1.5KE170	6.2	244	
180	1.0	1N6302	1.5KE180	5.8	258	
200	1.0	1N6303	1.5KE200	5.2	287	
220	1.0		1.5KE220	4.3	344	
250	1.0		1.5KE250	5.0	360	

Breakdown Voltage for Standard is ±10% Tolerance; ±5% version is available by adding "A", i.e., 1N6267A, 1.5KE6.8A. Clipper (back to back) versions are available by ordering the 1.5KE series with a "C" or "CA" suffix, i.e., 1.5KE6.8C or 1.5KE6.8CA.


CASE 41-11


CASE 119-01

PEAK POWER DISSIPATION @ 1.0 ms = 1500 WATTS

V_{RWM} Working Peak Reverse Voltage (Blocking or Stand-Off Voltage)	Device Type	Clipper (Back To Back) Version	I_{RSM} Maximum Reverse Surge Current Amp	V_{RSM} Maximum Reverse Voltage @ I_{RSM} Volts	Case
5.0	1N6373 / ICTE-5 / MPTE-5	ICTE-5C	160	9.4	41-11
8.0	1N6374 / ICTE-8 / MPTE-8	1N6382	100	15	
10	1N6375 / ICTE-10 / MPTE-10	1N6383	90	16.7	
12	1N6376 / ICTE-12 / MPTE-12	1N6384	70	21.2	
15	1N6377 / ICTE-15 / MPTE-15	1N6385	60	25	
18	1N6378 / ICTE-18 / MPTE-18	1N6386	50	30	
22	1N6379 / ICTE-22 / MPTE-22	1N6387	40	37.5	
36	1N6380 / ICTE-36 / MPTE-36	1N6388	23	65.2	
45	1N6381 / ICTE-45 / MPTE-45	1N6389	19	78.9	

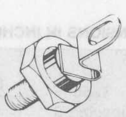
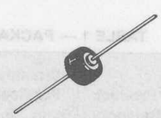
PEAK POWER DISSIPATION @ 1.0 ms = 8000 WATTS

V_R Operating Voltage Nom Vdc	$V_{(RMS)}$	Device Type	I_R Reverse Current μA	ΔV_Z Breakdown Voltage Min Volts	@ I_{ZT} mA	V_C Clamping Voltage Max Volts	@ I_{PP} Amp	V_F Forward Voltage Volts	@ I_F Amp	Case
14	10	MPZ5-16A	50	16	0.4	24	200	1.5	10	119-01
14	10	MPZ5-16B		16	0.4	20	200			
28	20	MPZ5-32A		32	0.2	50	100			
28	20	MPZ5-32B		32	0.2	45	100			
28	20	MPZ5-32C		32	0.2	40	100			
165	117	MPZ5-180A		180	0.03	250	20			
165	117	MPZ5-180B		180	0.03	225	20			
165	117	MPZ5-180C		180	0.03	205	20			

Automotive Transient Suppressors

Automotive Transient Suppressors are designed for protection against over-voltage conditions in the auto electrical system including the "LOAD DUMP" phenomenon that occurs when the battery open circuits while the car is running.

AUTOMOTIVE TRANSIENT SUPPRESSOR

	296-03	194-01/04			
	MR2525 MR2525R	MR2525L	MR2520L	MR2535L	MR2540L
V_{RRM} (Volts)	23	23	23	20	20
I_O (Amp)	25	6	6	35	50
$V_{(BR)}$ (Volts)	24–32	24–32	24–32	24–32	24–32
I_{RSM}* (Amp)	110	110	68	110	150
T_C @ Rated I_O (°C)	150	150	150	150	150
T (°C)	175	175	175	175	175

* Time Constant = 10 ms, Duty Cycle ≤ 1.0%, T_C = 25°C.

2

Lead Tape Packaging Standards for Axial-Lead Components

1.0 SCOPE — This document covers packaging requirements for the following axial-lead components' use in automatic testing and assembly equipment: Motorola Case 51 (DO-7), Case 52 (DO-13), Case 59 (DO-41), Case 267, Case 299 (DO-35), Case 59-04 and Case 17. Packaging, as covered in this document, shall consist of axial-lead components mounted by their leads on pressure-sensitive tape, wound onto a reel.

2.0 PURPOSE — This document establishes Motorola standard practices for lead-tape packaging of axial-lead components and meets the requirements of EIA Standard RS-296-D "Lead-taping of components on axial lead configuration for automatic insertion," level 1.

2

3.0 REQUIREMENTS

3.1 Component Leads

3.1.1 — Component leads shall not be bent beyond dimension E from their nominal position. See Figure 2.

3.1.2 — The "C" dimension shall be governed by the overall length of the reel packaged component. The distance between flanges shall be 0.059 inch to 0.315 inch greater than the overall component length. See Figures 2 and 3.

3.1.3 — Cumulative dimension "A" tolerance shall not exceed 0.059 over 5 in consecutive components.

ORIENTATION — All polarized components must be oriented in one direction. The cathode lead tape shall be blue, and the anode tape shall be white. See Figure 1.

3.3 Reeling

3.3.1 — Components on any reel shall not represent more than two date codes when date code identification is required.

3.3.2 — Components leads shall be positioned perpendicularly between pairs of 0.250 inch tape. See Figure 2.

3.3.3 — A minimum 1 inch leader of tape shall be provided before the first and last component on the reel.

3.3.4 — 50 lb. Kraft paper is wound between layers of components as far as necessary for component protection. Width of paper is 0.062 inch to 0.750 inch less than "C" dimension of reel. See Figure 3.

3.3.5 — Components shall be centered between tapes such that the difference between D1 and D2 does not exceed 0.055.

3.3.6 — Staple shall not be used for splicing. No more than 4 layers of tape shall be used in any splice area and no tape shall be offset from another by more than 0.031 inch noncumulative. Tape splices shall overlap at least 6 inches for butt joints and at least 3 inches for lap joints, and shall not be weaker than unspliced tape.

3.3.7 — Quantity per reel shall be as indicated in Table 1. Orders for tape and reeled product will only be processed and shipped in full reel increments. Scheduled orders must be in releases of full reel increments or multiples thereof. High volume orders and releases may be reeled on 14.00 inch reels at Motorola's option, therefore making the quantity per reel twice that shown for the 10.50 inch reels.

3.3.8 — A maximum of 0.25% of the components per reel quantity may be missing without consecutive missing per level 1 of RS-296-D.

3.3.9 — The single face roll pad shall be placed around the finished reel and taped securely. Each reel shall then be placed in an appropriate container.

3.4 MARKING — Minimum reel and carton marking shall consist of the following: See Figure 3.

Part number
Purchase order number
Quantity
Date of reeling (when applicable)
Manufacturer's name
Electrical value (when applicable)
Date codes (when applicable; see note 3.3.1)
Tape (when applicable)

4.0 — Requirements differing from this Motorola standard shall be negotiated with the factory.

The packages indicated in the following table are suitable for lead tape packaging. The table indicates the specific devices (rectifiers and/or zeners) that can be obtained from Motorola in reel packaging, and provides the appropriate packaging specification.

TABLE 1 — PACKAGING DETAILS (ALL DIMENSIONS IN INCHES)

Case Type	Product Category	Quantity Per Reel (Item 3.3.7)	Component Spacing A	Tape Spacing B	Reel Dimensions C	Reel Dimensions D (max)	Max Off Alignment E	Item Number
Case 51-02 (DO-7)	All	3000	0.200 ± 0.020	2.062 ± .059	3.00	10.50	0.047	1
Case 299-02 (DO-35)	Zeners	3000	0.200 ± 0.020	2.062 ± .059	3.00	10.50		2
Case 17-02	Zeners	2000	0.200 ± 0.015	2.062 ± .059	3.00	10.50		3
Case 59-03 (DO-41)	Zeners	3000	0.200 ± 0.015	2.062 ± .059	3.00	10.50		4
Case 59-01 (DO-41)	Zeners	3000	0.200 ± 0.015	2.062 ± .059	3.00	10.50		5
Case 59-01 (DO-41)	Rectifiers	6000	0.200 ± 0.020	2.062 ± .059	3.00	14.00		6
Case 59-04	Rectifiers	5000	0.200 ± 0.020	2.062 ± .059	3.00	14.00		7
Case 52-03 (DO-13)	Zeners	1500	0.400 ± 0.020	2.500 ± .059	3.81	14.00		8
Case 267-02	Rectifiers	1500	0.400 ± 0.020	2.062 ± .059	3.00	14.00		9
Case 41-11	Zeners	1250	0.200 ± 0.020	2.500 ± .059	3.81	14.00		10
Case 194-01	Rectifiers	900	0.500 ± 0.020	1.875 ± .059	3.00	14.00		11
Case 194-04	Rectifiers	900	0.400 ± 0.020	1.875 ± .059	3.00	14.00		12

FIGURE 1 — REEL PACKING

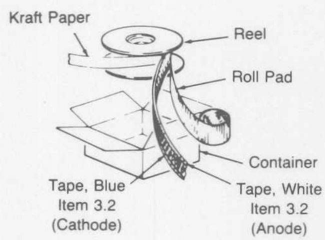


FIGURE 2 — COMPONENT SPACING

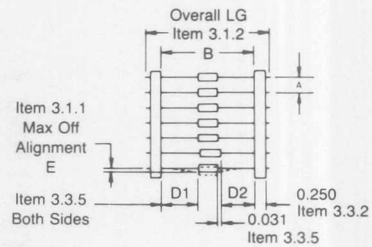
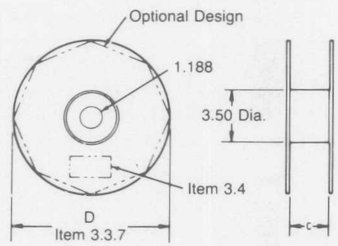


FIGURE 3 — REEL DIMENSIONS



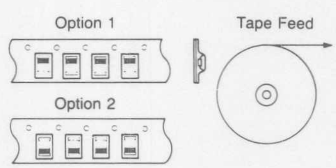
SURFACE MOUNT TAPE AND REEL

In conjunction with the industry trend to use automatic placement equipment for microminiature components, Motorola offers MLL34 and SOT-23 devices in the industry accepted 8 mm tape and reel format. MLL41 devices are offered in 12 mm tape. The current packaging method is plastic tape with embossed cavities, which serve as a pocket for the individual device. A sealing tape is then applied to retain the device.

- Device Orientation: Either in T1 (Option 1) or T2 (Option 2) configuration.
- Quantity Per Reel: 2,000 devices for MLL34.
  1,000 devices for MLL41.
  3,000 devices for SOT-23.
- Minimum Order Quantity: 1 reel.

For ordering information, please contact your local Motorola representative. (See listing on back cover.)

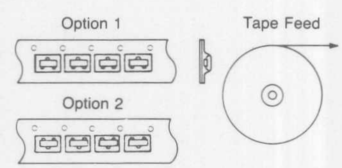
Tape & Reel Options
MLL34, MLL41



Polarity band indicates cathode.

Option 1 = T1 Designator, Cathode Facing Sprocket Holes
Option 2 = T2 Designator, Anode Facing Sprocket Holes

Tape & Reel Options
SOT-23



EIA Std RS481

Option 1 = T1 Designator
Option 2 = T2 Designator

2

Rectifier Data Sheets

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N1199 thru 1N1206

3

MEDIUM-CURRENT SILICON RECTIFIERS

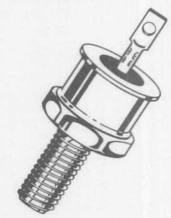
Silicon rectifiers for medium-current applications requiring:

- High Current Surge — 240 Amperes @ T_J = 190°C
- Peak Performance at Elevated Temperature — 12 Amperes @ T_C = 150°C

MEDIUM-CURRENT SILICON RECTIFIERS

50-600 VOLTS
12 AMPERES

DIFFUSED JUNCTION



*MAXIMUM RATINGS

Characteristic	Symbol	1N 1199	1N 1200	1N 1202	1N 1204	1N 1206	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, T_C = 150°C)	I_O	← 12 →					Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	← 240 (for 1 cycle) →					Amp
Operating Junction Temperature Range	T_J	← -65 to +190 →					°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W

*ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (i_F = 40 A, T_C = 25°C)	v_F	1.8	Volts
Maximum Instantaneous Reverse Current (Rated voltage, T_C = 150°C)	i_R	10	mA

*Indicates JEDEC registered data.

MECHANICAL CHARACTERISTICS

Case: Welded, hermetically sealed

Finish: All external surfaces are corrosion-resistant and the terminal lead is readily solderable

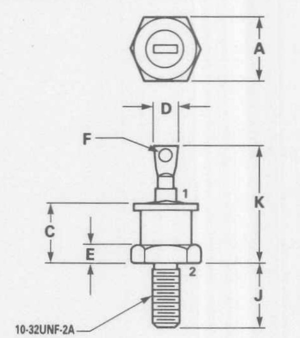
Polarity: Cathode to case (reverse polarity units are available and designed by an "R" suffix, i.e., 1N1202R)

Mounting Positions: Any

Stud Torque: 15 in/lbs max

Maximum Terminal Temperature for Soldering Purposes: 275°C for 10 seconds at 3 kg tension.

Weight: 6 grams (approx)



STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N1199A thru 1N1206A

3

MEDIUM-CURRENT SILICON RECTIFIERS

Silicon rectifiers for medium-current applications requiring:

- High Current Surge — 240 Amperes @ $T_J = 200°C$
- Peak Performance at Elevated Temperature — 12 Amperes @ $T_C = 150°C$

MEDIUM-CURRENT SILICON RECTIFIERS

50–600 VOLTS
12 AMPERES
DIFFUSED JUNCTION

*MAXIMUM RATINGS

Characteristic	Symbol	1N 1199A	1N 1200A	1N 1202A	1N 1204A	1N 1206A	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage (Halfwave, single phase, 60 Hz peak)	V_{RSM}	100	200	350	600	800	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, $T_C = 150°C$)	I_O	← 12 →					Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	← 240 (for 1 cycle) →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← −65 to +200 →					°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W

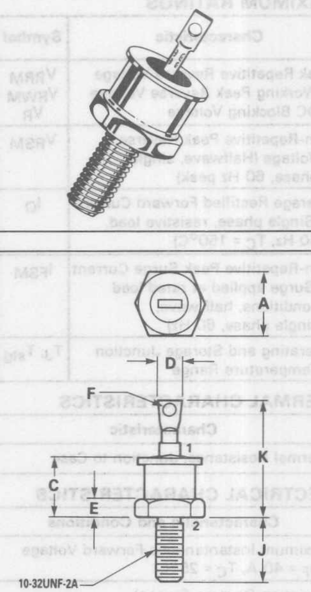
*ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage ($i_F = 40$ A, $T_C = 25°C$)	v_F	1.35	Volts
Maximum Average Reverse Current at Rated Conditions	I_{RO}		mA
1N1199A		3.0	
1N1200A		2.5	
1N1202A		2.0	
1N1204A		1.5	
1N1206A		1.0	

*Indicates JEDEC registered data.

MECHANICAL CHARACTERISTICS

Case: Welded, hermetically sealed
Finish: All external surfaces are corrosion-resistant and the terminal lead is readily solderable
Polarity: Cathode to case (reverse polarity units are available and designed by an "R" suffix, i.e., 1N1202RA)
Mounting Positions: Any
Stud Torque: 15 in/lbs max
Maximum Terminal Temperature for Soldering Purposes: 275°C for 10 seconds at 3 kg tension.
Weight: 6 grams (approx)



STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N1199B thru 1N1206B

MEDIUM-CURRENT SILICON RECTIFIERS

Compact, highly efficient silicon rectifiers for medium-current applications requiring:

- High Current Surge — 250 Amperes @ $T_J = 200°C$
- Peak Performance at Elevated Temperature — 12 Amperes @ $T_C = 150°C$

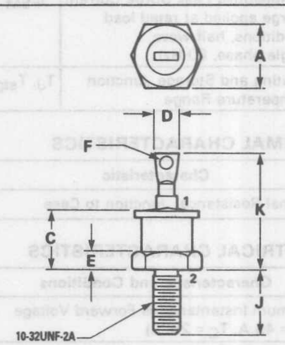
MEDIUM-CURRENT SILICON RECTIFIERS

50-600 VOLTS
12 AMPERES

DIFFUSED JUNCTION

*MAXIMUM RATINGS

Characteristic	Symbol	1N 1199B	1N 1200B	1N 1202B	1N 1204B	1N 1206B	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage (Halfwave, single phase, 60 Hz peak)	V_{RSM}	100	200	350	600	800	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, $T_C = 150°C$)	I_O	← 12 →					Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	← 250 (for 1 cycle) →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +200 →					°C



STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W

*ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage ($i_F = 40$ A, $T_C = 25°C$)	v_F	1.2	Volts
Maximum Reverse Current (Rated dc voltage, $T_C = 150°C$)	I_R	1.0	mA
Maximum Average Reverse Current at Rated Conditions	I_{RO}	0.9	mA
DC Forward Voltage ($I_F = 12$ A, $T_C = 25°C$)	V_F	1.1	Volts
Reverse Recovery Time ($I_{FM} = 40$ A, di/dt = 25 A/μs to $I_{FM} = 0$, $t_p \geqslant 4.0$ μs, 60 pulses/second, 25°C)	t_{rr}	5.0	μs

*Indicates JEDEC registered data.

MECHANICAL CHARACTERISTICS

Case: Metal hermetically sealed
Finish: All external surfaces are corrosion-resistant and the terminal lead is readily solderable
Polarity: Cathode to case (reverse polarity units are available and designed by an "R" suffix, i.e., 1N1202RB)
Mounting Positions: Any
Stud Torque: 15 in/lbs max
Maximum Terminal Temperature for Soldering Purposes: 275°C for 10 seconds at 3 kg tension.
Weight: 6 grams (approx)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3208 thru 1N3212

MEDIUM-CURRENT RECTIFIERS

. . . for applications requiring low forward voltage drop and rugged construction.

- High Surge Handling Ability
- Rugged Construction
- Reverse Polarity Available; Eliminates Need for Insulating Hardware in Many Cases
- Hermetically Sealed

15-AMP RECTIFIERS

SILICON DIFFUSED-JUNCTION

3

***MAXIMUM RATINGS**

Rating	Symbol	1N3208 1N3208R	1N3209 1N3209R	1N3210 1N3210R	1N3211 1N3211R	1N3212 1N3212R	Unit
DC Blocking Voltage	V_R	50	100	200	300	400	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	Volts
Average Half-Wave Rectified Forward Current With Resistive Load	I_O**	15	15	15	15	15	Amp
Peak One Cycle Surge Current (60 Hz and 25°C Case Temperature)	I_{FSM}	250	250	250	250	250	Amp
Operating Junction Temperature	T_J	←	—	-65 to +175	—	→	°C
Storage Temperature	T_{stg}	←	—	-65 to +175	—	→	°C

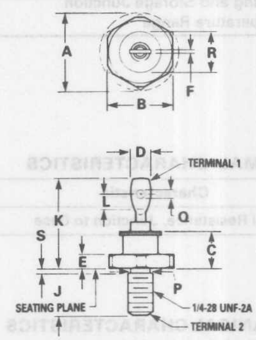
***ELECTRICAL CHARACTERISTICS** (All Types) at 25°C Case Temperature

Characteristic	Symbol	Value	Unit
Maximum Forward Voltage at 40 Amp DC Forward Current	V_F	1.5	Volts
Maximum Reverse Current at Rated DC Reverse Voltage	I_R	1.0	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typical	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.7	°C/W

*Indicates JEDEC registered data.
**T_C = 150°C



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	20.07	—	0.790
B	16.94	17.45	0.669	0.687
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	19.05	25.40	0.750	1.00
L	3.96	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	16.94	—	0.667
S	—	2.26	—	0.089

CASE 42A-01
DO-203AB
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded hermetically sealed construction
FINISH: All external surfaces corrosion-resistant and the terminal lead is readily solderable
WEIGHT: 25 grams (approx.)
POLARITY: Cathode connected to case (reverse polarity available denoted by Suffix R, ie: 1N3212R)
MOUNTING POSITION: Any

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3491
thru
1N3495

Designers Data Sheet

MEDIUM-CURRENT SILICON RECTIFIERS

. . . compact, highly efficient silicon rectifiers for Class 5-7 truck applications.

Designer's Data for "Worst Case" Conditions

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing device characteristics boundaries — are given to facilitate "worst case" design.

SILICON RECTIFIERS
25 AMPERE

50–400 VOLTS
DIFFUSED JUNCTION

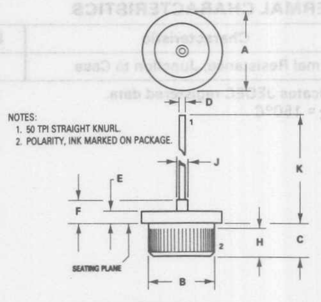
3

*MAXIMUM RATINGS

Rating	Symbol	1N3491	1N3492	1N3493	1N3494	1N3495	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, see Figure 3) $T_C = 100°C$	I_O	25					Amp
Nonrepetitive Peak Surge Current (surge applied at rated load conditions, see Figure 5)	I_{FSM}	300 (for 1/2 cycle)					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175					°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	°C/Watt



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.494	16.256	0.610	0.640
B	12.725	12.827	0.501	0.505
C	5.08	6.35	0.200	0.250
D	1.193	1.346	0.047	0.053
E	2.032	4.826	0.080	0.190
F	—	10.77	—	0.424
H	4.572	6.350	0.180	0.250
J	—	3.556	—	0.140
K	12.70	—	0.500	—

CASE 43-02
DO-208AA
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed construction.

FINISH: All external surfaces corrosion-resistant and the terminal lead is readily solderable.

POLARITY: CATHODE TO CASE (reverse polarity units are available upon request and are designated by an "R" suffix i.e. MR327R or 1N3491R).

MOUNTING POSITIONS: Any.

*Indicates JEDEC registered data for 1N3491–1N3495

*ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Instantaneous Forward Voltage Drop (i_F = 57 Amps, T_J = 25°C)	v_F	1.7	Volts
Full Cycle Average Reverse Current (18 Amp AV and V_r, single phase, 60 Hz, T_C = 150°C)	$I_{R(AV)}$		mA
1N3491		10	
1N3492		10	
1N3493		8.0	
1N3494		6.0	
1N3495		4.0	
DC Reverse Current (Rated V_R, T_C = 25°C)	I_R	1.0	mA

FIGURE 1 — MAXIMUM FORWARD VOLTAGE DROP

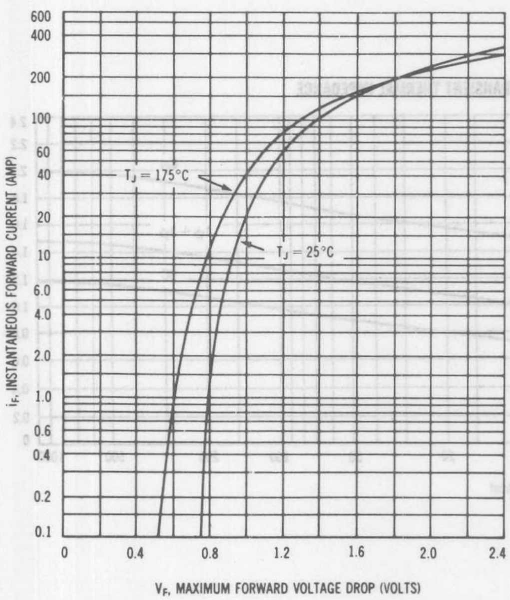


FIGURE 2 — MAXIMUM FORWARD POWER DISSIPATION

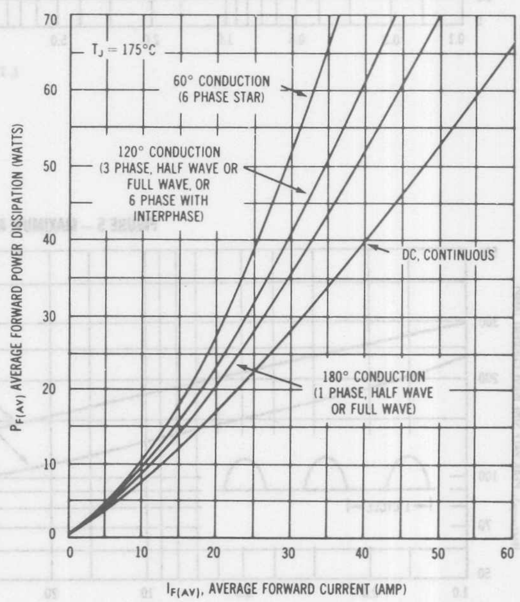


FIGURE 3 — MAXIMUM CURRENT RATINGS

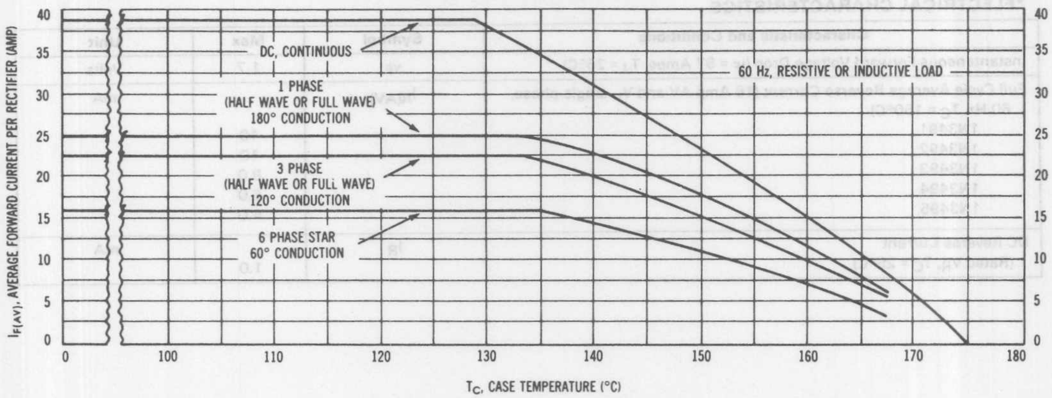


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FIGURE 4 — MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE

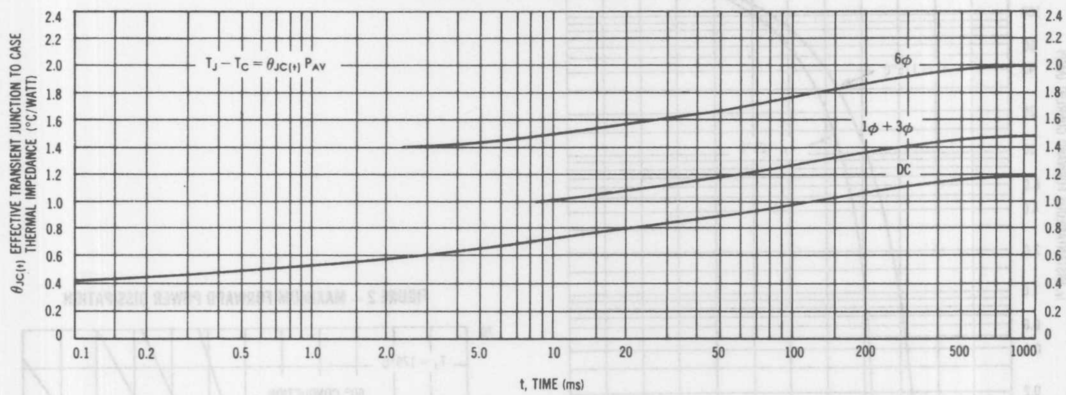
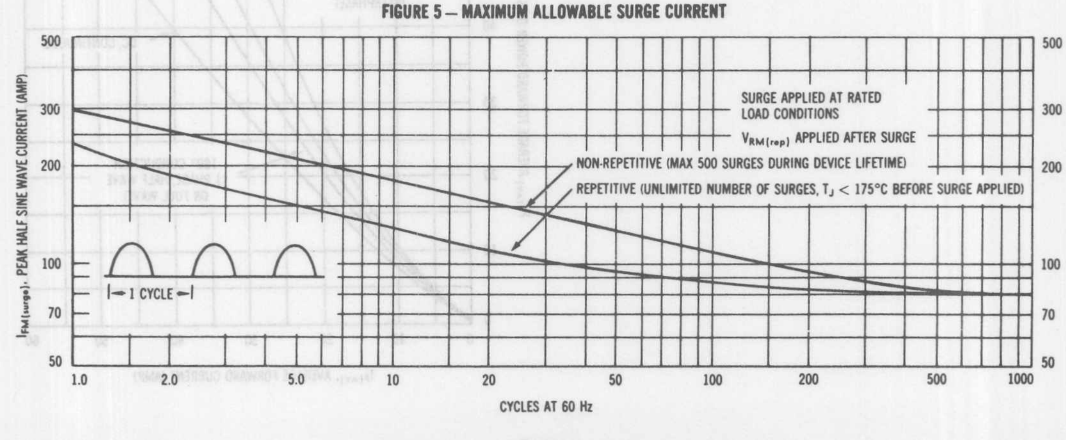


FIGURE 5 — MAXIMUM ALLOWABLE SURGE CURRENT



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 6 — RECTIFICATION EFFICIENCY

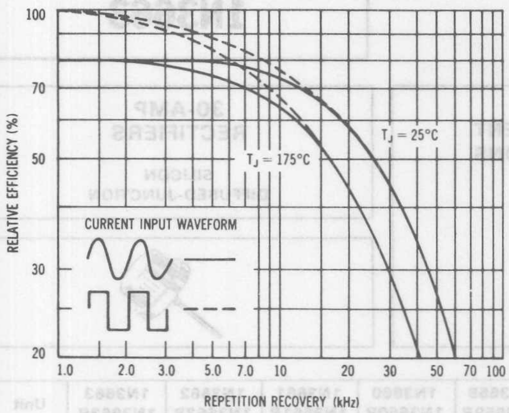


FIGURE 7 — REVERSE RECOVERY TIME

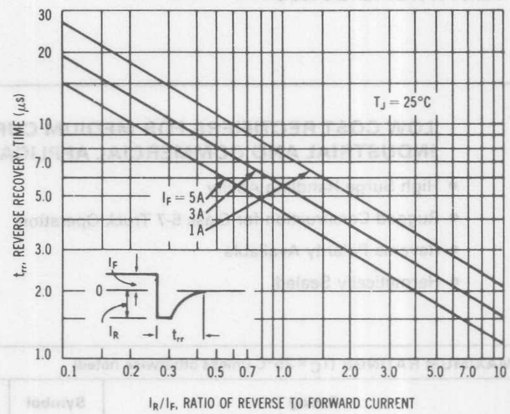


FIGURE 8 — JUNCTION CAPACITANCE

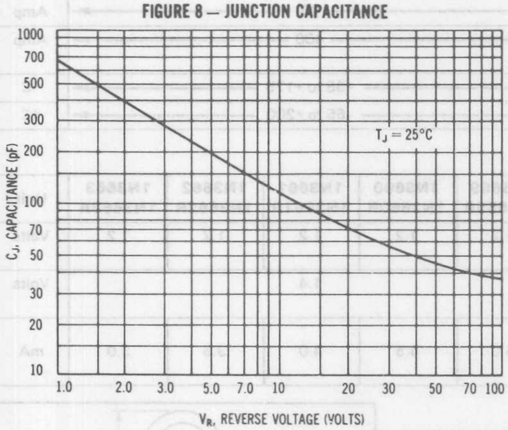
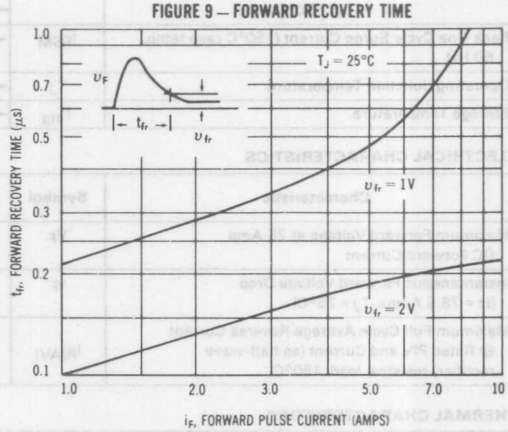
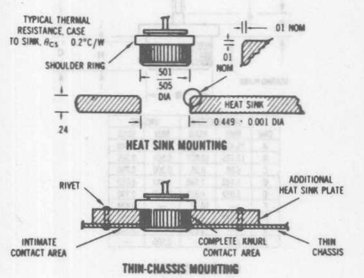


FIGURE 9 — FORWARD RECOVERY TIME





MOUNTING PROCEDURES

MR327-MR331 and 1N3491-1N3495 rectifiers are designed to be press-fitted in a heat sink in order to attain full device ratings. Recommended procedures for this type of mounting are as follows:

1. Drill a hole in the heat sink 0.499 ± .001 inch in diameter.
2. Break the hole edge as shown to prevent shearing off the knurled edge of the rectifier when it is pressed into the hole.
3. The depth and width of the break should be 0.010 inch maximum to retain maximum heat sink surface contact.
4. To prevent damage to the rectifier during press-in, the pressing force should be applied only on the shoulder ring of the rectifier case as shown in the figure.
5. The pressing force should be applied evenly about the shoulder ring to avoid tilting or canting of the rectifier case in the hole during the press-in operation. Also, the use of a light industrial lubricant will be of considerable aid.

1N3659 thru 1N3663

30-AMP RECTIFIERS

SILICON DIFFUSED-JUNCTION

LOW COST RECTIFIERS FOR MEDIUM CURRENT INDUSTRIAL AND COMMERCIAL APPLICATIONS

- High Surge Handling Ability
- Rugged Construction for Class 5-7 Truck Operation
- Reverse Polarity Available
- Hermetically Sealed

3

***MAXIMUM RATINGS** (T_C = 25°C unless otherwise noted)

Rating	Symbol	1N3659 1N3659R	1N3660 1N3660R	1N3661 1N3661R	1N3662 1N3662R	1N3663 1N3663R	Unit
Peak Repetitive Reverse Voltage DC Blocking Voltage	V_{RRM} V_R	50	100	200	300	400	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	Volts
Average Half-Wave Rectified Forward Current with Resistive Load @ 100°C case / @ 150°C case	I_O	← 30 → / ← 25 →					Amp / Amp
Peak One Cycle Surge Current (150°C case temp, 60 Hz)	I_{FSM}	← 400 →					Amp
Operating Junction Temperature	T_J	← -65 to +175 →					°C
Storage Temperature	T_{stg}	← -65 to +200 →					°C

***ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	1N3659 1N3659R	1N3660 1N3660R	1N3661 1N3661R	1N3662 1N3662R	1N3663 1N3663R	Unit
Maximum Forward Voltage at 25 Amp DC Forward Current	V_F	1.2	1.2	1.2	1.2	1.2	Volts
Instantaneous Forward Voltage Drop (i_F = 78.5 Amps, T_J = 25°C)	v_F			1.4			Volts
Maximum Full Cycle Average Reverse Current @ Rated PIV and Current (as half-wave rectifier, resistive load, 150°C)	$I_{R(AV)}$	5.0	4.5	4.0	3.5	3.0	mA

***THERMAL CHARACTERISTICS**

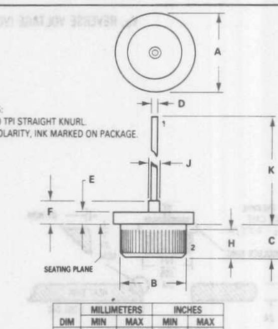
Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	°C/W

*Indicates JEDEC registered data.

MECHANICAL CHARACTERISTICS

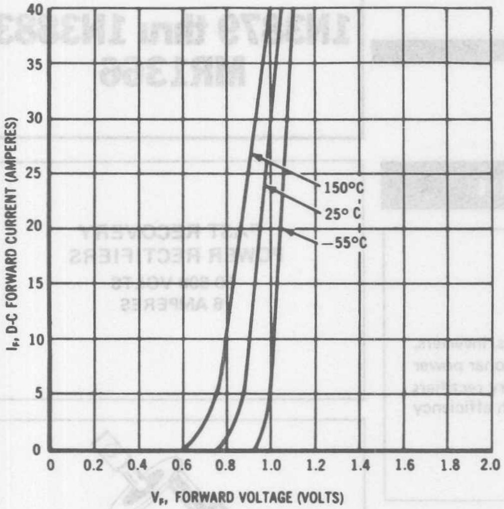
CASE: Welded hermetically sealed construction
FINISH: All external surfaces corrosion resistant, terminals readily solderable
WEIGHT: 9 grams (approx.)
POLARITY: Cathode connected to case (reverse polarity available denoted by Suffix R, i.e.: 1N3660R)
MOUNTING POSITION: Any

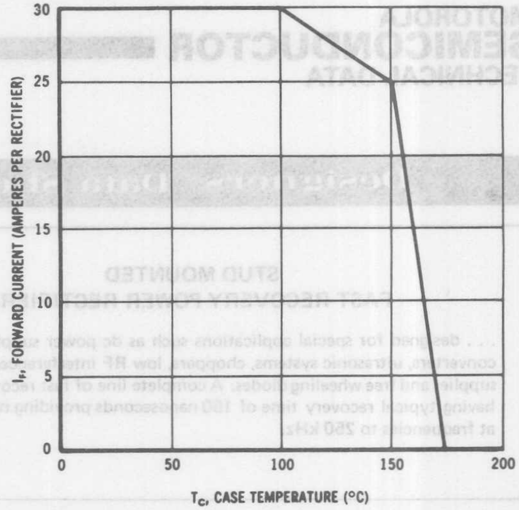
NOTES:
1. 50 TPI STRAIGHT KNURL.
2. POLARITY, INK MARKED ON PACKAGE.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.494	16.256	0.610	0.640
B	12.725	12.827	0.501	0.505
C	5.08	6.35	0.200	0.250
D	1.193	1.346	0.047	0.053
E	2.032	4.826	0.080	0.190
F	—	10.77	—	0.424
H	4.572	6.350	0.180	0.250
J	—	3.556	—	0.140
K	12.70	—	0.500	—

**CASE 43-02
DO-208AA
METAL**



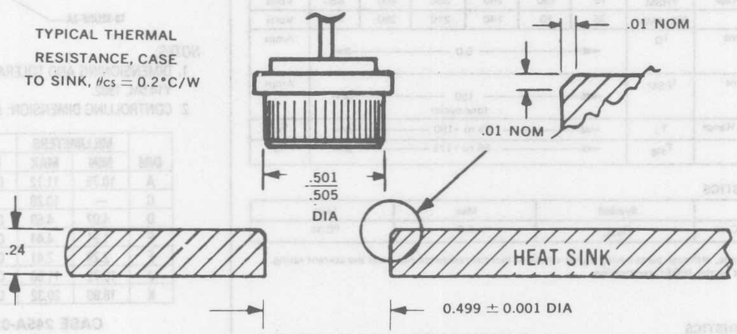


1N3659-1N3663 rectifiers are designed for press-fitted mounting in a heat sink. Recommended procedures for this type of mounting are as follows:

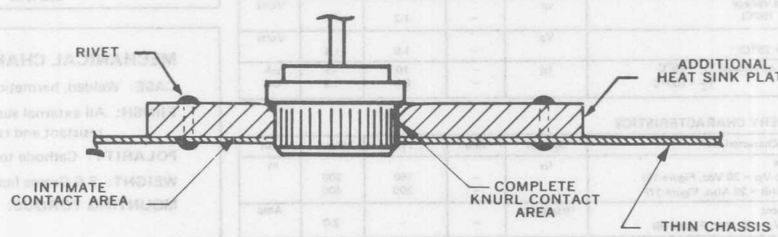
1. Drill a hole in the heat sink 0.499 ± .001 inch in diameter.
2. Break the hole edge as shown to prevent shearing off the knurled edge of the rectifier when it is pressed into the hole.
3. The depth of the break should be 0.010 inch maximum to retain maximum heat sink surface contact with the knurled rectifier surface.
4. Width of the break should be 0.010 inch as shown.

These procedures will allow proper entry of the rectifier knurled surface, provide good rectifier-heat sink surface contact, and assure reliable rectifier operation. If the break is made too deep, thereby reducing contact area for heat transfer, reliability of operation will be impaired.

These devices can be mounted in a thin chassis by inserting the rectifier through an additional heat sink plate which is mounted in intimate contact with the upper side of the chassis. This provides additional contact area for the rectifier knurled edge, as well as additional heat sink capacity.



HEAT SINK MOUNTING



THIN-CHASSIS MOUNTING

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3879 thru 1N3883
MR1366

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

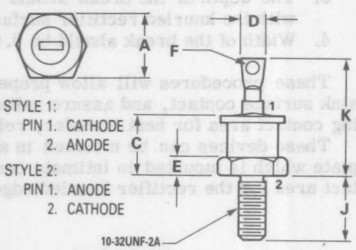
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

FAST RECOVERY POWER RECTIFIERS
50-600 VOLTS
6 AMPERES

3

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.



STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

*MAXIMUM RATINGS

Rating	Symbol	1N3879	1N3880	1N3881	1N3882	1N3883	MR1366	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	350	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100^oC$)	I_O	← 6.0 →						Amps
Non-Repetitive Peak Surge Current (surge applied at rated load continuous)	I_{FSM}	← 150 (one cycle) →						Amps
Operating Junction Temperature Range	T_J	← -65 to +150 →						^oC
Storage Temperature Range	T_{stg}	← -65 to +175 →						^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	$^oC/W$

Motorola guarantees the listed value, although parts having higher values of thermal resistance will meet the current rating. Thermal resistance is not required by the JEDEC registration.

*ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (i_F = 19 Amp, T_J = 150°C)	v_F	–	1.2	1.5	Volts
Forward Voltage (I_F = 6.0 Amp, $T_C = 25^oC$)	V_F	–	1.0	1.4	Volts
Reverse Current (rated dc voltage) $T_C = 25^oC$ $T_C = 100^oC$	I_R	– –	10 0.5	15 1.0	μA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time *(I_{FM} = 1.0 Amp to V_R = 30 Vdc, Figure 16) (I_{FM} = 36 Amp, di/dt = 25 A/μs, Figure 17)	t_{rr}	– –	150 200	200 400	ns
Reverse Recovery Current *(I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16)	$I_{RM(REC)}$	–	–	2.0	Amp

*Indicates JEDEC Registered Data for 1N3879 Series.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and readily solderable
POLARITY: Cathode to Case
WEIGHT: 5.6 Grams (approximately)
MOUNTING TORQUE: 15 in-lbs max.

FIGURE 1 – FORWARD VOLTAGE

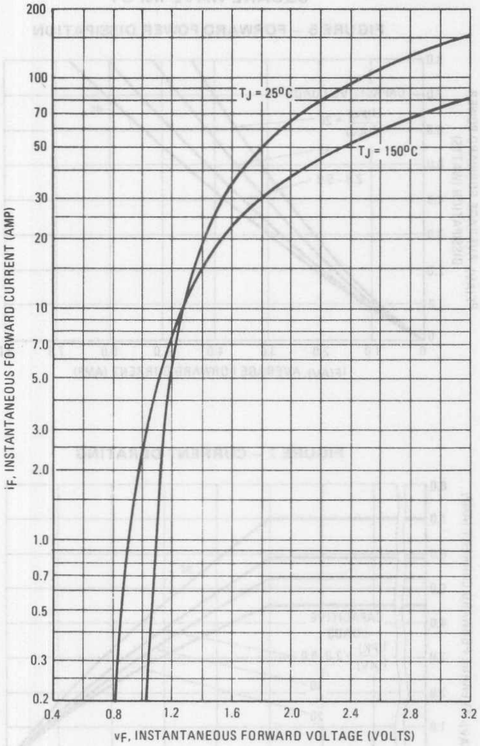
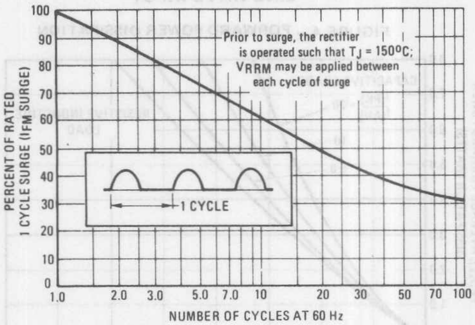
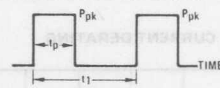


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

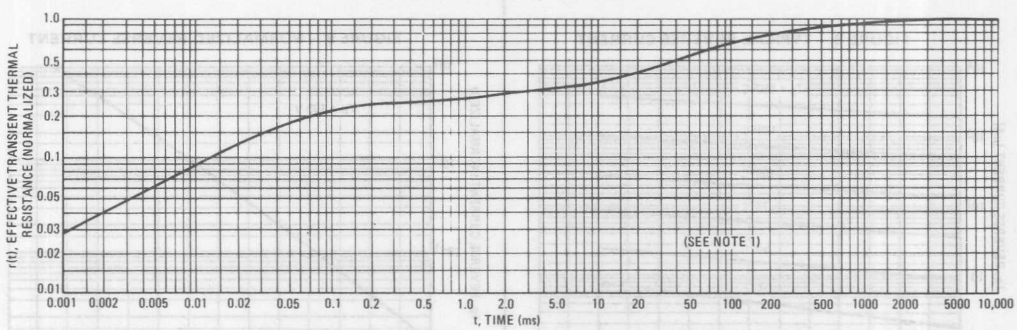
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$

FIGURE 3 – THERMAL RESPONSE



3

SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION

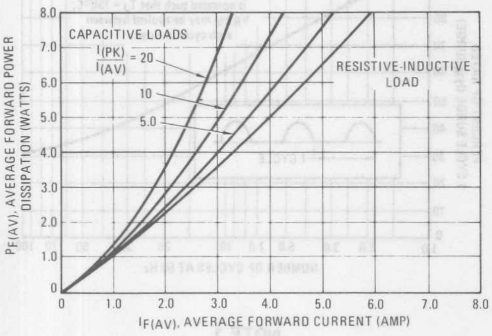


FIGURE 6 – CURRENT DERATING

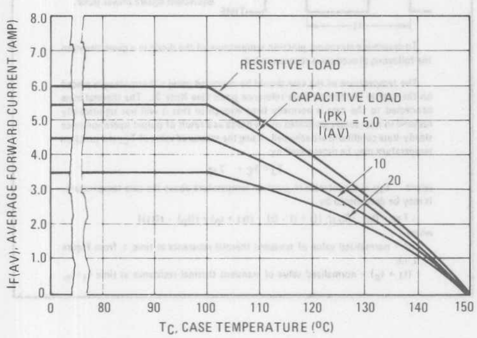
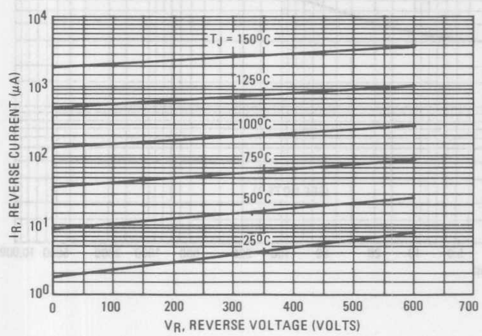


FIGURE 8 – TYPICAL REVERSE CURRENT



SQUARE WAVE INPUT

FIGURE 5 – FORWARD POWER DISSIPATION

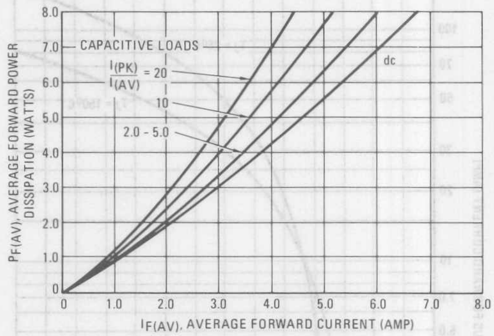


FIGURE 7 – CURRENT DERATING

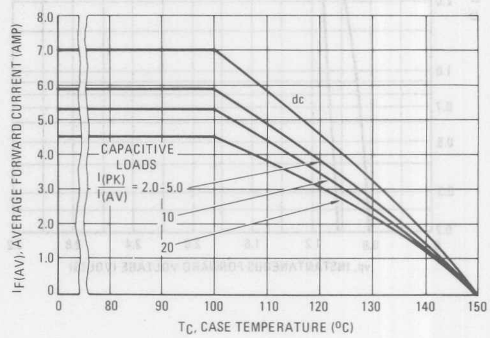
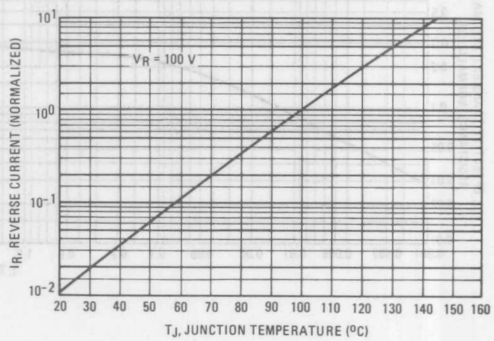


FIGURE 9 – NORMALIZED REVERSE CURRENT



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 – FORWARD RECOVERY TIME

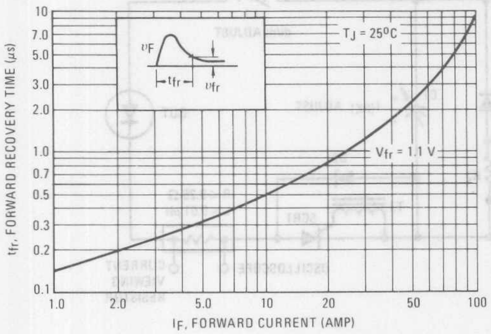
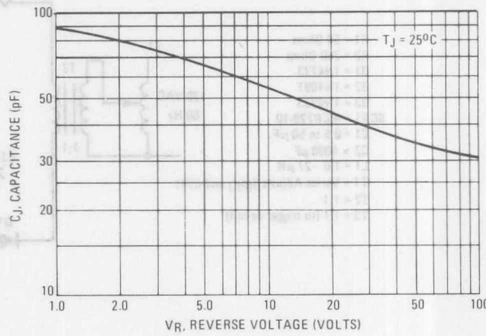


FIGURE 11 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(SEE NOTE 2)

FIGURE 12 – $T_J = 25^oC$

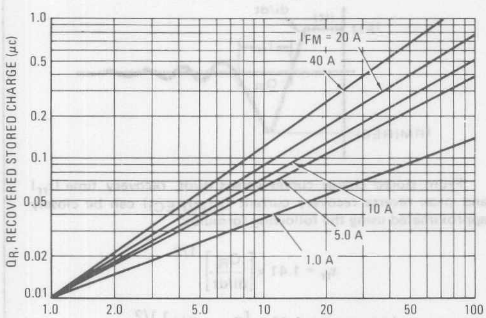


FIGURE 13 – $T_J = 75^oC$

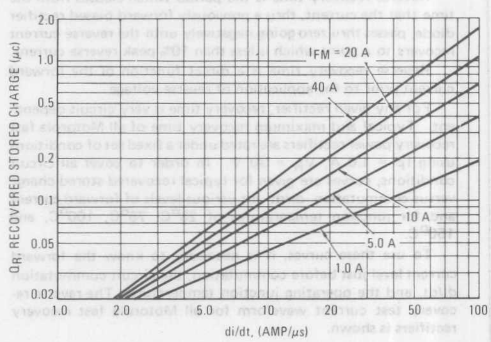


FIGURE 14 – $T_J = 100^oC$

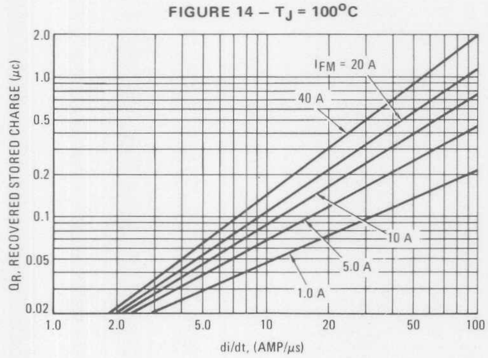


FIGURE 15 – $T_J = 150^oC$

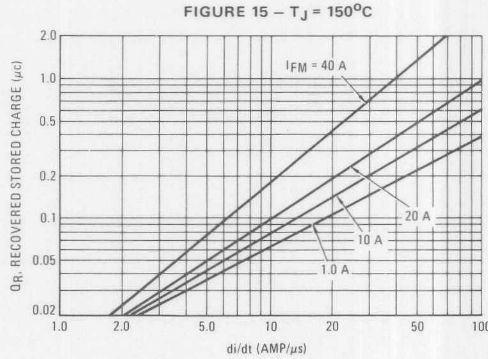
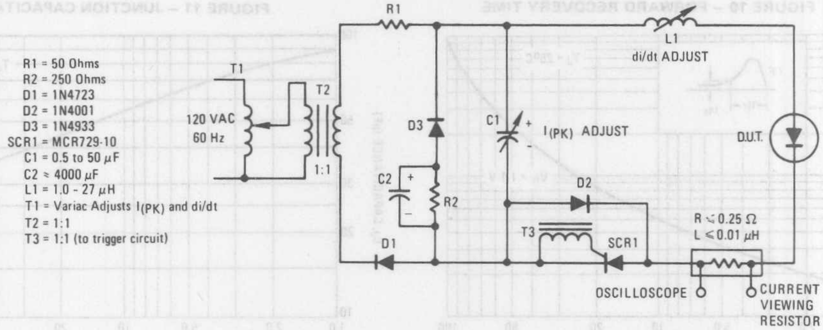


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT



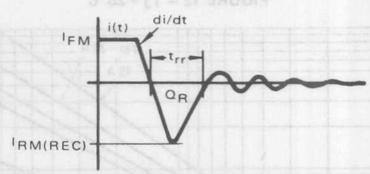
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3889 thru 1N3893
MR1376

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

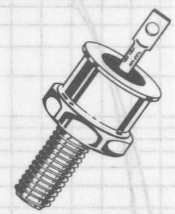
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

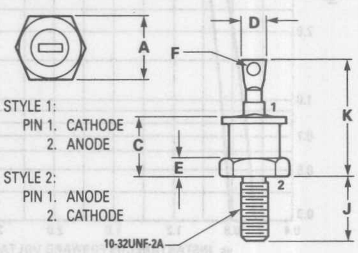
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
12 AMPERES





STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

*MAXIMUM RATINGS

Rating	Symbol	1N3889	1N3890	1N3891	1N3892	1N3893	MR1376	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	350	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100^oC$)	I_O	← 12 →						Amps
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	← 200 (one cycle) →						Amp
Operating Junction Temperature Range	T_J	← −65 to +150 →						^oC
Storage Temperature Range	T_{stg}	← −65 to +175 →						^oC

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	$^oC/W$

Motorola guarantees the listed value, although parts having higher values of thermal resistance will meet the current rating. Thermal resistance is not required by the JEDEC registration.

*ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (i_F = 38 Amp, $T_J = 150^oC$)	v_F	–	1.2	1.5	Volts
Forward Voltage (I_F = 12 Amp, $T_C = 25^oC$)	V_F	–	1.0	1.4	Volts
Reverse Current (rated dc voltage) $T_C = 25^oC$	I_R	–	10	25	μA
$T_C = 100^oC$		–	0.5	3.0	mA

*REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time	t_{rr}				ns
(I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16)		–	150	200	
(I_{FM} = 36 Amp, di/dt = 25 A/μs, Figure 17)		–	200	400	
Reverse Recovery Current (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16)	$I_{RM(REC)}$	–	–	2.0	Amp

*Indicates JEDEC Registered Data for 1N3889 Series.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and readily solderable
POLARITY: Cathode to Case
WEIGHT: 5.6 grams (approximately)
MOUNTING TORQUE: 15 in-lbs max.

3

FIGURE 1 – FORWARD VOLTAGE

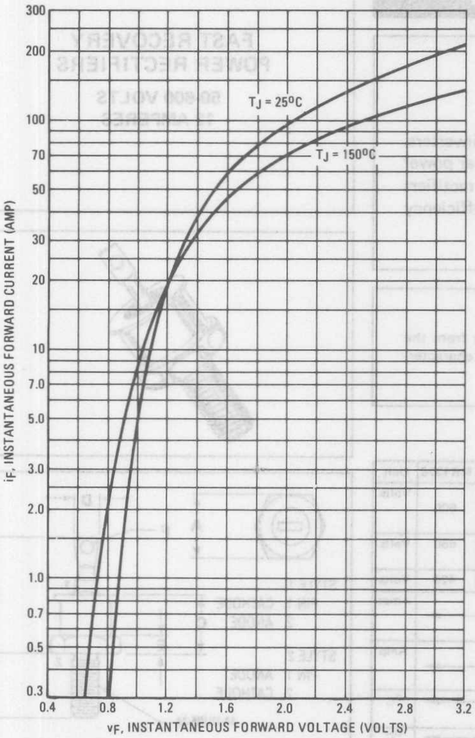
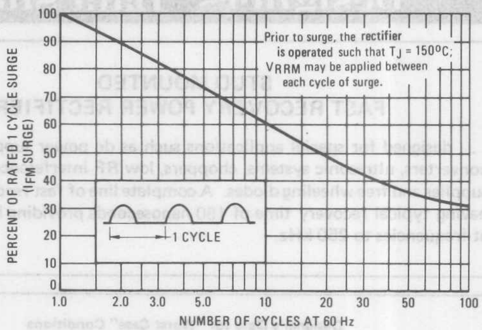
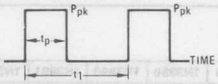


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

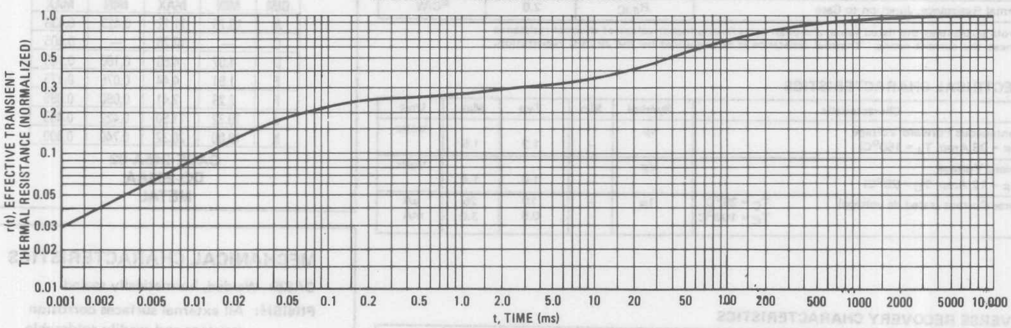
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 3 – THERMAL RESPONSE



SINE WAVE INPUT

FIGURE 4 — FORWARD POWER DISSIPATION

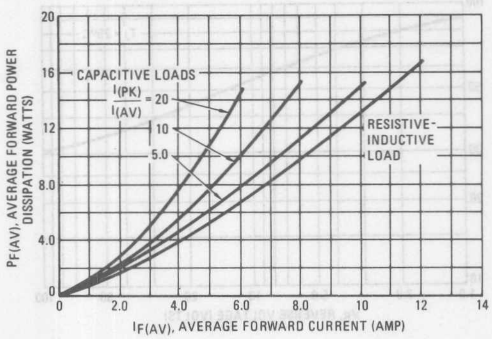


FIGURE 6 — CURRENT DERATING

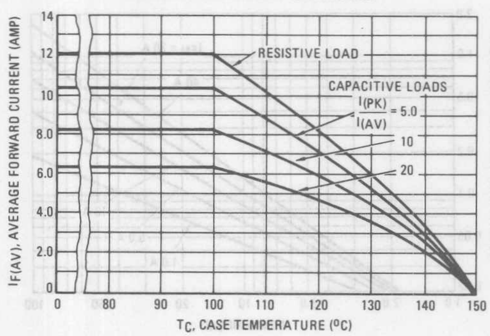
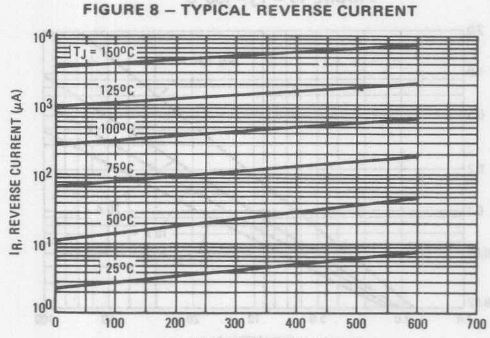


FIGURE 8 — TYPICAL REVERSE CURRENT



SQUARE WAVE INPUT

FIGURE 5 — FORWARD POWER DISSIPATION

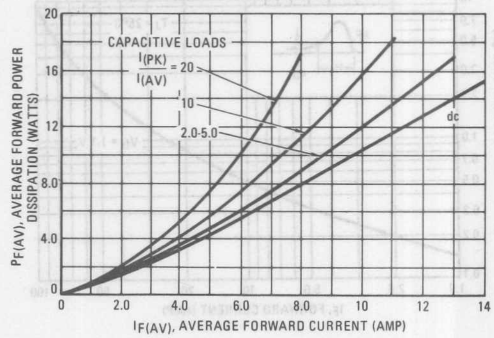


FIGURE 7 — CURRENT DERATING

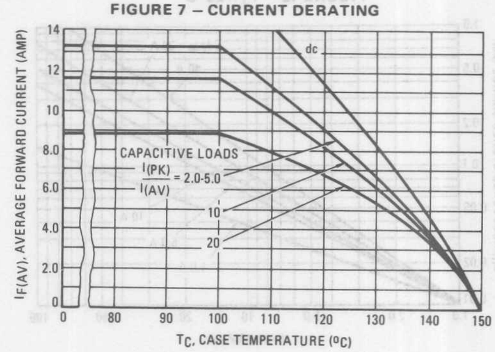
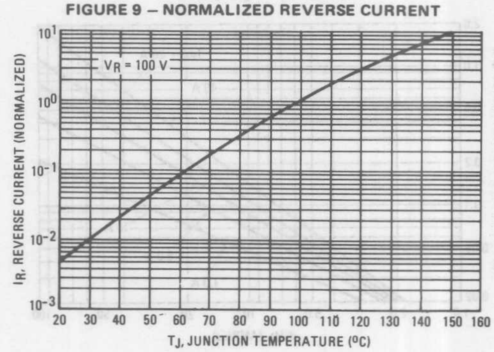


FIGURE 9 — NORMALIZED REVERSE CURRENT



3

3

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 – FORWARD RECOVERY TIME

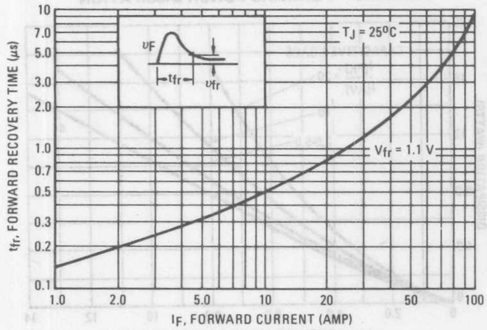
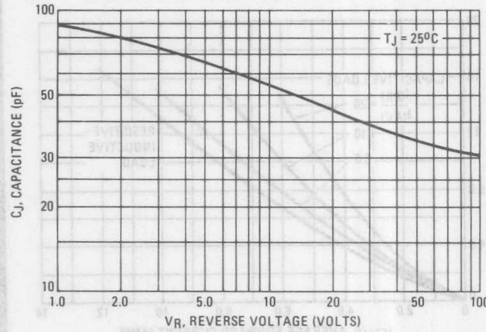


FIGURE 11 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 – $T_J = 25^oC$

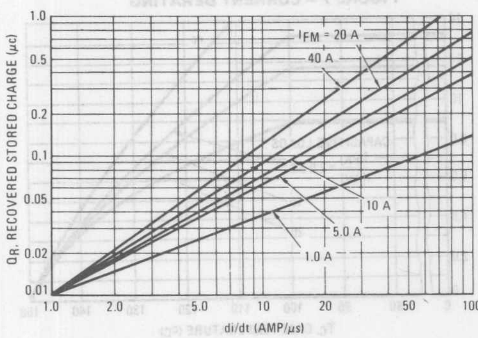


FIGURE 13 – $T_J = 75^oC$

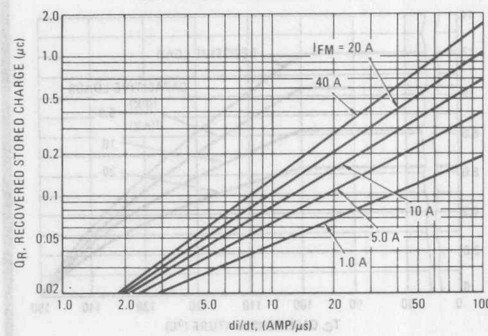


FIGURE 14 – $T_J = 100^oC$

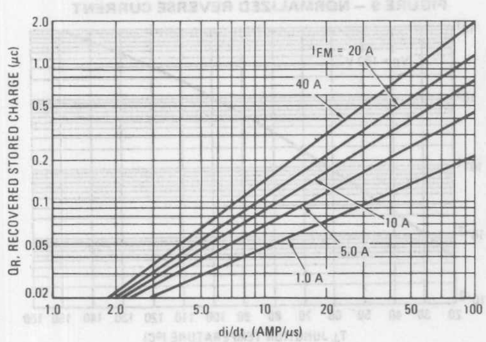


FIGURE 15 – $T_J = 150^oC$

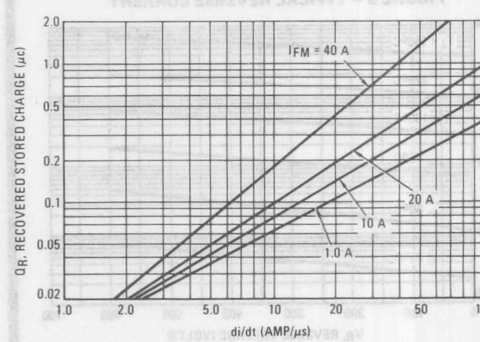
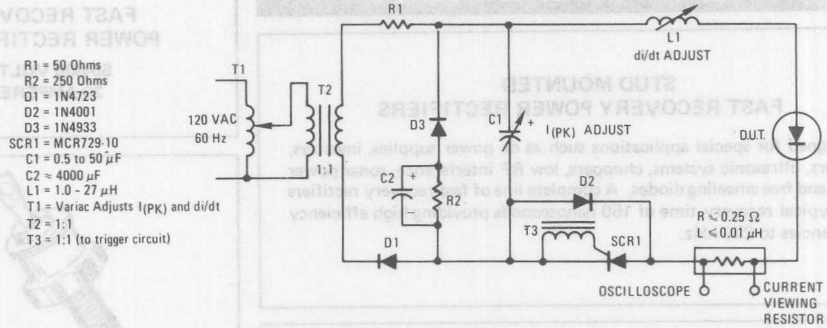


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT



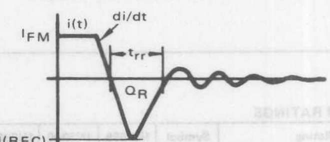
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3899 thru 1N3903
MR1386

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

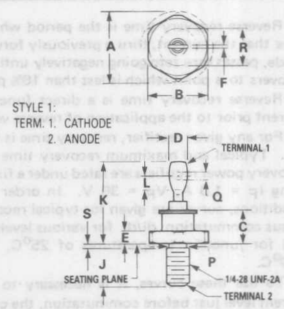
FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
20 AMPERES

3

Designers Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.



STYLE 1:
TERM. 1. CATHODE
2. ANODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	–	20.07	–	0.790
B	16.94	17.45	0.669	0.687
C	–	11.43	–	0.450
D	–	9.53	–	0.375
E	2.92	5.08	0.115	0.200
F	–	2.03	–	0.080
J	10.72	11.51	0.422	0.453
K	19.05	25.40	0.750	1.00
L	3.96	–	0.156	–
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	–	16.94	–	0.667
S	–	2.26	–	0.089

CASE 42A-01
DO-203AB
METAL

*MAXIMUM RATINGS

Rating	Symbol	1N3899	1N3900	1N3901	1N3902	1N3903	MR1386	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	350	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100°C$)	I_O	20						Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	250 (one cycle)						Amps
Operating Junction Temperature Range	T_J	-65 to +150						°C
Storage Temperature Range	T_{stg}	-65 to +175						°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.8	°C/W

*ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage ($I_F = 63$ Amp, $T_J = 150°C$)	v_F	–	1.2	1.5	Volts
Forward Voltage ($I_F = 20$ Amp, $T_C = 25°C$)	V_F	–	1.1	1.4	Volts
Reverse Current (rated dc voltage) $T_C = 25°C$ $T_C = 100°C$	I_R	– –	10 0.5	50 6.0	μA mA

*REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 16) ($I_{FM} = 36$ Amp, di/dt = 25 A/μs, Figure 17)	t_{rr}	 – –	 150 200	 200 400	ns
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 16)	$I_{RM(REC)}$	–	–	3.0	Amp

*Indicates JEDEC Registered Data for 1N3899 Series.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and readily solderable

POLARITY: Cathode to Case

WEIGHT: 17 Grams (Approximately)

MOUNTING TORQUE: 25 in-lbs max.

FIGURE 1 – FORWARD VOLTAGE

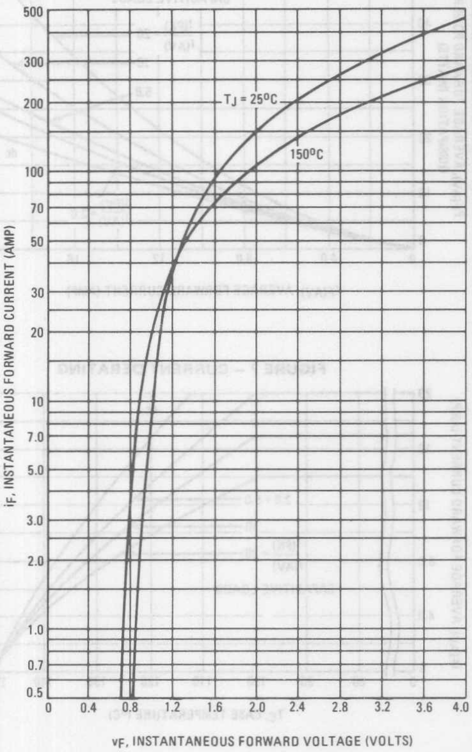
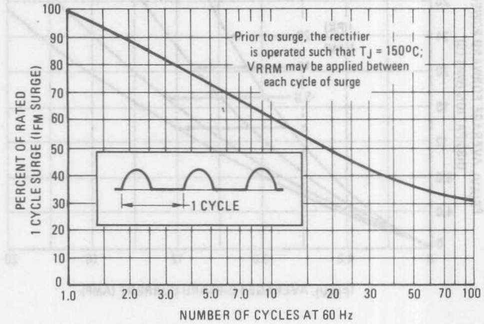
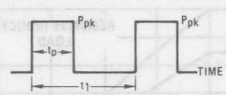


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

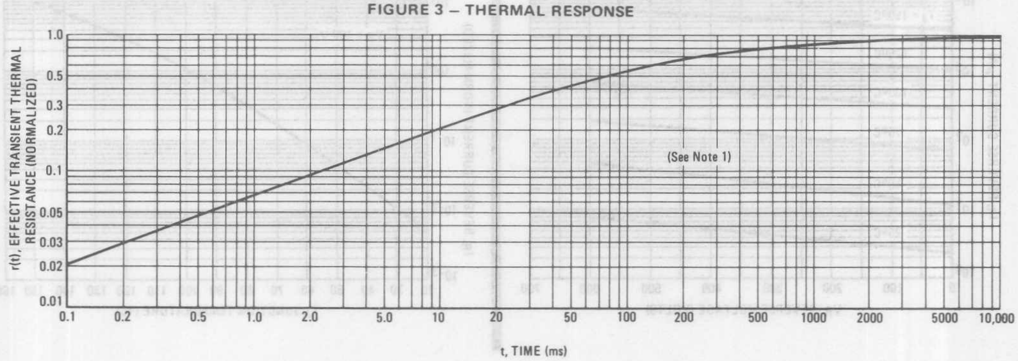
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

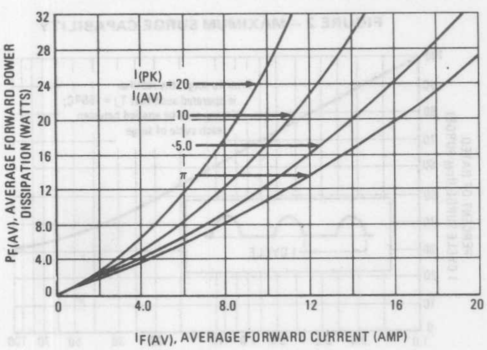
FIGURE 3 – THERMAL RESPONSE



3

SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION



SQUARE WAVE INPUT

FIGURE 5 – FORWARD POWER DISSIPATION

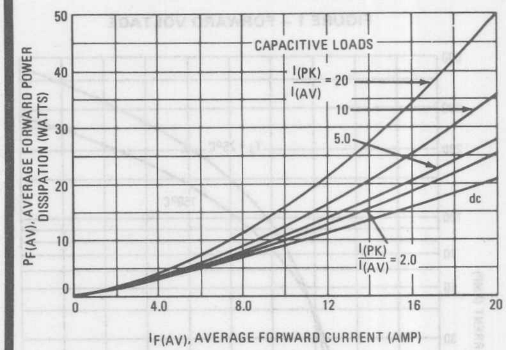


FIGURE 6 – CURRENT DERATING

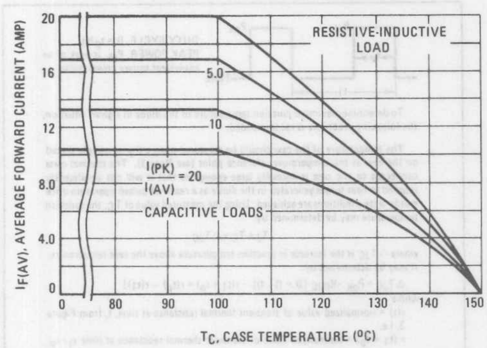


FIGURE 7 – CURRENT DERATING

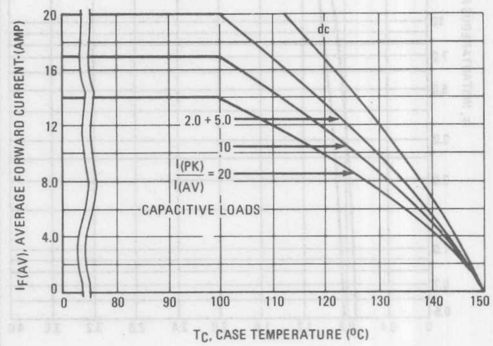


FIGURE 8 – TYPICAL REVERSE CURRENT

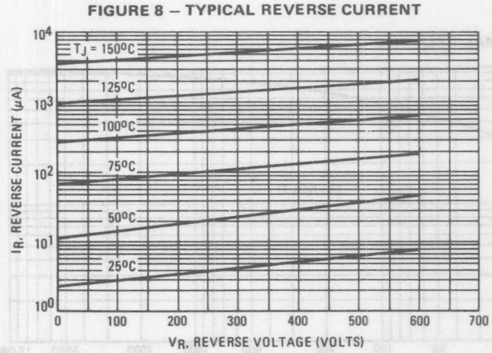
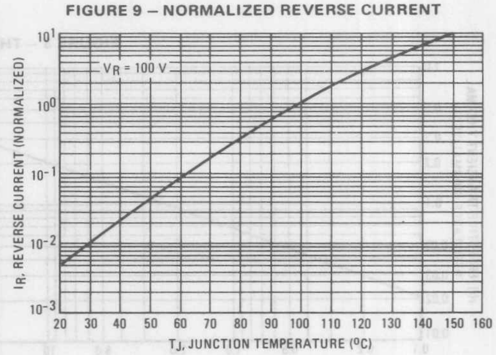


FIGURE 9 – NORMALIZED REVERSE CURRENT



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 – FORWARD RECOVERY TIME

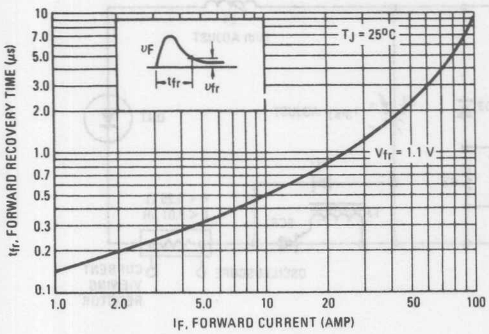
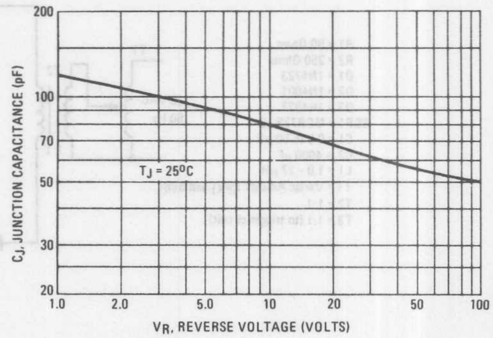


FIGURE 11 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 – $T_J = 25^oC$

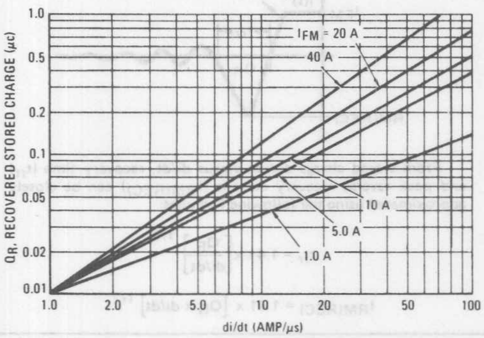
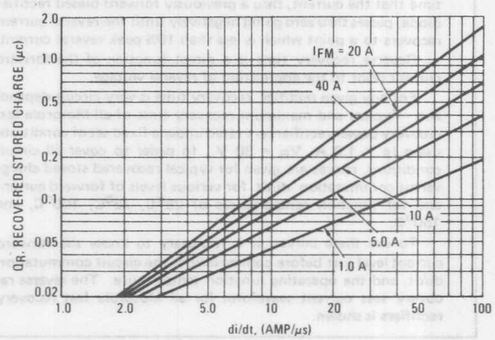


FIGURE 13 – $T_J = 75^oC$



STORED CHARGE DATA

FIGURE 14 – $T_J = 100^oC$

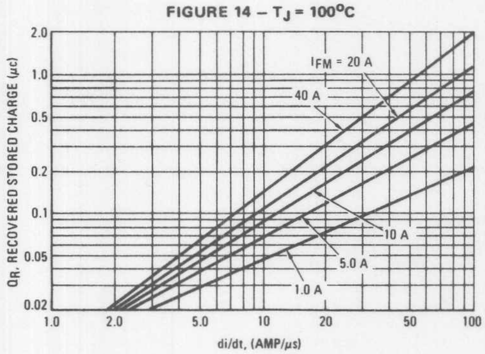


FIGURE 15 – $T_J = 150^oC$

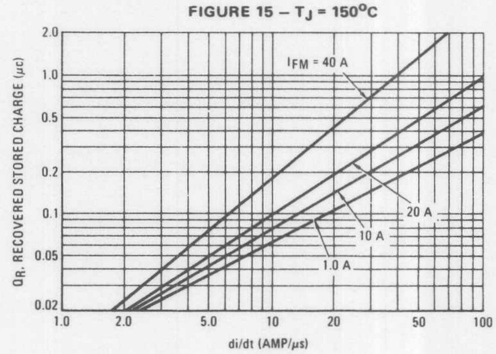
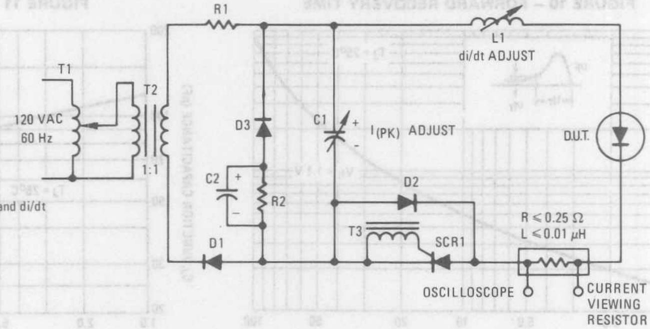


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT

R1 = 50 Ohms
R2 = 250 Ohms
D1 = 1N4723
D2 = 1N4001
D3 = 1N4933
SCR1 = MCR729-10
C1 = 0.5 to 50 μF
C2 ≈ 4000 μF
L1 = 1.0 - 27 μH
T1 = Variac Adjusts $I_{(PK)}$ and di/dt
T2 = 1:1
T3 = 1:1 (to trigger circuit)



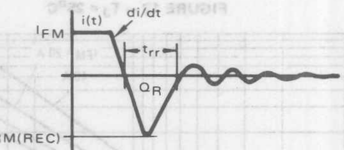
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3909 thru 1N3913
MR1396

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

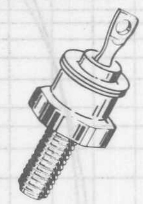
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

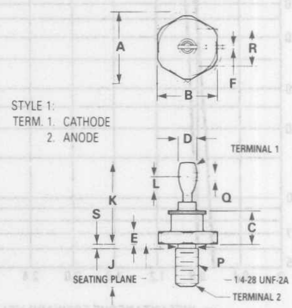
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics -- are given to facilitate "worst case" design.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
30 AMPERES





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	20.07	—	0.790
B	16.94	17.45	0.669	0.687
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	19.05	25.40	0.750	1.00
L	3.96	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	16.94	—	0.667
S	—	2.26	—	0.089

CASE 42A-01
DO-203AB
METAL

*MAXIMUM RATINGS

Rating	Symbol	1N3909	1N3910	1N3911	1N3912	1N3913	MR1396	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	350	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100°C$)	I_O	← 30 →						Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	← 300 →						Amp
Operating Junction Temperature Range	T_J	← -65 to +150 →						°C
Storage Temperature Range	T_{stg}	← -65 to +175 →						°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.2	°C/W

*ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (i_F = 93 Amp, T_J = 150°C)	v_F	—	1.2	1.5	Volts
Forward Voltage (I_F = 30 Amp, T_C = 25°C)	V_F	—	1.1	1.4	Volts
Reverse Current (rated dc voltage) T_C = 25°C T_C = 100°C	I_R	— —	10 0.5	25 1.0	μA mA

*REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16) (I_{FM} = 36 Amp, di/dt = 25 A/μs, Figure 17)	t_{rr}	 — —	 150 200	 200 400	ns
Reverse Recovery Current (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16)	$I_{RM(REC)}$	—	1.5	2.0	Amp

*Indicates JEDEC Registered Data for 1N3909 Series.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and readily solderable

POLARITY: Cathode to Case

WEIGHT: 17 Grams (Approximately)

MOUNTING TORQUE: 25 in-lbs max.

FIGURE 1 – FORWARD VOLTAGE

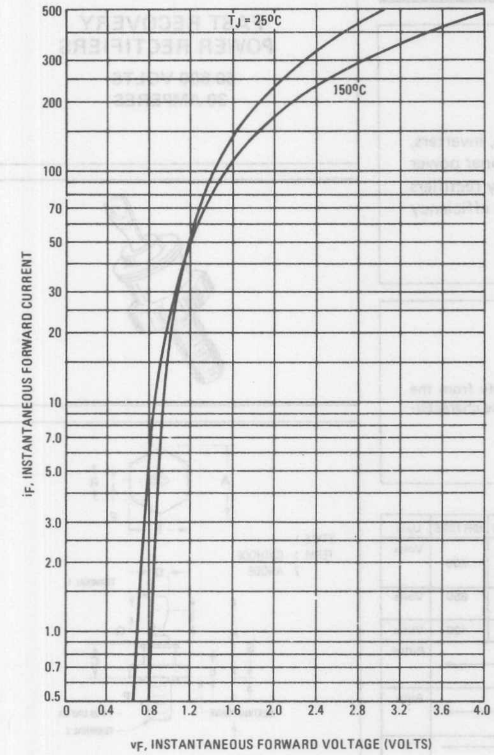
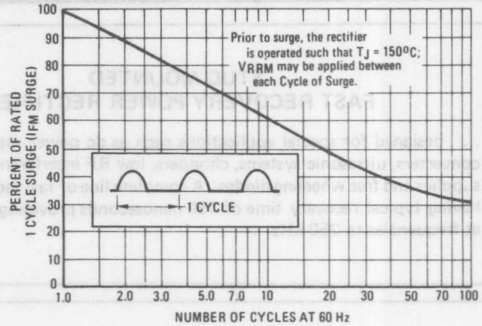
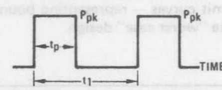


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

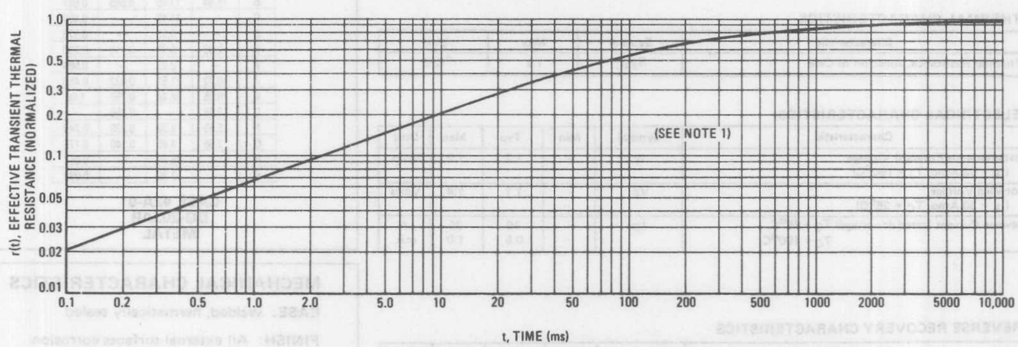
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 3 – THERMAL RESPONSE



SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION

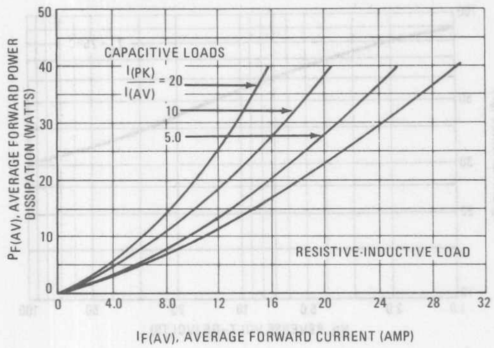


FIGURE 6 – CURRENT DERATING

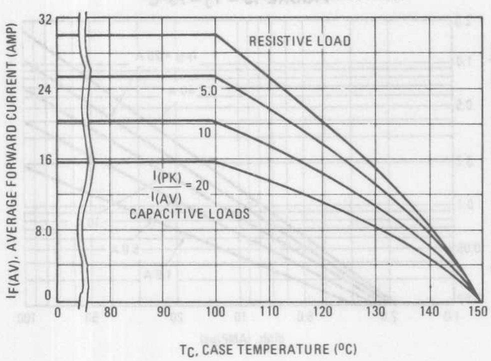
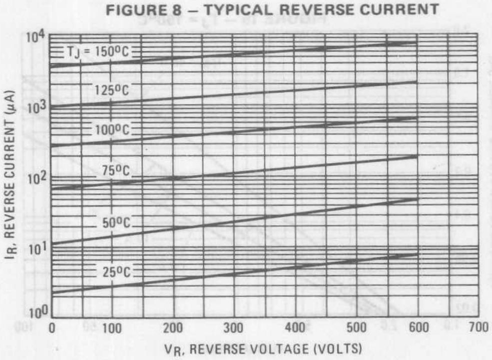


FIGURE 8 – TYPICAL REVERSE CURRENT



SQUARE WAVE INPUT

FIGURE 5 – FORWARD POWER DISSIPATION

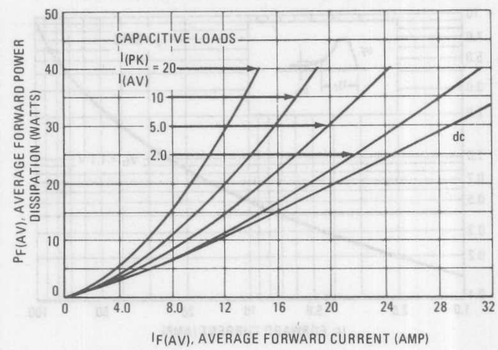


FIGURE 7 – CURRENT DERATING

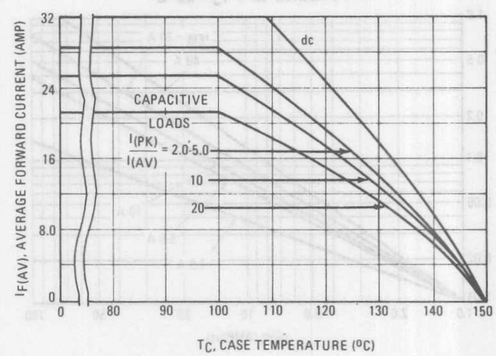
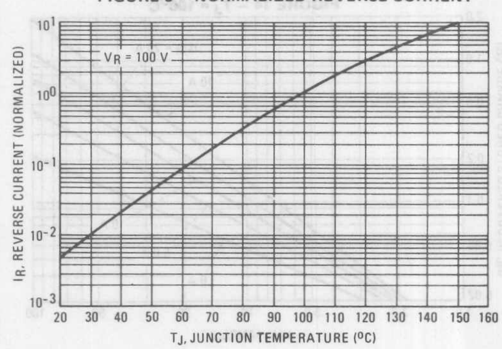


FIGURE 9 – NORMALIZED REVERSE CURRENT



3

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 — FORWARD RECOVERY TIME

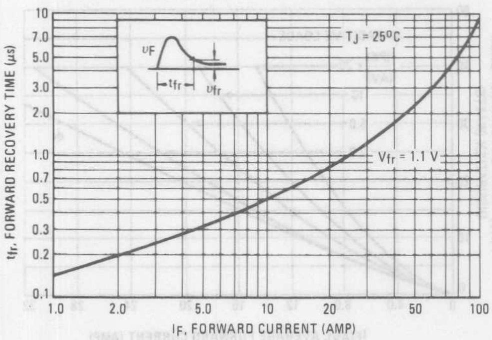
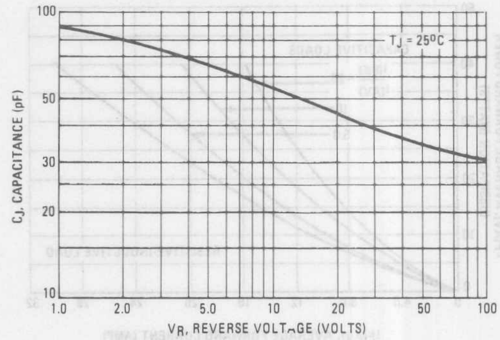


FIGURE 11 — JUNCTION CAPACITANCE



3

TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 — $T_J = 25^oC$

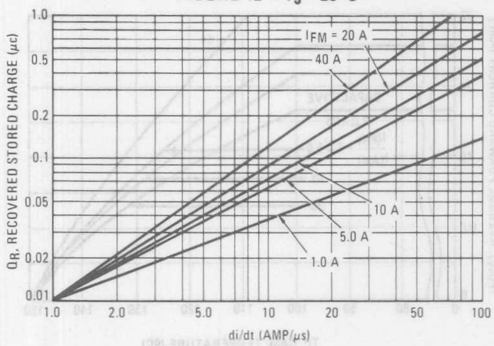


FIGURE 13 — $T_J = 75^oC$

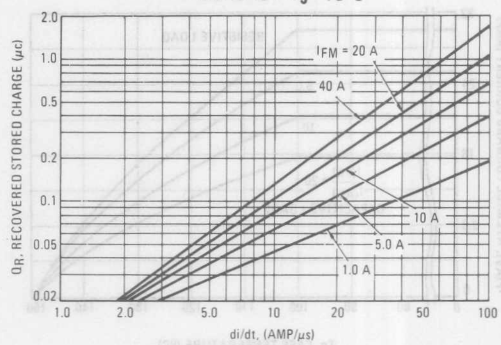


FIGURE 14 — $T_J = 100^oC$

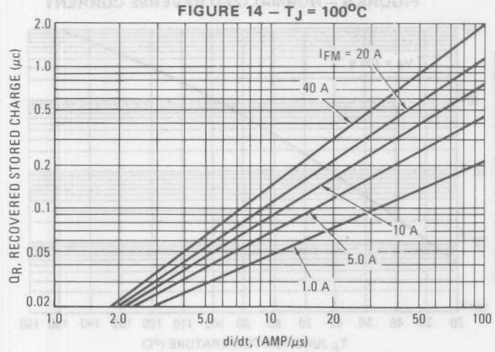


FIGURE 15 — $T_J = 150^oC$

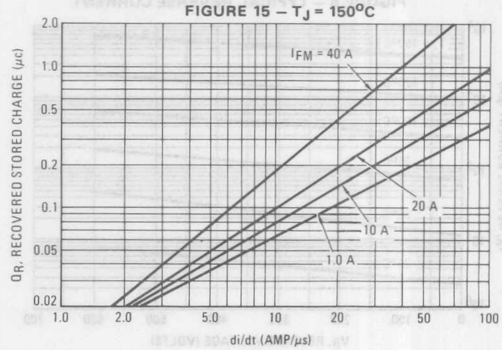
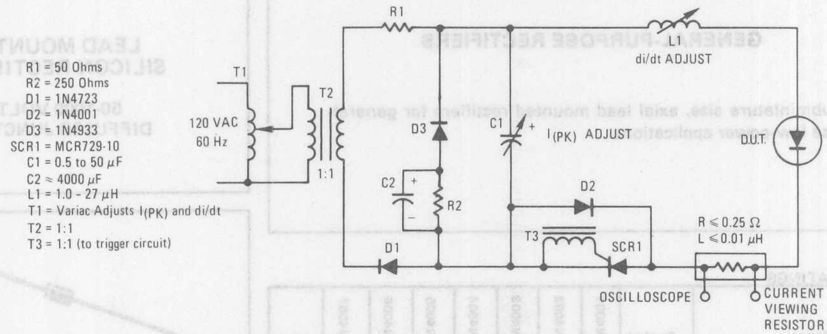


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT



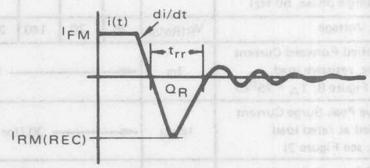
NOTE 3

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

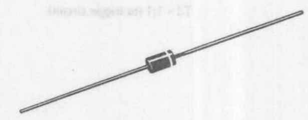
1N4001 thru 1N4007

GENERAL-PURPOSE RECTIFIERS

. . . subminiature size, axial lead mounted rectifiers for general-purpose low-power applications.

LEAD MOUNTED SILICON RECTIFIERS

50-1000 VOLTS
DIFFUSED JUNCTION



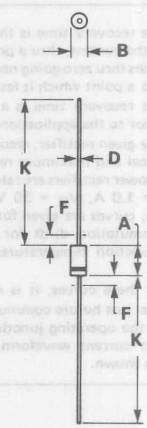
***MAXIMUM RATINGS**

Rating	Symbol	1N4001	1N4002	1N4003	1N4004	1N4005	1N4006	1N4007	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage (halfwave, single phase, 60 Hz)	V_{RSM}	60	120	240	480	720	1000	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (single phase, resistive load, 60 Hz, see Figure 8, $T_A = 75°C$)	I_O	← 1.0 →							Amp
Non-Repetitive Peak Surge Current (surge applied at rated load conditions, see Figure 2)	I_{FSM}	← 30 (for 1 cycle) →							Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +175 →							°C

***ELECTRICAL CHARACTERISTICS**

Characteristic and Conditions	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage Drop ($i_F = 1.0$ Amp, $T_J = 25°C$) Figure 1	v_F	0.93	1.1	Volts
Maximum Full-Cycle Average Forward Voltage Drop ($I_O = 1.0$ Amp, $T_L = 75°C$, 1 inch leads)	$V_{F(AV)}$	–	0.8	Volts
Maximum Reverse Current (rated dc voltage) $T_J = 25°C$ / $T_J = 100°C$	I_R	0.05 1.0	10 50	μA
Maximum Full-Cycle Average Reverse Current ($I_O = 1.0$ Amp, $T_L = 75°C$, 1 inch leads	$I_{R(AV)}$	–	30	μA

*Indicates JEDEC Registered Data.



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	—	1.27	—	0.050
K	27.94	—	1.100	—

CASE 59-03
DO-41
PLASTIC

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 350°C, 3/8" from case for 10 seconds at 5 lbs. tension

FINISH: All external surfaces are corrosion-resistant, leads are readily solderable

POLARITY: Cathode indicated by color band

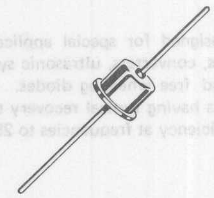
WEIGHT: 0.40 Grams (approximately)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4719 thru 1N4725

SILICON RECTIFIERS

3.0 AMPERES
50-1000 VOLTS
DIFFUSED JUNCTION



LEAD MOUNTED POWER RECTIFIERS

. . . having low forward voltage drop and hermetic metal packages. High surge current capability and good thermal characteristics provide reliable operation.

- $R_{\theta JA}$ = 30°C/W

***MAXIMUM RATINGS** (Both Package Types) T_A = 25°C unless otherwise noted.

Rating	Symbol	1N4719	1N4720	1N4721	1N4722	1N4723	1N4724	1N4725	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Nonrepetitive Peak Reverse Voltage (one half-wave, single phase, 60 cycle peak)	V_{RSM}	100	200	300	500	720	1000	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (single phase, resistive load, 60 Hz, T_A = 75°C)	I_O	← 3.0 →							Amp
Nonrepetitive Peak Surge Current (superimposed on rated current at rated voltage, T_A = 75°C)	I_{FSM}	← 300 (for 1/2 cycle) →							Amp
Operating and Case Temperature	T_J, T_{stg}	← −65 to +175 →							°C

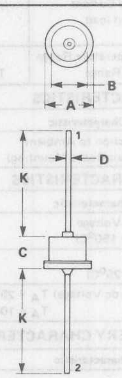
ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Max Limit	Unit
*Instantaneous Forward Voltage (i_F = 3.0 A, T_J = 75°C, Half Wave Rectifier)	v_F	1.0	Volts
*Full Cycle Average Reverse Current (I_O = 3.0 Amps and Rated V_R, T_A = 75°C, Half Wave Rectifier)	$I_{R(AV)}$	1.5	mA
DC Reverse Current (Rated V_R, T_A = 25°C)	I_R	0.5	mA

*Indicates JEDEC Registered Data.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed construction
FINISH: All external surfaces corrosion-resistant and leads readily solderable.
POLARITY: CATHODE TO CASE
MOUNTING POSITIONS: Any.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	11.43	—	0.450
B	—	8.89	—	0.350
C	—	7.62	—	0.300
D	1.17	1.42	0.046	0.056
K	24.89	—	0.980	—

CASE 60-1
METAL

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4933 thru 1N4937

Designers Data Sheet

AXIAL-LEAD, FAST-RECOVERY RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

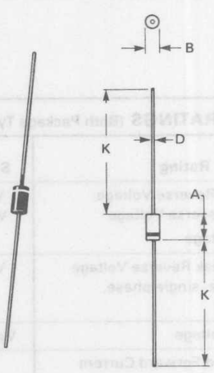
FAST RECOVERY RECTIFIERS

50–600 VOLTS
1 AMPERE

3

Designer's Data for "Worst Case" Conditions

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing device characteristics boundaries — are given to facilitate "worst case" design.



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04
PLASTIC

***MAXIMUM RATINGS**

Rating	Symbol	1N4933	1N4934	1N4935	1N4936	1N4937	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_A = 75°C$)	I_O	←	—	1.0	—	→	Amp
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	←	—	30	—	→	Amps
Operating Junction Temperature Range	T_J	←	—	−65 to +150	—	→	°C
Storage Temperature Range	T_{stg}	←	—	−65 to +175	—	→	°C

***THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Typical Printed Circuit Board Mounting)	$R_{\theta JA}$	65	°C/W

***ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Typ	Max	Unit
*Instantaneous Forward Voltage ($i_F = 3.14$ Amp, $T_J = 150°C$)	v_F	–	1.0	1.2	Volts
Forward Voltage ($I_F = 1.0$ Amp, $T_A = 25°C$)	V_F	–	1.0	1.2	Volts
*Reverse Current (Rated dc Voltage) $T_A = 25°C$	I_R	–	1.0	5.0	μA
$T_A = 100°C$		–	50	100	

***REVERSE RECOVERY CHARACTERISTICS**

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time ($I_F = 1.0$ Amp to $V_R = 30$ Vdc) (Figure 21)	t_{rr}	–	150	200	ns
($I_{FM} = 15$ Amp, $di/dt = 10A/\mu s$ (Figure 22)		–	175	300	
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc) (Figure 21)	$I_{RM(REC)}$	–	1.0	2.0	Amp

*Indicates JEDEC Registered Data

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic
FINISH: External leads are readily solderable
POLARITY: Cathode indicated by polarity band
WEIGHT: 0.4 Gram (approximately)

FIGURE 1 – FORWARD VOLTAGE

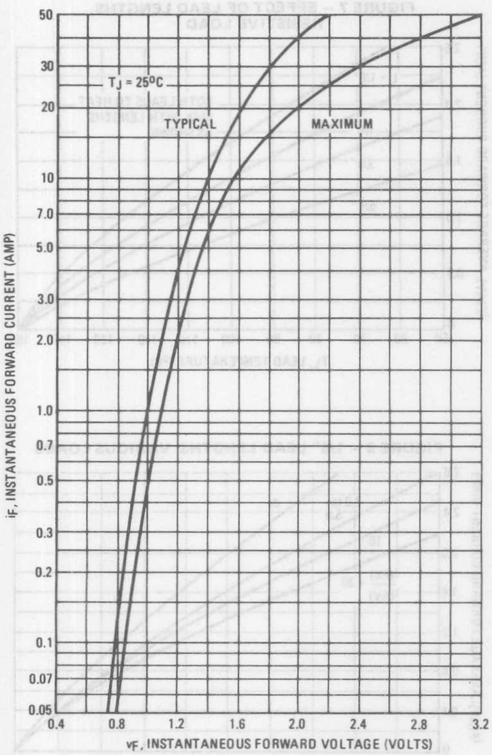


FIGURE 2 – MAXIMUM SURGE CAPABILITY

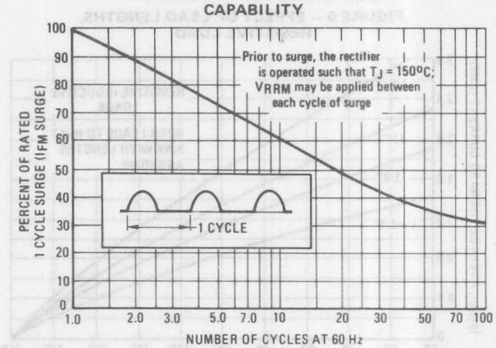
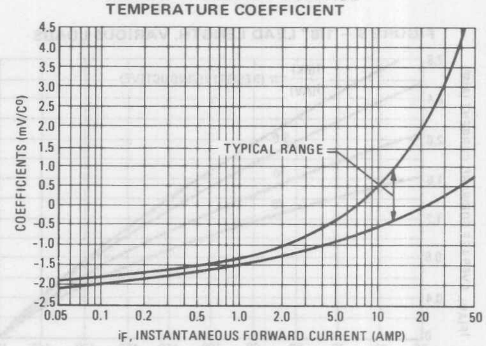
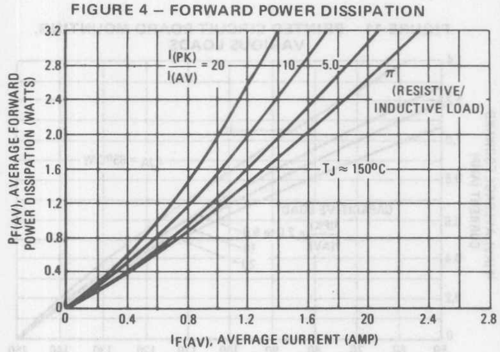


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT



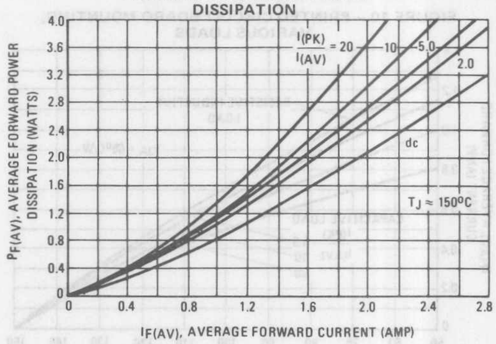
SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION



SQUARE WAVE INPUT

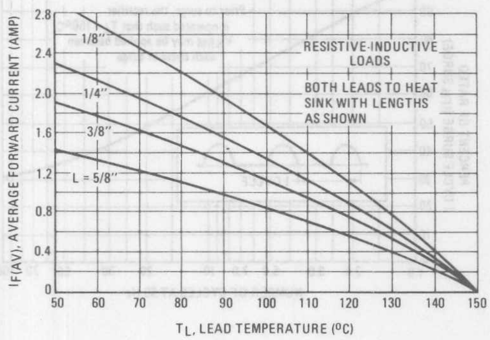
FIGURE 5 – FORWARD POWER DISSIPATION



MAXIMUM CURRENT RATINGS

SINE WAVE INPUT

FIGURE 6 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD



SQUARE WAVE INPUT

FIGURE 7 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

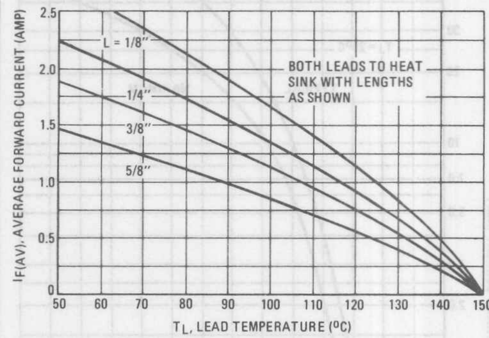


FIGURE 8 – 1/8" LEAD LENGTH, VARIOUS LOADS

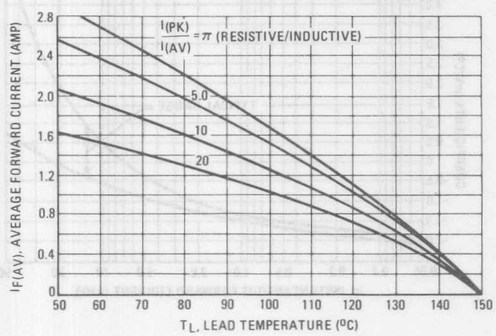


FIGURE 9 – 1/8" LEAD LENGTHS, VARIOUS LOADS

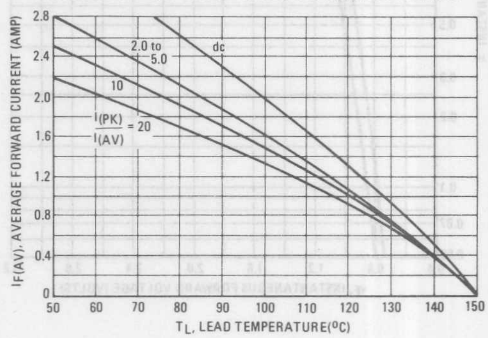


FIGURE 10 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

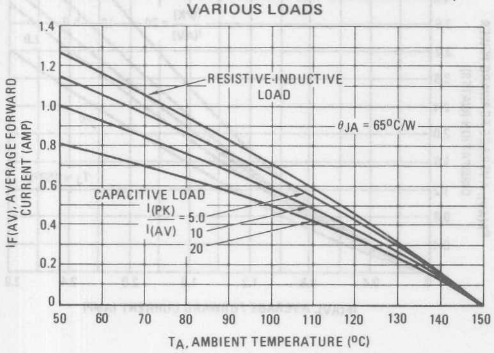


FIGURE 11 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

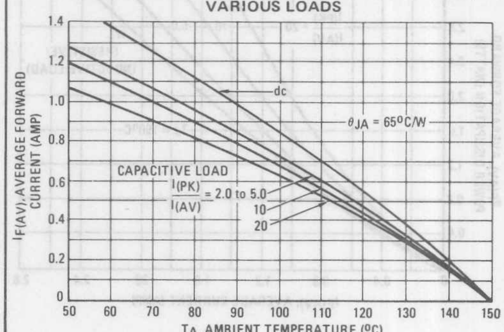


FIGURE 12 – THERMAL RESPONSE

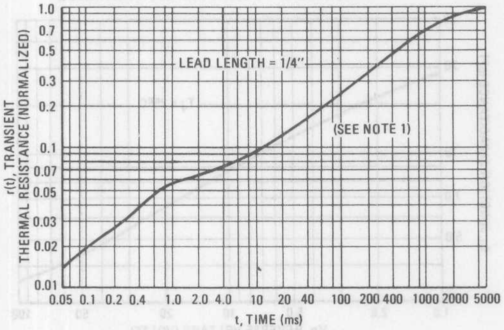
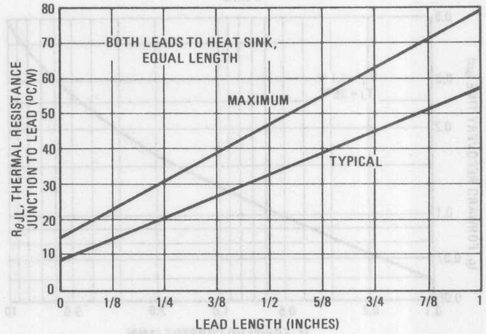
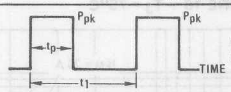


FIGURE 13 – THERMAL RESISTANCE



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

NOTE 2

Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR θ_{JA} IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	65	72	82	92	°C/W
2	74	81	91	101	°C/W
3	40				°C/W

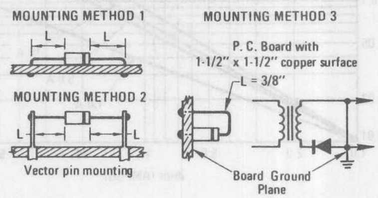
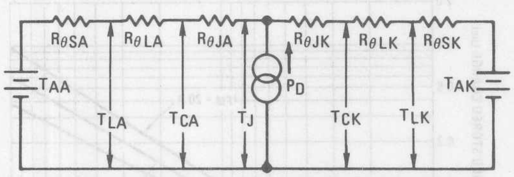


FIGURE 14 – THERMAL CIRCUIT MODEL
(For Heat Conduction Through The Leads)



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature
T_L = Lead Temperature
T_C = Case Temperature
T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Power Dissipation
(Subscripts A and K refer to anode and cathode sides respectively.)

Values for thermal resistance components are:
$R_{\theta L}$ = 112°C/W/IN. Typically and 128°C/W/IN Maximum
$R_{\theta J}$ = 18°C/W Typically and 30°C/W Maximum

The maximum lead temperature may be calculated as follows:

$$T_L = 150^\circ - \Delta T_{JL}$$

ΔT_{JL} can be calculated as shown in NOTE 1 or it may be approximated as follows:

$\Delta T_{JL} \approx R_{\theta JL} \bullet P_F$; P_F may be formulated for sine-wave operation from Figure 3 or from Figure 4 for square-wave operation.

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 15 – FORWARD RECOVERY TIME

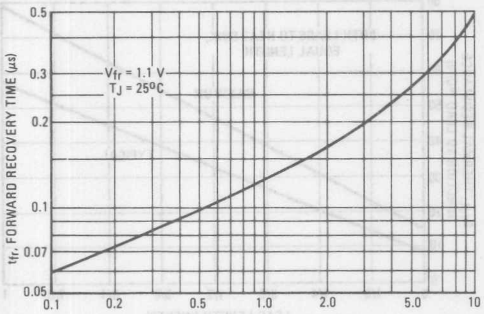
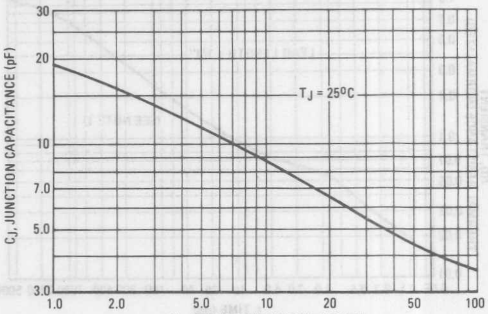


FIGURE 16 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGED DATA

FIGURE 17 – T_J = 25°C

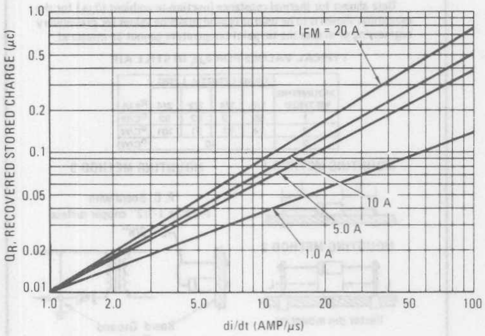


FIGURE 18 – T_J = 75°C

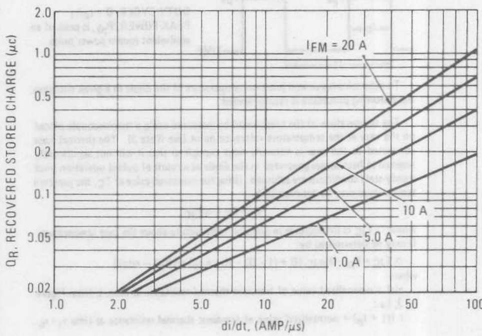


FIGURE 19 – T_J = 100°C

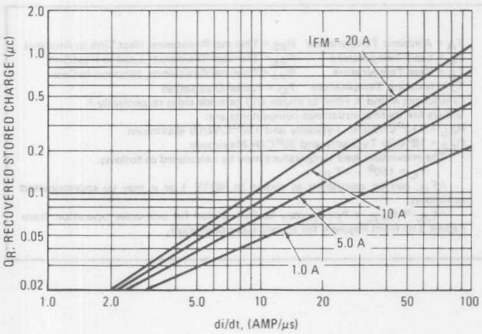


FIGURE 20 – T_J = 150°C

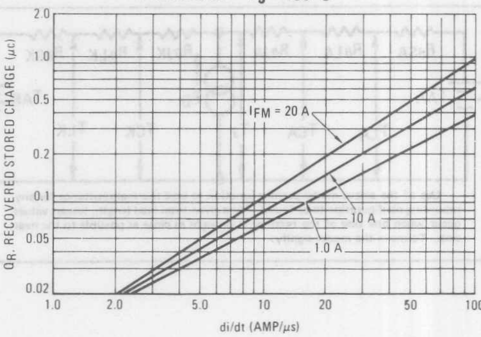
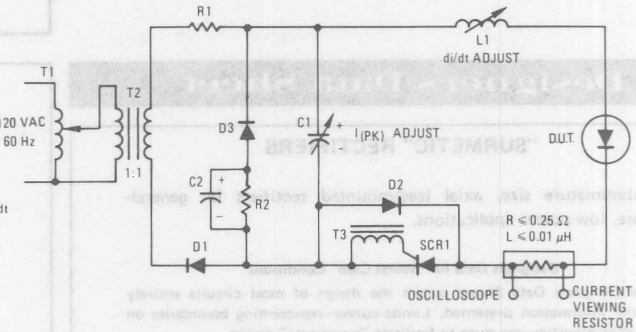


FIGURE 21 — JEDEC REVERSE RECOVERY CIRCUIT

R1 = 50 Ohms
R2 = 250 Ohms
D1 = 1N4723
D2 = 1N4001
D3 = 1N4934
SCR1 = MCR729-10
C1 = 0.5 to 50 μF
C2 ≈ 4000 μF
L1 = 1.0 - 27 μH
T1 = Variac Adjusts $I_{(PK)}$ and di/dt
T2 = 1:1
T3 = 1:1 (to trigger circuit)



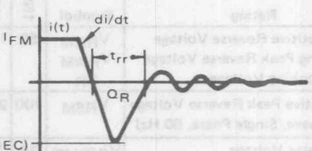
NOTE 3

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

FIGURE 22 — TYPICAL REVERSE LEAKAGE

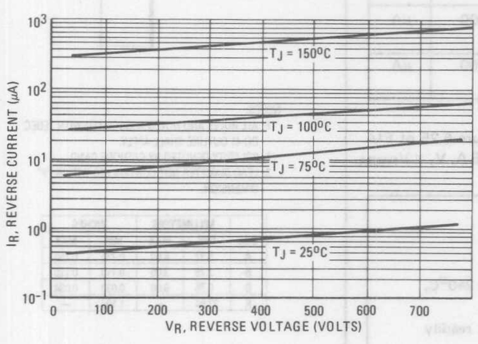
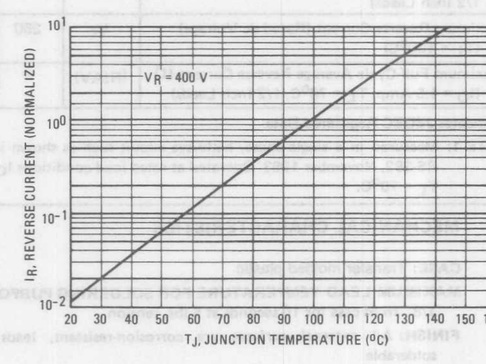


FIGURE 23 — NORMALIZED REVERSE CURRENT



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5391 thru 1N5399

Designers Data Sheet

"SURMETIC" RECTIFIERS

. . . subminiature size, axial lead-mounted rectifiers for general-purpose, low-power applications.

Designers Data for "Worst Case" Conditions

The Designers Data Sheets permit the design of most circuits entirely from the information presented. Limits curves—representing boundaries on device characteristics—are given to facilitate "worst-case" design.

LEAD-MOUNTED SILICON RECTIFIERS

50–1000 VOLTS
DIFFUSED JUNCTION

3

*MAXIMUM RATINGS

Rating	Symbol	1N5391	1N5392	1N5393	1N5395	1N5397	1N5398	1N5399	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Nonrepetitive Peak Reverse Voltage (Halfwave, Single Phase, 60 Hz)	V_{RSM}	100	200	300	525	800	1000	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (Single Phase, Resistive Load, 60 Hz, $T_L = 70°C$, 1/2" From Body)	I_O	← 1.5 →							Amp
Nonrepetitive Peak Surge Current (Surge Applied at Rated Load Conditions, See Figure 2)	I_{FSM}	← 50 (for 1 cycle) →							Amp
Storage Temperature Range	T_{stg}	← −65 to +175 →							°C
Operating Temperature Range	T_L	← −65 to +170 →							°C
DC Blocking Voltage Temperature	T_L	← 150 →							°C

*ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage Drop ($i_F = 4.7$ Amp Peak, $T_L = 170°C$, 1/2 Inch Leads)	v_F	–	1.4	Volts
Maximum Reverse Current (Rated dc Voltage) ($T_L = 150°C$)	I_R	250	300	μA
Maximum Full-Cycle Average Reverse Current (1) ($I_O = 1.5$ Amp, $T_L = 70°C$, 1/2 Inch Leads)	$I_{R(AV)}$	–	300	μA

*Indicates JEDEC Registered Data.

NOTE 1: Measured in a single-phase, halfwave circuit such as shown in Figure 6.25 of EIA RS-282, November 1963. Operated at rated load conditions $I_O = 1.5$ A, $V_r = V_{RWM}$, $T_L = 70°C$.

MECHANICAL CHARACTERISTICS

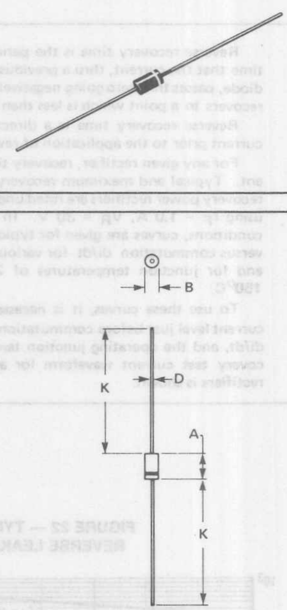
CASE: Transfer molded plastic

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 240°C, 1/8" from case for 10 seconds at 5 lbs. tension

FINISH: All external surfaces are corrosion-resistant, leads are readily solderable

POLARITY: Cathode indicated by color band

WEIGHT: 0.40 grams (approximately)



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04
PLASTIC

FIGURE 1 – FORWARD VOLTAGE

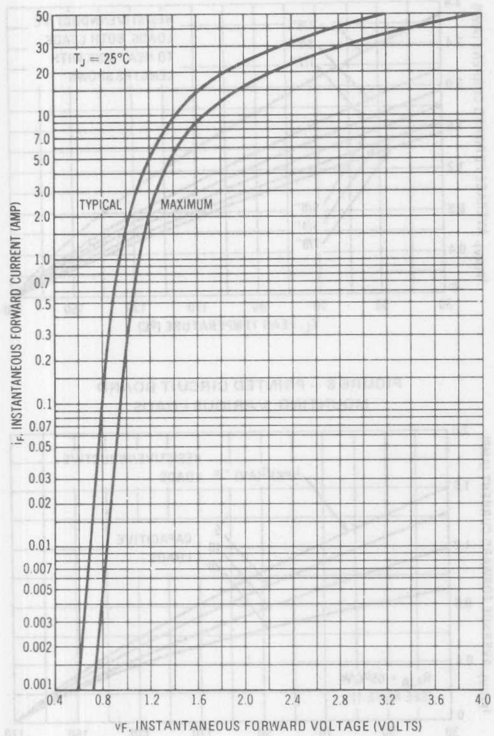


FIGURE 2 – MAXIMUM NONREPETITIVE SURGE CURRENT

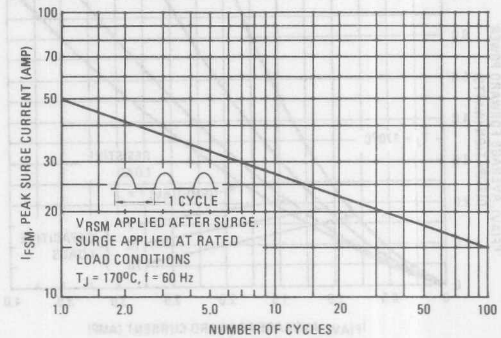


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

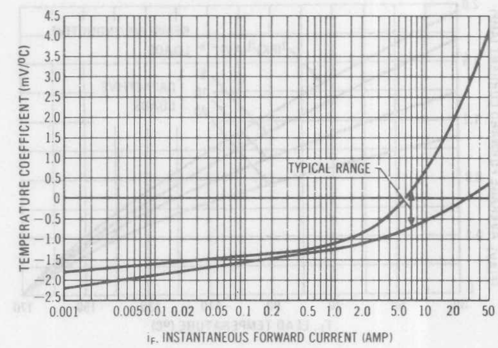
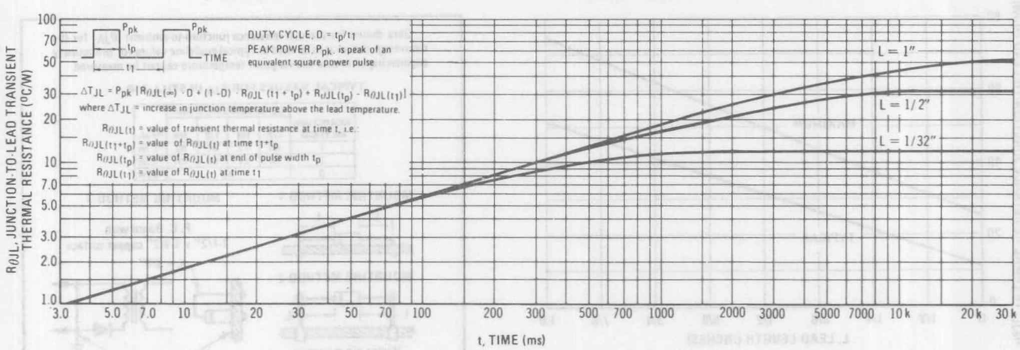


FIGURE 4 – TYPICAL TRANSIENT THERMAL RESISTANCE



The temperature of the lead should be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

3

FIGURE 5 – FORWARD POWER DISSIPATION

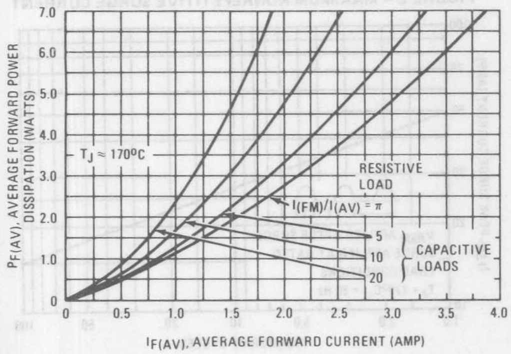


FIGURE 6 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

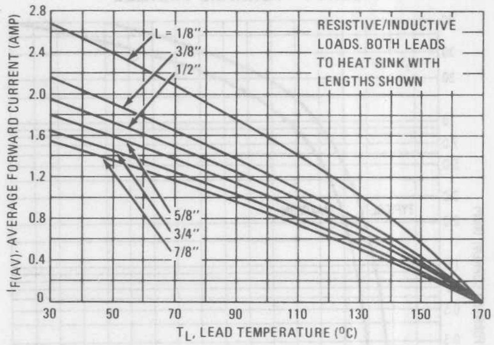


FIGURE 7 – 1/2" LEAD LENGTH, VARIOUS LOADS

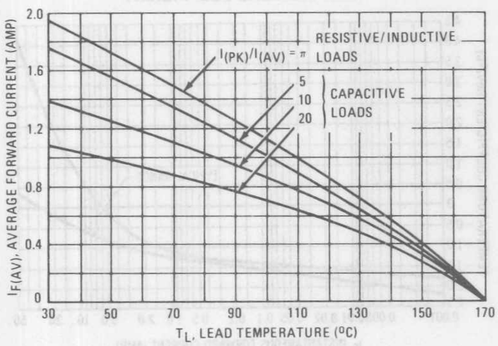


FIGURE 8 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

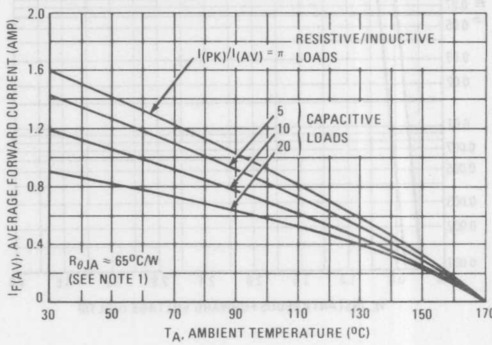
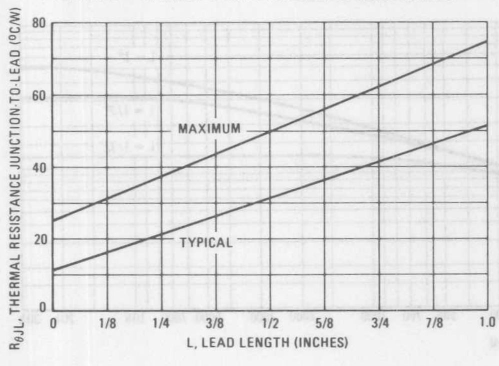


FIGURE 9 – STEADY-STATE THERMAL RESISTANCE



NOTE 1

Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR θ_{JA} IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN) 1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	65	72	82	92	°C/W
2	74	81	91	101	°C/W
3		40			°C/W

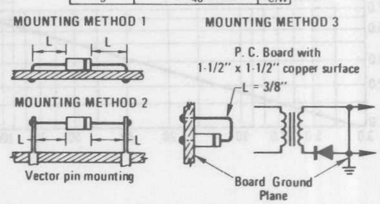


FIGURE 10 – FORWARD RECOVERY TIME

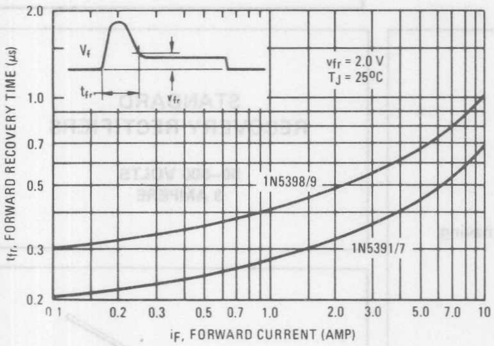


FIGURE 11 – REVERSE RECOVERY TIME

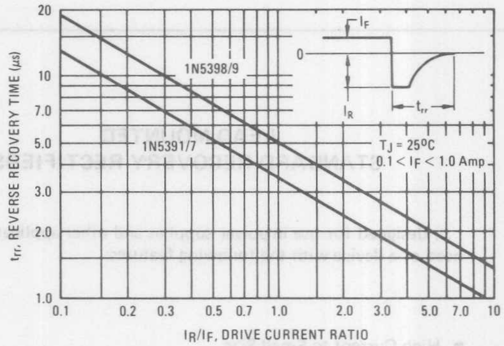


FIGURE 12 – JUNCTION CAPACITANCE

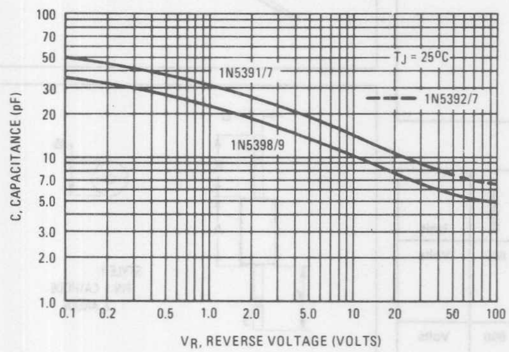


FIGURE 13 – RECTIFICATION WAVEFORM EFFICIENCY FOR SINE WAVE

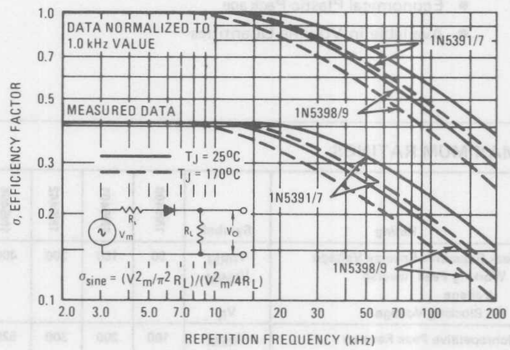
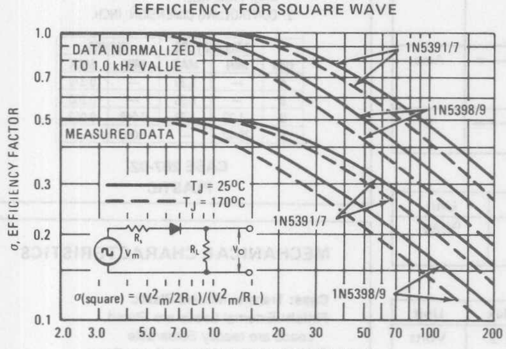


FIGURE 14 – RECTIFICATION WAVEFORM EFFICIENCY FOR SQUARE WAVE



RECTIFIER EFFICIENCY NOTE

The rectification efficiency factor σ shown in Figures 13 and 14 was calculated using the formula:

$$\sigma = \frac{P_{dc}}{P_{rms}} = \frac{\dfrac{V^2{}_{O(dc)}}{R_L}}{\dfrac{V^2{}_{O(rms)}}{R_L}} \bullet 100\% = \frac{V^2{}_{O(dc)}}{V^2{}_{O(ac)} + V^2{}_{O(dc)}} \bullet 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assumed lossless, the maximum theoretical efficiency factor becomes 40%; for a square wave input of amplitude V_m, the efficiency factor becomes 50%. (A full wave circuit has twice these efficiencies).

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 11) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current thereby reducing the value of the efficiency factor σ, as shown in Figures 13 and 14.

It should be emphasized that Figures 13 and 14 show waveform efficiency only; they do not account for diode losses. Data was obtained by measuring the ac component of V_O with a true rms voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for the Figures.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5400 thru 1N5406

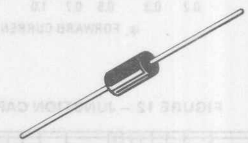
LEAD MOUNTED STANDARD RECOVERY RECTIFIERS

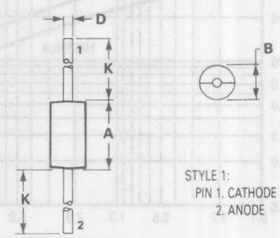
. . . designed for use in power supplies and other applications having need of a device with the following features:

- High Current to Small Size
- High Surge Current Capability
- Low Forward Voltage Drop
- Economical Plastic Package
- Available in Volume Quantities

STANDARD RECOVERY RECTIFIERS

50–600 VOLTS
3 AMPERE





NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	1N5400	1N5401	1N5402	1N5404	1N5406	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	100	200	300	525	800	Volts
Average Rectified Forward Current (Single Phase Resistive Load, (1/2″ Leads, T_L = 105°C)	I_O	← 3.0 →					Amp
Nonrepetitive Peak Surge Current (Surge Applied at Rated Load Conditions)	I_{FSM}	← 200 (one cycle) →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← −65 to +175 →					°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Unit
Thermal Resistance, Junction to Ambient (PC Board Mount, 1/2″ Leads)	$R_{\theta JA}$	53	°C/W

*ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (1) (i_F = 9.4 Amp)	v_F	—	—	1.2	Volts
Average Reverse Current (1) DC Reverse Current (Rated dc Voltage, T_L = 150°C)	$I_{R(AV)}$ I_R	—	—	500 500	μA

*JEDEC Registered Data.

(1) Measured in a single-phase half-wave circuit such as shown in Figure 6.25 of EIA RS-282, November 1963. Operated at rated load conditions T_L = 105°C, I_O = 3.0 A, V_r = V_{RWM}.

MECHANICAL CHARACTERISTICS

Case: Transfer Molded Plastic
Finish: External Leads are Plated, Leads are readily Solderable
Polarity: Indicated by Cathode Band
Weight: 1.1 Grams (Approximately)
Maximum Lead Temperature for **Soldering Purposes:**
240°C, 1/8″ from case for 10 s at 5.0 lb. tension

3

FIGURE 1 – FORWARD VOLTAGE

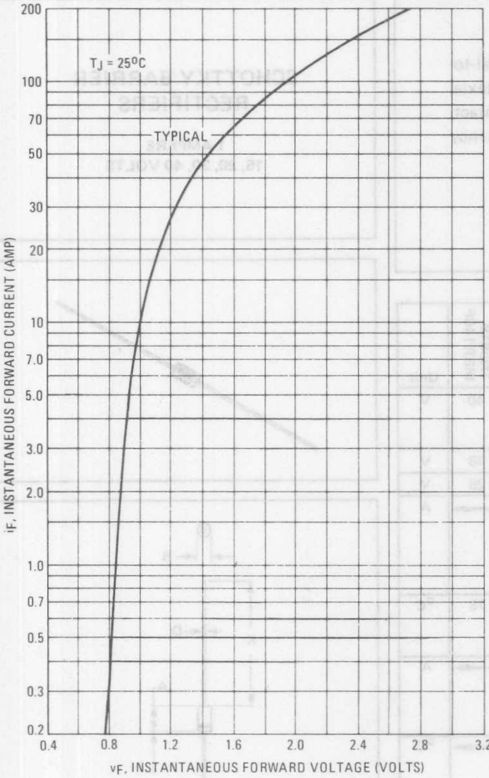


FIGURE 2 – MAXIMUM NONREPETITIVE SURGE CURRENT

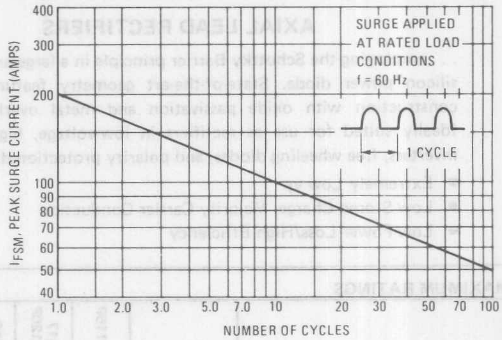
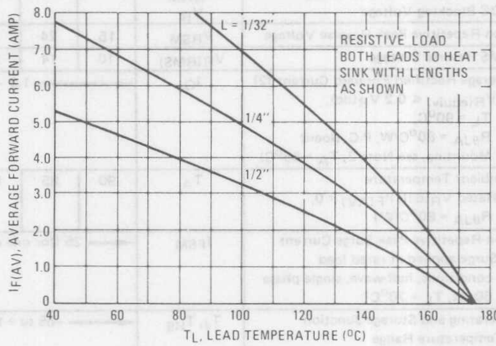


FIGURE 3 – CURRENT DERATING VARIOUS LEAD LENGTHS



NOTE 1 – AMBIENT MOUNTING DATA

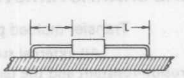
Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3	28				°C/W

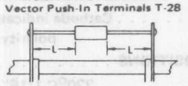
MOUNTING METHOD 1

P.C. Board Where Available Copper Surface area is small.



MOUNTING METHOD 2

Vector Push-In Terminals T-28



MOUNTING METHOD 3

P.C. Board with 1-1/2" x 1-1/2" Copper Surface

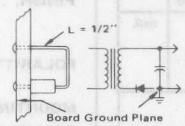
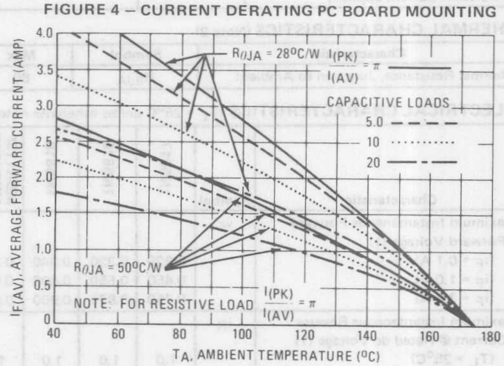


FIGURE 4 – CURRENT DERATING PC BOARD MOUNTING



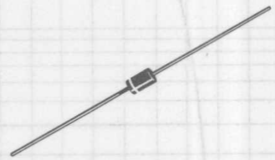
AXIAL LEAD RECTIFIERS

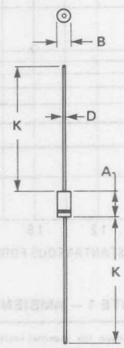
. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency

SCHOTTKY BARRIER RECTIFIERS

1 AMPERE
15, 20, 30, 40 VOLTS





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04 PLASTIC

*MAXIMUM RATINGS

Rating	Symbol	MBR115P	1N5817 MBR120P	1N5818 MBR130P	1N5819 MBR140P	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	15	20	30	40	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	15	24	36	48	V
RMS Reverse Voltage	$V_{R(RMS)}$	10	14	21	28	V
Average Rectified Forward Current (2) ($V_{R(equiv)} \leq 0.2\ V_R(dc)$, $T_L = 90^oC$, $R_{\theta JA} = 80^oC/W$, P.C. Board Mounting, see Note 2, $T_A = 55^oC$)	I_O	← 1.0 →				A
Ambient Temperature (Rated $V_R(dc)$, $P_{F(AV)} = 0$, $R_{\theta JA} = 80^oC/W$)	T_A	90	85	80	75	^oC
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half-wave, single phase 60 Hz, $T_L = 70^oC$)	I_{FSM}	← 25 (for one cycle) →				A
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	T_J, T_{stg}	← −65 to +125 →				^oC
Peak Operating Junction Temperature (Forward Current applied)	$T_{J(pk)}$	← 150 →				^oC

*THERMAL CHARACTERISTICS (Note 2)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	80	$^oC/W$

*ELECTRICAL CHARACTERISTICS ($T_L = 25^oC$ unless otherwise noted) (2)

Characteristic	Symbol	1N5817	1N5818	1N5819	MBR115P MBR120P MBR130P	MBR140P	Unit
Maximum Instantaneous Forward Forward Voltage (1)	v_F						V
(i_F = 0.1 A)		0.320	0.330	0.340	0.350	0.350	
(i_F = 1.0 A)		0.450	0.550	0.600	0.550	0.600	
(i_F = 3.0 A)		0.750	0.875	0.900	0.850	0.900	
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1)	i_R						mA
($T_L = 25^oC$)		1.0	1.0	1.0	1.0	1.0	
($T_L = 100^oC$)		10	10	10	10	10	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.
(2) Lead Temperature reference is cathode lead 1/32" from case.
*Indicates JEDEC Registered Data for 1N5817-19.

MECHANICAL CHARACTERISTICS

CASE . . . . Transfer molded plastic
FINISH . . . . All external surfaces corrosion-resistant and the terminal leads are readily solderable
POLARITY . . . . Cathode indicated by polarity band
MOUNTING POSITIONS . . . . Any
SOLDERING . . . . 220^oC 1/16" from case for ten seconds

NOTE 1 — DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.1 V_{RWM}. Proper derating may be accomplished by use of equation (1).

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}P_{F(AV)} - R_{\theta JA}P_{R(AV)} \quad (1)$$

where $T_{A(max)}$ = Maximum allowable ambient temperature
$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest)
$P_{F(AV)}$ = Average forward power dissipation
$P_{R(AV)}$ = Average reverse power dissipation
$R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figures 1, 2, and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2).

$$T_R = T_{J(max)} - R_{\theta JA}P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2, and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2, and 3 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design, that is:

$$V_{R(equiv)} = V_{in(PK)} \times F \quad (4)$$

The factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

EXAMPLE: Find $T_{A(max)}$ for 1N5818 operated in a 12-volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 0.4 A ($I_{F(AV)}$ = 0.5 A), $I_{(FM)}/I_{(AV)}$ = 10, Input Voltage = 10 $V_{(rms)}$, $R_{\theta JA}$ = 80°C/W.

Step 1. Find $V_{R(equiv)}$. Read F = 0.65 from Table 1,
$\therefore V_{R(equiv)} = (1.41)(10)(0.65) = 9.2$ V.

Step 2. Find T_R from Figure 2. Read T_R = 109°C
@ V_R = 9.2 V and $R_{\theta JA}$ = 80°C/W.

Step 3. Find $P_{F(AV)}$ from Figure 4. **Read $P_{F(AV)}$ = 0.5 W
@ $\frac{I_{(FM)}}{I_{(AV)}} = 10$ and $I_{F(AV)}$ = 0.5 A.

Step 4. Find $T_{A(max)}$ from equation (3).
$T_{A(max)} = 109 - (80)(0.5) = 69$°C.

**Values given are for the 1N5818. Power is slightly lower for the 1N5817 because of its lower forward voltage, and higher for the 1N5819. Variations will be similar for the MBR-prefix devices, using $P_{F(AV)}$ from Figure 7.

TABLE 1 — VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped*†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2.0\ V_{in(PK)}$. †Use line to center tap voltage for V_{in}.

FIGURE 1 — MAXIMUM REFERENCE TEMPERATURE 1N5817/MBR115P/MBR120P

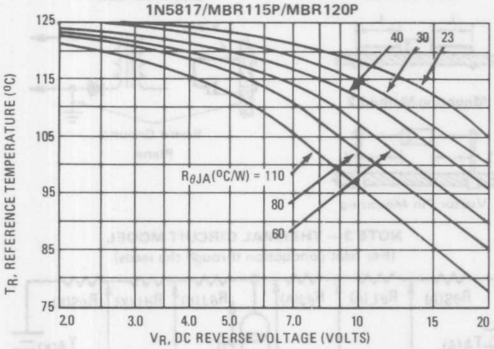


FIGURE 2 — MAXIMUM REFERENCE TEMPERATURE 1N5818/MBR130P

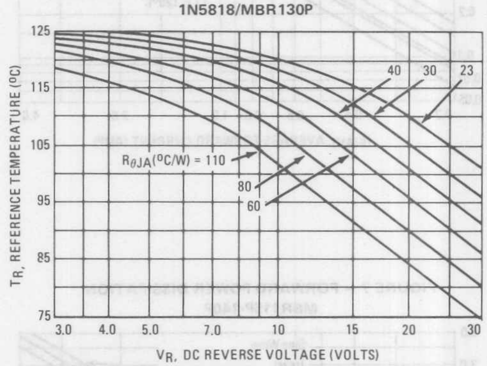


FIGURE 3 — MAXIMUM REFERENCE TEMPERATURE 1N5819/MBR140P

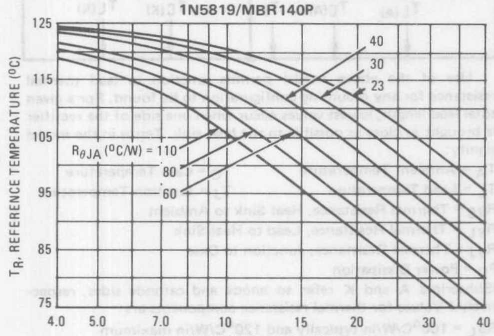
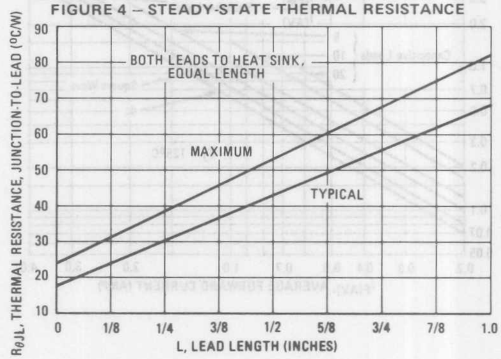


FIGURE 4 — STEADY-STATE THERMAL RESISTANCE



THERMAL CHARACTERISTICS

FIGURE 5 — THERMAL RESPONSE

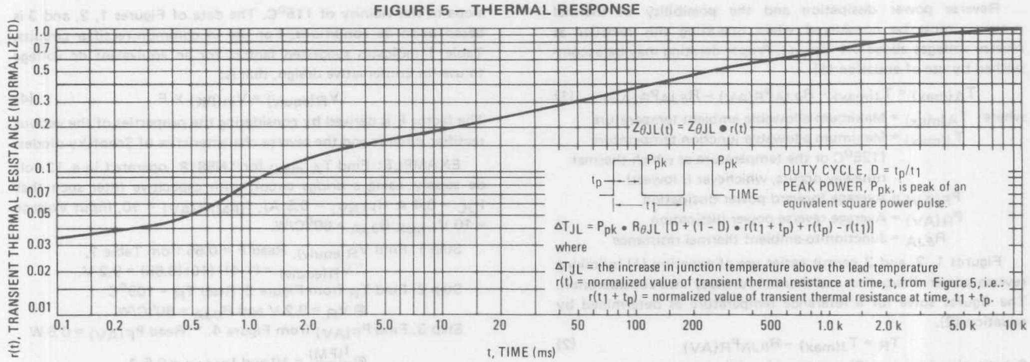


FIGURE 6 — FORWARD POWER DISSIPATION
1N5817-19

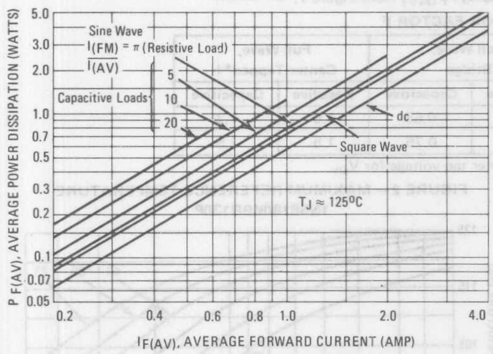
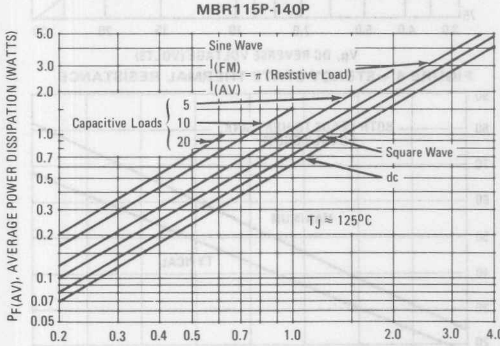


FIGURE 7 — FORWARD POWER DISSIPATION
MBR115P-140P



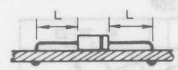
NOTE 2 — MOUNTING DATA

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering, or in case the tie point temperature cannot be measured.

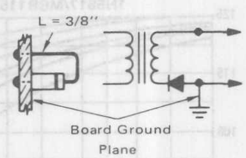
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting Method	Lead Length, L (in) 1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	52	65	72	85	$^oC/W$
2	67	80	87	100	$^oC/W$
3		50			$^oC/W$

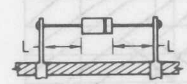
Mounting Method 1
P.C. Board with 1-1/2" X 1-1/2" copper surface.



Mounting Method 3
P.C. Board with 1-1/2" X 1-1/2" copper surface.

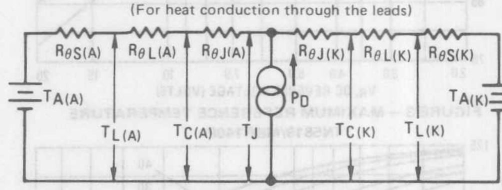


Mounting Method 2



Vector Pin Mounting

NOTE 3 — THERMAL CIRCUIT MODEL
(For heat conduction through the leads)



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature T_C = Case Temperature
T_L = Lead Temperature T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Power Dissipation

(Subscripts A and K refer to anode and cathode sides, respectively.) Values for thermal resistance components are:
$R_{\theta L} = 100^oC/W/in$ typically and $120^oC/W/in$ maximum
$R_{\theta J} = 36^oC/W$ typically and $46^oC/W$ maximum.

FIGURE 8 – TYPICAL FORWARD VOLTAGE

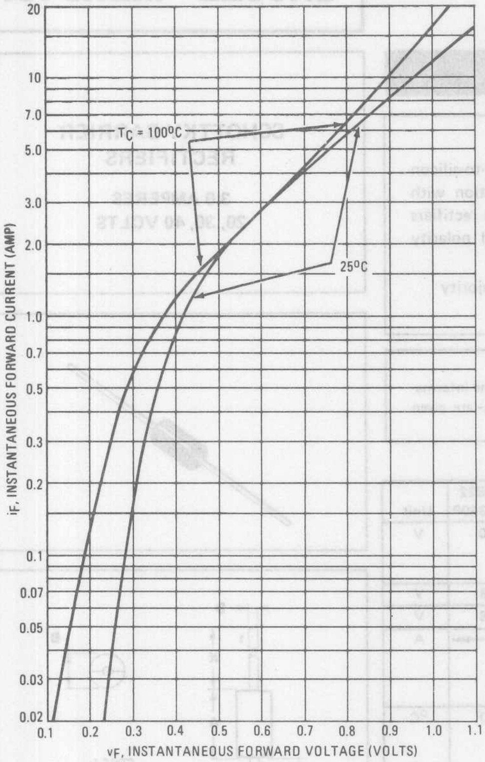


FIGURE 9 – MAXIMUM NON-REPETITIVE SURGE CURRENT

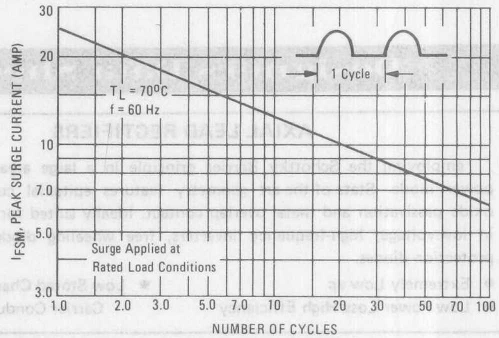


FIGURE 10 – TYPICAL REVERSE CURRENT

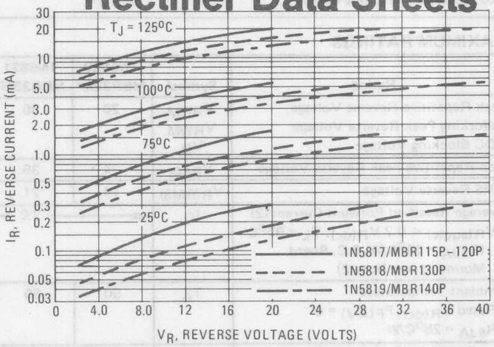
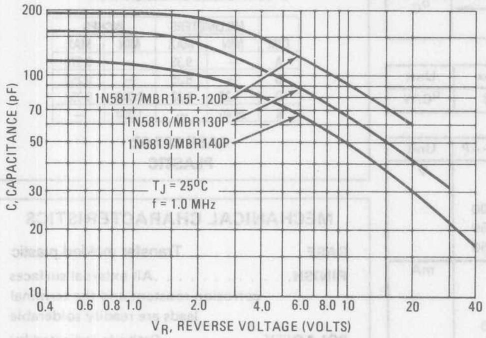


FIGURE 11 – TYPICAL CAPACITANCE



NOTE 4 – HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss: it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

(For 50 V and 60 V, see MBR150, 160 Data Sheet)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5820 MBR320P
1N5821 MBR330P
1N5822 MBR340P

Designers Data Sheet

AXIAL LEAD RECTIFIERS

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Power Loss/High Efficiency
- Low Stored Charge, Majority Carrier Conduction

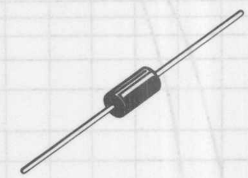
Designer's Data for Worst-Case Conditions

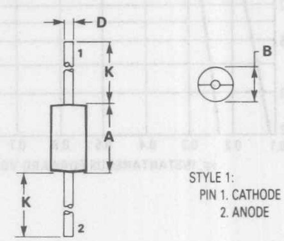
The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves—representing boundaries on device characteristics—are given to facilitate worst-case design.

3

SCHOTTKY BARRIER RECTIFIERS

3.0 AMPERES
20, 30, 40 VOLTS





STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

*MAXIMUM RATINGS

Rating	Symbol	1N5820 MBR320P	1N5821 MBR330P	1N5822 MBR340P	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	24	36	48	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified Forward Current (2) $V_{R(equiv)} \leq 0.2\ V_{R(dc)}$, $T_L = 95^oC$ ($R_{\theta JA} = 28^oC/W$, P.C. Board Mounting, see Note 2)	I_O	←	3.0	→	A
Ambient Temperature Rated $V_{R(dc)}$, $P_{F(AV)} = 0$ $R_{\theta JA} = 28^oC/W$	T_A	90	85	80	^oC
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, half wave, single phase 60 Hz, $T_L = 75^oC$)	I_{FSM}	←	80 (for one cycle)	→	A
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	T_J, T_{stg}	←	−65 to +125	→	^oC
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	←	150	→	^oC

*THERMAL CHARACTERISTICS (Note 2)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	28	$^oC/W$

*ELECTRICAL CHARACTERISTICS ($T_L = 25^oC$ unless otherwise noted) (2)

Characteristic	Symbol	1N5820	1N5821	1N5822	MBR---P	Unit
Maximum Instantaneous Forward Voltage (1)	v_F					V
($i_F = 1.0$ Amp)		0.370	0.380	0.390	0.400	
($i_F = 3.0$ Amp)		0.475	0.500	0.525	0.550	
($i_F = 9.4$ Amp)		0.850	0.900	0.950	0.950	
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1)	i_R					mA
$T_L = 25^oC$		2.0	2.0	2.0	2.0	
$T_L = 100^oC$		20	20	20	20	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.
(2) Lead Temperature reference is cathode lead 1/32″ from case.
*Indicates JEDEC Registered Data for 1N5820-22.

MECHANICAL CHARACTERISTICS

CASE . . . . Transfer molded plastic
FINISH . . . . All external surfaces corrosion-resistant and the terminal leads are readily solderable
POLARITY . . . . Cathode indicated by polarity band
MOUNTING POSITIONS . . . . Any
SOLDERING . . . . . . 220°C 1/16″ from case for ten seconds

NOTE 1 – DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.1 V_{RWM}. Proper derating may be accomplished by use of equation (1).

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}P_{F(AV)} - R_{\theta JA}P_{R(AV)} \quad (1)$$

where $T_{A(max)}$ = Maximum allowable ambient temperature
$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest)
$P_{F(AV)}$ = Average forward power dissipation
$P_{R(AV)}$ = Average reverse power dissipation
$R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figures 1, 2, and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2).

$$T_R = T_{J(max)} - R_{\theta JA}P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2, and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2, and 3 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design, that is:

$$V_{R(equiv)} = V_{(FM)} \times F \quad (4)$$

The factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

EXAMPLE: Find $T_{A(max)}$ for 1N5821 operated in a 12-volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 2.0 A ($I_{F(AV)}$ = 1.0 A), $I_{(FM)}/I_{(AV)}$ = 10, Input Voltage = 10 $V_{(rms)}$, $R_{\theta JA}$ = 40°C/W.

Step 1. Find $V_{R(equiv)}$. Read F = 0.65 from Table 1,
$\therefore V_{R(equiv)} = (1.41)(10)(0.65) = 9.2$ V.

Step 2. Find T_R from Figure 2. Read T_R = 108°C
@ V_R = 9.2 V and $R_{\theta JA}$ = 40°C/W.

Step 3. Find $P_{F(AV)}$ from Figure 6. **Read $P_{F(AV)}$ = 0.85 W
@ $\frac{I_{(FM)}}{I_{(AV)}}$ = 10 and $I_{F(AV)}$ = 1.0 A.

Step 4. Find $T_{A(max)}$ from equation (3).
$T_{A(max)} = 108 - (0.85)(40) = 74$°C.

**Values given are for the 1N5821. Power is slightly lower for the 1N5820 because of its lower forward voltage, and higher for the 1N5822. Variations will be similar for the MBR-prefix devices, using $P_{F(AV)}$ from Figure 7.

TABLE 1 – VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped*†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2.0\ V_{in(PK)}$. †Use line to center tap voltage for V_{in}.

FIGURE 1 – MAXIMUM REFERENCE TEMPERATURE 1N5820/MBR320P

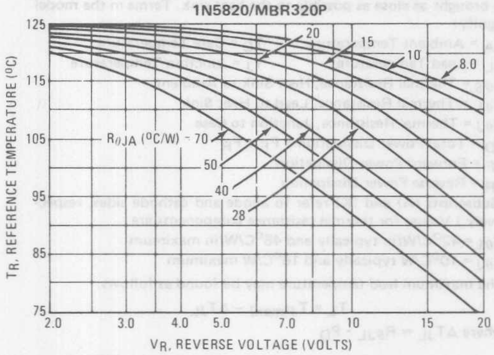


FIGURE 2 – MAXIMUM REFERENCE TEMPERATURE 1N5821/MBR330P

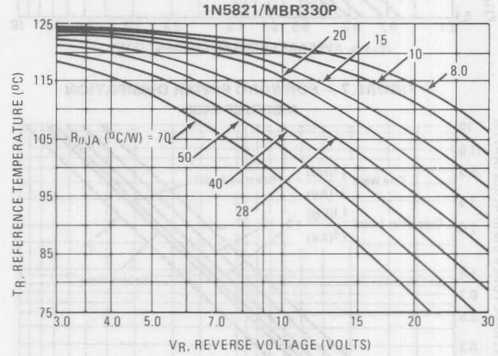


FIGURE 3 – MAXIMUM REFERENCE TEMPERATURE 1N5822/MBR340P

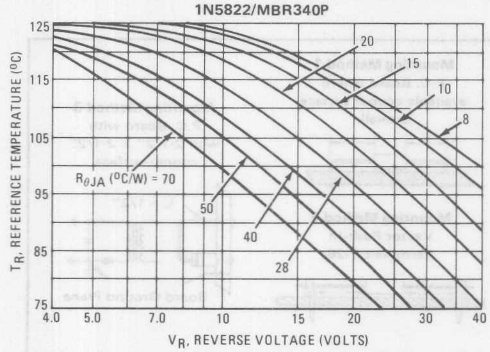
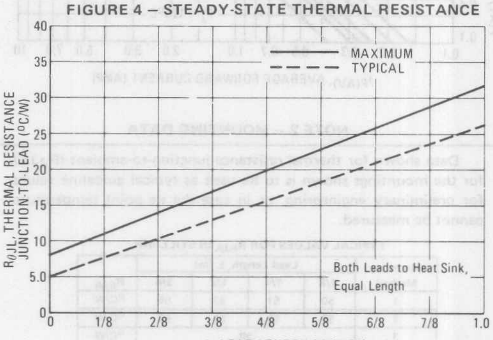


FIGURE 4 – STEADY-STATE THERMAL RESISTANCE



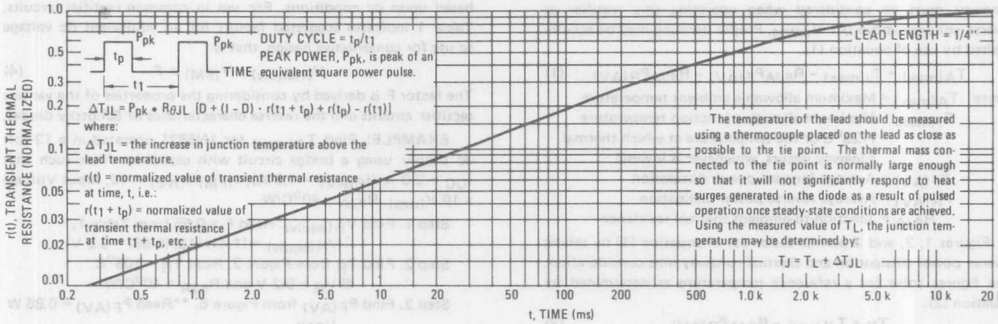


FIGURE 6 — FORWARD POWER DISSIPATION 1N5820-22

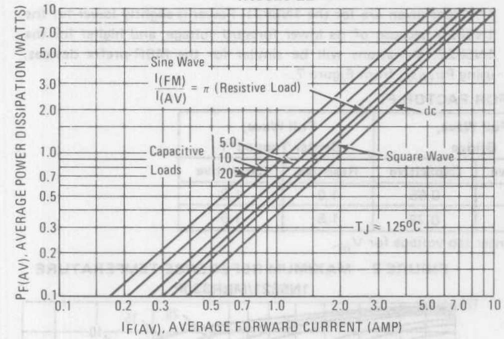
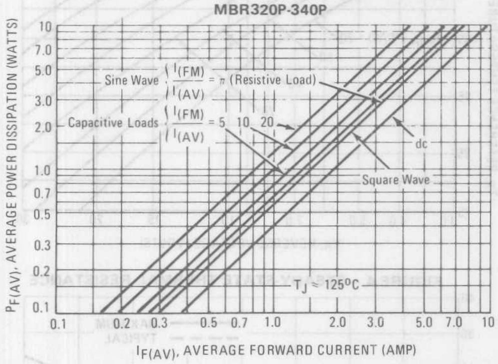


FIGURE 7 — FORWARD POWER DISSIPATION MBR320P-340P



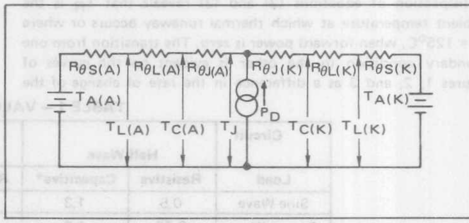
NOTE 2 — MOUNTING DATA

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering, or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting Method	Lead Length, L (in) 1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3		28			°C/W

NOTE 3 — APPROXIMATE THERMAL CIRCUIT MODEL



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature $\quad$ T_C = Case Temperature
T_L = Lead Temperature $\quad$ T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Total Power Dissipation = $P_F + P_R$
P_F = Forward Power Dissipation
P_R = Reverse Power Dissipation

(Subscripts (A) and (K) refer to anode and cathode sides, respectively.) Values for thermal resistance components are:

$R_{\theta L}$ = 42°C/W/in typically and 48°C/W/in maximum
$R_{\theta J}$ = 10°C/W typically and 16°C/W maximum

The maximum lead temperature may be found as follows:

$$T_L = T_{J(max)} - \Delta T_{JL}$$

where $\Delta T_{JL} \approx R_{\theta JL} \cdot P_D$

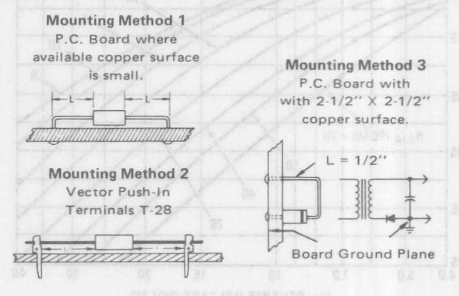


FIGURE 8 – TYPICAL FORWARD VOLTAGE

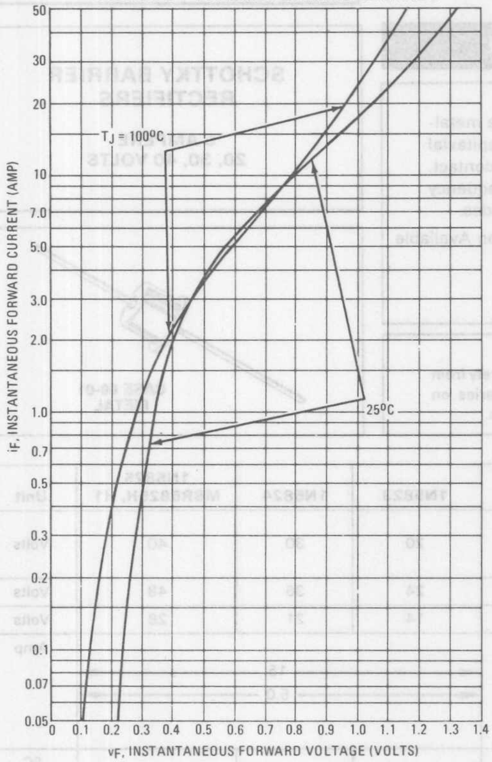


FIGURE 9 – MAXIMUM NON-REPETITIVE SURGE CURRENT

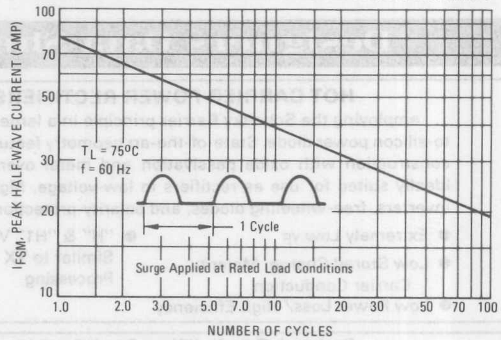


FIGURE 10 – TYPICAL REVERSE CURRENT

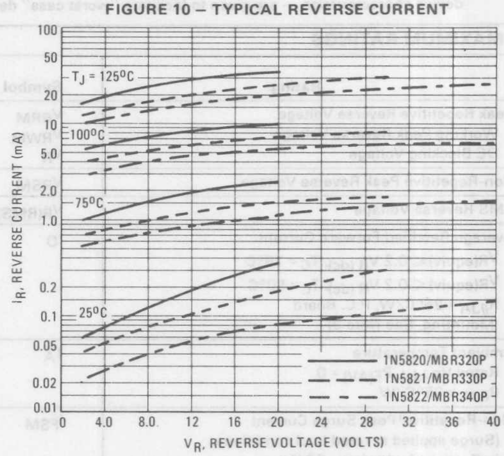
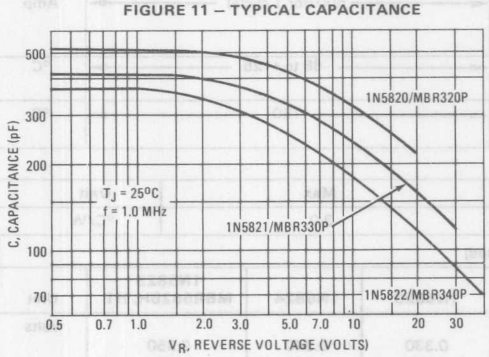


FIGURE 11 – TYPICAL CAPACITANCE



NOTE 4 – HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11.)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5823, 1N5824
1N5825
MBR5825,H,H1

Designers Data Sheet

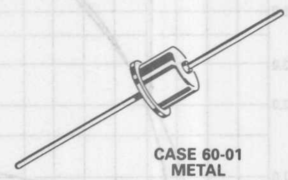
HOT CARRIER POWER RECTIFIERS

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/ High Efficiency
- "H" & "H1" Version Available Similar to TX Processing

SCHOTTKY BARRIER RECTIFIERS

5 AMPERE
20, 30, 40 VOLTS



CASE 60-01
METAL

3

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

*MAXIMUM RATINGS

Rating	Symbol	1N5823	1N5824	1N5825 MBR5825H, H1	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	24	36	48	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	Volts
Average Rectified Forward Current $V_{R(equiv)} \leq 0.2\ V_{R\ (dc)}$, $T_C = 75°C$ $V_{R(equiv)} \leq 0.2\ V_{R\ (dc)}$, $T_L = 80°C$ $R_{\theta JA} = 25°C/W$, P.C. Board Mounting, See Note 3)	I_O	← 15 → ← 5.0 →			Amp
Ambient Temperature Rated $V_{R\ (dc)}$, $P_{F(AV)} = 0$ $R_{\theta JA} = 25°C/W$	T_A	65	60	55	°C
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase 60 Hz)	I_{FSM}	← 500 (for 1 cycle) →			Amp
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	T_J, T_{stg}	← -65 to +125 →			°C
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	← 150 →			°C

*THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	°C/W

*ELECTRICAL CHARACTERISTICS ($T_C = 25°C$ unless otherwise noted)

Characteristic	Symbol	1N5823	1N5824	1N5825 MBR5825H, H1	Unit
Maximum Instantaneous Forward Voltage (1) ($i_F = 3.0$ Amp) ($i_F = 5.0$ Amp) ($i_F = 15.7$ Amp)	v_F	 0.330 0.360 0.470	 0.340 0.370 0.490	 0.350 0.380 0.520	Volts
Maximum Instantaneous Reverse Current @ rated dc Voltage $T_C = 25°C$ $T_C = 100°C$	i_R	 10 100	 10 125	 10 150	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0% *Indicates JEDEC Registered Data for 1N5823–1N5825

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.1 V_{RWM}. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA} P_{F(AV)} - R_{\theta JA} P_{R(AV)} \quad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest).

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figures 1, 2 and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA} P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA} P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2 and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2 and 3 is based upon dc conditions. For use in common rectifier circuits, Table I indicates suggested factors for an equivalent dc voltage to use for conservative design, i.e.:

$$V_{R(equiv)} = V_{IN(PK)} \times F \quad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

Example: Find $T_{A(max)}$ for 1N5825 operated in a 12-Volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 10 A ($I_{F(AV)}$ = 5 A), $I_{(PK)}/I_{(AV)}$ = 10, Input Voltage = 10 V(rms), $R_{\theta JA}$ = 10°C/W.

Step 1: Find $V_{R(equiv)}$. Read F = 0.65 from Table I ∴ $V_{R(equiv)}$ = (1.41)(10)(0.65) = 9.2 V

Step 2: Find T_R from Figure 3. Read T_R = 113°C @ V_R = 9.2 V & $R_{\theta JA}$ = 10°C/W.

Step 3: Find $P_{F(AV)}$ from Figure 4. **Read $P_{F(AV)}$ = 5.5 W @ $\frac{I_{(PK)}}{I_{(AV)}}$ = 10 & $I_{F(AV)}$ = 5 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 113-(10)(5.5) = 58°C.

**Value given are for the 1N5825. Power is slightly lower for the other units because of their lower forward voltage.

TABLE I – VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped *†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2\ V_{in(PK)}$ †Use line to center tap voltage for V_{in}.

FIGURE 1 – MAXIMUM REFERENCE TEMPERATURE – 1N5823

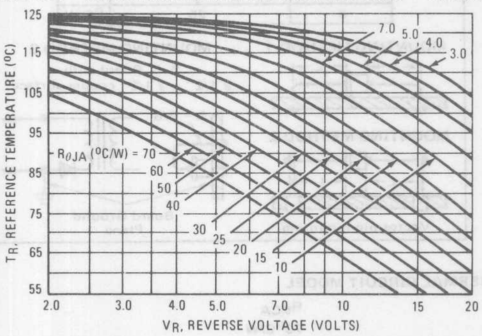


FIGURE 2 – MAXIMUM REFERENCE TEMPERATURE – 1N5824

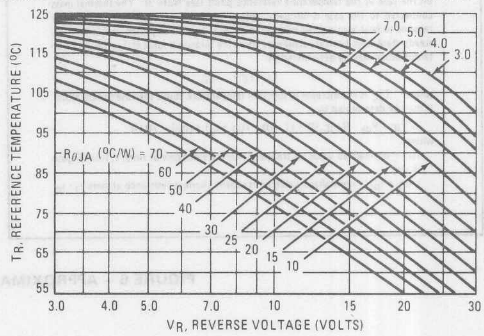


FIGURE 3 – MAXIMUM REFERENCE TEMPERATURE 1N5825 AND MBR5825H, H1

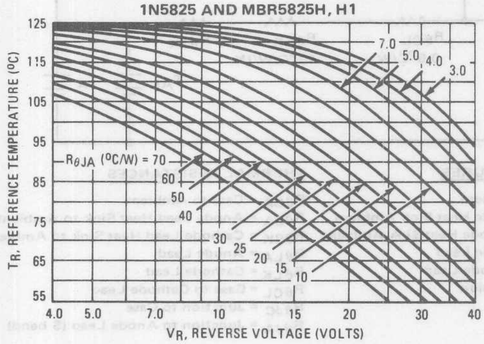
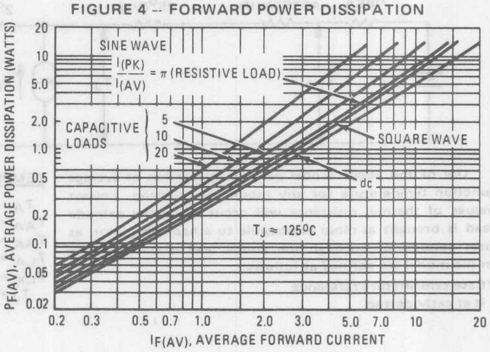
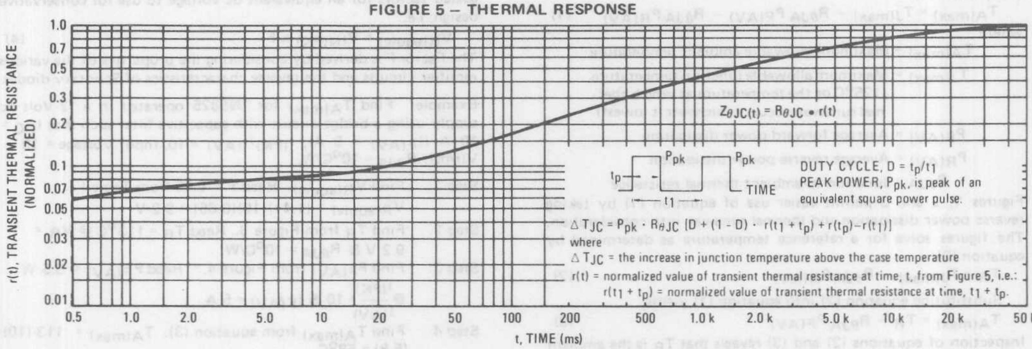


FIGURE 4 – FORWARD POWER DISSIPATION

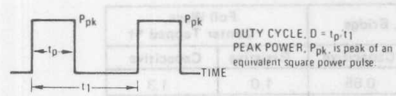


THERMAL CHARACTERISTICS

FIGURE 5 – THERMAL RESPONSE



NOTE 2 – FINDING JUNCTION TEMPERATURE



To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

r(t) = normalized value of transient thermal resistance at time, t, from Figure 5, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$

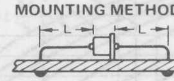
NOTE 3 – MOUNTING DATA

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering.

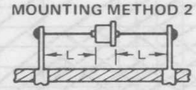
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN) 1/4	1	$R_{\theta JA}$
1	55	60	°C/W
2	65	70	°C/W
3	25		°C/W

MOUNTING METHOD 1



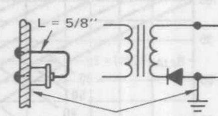
MOUNTING METHOD 2



Vector pin mounting

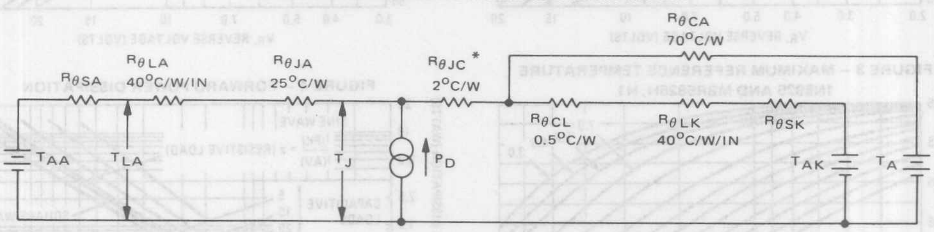
MOUNTING METHOD 3

P. C. Board with 2 1/2" x 2 1/2" copper surface



Board Ground Plane

FIGURE 6 – APPROXIMATE THERMAL CIRCUIT MODEL



Use of the above model permits calculation of average junction temperature for any mounting situation. Lowest values of thermal resistance will occur when the cathode lead is brought as close as possible to a heat dissipator; as heat conduction through the anode lead is small. Terms in the model are defined as follows:

*Case temperature reference is at cathode end.

TEMPERATURES

T_A = Ambient
T_{AA} = Anode Heat Sink Ambient
T_{AK} = Cathode Heat Sink Ambient
T_{LA} = Anode Lead
T_{LK} = Cathode Lead
T_J = Junction

THERMAL RESISTANCES

$R_{\theta CA}$ = Case to Ambient
$R_{\theta SA}$ = Anode Lead Heat Sink to Ambient
$R_{\theta SK}$ = Cathode Lead Heat Sink to Ambient
$R_{\theta LA}$ = Anode Lead
$R_{\theta LK}$ = Cathode Lead
$R_{\theta CL}$ = Case to Cathode Lead
$R_{\theta JC}$ = Junction to Case
$R_{\theta JA}$ = Junction to Anode Lead (S bend)

FIGURE 7 – TYPICAL FORWARD VOLTAGE

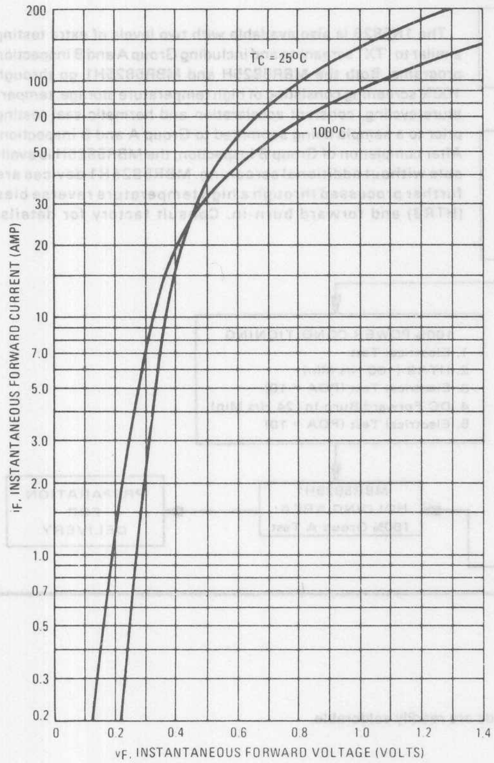


FIGURE 8 – MAXIMUM SURGE CAPABILITY

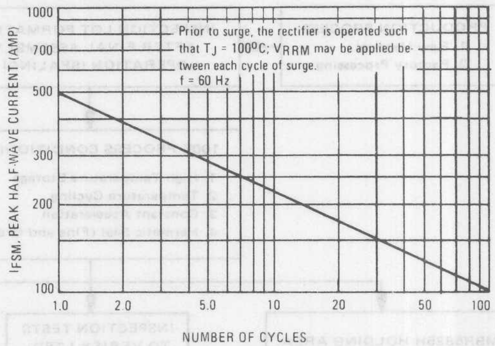


FIGURE 9 – TYPICAL REVERSE CURRENT

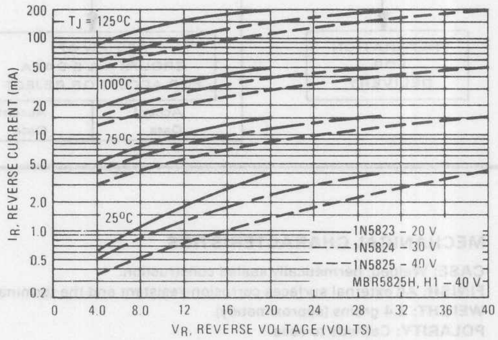
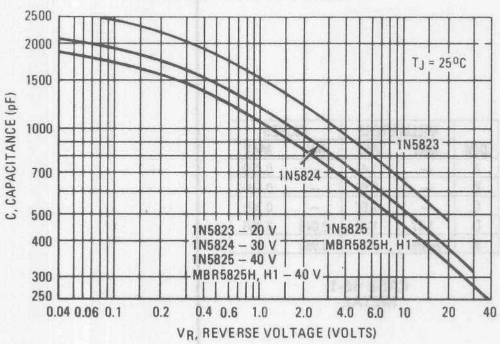


FIGURE 10 – CAPACITANCE

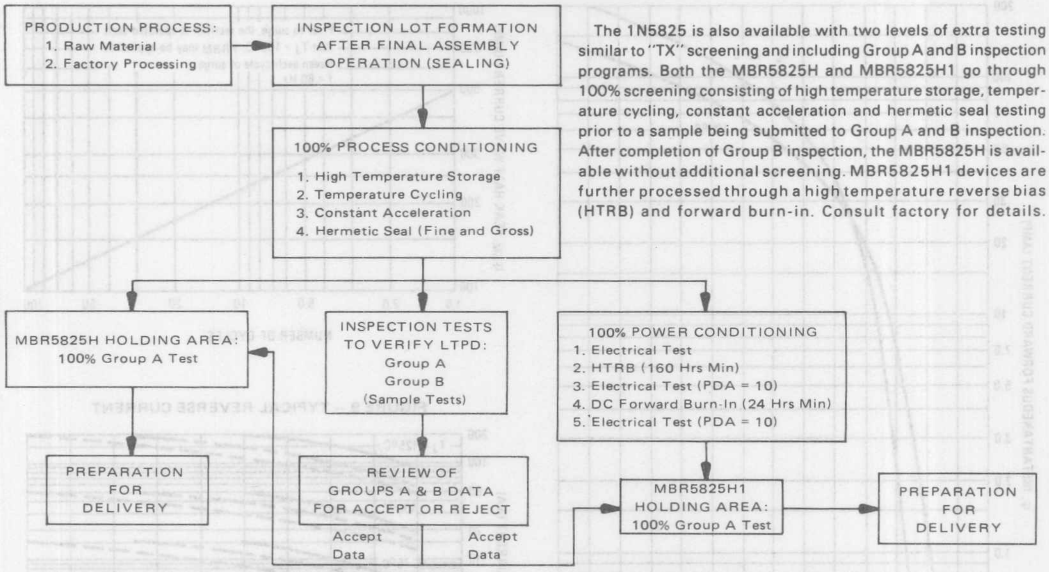


NOTE 4 – HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10).

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

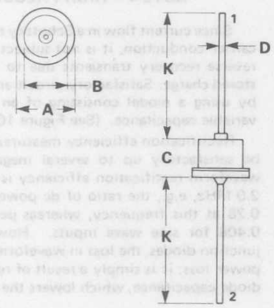
NOTE 5 – HI-REL PROGRAM OPTIONS



The 1N5825 is also available with two levels of extra testing similar to "TX" screening and including Group A and B inspection programs. Both the MBR5825H and MBR5825H1 go through 100% screening consisting of high temperature storage, temperature cycling, constant acceleration and hermetic seal testing prior to a sample being submitted to Group A and B inspection. After completion of Group B inspection, the MBR5825H is available without additional screening. MBR5825H1 devices are further processed through a high temperature reverse bias (HTRB) and forward burn-in. Consult factory for details.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed construction.
FINISH: All external surfaces corrosion-resistant and the terminal leads are readily solderable.
WEIGHT: 2.4 grams (approximately).
POLARITY: Cathode to case.
MOUNTING POSITONS: Any



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	11.43	—	0.450
B	—	8.89	—	0.350
C	—	7.62	—	0.300
D	1.17	1.42	0.046	0.056
K	24.89	—	0.980	—

CASE 60-1
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5826
1N5827
1N5828

Designers Data Sheet

HOT CARRIER POWER RECTIFIER

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- High Surge Capacity

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

SCHOTTKY
BARRIER
RECTIFIERS

15 AMPERE
20,30,40 VOLTS

*MAXIMUM RATINGS

Rating	Symbol	1N5826	1N5827	1N5828	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	24	36	48	Volts
Average Rectified Forward Current $V_{R(equiv)} \leq 0.2\ V_{R(dc)}$, $T_C = 85^{\circ}C$	I_O	← 15 →			Amp
Ambient Temperature Rated $V_{R(dc)}$, $P_{F(AV)} = 0$, $R_{\theta JA} = 5.0^{\circ}C/W$	T_A	95	90	85	$^{\circ}C$
Non-Repetitive Peak Surge Current (surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	← 500 (for 1 cycle) →			Amp
Operating and Storage Junction Temperature Range (Reverse voltage applied)	T_J, T_{stg}	← −65 to +125 →			$^{\circ}C$
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	← 150 →			$^{\circ}C$

*THERMAL CHARACTERISTICS

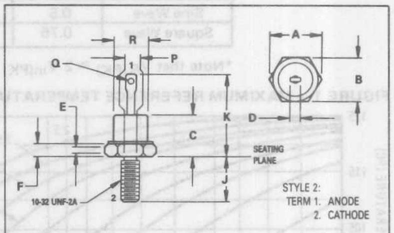
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.5	$^{\circ}C/W$

*ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic	Symbol	1N5826	1N5827	1N5828	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 8.0 Amp) (i_F = 15 Amp) (i_F = 47.1 Amp)	v_F	 0.380 0.440 0.670	 0.400 0.470 0.770	 0.420 0.500 0.870	Volts
Maximum Instantaneous Reverse Current @ rated dc Voltage (1) $T_C = 100^{\circ}C$	i_R	10 75	10 75	10 75	mA

*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.



STYLE 2:
TERM 1. ANODE
2. CATHODE

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED DO-4 OUTLINE SHALL APPLY.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	12.82	—	0.505
B	10.77	11.09	0.424	0.437
C	—	10.28	—	0.405
D	—	6.35	—	0.250
E	1.53	—	0.060	—
F	1.91	4.44	0.075	0.175
J	10.72	11.50	0.422	0.453
K	15.24	20.32	0.600	0.800
P	4.14	4.80	0.163	0.189
Q	1.53	2.41	0.060	0.095
R	6.74	10.76	0.265	0.424

CASE 56-03
DO-203AA
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and terminal leads are readily solderable.

POLARITY: Cathode to Case

MOUNTING POSITION: Any

STUD TORQUE: 15 in. lb. max

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.2 V_{RWM}. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}\,P_{F(AV)} - R_{\theta JA}\,P_{R(AV)} \quad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest).

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figures 1, 2 and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA}\,P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}\,P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2 and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2 and 3 is based upon dc conditions. For use in common rectifier circuits, Table I indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in(PK)} \times F \quad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

Example: Find $T_{A(max)}$ for 1N5828 operated in a 12-Volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 10 A ($I_{F(AV)}$ = 5 A), $I_{(PK)}/I_{(AV)}$ = 20, Input Voltage = 10 V(rms), $R_{\theta JA}$ = 5°C/W.

Step 1: Find $V_{R(equiv)}$. Read F = 0.65 from Table I ∴ $V_{R(equiv)}$ = (1.41)(10)(0.65) = 9.18 V

Step 2: Find T_R from Figure 3. Read T_R = 121°C @ V_R = 9.18 & $R_{\theta JA}$ = 5°C/W

Step 3: Find $P_{F(AV)}$ from Figure 4.** Read $P_{F(AV)}$ = 10 W @ $\frac{I_{(PK)}}{I_{(AV)}}$ = 20 & $I_{F(AV)}$ = 5 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 121-(5)(10) = 71°C

** Value given are for the 1N5828. Power is slightly lower for the other units because of their lower forward voltage.

TABLE I – VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped *†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

*Note that $V_{R(PK)} \approx 2\,V_{in(PK)}$ *†Use line to center tap voltage for V_{in}.

FIGURE 1 – MAXIMUM REFERENCE TEMPERATURE – 1N5826

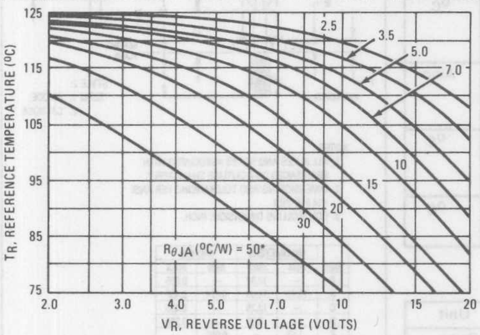


FIGURE 2 – MAXIMUM REFERENCE TEMPERATURE – 1N5827

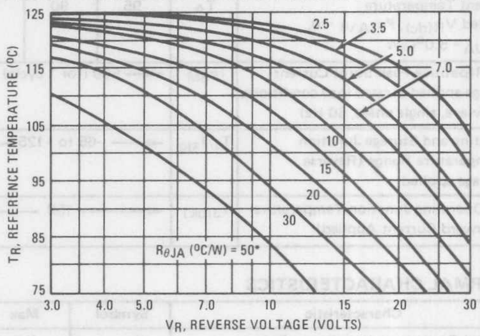


FIGURE 3 – MAXIMUM REFERENCE TEMPERATURE – 1N5828

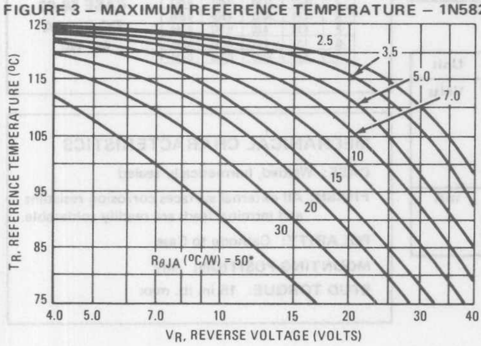
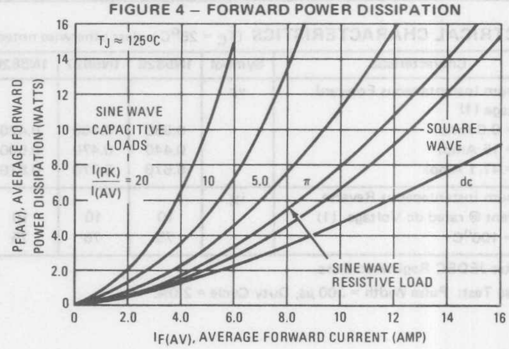


FIGURE 4 – FORWARD POWER DISSIPATION



*No external heat sink.

FIGURE 5 — TYPICAL FORWARD VOLTAGE

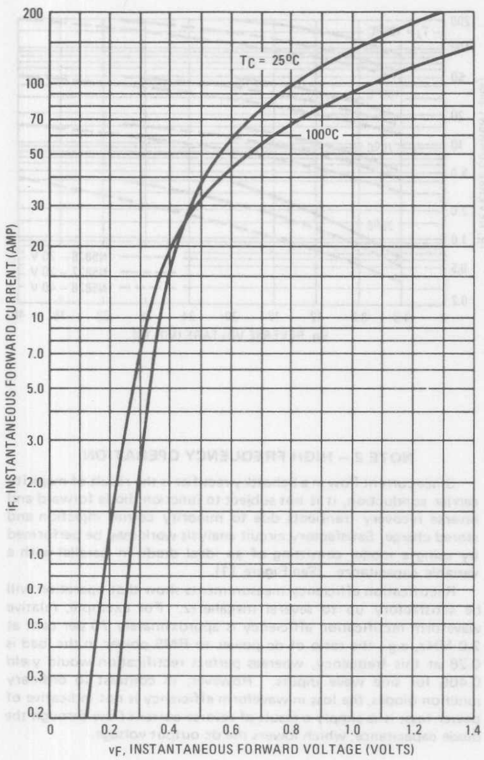


FIGURE 6 — MAXIMUM SURGE CAPABILITY

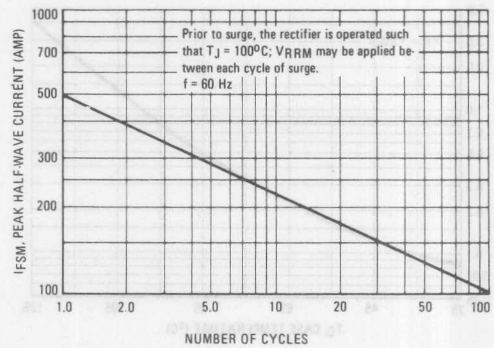


FIGURE 7 — CURRENT DERATING

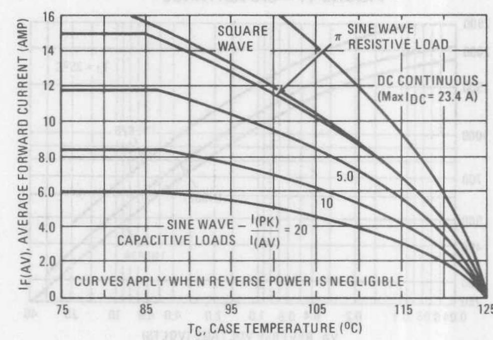


FIGURE 8 — THERMAL RESPONSE

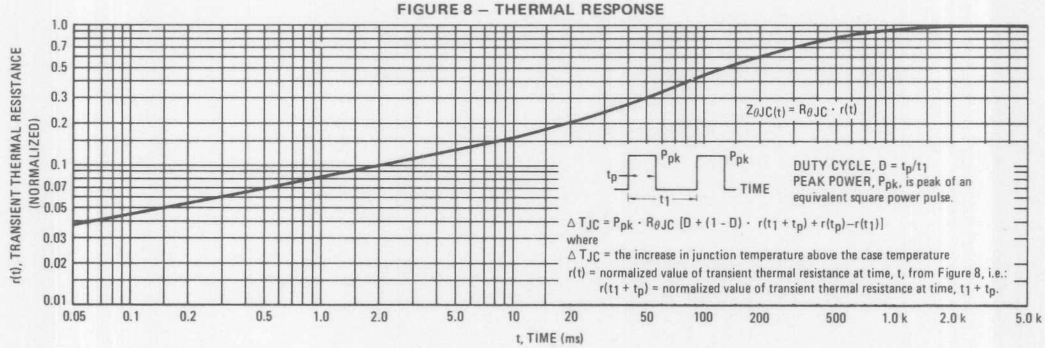


FIGURE 9 – NORMALIZED REVERSE CURRENT

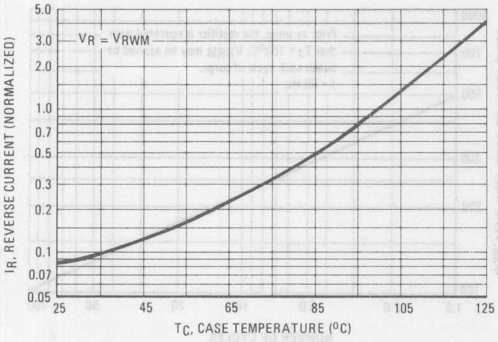


FIGURE 10 – TYPICAL REVERSE CURRENT

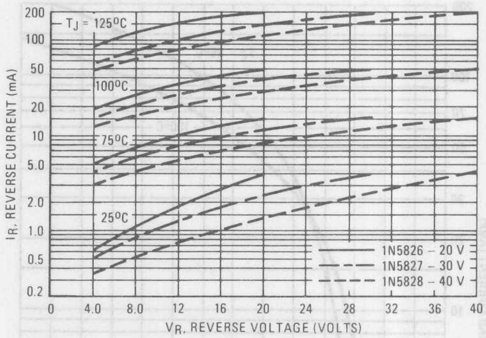
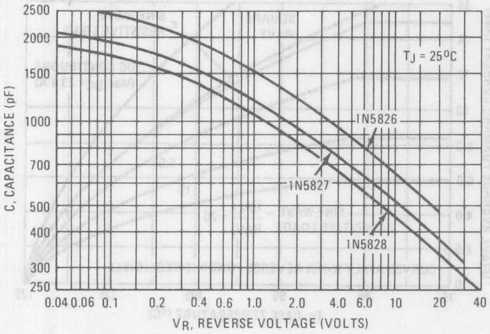


FIGURE 11 – CAPACITANCE



NOTE 2 – HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11).

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5829
1N5830
1N5831
MBR5831H, H1

Designer's Data Sheet

Hot Carrier Power Rectifiers

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- High Surge Capacity
- High Reliability Processing Similar to JAN,JTX Processing Available (See Note 3)

25 AMPERE
20, 30, 40 VOLTS

3

CASE 56-03
DO-203AA
METAL

MAXIMUM RATINGS

Rating	Symbol	*1N5829	*1N5830	*1N5831 MBR5831H,H1	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	24	36	48	Volts
Average Rectified Forward Current $V_{R(equiv)} \leq 0.2\ V_{R(dc)}$, $T_C = 85°C$	I_O		25		Amps
Ambient Temperature Rated $V_{R(dc)}$, $P_{F(AV)} = 0$, $R_{\theta JA} = 3.5°C/W$	T_A	90	85	80	°C
Nonrepetitive Peak Surge Current (surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}		800 (for 1 cycle)		Amps
Operating and Storage Junction Temperature Range (Reverse voltage applied)	T_J, T_{stg}		−65 to +125		°C
Peak Operating Junction Temperature (Foward Current Applied)	$T_{J(pk)}$		150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.75	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25°C$ unless otherwise noted)

Characteristic	Symbol	*1N5829	*1N5830	*1N5831 MBR5831H,H1	Unit
Maximum Instantaneous Forward Voltage(1) (i_F = 10 Amps) (i_F = 25 Amps) (i_F = 78.5 Amps)	v_F	 0.360 0.440 0.720	 0.370 0.460 0.770	 0.380 0.480 0.820	Volts
Maximum Instantaneous Reverse Current @ Rated dc Voltage(1) (T_C = 100°C)	i_R	20 150	20 150	20 150	mA

*Indicates JEDEC Registered Data.
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.2 V_{RWM}. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}\,P_{F(AV)} - R_{\theta JA}\,P_{R(AV)} \quad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest).

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JC}$ = Junction-to-ambient thermal resistance

Figures 1, 2 and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA}\,P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation 91) yields:

$$T_{A(max)} = T_R - R_{\theta JA}\,P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2 and 3 as a difference in the rate of change of the slope in the vicinity of 115°C.

The data of Figures 1, 2 and 3 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in(PK)} \times F \quad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

Example: Find $T_{A(max)}$ for 1N5831 operated in a 12-Volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 16 A ($I_{F(AV)}$ = 8 A), $I_{(PK)}/I_{(AV)}$ = 20, Input Voltage = 10 V(rms), $R_{\theta JA}$ = 5°C/W.

Step 1: Find $V_{R(equiv)}$. Read F = 0.65 from Table 1
$V_{R(equiv)}$ = (1.41)(10)(0.65) = 9.18 V

Step 2: Find T_R from Figure 3. Read T_R = 113°C @ V_R = 9.18 & $R_{\theta JA}$ = 5°C/W

Step 3: Find $P_{F(AV)}$ from Figure 4.** Read $P_{F(AV)}$ = 12.8 W @ $\frac{I_{(PK)}}{I_{(AV)}}$ = 20 & $I_{F(AV)}$ = 8 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 113-(5) (12.8) = 49°C

**Value given are for the 1N5828. Power is slightly lower for the other units because of their lower forward voltage.

Table 1. Values for Factor F

Circuit Load	Half Wave		Full Wave, Bridge		Full Wave Center Tapped††	
	Resistive	Capacitive†	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

†Note that $V_{R(PK)} \approx 2\,V_{in(PK)}$

††Use line to center tape voltage for V_{in}.

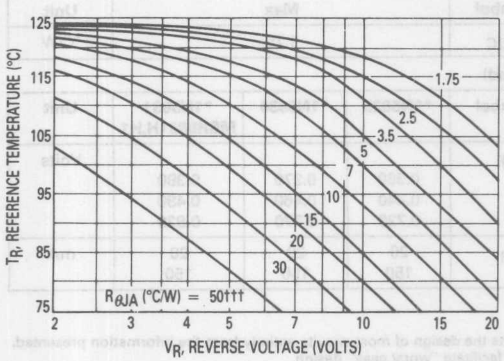


Figure 1. Maximum Reference Temperature — 1N5829

†††NO EXTERNAL HEAT SINK

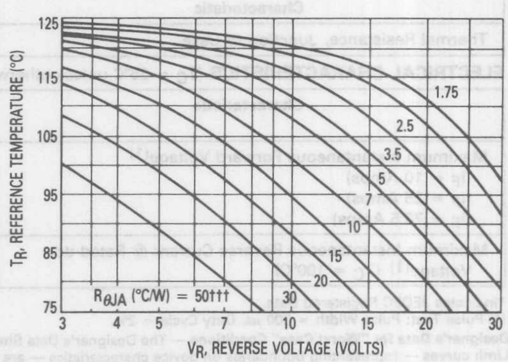
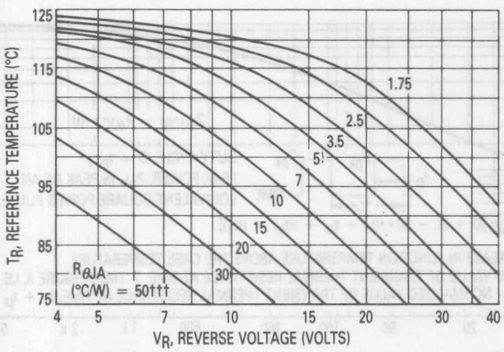


Figure 2. Maximum Reference Temperature — 1N5830



†††NO EXTERNAL HEAT SINK.

Figure 3. Maximum Reference Temperature — 1N5831

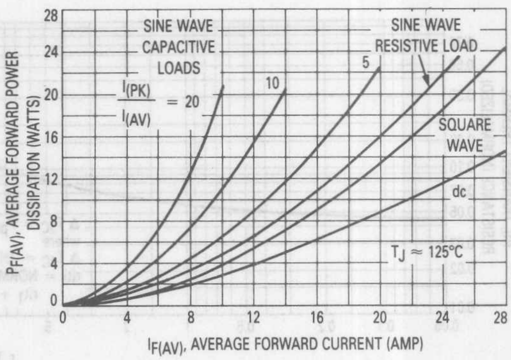


Figure 4. Forward Power Dissipation

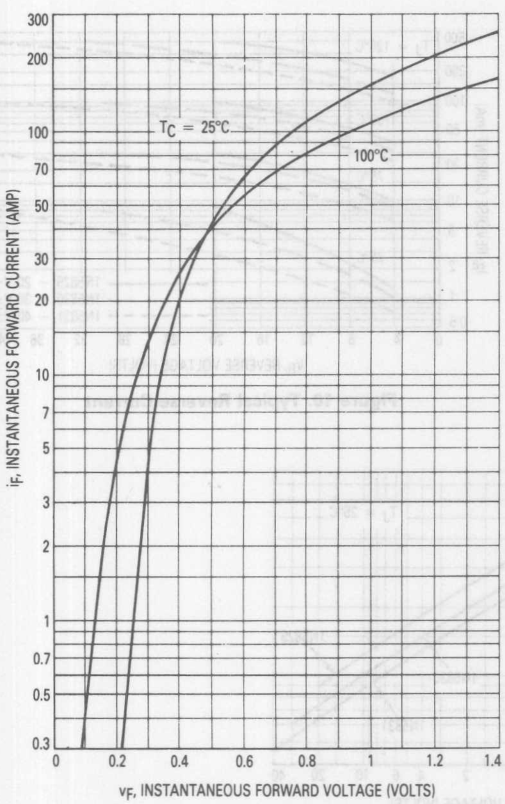


Figure 5. Typical Forward Voltage

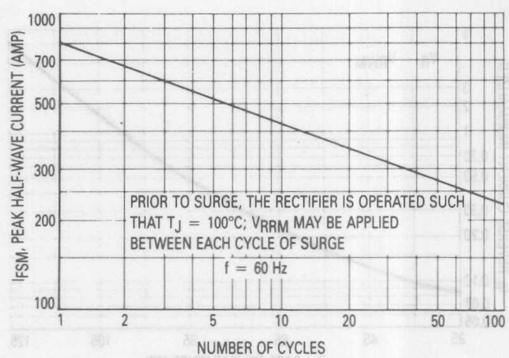


Figure 6. Maximum Surge Capability

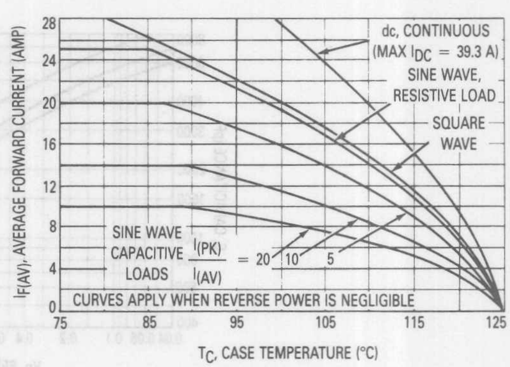


Figure 7. Current Derating

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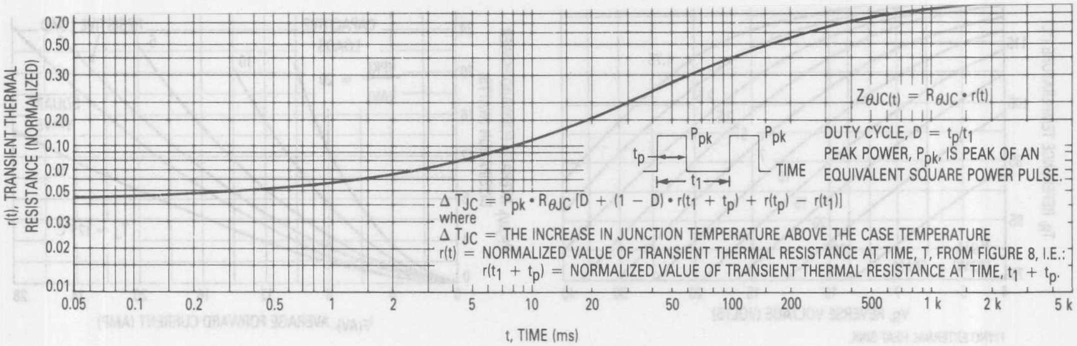


Figure 8. Thermal Response

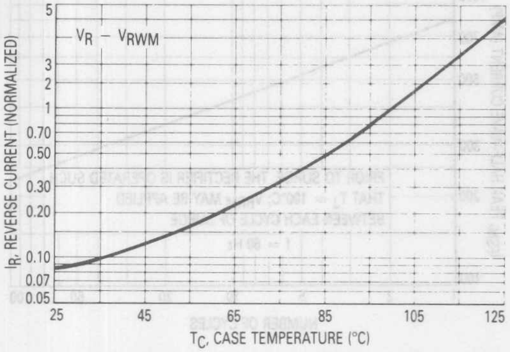


Figure 9. Normalized Reverse Current

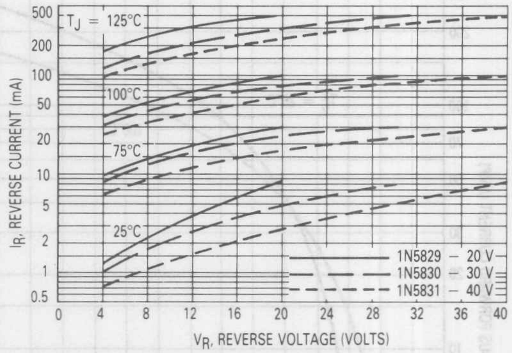


Figure 10. Typical Reverse Current

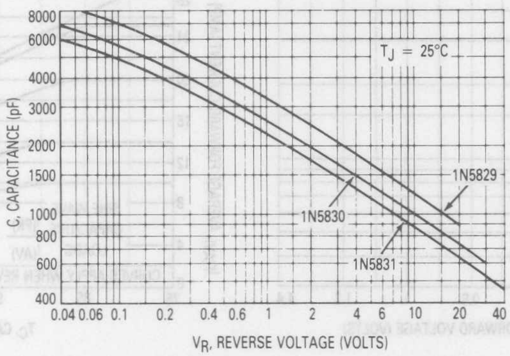


Figure 11. Capacitance

NOTE 2 — HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11.)

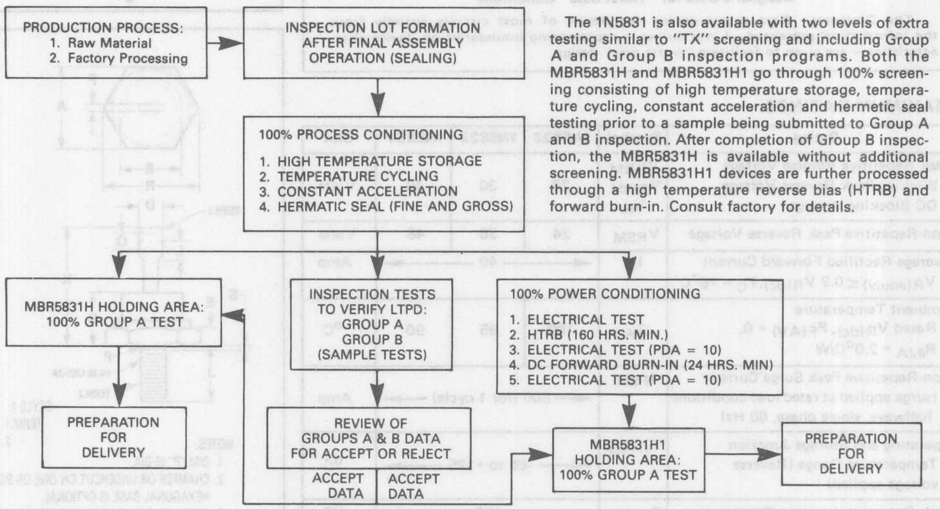
Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicate of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

MECHANICAL CHARACTERISTICS

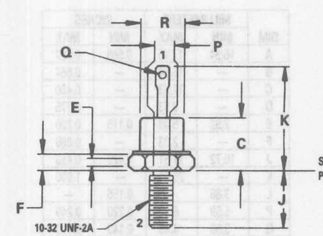
CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and terminal leads are readily solderable.
POLARITY: Cathode to Case
MOUNTING POSITIONS: Any
STUD TORQUE: 15 in. lb. Max

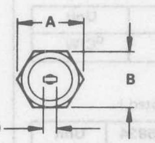
NOTE 3 — HI-REL PROGRAM OPTIONS

The 1N5831 is also available with two levels of extra testing similar to "TX" screening and including Group A and Group B inspection programs. Both the MBR5831H and MBR5831H1 go through 100% screening consisting of high temperature storage, temperature cycling, constant acceleration and hermetic seal testing prior to a sample being submitted to Group A and B inspection. After completion of Group B inspection, the MBR5831H is available without additional screening. MBR5831H1 devices are further processed through a high temperature reverse bias (HTRB) and forward burn-in. Consult factory for details.



OUTLINE DIMENSIONS





CASE 56-03
DO-203AA
METAL

STYLE 2:
TERM 1. ANODE
2. CATHODE

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED DO-4 OUTLINE SHALL APPLY.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	12.82	—	0.505
B	10.77	11.09	0.424	0.437
C	—	10.28	—	0.405
D	—	6.35	—	0.250
E	1.53	—	0.060	—
F	1.91	4.44	0.075	0.175
J	10.72	11.50	0.422	0.453
K	15.24	20.32	0.600	0.800
P	4.14	4.80	0.163	0.189
Q	1.53	2.41	0.060	0.095
R	6.74	10.76	0.265	0.424

1N5832
1N5833
1N5834

Designers Data Sheet

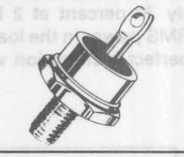
HOT CARRIER POWER RECTIFIER

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- High Surge Capacity

SCHOTTKY BARRIER RECTIFIERS

40 AMPERE
20,30,40 VOLTS



Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

3

*MAXIMUM RATINGS

Rating	Symbol	1N5832	1N5833	1N5834	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	24	36	48	Volts
Average Rectified Forward Current $V_{R(equiv)} \le 0.2\ V_{R(dc)}, T_C = 75^oC$	I_O	←	40	→	Amp
Ambient Temperature Rated $V_{R(dc)}$, $P_{F(AV)} = 0$, $R_{\theta JA} = 2.0^oC/W$	T_A	100	95	90	^oC
Non-Repetitive Peak Surge Current (surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	←	800 (for 1 cycle)	→	Amp
Operating and Storage Junction Temperature Range (Reverse voltage applied)	T_J, T_{stg}	←	-65 to +125	→	^oC
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	←	150	→	^oC

*THERMAL CHARACTERISTICS

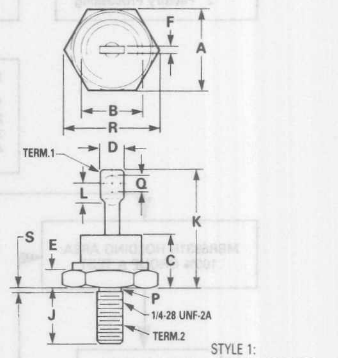
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	$^oC/W$

*ELECTRICAL CHARACTERISTICS ($T_C = 25^oC$ unless otherwise noted.)

Characteristic	Symbol	1N5832	1N5833	1N5834	Unit
Maximum Instantaneous Forward Voltage(1)	v_F				Volts
(i_F = 10 Amp)		0.360	0.370	0.380	
(i_F = 40 Amp)		0.520	0.550	0.590	
(i_F = 125 Amp)		0.980	1.080	1.180	
Maximum Instantaneous Reverse Current @ rated dc Voltage (1)	i_R	20	20	20	mA
$T_C = 100^oC$		150	150	150	

*Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.



STYLE 1:
TERM.1. CATHODE
2. ANODE (CASE)

NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

CASE 257-01
DO-203AB
METAL

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 0.2 V_{RWM}. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}\,P_{F(AV)} - R_{\theta JA}\,P_{R(AV)} \qquad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (125°C or the temperature at which thermal runaway occurs, whichever is lowest).

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JC}$ = Junction-to-ambient thermal resistance

Figures 1, 2 and 3 permit easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figures solve for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA}\,P_{R(AV)} \qquad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}\,P_{F(AV)} \qquad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where T_J = 125°C, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figures 1, 2 and 3 as a difference in the rate of change of the slope in the vicinity of 115°C. The data of Figures 1, 2 and 3 is based upon dc conditions. For use in common rectifier circuits, Table I indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in(PK)} \times F \qquad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the reverse characteristics of Schottky diodes.

Example: Find $T_{A(max)}$ for 1N5834 operated in a 12-Volt dc supply using a bridge circuit with capacitive filter such that I_{DC} = 30 A ($I_{F(AV)}$ = 15 A), $I_{(PK)}/I_{(AV)}$ = 10, Input Voltage = 10 V(rms), $R_{\theta JA}$ = 3°C/W.

Step 1: Find $V_{R(equiv)}$. Read F = 0.65 from Table I ∴
$V_{R(equiv)}$ = (10)(1.41)(0.65) = 9.18 V

Step 2: Find T_R from Figure 3. Read T_R = 118°C @ V_R = 9.18 V & $R_{\theta JA}$ = 3°C/W

Step 3: Find $P_{F(AV)}$ from Figure 4.†Read $P_{F(AV)}$ = 20 W @ $\frac{I_{(PK)}}{I_{(AV)}}$ = 10 & $I_{F(AV)}$ = 15 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 118-(3)(20) = 58°C

†Values given are for the 1N5834. Power is slightly lower for the other units because of their lower forward voltage.

TABLE I – VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave, Center Tapped (1),(2)	
Load	Resistive	Capacitive (1)	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.5	1.3	0.5	0.65	1.0	1.3
Square Wave	0.75	1.5	0.75	0.75	1.5	1.5

(1) Note that $V_{R(PK)} \approx 2\,V_{in(PK)}$

(2) Use line to center tap voltage for V_{in}.

FIGURE 1 – MAXIMUM REFERENCE TEMPERATURE – 1N5832

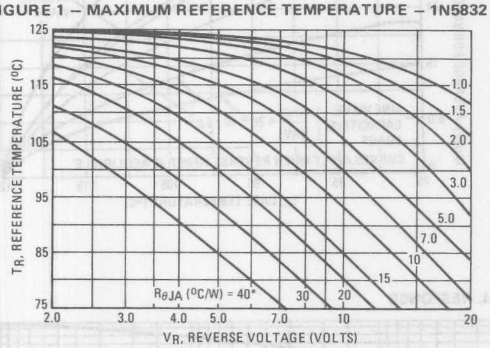


FIGURE 2 – MAXIMUM REFERENCE TEMPERATURE – 1N5833

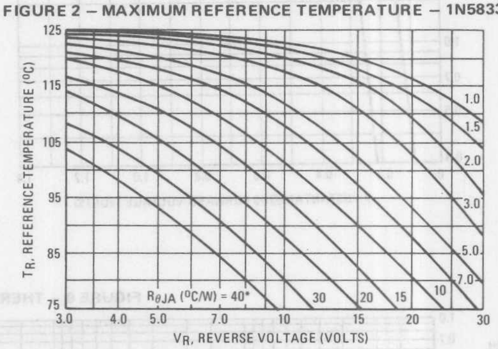
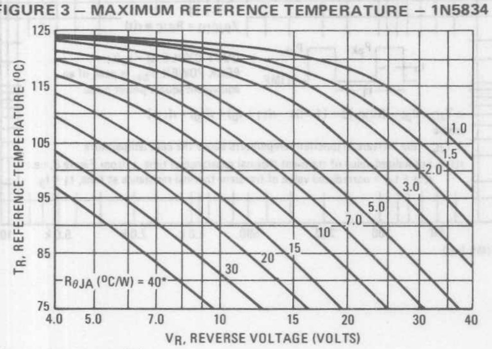
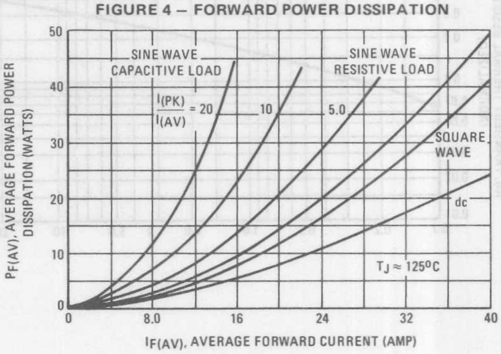


FIGURE 3 – MAXIMUM REFERENCE TEMPERATURE – 1N5834



*No external heat sink.

FIGURE 4 – FORWARD POWER DISSIPATION



3

FIGURE 5 — TYPICAL FORWARD VOLTAGE

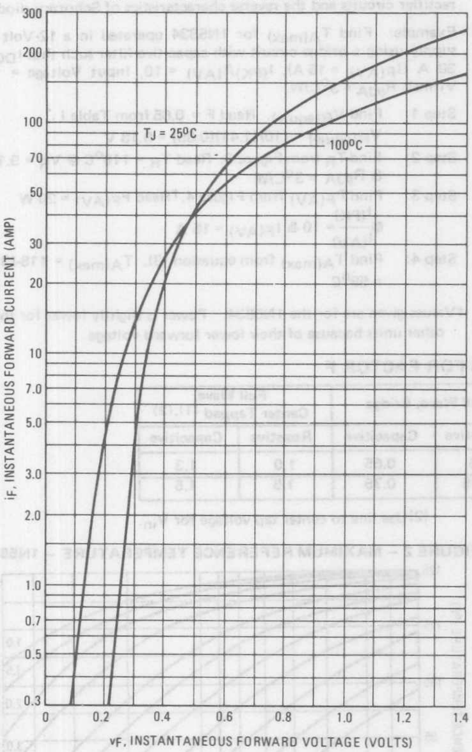


FIGURE 6 — MAXIMUM SURGE CAPABILITY

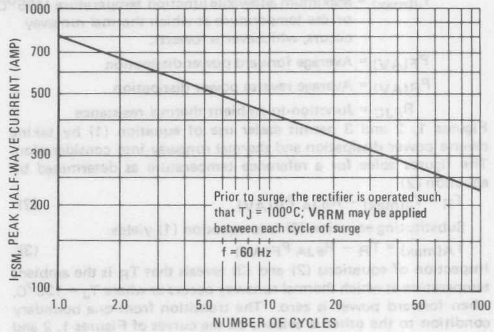


FIGURE 7 — CURRENT DERATING

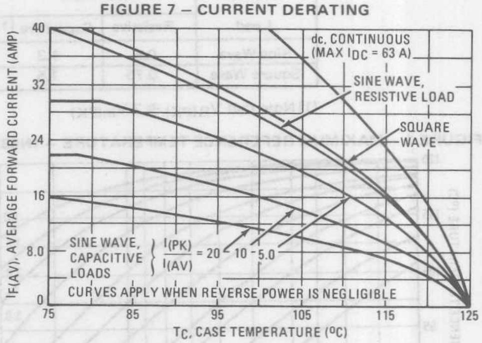


FIGURE 8 — THERMAL RESPONSE

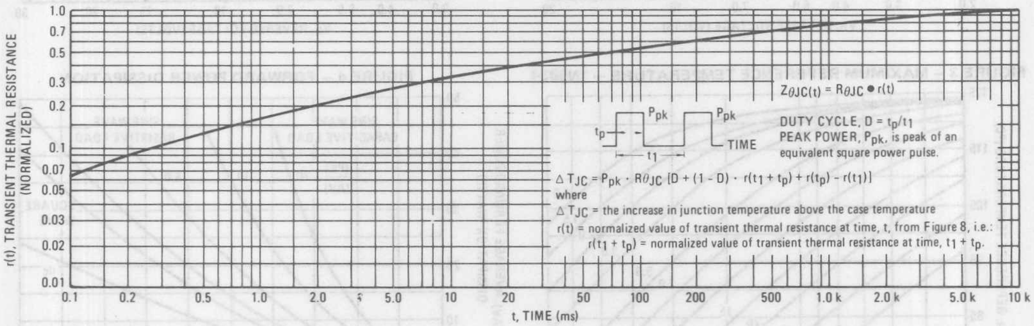


FIGURE 9 – NORMALIZED REVERSE CURRENT

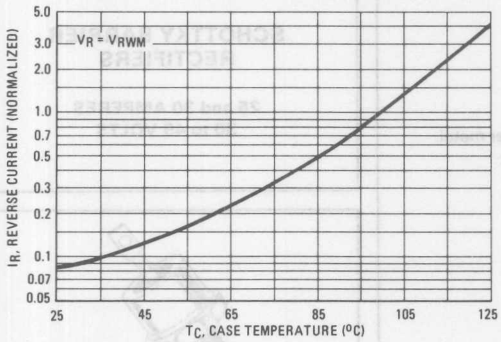


FIGURE 10 – TYPICAL REVERSE CURRENT

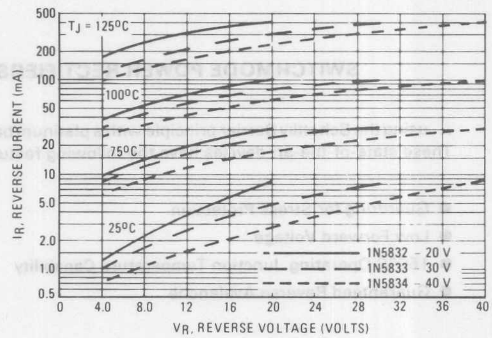
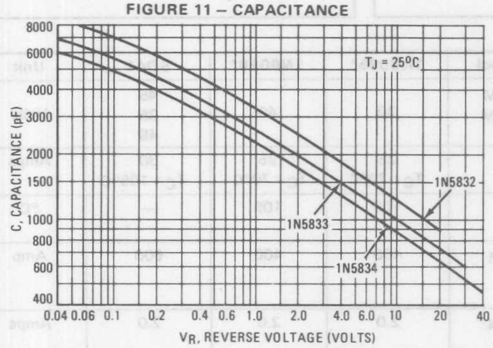


FIGURE 11 – CAPACITANCE



NOTE 2: HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 11).

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and terminal lead is readily solderable.

POLARITY: Cathode to Case

MOUNTING POSITION: Any

STUD TORQUE: 25 in. lb. Max

SOLDER HEAT: See Note 3

NOTE 3: SOLDER HEAT

The excellent heat transfer property of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires. Motorola suggests a heat sink be clamped between the eyelet and the body during any soldering operation.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N6095
1N6096
SD41

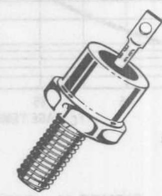
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature Capability
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

25 and 30 AMPERES
30 to 45 VOLTS



CASE 56-03
DO-203AA
METAL

MAXIMUM RATINGS

Rating	Symbol	1N6095*	1N6096*	SD41	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	40	45 35 45	Volts
Average Rectified Forward Current (Rated V_R)	I_O	25 $T_C = 70°C$	25 $T_C = 70°C$	30 $T_C = 105°C$	Amps
Case Temperature (Rated V_R)	T_C	105	105	—	°C
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	400	400	600	Amp
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 10. (1)	I_{RRM}	2.0	2.0	2.0	Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to + 125	-65 to + 125	-55 to + 150°C	°C
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	150	150	150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	—	—	700	V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	1N6095*	1N6096*	SD41	Unit
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	←	2.0	→	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	1N6095*	1N6096*	SD41	Unit
Maximum Instantaneous Forward Voltage (2) (i_F = 30 Amp, T_C = 125°C) (i_F = 78.5 Amp, T_C = 70°C)	v_F	— 0.86	— 0.86	0.55 —	Volts
Maximum Instantaneous Reverse Current (2) (Rated dc Voltage, T_C = 125°C)	i_R	250	250	125 @ V_R = 35 V	mA
Capacitance (100 kHz ≥ f ≥ 1.0 MHz)	C_t	6000 V_R = 1.0 V	6000 V_R = 1.0 V	2000 V_R = 5.0 V	pF

*Indicates JEDEC Registered Data.
(1) Not JEDEC requirement, but a Motorola product capability.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

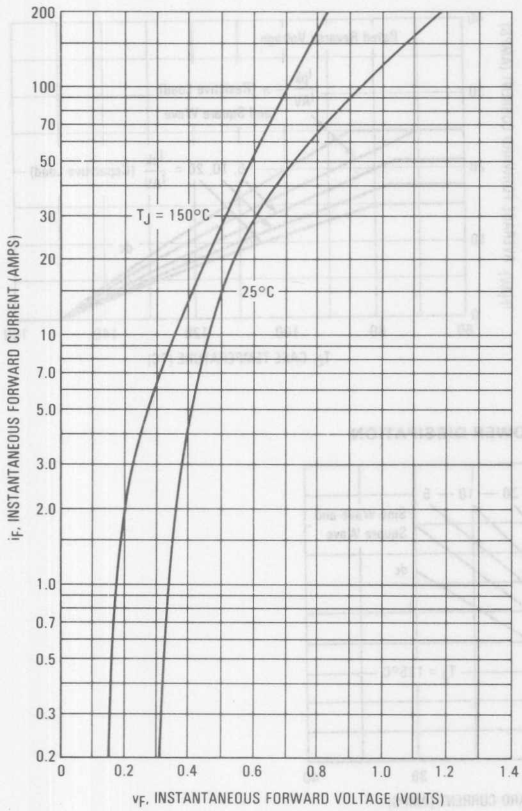


FIGURE 2 — TYPICAL REVERSE CURRENT

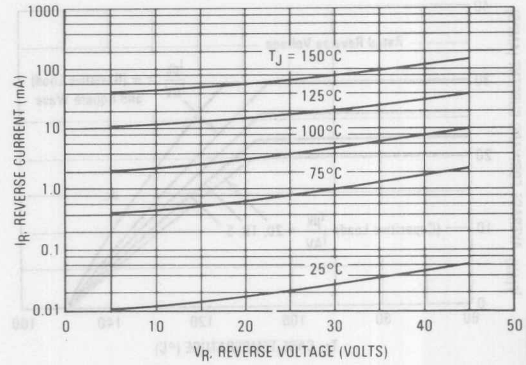
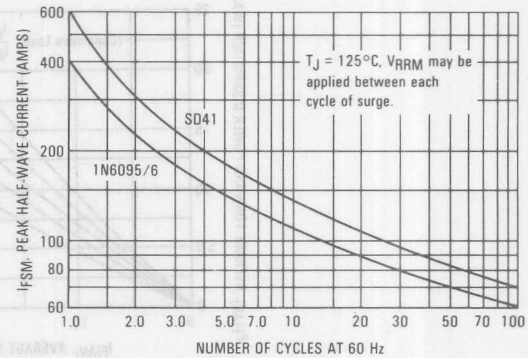


FIGURE 3 — MAXIMUM SURGE CAPABILITY

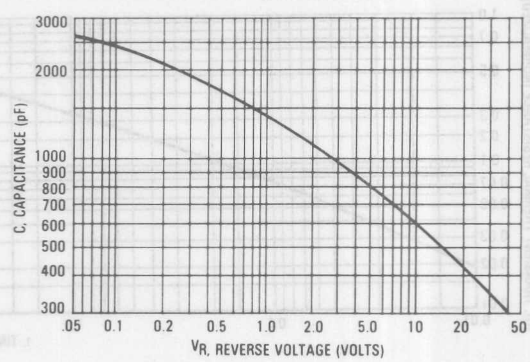


HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 4.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficieny is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 4 — CAPACITANCE



3

FIGURE 5 — SD41 CURRENT DERATING

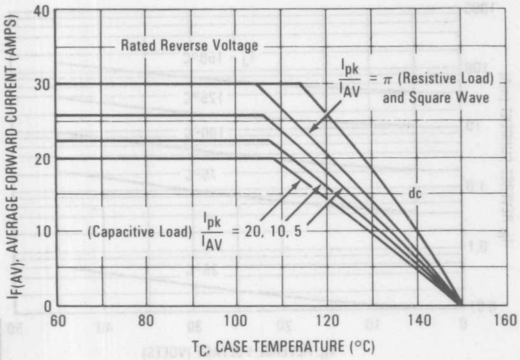


FIGURE 6 — 1N6095/6 CURRENT DERATING

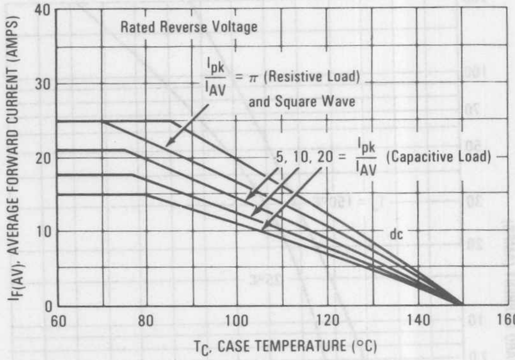


FIGURE 7 — FORWARD POWER DISSIPATION

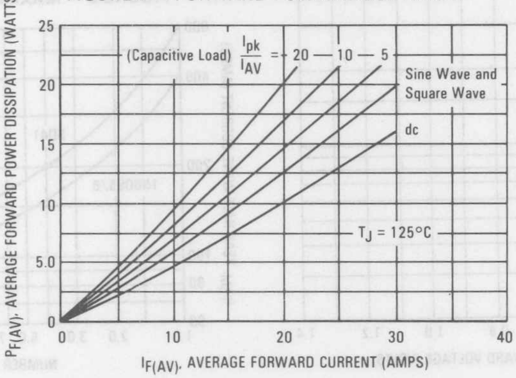
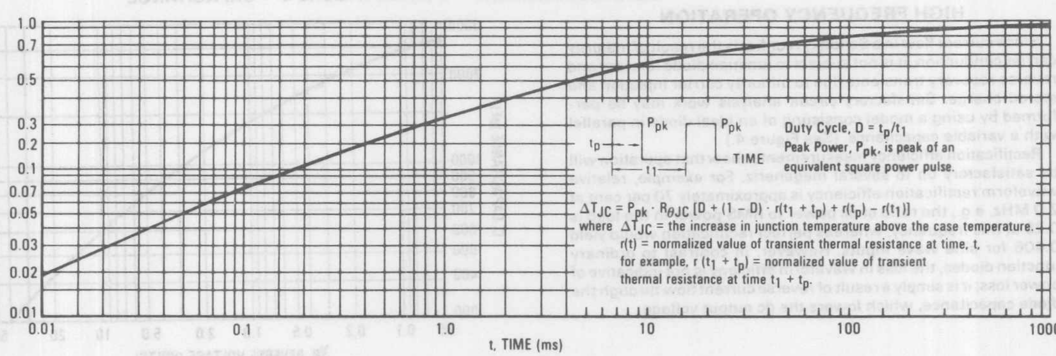


FIGURE 8 — THERMAL RESPONSE



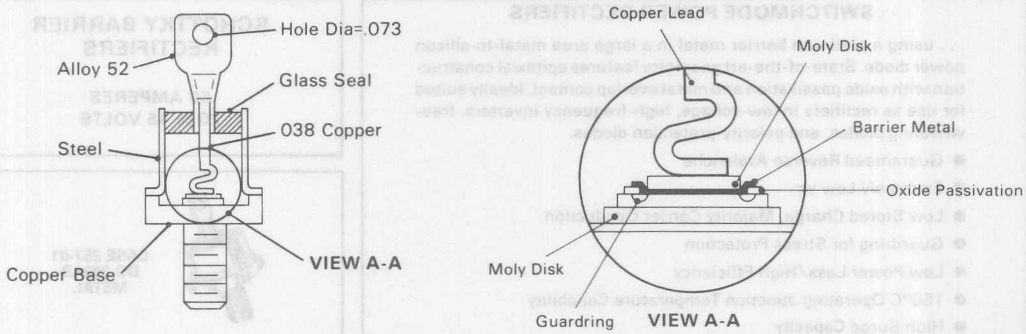


FIGURE 9 — SCHOTTKY RECTIFIER

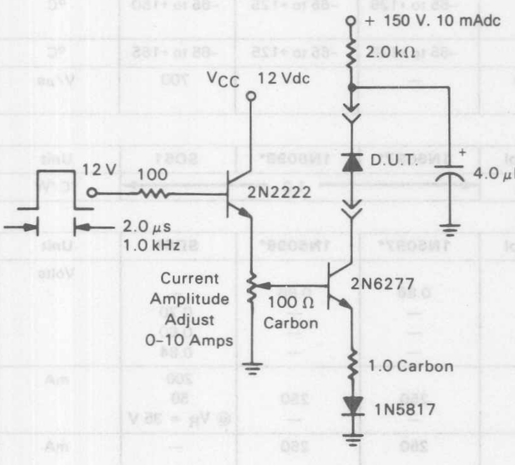
Motorola builds quality and reliability into its Schottky Rectifiers.

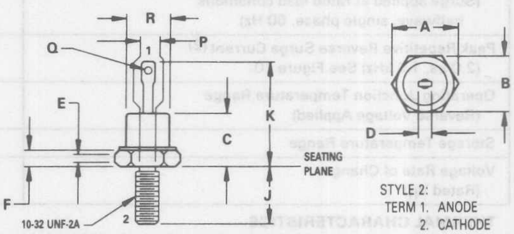
First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not required. The guardring also operates like a zener to absorb over-voltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The top copper lead is also stress-relieved. These two features give the unit the capability of passing stringent thermal fatigue tests for 5,000 cycles. The top copper lead provides a low resistance to current and therefore does not contribute to device heating; a heat sink should be used when attaching wires.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche.

FIGURE 10 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT





STYLE 2:
TERM 1. ANODE
2. CATHODE

Torque limit 25 in. lb. max

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED DO-4 OUTLINE SHALL APPLY.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	12.82	—	0.505
B	10.77	11.09	0.424	0.437
C	—	10.28	—	0.405
D	—	6.35	—	0.250
E	1.53	—	0.060	—
F	1.91	4.44	0.075	0.175
J	10.72	11.50	0.422	0.453
K	15.24	20.32	0.600	0.800
P	4.14	4.80	0.163	0.189
Q	1.53	2.41	0.060	0.095
R	6.74	10.76	0.265	0.424

CASE 56-03
DO-203AA
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N6097
1N6098
SD51

SWITCHMODE POWER RECTIFIERS

. . . using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Guaranteed Reverse Avalanche
- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Guardring for Stress Protection
- Low Power Loss/High Efficiency
- 150°C Operating Junction Temperature Capability
- High Surge Capacity

SCHOTTKY BARRIER RECTIFIERS

60 AMPERES
20 to 45 VOLTS

CASE 257-01
DO-203AB
METAL

3

MAXIMUM RATINGS

Rating	Symbol	1N6097*	1N6098*	SD51	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	40	45 35 45	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz)	I_{FRM}	—	—	120 T_C = 90°C	Amps
Average Rectified Forward Current (Rated V_R)	I_O	50 T_C = 70°C	50 T_C = 70°C	—	Amps
Case Temperature (Rated V_R)	T_C	115	115	—	°C
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	← 800 →			Amps
Peak Repetitive Reverse Surge Current (2) (2.0 μs, 1.0 kHz) See Figure 10.	I_{RRM}	← 2.0 →			Amps
Operating Junction Temperature Range (Reverse Voltage Applied)	T_J	-65 to +125	-65 to +125	-65 to +150	°C
Storage Temperature Range	T_{stg}	-65 to +125	-65 to +125	-65 to +165	°C
Voltage Rate of Change (Rated V_R)	dv/dt	—	—	700	V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	1N6097*	1N6098*	SD51	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	← 1.0 →			°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	1N6097*	1N6098*	SD51	Unit
Maximum Instantaneous Forward Voltage (2)	v_F				Volts
(i_F = 157 Amp, T_C = 70°C)		0.86	0.86		
(i_F = 60 Amp)		—	—	0.70	
(i_F = 60 Amp, T_C = 125°C)		—	—	0.60	
(i_F = 120 Amp, T_C = 125°C)		—	—	0.84	
Maximum Instantaneous Reverse Current (2)	i_R			200	mA
(Rated Voltage, T_C = 125°C)		250	250	50	
(Rated Voltage, T_C = 25°C)		—	—	@ V_R = 35 V	
DC Reverse Current (Rated Voltage, T_C = 115°C)	I_R	250	250	—	mA
Maximum Capacitance (100 kHz ≤ f ≤ 1.0 MHz)	C_t	7000 V_R = 1.0 Vdc	7000 V_R = 1.0 Vdc	4000 V_R = 5.0 Vdc	pF

*Indicates JEDEC Registered Data.
(1) Not a JEDEC requirement, but of Motorola product capability.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

FIGURE 1 — TYPICAL FORWARD VOLTAGE

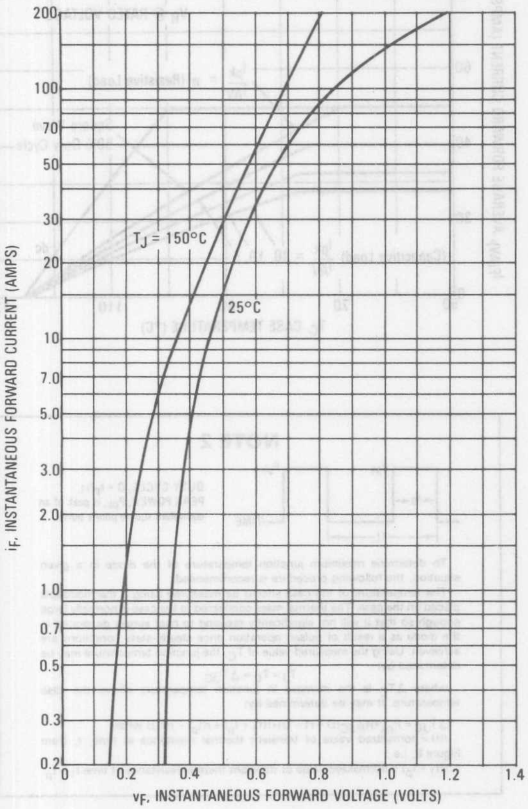


FIGURE 2 — TYPICAL REVERSE CURRENT

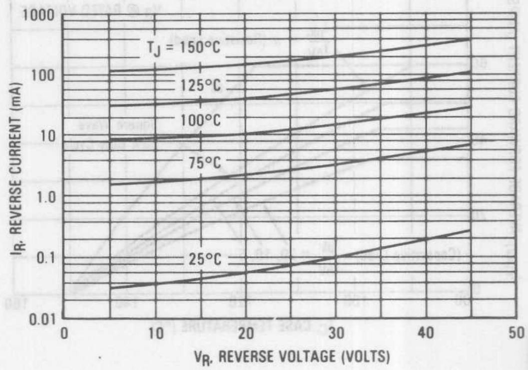
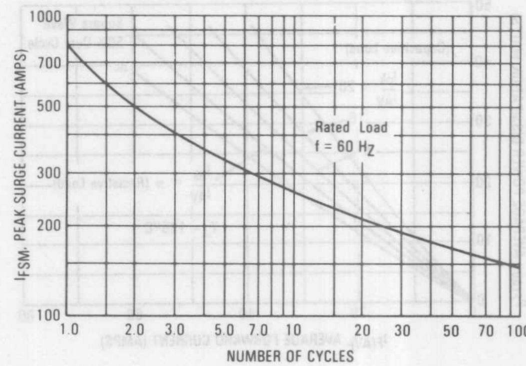


FIGURE 3 — TYPICAL SURGE CAPABILITY



NOTE 1
HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 4.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 4 — CAPACITANCE

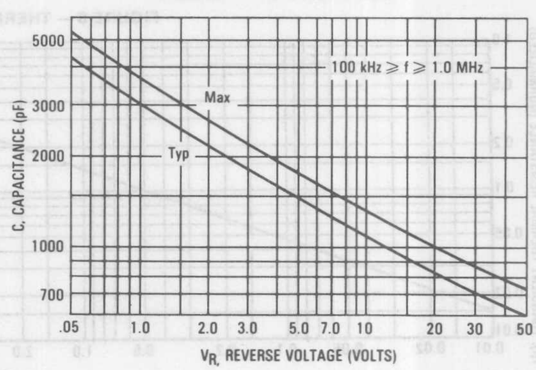


FIGURE 5 — CURRENT DERATING (SD51)

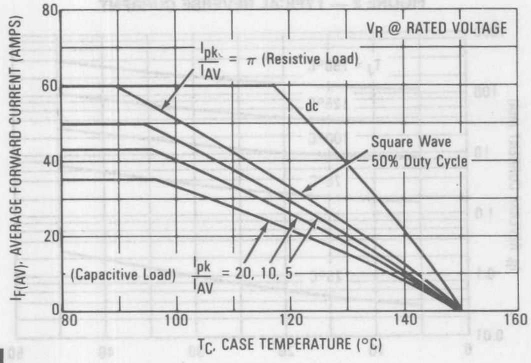


FIGURE 6 — CURRENT DERATING (1N6097/1N6098)

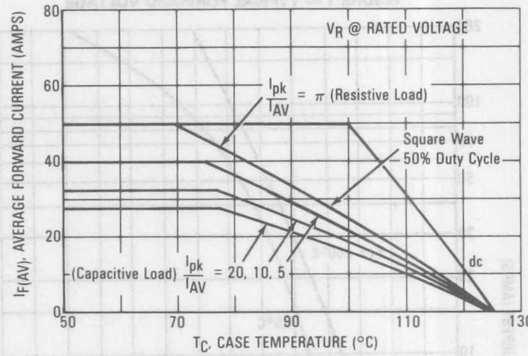


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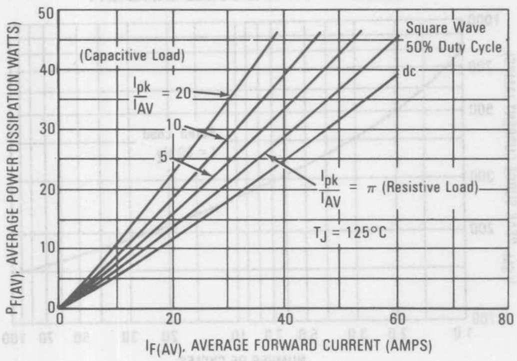
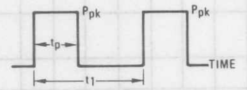
FIGURE 7 — POWER DISSIPATION



NOTE 2



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_C is the increase in junction temperature above the case temperature. It may be determined by:

$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC}[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$ where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 8, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 8 — THERMAL RESPONSE

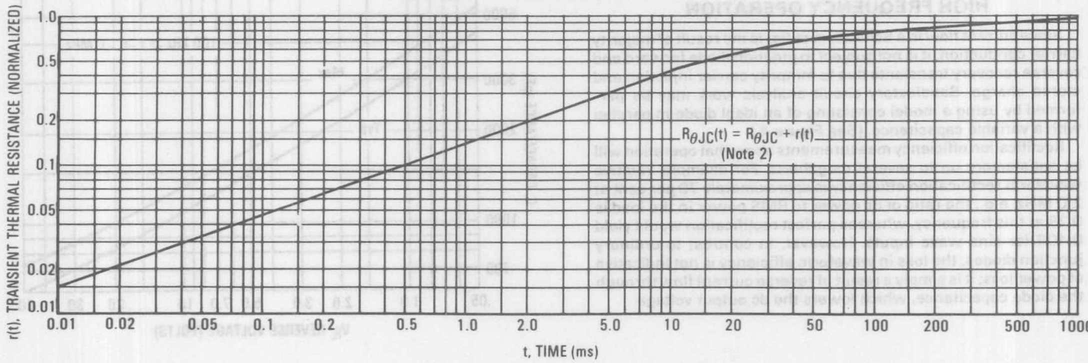
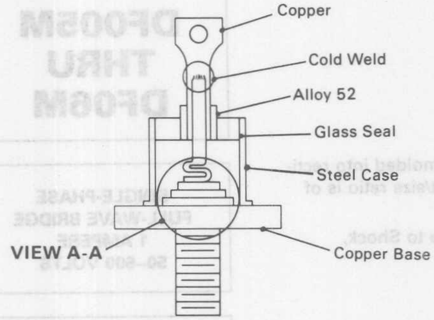


FIGURE 9 — SCHOTTKY RECTIFIER



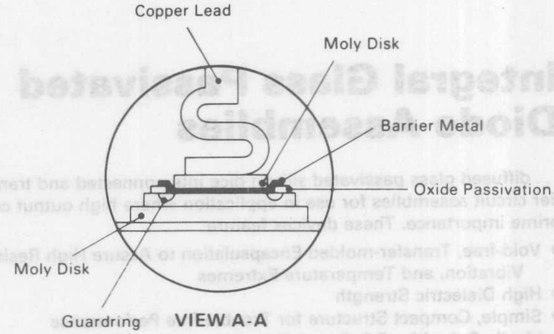


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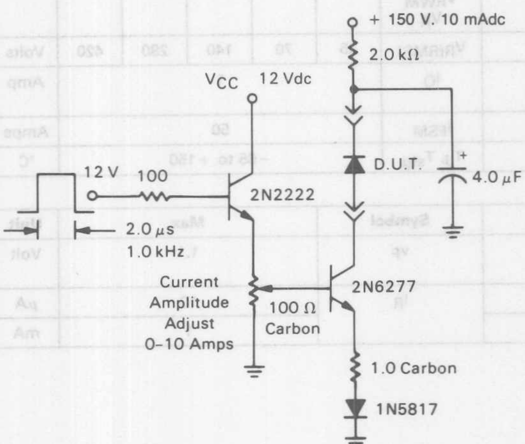
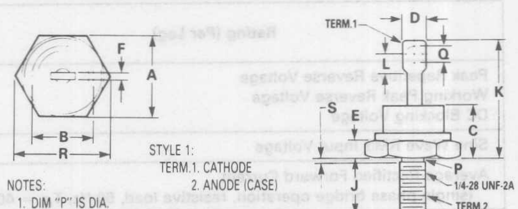
FIGURE 10 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT





STYLE 1:
TERM.1. CATHODE
2. ANODE (CASE)

NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

CASE 257-01
DO-203AB
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and terminal lead is readily solderable.

POLARITY: Cathode-to-Case

MOUNTING POSITION: Any

STUD TORQUE: 25 in.-lb Max

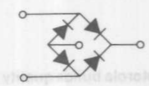
SOLDER HEAT: The excellent heat transfer property of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires. Motorola suggests a heat sink be clamped between the eyelet and the body during any soldering operation.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Integral Glass Passivated Diode Assemblies

DF005M THRU DF06M

SINGLE-PHASE FULL-WAVE BRIDGE 1 AMPERE 50–600 VOLTS



CASE 379-01 PLASTIC

... diffused glass passivated silicon dice interconnected and transfer molded into rectifier circuit assemblies for use in application where high output current/size ratio is of prime importance. These devices feature:

- Void-free, Transfer-molded Encapsulation to Assure High Resistance to Shock, Vibration, and Temperature Extremes
- High Dielectric Strength
- Simple, Compact Structure for Trouble-free Performance
- Ideally Suited for P.C. Board Mounting
- High Surge Capability — 50 Amps
- 4 Pin Dual-In Line Miniature Package
- Compatible with Automatic Assembly Techniques

3

Mechanical Characteristics:

CASE: Transfer molded plastic
POLARITY: Terminal designation on case
+ DC output
− DC output
~ AC input
MOUNTING POSITION: Any
WEIGHT: 1 gram (approx.)
TERMINALS: Readily solderable connections, corrosion resistant.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating (Per Leg)	Symbol	DF 005M	01M	02M	04M	06M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (single phase bridge operation, resistive load, 60 Hz, T_A = 40°C)	I_O			1			Amp
Non-Repetitive Peak Surge Current	I_{FSM}			50			Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}			−65 to +150			°C

ELECTRICAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
Maximum Instantaneous Forward Voltage Drop Per Bridge Diode at 1 Adc, T_J = 25°C		v_F	1.1	Volt
Maximum Reverse Current (Rated dc Blocking Voltage Per Diode)	@ T_A = 25°C	I_R	10	μA
	@ T_A = 100°C		1	mA

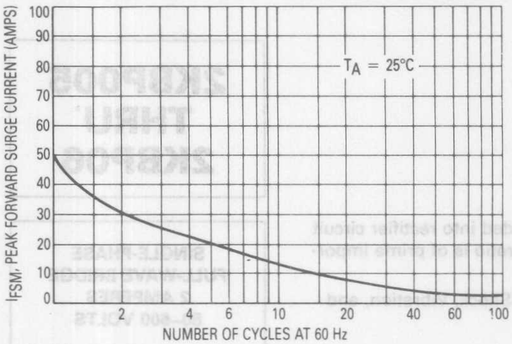


Figure 1. Maximum Non-Repetitive Forward Surge Current

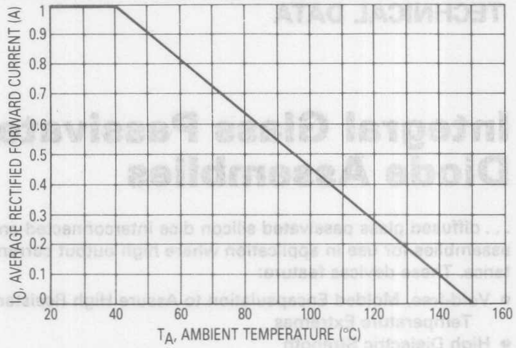


Figure 2. Forward Current Derating Curve

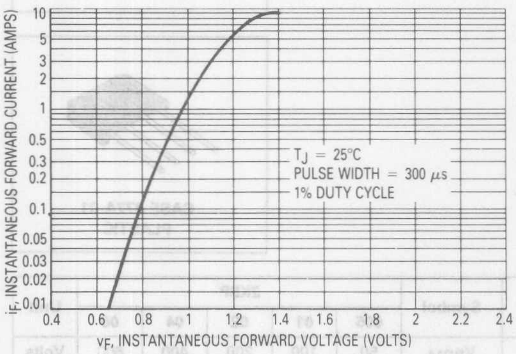


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

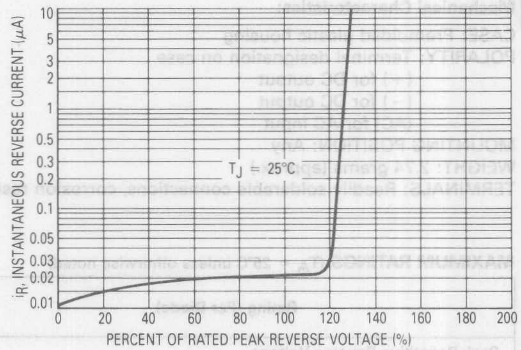
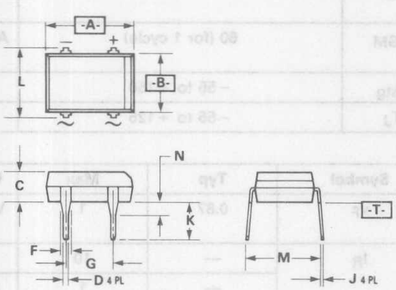


Figure 4. Typical Reverse Characteristics Per Diode

OUTLINE DIMENSIONS



NOTES:
1. POSITIONAL TOLERANCE FOR DIMENSION D (4 PL): ⌖ ϕ 0.25 (0.010) Ⓜ T A Ⓜ
2. POSITIONAL TOLERANCE FOR DIMENSION J (4 PL): ⌖ ϕ 0.25 (0.010) Ⓜ T B Ⓜ
3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
4. CONTROLLING DIMENSION: INCH.

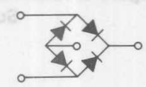
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.94	9.34	0.352	0.368
B	6.20	6.47	0.244	0.255
C	2.85	3.50	0.112	0.138
D	0.46	0.63	0.018	0.025
F	0.89	1.39	0.035	0.055
G	4.95 BSC		0.195 BSC	
J	0.18	0.30	0.007	0.012
K	3.92	4.19	0.154	0.165
L	7.37 BSC		0.290 BSC	
M	7.62	8.89	0.300	0.350
N	1.20	1.70	0.047	0.067

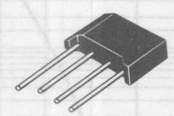
CASE 379-01
PLASTIC

Integral Glass Passivated Diode Assemblies

2KBP005 THRU 2KBP06

SINGLE-PHASE FULL-WAVE BRIDGE
2 AMPERES
50–600 VOLTS





CASE 377A-01
PLASTIC

3

. . . diffused glass passivated silicon dice interconnected and molded into rectifier circuit assemblies for use in application where high output current/size ratio is of prime importance. These devices feature:

- Void-free, Molded Encapsulation to Assure High Resistance to Shock, Vibration, and Temperature Extremes
- High Dielectric Strength
- Simple, Compact Structure for Trouble-free Performance
- Ideally Suited for P.C. Board Mounting
- High Surge Capability — 60 Amps
- Compatible with Automatic Assembly Techniques

Mechanical Characteristics:

CASE: Premolded plastic housing
POLARITY: Terminal designation on case
(+) for DC output
(−) for DC output
(AC) for AC input
MOUNTING POSITION: Any
WEIGHT: 2.74 grams (approx.)
TERMINALS: Readily solderable connections, corrosion resistant.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating (Per Diode)	Symbol	2KBP 005	2KBP 01	2KBP 02	2KBP 04	2KBP 06	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (single phase bridge operation, resistive load, 60 Hz, T_A = 50°C)	I_O	2					Amps
Non-Repetitive Peak Surge Current (Preceded and followed by rated current and voltage, T_A = 50°C)	I_{FSM}	60 (for 1 cycle)					Amps
Storage Junction Temperature Range	T_{stg}	−55 to +150					°C
Operating Temperature Range	T_J	−55 to +125					°C

ELECTRICAL CHARACTERISTICS

Characteristic		Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) (i_F = 1 Amp, T_J = 25°C)		v_F	0.87	1	Volts
Reverse Current at Rated DC Blocking Voltage Per Diode	@ T_A = 25°C	I_R	—	10	μA
	@ T_A = 100°C		—	1	mA

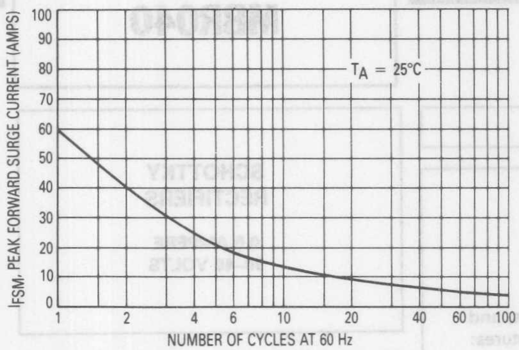


Figure 1. Maximum Non-Repetitive Forward Surge Current

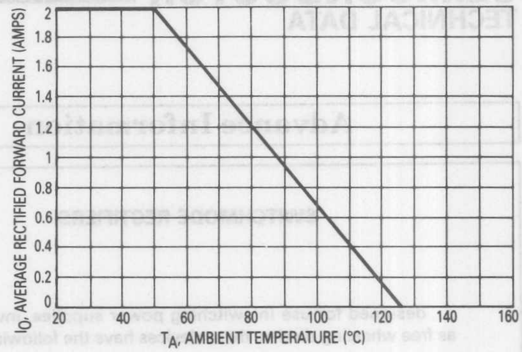


Figure 2. Forward Current Derating Curve

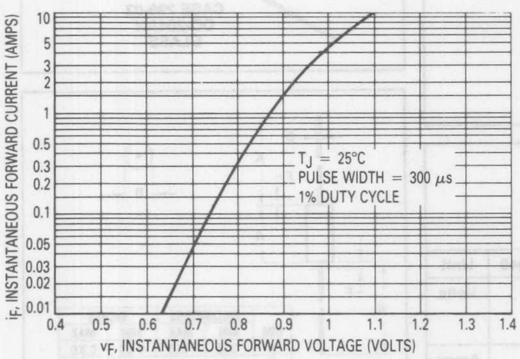


Figure 3. Typical Instantaneous Forward Per Bridge Diode

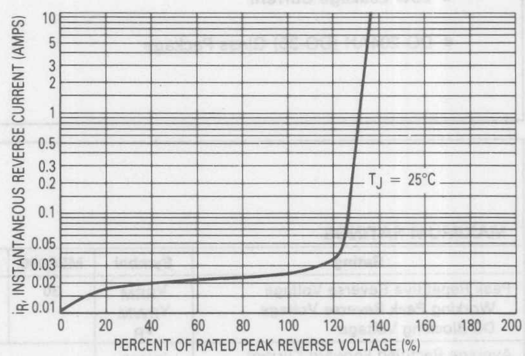
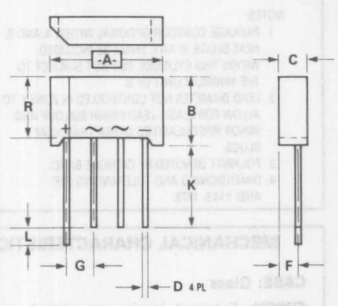


Figure 4. Typical Reverse Characteristics Per Diode

OUTLINE DIMENSIONS



NOTES:
1. POSITIONAL TOLERANCE FOR DIMENSION ϕD (4 PL):
   ⌖ ϕ 0.25 (0.010) Ⓜ A Ⓜ
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.75	16.07	0.620	0.633
B	9.55	9.90	0.376	0.390
C	3.81	4.08	0.150	0.161
D	0.74	0.83	0.029	0.033
F	2.67 BSC		0.105 BSC	
G	3.81 BSC		0.150 BSC	
K	9.91	13.41	0.390	0.528
L	1.50	3.50	0.059	0.138
R	8.85	9.01	0.335	0.355

CASE 377A-01
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR030
MBR040

3

Advance Information

SWITCHMODE RECTIFIERS

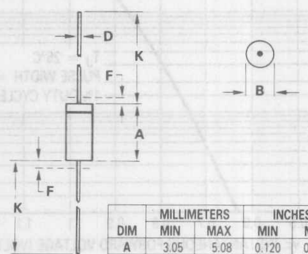
. . . designed for use in switching power supplies, inverters, and as free wheeling diodes, these devices have the following features:

- Low Forward Voltage
- Low Leakage Current
- DO-204AH (DO-35) Glass Package

SCHOTTKY RECTIFIERS

0.5 AMPERE
30–40 VOLTS

CASE 299-02
DO-204AH
GLASS



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	—	1.27	—	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

MAXIMUM RATINGS

Rating	Symbol	MBR030	MBR040	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	30	40	Volts
Average Rectified Forward Current (Rated V_R) $T_L = 90°C$, L = 3/8" $T_A = 60°C$, L = 3/8", (Mt. Method #1)	$I_{F(AV)}$	 0.5 0.5		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	15.0		Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	−65 to +150		

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Lead = 3/8"	$R_{\theta JL}$	180	190	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Foward Voltage (1) (i_F = 0.1 A, T_J = 25°C) (i_F = 0.5 A, T_J = 25°C)	v_F	 0.460 0.610	 0.500 0.750	Volts
Reverse Current (Rated dc Voltage, T_J = 150°C) (Rated dc Voltage, T_J = 25°C)	i_R	 0.6 0.003	 1.0 0.001	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

MECHANICAL CHARACTERISTICS

CASE: Glass
FINISH: External leads are plated and are readily solderable
POLARITY: Cathod indicated by polarity band.
WEIGHT: 0.2 Gram (approximately).
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/8" from case for 10 seconds.

FIGURE 1 — TYPICAL FORWARD VOLTAGE

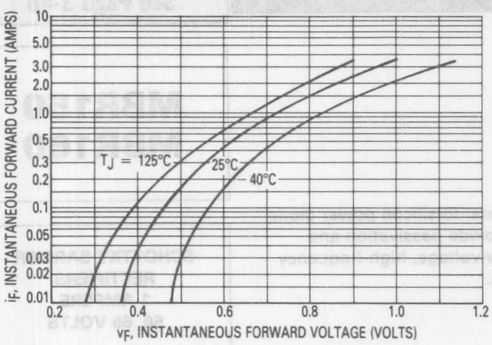


FIGURE 2 — CURRENT DERATING, PRINTED CIRCUIT BOARD MOUNTING

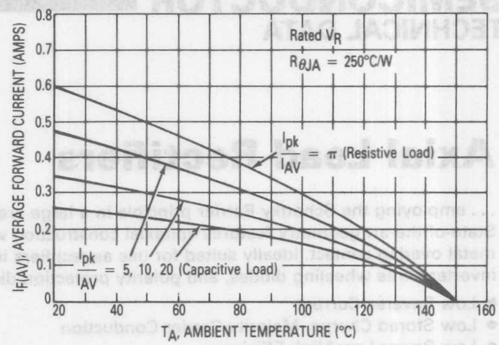


FIGURE 3 — TYPICAL CAPACITANCE

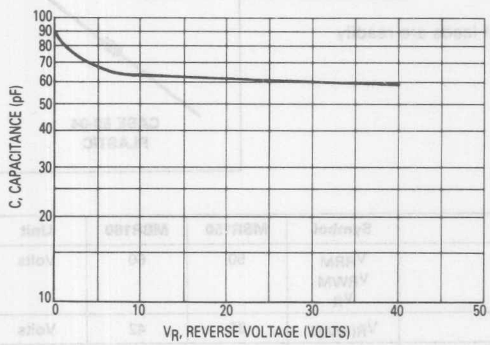


FIGURE 4 — CURRENT DERATING, LEAD TEMPERATURE

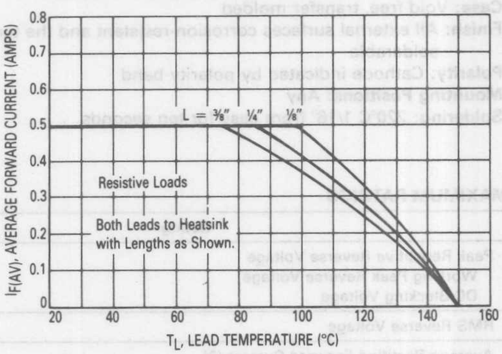
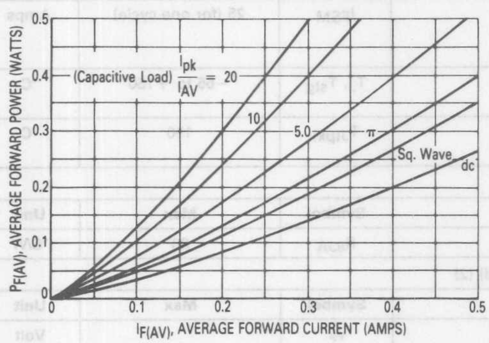


FIGURE 5 — FORWARD POWER DISSIPATION

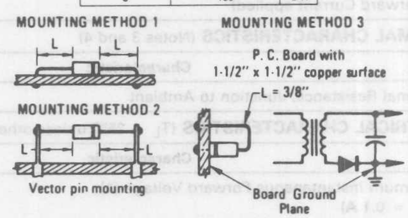


NOTE 1

Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR θ_{JA} IN STILL AIR

MOUNTING METHOD	1/8	1/4	3/8	$R_{\theta JA}$
1	200	225	250	°C/W
2	210	235	260	°C/W
3		150		°C/W



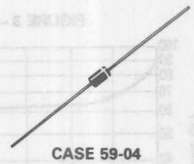
MBR150
MBR160

Axial Lead Rectifiers

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Low Reverse Current
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction

SCHOTTKY BARRIER RECTIFIERS
1 AMPERE
50, 60 VOLTS



CASE 59-04
PLASTIC

3

Mechanical Characteristics:
Case: Void free, transfer molded
Finish: All external surfaces corrosion-resistant and the terminal leads are readily solderable
Polarity: Cathode indicated by polarity band
Mounting Positions: Any
Soldering: 220°C 1/16″ from case for ten seconds

MAXIMUM RATINGS

Rating	Symbol	MBR150	MBR160	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	60	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	42	Volts
Average Rectified Forward Current (2) ($V_{R(equiv)} \leq 0.2\ V_R(dc)$, $T_L = 90°C$, $R_{\theta JA} = 80°C/W$, P.C. Board Mounting, see Note 3, $T_A = 55°C$)	I_O	1		Amp
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, half-wave, single phase, 60 Hz, $T_L = 70°C$)	I_{FSM}	25 (for one cycle)		Amps
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	T_J, T_{stg}	−65 to +150		°C
Peak Operating Junction Temperature (Forward Current applied)	$T_{J(pk)}$	150		°C

THERMAL CHARACTERISTICS (Notes 3 and 4)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	80	°C/W

ELECTRICAL CHARACTERISTICS ($T_L = 25°C$ unless otherwise noted) (2)

Characteristic	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (1) ($i_F = 0.1$ A) ($i_F = 1$ A) ($i_F = 3$ A)	v_F	 0.550 0.750 1.000	Volt
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1) ($T_L = 25°C$) ($T_L = 100°C$)	i_R	 0.5 5	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.
(2) Lead Temperature reference is cathode lead 1/32″ from case.

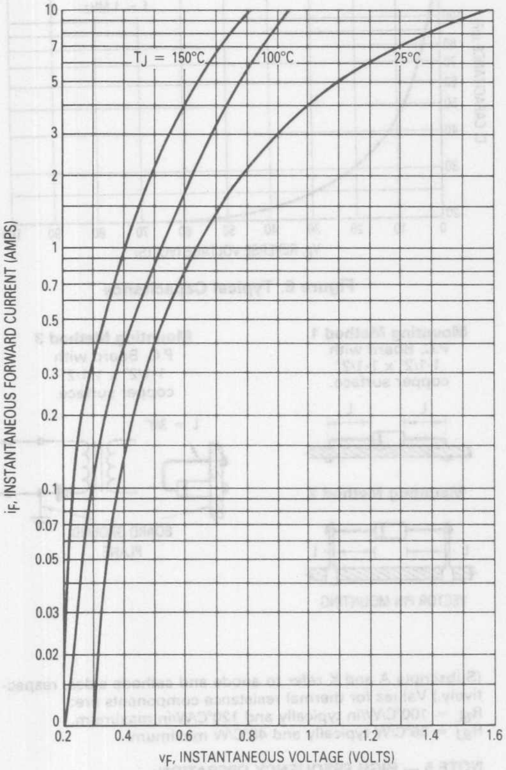


Figure 1. Typical Forward Voltage

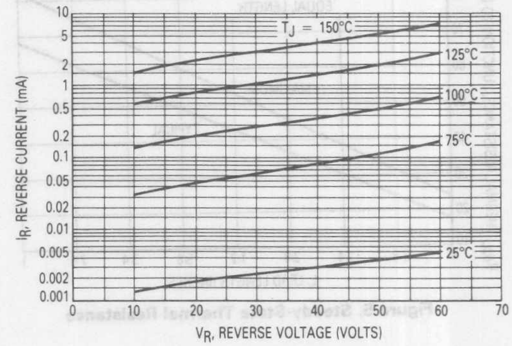


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

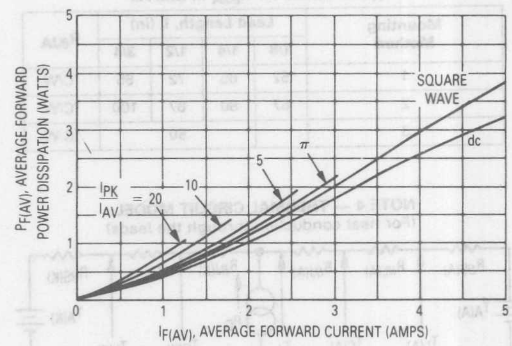


Figure 3. Forward Power Dissipation

THERMAL CHARACTERISTICS

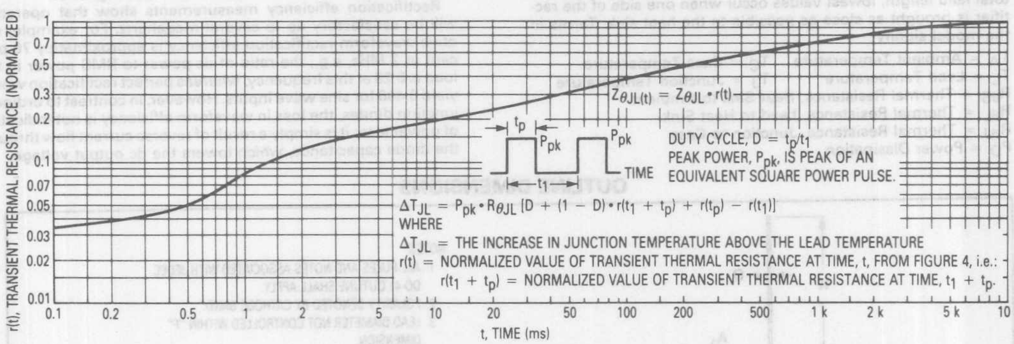


Figure 4. Thermal Response

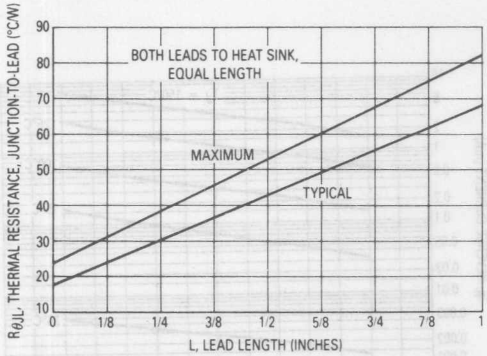


Figure 5. Steady-State Thermal Resistance

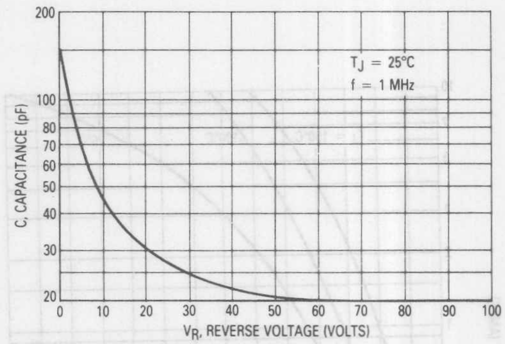


Figure 6. Typical Capacitance

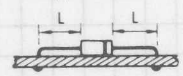
NOTE 3 — MOUNTING DATA:

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mounting shown is to be used as a typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

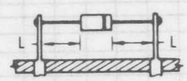
Typical Values for $R_{\theta JA}$ in Still Air

Mounting Method	Lead Length, L (in)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	52	65	72	85	°C/W
2	67	80	87	100	°C/W
3			50		°C/W

Mounting Method 1
P.C. Board with
1-1/2″ x 1-1/2″
copper surface.

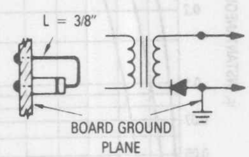


Mounting Method 2

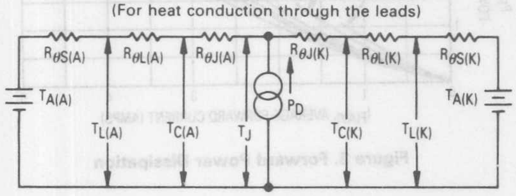


VECTOR PIN MOUNTING

Mounting Method 3
P.C. Board with
1-1/2″ x 1-1/2″
copper surface.



NOTE 4 — THERMAL CIRCUIT MODEL:
(For heat conduction through the leads)



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature T_C = Case Temperature
T_L = Lead Temperature T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Power Dissipation

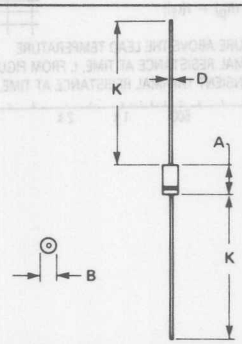
(Subscripts A and K refer to anode and cathode sides, respectively.) Values for thermal resistance components are:
$R_{\theta L}$ = 100°C/W/in typically and 120°C/W/in maximum.
$R_{\theta J}$ = 36°C/W typically and 46°C/W maximum.

NOTE 5 — HIGH FREQUENCY OPERATION:

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 6.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximatley 70 percent at 2 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss: it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

OUTLINE DIMENSIONS



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR320 MBR340 MBR330 MBR350 MBR360

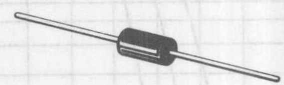
AXIAL LEAD RECTIFIERS

. . . employing the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free wheeling diodes, and polarity protection diodes.

- Extremely Low v_F
- Low Power Loss/High Efficiency
- Highly Stable Oxide Passivated Junction
- Low Stored Charge, Majority Carrier Conduction

SCHOTTKY BARRIER RECTIFIERS

3.0 AMPERES
20, 30, 40, 50, 60 VOLTS



CASE 267-02
PLASTIC

3

MAXIMUM RATINGS

Rating	Symbol	MBR320	MBR330	MBR340	MBR350	MBR360	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	V
Average Rectified Forward Current $T_A = 65°C$ ($R_{\theta JA} = 28°C/W$, P.C. Board Mounting, see Note 3)	I_O			3.0			A
Nonrepetitive Peak Surge Current (2) (Surge applied at rated load conditions, half wave, single phase 60 Hz, $T_L = 75°C$)	I_{FSM}			80			A
Operating and Storage Junction Temperature Range (Reverse Voltage applied)	T_J, T_{stg}			−65 to 150°C			°C
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$			150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient, (see Note 3, Mounting Method 3)	$R_{\theta JA}$	28	°C/W

ELECTRICAL CHARACTERISTICS ($T_L = 25°C$ unless otherwise noted)(2)

Characteristic	Symbol	MBR320	MBR330	MBR340	MBR350	MBR360	Unit
Maximum Instantaneous Forward Voltage (1) ($i_F = 1.0$ Amp) ($i_F = 3.0$ Amp) ($i_F = 9.4$ Amp)	v_F		 0.500 0.600 0.850		 0.600 0.740 1.080		V
Maximum Instantaneous Reverse Current @ Rated dc Voltage (1) $T_L = 25°C$ $T_L = 100°C$	i_R			 0.60 20			mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.
(2) Lead Temperature reference is cathode lead 1/32″ from case.

FIGURE 1 — TYPICAL FORWARD VOLTAGE

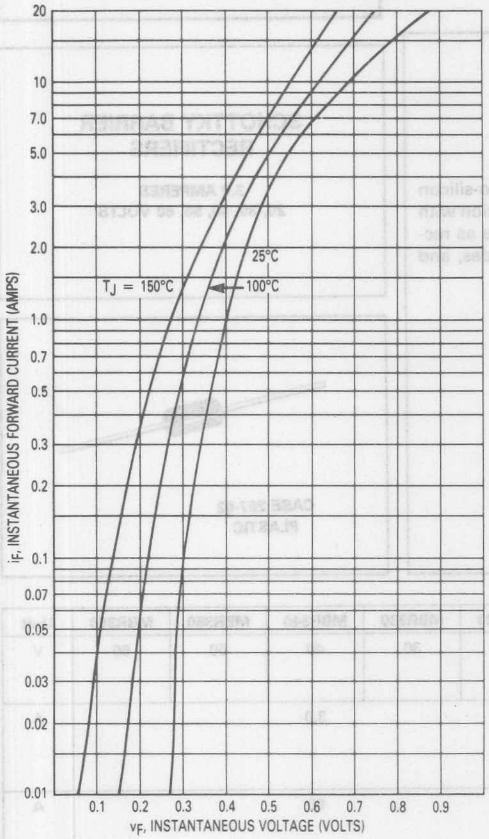
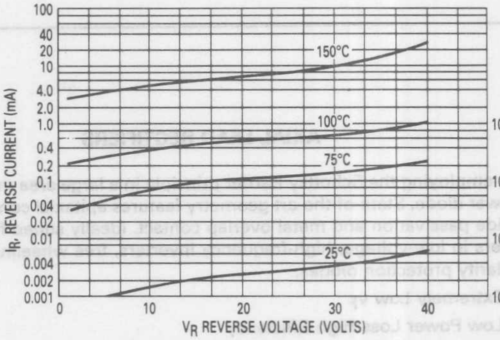


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING
(MOUNTING METHOD #3 PER NOTE 3)

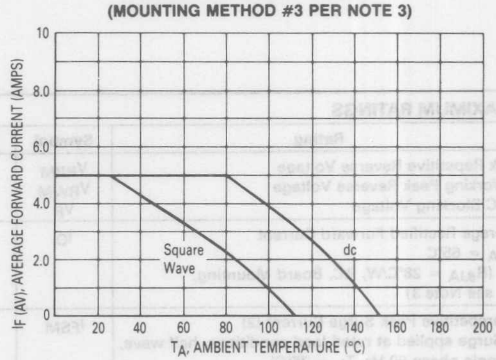


FIGURE 4 — POWER DISSIPATION

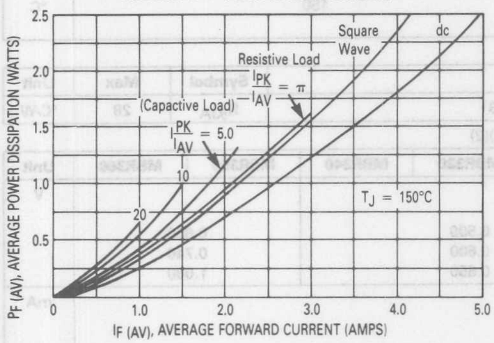
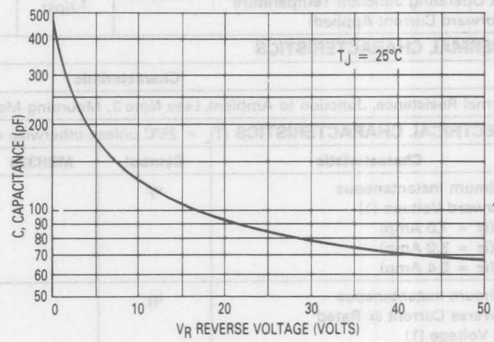


FIGURE 5 — TYPICAL CAPACITANCE



MBR350 AND 360

FIGURE 6 — TYPICAL FORWARD VOLTAGE

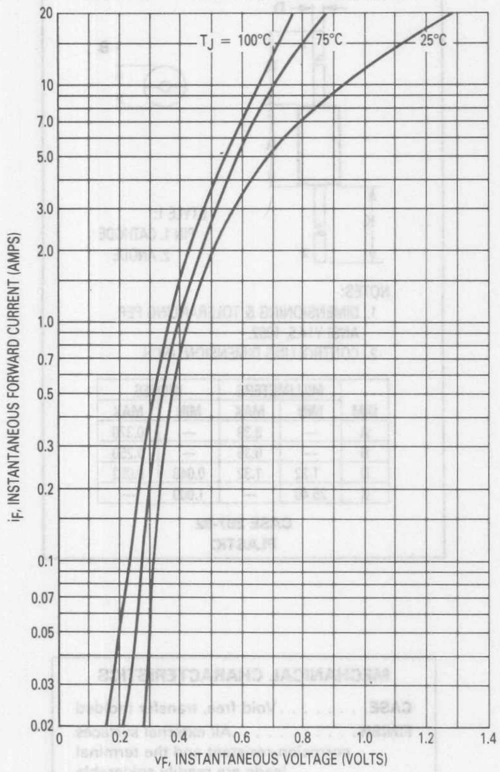
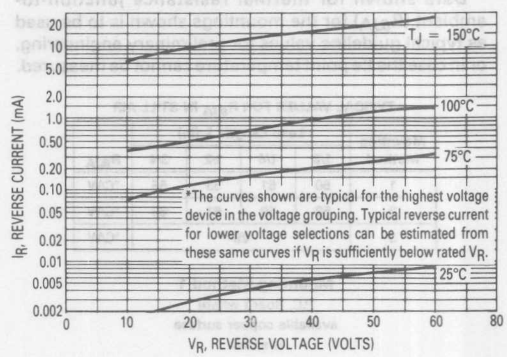


FIGURE 7 — TYPICAL REVERSE CURRENT*



3

FIGURE 8 — CURRENT DERATING AMBIENT (MOUNTING METHOD #3 PER NOTE 3)

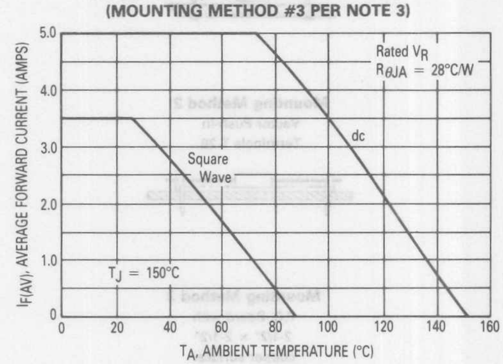


FIGURE 9 — POWER DISSIPATION

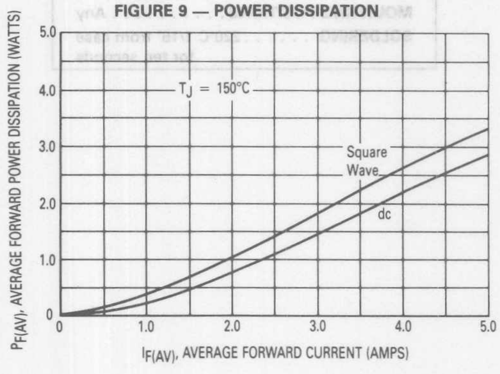
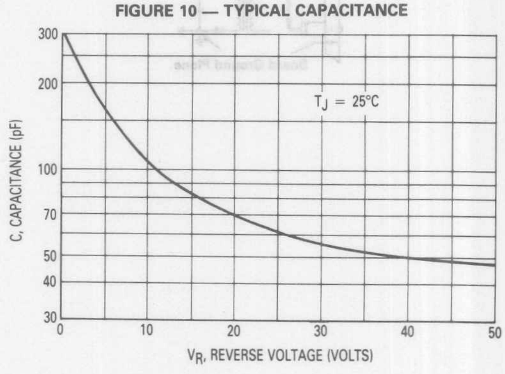


FIGURE 10 — TYPICAL CAPACITANCE



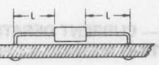
NOTE 3 — MOUNTING DATA

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering, or in case the tie point temperature cannot be measured.

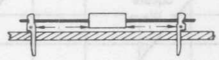
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

Mounting Method	Lead Length, L (in)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3		28			°C/W

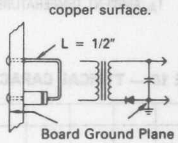
Mounting Method 1
P.C. Board where available copper surface is small.



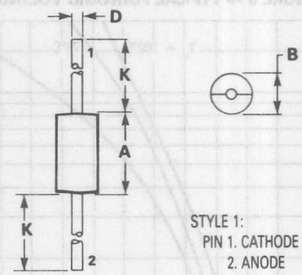
Mounting Method 2
Vector Push-In Terminals T-28



Mounting Method 3
P.C. Board with 2-1/2" × 2-1/2" copper surface.



OUTLINE DIMENSIONS



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

MECHANICAL CHARACTERISTICS

CASE. . . . . Void free, transfer molded
FINISH. . . . . .All external surfaces corrosion-resistant and the terminal leads are readily solderable
POLARITY. . . . . Cathode indicated by polarity band
MOUNTING POSITIONS. . . . . Any
SOLDERING . . . . . .220°C 1/16" from case for ten seconds

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR320P MBR330P
MBR340P
See Page 3-50

MBR735
MBR745

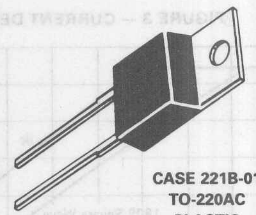
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, VO at 1/8″

SCHOTTKY BARRIER RECTIFIERS

7.5 AMPERES
35 and 45 VOLTS



CASE 221B-01
TO-220AC
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR735	MBR745	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 105°C$	$I_{F(AV)}$	7.5	7.5	Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 105°C$	I_{FRM}	15	15	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Rating	Symbol	MBR735	MBR745	Unit
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	3.0	°C/W
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	60	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	MBR735	MBR745	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 7.5 Amp, $T_C = 125°C$) (i_F = 15 Amp, $T_C = 125°C$) (i_F = 15 Amp, $T_C = 25°C$)	v_F	 0.57 0.72 0.84	 0.57 0.72 0.84	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 125°C$) (Rated dc Voltage, $T_C = 25°C$)	i_R	 15 0.1	 15 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ⩽ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

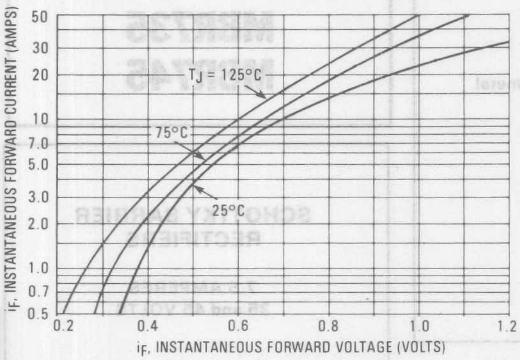
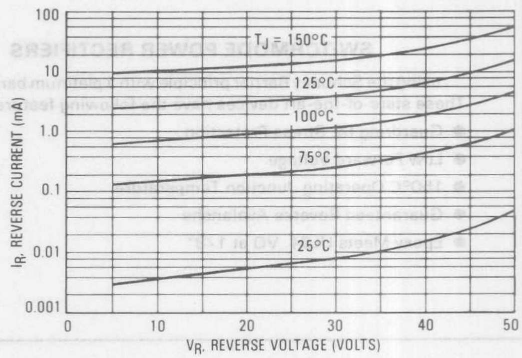


FIGURE 2 — TYPICAL REVERSE CURRENT



3

FIGURE 3 — CURRENT DERATING, CASE

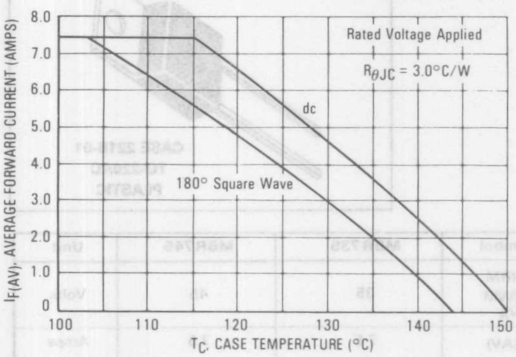


FIGURE 4 — CURRENT DERATING, AMBIENT

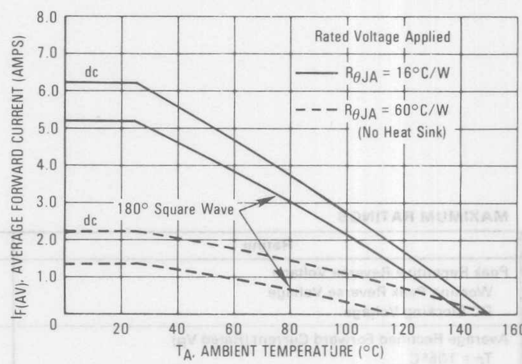
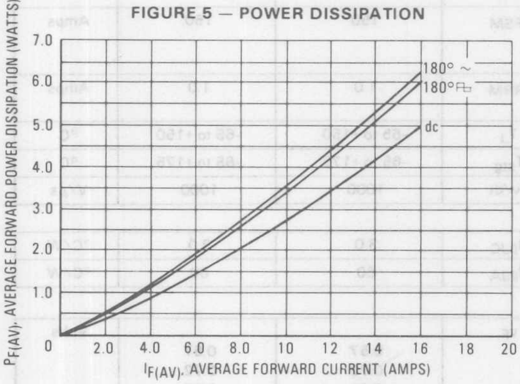
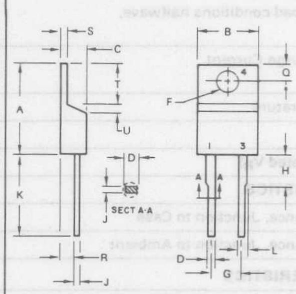


FIGURE 5 — POWER DISSIPATION





STYLE 1
PIN 1 CATHODE
2 N/A
3 ANODE
4 CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

POLARITY: CATHODE-TO-CASE

CASE 221B-01

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR1035
MBR1045

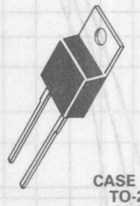
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, V0 at 1/8″

SCHOTTKY BARRIER RECTIFIERS

10 AMPERES
20 to 45 VOLTS



CASE 221B-01
TO-220AC
PLASTIC

3

MAXIMUM RATINGS

Rating	Symbol	MBR1035	MBR1045	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 135°C$	$I_{F(AV)}$	10	10	Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 135°C$	I_{FRM}	20	20	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 12	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	-65 to + 150	-65 to + 150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	MBR1035	MBR1045	Unit
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	2.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	MBR1035	MBR1045	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 10 A, T_C = 125°C) (i_F = 20 A, T_C = 125°C) (i_F = 20 A, T_C = 25°C)	v_F	 0.57 0.72 0.84	 0.57 0.72 0.84	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 15 0.1	 15 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — MAXIMUM FORWARD VOLTAGE

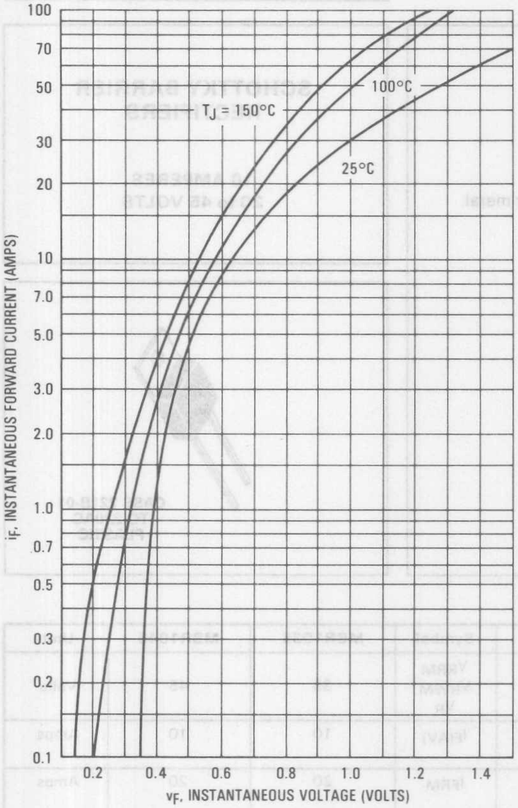


FIGURE 2 — TYPICAL FORWARD VOLTAGE

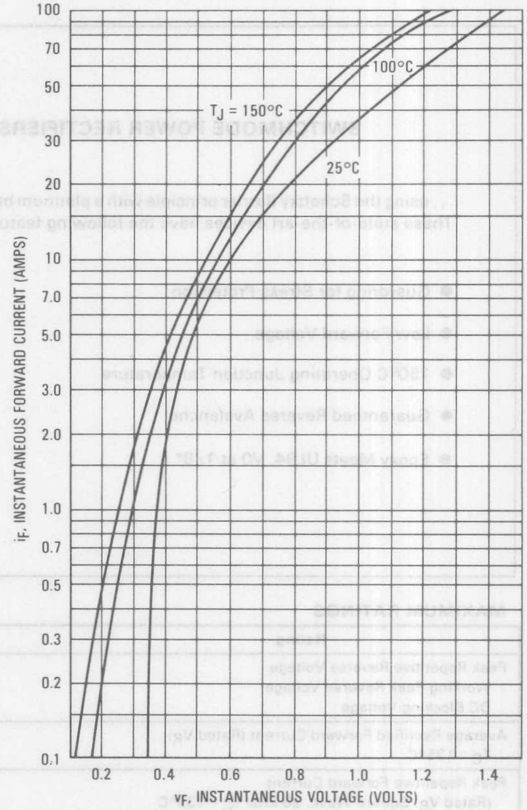


FIGURE 3 — MAXIMUM REVERSE CURRENT

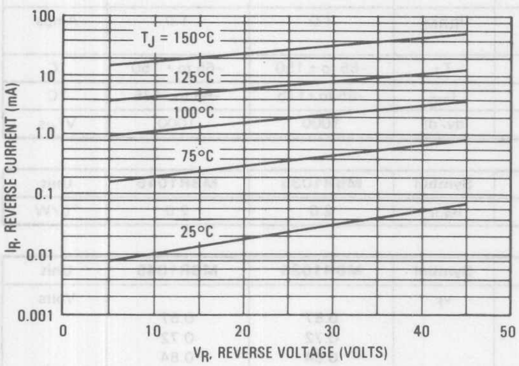


FIGURE 4 — MAXIMUM SURGE CAPABILITY

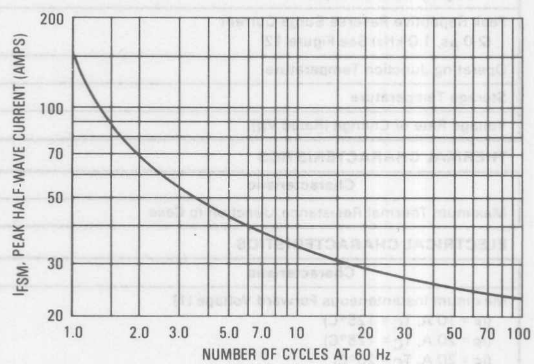


FIGURE 5 — CURRENT DERATING, INFINITE HEATSINK

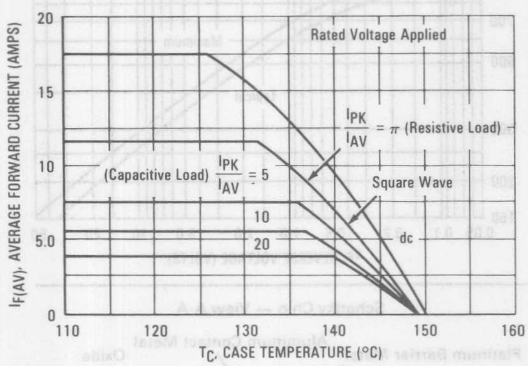


FIGURE 6 — CURRENT DERATING, $R_{\theta JA}$ = 16° C/W

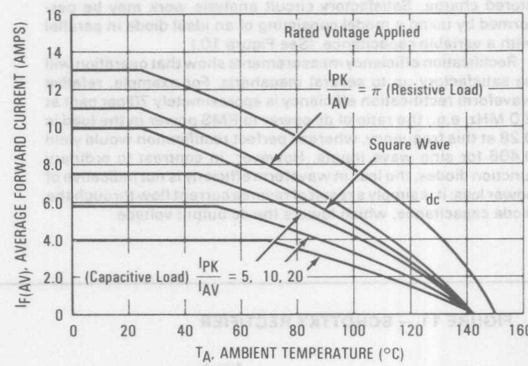


FIGURE 7 — FORWARD POWER DISSIPATION

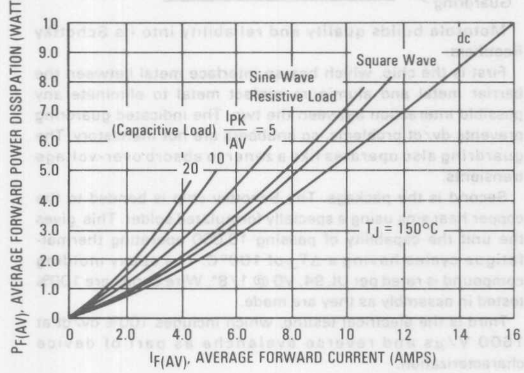


FIGURE 8 — CURRENT DERATING, FREE AIR

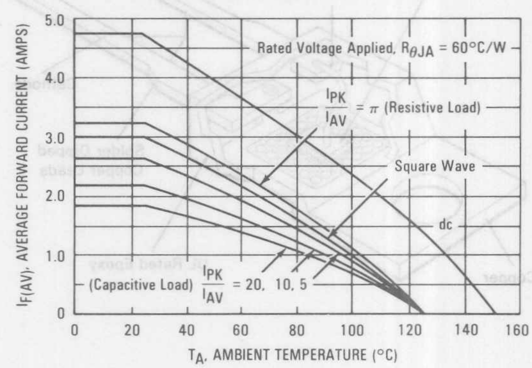
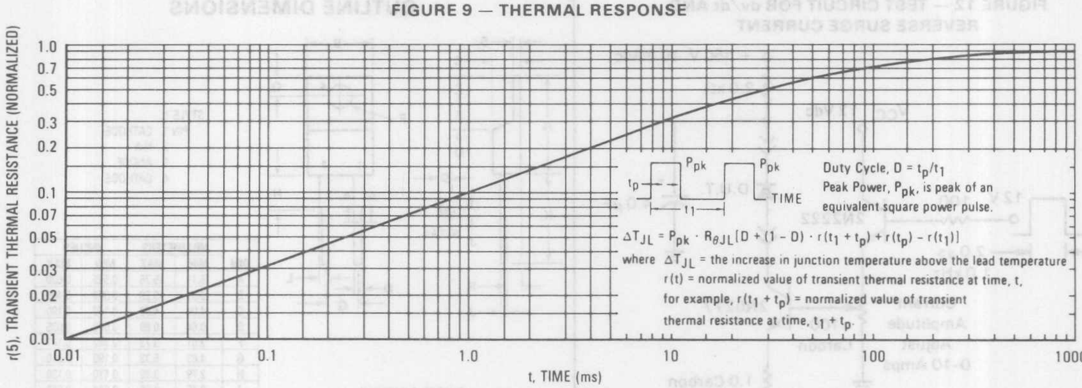


FIGURE 9 — THERMAL RESPONSE



HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficieny is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 10 — CAPACITANCE

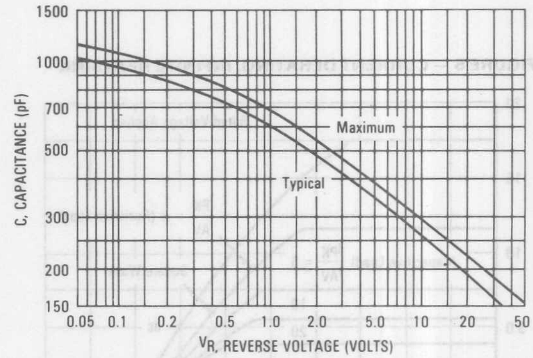
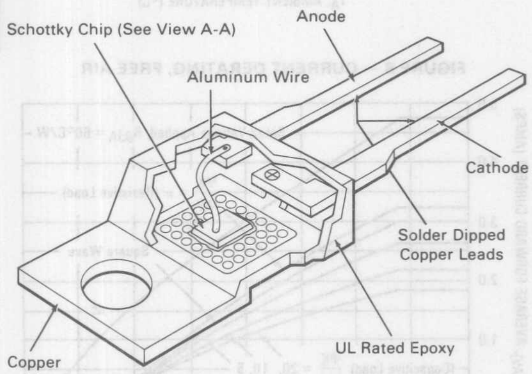
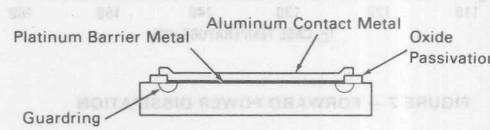


FIGURE 11 — SCHOTTKY RECTIFIER





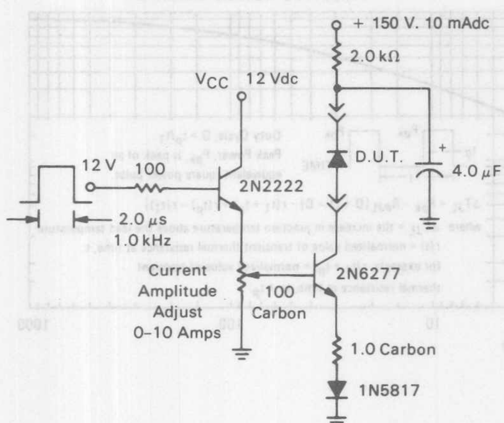
Motorola builds quality and reliability into its Schottky Rectifiers.

First is the chip, which has an interface metal between the barrier metal and aluminum-contact metal to eliminate any possible interaction between the two. The indicated guardring prevents dv/dt problems, so snubbers are not mandatory. The guardring also operates like a zener to absorb over-voltage transients.

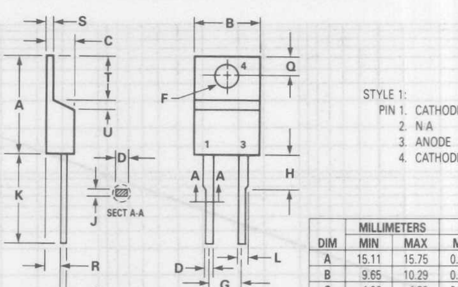
Second is the package. The Schottky chip is bonded to the copper heat sink using a specially formulated solder. This gives the unit the capability of passing 10,000 operating thermal-fatigue cycles having a ΔT_J of 100°C. The epoxy molding compound is rated per UL 94, V0 @ 1/8". Wire bonds are 100% tested in assembly as they are made.

Third is the electrical testing, which includes 100% dv/dt at 1600 V/μs and reverse avalanche as part of device characterization.

FIGURE 12 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT



OUTLINE DIMENSIONS



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

CASE 221B-01
TO-220AC
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

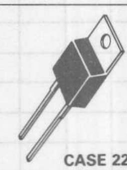
Switchmode Power Rectifiers

MBR1060
MBR1070
MBR1080
MBR1090
MBR10100

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guard-Ring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, VO at 1/8″
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction

SCHOTTKY BARRIER RECTIFIERS
10 AMPERES
60–100 VOLTS



CASE 221B-01
TO-220AC
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR 1060	MBR 1070	MBR 1080	MBR 1090	MBR 10100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	70	80	90	100	Volts
Average Rectified Forward Current (Rated V_R) T_C = 133°C	$I_{F(AV)}$			10			Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) T_C = 133°C	I_{FRM}			20			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}			150			Amps
Peak Repetitive Reverse Surge Current (2 µs, 1 kHz)	I_{RRM}			0.5			Amp
Operating Junction Temperature	T_J			−65 to +150			°C
Storage Temperature	T_{stg}			−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt			1000			V/µs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2 60	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 10 Amp, T_C = 125°C) (i_F = 10 Amp, T_C = 25°C) (i_F = 20 Amp, T_C = 125°C) (i_F = 20 Amp, T_C = 25°C)	v_F	 0.7 0.8 0.85 0.95	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 150 0.15	mA

(1) Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2%.

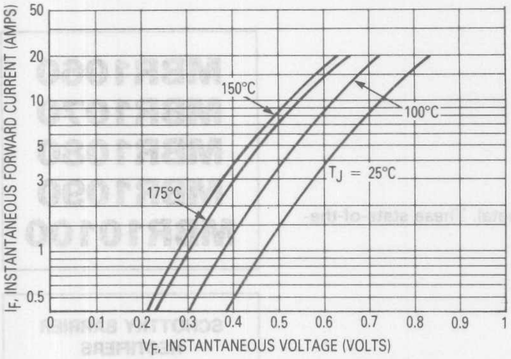


Figure 1. Typical Forward Voltage

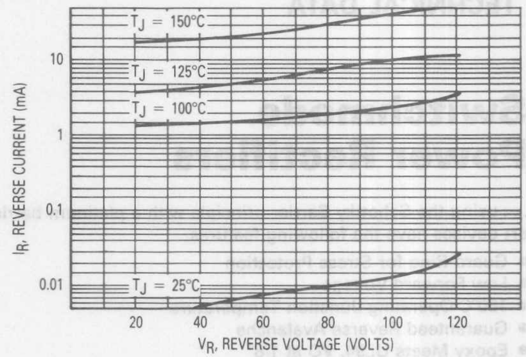


Figure 2. Typical Reverse Current

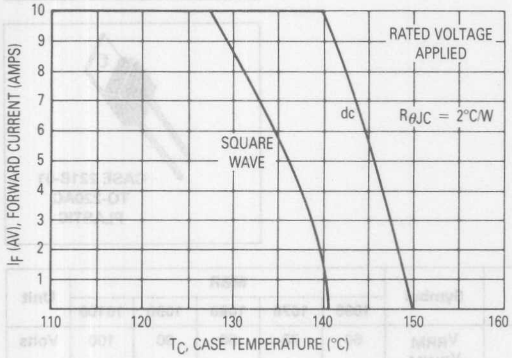


Figure 3. Current Derating, Case

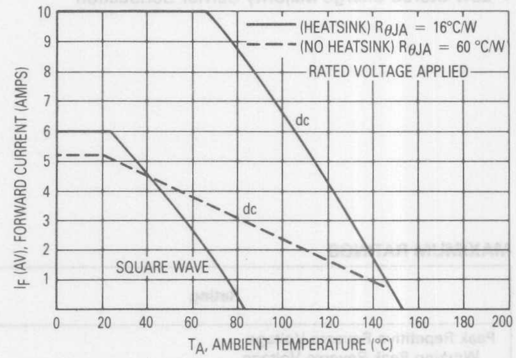


Figure 4. Current Derating, Ambient

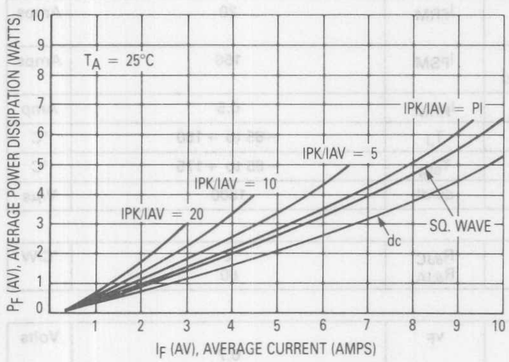
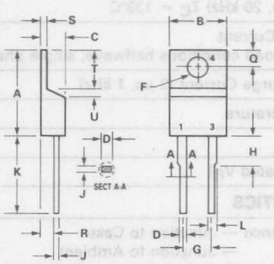


Figure 5. Forward Power Dissipation



STYLE 1:
PIN 1. CATHODE
2. N.A.
3. ANODE
4. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

Polarity: Cathode-To-Case

CASE 221B-01
TO-220AC
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR1535CT
MBR1545CT

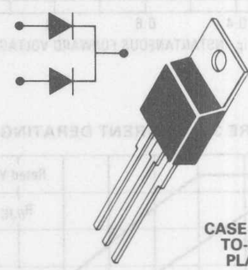
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Center-Tap Configuration
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, VO at 1/8″

SCHOTTKY BARRIER RECTIFIERS

15 AMPERES
35 and 45 VOLTS



CASE 221A-04
TO-220AB
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR1535CT	MBR1545CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current Per Diode $T_C = 105°C$ (Rated V_R) Per Device	$I_{F(AV)}$	7.5 15	7.5 15	Amps
Peak Repetitive Forward Current, $T_C = 105°C$ (Rated V_R, Square Wave, 20 kHz) Per Diode	I_{FRM}	15	15	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs
THERMAL CHARACTERISTICS PER DIODE				
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	3.0	°C/W
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	60	°C/W
ELECTRICAL CHARACTERISTICS PER DIODE				
Maximum Instantaneous Forward Voltage (1) (i_F = 7.5 Amp, T_C = 125°C) (i_F = 15 Amp, T_C = 125°C) (i_F = 15 Amp, T_C = 25°C)	v_F	 0.57 0.72 0.84	 0.57 0.72 0.84	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 15 0.1	 15 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

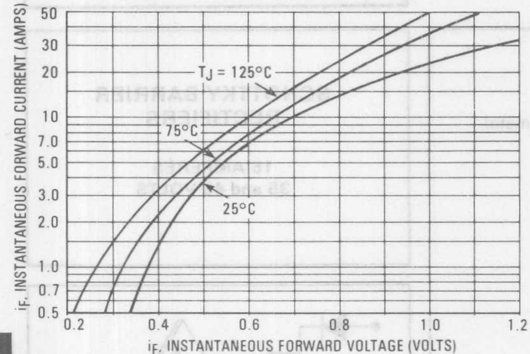


FIGURE 2 — TYPICAL REVERSE CURRENT

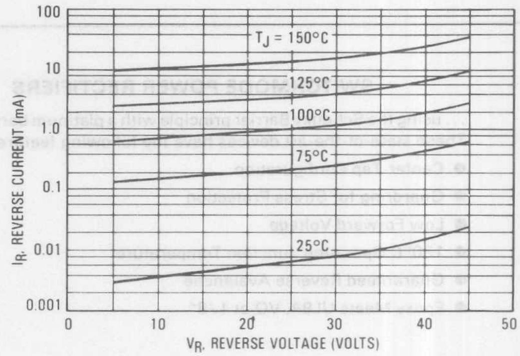


FIGURE 3 — CURRENT DERATING, CASE

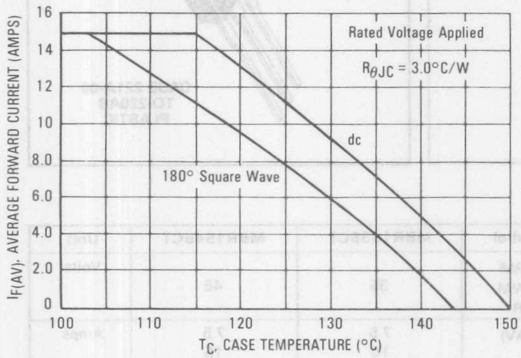


FIGURE 4 — CURRENT DERATING, AMBIENT

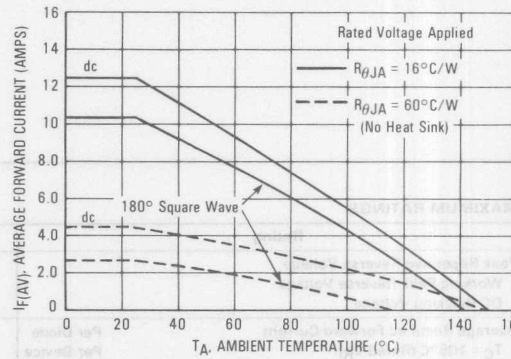
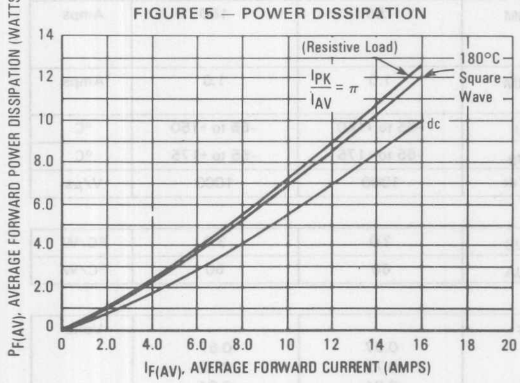
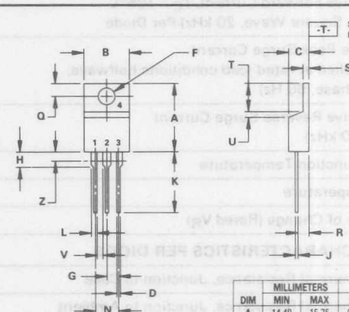


FIGURE 5 — POWER DISSIPATION





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

CASE 221A-04
TO-220AB
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR1635
MBR1645

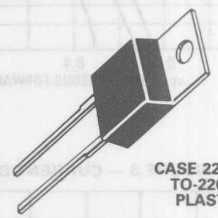
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

16 AMPERES
35 and 45 VOLTS



CASE 221B-01
TO-220AC
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR1635	MBR1645	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 125°C$	$I_{F(AV)}$	16	16	Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 125°C$	I_{FRM}	32	32	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Rating	Symbol	MBR1635	MBR1645	Unit
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	1.5	°C/W

ELECTRICAL CHARACTERISTICS

Rating	Symbol	MBR1635	MBR1645	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 16 Amp, T_C = 125°C) (i_F = 16 Amp, T_C = 25°C)	v_F	 0.57 0.63	 0.57 0.63	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 40 0.2	 40 0.2	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

3

FIGURE 1 — TYPICAL FORWARD VOLTAGE

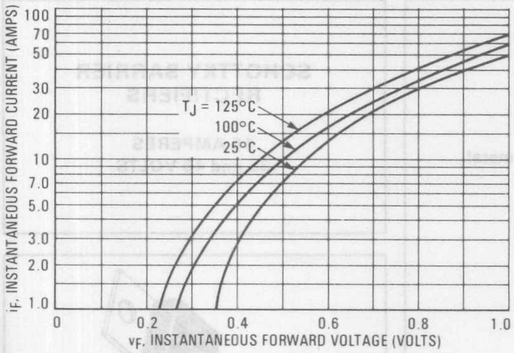


FIGURE 2 — TYPICAL REVERSE CURRENT

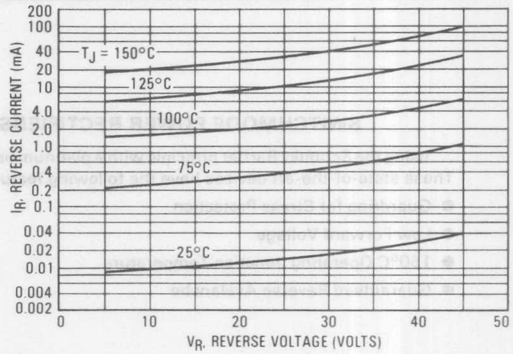


FIGURE 3 — CURRENT DERATING, CASE

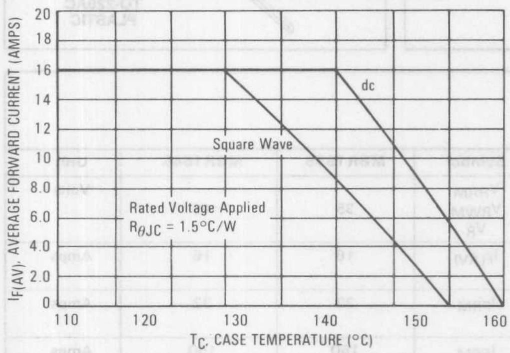


FIGURE 4 — CURRENT DERATING, AMBIENT

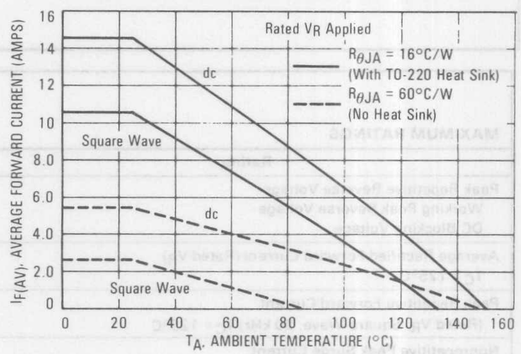
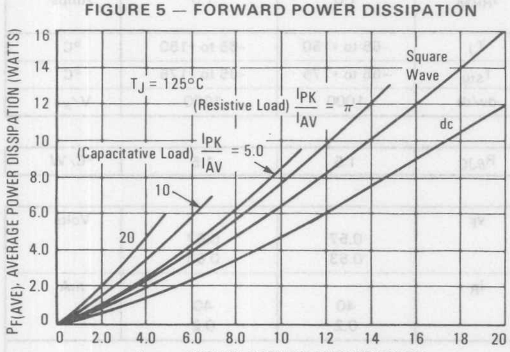
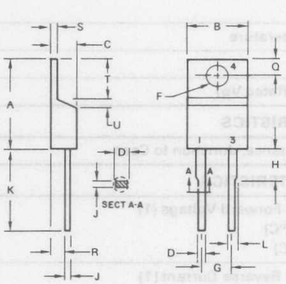


FIGURE 5 — FORWARD POWER DISSIPATION





STYLE 1:
PIN 1. CATHODE
2. N.A.
3. ANODE
4. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

CATHODE COMMON TO TAB

CASE 221B-01
TO-220AC
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR2035CT
MBR2045CT

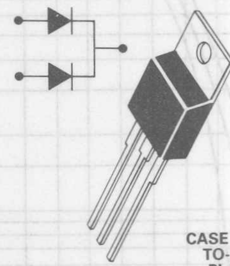
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, V0 at 1/8"

SCHOTTKY BARRIER RECTIFIERS

20 AMPERES
35 and 45 VOLTS



CASE 221A-04
TO-220AB
PLASTIC

3

MAXIMUM RATINGS

Rating	Symbol	MBR2035CT	MBR2045CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 135°C$	$I_{F(AV)}$	20	20	Amps
Peak Repetitive Forward Current Per Diode Leg (Rated V_R, Square Wave, 20 kHz) $T_C = 135°C$	I_{FRM}	20	20	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 11	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Rating	Symbol	MBR2035CT	MBR2045CT	Unit
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	2.0	°C/W

ELECTRICAL CHARACTERISTICS

Rating	Symbol	MBR2035CT	MBR2045CT	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 10 Amp, $T_C = 125°C$) (i_F = 20 Amp, $T_C = 125°C$) (i_F = 20 Amp, $T_C = 25°C$)	v_F	 0.57 0.72 0.84	 0.57 0.72 0.84	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 125°C$) (Rated dc Voltage, $T_C = 25°C$)	i_R	 15 0.1	 15 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — MAXIMUM FORWARD VOLTAGE

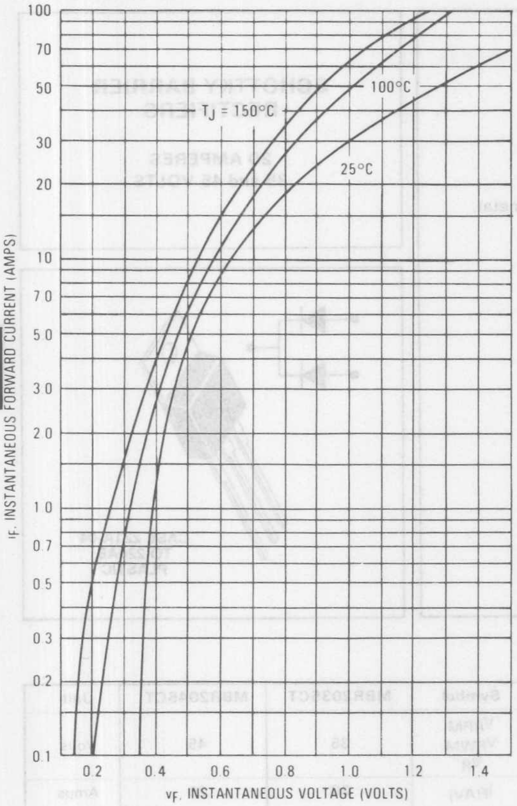


FIGURE 2 — TYPICAL FORWARD VOLTAGE

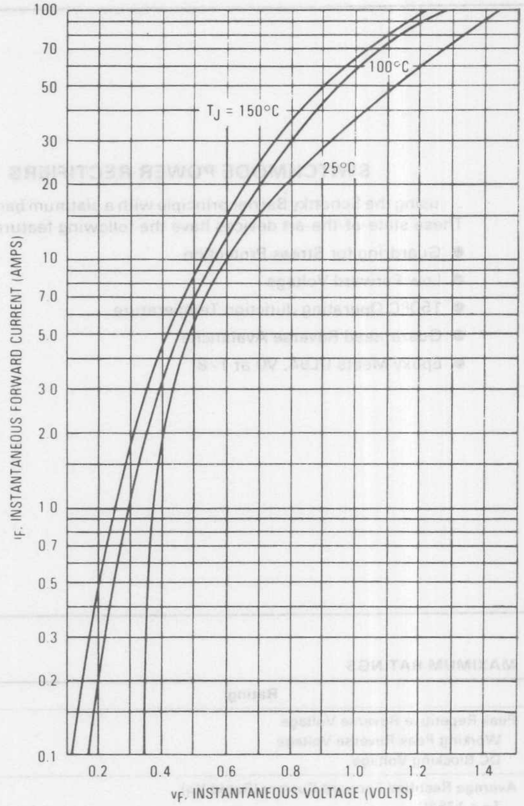


FIGURE 3 — MAXIMUM REVERSE CURRENT

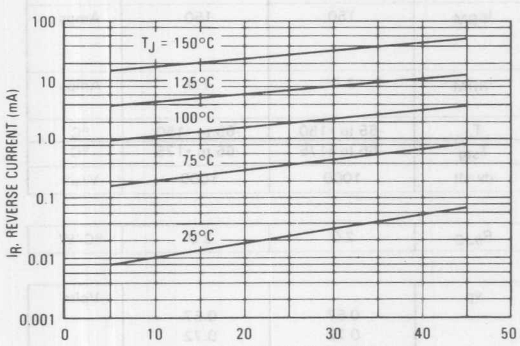
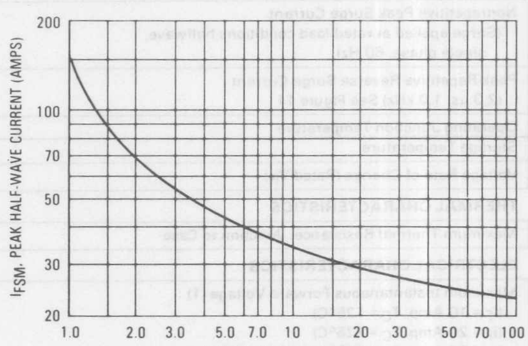


FIGURE 4 — MAXIMUM SURGE CAPABILITY



3

FIGURE 5 — CURRENT DERATING, INFINITE HEATSINK

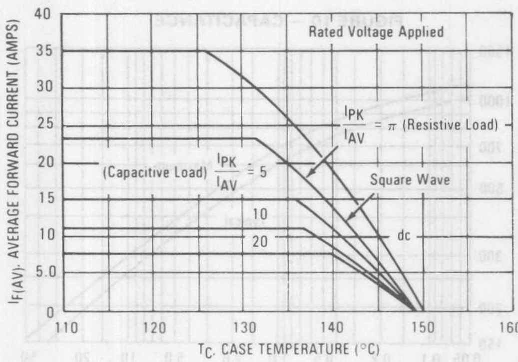


FIGURE 6 — CURRENT DERATING, $R_{\theta JA}$ = 16° C/W

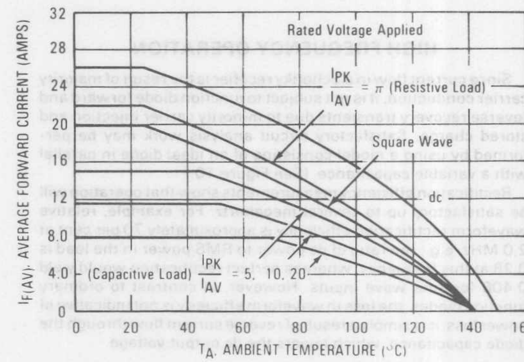


FIGURE 7 — FORWARD POWER DISSIPATION

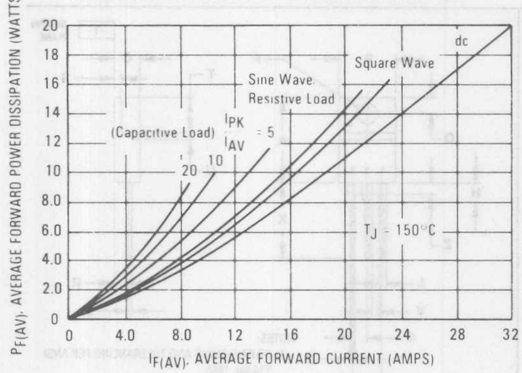


FIGURE 8 — CURRENT DERATING, FREE AIR

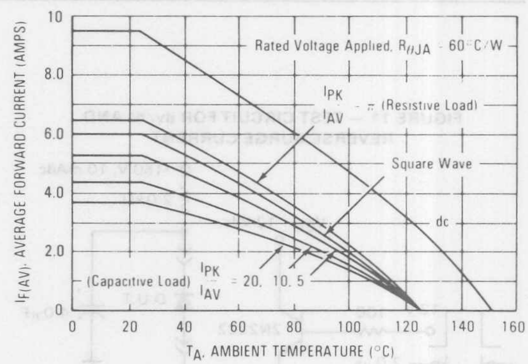
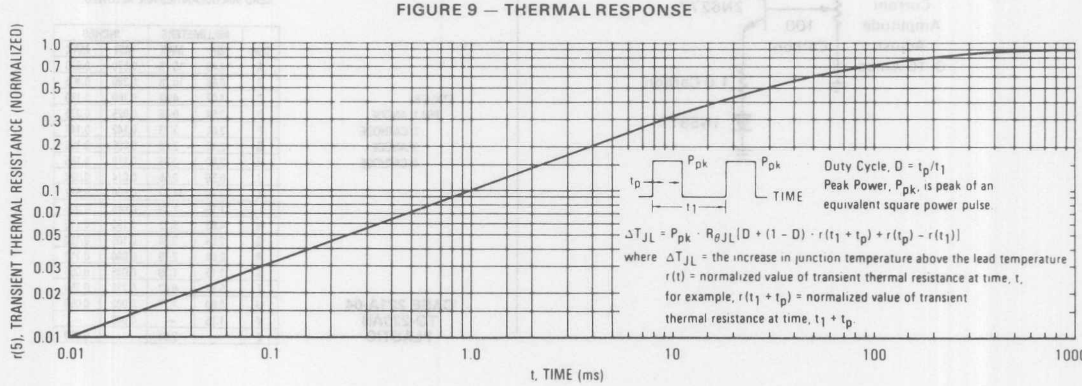


FIGURE 9 — THERMAL RESPONSE



HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 10.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficieny is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 10 — CAPACITANCE

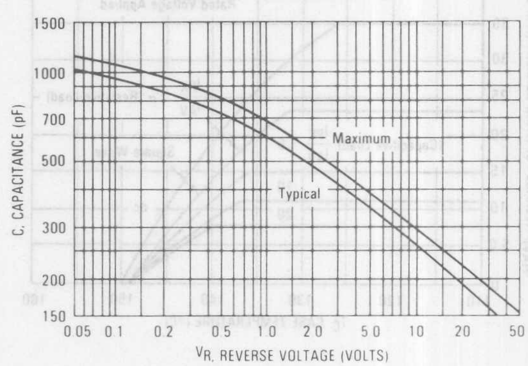
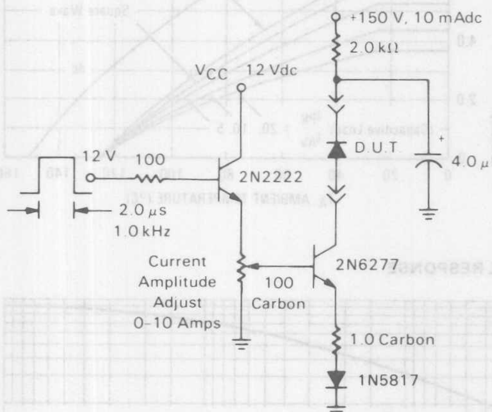
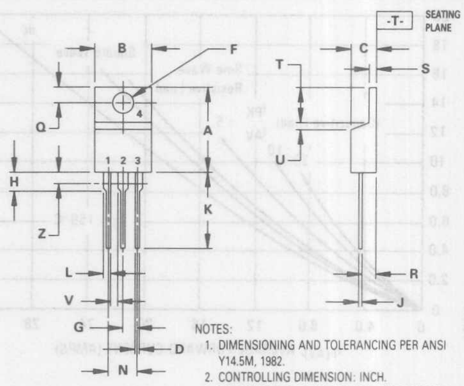


FIGURE 11 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

CASE 221A-04
TO-220AB
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

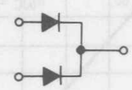
MBR2060CT
MBR2070CT
MBR2080CT
MBR2090CT
MBR20100CT

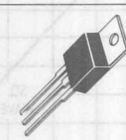
Switchmode Power Rectifiers

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- 20 Amps Total (10 Amps Per Diode Leg)
- Guard-Ring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche
- Epoxy Meets UL94, VO at 1/8″
- Low Power Loss/High Efficiency
- High Surge Capacity
- Low Stored Charge Majority Carrier Conduction

SCHOTTKY BARRIER RECTIFIERS
20 AMPERES
60–100 VOLTS





CASE 221A-04
TO-220AB
PLASTIC

MAXIMUM RATINGS PER DIODE LEG

Rating	Symbol	MBR 2060CT	MBR 2070CT	MBR 2080CT	MBR 2090CT	MBR 20100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	70	80	90	100	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 133°C$	$I_{F(AV)}$			10			Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 133°C$	I_{FRM}			20			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}			150			Amps
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I_{RRM}			0.5			Amp
Operating Junction Temperature	T_J			−65 to +150			°C
Storage Temperature	T_{stg}			−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt			1000			V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance — Junction to Case — Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2 60	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE LEG

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 10 Amp, T_C = 125°C) (i_F = 10 Amp, T_C = 25°C) (i_F = 20 Amp, T_C = 125°C) (i_F = 20 Amp, T_C = 25°C)	v_F	 0.7 0.8 0.85 0.95	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 150 0.15	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

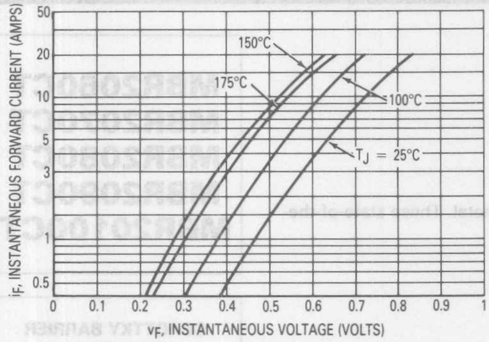


Figure 1. Typical Forward Voltage Per Diode

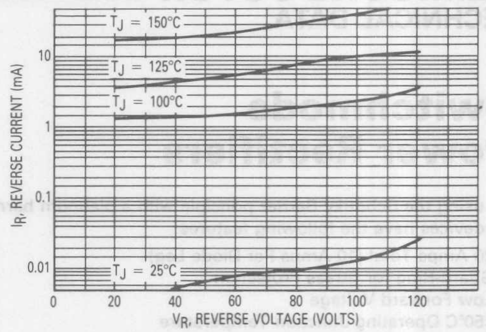


Figure 2. Typical Reverse Current Per Diode

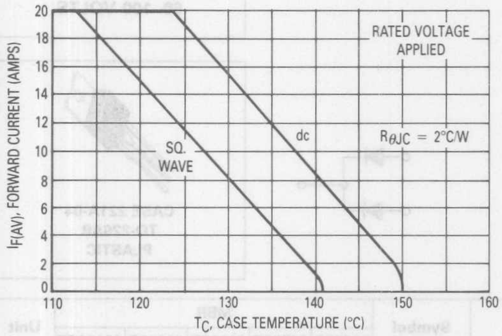


Figure 3. Current Derating, Case

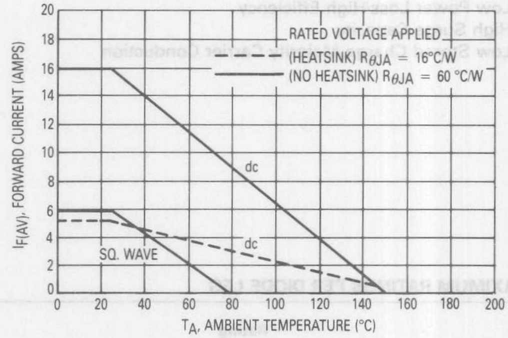


Figure 4. Current Derating, Ambient

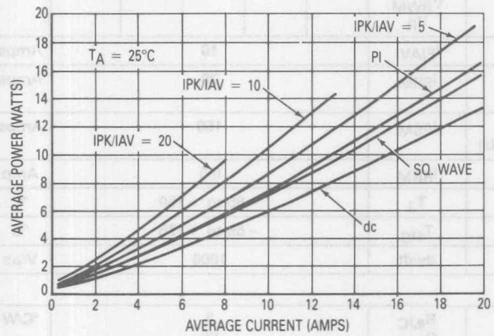
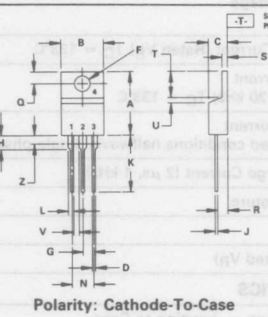


Figure 5. Average Power Dissipation and Average Current



STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

Polarity: Cathode-To-Case

NOTES:
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2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

CASE 221A-04
TO-220AB
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR2535CT
MBR2545CT

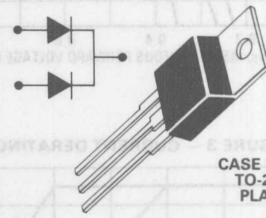
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

30 AMPERES
35 and 45 VOLTS



CASE 221A-04
TO-220AB
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBR2535CT	MBR2545CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 130°C$	$I_{F(AV)}$	30	30	Amps
Peak Repetitive Forward Current Per Diode Leg (Rated V_R, Square Wave, 20 kHz) $T_C = 130°C$	I_{FRM}	30	30	Amps
Nonrepetitive Peak Surge Current per Diode Leg (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	150	150	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	1.0	Amps
Operating Junction Temperature	T_J	−65 to +150	−65 to +150	°C
Storage Temperature	T_{stg}	−65 to +175	−65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs
THERMAL CHARACTERISTICS PER DIODE LEG				
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	1.5	°C/W
ELECTRICAL CHARACTERISTICS PER DIODE LEG				
Maximum Instantaneous Forward Voltage (1) (i_F = 30 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 25°C)	v_F	 0.73 0.82	 0.73 0.82	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 40 0.2	 40 0.2	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

3

FIGURE 1 — TYPICAL FORWARD VOLTAGE

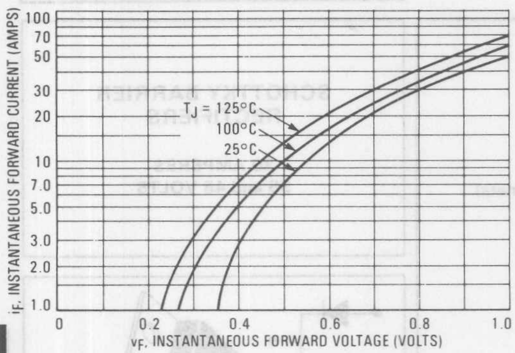
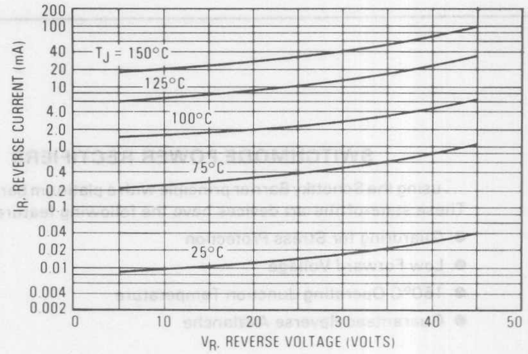


FIGURE 2 — TYPICAL REVERSE CURRENT



3

FIGURE 3 — CURRENT DERATING, CASE

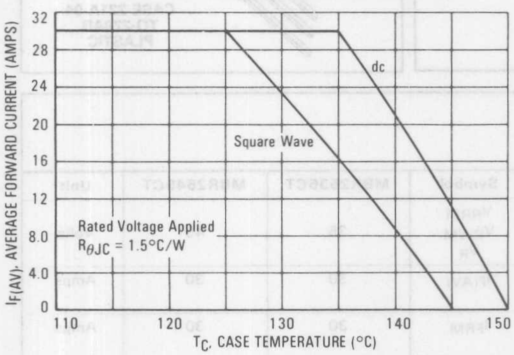


FIGURE 4 — CURRENT DERATING, AMBIENT

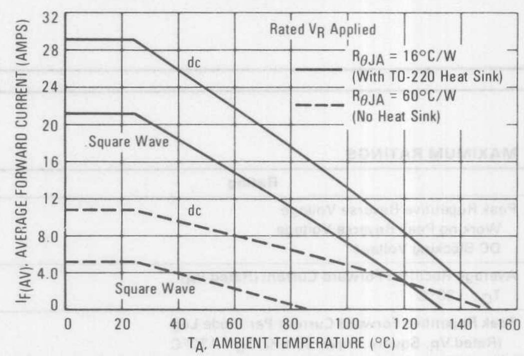
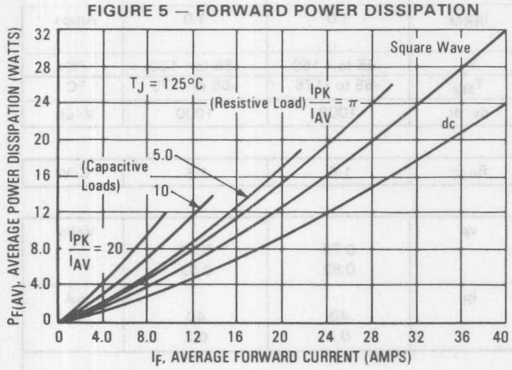
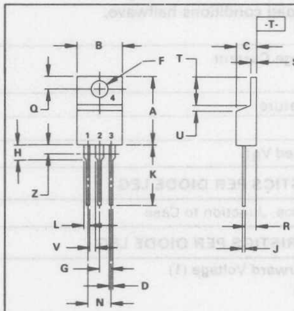


FIGURE 5 — FORWARD POWER DISSIPATION





STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

CASE 221A-04
TO-220AB
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR3020CT
MBR3035CT
MBR3045CT
SD241

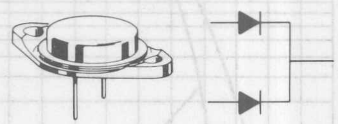
SWITCHMODE POWER RECTIFIERS

... using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction
- Guardring for Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

30 AMPERES
20 to 45 VOLTS



CASE 11-03
TO-204AA
METAL

MAXIMUM RATINGS

Rating	Symbol	MBR3020CT	MBR3035CT	MBR3045CT	SD241	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	35	45	45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 105°C$ — Per Device Per Diode	I_O	30 15	30 15	30 15	30 15	Amps
Peak Repetitive Forward Current, Per Diode (Rated V_R, Square Wave, 20 kHz)	I_{FRM}	30	30	30	30	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	400	400	400	400	Amps
Peak Repetitive Reverse Current, Per Diode (2.0 μs, 1.0 kHz) See Figure 8	I_{RRM}	2.0	2.0	2.0	2.0	Amps
Operating Junction Temperature	T_J	-65 to +150	-65 to +150	-65 to +150	-65 to +150	°C
Storage Temperature	T_{stg}	-65 to +175	-65 to +175	-65 to +175	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)	$T_{J(pk)}$	175	175	175	175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	1000	1000	V/μs

THERMAL CHARACTERISTICS PER DIODE

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	1.4	1.4	1.4	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Maximum Instantaneous Forward Voltage (1) (i_F = 10 Amp, T_C = 125°C) (i_F = 20 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 25°C)	v_F	 — 0.60 0.72 0.76	 — 0.60 0.72 0.76	 — 0.60 0.72 0.76	 0.47 0.60 — —	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 60 1.0	 60 1.0	 60 1.0	 100 V_R = 35 V	mA
Capacitance	C_t	2000	2000	2000	2000	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

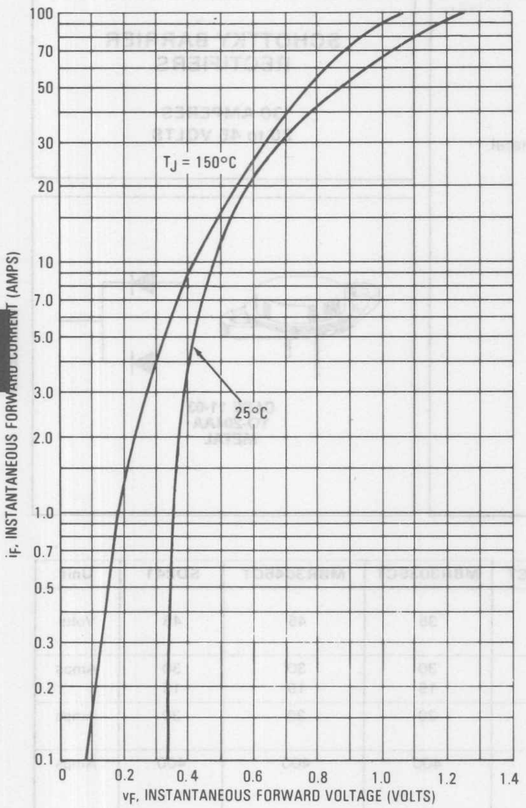


FIGURE 2 — TYPICAL REVERSE CURRENT

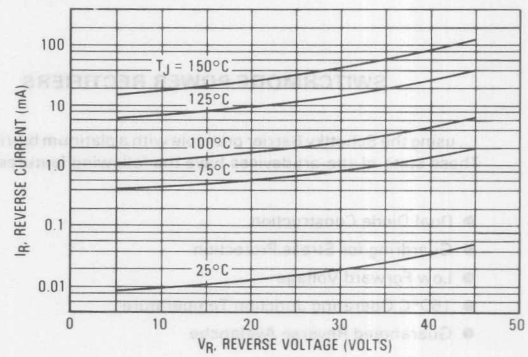


FIGURE 3 — MAXIMUM SURGE CAPABILITY

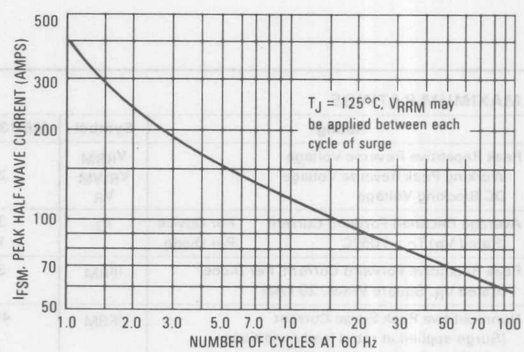


FIGURE 4 — CURRENT DERATING

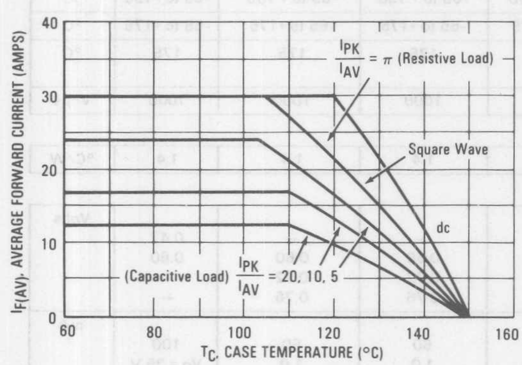


FIGURE 5 — FORWARD POWER DISSIPATION

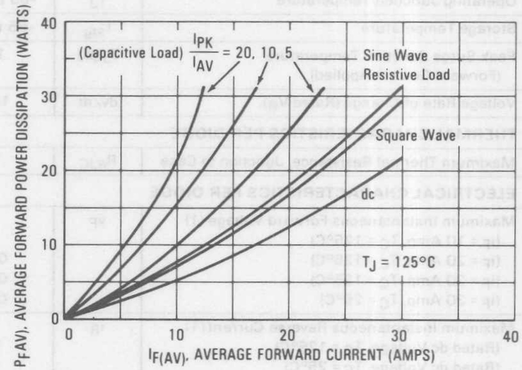
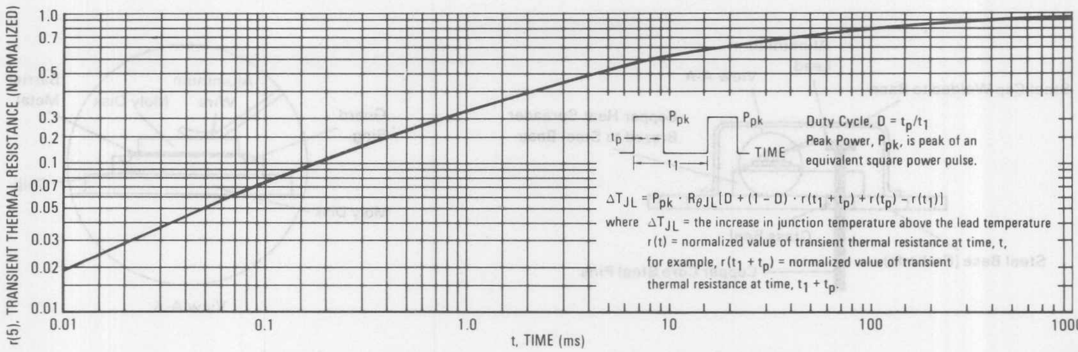


FIGURE 6 — THERMAL RESPONSE PER DIODE LEG



HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 7.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficieny is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 7 — CAPACITANCE

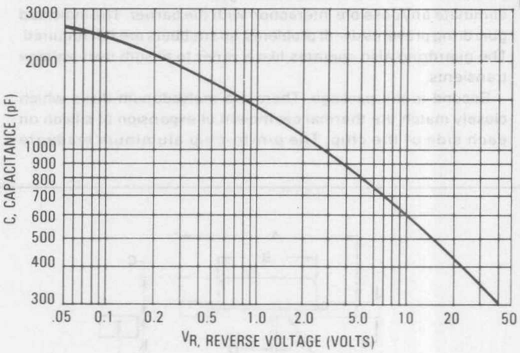


FIGURE 8 — TEST CIRCUIT FOR REPETITIVE REVERSE CURRENT

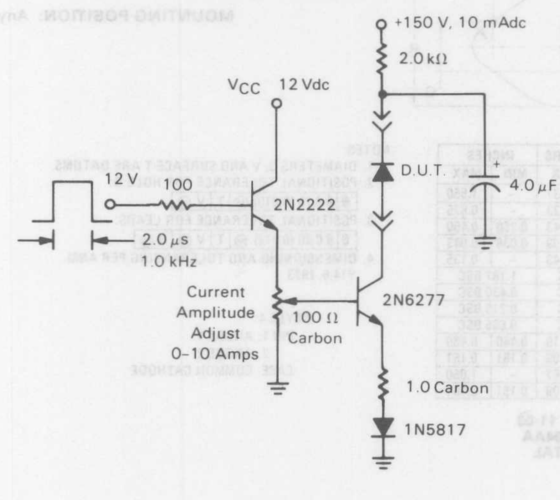
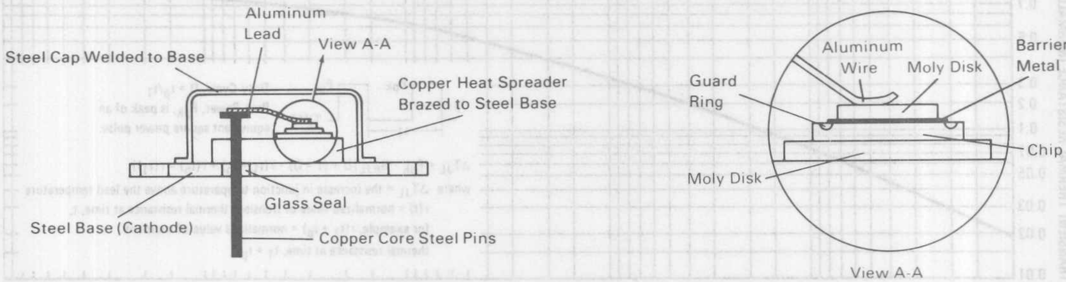


FIGURE 9 — SCHOTTKY RECTIFIER



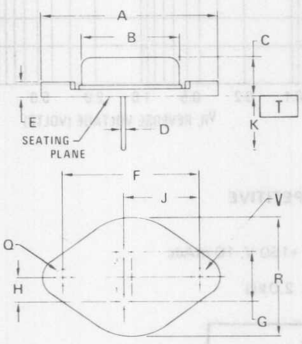
3

Motorola builds quality and reliability into its Schottky Rectifiers.

First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not required. The guardring also operates like a zener to absorb over-voltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The pin-to-chip aluminum leadwire provides stress relief. These two features give the unit the capability of passing stringent thermal fatigue tests for 5,000 cycles. Copper-core steel pins match the expansion coefficient of the glass and are long enough (0.440 in. min.) to reach through a heat sink to a printed circuit board.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche.



MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed.

FINISH: All external surfaces corrosion resistant and terminal lead is readily solderable.

POLARITY: Cathode to Case.

MOUNTING POSITION: Any.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	–	39.37	–	1.550
B	–	22.23	–	0.875
C	6.35	11.43	0.250	0.450
D	0.97	1.09	0.038	0.043
E	–	3.43	–	0.135
F	30.15 BSC		1.187 BSC	
G	10.92 BSC		0.430 BSC	
H	5.46 BSC		0.215 BSC	
J	16.89 BSC		0.665 BSC	
K	11.18	12.19	0.440	0.480
Q	3.84	4.09	0.151	0.161
R	–	26.67	–	1.050
V	3.84	4.09	0.151	0.161

NOTES:
1. DIAMETERS Q, V AND SURFACE T ARE DATUMS.
2. POSITIONAL TOLERANCE FOR HOLE Q:
   | ⌖ | ⌀ 0.25 (0.010) Ⓜ | T | V Ⓜ |
3. POSITIONAL TOLERANCE FOR LEADS:
   | ⌖ | ⌀ 0.30 (0.012) Ⓜ | T | V Ⓜ | Q Ⓜ |
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

STYLE 4:
PIN 1. ANODE 1
2. ANODE 2
CASE. COMMON CATHODE

CASE 11-03
TO-204AA
METAL

MBR3035PT
MBR3045PT

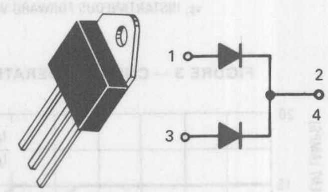
SWITCHMODE POWER RECTIFIERS

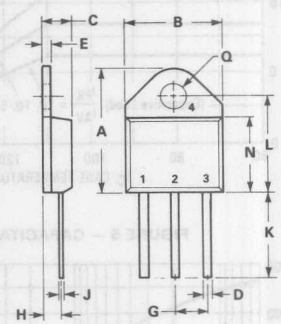
. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — Terminals 1 and 3 May Be Connected For Parallel Operation At Full Rating
- Guardring For Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

30 AMPERES
35 to 45 VOLTS





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	0.830
B	15.49	15.90	0.610	0.626
C	4.19	5.08	0.165	0.200
D	1.02	1.65	0.040	0.065
E	1.35	1.65	0.053	0.065
G	5.21	5.72	0.205	0.225
H	2.65	2.94	0.104	0.116
J	0.38	0.64	0.015	0.025
K	12.70	15.49	0.500	0.610
L	15.88	16.51	0.625	0.650
N	12.19	12.70	0.480	0.500
Q	4.04	4.22	0.159	0.166

CASE 340-02
TO-218AC
PLASTIC

RATINGS

Rating		Symbol	Maximum	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	MBR3035PT MBR3045PT	V_{RRM} V_{RWM} V_R	35 45	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 105°C$	Per Device Per Diode	$I_{F(AV)}$	30 15	Amps
Peak Repetitive Forward Current, Per Diode (Rated V_R, Square Wave, 20 kHz)		I_{FRM}	30	Amps
Nonrepetitive Peak Surge Current (Surge Applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	200	Amps
Peak Repetitive Reverse Current, Per Diode (2.0 μs, 1.0 kHz) See Figure 6		I_{RRM}	2.0	Amps
Operating Junction Temperature		T_J	-65 to +150	°C
Storage Temperature		T_{stg}	-65 to +175	°C
Peak Surge Junction Temperature (Forward Current Applied)		$T_{J(pk)}$	175	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

THERMAL CHARACTERISTICS PER DIODE

Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Instantaneous Forward Voltage (1) (i_F = 20 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 125°C) (i_F = 30 Amp, T_C = 25°C)	v_F	 0.60 0.72 0.76	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 100 1.0	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

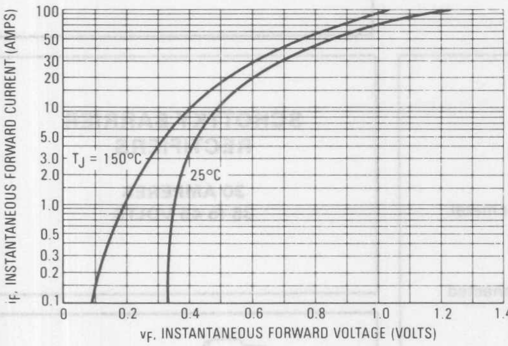


FIGURE 2 — TYPICAL REVERSE CURRENT

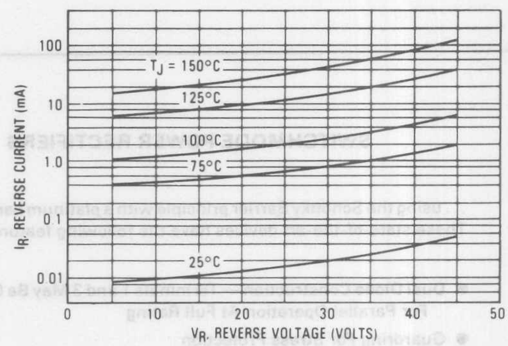


FIGURE 3 — CURRENT DERATING PER LEG

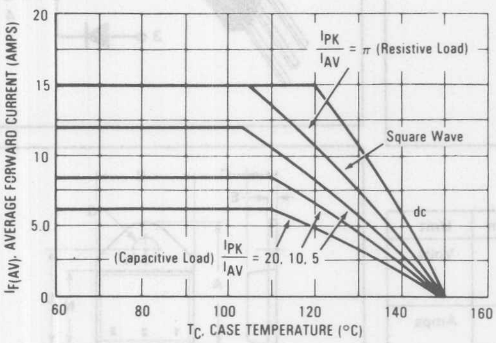


FIGURE 4 — FORWARD POWER DISSIPATION PER LEG

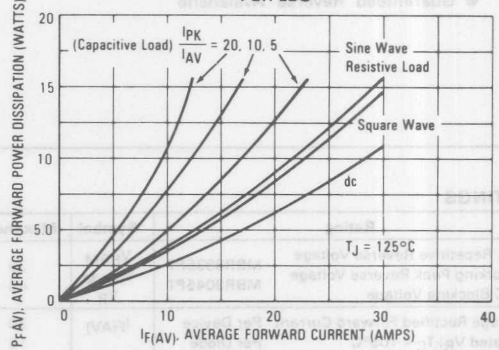


FIGURE 5 — CAPACITANCE

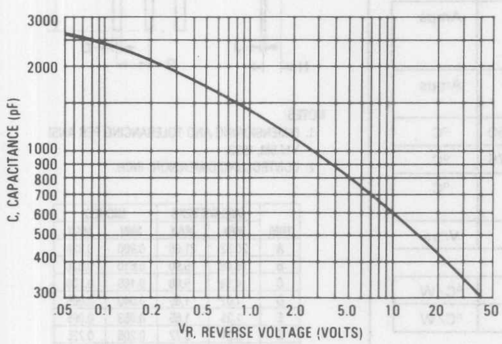
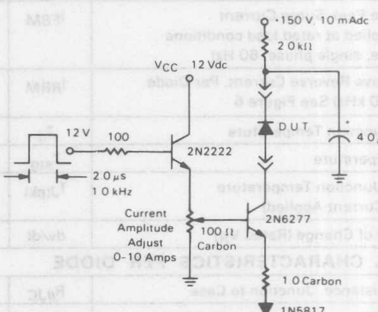


FIGURE 6 — TEST CIRCUIT FOR REPETITIVE REVERSE CURRENT



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR3520
MBR3535
MBR3545,H,H1

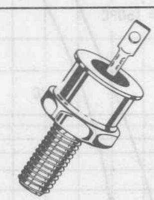
SWITCHMODE POWER RECTIFIERS

. . . using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Guardring for dv/dt Stress Protection
- Guaranteed Reverse Surge Current/Avalanche
- 150°C Operating Junction Temperature

SCHOTTKY BARRIER RECTIFIERS

35 AMPERES
20 to 45 VOLTS



CASE 56-03
DO-203AA
METAL

3

MAXIMUM RATINGS

Rating	Symbol	MBR3520	MBR3535	MBR3545, H, H1*	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	35	45	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz, T_C = 110°C)	I_{FRM}	70			Amps
Average Rectified Forward Current (Rated V_R, T_C = 110°C)	$I_{F(AV)}$	35			Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 8	I_{RRM}	2.0			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	600			Amps
Operating Junction Temperature	T_J	-65 to +150			°C
Storage Temperature	T_{stg}	-65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000			V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.3	1.5	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (1)	v_F			Volts
(i_F = 35 Amp, T_C = 125°C)		0.49	0.55	
(i_F = 35 Amp, T_C = 25°C)		0.55	0.63	
(i_F = 70 Amp, T_C = 125°C)		0.60	0.69	
Instantaneous Reverse Current (1)	i_R			mA
(Rated Voltage, T_C = 125°C)		60	100	
(Rated Voltage, T_C = 25°C)		0.1	0.3	
Capacitance (V_R = 1.0 Vdc, 100 kHz > f > 1.0 MHz, T_C = 25°C)	C_t	3000	3700	pF

*H and H1 devices include extra testing. See Figure 10.
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%

3

FIGURE 1 — MAXIMUM FORWARD VOLTAGE

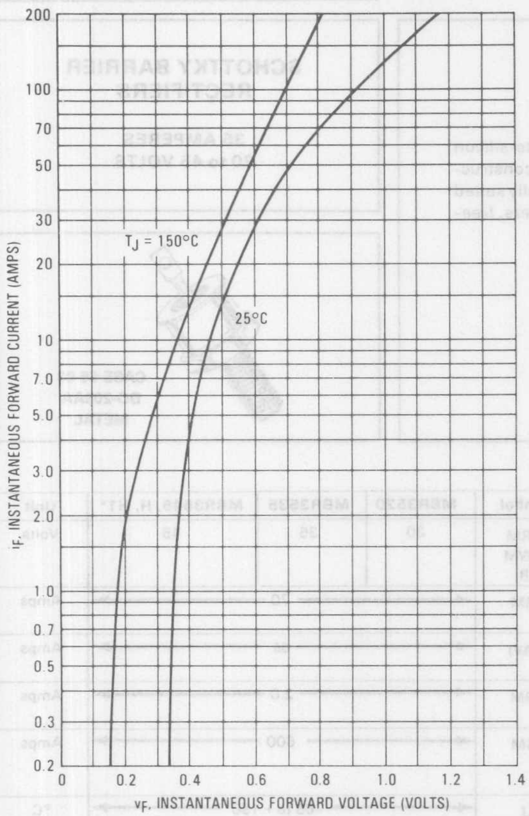


FIGURE 2 — MAXIMUM REVERSE CURRENT

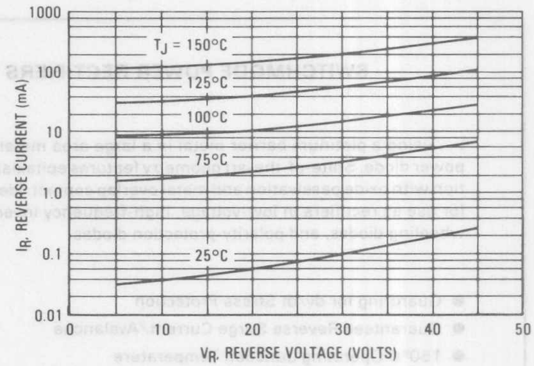


FIGURE 3 — MAXIMUM SURGE CAPABILITY

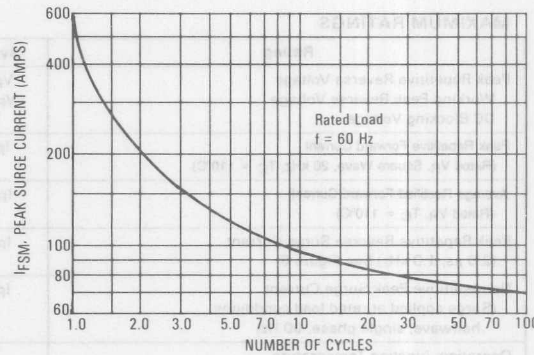


FIGURE 4 — CURRENT DERATING

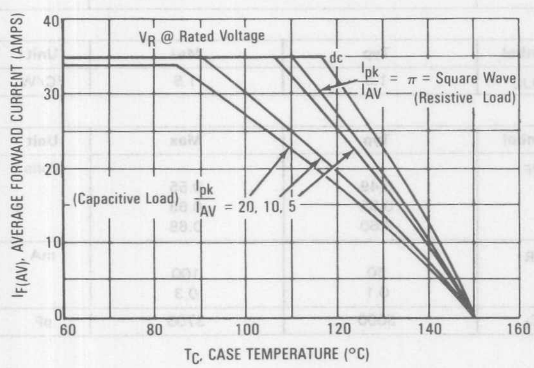


FIGURE 5 — POWER DISSIPATION

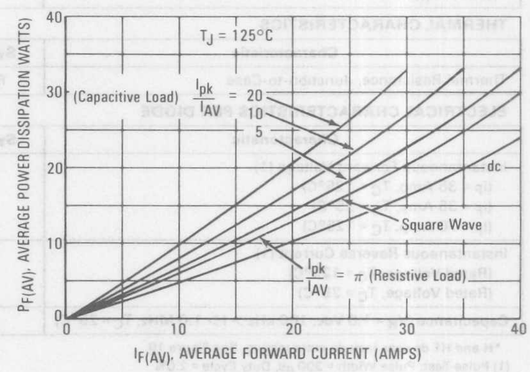
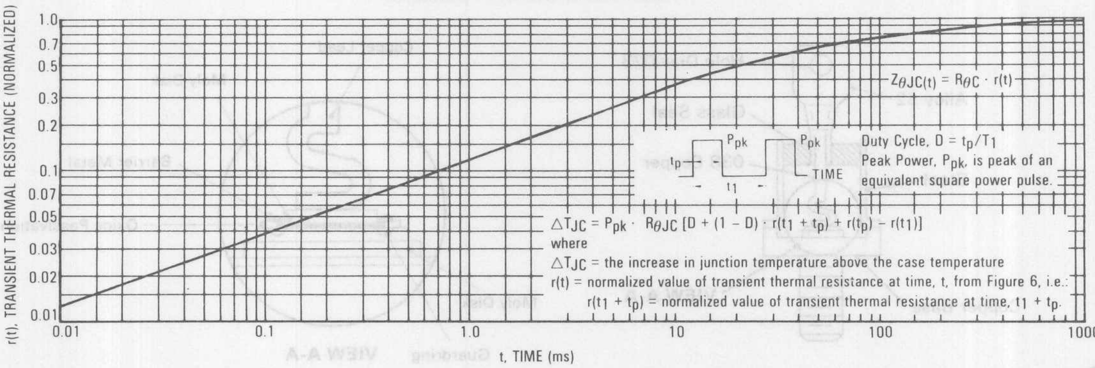


FIGURE 6 — THERMAL RESPONSE



HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 7.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 7 — CAPACITANCE

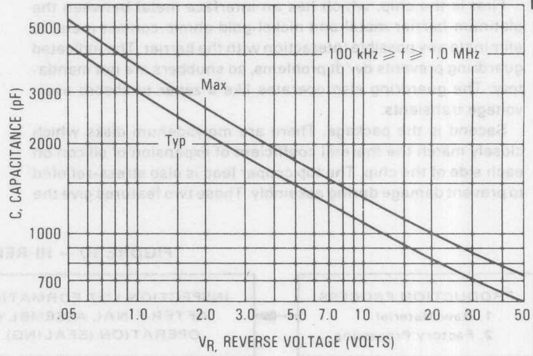
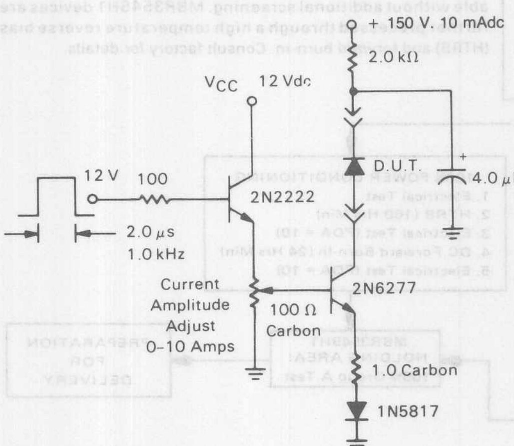
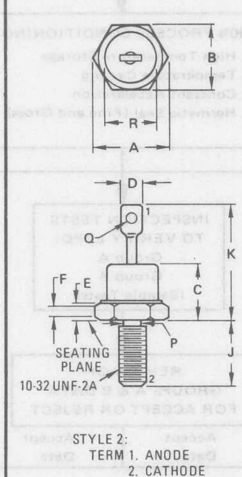


FIGURE 8 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT





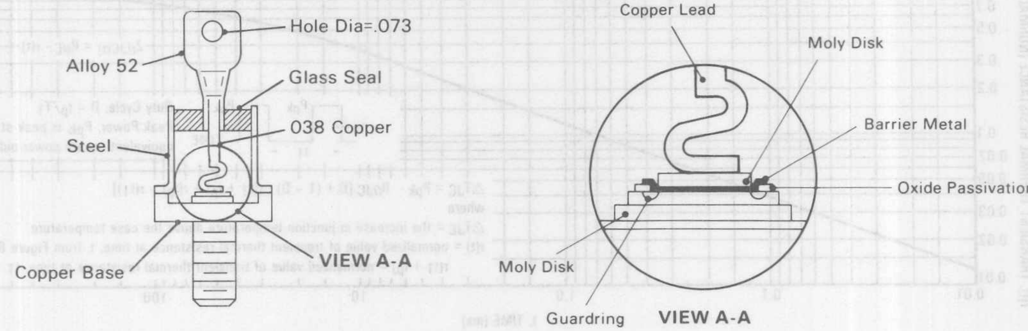
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	11.94	12.83	0.470	0.505
B	10.77	11.10	0.424	0.437
C	–	10.29	–	0.405
D	–	6.35	–	0.250
E	1.91	4.45	0.075	0.175
F	1.52	–	0.060	–
J	10.72	11.51	0.422	0.453
K	–	20.32	–	0.800
P	4.14	4.80	0.163	0.189
Q	1.52	–	0.060	–
R	–	10.77	–	0.424

All JEDEC dimensions and notes apply

STYLE 2:
TERM 1. ANODE
2. CATHODE

CASE 56-03
DO-203AA
METAL

FIGURE 9 — SCHOTTKY RECTIFIER



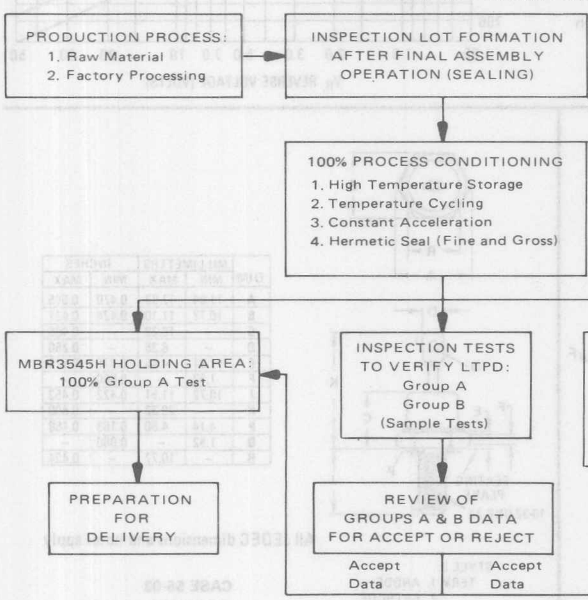
Motorola builds quality and reliability into its Schottky Rectifiers.

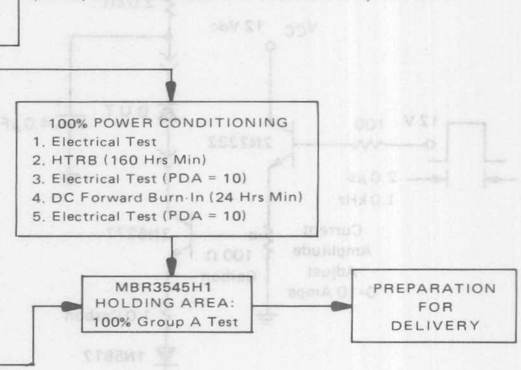
First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not mandatory. The guardring also operates like a zener to absorb overvoltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The top copper lead is also stress-relieved to prevent damage during assembly. These two features give the unit the capability of passing powered thermal fatigue tests for 5,000 cycles. The top copper lead provides a low resistance to current and therefore does not contribute to device heating; a heat sink should be used when attaching wires.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche. Devices are also 100% reverse scope tested for trace anomalies.

FIGURE 10 — HI-REL PROGRAM OPTIONS





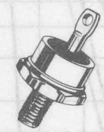
The MBR3545 is also available with two levels of extra testing similar to "TX" screening and including Group A and B inspection programs. Both the MBR3545H and MBR3545H1 go through 100% screening consisting of high temperature storage, temperature cycling, constant acceleration and hermetic seal testing prior to a sample being submitted to Group A and B inspection. After completion of Group B inspection, the MBR3545H is available without additional screening. MBR3545H1 devices are further processed through a high temperature reverse bias (HTRB) and forward burn-in. Consult factory for details.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Switchmode Power Rectifiers

MBR6015L
MBR6020L
MBR6025L
MBR6030L

SCHOTTKY RECTIFIERS
60 AMPERES
15 TO 30 VOLTS



CASE 257-01
DO-203AB
METAL

... using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Guaranteed Reverse Avalanche
- Guardring for dv/dt Stress Protection
- 175°C Operating Junction Temperature
- Extremely Low Forward Voltage

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	MBR6015L MBR6020L MBR6025L MBR6030L	V_{RRM} V_{RWM} V_R	15 20 25 30	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 90°C$		I_{FRM}	150	Amps
Average Rectified Forward Current (Rated V_R) $T_C = 120°C$		I_O	60	Amps
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz) See Figure 7		I_{RRM}	2	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	1000	Amps
Operating Junction Temperature		T_J	−65 to +150	°C
Storage Temperature Range		T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (1) (i_F = 30 Amps, T_C = 25°C) (i_F = 60 Amps, T_C = 25°C) (i_F = 30 Amps, T_C = 150°C) (i_F = 60 Amps, T_C = 150°C)	v_F	 0.42 0.48 0.30 0.38	Volts
Maximum Instantaneous Reverse Current (1) (Rated Voltage, T_C = 25°C) (Rated Voltage, T_C = 125°C)	i_R	 50 280	mA
Capacitance (V_R = 1 Vdc, 100 kHz ≤ f ≤ 1 MHz)	C_t	6000	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

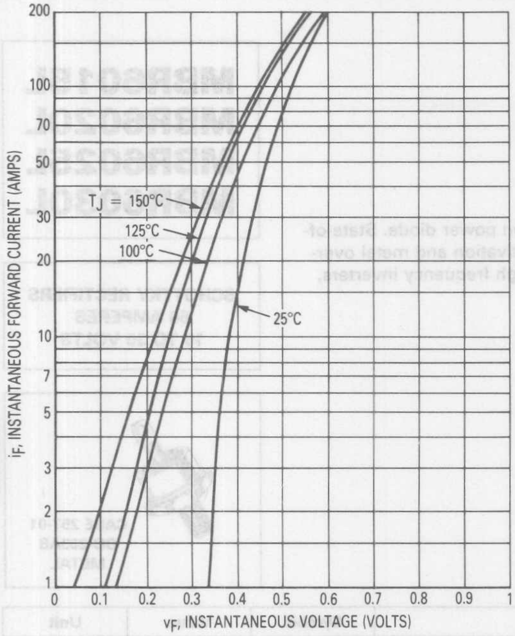


Figure 1. Typical Forward Voltage

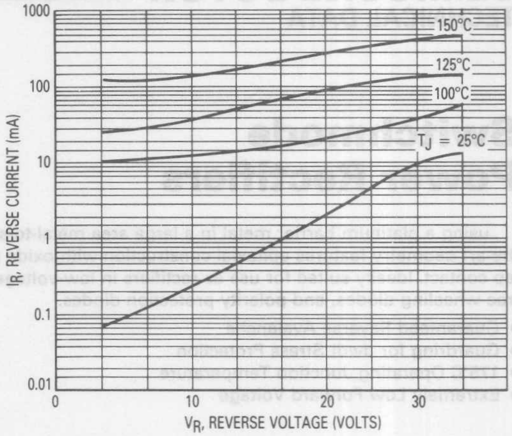


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

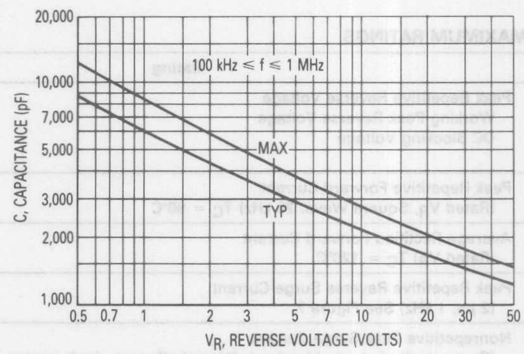


Figure 3. Capacitance

NOTE 1

HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 4.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 percent at 2 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

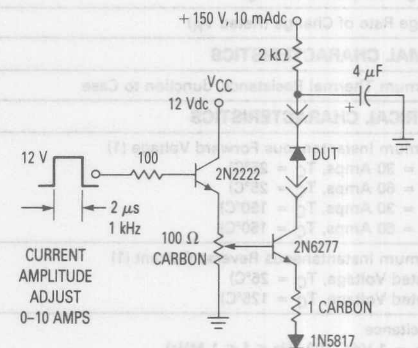


Figure 4. Test Circuit for dv/dt and Reverse Surge Current

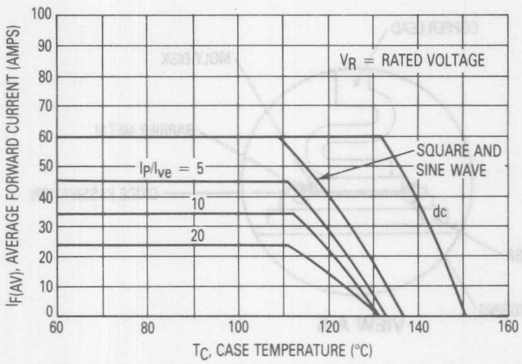


Figure 5. Forward Current Derating

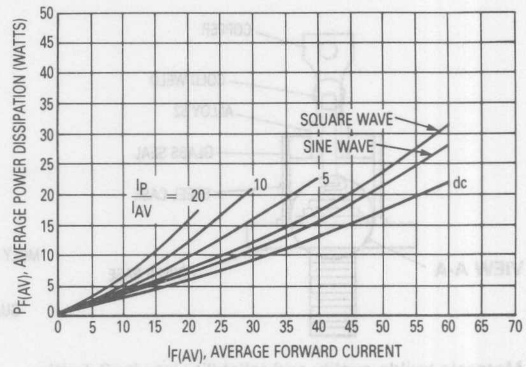
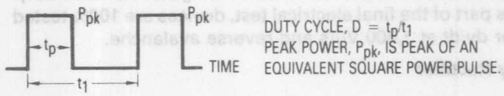


Figure 6. Power Dissipation

NOTE 2



To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_C is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC}[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 7, i.e.:

$r(t_1 - t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

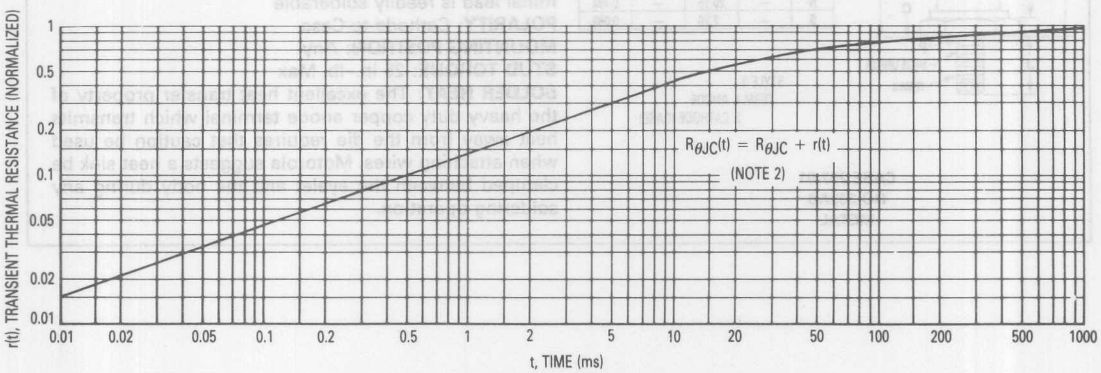
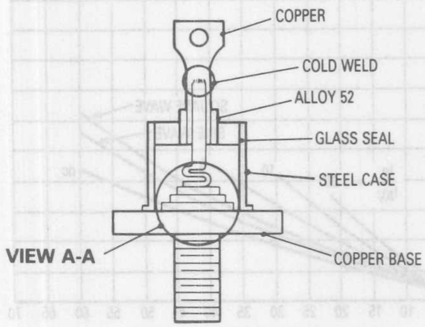
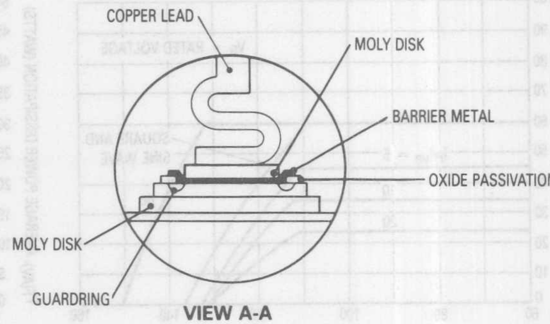


Figure 7. Thermal Response





Motorola builds quality and reliability into its Schottky Rectifiers.

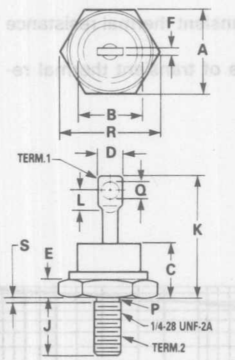
First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not mandatory. The guardring also operates like a zener to absorb overvoltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The top copper lead has a stress relief feature which protects the die during assembly. These two features give the unit the capability of passing stringent thermal fatique tests for 5,000 cycles. The top copper lead provides a low resistance to current and therefore does not contribute to device heating; a heat sink should be used when attaching wires.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche.

Figure 8. Schottky Rectifier

OUTLINE DIMENSIONS



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

STYLE 2:
TERM.1. ANODE
2. CATHODE (CASE)

NOTES:
1. DIM "P" IS DIA.
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4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

CASE 257-01
DO-203AB
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and terminal lead is readily solderable
POLARITY: Cathode-to-Case
MOUNTING POSITION: Any
STUD TORQUE: 25 in.–lb. Max
SOLDER HEAT: The excellent heat transfer property of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires. Motorola suggests a heat sink be clamped between the eyelet and the body during any soldering operation.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR5825H, H1
See Page 3-54
MBR5831H, H1
See Page 3-63

MBR6035
MBR6045, H, H1

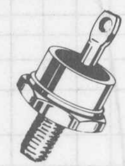
SWITCHMODE POWER RECTIFIERS

. . . using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high-frequency inverters, free-wheeling diodes, and polarity-protection diodes.

- Guaranteed Reverse Avalanche
- Guardring for dv/dt Stress Protection
- 150°C Operating Junction Temperature
- Low Forward Voltage

SCHOTTKY RECTIFIERS

60 AMPERES
35 AND 45 VOLTS



CASE 257-01
DO-203AB
METAL

3

MAXIMUM RATINGS

Rating	Symbol	MBR6035 MBR6035B	MBR6045, H, H1* MBR6045B	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 100°C$	I_{FRM}	120		Amps
Average Rectified Forward Current (Rated V_R) $T_C = 100°C$	I_O	60		Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 7	I_{RRM}	2.0		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	800		Amps
Operating Junction Temperature	T_J	−65 to +150		°C
Storage Temperature	T_{stg}	−65 to +175		°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000		V/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.85	1.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (1)	v_F			Volts
(i_F = 60 Amp, T_C = 25°C)		0.65	0.70	
(i_F = 60 Amp, T_C = 125°C)		0.57	0.60	
(i_F = 120 Amp, T_C = 125°C)		0.70	0.76	
Instantaneous Reverse Current (1)	i_R			mA
(Rated Voltage, T_C = 25°C)		0.1	0.3	
(Rated Voltage, T_C = 125°C)		55	100	
Capacitance (V_R = 1.0 Vdc, 100 kHz ≤ 1.0 MHz)	C_t	3000	3700	pF

*H and H1 devices include extra testing.
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

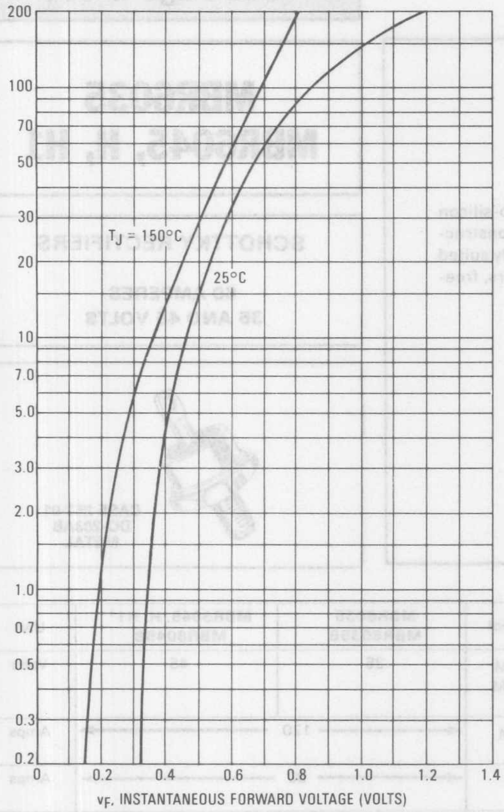


FIGURE 2 — TYPICAL REVERSE CURRENT

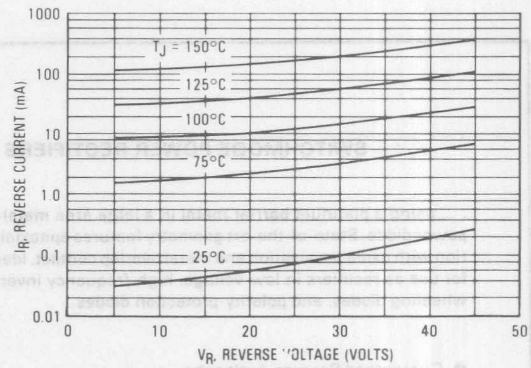
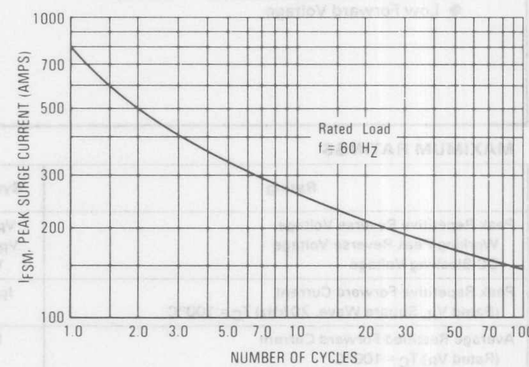


FIGURE 3 — MAXIMUM SURGE CAPABILITY



NOTE 1
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Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 4.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 4 — CAPACITANCE

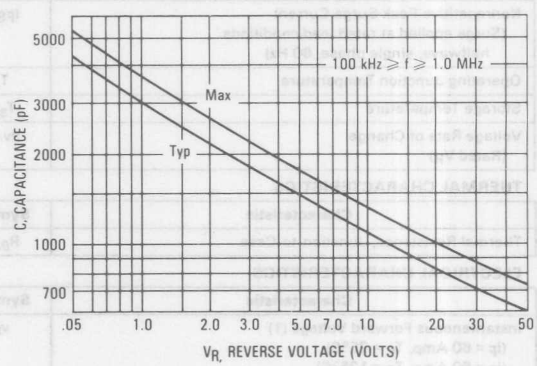


FIGURE 5 — FORWARD CURRENT DERATING

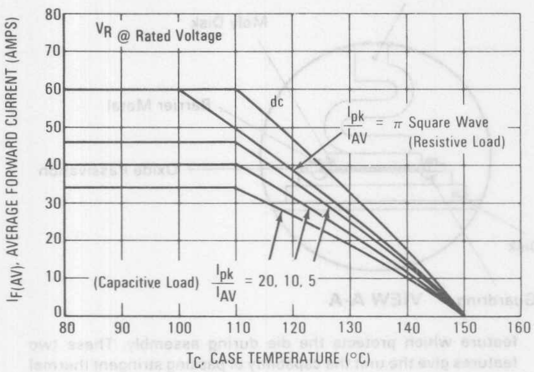
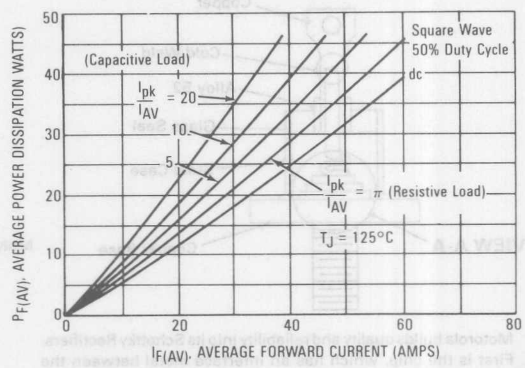
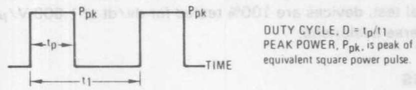


FIGURE 6 — POWER DISSIPATION



NOTE 2



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_C is the increase in junction temperature above the case temperature. It may be determined by:

$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC}[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$ where
$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 8, i.e.:
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FIGURE 7 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT

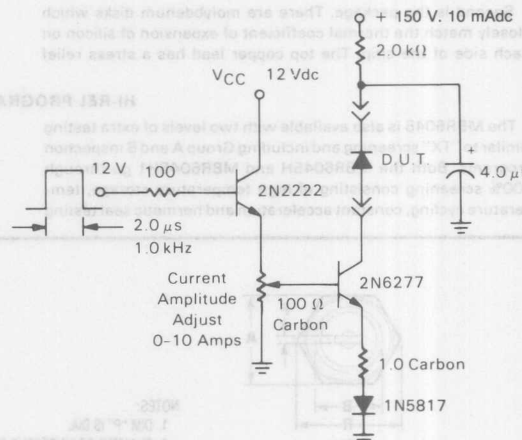
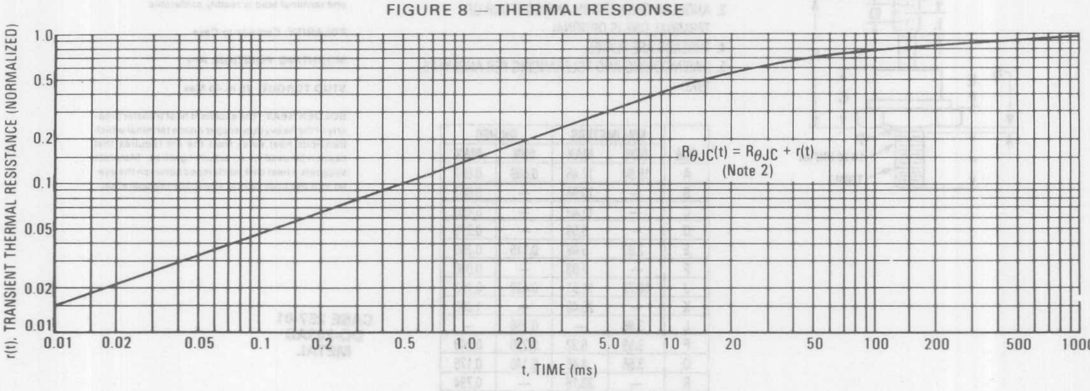
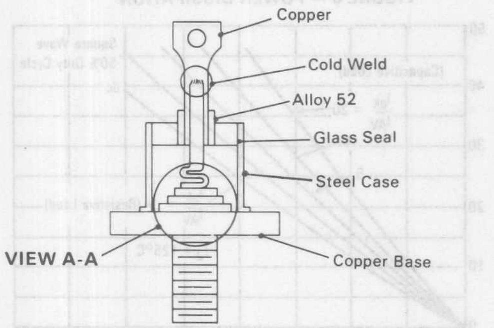


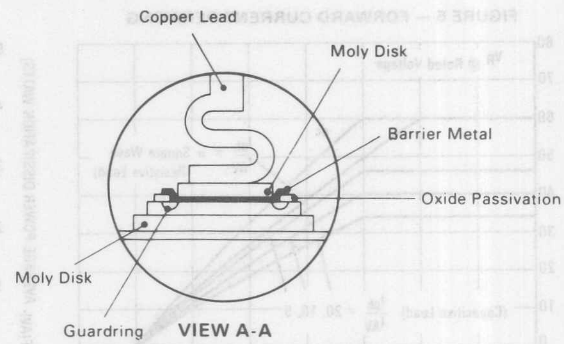
FIGURE 8 — THERMAL RESPONSE



3

FIGURE 9 — SCHOTTKY RECTIFIER





Motorola builds quality and reliability into its Schottky Rectifiers.

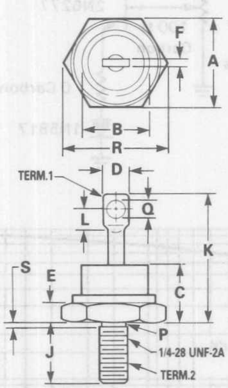
First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not mandatory. The guardring also operates like a zener to absorb overvoltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The top copper lead has a stress relief feature which protects the die during assembly. These two features give the unit the capability of passing stringent thermal fatigue tests for 5,000 cycles. The top copper lead provides a low resistance to current and therefore does not contribute to device heating; a heat sink should be used when attaching wires.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche.

HI-REL PROGRAM OPTIONS

The MBR6045 is also available with two levels of extra testing similar to "TX" screening and including Group A and B inspection programs. Both the MBR6045H and MBR6045H1 go through 100% screening consisting of high temperature storage, temperature cycling, constant acceleration and hermetic seal testing prior to a sample being submitted to Group A and B inspection. After completion of Group B inspection, the MBR6045H is available without additional screening. MBR6045H1 devices are further processed through a high temperature reverse bias (HTRB) and forward burn-in. Consult factory for details.



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CASE: Welded, hermetically sealed

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MOUNTING POSITION: Any

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CASE 257-01
DO-203AB
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR6535
MBR6545

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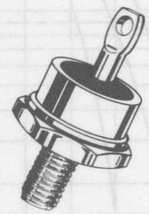
HIGH TEMPERATURE SCHOTTKY RECTIFIERS

65 AMPERES
35 and 45 VOLTS



CASE 257-01
DO-203AB
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Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 120°C$	I_{FRM}	130	130	Amps
Average Rectified Forward Current (Rated V_R) $T_C = 120°C$	I_O	65	65	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 7	I_{RRM}	2.0	2.0	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	800	800	Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	1.0	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (1) (i_F = 65 Amp, $T_C = 25°C$) (i_F = 65 Amp, $T_C = 150°C$) (i_f = 130 Amp, $T_C = 150°C$)	v_F	 0.78 0.62 0.73	 0.78 0.62 0.73	Volts
Maximum Instantaneous Reverse Current (1) (Rated Voltage, $T_C = 25°C$) (Rated Voltage, $T_C = 150°C$)	i_R	 0.07 125	 0.07 125	mA
Capacitance (V_R = 1.0 Vdc, 100 kHz ≤ f ≤ 1.0 MHz)	C_t	3700	3700	pF

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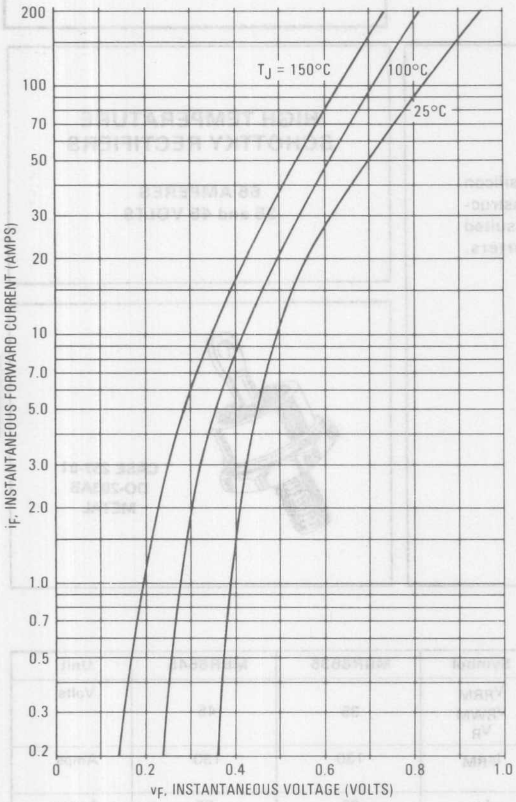

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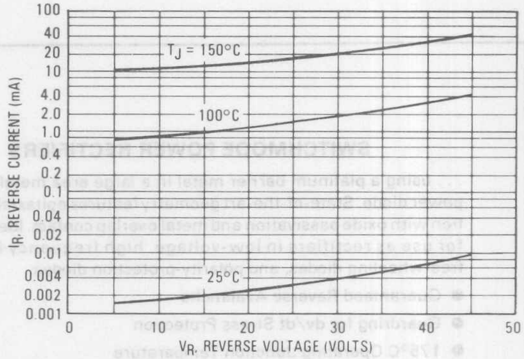

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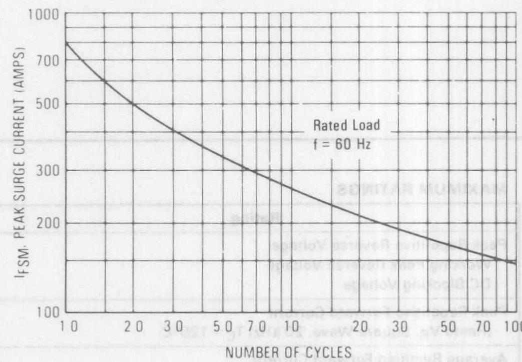

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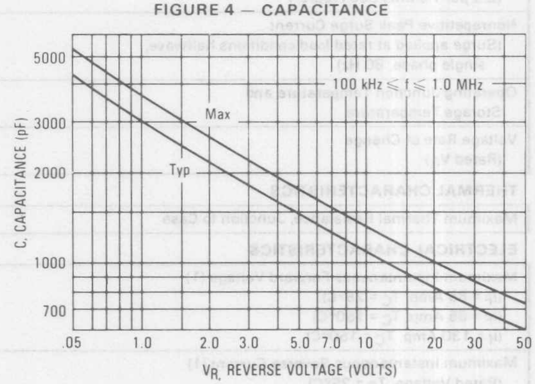

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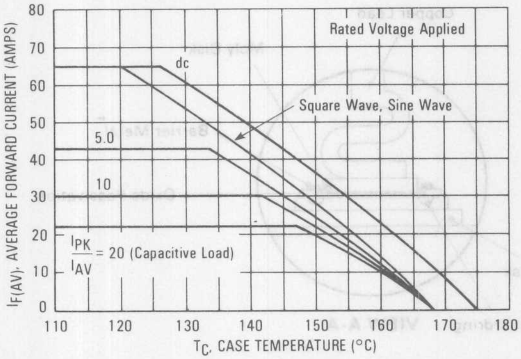

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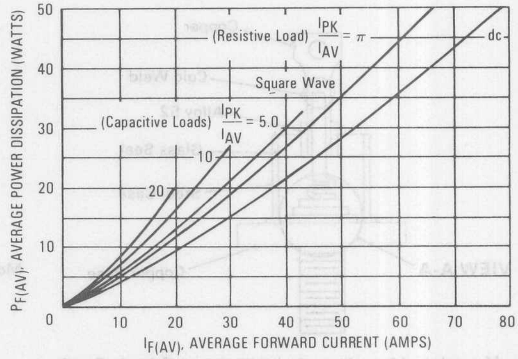

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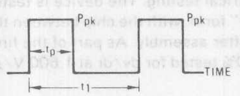

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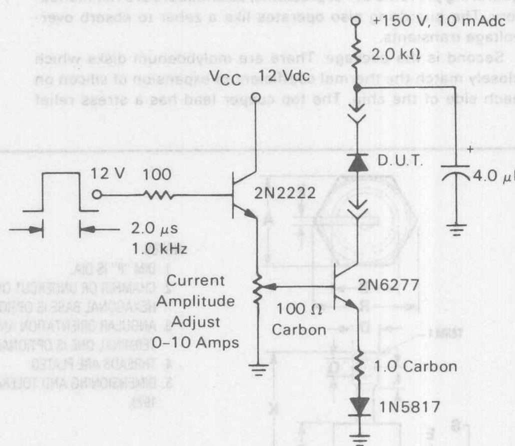

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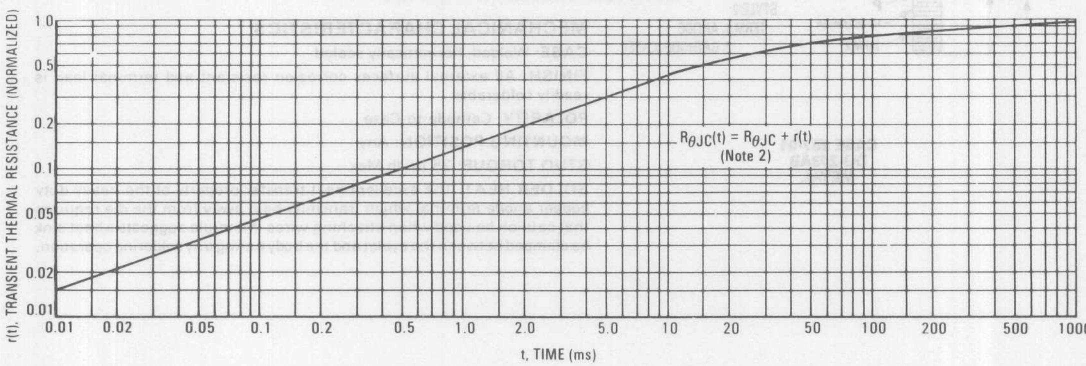

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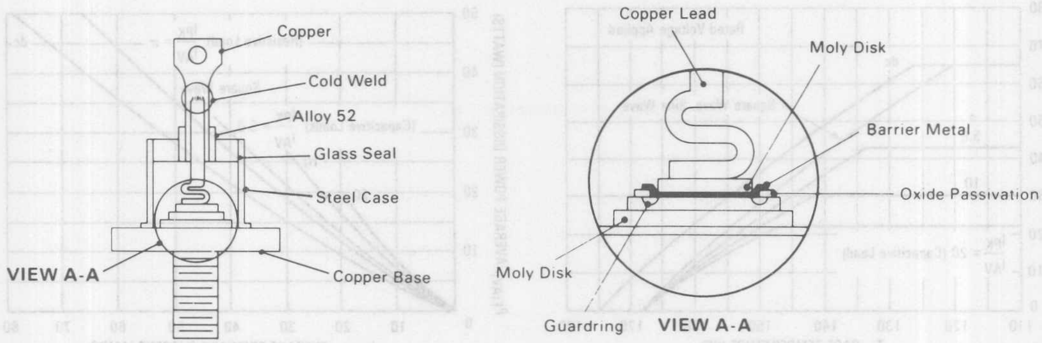

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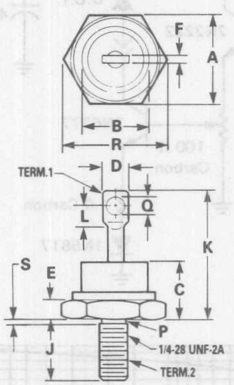

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CASE 257-01
DO-203AB
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MBR7535 MBR7540 MBR7545

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- Extremely Low v_F
- Low Stored Charge, Majority Carrier Conduction
- Low Power Loss/ High Efficiency
- High Surge Capacity

SCHOTTKY BARRIER RECTIFIERS

75 AMPERES
20 to 45 VOLTS

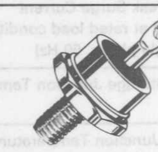
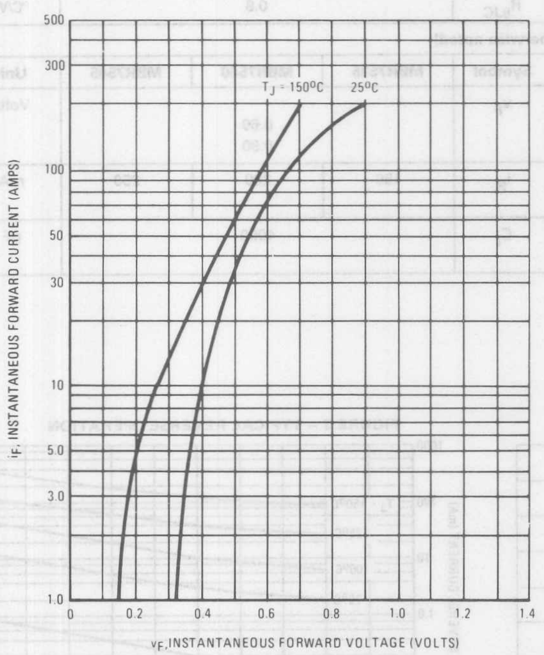
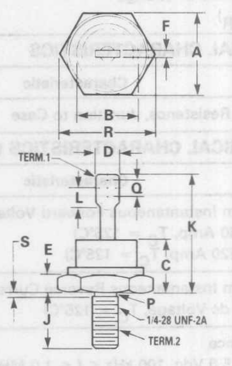


FIGURE 1 – TYPICAL FORWARD VOLTAGE





STYLE 2:
TERM.1. ANODE
2. CATHODE (CASE)

NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

CASE 257-01
DO-203AB
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion-resistant and terminal lead is readily solderable.
POLARITY: Cathode to case
MOUNTING POSITIONS: Any
STUD TORQUE: 25 in. lb. max

3

MAXIMUM RATINGS

Rating	Symbol	MBR7535	MBR7540	MBR7545	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	40	45	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz)	I_{FRM}		150 $T_C = 90°C$		Amp
Average Rectified Forward Current (Rated V_R)	I_O		70 $T_C = 90°C$		Amp
Non-repetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}		1000		Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}		−65 to +150		°C
Peak Operating Junction Temperature (Forward Current Applied)	$T_{J(pk)}$		175		°C
Voltage Rate of Change (Rated V_R)	dv/dt		1000		v/μs

THERMAL CHARACTERISTICS

Characteristic	Symbol	MBR7535	MBR7540	MBR7545	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		0.8		°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	MBR7535	MBR7540	MBR7545	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 60 Amp, T_C = 125°C) (i_F = 220 Amp, T_C = 125°C)	v_F		 0.60 0.90		Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C)	i_R	150	200	250	mA
Capacitance (V_R = 5.0 Vdc, 100 kHz ≤ f ≤ 1.0 MHz)	C_t		4000		pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%

FIGURE 2 – CURRENT DERATING

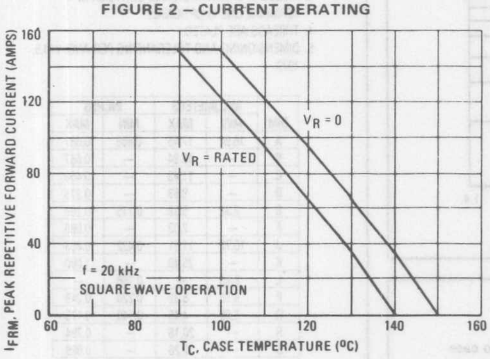
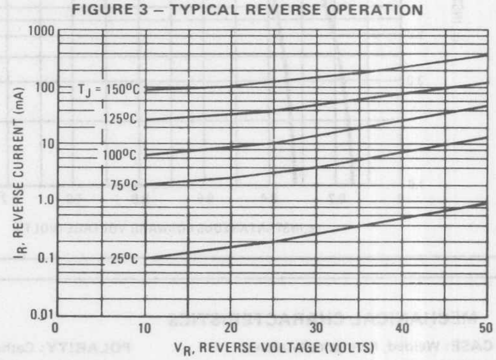


FIGURE 3 – TYPICAL REVERSE OPERATION



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR8035
MBR8045

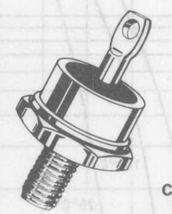
SWITCHMODE POWER RECTIFIERS

. . . using a platinum barrier metal in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlap contact. Ideally suited for use as rectifiers in low-voltage, high frequency inverters, freewheeling diodes, and polarity-protection diodes.

- Guaranteed Reverse Avalanche
- Guardring for dv/dt Stress Protection
- 175°C Operating Junction Temperature
- Low Forward Voltage

SCHOTTKY RECTIFIERS

80 AMPERES
35 and 45 VOLTS



CASE 257-01
DO-203AB
METAL

3

MAXIMUM RATINGS

Rating	Symbol	MBR8035	MBR8045	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	35	45	Volts
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz) $T_C = 120°C$	I_{FRM}	160	160	Amps
Average Rectified Forward Current (Rated V_R) $T_C = 120°C$	I_O	80	80	Amps
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz) See Figure 7	I_{RRM}	2.0	2.0	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	1000	1000	Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	-65 to +175	-65 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1000	1000	V/μs

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.80	0.80	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (1) (i_F = 80 Amp, T_C = 25°C) (i_F = 80 Amp, T_C = 150°C) (i_F = 160 Amp, T_C = 150°C)	v_F	 0.72 0.59 0.67	 0.72 0.59 0.67	Volts
Maximum Instantaneous Reverse Current (1) (Rated Voltage, T_C = 25°C) (Rated Voltage, T_C = 150°C)	i_R	 1.0 150	 1.0 150	mA
Capacitance (V_R = 1.0 Vdc, 100 kHz ≤ f ≤ 1.0 MHz)	C_t	5000	5000	pF

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE

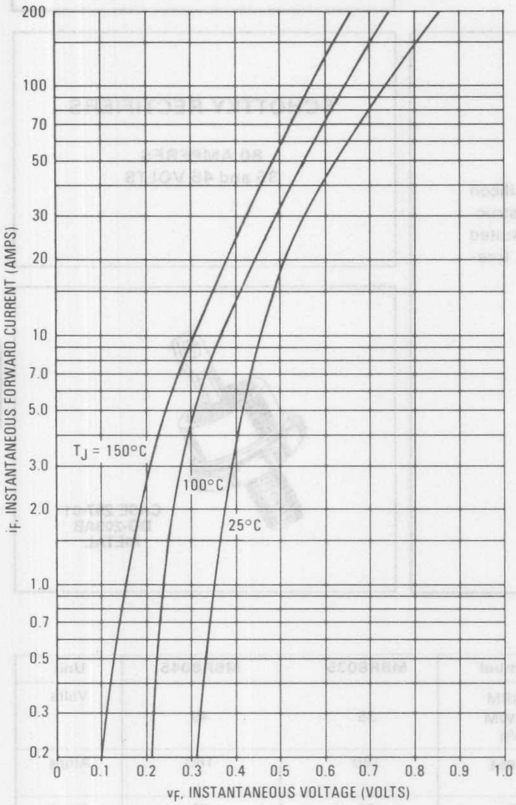


FIGURE 2 — TYPICAL REVERSE CURRENT

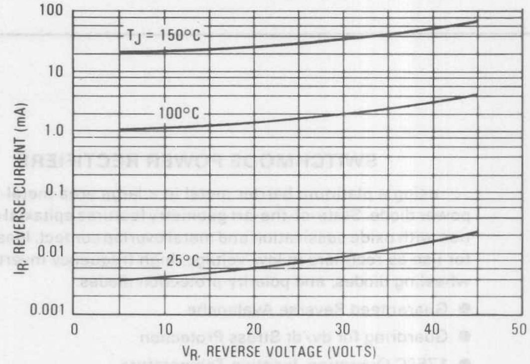


FIGURE 3 — MAXIMUM SURGE CAPABILITY

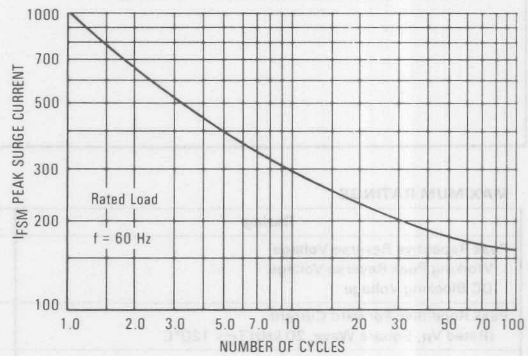
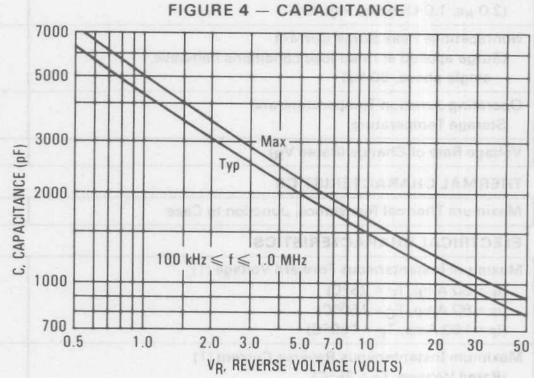


FIGURE 4 — CAPACITANCE



NOTE 1
HIGH FREQUENCY OPERATION

Since current flow in a Schottky rectifier is the result of majority carrier conduction, it is not subject to junction diode forward and reverse recovery transients due to minority carrier injection and stored charge. Satisfactory circuit analysis work may be performed by using a model consisting of an ideal diode in parallel with a variable capacitance. (See Figure 4.)

Rectification efficiency measurements show that operation will be satisfactory up to several megahertz. For example, relative waveform rectification efficiency is approximately 70 per cent at 2.0 MHz, e.g., the ratio of dc power to RMS power in the load is 0.28 at this frequency, whereas perfect rectification would yield 0.406 for sine wave inputs. However, in contrast to ordinary junction diodes, the loss in waveform efficiency is not indicative of power loss; it is simply a result of reverse current flow through the diode capacitance, which lowers the dc output voltage.

FIGURE 5 — FORWARD CURRENT DERATING

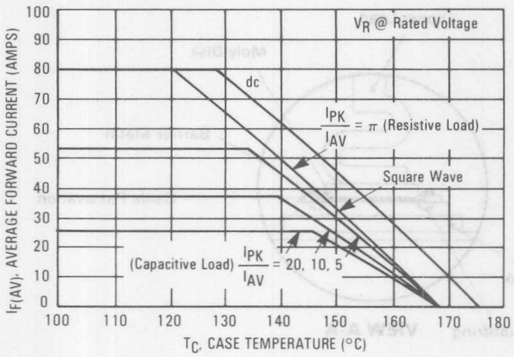
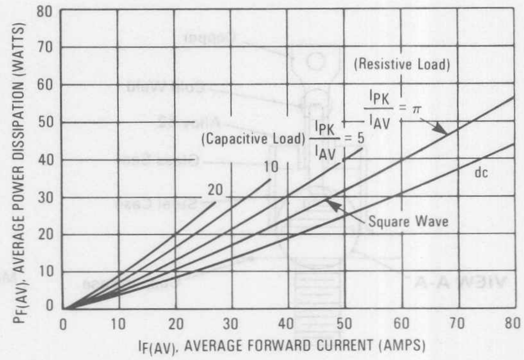
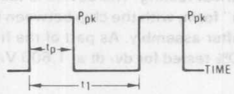


FIGURE 6 — POWER DISSIPATION



NOTE 2



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_C is the increase in junction temperature above the case temperature. It may be determined by:

$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC}[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$ where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 8, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 7 — TEST CIRCUIT FOR dv/dt AND REVERSE SURGE CURRENT

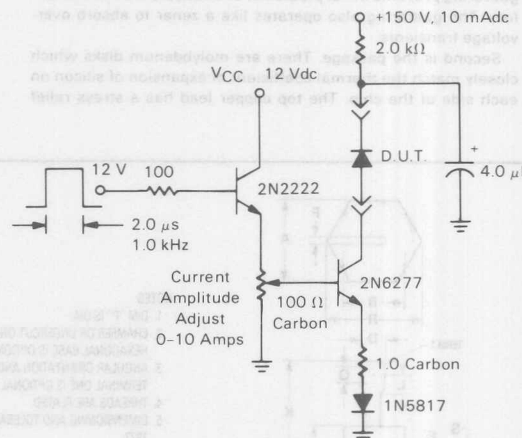


FIGURE 8 — THERMAL RESPONSE

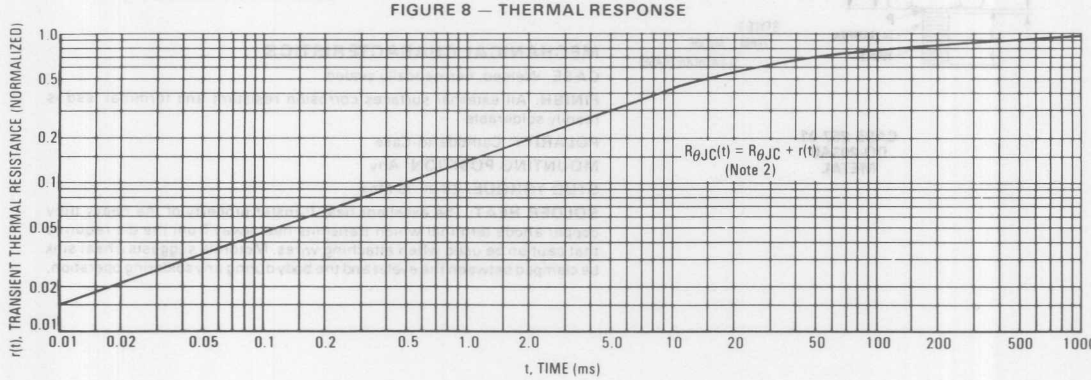
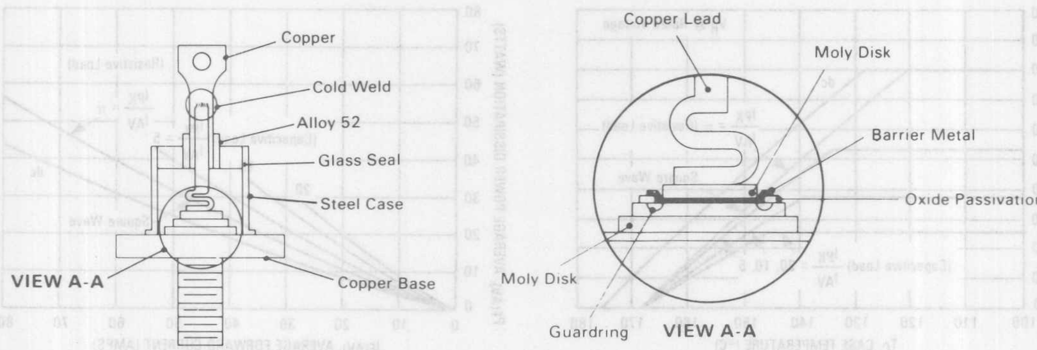


FIGURE 9 — SCHOTTKY RECTIFIER

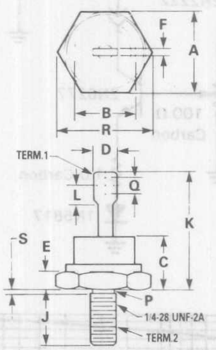


Motorola builds quality and reliability into its Schottky Rectifiers.

First is the chip, which has an interface metal between the platinum-barrier metal and nickel-gold ohmic-contact metal to eliminate any possible interaction with the barrier. The indicated guardring prevents dv/dt problems, so snubbers are not mandatory. The guardring also operates like a zener to absorb overvoltage transients.

Second is the package. There are molybdenum disks which closely match the thermal coefficient of expansion of silicon on each side of the chip. The top copper lead has a stress relief feature which protects the die during assembly. These two features give the unit the capability of passing stringent thermal fatigue tests for 5,000 cycles. The top copper lead provides a low resistance to current and therefore does not contribute to device heating; a heat sink should be used when attaching wires.

Third is the redundant electrical testing. The device is tested before assembly in "sandwich" form, with the chip between the moly disks. It is tested again after assembly. As part of the final electrical test, devices are 100% tested for dv/dt at 1,600 V/μs and reverse avalanche.



NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

STYLE 2:
TERM.1. ANODE
2. CATHODE (CASE)

CASE 257-01
DO-203AB
METAL

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and terminal lead is readily solderable

POLARITY: Cathode-to-Case

MOUNTING POSITION: Any

STUD TORQUE: 25 in.-lb Max

SOLDER HEAT: The excellent heat transfer property of the heavy duty copper anode terminal which transmits heat away from the die requires that caution be used when attaching wires. Motorola suggests a heat sink be clamped between the eyelet and the body during any soldering operation.

MBR12035CT
MBR12045CT
MBR12050CT
MBR12060CT

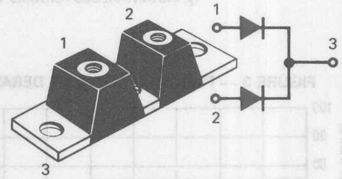
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

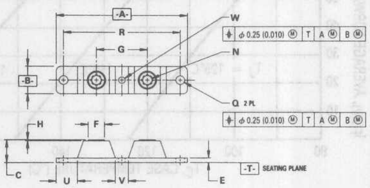
- Dual Diode Construction — May Be Paralleled For Higher Current Output
- Guardring For Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

120 AMPERES
35 to 60 VOLTS



3



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
POWER TAP

Terminal Penetration	0.280 Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

MAXIMUM RATINGS

Rating		Symbol	Max	Unit
Peak Repetitive Reverse Voltage	MBR12035CT	V_{RRM}	35	Volts
	MBR12045CT		45	
Working Peak Reverse Voltage	MBR12050CT	V_{RWM}	50	
DC Blocking Voltage	MBR12060CT	V_R	60	
Average Rectified Forward Current Per Device (Rated V_R) $T_C = 140°C$	Per Leg	$I_{F(AV)}$	120 60	Amps
Peak Repetitive Forward Current, Per Leg (Rated V_R, Square Wave, 20 kHz), $T_C = 140°C$		I_{FRM}	120	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	800	Amps
Peak Repetitive Reverse Current, Per Leg (2.0 μs, 1.0 kHz) See Figure 6		I_{RRM}	2.0	Amps
Operating Junction and Storage Temperature		T_J, T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

THERMAL CHARACTERISTICS PER LEG

Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.85	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Characteristic	Symbol	Max	Unit
Instantaneous Forward Voltage (1)	v_F		Volts
(i_F = 60 Amp, T_J = 125°C)		0.590	
(i_F = 120 Amp, T_J = 175°C)		0.620	
(i_F = 120 Amp, T_J = 125°C)		0.680	
(i_F = 120 Amp, T_J = 25°C)		0.830	
Instantaneous Reverse Current (1)	i_R		mA
(Rated dc Voltage, T_J = 125°C)		25	
(Rated dc Voltage, T_J = 25°C)		0.25	

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — TYPICAL FORWARD VOLTAGE PER LEG

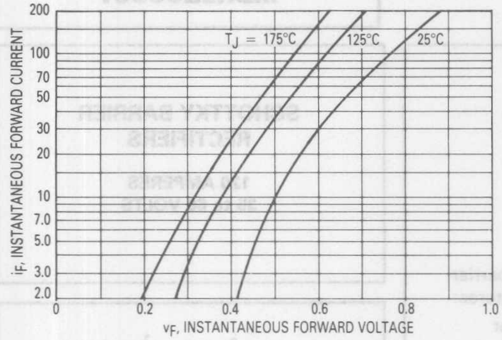


FIGURE 2 — TYPICAL REVERSE CURRENT, PER LEG*

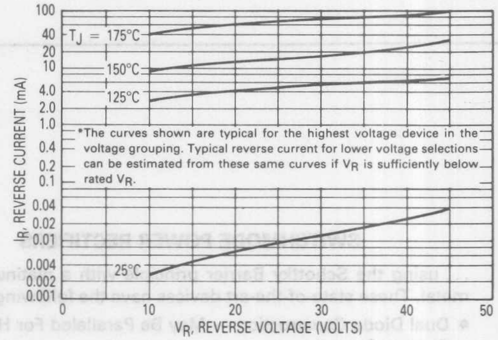


FIGURE 3 — FORWARD CURRENT DERATING, PER LEG

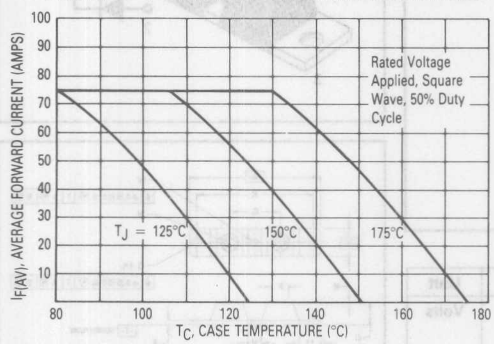


FIGURE 4 — POWER DISSIPATION PER LEG

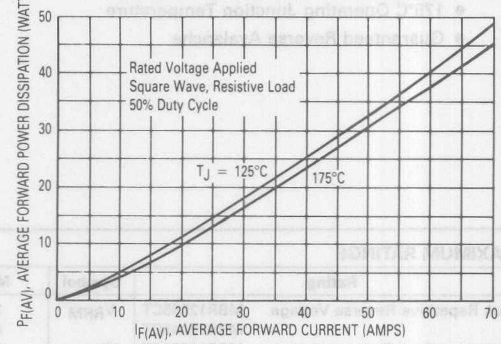


FIGURE 5 — TYPICAL CAPACITANCE, PER LEG

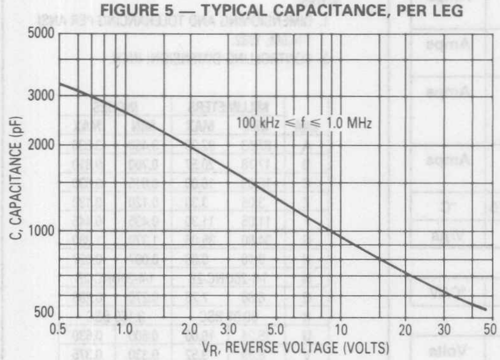
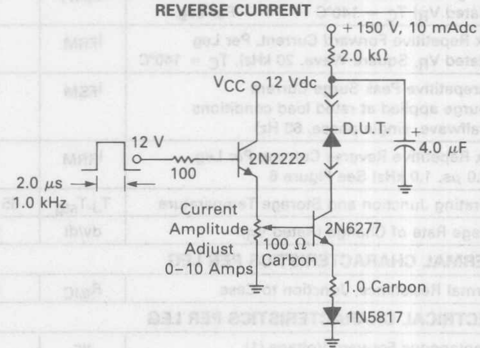


FIGURE 6 — TEST CIRCUIT FOR REPETITIVE REVERSE CURRENT



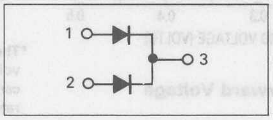
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

PowerTap Switchmode Power Rectifiers

MBR20015CTL
MBR20020CTL
MBR20025CTL
MBR20030CTL

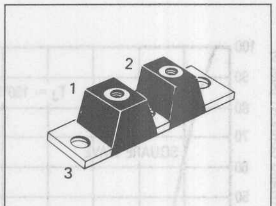
. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — May Be Paralleled For Higher Current Output
- Guardring For Stress Protection
- Low Forward Voltage
- 150°C Operating Junction Temperature
- Guaranteed Reverse Avalanche



LOW V_F
SCHOTTKY BARRIER RECTIFIERS
200 AMPERES
15 to 30 VOLTS

3



MAXIMUM RATINGS

Rating		Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	MBR20015CTL MBR20020CTL MBR20025CTL MBR20030CTL	V_{RRM} V_{RWM} V_R	15 20 25 30	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 140°C$	Per Device Per Leg	$I_{F(AV)}$	200 100	Amps
Peak Repetitive Forward Current, Per Leg (Rated V_R, Square Wave, 20 kHz), $T_C = 140°C$		I_{FRM}	200	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	1500	Amps
Peak Repetitive Reverse Current, Per Leg (2 μs, 1.0 kHz) See Figure 6		I_{RRM}	2	Amps
Storage Temperature		T_{stg}	−65 to +175	°C
Operating Junction and Storage Temperature		T_J, T_{stg}	−65 to +150	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

THERMAL CHARACTERISTICS PER LEG

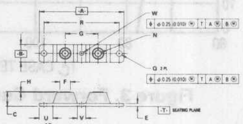
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.4	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Instantaneous Forward Voltage (1) (i_F = 100 Amp, T_J = 150°C) (i_F = 200 Amp, T_J = 150°C) (i_F = 100 Amp, T_J = 25°C) (i_F = 200 Amp, T_J = 25°C)	v_F	 0.39 0.48 0.46 0.55	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_J = 100°C) (Rated dc Voltage, T_J = 25°C)	i_R	 500 5	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

OUTLINE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
PowerTap

Terminal Penetration	0.280 Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

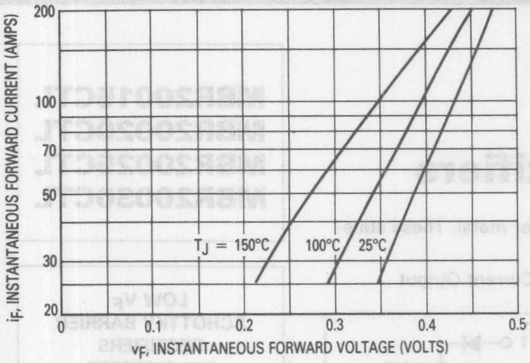
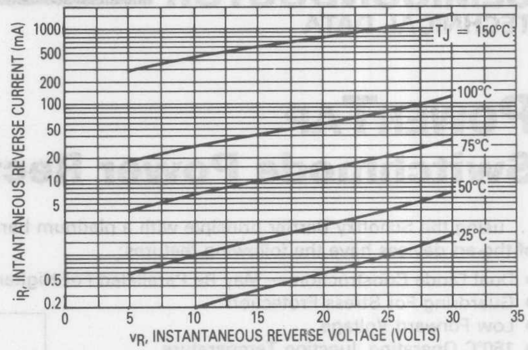


Figure 1. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

Figure 2. Typical Instantaneous Reverse Current, Per Leg*

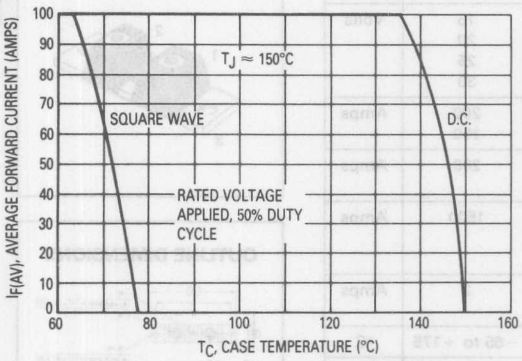


Figure 3. Forward Current Derating, Per Leg

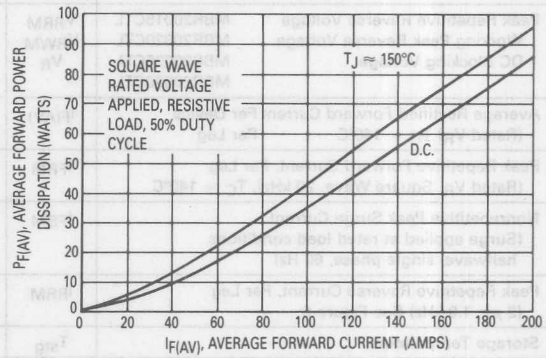


Figure 4. Power Dissipation Per Leg

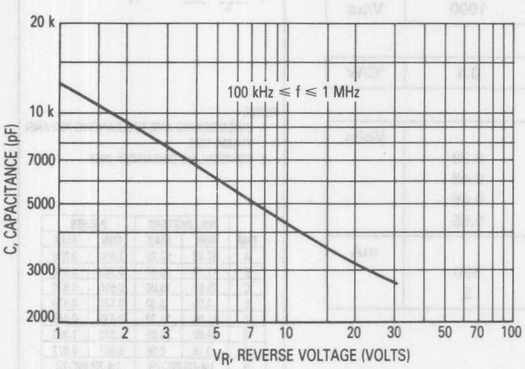


Figure 5. Typical Capacitance, Per Leg

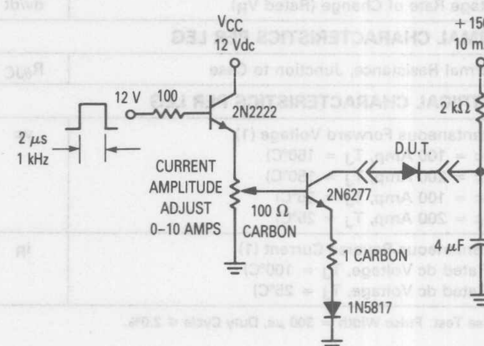


Figure 6. Test Circuit For Repetitive Reverse Current

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBR20035CT
MBR20045CT
MBR20050CT
MBR20060CT

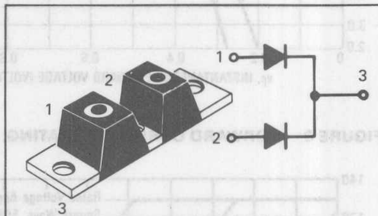
SWITCHMODE POWER RECTIFIERS

. . . using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — May Be Paralleled For Higher Current Output
- Guardring For Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

SCHOTTKY BARRIER RECTIFIERS

200 AMPERES
35 to 60 VOLTS



MAXIMUM RATINGS

Rating		Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	MBR20035CT MBR20045CT MBR20050CT MBR20060CT	V_{RRM} V_{RWM} V_R	35 45 50 60	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 140°C$	Per Device Per Leg	$I_{F(AV)}$	200 100	Amps
Peak Repetitive Forward Current, Per Leg (Rated V_R, Square Wave, 20 kHz), $T_C = 140°C$		I_{FRM}	200	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	1500	Amps
Peak Repetitive Reverse Current, Per Leg (2.0 μs, 1.0 kHz) See Figure 6		I_{RRM}	2.0	Amps
Operating Junction and Storage Temperature		T_J, T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

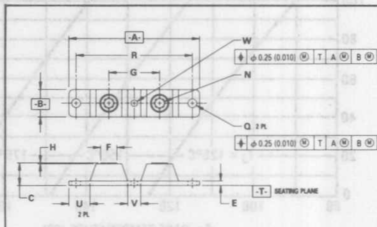
THERMAL CHARACTERISTICS PER LEG

Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.5	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Instantaneous Forward Voltage (1) (i_F = 200 Amp, T_J = 175°C) (i_F = 200 Amp, T_J = 125°C) (i_F = 100 Amp, T_J = 125°C) (i_F = 100 Amp, T_J = 25°C)	v_F	 0.650 0.825 0.710 0.800	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	i_R	 50 0.5	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
POWER TAP®

Terminal Penetration	0.280 in. Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

3

FIGURE 1 — TYPICAL FORWARD VOLTAGE, PER LEG

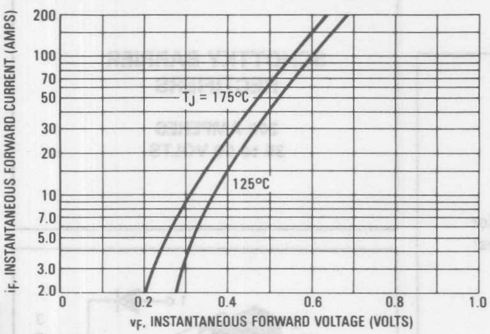
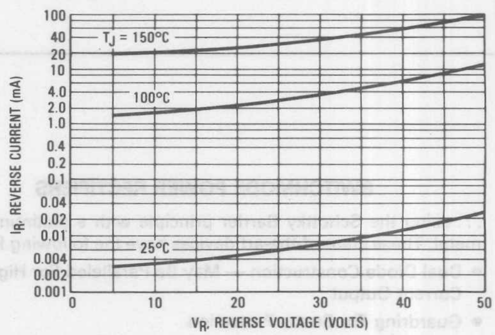


FIGURE 2 — TYPICAL REVERSE CURRENT, PER LEG



3

FIGURE 3 — FORWARD CURRENT DERATING, PER LEG

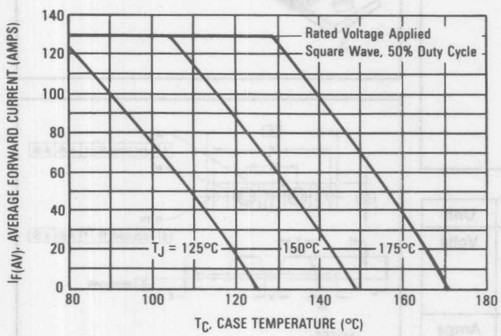


FIGURE 4 — POWER DISSIPATION, PER LEG

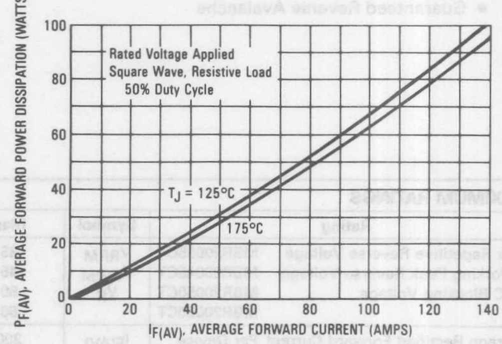


FIGURE 5 — CAPACITANCE, PER LEG

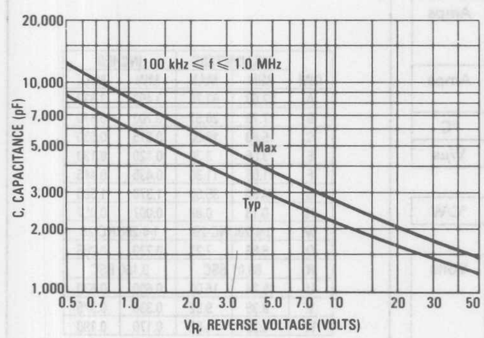
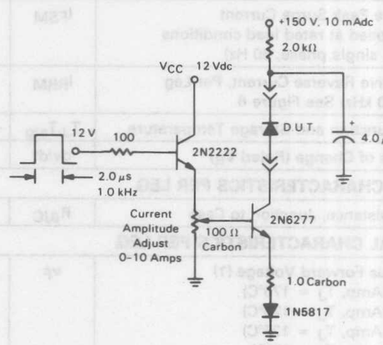


FIGURE 6 — TEST CIRCUIT FOR REPETITIVE REVERSE CURRENT



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

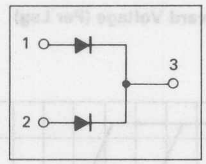
POWER TAP
Switchmode Power Rectifiers

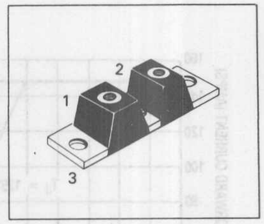
... using the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

- Dual Diode Construction — May Be Paralleled For Higher Current Output
- Guardring For Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Guaranteed Reverse Avalanche

MBR30035CT
MBR30045CT
MBR30050CT
MBR30060CT

SCHOTTKY BARRIER RECTIFIERS
300 AMPERES
35 TO 60 VOLTS





3

MAXIMUM RATINGS

Rating		Symbol	Max	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	MBR30035CT MBR30045CT MBR30050CT MBR30060CT	V_{RRM} V_{RWM} V_R	35 45 50 60	Volts
Average Rectified Forward Current (Rated V_R) T_C = 140°C	Per Device Per Leg	$I_{F(AV)}$	300 150	Amps
Peak Repetitive Forward Current, Peg Leg (Rated V_R, Square Wave, 20 kHz), T_C = 140°C		I_{FRM}	300	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	2500	Amps
Peak Repetitive Reverse Current, Per Leg (2 μs, 1 kHz) See Figure 6		I_{RRM}	2	Amps
Operating Junction and Storage Temperature		T_J, T_{stg}	−65 to +175	°C
Voltage Rate of Change (Rated V_R)		dv/dt	1000	V/μs

THERMAL CHARACTERISTICS PER LEG

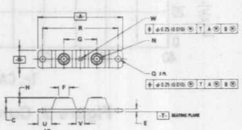
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.4	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Instantaneous Forward Voltage (1) (i_F = 150 Amps, T_C = 175°C) (i_F = 150 Amps, T_C = 125°C) (i_F = 300 Amps, T_C = 125°C) (i_F = 150 Amps, T_C = 25°C) (i_F = 300 Amps, T_C = 25°C)	v_F	 0.57 0.64 0.78 0.74 0.82	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 75 0.8	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

OUTLINE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
POWERTAP

Terminal Penetration	0.280″ Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

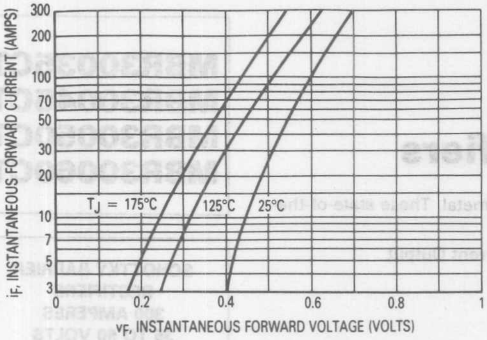


Figure 1. Typical Forward Voltage (Per Leg)

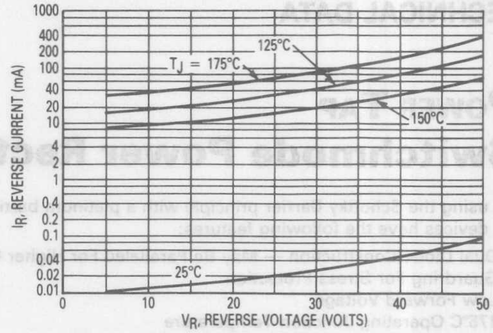


Figure 2. Typical Reverse Current (Per Leg)*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

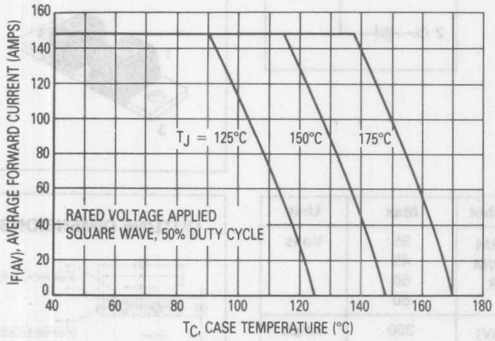


Figure 3. Current Derating (Per Leg)

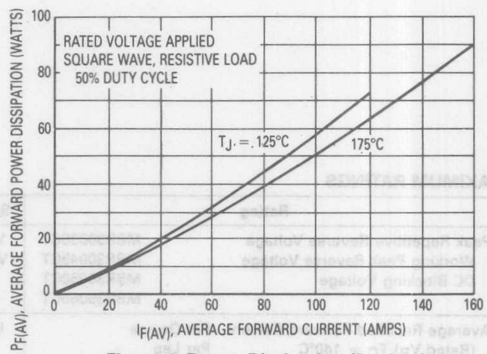


Figure 4. Power Dissipation (Per Leg)

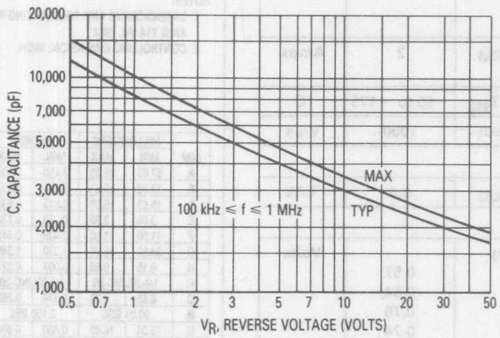


Figure 5. Capacitance (Per Leg)

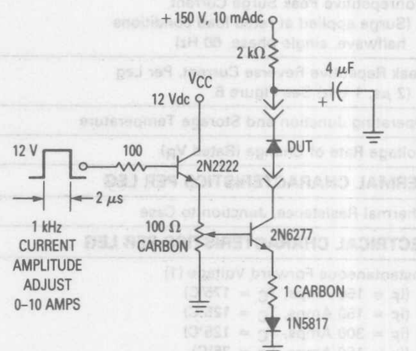


Figure 6. Test Circuit For Repetitive Reverse Current

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MBRD320
MBRD330
MBRD340
MBRD350
MBRD360

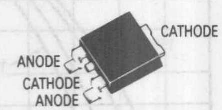
Switchmode Power Rectifiers
DPAK Surface Mount Package

SCHOTTKY BARRIER RECTIFIERS
3 AMPERES
20 TO 60 VOLTS

. . . designed for use as output rectifiers, free wheeling, protection and steering diodes in switching power supplies, inverters and other inductive switching circuits. These state-of-the-art devices have the following features:

- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- Guaranteed Reverse Avalanche

Mechanical Characteristics
- Case: Epoxy, Molded
- Finish: All External Surface Corrosion Resistance and Terminal Leads are Readily Solderable
- Lead Formed for Surface Mount
- Available in 16 mm Tape and Reel or Plastic Rails
- Compact Size
- Lead and Mounting Surface Temperature for Soldering Purposes 260°C Max. for 10 Seconds



CASE 369A-04
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBRD 320	MBRD 330	MBRD 340	MBRD 350	MBRD 360	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	Volts
Average Rectified Forward Current (T_C = +125°C, Rated V_R)	$I_{F(AV)}$			3			Amps
Peak Repetitive Forward Current, T_C = +125°C (Rated V_R, Square Wave, 20 kHz)	I_{FRM}			6			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}			75			Amps
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I_{RRM}			1			Amp
Operating Junction Temperature	T_J			−65 to +150			°C
Storage Temperature	T_{stg}			−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt			1000			V/μs

THERMAL CHARACTERISTICS

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	6	°C/W
Maximum Thermal Resistance, Junction to Ambient (1)	$R_{\theta JA}$	80	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (2) i_F = 3 Amps, T_C = +25°C i_F = 3 Amps, T_C = +125°C i_F = 6 Amps, T_C = +25°C i_F = 6 Amps, T_C = +125°C	v_F	 0.6 0.45 0.7 0.625	Volts
Maximum Instantaneous Reverse Current (2) (Rated dc Voltage, T_C = +25°C) (Rated dc Voltage, T_C = +125°C)	i_R	 0.2 20	mA

(1) Rating applies when surface mounted on the minimum pad size recommended.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

3

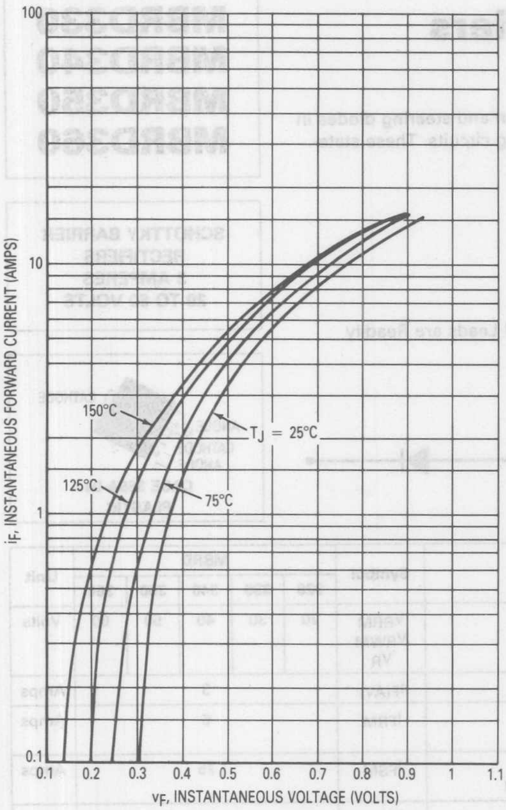
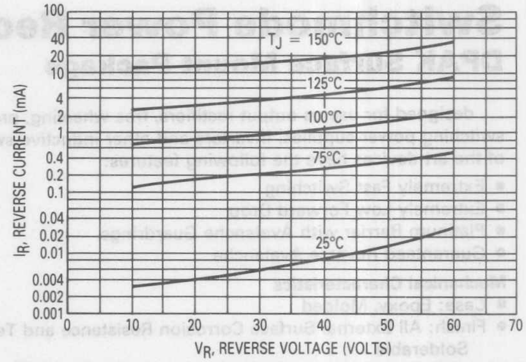


Figure 1. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Reverse Current

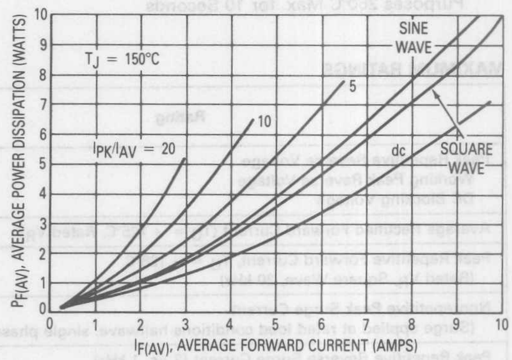


Figure 3. Average Power Dissipation

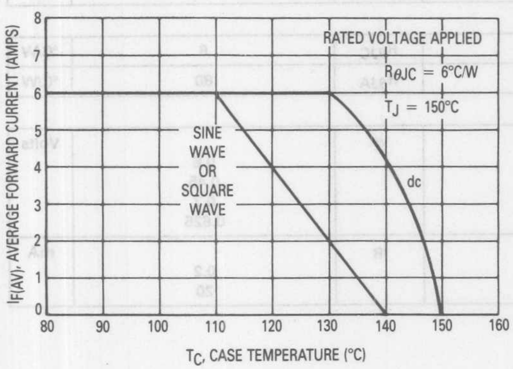


Figure 4. Current Derating, Case

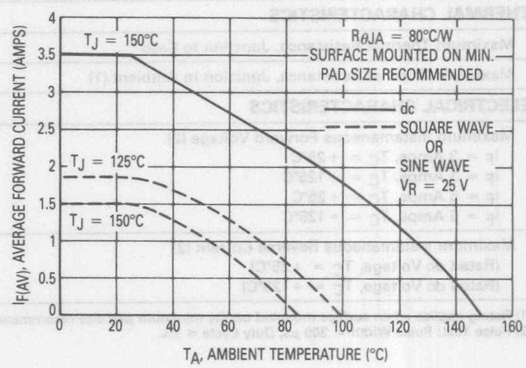


Figure 5. Current Derating, Ambient

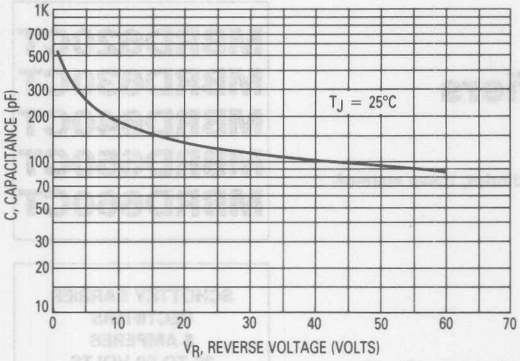
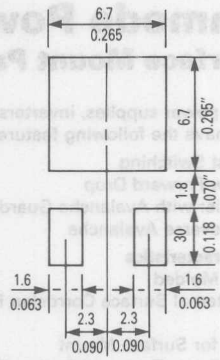
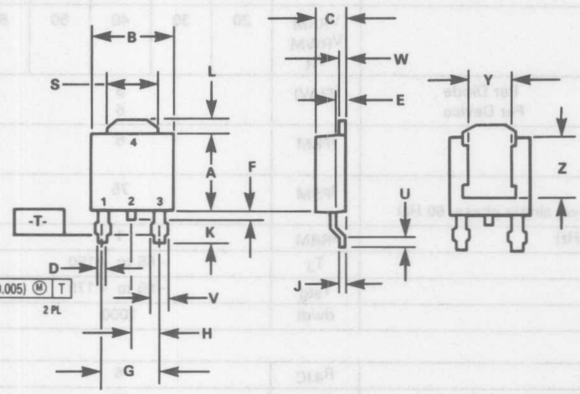


Figure 6. Typical Capacitance

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



OUTLINE DIMENSIONS



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.69	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.88	0.025	0.035
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	6.46	0.58	0.018	0.023
K	2.59	2.89	0.102	0.114
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—
Z	3.69	—	0.145	—

NOTES:
1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

CASE 369A-04
PLASTIC

Switchmode Power Rectifiers
DPAK Surface Mount Package

MBRD620CT
MBRD630CT
MBRD640CT
MBRD650CT
MBRD660CT

SCHOTTKY BARRIER RECTIFIERS
6 AMPERES
20 TO 60 VOLTS

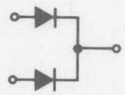
. . . in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

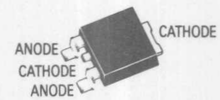
- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- Guaranteed Reverse Avalanche

Mechanical Characteristics

- Case: Epoxy, Molded
- Finish: All External Surface Corrosion Resistance and Terminal Leads are Readily Solderable
- Lead Formed for Surface Mount
- Available in 16 mm Tape and Reel or Plastic Rails
- Compact Size
- Lead and Mounting Surface Temperature for Soldering Purposes 260°C Max. for 10 Seconds

3





CASE 369A-04
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MBRD 620CT	MBRD 630CT	MBRD 640CT	MBRD 650CT	MBRD 660CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	50	60	Volts
Average Rectified Forward Current Per Diode $T_C = 130°C$ (Rated V_R) Per Device	$I_{F(AV)}$			3 6			Amps
Peak Repetitive Forward Current, $T_C = 130°C$ (Rated V_R, Square Wave, 20 kHz) Per Diode	I_{FRM}			6			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}			75			Amps
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I_{RRM}			1			Amp
Operating Junction Temperature	T_J			−65 to +150			°C
Storage Temperature	T_{stg}			−65 to +175			°C
Voltage Rate of Change (Rated V_R)	dv/dt			1000			V/μs

THERMAL CHARACTERISTICS PER DIODE

Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	6	°C/W
Maximum Thermal Resistance, Junction to Ambient (1)	$R_{\theta JA}$	80	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Maximum Instantaneous Forward Voltage (2) i_F = 3 Amps, T_C = 25°C i_F = 3 Amps, T_C = 125°C i_F = 6 Amps, T_C = 25°C i_F = 6 Amps, T_C = 125°C	v_F	 0.7 0.65 0.9 0.85	Volts
Maximum Instantaneous Reverse Current (2) (Rated dc Voltage, T_C = 25°C) (Rated dc Voltage, T_C = 125°C)	i_R	 0.1 15	mA

(1) Rating applies when surface mounted on the minimum pad size recommended.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

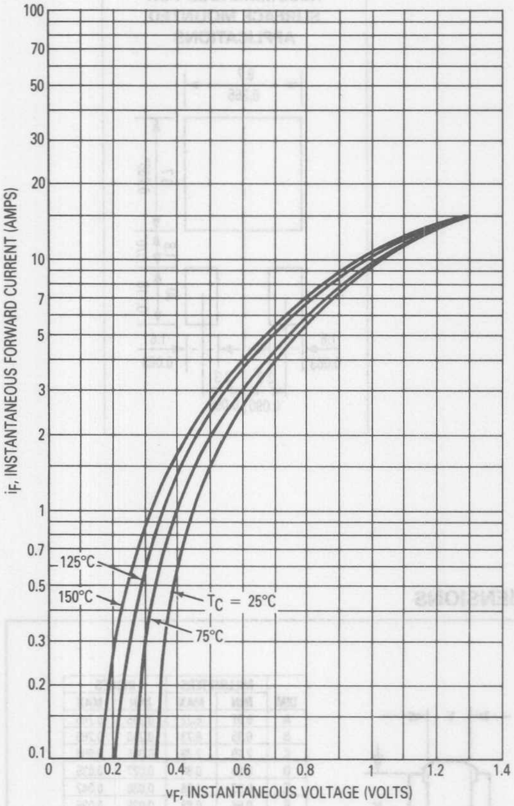
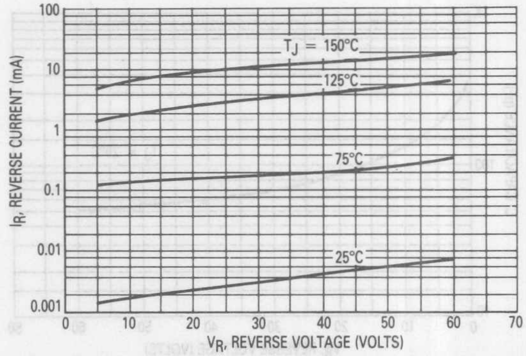


Figure 1. Typical Forward Voltage, Per Leg



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Reverse Current,* Per Leg

3

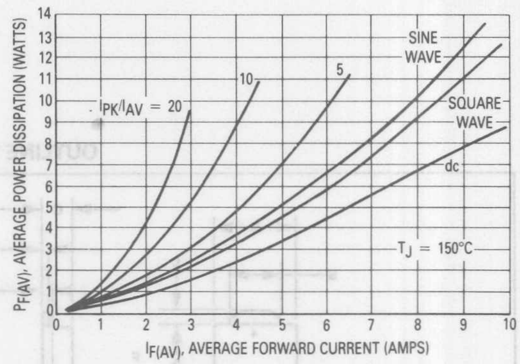


Figure 3. Average Power Dissipation, Per Leg

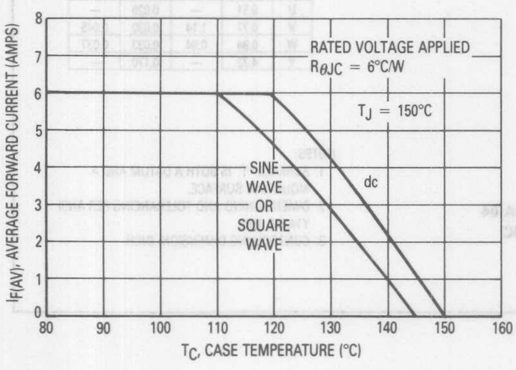


Figure 4. Current Derating, Case, Per Leg

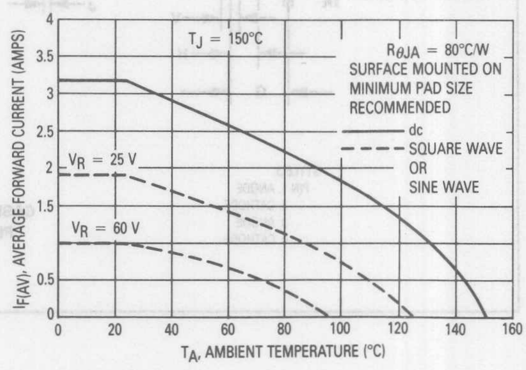


Figure 5. Current Derating, Ambient, Per Leg

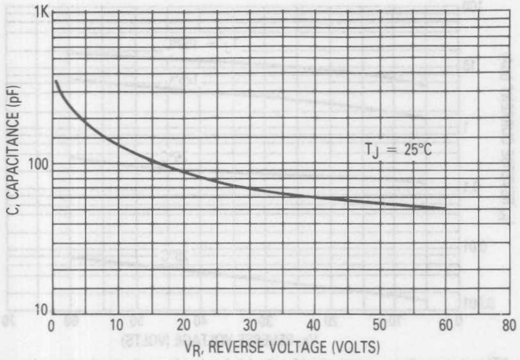
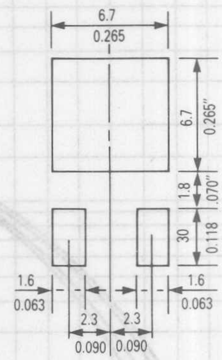
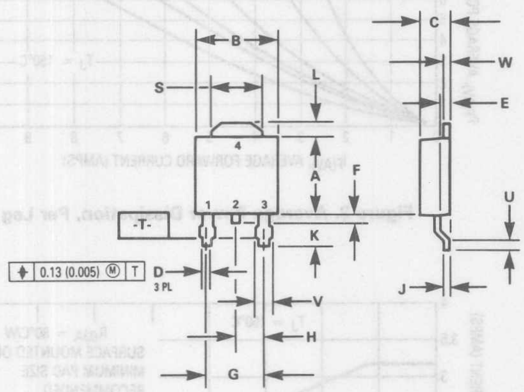


Figure 6. Typical Capacitance, Per Leg

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



OUTLINE DIMENSIONS



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.69	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.88	0.025	0.035
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	6.46	0.58	0.018	0.023
K	2.59	2.89	0.102	0.114
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—

STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

CASE 369A-04
PLASTIC

NOTES:
1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Switchmode Rectifiers

... designed for use in switching power supplies, inverters, and as free wheeling diodes, these devices have the following features:

- Low Forward Voltage
- Low Leakage Current
- Leadless Package for Surface Mount Technology

Mechanical Characteristics:

Case: Glass

Finish: End caps are plated and are readily solderable

Polarity: Cathode indicated by polarity band

Maximum Lead Temperature For Soldering Purposes:

230°C, @ end cap for 10 seconds.

MBRL120
MBRL130
MBRL140

LEADLESS SCHOTTKY RECTIFIERS
1 AMPERE
20–40 VOLTS

CASE 362B-01

3

MAXIMUM RATINGS

Rating	Symbol	MBRL 120	MBRL 130	MBRL 140	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	30	40	Volts
Average Rectified Forward Current (Rated V_R) T_C = 75°C, T_A = 50°C, Mounting Per Note 1	$I_{F(AV)}$		1		Amp
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}		20		Amps
Operating Junction and Storage Temperature	T_J, T_{stg}		−65 to +150		°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to End Cap	$R_{\theta JC}$	40	65	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Instantaneous Forward Voltage (1) (i_F = 1 A, T_J = 25°C) (i_F = 1 A, T_J = 125°C)	v_F	 0.690 0.650	Volts
Reverse Current (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	i_R	 10 0.1	mA

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

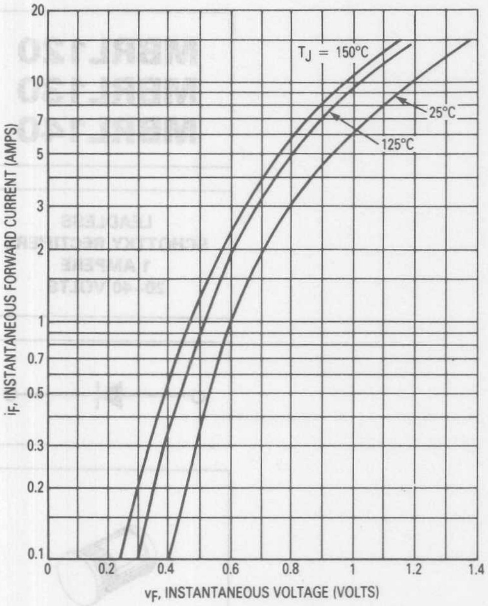
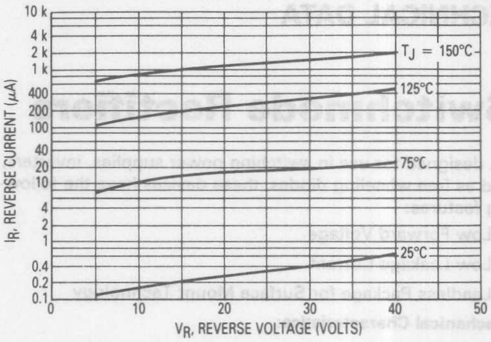


Figure 1. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

Figure 2. Typical Reverse Current*

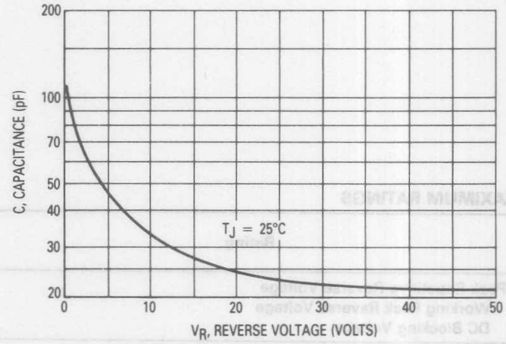


Figure 3. Typical Capacitance

3

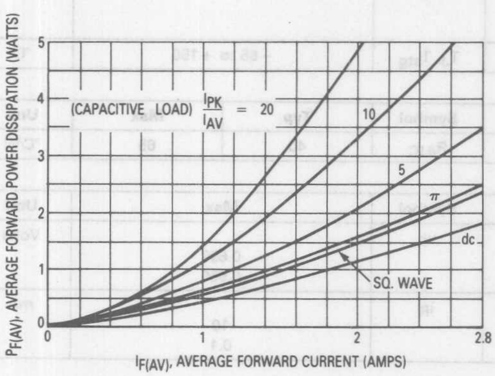


Figure 4. Forward Power Dissipation

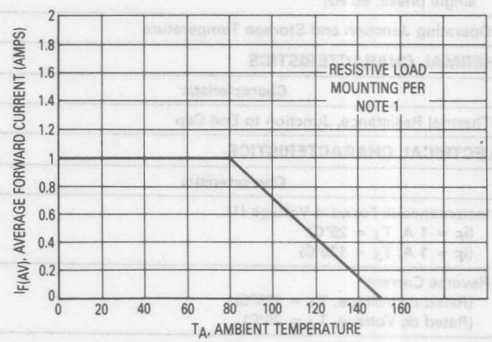
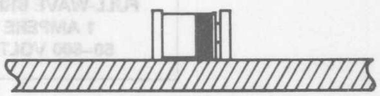


Figure 5. Current Derating, Printed Circuit Board Mounting

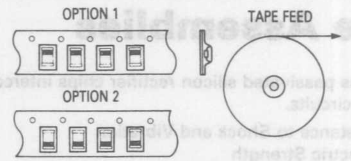
Note 1: Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mounting shown is to be used as a typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

Typical Values for θ_{JA} in Still Air = 118°C/W

PC Board with 1/4″ x 1/4″ Copper Mounting Pads



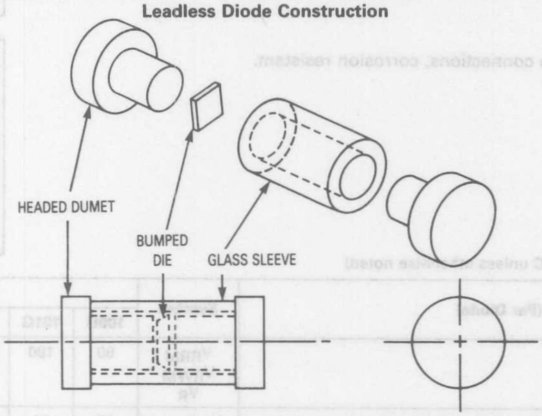
Tape & Reel Options
12 mm Tape
MLL41



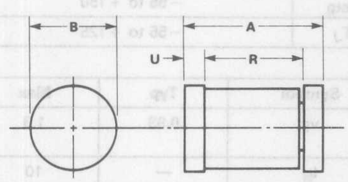
POLARITY BAND INDICATES CATHODE.

OPTION 1 = T1 DESIGNATOR
OPTION 2 = T2 DESIGNATOR

Leadless Diode Construction



OUTLINE DIMENSIONS



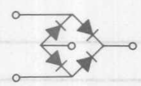
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.80	5.20	0.189	0.205
B	2.39	2.59	0.094	0.102
R	3.68	4.54	0.145	0.179
U	0.30	0.55	0.012	0.022

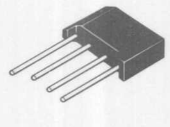
MLL41
CASE 362B-01

Integral Glass Passivated Diode Assemblies

MDA100G THRU MDA106G

**SINGLE-PHASE FULL-WAVE BRIDGE
1 AMPERE
50–600 VOLTS**





CASE 377A-01
PLASTIC

. . . with glass passivated silicon rectifier chips interconnected and encapsulated into rectifier bridge circuits.

- High Resistance to Shock and Vibration
- High Dielectric Strength
- Ideal for Printed Circuit Board

Mechanical Characteristics:
CASE: Premolded plastic housing
POLARITY: Terminal designation on case
(+) for DC output
(−) for DC output
(AC) for AC input
MOUNTING POSITION: Any
WEIGHT: 2.74 grams (approx.)
TERMINALS: Readily solderable connections, corrosion resistant.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating (Per Diode)	Symbol	MDA 100G	101G	102G	104G	106G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase bridge operation, resistive load, 60 Hz, T_A = 75°C)	I_O	1					Amp
Non-Repetitive Peak Surge Current (Preceded and followed by rated current and voltage, T_A = 75°C)	I_{FSM}	30 (for 1 cycle)					Amps
Storage Junction Temperature Range	T_{stg}	−55 to +150					°C
Operating Temperature Range	T_J	−55 to +125					°C

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) (i_F = 1.57 Amps, T_J = 25°C)	v_F	0.93	1.3	Volts
Reverse Current (Per Diode) (Rated V_R, @ T_A = 25°C)	I_R	—	10	μA

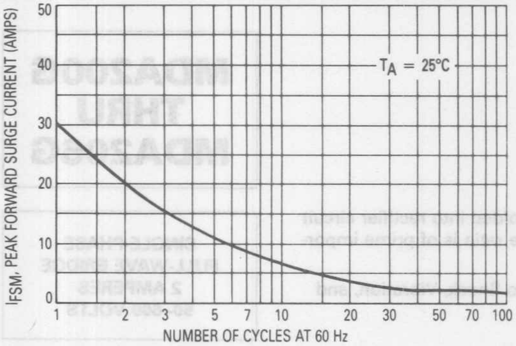


Figure 1. Maximum Non-Repetitive Forward Surge Current

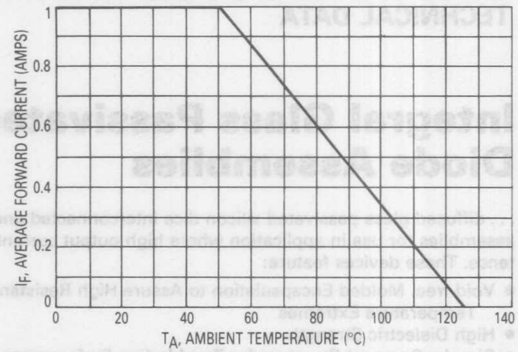


Figure 2. Typical Forward Current Derating Curve

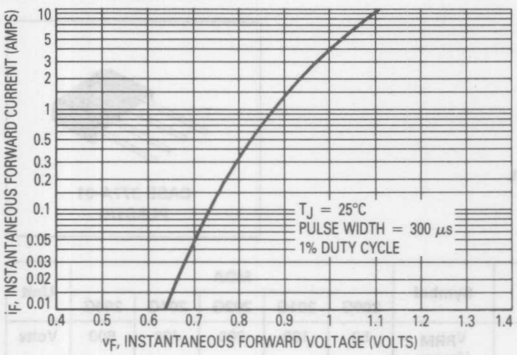


Figure 3. Typical Instantaneous Forward Per Bridge Element

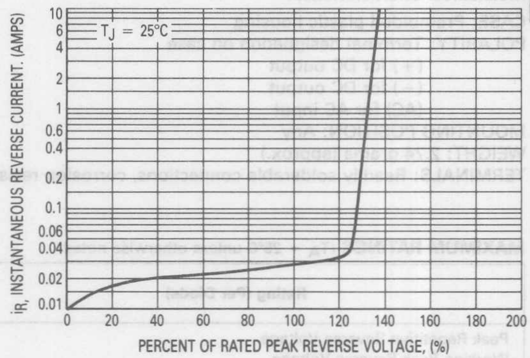
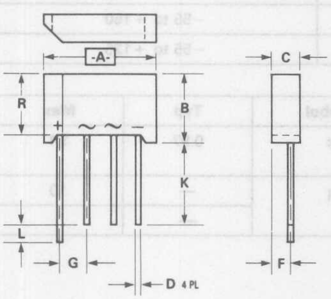


Figure 4. Typical Reverse Characteristics Per Diode

OUTLINE DIMENSIONS



NOTES:
1. POSITIONAL TOLERANCE FOR DIMENSION ϕD (4 PL): ϕ 0.25 (0.010) Ⓜ A Ⓜ
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.75	16.07	0.620	0.633
B	9.55	9.90	0.376	0.390
C	3.81	4.08	0.150	0.161
D	0.74	0.83	0.029	0.033
F	2.67 BSC		0.105 BSC	
G	3.81 BSC		0.150 BSC	
K	9.91	13.41	0.390	0.528
L	1.50	3.50	0.059	0.138
R	8.85	9.01	0.335	0.355

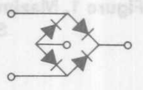
CASE 377A-01
PLASTIC

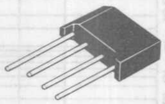
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Integral Glass Passivated Diode Assemblies

MDA200G THRU MDA206G

SINGLE-PHASE FULL-WAVE BRIDGE 2 AMPERES 50–600 VOLTS





CASE 377A-01 PLASTIC

. . . diffused glass passivated silicon dice interconnected and molded into rectifier circuit assemblies for use in application where high output current/size ratio is of prime importance. These devices feature:

- Void-free, Molded Encapsulation to Assure High Resistance to Shock, Vibration, and Temperature Extremes
- High Dielectric Strength
- Simple, Compact Structure for Trouble-free Performance
- Ideally Suited for P.C. Board Mounting
- High Surge Capability — 50 Amps
- Compatible with Automatic Assembly Techniques

3

Mechanical Characteristics:

CASE: Premolded plastic housing
POLARITY: Terminal designation on case
(+) for DC output
(−) for DC output
(AC) for AC input
MOUNTING POSITION: Any
WEIGHT: 2.74 grams (approx.)
TERMINALS: Readily solderable connections, corrosion resistant.

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating (Per Diode)	Symbol	MDA 200G	201G	202G	204G	206G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (single phase bridge operation, resistive load, 60 Hz, T_A = 50°C)	I_O	2					Amps
Non-Repetitive Peak Surge Current (Preceded and followed by rated current and voltage, T_A = 50°C)	I_{FSM}	50 (for 1 cycle)					Amps
Storage Junction Temperature Range	T_{stg}	−55 to +150					°C
Operating Temperature Range	T_J	−55 to +125					°C

ELECTRICAL CHARACTERISTICS

Characteristic		Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) (i_F = 3.14 Amps, T_J = 25°C)		v_F	0.97	1.1	Volts
Reverse Current at Rated DC Blocking Voltage Per Diode	@ T_A = 25°C	I_R	—	10	µA
	@ T_A = 100°C		—	1	mA

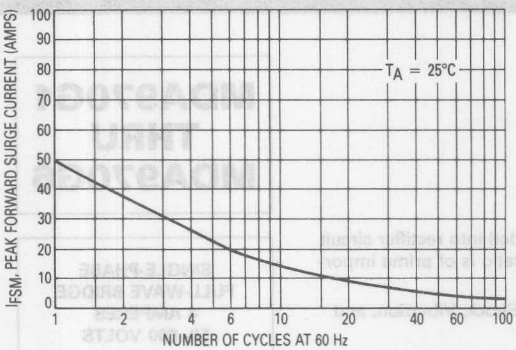


Figure 1. Maximum Non-Repetitive Forward Surge Current

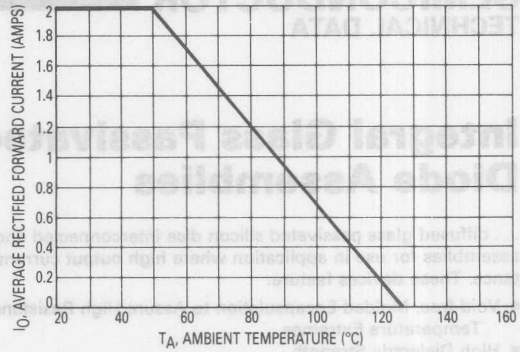


Figure 2. Forward Current Derating Curve

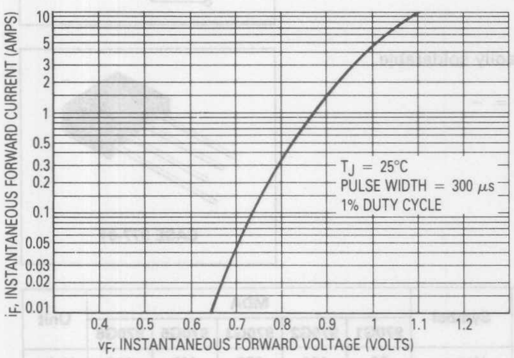


Figure 3. Typical Instantaneous Forward Per Bridge Diode

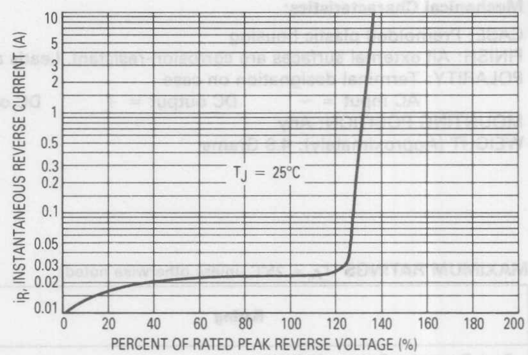
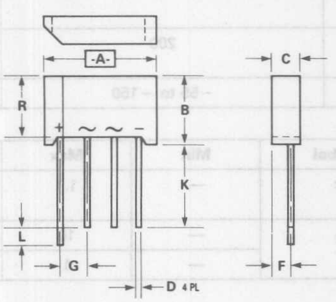


Figure 4. Typical Reverse Characteristics Per Diode

OUTLINE DIMENSIONS



NOTES:
1. POSITIONAL TOLERANCE FOR DIMENSION ϕD (4 PL):
   ⌖ ϕ 0.25 (0.010) Ⓜ A Ⓜ
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	15.75	16.07	0.620	0.633
B	9.55	9.90	0.376	0.390
C	3.81	4.08	0.150	0.161
D	0.74	0.83	0.029	0.033
F	2.67 BSC		0.105 BSC	
G	3.81 BSC		0.150 BSC	
K	9.91	13.41	0.390	0.528
L	1.50	3.50	0.059	0.138
R	8.85	9.01	0.335	0.355

CASE 377A-01
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Integral Glass Passivated Diode Assemblies

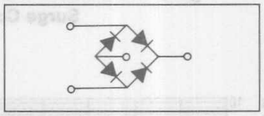
MDA970G1 THRU MDA970G6

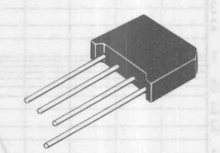
SINGLE-PHASE
FULL-WAVE BRIDGE
4 AMPERES
50–600 VOLTS

. . . diffused glass passivated silicon dice interconnected and molded into rectifier circuit assemblies for use in application where high output current/size ratio is of prime importance. These devices feature:

- Void-free, Molded Encapsulation to Assure High Resistance to Shock, Vibration, and Temperature Extremes
- High Dielectric Strength
- Simple, Compact Structure for Trouble-free Performance
- Ideally Suited for P.C. Board Mounting
- High Surge Capability — 200 Amps
- Compatible with Automatic Assembly Techniques

3





CASE 377-01

Mechanical Characteristics:

CASE: Premolded plastic housing
FINISH: All external surfaces are corrosion-resistant. Leads are readily solderable.
POLARITY: Terminal designation on case
AC input = ~ DC output = + DC output = −
MOUNTING POSITION: Any
WEIGHT (Approximately): 4.8 Grams

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating	Symbol	MDA 970G1	970G2	970G3	970G5	970G6	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current T_A = 50°C	I_O			4			Amps
Peak Forward Surge Current, 8.3 ms Single Half Sine-Wave Superimposed on Rated Load	I_{FSM}			200			Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}			−55 to +150			°C

ELECTRICAL CHARACTERISTICS

Characteristic		Symbol	Min	Max	Unit
Instantaneous Forward Voltage (Per Diode) (i_F = 6.28 Amps, T_J = 25°C)		v_F	—	1.1	Vdc
Reverse Current at Rated DC Blocking Voltage Per Diode	@ T_A = 25°C	I_R	—	10	μA
	@ T_A = 100°C		—	1	mA

MDA970G1 thru MDA970G6

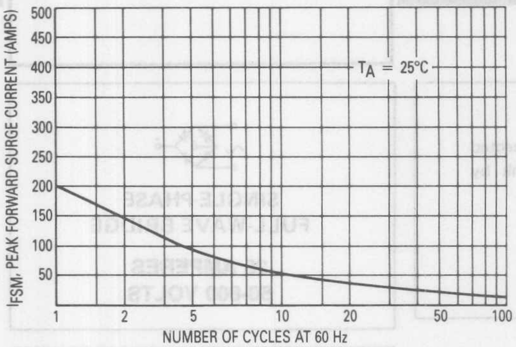


Figure 1. Maximum Non-Repetitive Forward Surge Current

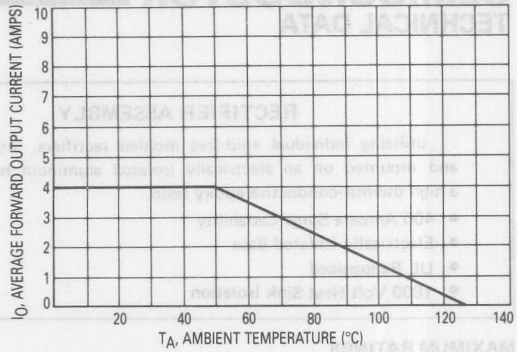


Figure 2. Forward Current Derating Curve

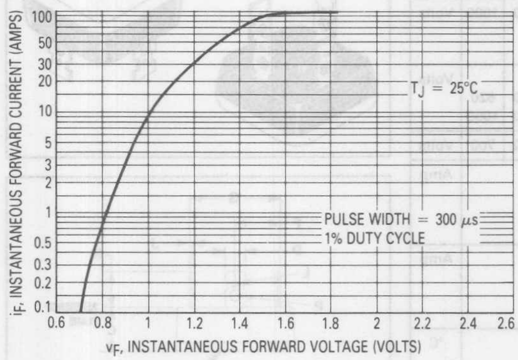


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

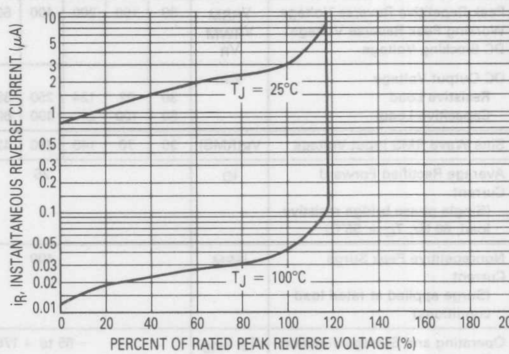
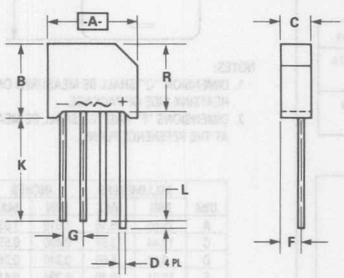


Figure 4. Typical Reverse Characteristics Per Diode

OUTLINE DIMENSIONS



NOTES:
1. POSITIONAL TOLERANCE FOR DIMENSION ϕD (4 PL):
   ϕ 0.25 (0.010) Ⓜ A Ⓜ
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	18.50	19.50	0.728	0.768
B	15.50	16.00	0.610	0.630
C	6.20	6.50	0.244	0.256
D	1.25	1.34	0.049	0.053
F	4.20 BSC		0.165 BSC	
G	5.08 BSC		0.200 BSC	
K	19.99	24.00	0.787	0.945
L	1.50	3.50	0.059	0.138
R	14.20	14.60	0.559	0.575

CASE 377-01
PLASTIC

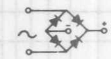
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MDA2500 Series

RECTIFIER ASSEMBLY

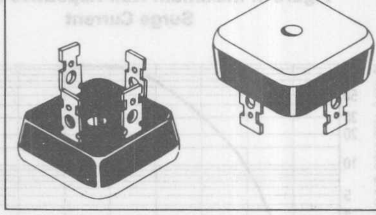
. . . utilizing individual void-free molded rectifiers, interconnected and mounted on an electrically isolated aluminum heat sink by a high thermal-conductive epoxy resin.

- 400 Ampere Surge Capability
- Electrically Isolated Base
- UL Recognized
- 1800 Volt Heat Sink Isolation



SINGLE-PHASE
FULL-WAVE BRIDGE

25 AMPERES
50-600 VOLTS



3

MAXIMUM RATINGS

Rating (Per Diode)	Symbol	MDA 2500	2501	2502	2504	2506	2508	2510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
DC Output Voltage	Vdc								Volts
Resistive Load		30	62	124	250	380	500	620	
Capacitive Load		50	100	200	400	600	600	1000	
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (Single phase bridge resistive load, 60 Hz, $T_C = 55°C$)	I_O				25				Amp
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}				400				Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}				−65 to +175				°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$			°C/W
Each Die		4.5	6.0	
Total Bridge		2.0	2.8	

ELECTRICAL CHARACTERISTICS ($T_C = 25°C$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) ($i_F = 40$ A)*	v_F	—	0.95	1.05	Volts
Reverse Current (Per Diode) (Rated V_R)	I_R	—	—	10	μA

MECHANICAL CHARACTERISTICS

CASE: Plastic case with an electrically isolated aluminum base.

POLARITY: Terminal designation embossed on case:
+DC output
−DC output
AC not marked

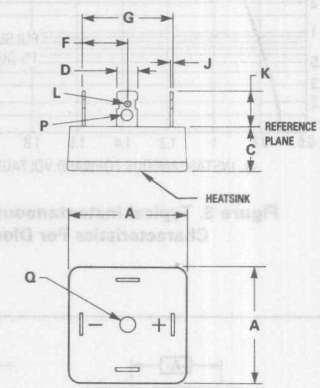
MOUNTING POSITION: Bolt down. Highest heat transfer efficiency accomplished through the surface opposite the terminals. Use silicone heat sink compound on mounting surface for maximum heat transfer.

WEIGHT: 25 grams (approx.)

TERMINALS: Suitable for fast-on connections. Readily solderable, corrosion resistant. Soldering recommended for applications greater than 15 amperes.

MOUNTING TORQUE: 20 in. lb. max.

*Pulse Width = 100 ms, Duty Cycle ≤ 2%.



NOTES:
1. DIMENSION "Q" SHALL BE MEASURED ON HEATSINK SIDE OF PACKAGE.
2. DIMENSIONS "F" AND "G" SHALL BE MEASURED AT THE REFERENCE PLANE.

DIM	MILLIMETERS MIN	MAX	INCHES MIN	MAX
A	25.65	26.16	1.010	1.030
C	12.44	13.97	0.490	0.550
D	6.10	6.60	0.240	0.260
F	10.01	10.49	0.394	0.413
G	19.99	21.01	0.787	0.827
J	0.71	0.86	0.028	0.034
K	9.52	11.43	0.375	0.450
L	1.52	2.06	0.060	0.081
P	2.79	2.92	0.110	0.115
Q	4.42	4.67	0.174	0.184

CASE 309A-03

FIGURE 1 – FORWARD VOLTAGE

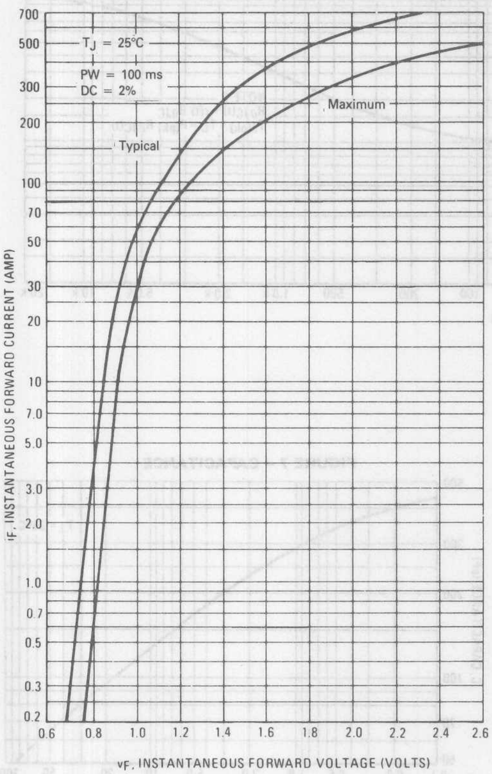


FIGURE 2 – NON REPETITIVE SURGE CURRENT

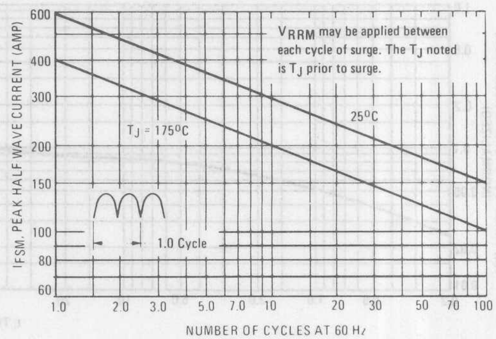


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

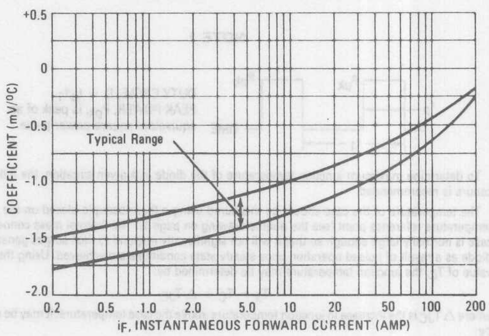


FIGURE 4 – CURRENT DERATING

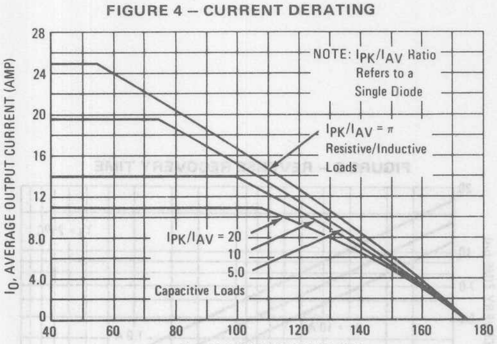


FIGURE 5 – FORWARD POWER DISSIPATION

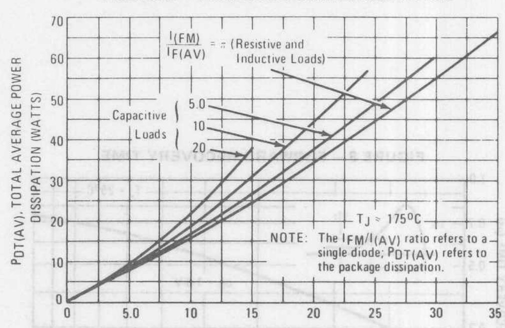
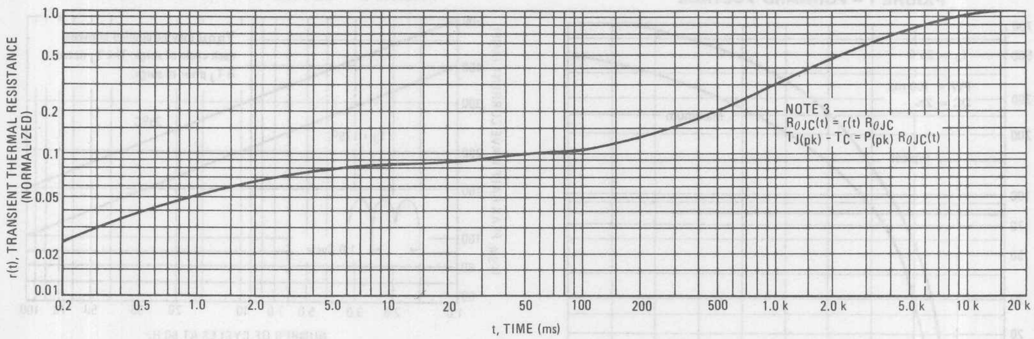
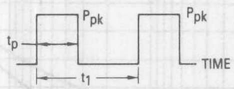


FIGURE 6 – TYPICAL THERMAL RESPONSE



3

NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see the outline drawing on page 1). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC} [D + (1 - D) \bullet r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 6, i.e.,
$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 7 – CAPACITANCE

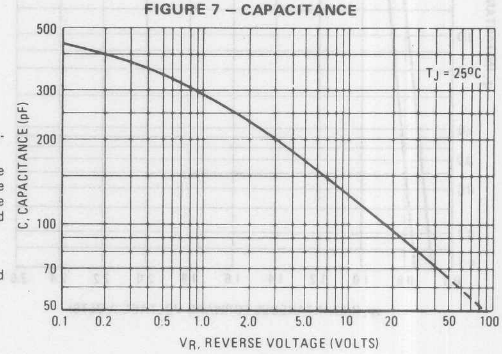


FIGURE 8 – FORWARD RECOVERY TIME

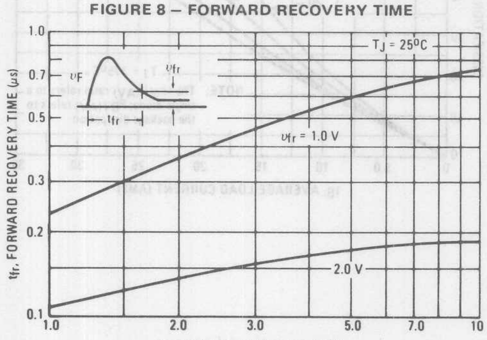
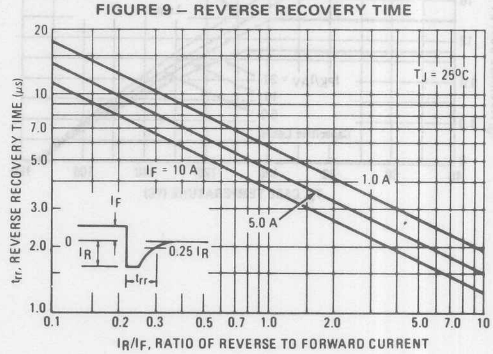


FIGURE 9 – REVERSE RECOVERY TIME



AMBIENT TEMPERATURE DERATING INFORMATION

FIGURE 10A — THERMALLOY HEAT SINK 6005B

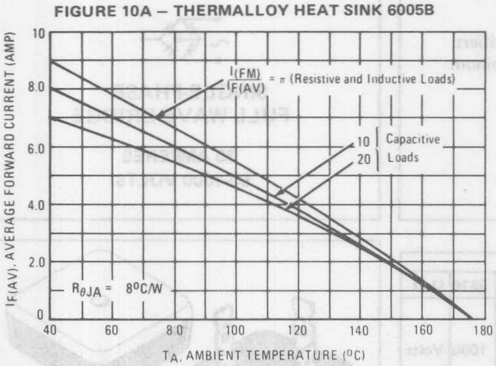
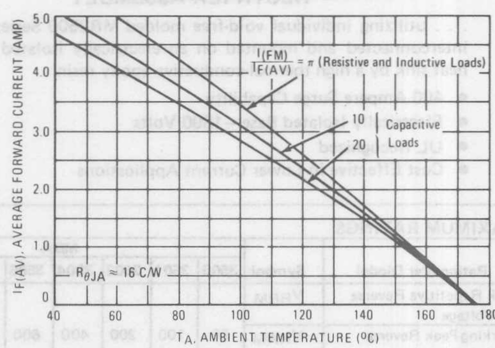


FIGURE 10B — IERC HEAT SINK UP3



NOTE 2: THERMAL COUPLING AND EFFECTIVE THERMAL RESISTANCE

In multiple chip devices where there is coupling of heat between die, the junction temperature can be calculated as follows:

(1) $\Delta T_{J1} = R_{\theta 1}P_{D1} + R_{\theta 2}K_{\theta 2}P_{D2} + R_{\theta 3}K_{\theta 3}P_{D3} + R_{\theta 4}K_{\theta 4}P_{D4}$

where ΔT_{J1} is the change in junction temperature of diode 1, $R_{\theta 1}$ through 4 is the thermal resistance of diodes 1 through 4, P_{D1} through 4 is the power dissipated in diodes 1 through 4, $K_{\theta 2}$ through 4 is the thermal coupling between diode 1, and diodes 2 through 4.

An effective package thermal resistance can be defined as follows:

$$(2)\quad R_{\theta(EFF)} = \Delta T_{J1}/P_{DT}$$

where P_{DT} is the total package power dissipation.

Assuming equal thermal resistance for each die, equation (1) simplifies to

$$(3)\quad \Delta T_{J1} = R_{\theta 1}(P_{D1} + K_{\theta 2}P_{D2} + K_{\theta 3}P_{D3} + K_{\theta 4}P_{D4})$$

For the conditions where $P_{D1} = P_{D2} = P_{D3} = P_{D4}$, $P_{DT} = 4\,P_{D1}$, equation (3) can be further simplified and by substituting into equation (2) results in

$$(4)\quad R_{\theta(EFF)} = R_{\theta 1}(1 + K_{\theta 2} + K_{\theta 3} + K_{\theta 4})/4$$

When the case is used as a reference point, coupling between opposite die is negligible for the MDA2500, and coupling between adjacent die is approximately 6%.

NOTE 3: SPLIT LOAD DERATING INFORMATION

Bridge rectifiers are used in two basic configurations as shown by circuits A and B of Figure 11. The current derating data of Figure 4 applies to the standard bridge circuit (A) where $I_A = I_B$. For circuit B where $I_A \neq I_B$, derating information can be calculated as follows:

$$(6)\quad T_{R(max)} = T_{J(max)} - \Delta T_{J1}$$

Where $T_{R(max)}$ is the reference temperature (either case or ambient), ΔT_{J1} can be calculated using equation (3) in Note 2.

For example, to determine $T_{C(max)}$ for the MDA2500 with the following capacitive load conditions:

I_A = 20 A average with a peak of 60 A,
I_B = 10 A average with a peak of 70 A,

first calculate the peak to average ratio for I_A. $I_{(PK)}/I_{(AV)}$ = 60/10 = 6.0. (Note that the peak to average ratio is on a per diode basis and each diode provides 10 A average.)

From Figure 5, for an average current of 20 A and an $I_{(PK)}/I_{(AV)}$ = 6.0, read $P_{DT(AV)}$ = 40 watts or 10 watts/diode. Thus $P_{D1} = P_{D3}$ = 10 watts.

Similarly, for a load current I_B of 10 A, diode #2 and diode #4 each see 5.0 A average resulting in an $I_{(PK)}/I_{(AV)}$ = 14. Thus, the package power dissipation for 10 A is 20 watts or 5.0 watts/diode. Therefore, $P_{D2} = P_{D4}$ = 5.0 watts.

The maximum junction temperature occurs in diodes #1 and #3. From equation (3) for diode #1,

$$\Delta T_{J1} = 10[10 + 0(5) + 0.06(10) + 0.06(5)]$$

$$\Delta T_{J1} \approx 109^{\circ}C.$$

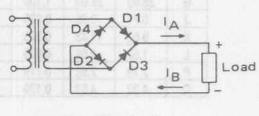
Thus, $T_{C(max)} = 175 - 109 = 66^{\circ}C$.

The total package dissipation in this example is

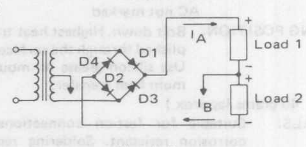
$$P_{DT(AV)} = 2 \times 10 + 2 \times 5.0 = 30 \text{ watts},$$

which must be considered when selecting a heat sink.

FIGURE 11 — BASIC CIRCUIT USES FOR BRIDGE RECTIFIERS



Circuit A



Circuit B

3

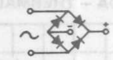
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MDA3500 Series

RECTIFIER ASSEMBLY

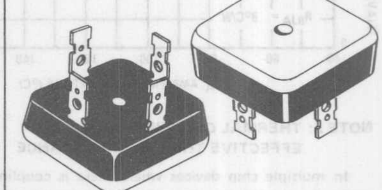
. . . utilizing individual void-free molded MR2500 Series rectifiers, interconnected and mounted on an electrically isolated aluminum heat sink by a high thermal-conductive epoxy resin.

- 400 Ampere Surge Capability
- Electrically Isolated Base—1800 Volts
- UL Recognized
- Cost Effective in Lower Current Applications



SINGLE-PHASE FULL-WAVE BRIDGE

35 AMPERES 50-1000 VOLTS



3

MAXIMUM RATINGS

Rating (Per Diode)	Symbol	MDA 3500	3501	3502	3504	3506	3508	3510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
DC Output Voltage Resistive Load Capacitive Load	 Vdc Vdc	 30 50	 62 100	 124 200	 250 400	 380 600	 500 800	 630 1000	 Volts Volts
Sine Wave RMS Input Voltage	$V_{R(RMS)}$	35	70	140	280	420	560	700	Volts
Average Rectified Forward Current (Single phase bridge resistive load, 60 Hz, $T_C = 55^oC$)	I_O	← 35 →							Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	← 400 →							Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +175 →							^oC

THERMAL CHARACTERISTICS (Total Bridge)

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.4	1.87	$^oC/W$

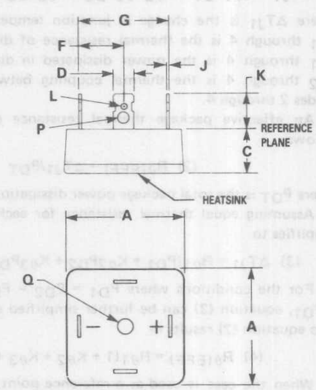
ELECTRICAL CHARACTERISTICS ($T_C = 25^oC$ unless otherwise noted).

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (Per Diode) (i_F = 55 A)*	v_F	—	1.0	1.1	Volts
Reverse Current (Per Diode) (Rated V_R)	I_R	—	—	10	μA

MECHANICAL CHARACTERISTICS

CASE: Plastic case with an electrically isolated aluminum base.
POLARITY: Terminal-designation embossed on case
+DC output
-DC output
AC not marked
MOUNTING POSITION: Bolt down. Highest heat transfer efficiency accomplished through the surface opposite the terminals. Use silicon grease on mounting surface for maximum heat transfer.
WEIGHT: 40 grams (approx.)
TERMINALS: Suitable for fast-on connections. Readily solderable, corrosion resistant. Soldering recommended for applications greater than 15 Amperes.
MOUNTING TORQUE: 20 in. lb. Max.

*Pulse Width = 100 ms, Duty Cycle ≤ 2%.



NOTES:
1. DIMENSION "Q" SHALL BE MEASURED ON HEATSINK SIDE OF PACKAGE.
2. DIMENSIONS F AND G SHALL BE MEASURED AT THE REFERENCE PLANE.

DIM	MILLIMETERS MIN	MAX	INCHES MIN	MAX
A	34.80	35.18	1.370	1.385
C	12.44	13.97	0.490	0.550
D	6.10	6.60	0.240	0.260
F	13.97	14.50	0.550	0.571
G	28.00	29.00	1.100	1.142
J	0.71	0.86	0.028	0.034
K	9.52	11.43	0.375	0.450
L	1.52	2.06	0.060	0.081
P	2.79	2.92	0.110	0.115
Q	4.32	4.83	0.170	0.190

CASE 309A-02

FIGURE 1 – FORWARD VOLTAGE

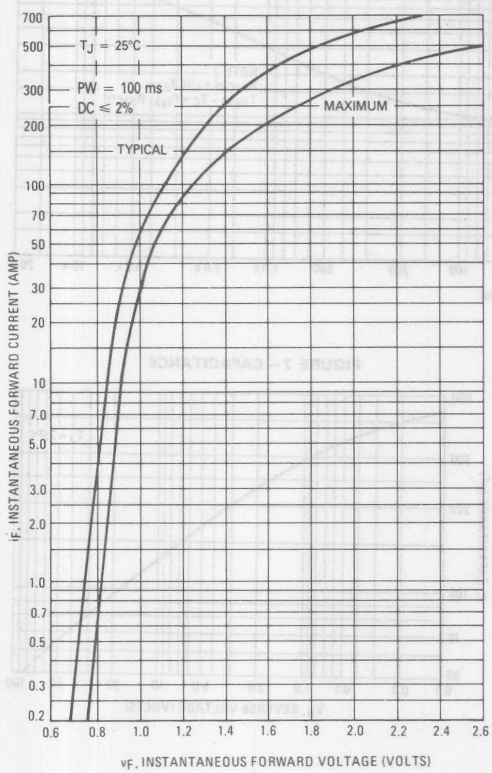


FIGURE 2 – NON REPETITIVE SURGE CURRENT

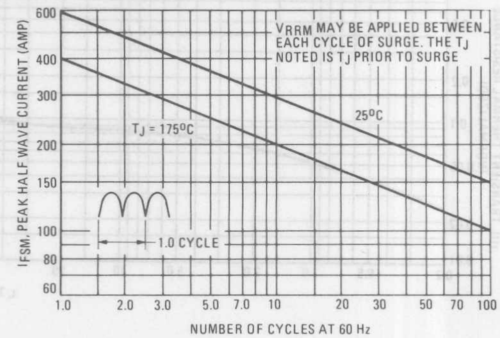


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

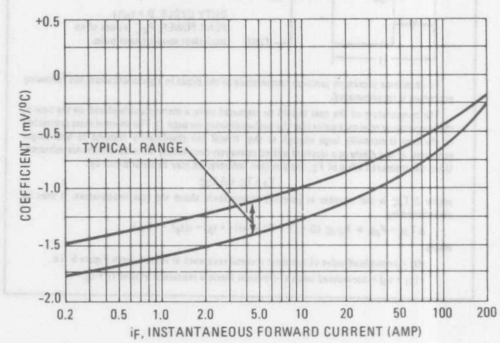


FIGURE 4 – CURRENT DERATING

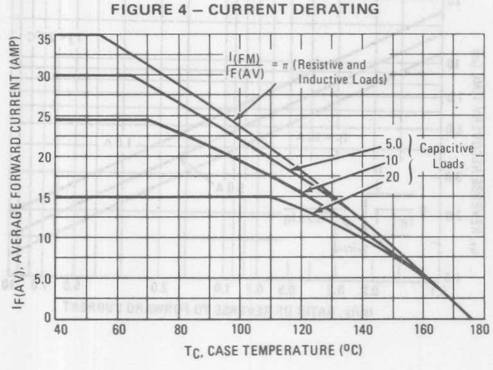


FIGURE 5 – FORWARD POWER DISSIPATION

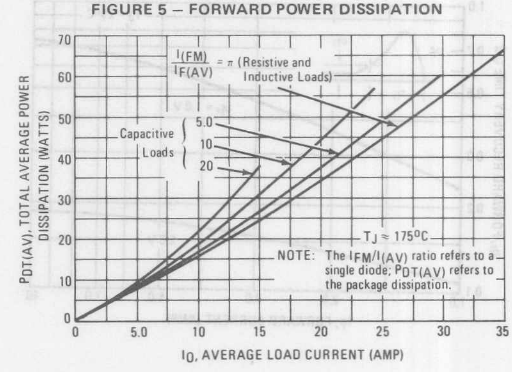
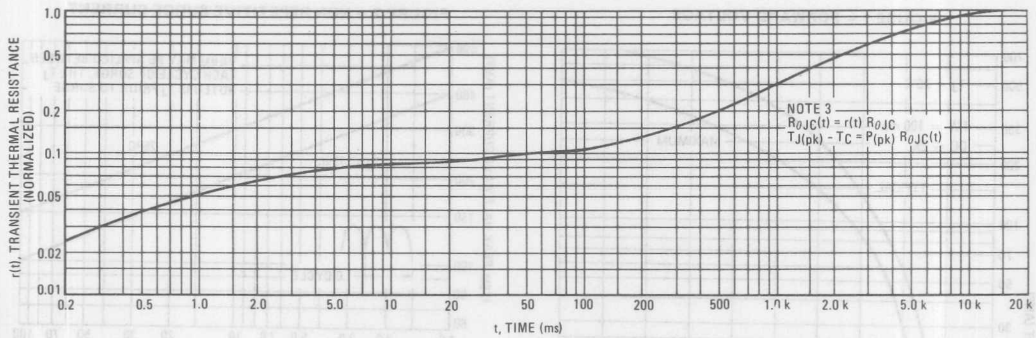
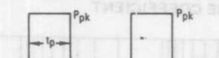


FIGURE 6 – TYPICAL THERMAL RESPONSE



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see the outline drawing on page 1). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC}\ [D + (1 - D) \bullet r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 6, i.e.,
$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 7 – CAPACITANCE

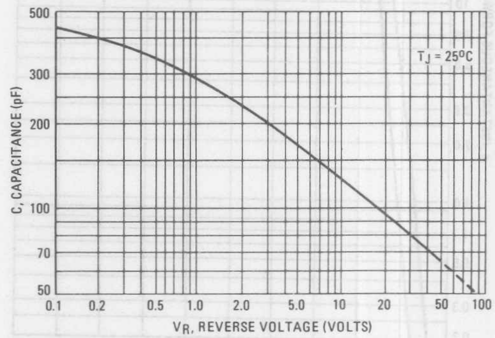


FIGURE 8 – FORWARD RECOVERY TIME

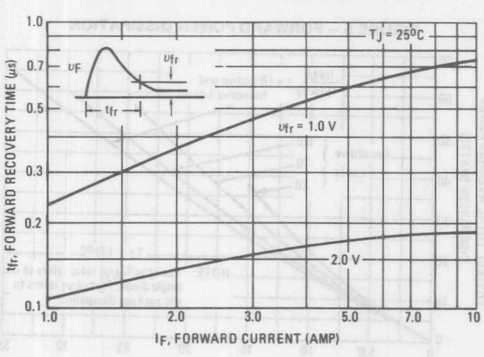
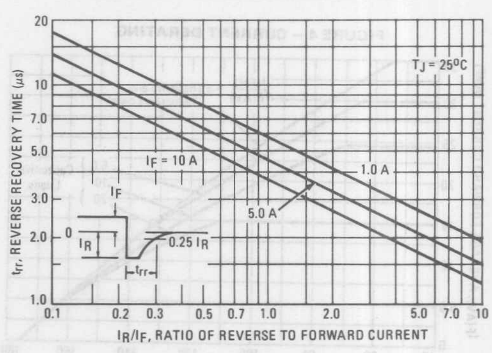


FIGURE 9 – REVERSE RECOVERY TIME



AMBIENT TEMPERATURE DERATING INFORMATION

FIGURE 10A — THERMALLOY HEATSINK 6005B

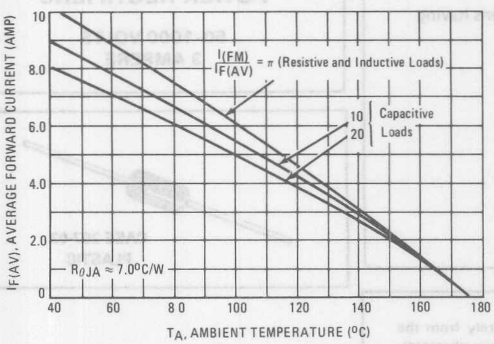
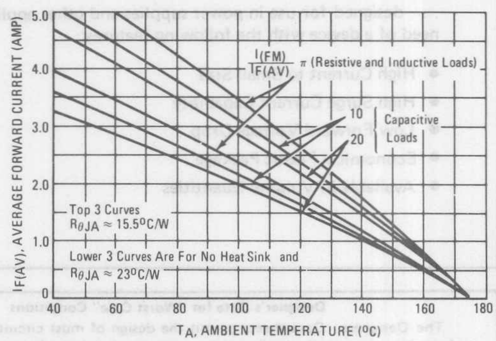


FIGURE 10B — IERC HEATSINK UP3 AND NO HEATSINK



NOTE 2: THERMAL COUPLING AND EFFECTIVE THERMAL RESISTANCE

In multiple chip devices where there is coupling of heat between die, the junction temperature can be calculated as follows:

(1) $\Delta T_{J1} = R_{\theta 1} P_{D1} + R_{\theta 2} K_{\theta 2} P_{D2} + R_{\theta 3} K_{\theta 3} P_{D3} + R_{\theta 4} K_{\theta 4} P_{D4}$

Where ΔT_{J1} is the change in junction temperature of diode 1
$R_{\theta 1}$ thru 4 is the thermal resistance of diodes 1 through 4
P_{D1} thru 4 is the power dissipated in diodes 1 through 4
$K_{\theta 2}$ thru 4 is the thermal coupling between diode 1 and diodes 2 through 4.

An effective package thermal resistance can be defined as follows:

(2) $R_{\theta(EFF)} = \Delta T_{J1}/P_{DT}$

Where: P_{DT} is the total package power dissipation

Assuming equal thermal resistance for each die, equation (1) simplifies to

(3) $\Delta T_{J1} = R_{\theta 1} (P_{D1} + K_{\theta 2} P_{D2} + K_{\theta 3} P_{D3} + K_{\theta 4} P_{D4})$

For the condiitons where $P_{D1} = P_{D2} = P_{D3} = P_{D4}$, $P_{DT} = 4 P_{D1}$, equation (3) can be further simplified and by substituting into equation (2) results in

(4) $R_{\theta(EFF)} = R_{\theta 1} (1 + K_{\theta 2} + K_{\theta 3} + K_{\theta 4})/4$

When the case is used as a reference point, coupling between die is neglegible for the MDA3500. When the bridge is used without a heatsink, coupling between die is approximately 70% and $R_{\theta 1}$ is $30^oC/W$,

$\therefore R_{\theta(EFF)} = 30\,[1 + (3)\,(.7)]/4 = 23^oC/W$

NOTE 3: SPLIT LOAD DERATING INFORMATION

Bridge rectifiers are used in two basic configurations as shown by circuits A and B of Figure 11. The current derating data of Figure 4 applies to the standard bridge circuit (A) where $I_A = I_B$. For circuit B where $I_A \neq I_B$, derating information can be calculated as follows:

(6) $T_{R(Max)} = T_{J(Max)} - \Delta T_{J1}$

Where $T_{R(Max)}$ is the reference temperature (either case or ambient)

ΔT_{J1} can be calculated using equation (3) in Note 2.

For example, to determine $T_{C(Max)}$ for the MDA3500 with the following capacitive load condiitons.

I_A = 20 A average with a peak of 60 A
I_B = 10 A average with a peak of 70 A

First calculate the peak to average ratio for I_A. $I_{(PK)}/I_{(AV)}$ = 60/10 = 6.0. (Note that the peak to average ratio is on a per diode basis and each diode provides 10 A average).

From Figure 5, for an average current of 20 A and an $I_{(PK)}/I_{(AV)}$ = 6.0 read $P_{DT(AV)}$ = 40 watts or 10 watts/diode. Thus $P_{D1} = P_{D3}$ = 10 watts.

Similarly, for a load current I_B of 10 A, diode #2 and diode #4 each see 5.0 A average resulting in an $I_{(PK)}/I_{(AV)}$ = 14.

Thus, the package power dissipation for 10 A is 20 watts or 5.0 watts/diode $\therefore P_{D2} = P_{D4}$ = 5.0 watts.

The maximum junction temperature occurs in diode #1 and #3. From equation (3) for diode #1 ΔT_{J1} = (7.5) (10), since coupling is negligible.

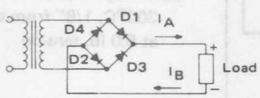
$\Delta T_{J1} \approx 75^oC$

Thus $T_{C(Max)} = 175 - 75 = 100^oC$

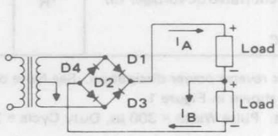
The total package dissipation in this example is:

$P_{DT(AV)} = 2 \times 10 + 2 \times 5.0$ = 30 watts, which must be considered when selecting a heat sink.

FIGURE 11– BASIC CIRCUIT USES FOR BRIDGE RECTIFIERS



Circuit A



Circuit B

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR500 MR501 MR502 MR504 MR506 MR508 MR510

Designers Data Sheet

MINIATURE SIZE, AXIAL LEAD MOUNTED STANDARD RECOVERY POWER RECTIFIERS

. . . designed for use in power supplies and other applications having need of a device with the following features:

- High Current to Small Size
- High Surge Current Capability
- Low Forward Voltage Drop
- Economical Plastic Package
- Available in Volume Quantities

STANDARD RECOVERY POWER RECTIFIERS

50-1000 VOLTS
3 AMPERE

CASE 267-02
PLASTIC

3

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

MAXIMUM RATINGS

Rating	Symbol	MR500	MR501	MR502	MR504	MR506	MR508	MR510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	850	1050	Volts
Average Rectified Forward Current (Single phase resistive load, $T_Z = 95°C$, PC Board Mounting) (1) (EIA Standard Conditions L = 1/32", $T_L = 85°C$)	I_O	← 3.0 → ← 8.0 →							Amp
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	← 100 → (one cycle)							Amp
Operating and Storage Junction Temperature Range (2)	T_J, T_{stg}	← -65 to +175 →							°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Recommended Printed Circuit Board Mounting, See Note 2).	$R_{\theta JA}$	28	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (3) (i_F = 9.4 Amp, T_J = 175°C) (i_F = 9.4 Amp, T_J = 25°C)	v_F	 – –	 0.9 1.04	 1.0 1.1	Volts
Reverse Current (rated dc voltage) (3) T_J = 25°C T_J = 100°C	I_R	 – –	 0.1 2.8	 5.0 25	μA

(1) Derate for reverse power dissipation. See Note on Page 2.
(2) Derate as shown in Figure 1.
(3) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2.0%.

MECHANICAL CHARACTERISTICS

Case: Transfer Molded Plastic
Finish: External Leads are Plated, Leads are readily Solderable
Polarity: Indicated by Cathode Band
Weight: 1.1 Grams (Approximately)
Maximum Lead Temperature for Soldering Purposes:
300°C, 1/8" from case for 10 s at 5.0 lb. tension

NOTE 1: DETERMINING MAXIMUM RATINGS

Reverse power dissipation and the possibility of thermal runaway must be considered when operating this rectifier at reverse voltages above 200 volts. Proper derating may be accomplished by use of equation (1):

$$T_{A(max)} = T_{J(max)} - R_{\theta JA}P_{F(AV)} - R_{\theta JA}P_{R(AV)} \quad (1)$$

where

$T_{A(max)}$ = Maximum allowable ambient temperature

$T_{J(max)}$ = Maximum allowable junction temperature (175^oC or the temperature at which thermal runaway occurs, whichever is lowest.)

$P_{F(AV)}$ = Average forward power dissipation

$P_{R(AV)}$ = Average reverse power dissipation

$R_{\theta JA}$ = Junction-to-ambient thermal resistance

Figure 1 permits easier use of equation (1) by taking reverse power dissipation and thermal runaway into consideration. The figure solves for a reference temperature as determined by equation (2):

$$T_R = T_{J(max)} - R_{\theta JA}P_{R(AV)} \quad (2)$$

Substituting equation (2) into equation (1) yields:

$$T_{A(max)} = T_R - R_{\theta JA}P_{F(AV)} \quad (3)$$

Inspection of equations (2) and (3) reveals that T_R is the ambient temperature at which thermal runaway occurs or where $T_J = 175^oC$, when forward power is zero. The transition from one boundary condition to the other is evident on the curves of Figure 1 as a difference in the rate of change of the slope in the vicinity of 165^oC. The data of Figure 1 is based upon dc conditions. For use in common rectifier circuits, Table 1 indicates suggested factors for an equivalent dc voltage to use for conservative design; i.e.:

$$V_{R(equiv)} = V_{in(PK)} \times F \quad (4)$$

The Factor F is derived by considering the properties of the various rectifier circuits and the rectifiers reverse characteristics.

Example: Find $T_{A(max)}$ for MR510 operated in a 400 Volt dc supply using a full wave center-tapped circuit with capacitive filter such that I_{DC} = 6.0 A, ($I_{F(AV)}$ = 3.0 A), $I_{(PK)}/I_{(AV)}$ = 10, Input Voltage = 283 V(rms) (line to center tap), $R_{\theta JA} = 28^oC/W$.

Step 1: Find $V_{R(equiv)}$. Read F = 1.11 from Table 1 ∴ $V_{R(equiv)}$ = 1.41)(283)(1.11) = 444 V

Step 2: Find T_R from Figure 1. Read $T_R = 167^oC$ @ V_R = 444 V & $R_{\theta JA} = 28^oC/W$.

Step 3: Find $P_{F(AV)}$ from Figure 8. Read $P_{F(AV)}$ = 4 W @ $\frac{I_{PK}}{I_{AV}}$ = 10 & $I_{F(AV)}$ = 3.0 A

Step 4: Find $T_{A(max)}$ from equation (3). $T_{A(max)}$ = 167-(28)(4) = 55^oC.

TABLE I – VALUES FOR FACTOR F

Circuit	Half Wave		Full Wave, Bridge		Full Wave Center-Tapped*†	
Load	Resistive	Capacitive*	Resistive	Capacitive	Resistive	Capacitive
Sine Wave	0.45	1.11	0.45	0.55	0.90	1.11
Square Wave	0.61	1.22	0.61	0.61	1.22	1.22

*Note that $V_{R(PK)} \approx 2\ V_{in(PK)}$ †Use line to center tap voltage for V_{in}.

FIGURE 1 – MAXIMUM REFERENCE TEMPERATURE

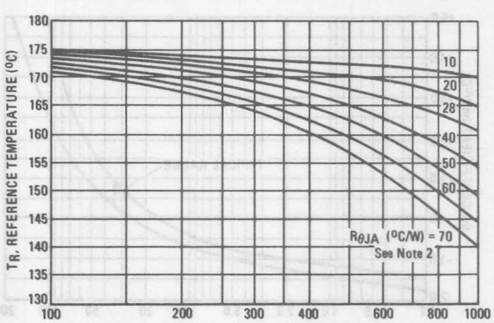
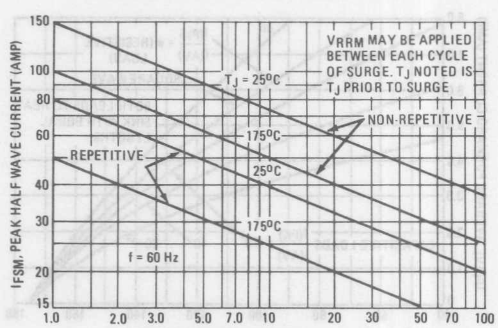


FIGURE 2 – MAXIMUM SURGE CAPABILITY



CURRENT DERATING
(Reverse Power Loss Neglected)

FIGURE 3 – PC BOARD MOUNTING

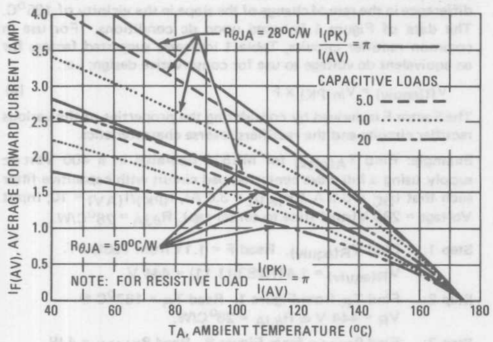


FIGURE 4 – SEVERAL LEAD LENGTHS

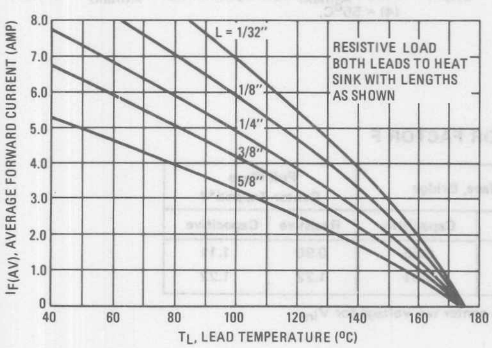


FIGURE 5 – 1/8" LEAD LENGTH

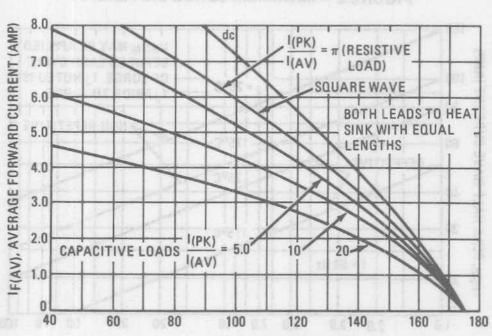


FIGURE 6 – MAXIMUM FORWARD VOLTAGE

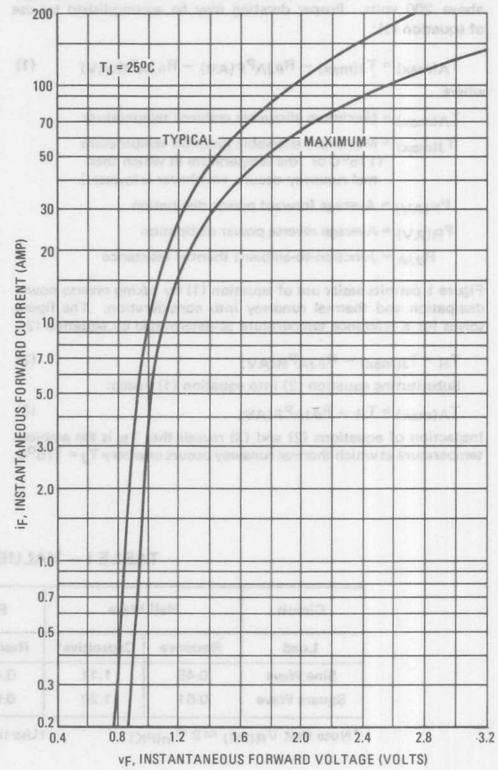


FIGURE 7 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

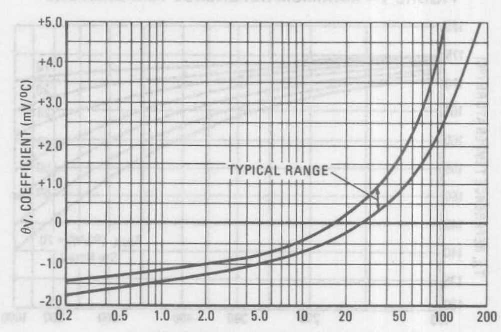


FIGURE 8 – FORWARD POWER DISSIPATION

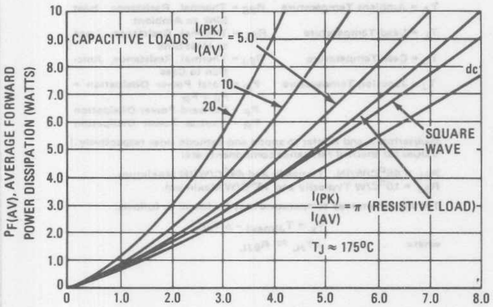
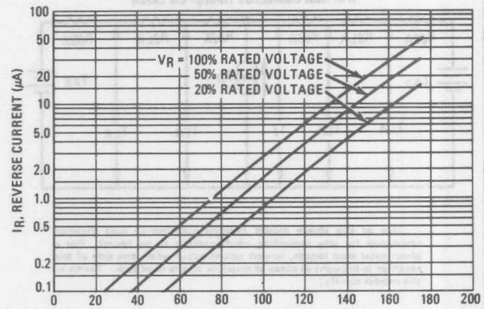


FIGURE 9 – TYPICAL REVERSE CURRENT



THERMAL CHARACTERISTICS

FIGURE 10 – THERMAL RESPONSE

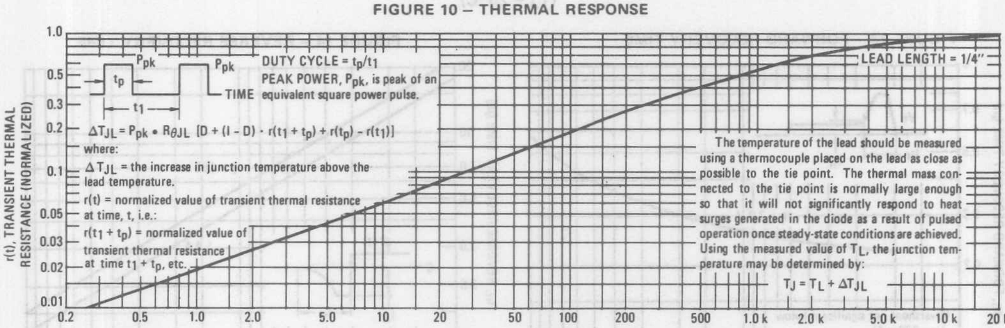
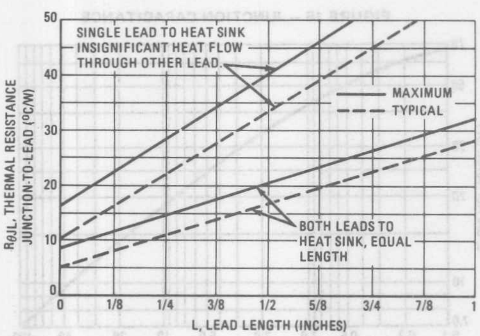


FIGURE 11 – STEADY-STATE THERMAL RESISTANCE



NOTE 2 – AMBIENT MOUNTING DATA

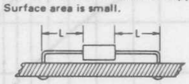
Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3			28		°C/W

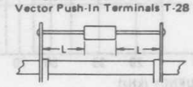
MOUNTING METHOD 1

P.C. Board Where Available Copper Surface area is small.



MOUNTING METHOD 2

Vector Push-In Terminals T-28



MOUNTING METHOD 3

P.C. Board with 1-1/2″ x 1-1/2″ Copper Surface

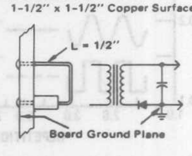
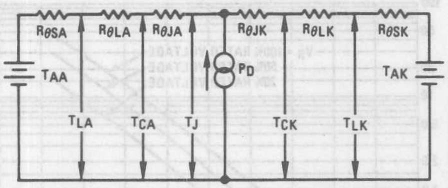


FIGURE 12 – APPROXIMATE THERMAL CIRCUIT MODEL

THERMAL CIRCUIT MODEL
(For Heat Conduction Through the Leads)



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature
T_L = Lead Temperature
T_C = Case Temperature
T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Total Power Dissipation = $P_F + P_R$
P_F = Forward Power Dissipation
P_R = Reverse Power Dissipation

(Subscripts A and K refer to anode and cathode sides respectively.) Values for thermal resistance components are:

$R_{\theta L}$ = 46°C/W/IN. Typically and 48°C/W/IN Maximum.
$R_{\theta J}$ = 10°C/W Typically and 16°C/W Maximum.

The maximum lead temperature may be found as follows:

$$T_L = T_{J(max)} - \Delta T_{JL}$$

where $\Delta T_{JL} \approx R_{\theta JL}$

TYPICAL DYNAMIC CHARACTERISTICS

($T_J = 25^oC$)

FIGURE 13 – FORWARD RECOVERY TIME

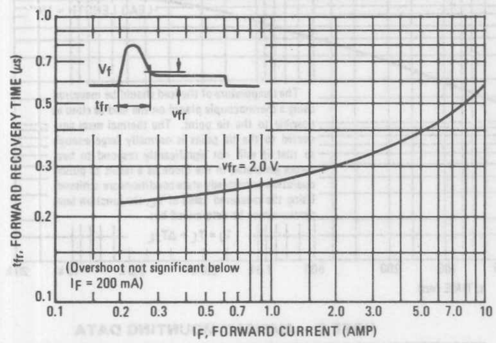


FIGURE 14 – REVERSE RECOVERY TIME

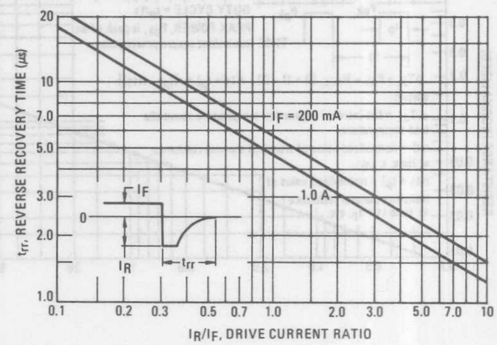


FIGURE 15 – RECTIFICATION WAVEFORM EFFICIENCY

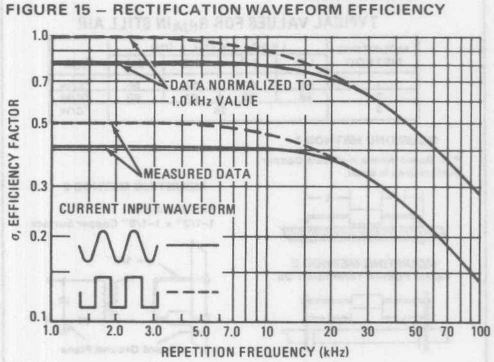
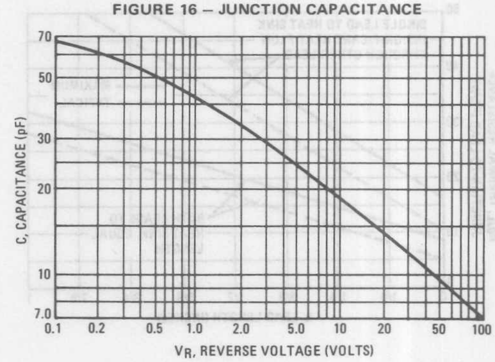
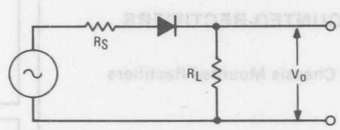


FIGURE 16 – JUNCTION CAPACITANCE



RECTIFIER EFFICIENCY NOTE

FIGURE 17 – SINGLE-PHASE HALF-WAVE RECTIFIER CIRCUIT



The rectification efficiency factor σ shown in Figure 15 was calculated using the formula:

$$\sigma = \frac{P_{(dc)}}{P_{(rms)}} = \frac{\dfrac{V^2{}_o(dc)}{R_L}}{\dfrac{V^2{}_o(rms)}{R_L}} \cdot 100\% = \frac{V^2{}_o(dc)}{V^2{}_o(ac) + V^2{}_o(dc)} \cdot 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assumed lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{(sine)} = \frac{\dfrac{V^2{}_m}{\pi^2 R_L}}{\dfrac{V^2{}_m}{4R_L}} \cdot 100\% = \frac{4}{\pi^2} \cdot 100\% = 40.6\% \quad (2)$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

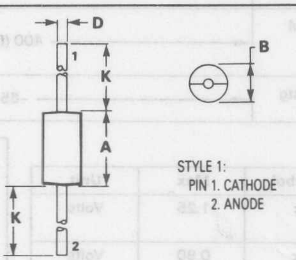
$$\sigma_{(square)} = \frac{\dfrac{V^2{}_m}{2R_L}}{\dfrac{V^2{}_m}{R_L}} \cdot 100\% = 50\% \quad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 14) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 15.

It should be emphasized that Figure 15 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_o with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for the figure.

OUTLINE DIMENSIONS



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR750
MR751 MR752
MR754 MR756

Designers Data Sheet

HIGH CURRENT LEAD MOUNTED RECTIFIERS

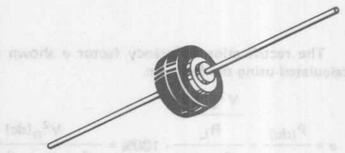
- Current Capacity Comparable To Chassis Mounted Rectifiers
- Very High Surge Capacity
- Insulated Case

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

HIGH CURRENT LEAD MOUNTED SILICON RECTIFIERS

50-600 VOLTS DIFFUSED JUNCTION



3

MAXIMUM RATINGS

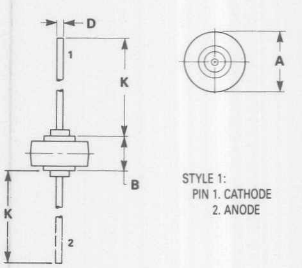
Characteristic	Symbol	MR750	MR751	MR752	MR754	MR756	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage (halfwave, single phase, 60 Hz peak)	V_{RSM}	60	120	240	480	720	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (single phase, resistive load, 60 Hz.) See Figures 5 and 6.	I_O	22 (T_L = 60°C, 1/8″ Lead Lengths) 6.0 (T_A = 60°C, P.C. Board mounting)					Amp
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	400 (for 1 cycle)					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175					°C

ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage Drop (i_F = 100 Amp, T_J = 25=C)	v_F	1.25	Volts
Maximum Forward Voltage Drop (I_F = 6.0 Amp, T_A = 25°C, 3/8″ leads)	V_F	0.90	Volts
Maximum Reverse Current (rated dc voltage) T_J = 25=C T_J = 100°C	I_R	0.25 1.0	mA

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 350°C 3/8″ from case for 10 seconds at 5.0 lbs. tension
FINISH: All external surfaces are corrosion-resistant, leads are readily solderable
POLARITY: Indicated by diode symbol
WEIGHT: 2.5 Grams (approx.)



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTE:
1. CATHODE SYMBOL ON PKG

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.43	8.69	0.332	0.342
B	5.94	6.25	0.234	0.246
D	1.27	1.35	0.050	0.053
K	25.15	25.65	0.990	1.010

CASE 194-04 PLASTIC

FIGURE 1 — FORWARD VOLTAGE

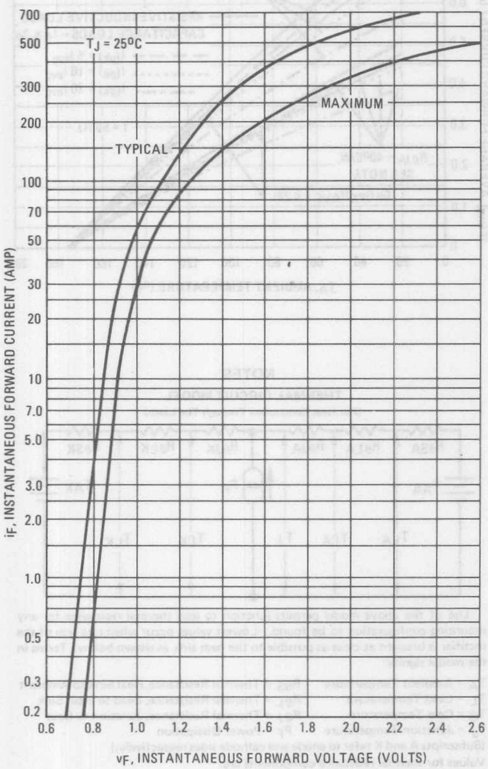


FIGURE 2 — MAXIMUM SURGE CAPABILITY

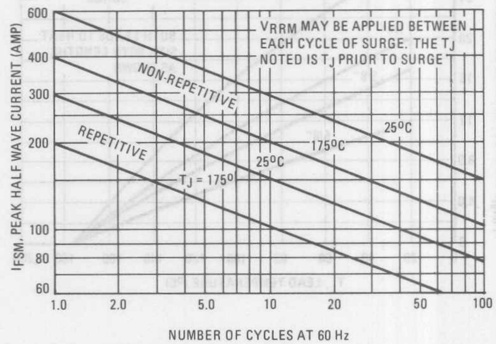


FIGURE 3 — FORWARD VOLTAGE TEMPERATURE COEFFICIENT

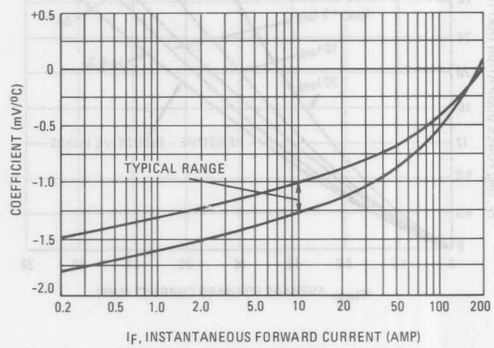


FIGURE 4 — TYPICAL TRANSIENT THERMAL RESISTANCE

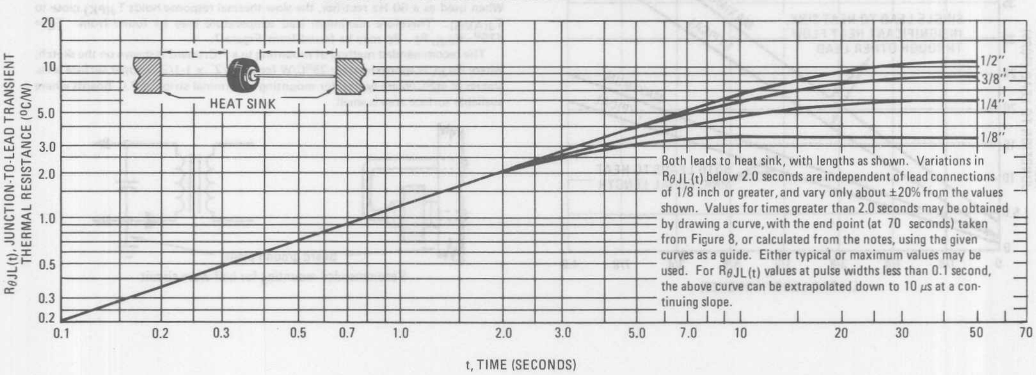


FIGURE 5 – MAXIMUM CURRENT RATINGS

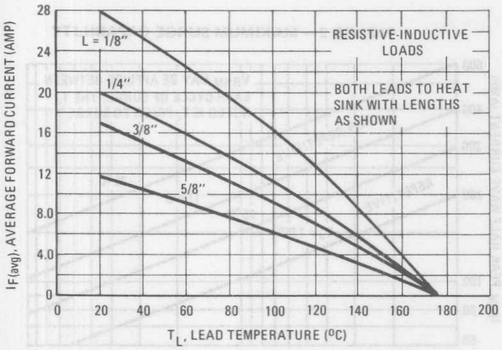


FIGURE 6 – MAXIMUM CURRENT RATINGS

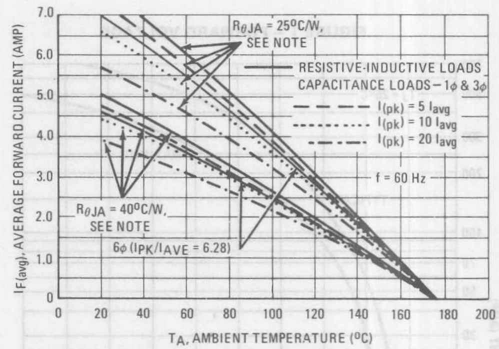


FIGURE 7 – POWER DISSIPATION

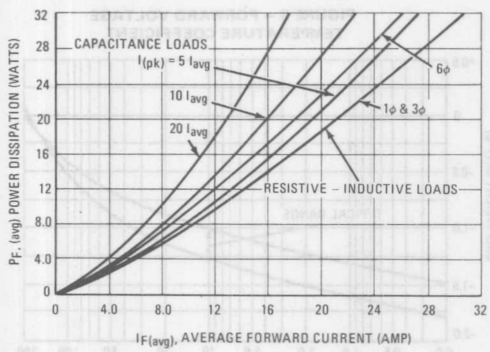
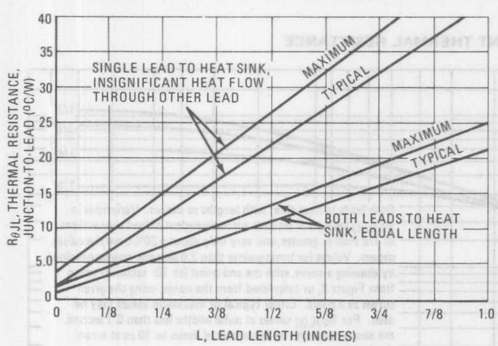


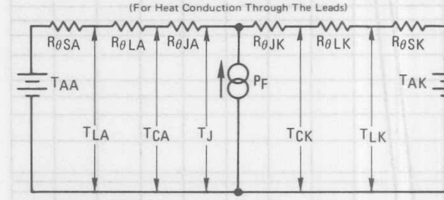
FIGURE 8 – STEADY STATE THERMAL RESISTANCE



NOTES

THERMAL CIRCUIT MODEL

(For Heat Conduction Through The Leads)



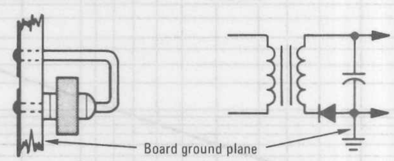
Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. Lowest values occur when one side of the rectifier is brought as close as possible to the heat sink as shown below. Terms in the model signify:

T_A = Ambient Temperature — $R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
T_L = Lead Temperature — $R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
T_C = Case Temperature — $R_{\theta J}$ = Thermal Resistance, Junction to Case
T_J = Junction Temperature — P_F = Power Dissipation

(Subscripts A and K refer to anode and cathode sides respectively.)
Values for thermal resistance components are:
$R_{\theta L}$ = 40°C/W/IN. Typically and 44°C/W/IN Maximum
$R_{\theta J}$ = 2°C/W Typically and 4°C/W Maximum

Since $R_{\theta J}$ is so low, measurements of the case temperature, T_C, will be approximately equal to junction temperature in practical lead mounted applications. When used as a 60 Hz rectifier, the slow thermal response holds $T_{J(PK)}$ close to $T_{J(AVG)}$. Therefore maximum lead temperature may be found from: $T_L = 175° - R_{\theta JL}\ P_F$. P_F may be found from Figure 7.

The recommended method of mounting to a P.C. board is shown on the sketch, where $R_{\theta JA}$ is approximately 25°C/W for a 1-1/2″ x 1-1/2″ copper surface area. Values of 40°C/W are typical for mounting to terminal strips or P.C. boards where available surface area is small.



Recommended mounting for half wave circuit

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 9 – RECTIFICATION EFFICIENCY

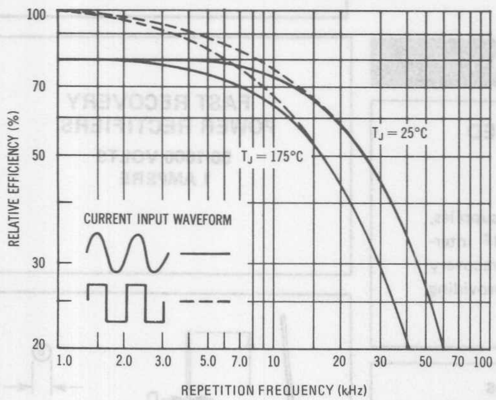


FIGURE 10 – REVERSE RECOVERY TIME

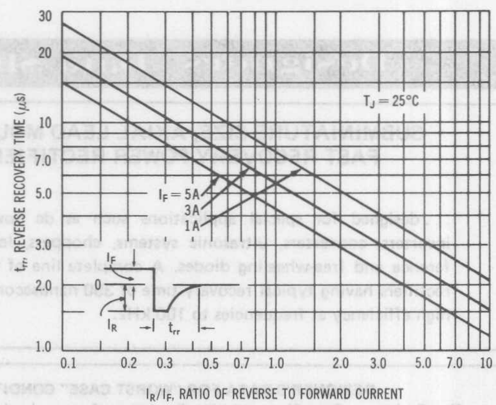


FIGURE 11 – JUNCTION CAPACITANCE

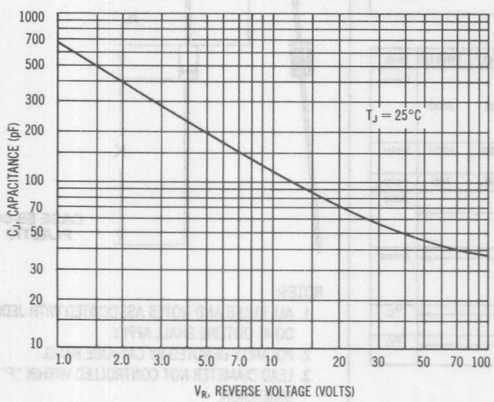


FIGURE 12 – FORWARD RECOVERY TIME

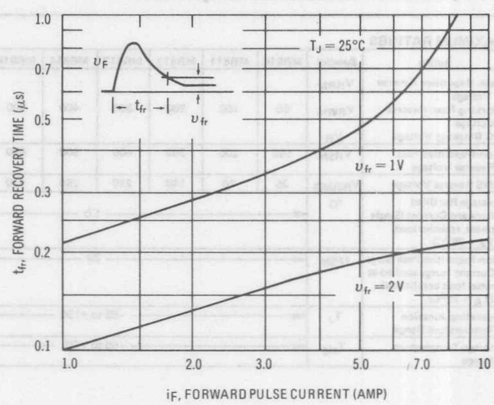
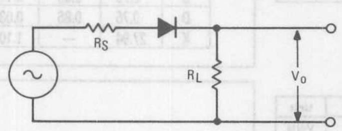


FIGURE 13 – SINGLE-PHASE HALF-WAVE RECTIFIER CIRCUIT



The rectification efficiency factor σ shown in Figure 9 was calculated using the formula:

$$\sigma = \frac{P_{(dc)}}{P_{(rms)}} = \frac{\frac{V^2{}_o(dc)}{R_L}}{\frac{V^2{}_o(rms)}{R_L}} \cdot 100\% = \frac{V^2{}_o(dc)}{V^2{}_o(ac) + V^2{}_o(dc)} \cdot 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assumed lossless, the maximum theoretical efficiency factor becomes:

$$\sigma(\text{sine}) = \frac{\frac{V^2{}_m}{\pi^2 R_L}}{\frac{V^2{}_m}{4R_L}} \cdot 100\% = \frac{4}{\pi^2} \cdot 100\% = 40.6\% \quad (2)$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma(\text{square}) = \frac{\frac{V^2{}_m}{2R_L}}{\frac{V^2{}_m}{R_L}} \cdot 100\% = 50\% \quad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 10) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 9.

It should be emphasized that Figure 9 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_o with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 9.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR810 thru MR814
MR816 thru MR818

Designers Data Sheet

SUBMINIATURE SIZE, AXIAL LEAD MOUNTED FAST RECOVERY POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free-wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 350 nanoseconds providing high efficiency at frequencies to 100 kHz.

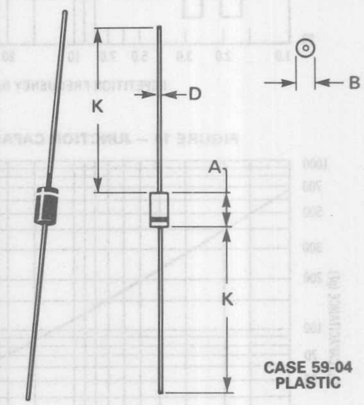
FAST RECOVERY POWER RECTIFIERS

50-1000 VOLTS
1 AMPERE

3

DESIGNER'S DATA FOR "WORST CASE" CONDITIONS

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing device characteristic boundaries — are given to facilitate "worst case" design.



CASE 59-04
PLASTIC

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

MAXIMUM RATINGS

Rating	Symbol	MR810	MR811	MR812	MR813	MR814	MR816	MR817	MR818	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	100	200	300	400	500	800	1000	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	420	560	700	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_A = 75^oC$)	I_O	←				1.0			→	Amp
Non-Repetitive Peak Surge Current (surge applied at rated load conditions) ($T_A = 75^oC$)	I_{FSM}	←				30			→	Amps
Operating Junction Temperature Range	T_J	←				-65 to +150			→	^oC
Storage Temperature Range	T_{stg}	←				-65 to +175			→	^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Typical Primted Circuit Board Mounting)	$R_{\theta JA}$	65	$^oC/W$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (i_F = 3.14 Amp, $T_J = 150^oC$)	v_F	–	1.1	1.2	Volts
Forward Voltage (I_F = 1.0 Amp, $T_A = 25^oC$)	V_F	–	1.0	1.2	Volts
Reverse Current (rated dc voltage) $T_A = 25^oC$ $T_A = 100^oC$	I_R	– –	1.0 50	10 100	μA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time (I_F = 1.0 Amp to V_R = 30 Vdc) (Figure 21) (I_F = 20 mA, I_R = 2.0 mA, Tektronix S-Plug-In) (Figure 22)	t_{rr}	– –	350 1.5	750 3.0	ns μs
Reverse Recovery Current (I_F = 1.0 Amp to V_R = 30 Vdc) (Figure 21)	$I_{RM(REC)}$		–	3.0	Amp

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic

FINISH: External leads are plated and are readily solderable

POLARITY: Cathode indicated by Polarity band

WEIGHT: 0.4 Grams (Approximately)

FIGURE 1 – FORWARD VOLTAGE

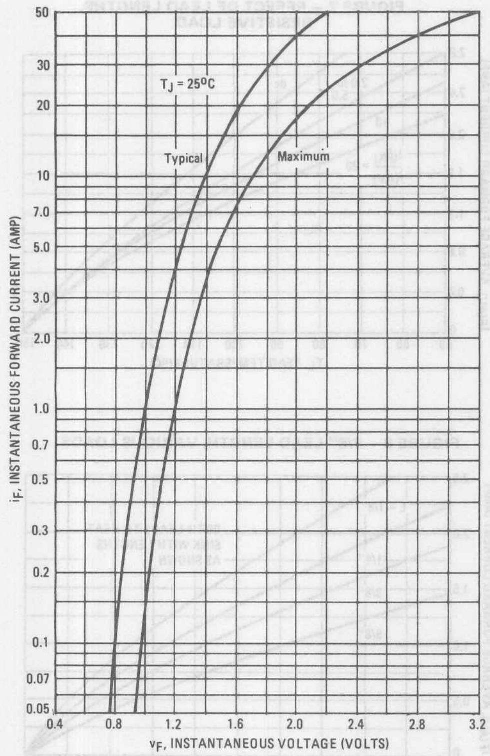


FIGURE 2 – MAXIMUM SURGE CAPABILITY

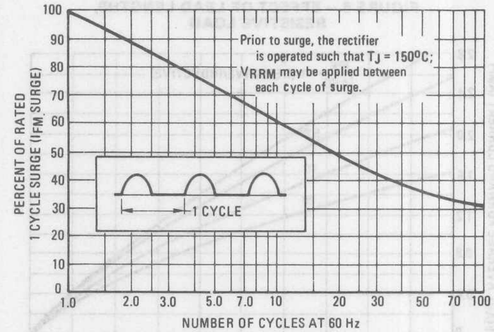


FIGURE 3 – TEMPERATURE COEFFICIENT

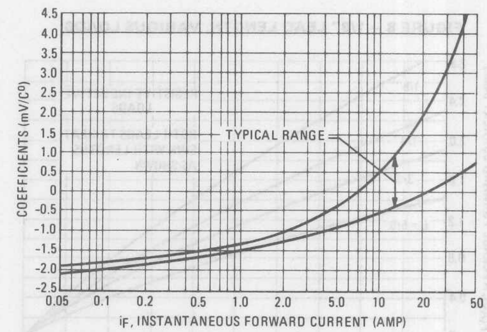


FIGURE 4 – FORWARD POWER DISSIPATION

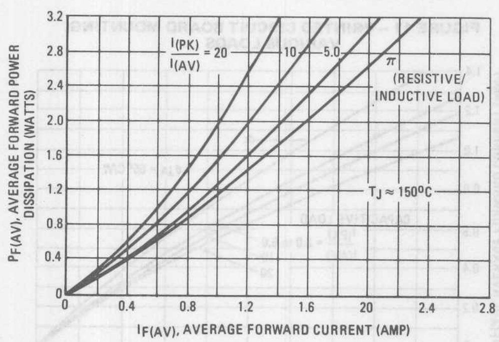
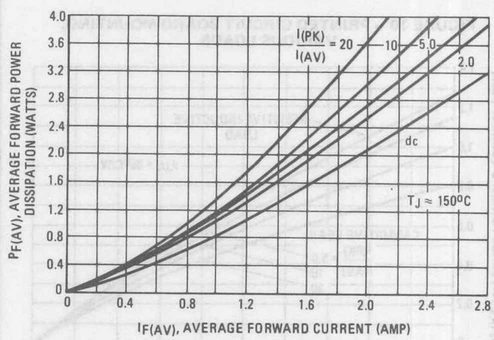


FIGURE 5 – FORWARD POWER DISSIPATION



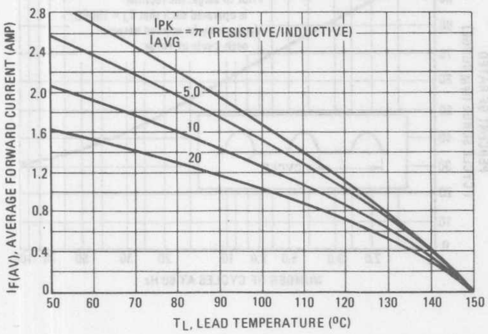
3

3

MAXIMUM CURRENT RATINGS
(SEE NOTES 1 and 2)

SINE WAVE INPUT

FIGURE 6 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD



SQUARE WAVE INPUT

FIGURE 7 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

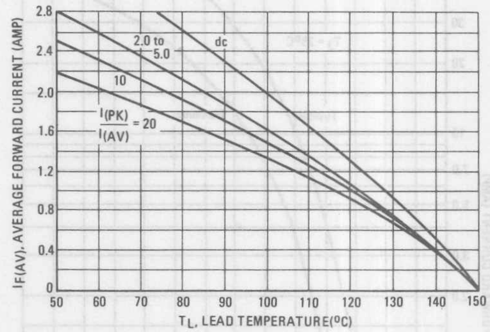


FIGURE 8 – 1/8″ LEAD LENGTH, VARIOUS LOADS

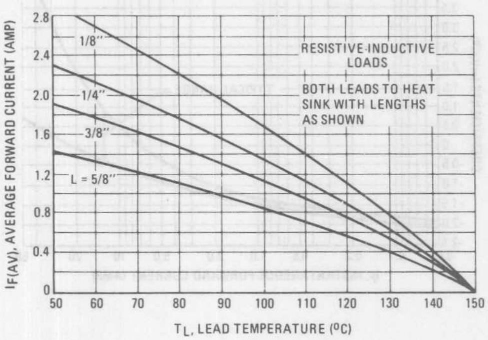


FIGURE 9 – 1/8″ LEAD LENGTH, VARIOUS LOADS

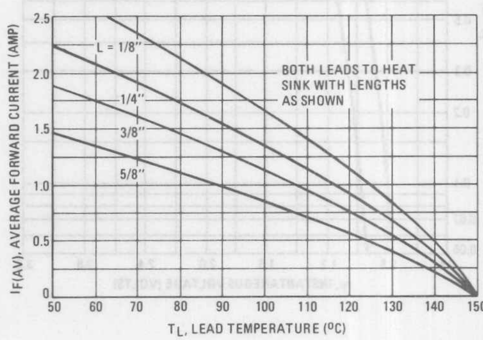


FIGURE 10 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

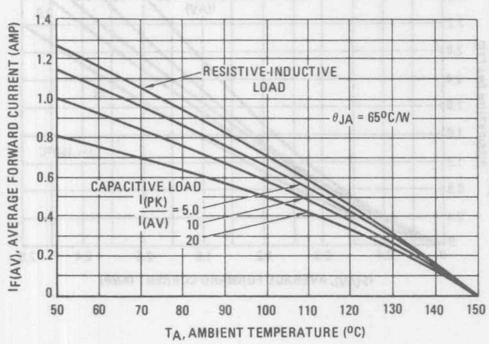


FIGURE 11 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

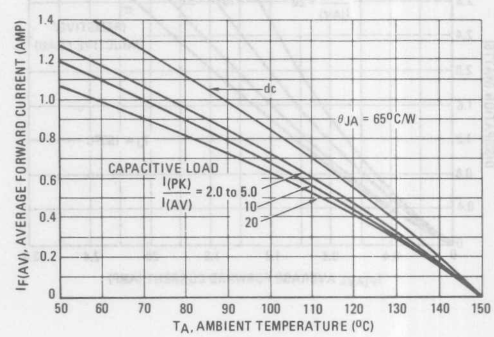


FIGURE 12 – THERMAL RESPONSE

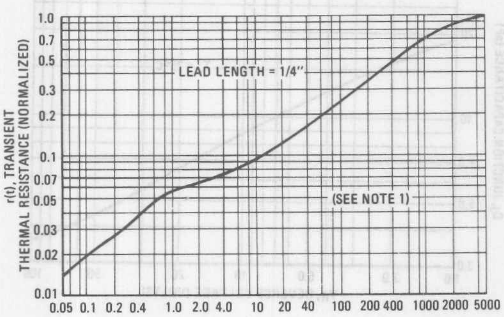
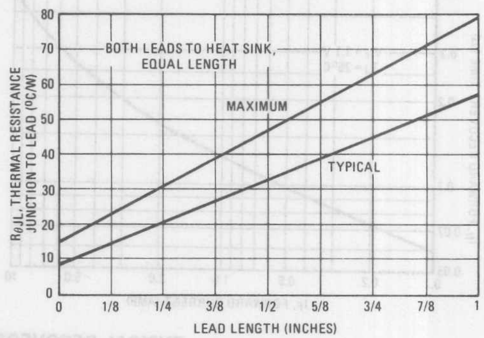
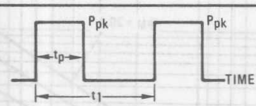


FIGURE 13 – THERMAL RESISTANCE



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} \left[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)\right]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 12, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

NOTE 2

Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR θ_{JA} IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN) 1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	65	72	82	92	°C/W
2	74	81	91	101	°C/W
3	40				°C/W

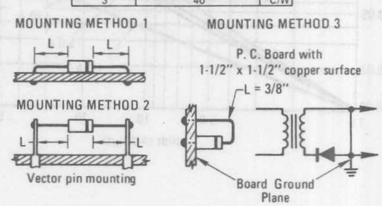
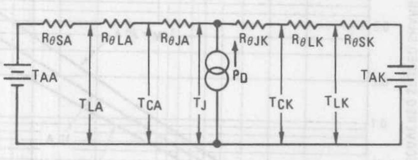


FIGURE 14 – THERMAL CIRCUIT MODEL



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature
T_L = Lead Temperature
T_C = Case Temperature
T_J = Junction Temperature
$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
$R_{\theta J}$ = Thermal Resistance, Junction to Case
P_D = Power Dissipation

(Subscripts A and K refer to anode and cathode sides respectively.)

Values for thermal resistance components are:

$R_{\theta L}$ = 112°C/W/IN. Typically and 128°C/W/IN Maximum

$R_{\theta J}$ = 18°C/W Typically and 30°C/W Maximum

The maximum lead temperature may be calculated as follows:

$$T_L = 150^{\circ} - \Delta T_{JL}$$

ΔT_{JL} can be calculated as shown in NOTE 1 or it may be approximated as follows:

$\Delta T_{JL} \approx R_{\theta JL} \bullet P_F$; P_F may be formulated for sine-wave operation from Figure 3 or from Figure 4 for square-wave operation.

TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 15 – FORWARD RECOVERY TIME

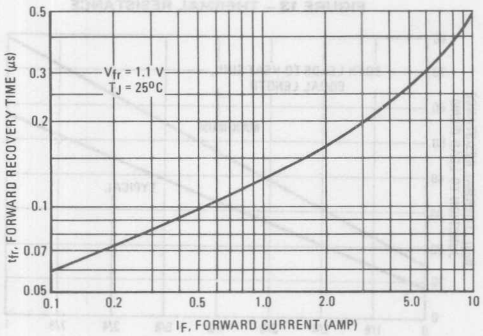
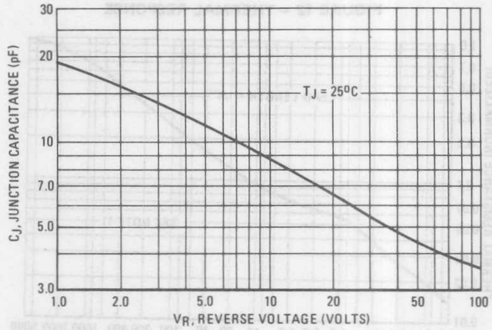


FIGURE 16 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA
(SEE NOTE 3)

FIGURE 17 – T_J = 25°C

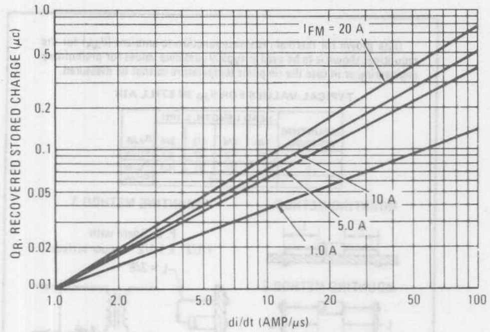


FIGURE 18 – T_J = 75°C

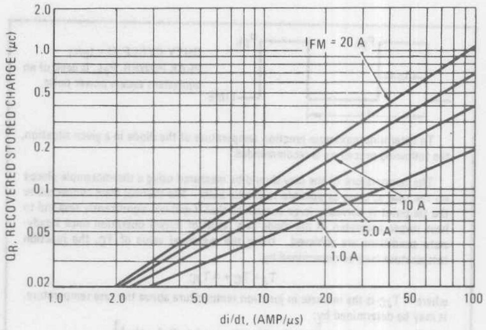


FIGURE 19 – T_J = 100°C

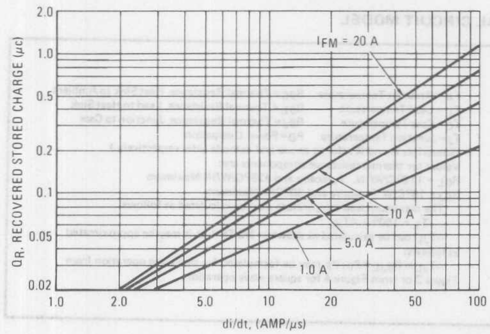


FIGURE 20 – T_J = 150°C

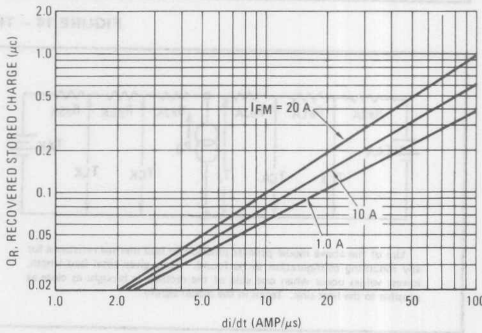
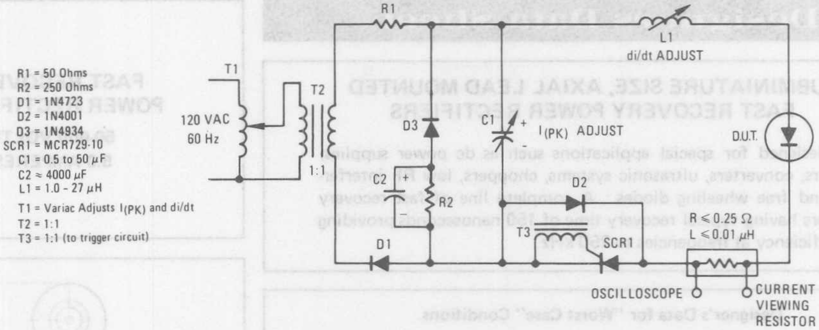


FIGURE 21 — JEDEC REVERSE RECOVERY CIRCUIT



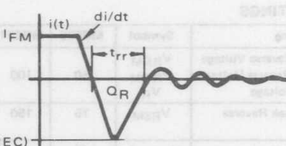
NOTE 3

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

FIGURE 22 — TYPICAL REVERSE LEAKAGE

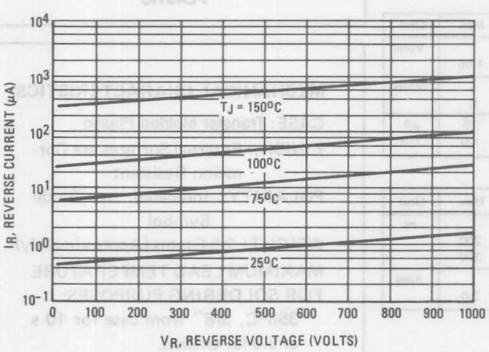
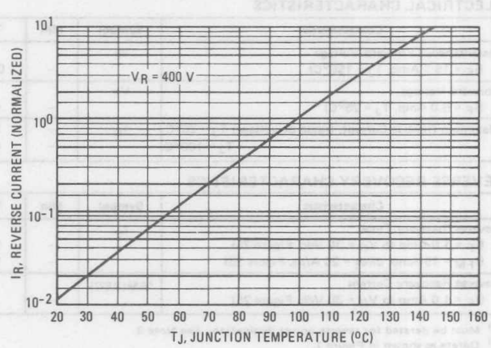


FIGURE 23 — TYPICAL REVERSE LEAKAGE



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR820
MR821 MR822
MR824 MR826

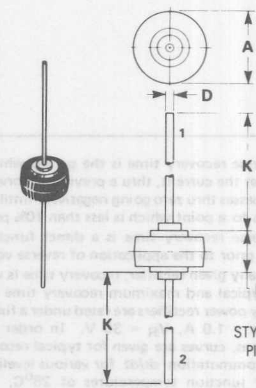
Designers Data Sheet

SUBMINIATURE SIZE, AXIAL LEAD MOUNTED FAST RECOVERY POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
5.0 AMPERES



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTE:
1. CATHODE SYMBOL ON PKG

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.43	8.69	0.332	0.342
B	5.94	6.25	0.234	0.246
D	1.27	1.35	0.050	0.053
K	25.15	25.65	0.990	1.010

CASE 194-04
PLASTIC

3

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves – representing boundaries on device characteristics – are given to facilitate "worst case" design.

MAXIMUM RATINGS

Rating	Symbol	MR820	MR821	MR822	MR824	MR826	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_A = 55^oC$) (1)	I_O	←		5.0		→	Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	←		300		→	Amp
Operating and Storage Junction Temperature Range (2)	T_J, T_{stg}	←		-65 to +175		→	^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Recommended Printed Circuit Board Mounting, See Note 6)	$R_{\theta JA}$	25	$^oC/W$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage ($i_F = 15.7$ Amp, $T_J = 150^oC$)	v_F	–	0.75	1.05	Volts
Forward Voltage ($I_F = 5.0$ Amp, $T_J = 25^oC$)	V_F	–	0.9	1.	Volts
Maximum Reverse Current, (rated dc voltage) $T_J = 25^oC$	I_R	–	5.0	25	μA
$T_J = 100^oC$		–	0.4	1.0	mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 25)	t_{rr}	–	150	200	ns
($I_{FM} = 15$ Amp, $di/dt = 25$ A/μs, Figure 26)		–	150	300	
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 25)	$I_{RM(REC)}$	–	–	2.0	Amp

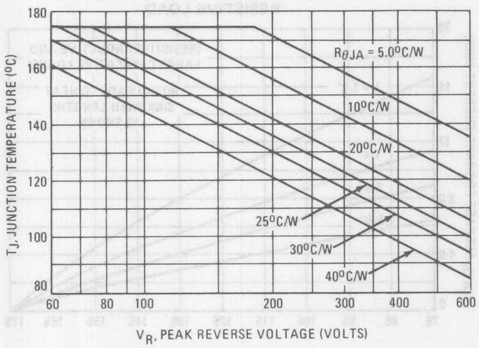
(1) Must be derated for reverse power dissipation. See Note 3
(2) Derate as shown in Figure 1.

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic
FINISH: External Surfaces are Corrosion Resistant
POLARITY: Indicated by Diode Symbol
WEIGHT: 2.5 Grams (Approximately)
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 350°C, 3/8" from case for 10 s at 5.0 lb. tension.

MAXIMUM CURRENT AND TEMPERATURE RATINGS

FIGURE 1 – MAXIMUM ALLOWABLE JUNCTION TEMPERATURE



NOTE 1

MAXIMUM JUNCTION TEMPERATURE DERATING

When operating this rectifier at junction temperatures over approximately 85°C, reverse power dissipation and the possibility of thermal runaway must be considered. The data of Figure 1 is based upon worst case reverse power and should be used to derate $T_{J(max)}$ from its maximum value of 175°C. See Note 3 for additional information on derating for reverse power dissipation.

When current ratings are computed from $T_{J(max)}$ and reverse power dissipation is also included, ratings vary with reverse voltage as shown on Figures 2 thru 5.

RESISTIVE LOAD RATINGS

PRINTED CIRCUIT BOARD MOUNTING – SEE NOTE 6

FIGURE 2 – SINE WAVE INPUT

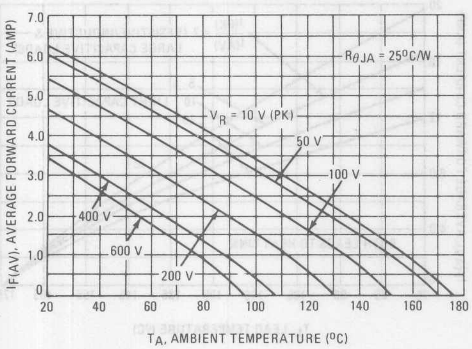


FIGURE 3 – SQUARE WAVE INPUT

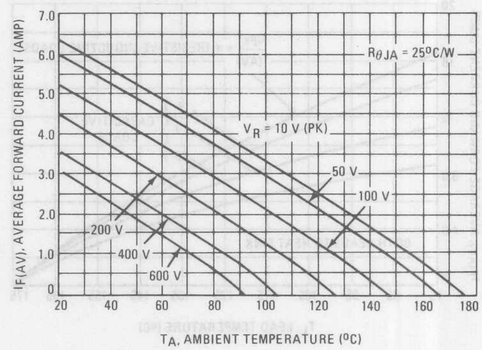


FIGURE 4 – SINE WAVE INPUT

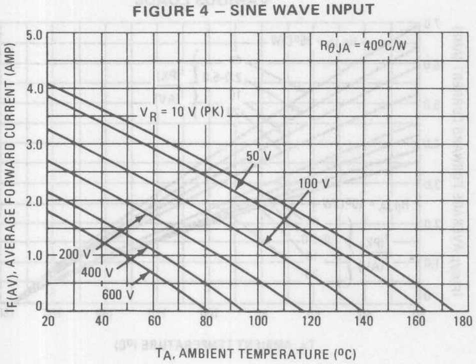
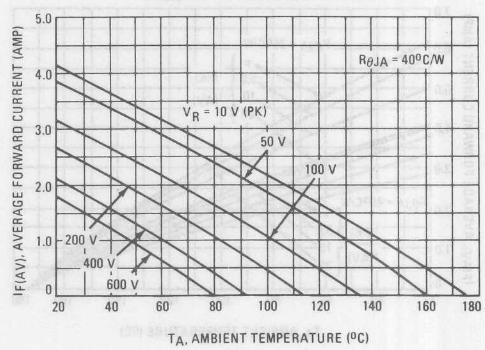


FIGURE 5 – SQUARE WAVE INPUT



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MAXIMUM CURRENT RATINGS

NOTE 2

Current derating data is based upon the thermal response data of Figure 29 and the forward power dissipation data of Figures 19 and 20. Since reverse power dissipation is not considered in Figures 6 thru 11, additional derating for reverse voltage and for junction to ambient thermal resistance must be applied. See Note 3.

SINE WAVE INPUT

FIGURE 6 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

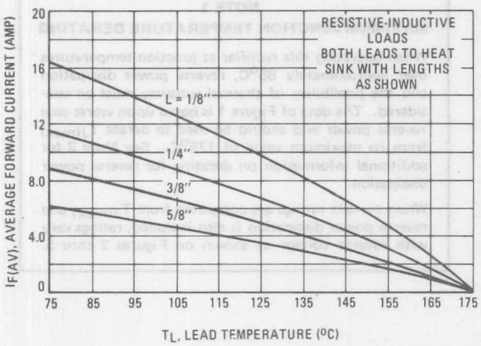


FIGURE 8 – 1/8" LEAD LENGTH, VARIOUS LOADS

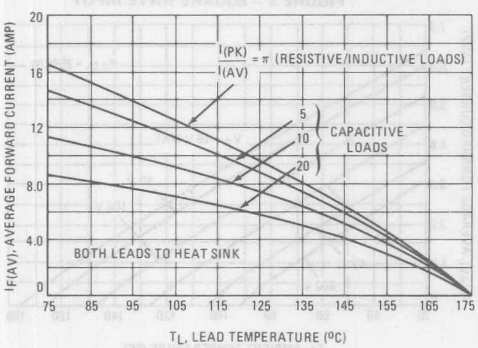
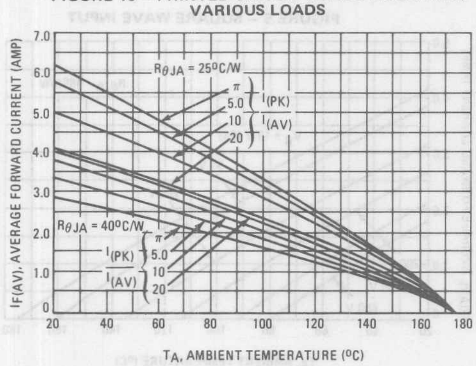


FIGURE 10 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS



SQUARE WAVE INPUT

FIGURE 7 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

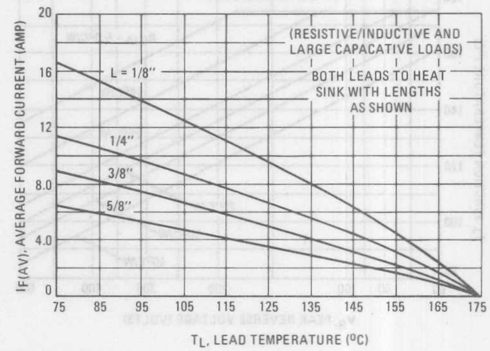


FIGURE 9 – 1/8" LEAD LENGTH, VARIOUS LOADS

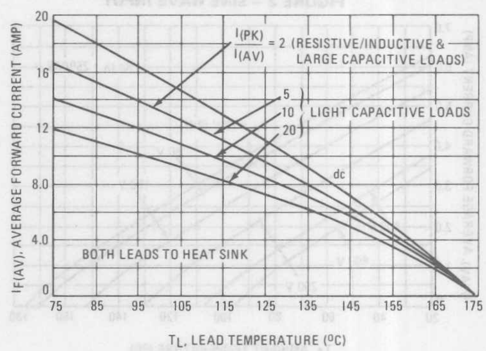
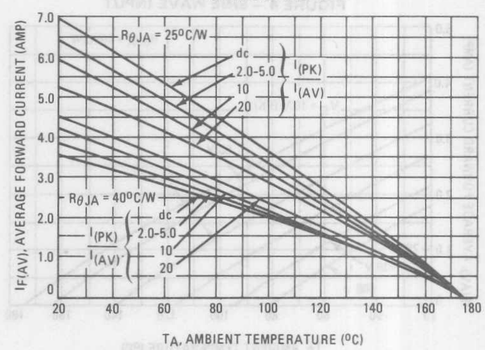


FIGURE 11 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS



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REVERSE POWER DISSIPATION AND CURRENT

NOTE 3
DERATING FOR REVERSE POWER DISSIPATION

In this rectifier, power loss due to reverse current is generally not negligible. For reliable circuit design, the maximum junction temperature must be limited to either 175°C or the temperature which results in thermal runaway. Proper derating may be accomplished by use of equation 1 or equation 2.

Equation 1 $T_A = T_1 - (175 - T_{J(max)}) - P_R R_{\theta JA}$

Where: T_1 = Maximum Allowable Ambient Temperature neglecting reverse power dissipation (from Figures 10 or 11)

$T_{J(max)}$ = Maximum Allowable Junction Temperature to prevent thermal runaway or 175°C, which ever is lower. (See Figure 1).

P_R = Reverse Power Dissipation (From Figure 12 or 13, adjusted for $T_{J(max)}$ as shown below)

$R_{\theta JA}$ = Thermal Resistance, Junction to Ambient.

When thermal resistance, junction to ambient, is over 20°C/W, the effect of thermal response is negligible. Satisfactory derating may be found by using:

Equation 2 $T_A = T_{J(max)} - (P_R + P_F) R_{\theta JA}$

P_F = Forward Power Dissipation (See Figures 19 & 20)

Other terms defined above.

The reverse power given on Figures 12 and 13 is calculated for $T_J = 150°C$. When T_J is lower, P_R will decrease; its value can be found by multiplying P_R by the normalized reverse current from Figure 14 at the temperature of interest.

The reverse power data is calculated for half wave rectification circuits. For full wave rectification using either a bridge or a center-tapped transformer, the data for resistive loads is equivalent when V_P is the line to line voltage across the rectifiers. For capacitive loads, it is recommended that the dc case on Figure 13 be used, regardless of input waveform, for bridge circuits. For capacitively loaded full wave center-tapped circuits, the 20:1 data of Figure 12 should be used for sine wave inputs and the capacitive load data of Figure 13 should be used for square wave inputs regardless of $I_{(pk)}/I_{(av)}$. For these two cases, V_P is the voltage across one leg of the transformer.

EXAMPLE:

Find Maximum Ambient Temperature for I_{AV} = 2 A, Capacitive Load of I_{PK}/I_{AV} = 20, Input Voltage = 120 V (rms) Sine Wave, $R_{\theta JA}$ = 25°C/W, Half Wave Circuit.

Solution 1:

Step 1: Find V_P; $V_P = \sqrt{2}\, V_{in}$ = 169 V, $V_{R(pk)}$ = 338 V
Step 2: Find $T_{J(max)}$ from Figure 1. Read $T_{J(max)}$ = 119°C.
Step 3: Find $P_{R(max)}$ from Figure 12. Read P_R = 770 mW @ 140°C
Step 4: Find I_R normalized from Figure 14. Read $I_{R(norm)}$ = 0.4
Step 5: Correct P_R to $T_{J(max)}$. $P_R = I_{R(norm)} \times P_R$ (Figure 12)
$P_R = 0.4 \times 770 = 310$ mW.
Step 6: Find P_F from Figure 19. Read P_F = 2.4 W.
Step 7: Compute T_A from $T_A = T_{J(max)} - (P_R + P_F) R_{\theta JA}$
$T_A = 119 - (0.31 + 2.4)(25)$
$T_A = 51°C$

Solution 2:

Steps 1 thru 5 are as above.
Step 6: Find $T_A = T_1$ from Figure 10. Read T_A = 115°C.
Step 7: Compute T_A from $T_A = T_1 - (175 - (T_{J(max)}) - P_R R_{\theta JA}$
$T_A = 115 - (175 - 119) - (0.31)(25)$
$T_A = 51°C$

At times, a discrepancy between methods will occur because thermal response is factored into Solution 2.

FIGURE 12 – SINE WAVE INPUT DISSIPATION

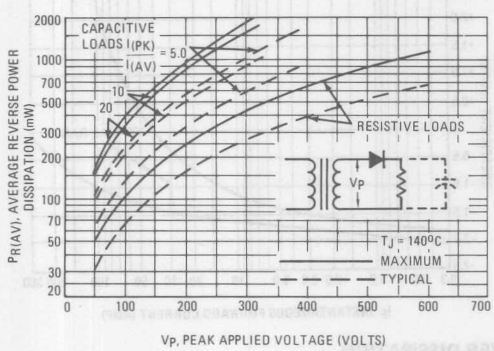


FIGURE 13 – SQUARE WAVE INPUT DISSIPATION

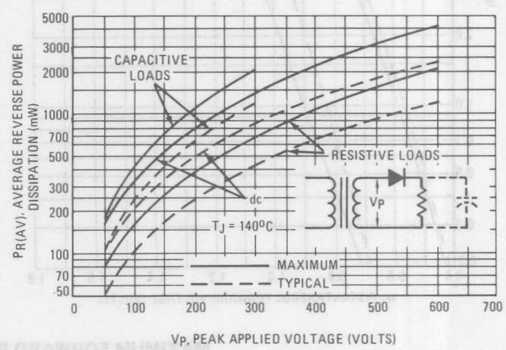


FIGURE 14 – NORMALIZED REVERSE CURRENT

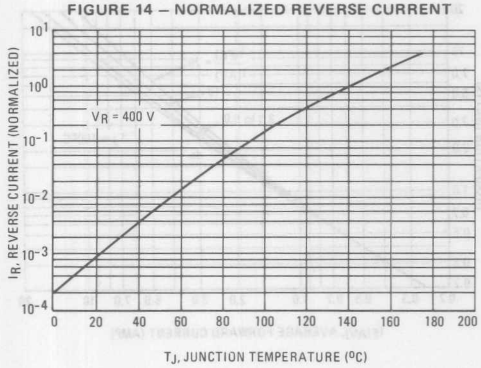
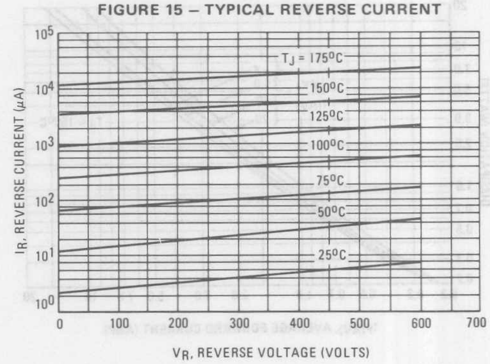


FIGURE 15 – TYPICAL REVERSE CURRENT



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STATIC CHARACTERISTICS

FIGURE 16 – FORWARD VOLTAGE

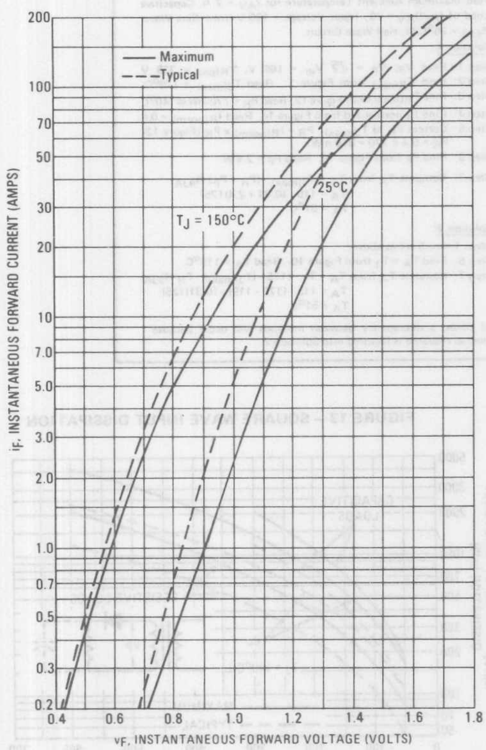


FIGURE 17 – MAXIMUM SURGE CAPABILITY

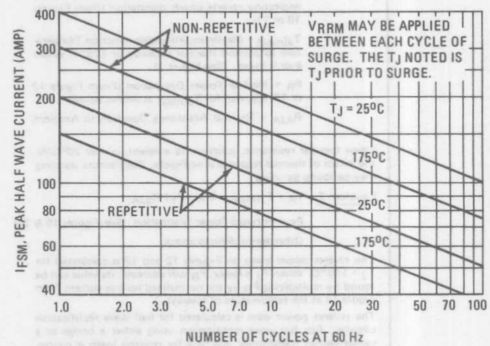
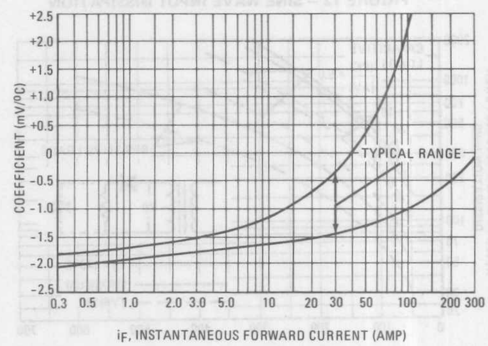


FIGURE 18 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT



MAXIMUM FORWARD POWER DISSIPATION

FIGURE 19 – SINE WAVE INPUT

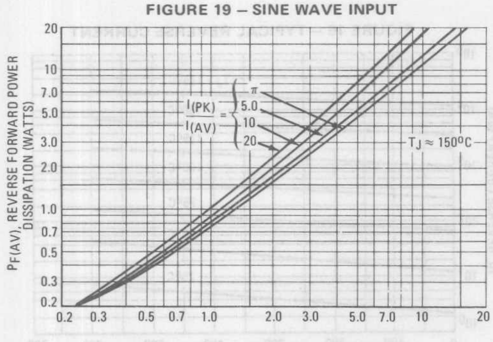
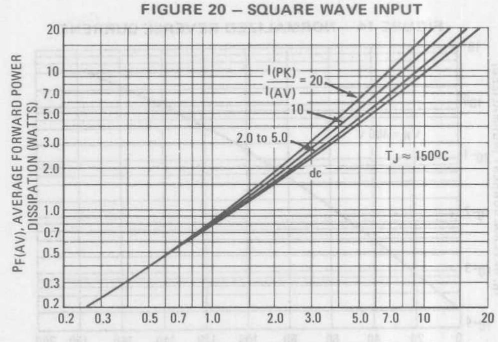


FIGURE 20 – SQUARE WAVE INPUT



TYPICAL RECOVERED STORED CHARGE DATA
(See Note 4)

FIGURE 21 — T_J = 25°C

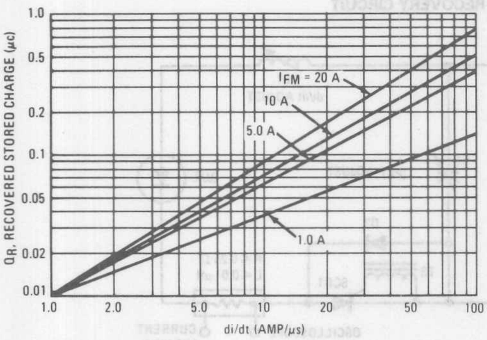


FIGURE 22 — T_J = 75°C

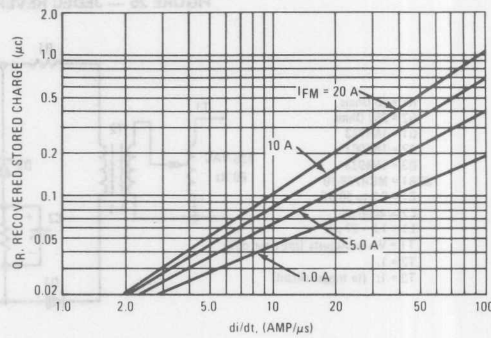


FIGURE 23 — T_J = 100°C

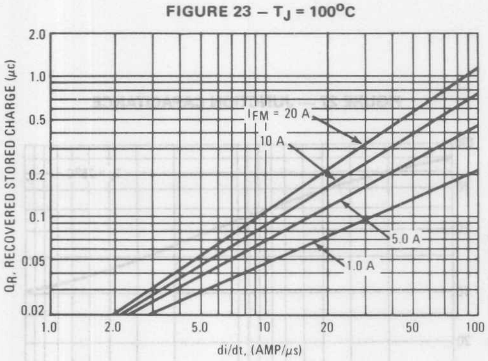
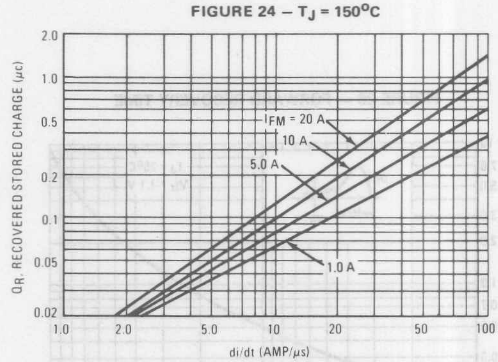


FIGURE 24 — T_J = 150°C



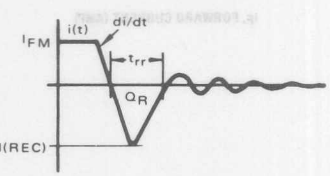
NOTE 4

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using $I_F \cong 1.0$ A, $V_R = 30$ V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

3

DYNAMIC CHARACTERISTICS

FIGURE 25 — JEDEC REVERSE RECOVERY CIRCUIT

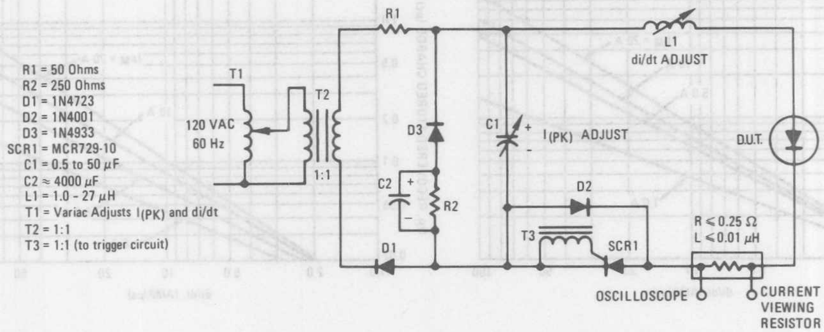


FIGURE 26 — FORWARD RECOVERY TIME

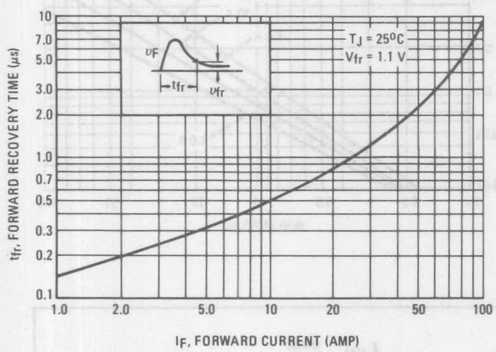
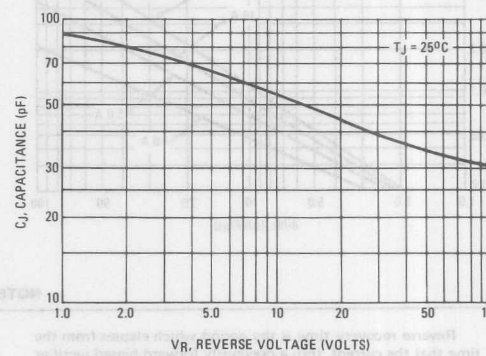
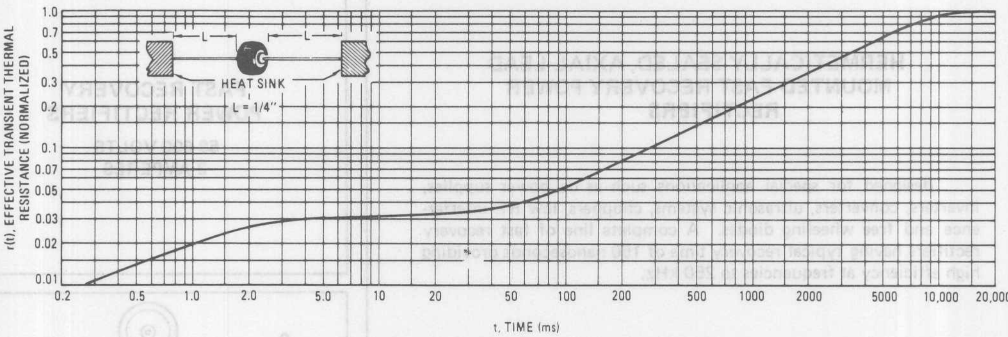


FIGURE 27 — JUNCTION CAPACITANCE



THERMAL CHARACTERISTICS

FIGURE 28 — THERMAL RESPONSE



NOTE 5

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the lead should be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

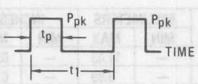
$$T_J = T_L + \Delta T_{JL}$$

where ΔT_{JL} is the increase in junction temperature above the lead temperature. It may be determined by:

$$\Delta T_{JL} = P_{pk} \cdot R_{\theta JL} \; [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

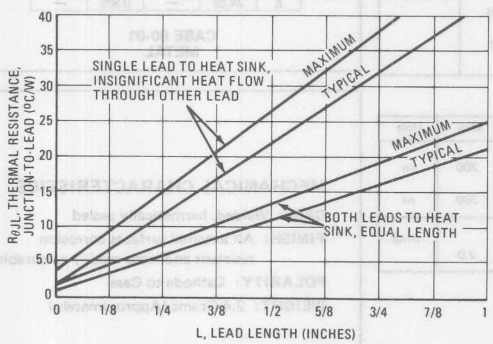
where r(t) = normalized value of transient thermal resistance at time t from Figure 29, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

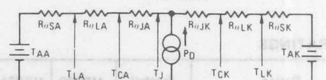


DUTY CYCLE = t_p/t_1
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

FIGURE 29 — STEADY-STATE THERMAL RESISTANCE



NOTE 6



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. Lowest values occur when one side of the rectifier is brought as close as possible to the heat sink as shown below. Terms in the model signify:

T_A = Ambient Temperature	$R_{\theta S}$ = Thermal Resistance, Heat sink to Ambient
T_L = Lead Temperature	$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
T_C = Case Temperature	$R_{\theta J}$ = Thermal Resistance, Junction to Case
T_J = Junction Temperature	P_D = Power Dissipation = $P_F + P_R$
	P_F = Forward Power Dissipation
	P_R = Reverse Power Dissipation

(Subscripts A and K refer to anode and cathode sides respectively) Values for thermal resistance components are:

$R_{\theta L}$ = 40°C/W/IN. Typically and 44°C/W/IN Maximum.
$R_{\theta J}$ = 2°C/W Typically and 4°C/W Maximum.

Since $R_{\theta J}$ is so low, measurements of the case temperature, T_C, will be approximately equal to junction temperature in practical lead mounted applications. When used as a 60 Hz rectifier, the slow thermal response holds $T_{J(PK)}$ close to $T_{J(AV)}$. Therefore maximum lead temperature may be found as follows:

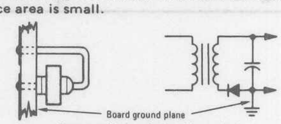
$$T_L = T_{J(max)} - \Delta T_{JL}$$

where

ΔT_{JL} can be approximated as follows:

$\Delta T_{JL} \approx R_{\theta JL} \cdot P_D$; P_D is the sum of forward and reverse power dissipation shown in Figures 12 & 19 for sine wave operation and Figures 13 & 20 for square wave operation.

The recommended method of mounting to a P.C. board is shown on the sketch, where $R_{\theta JA}$ is approximately 25°C/W for a 1-1/2" x 1-1/2" copper surface area. Values of 40°C/W are typical for mounting to terminal strips or P.C. boards where available surface area is small.



Recommended mounting for half wave circuit

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

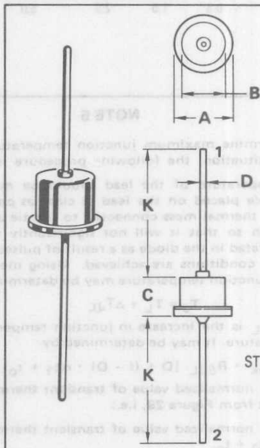
MR830 MR831 MR832 MR834 MR836

HERMETICALLY SEALED, AXIAL LEAD MOUNTED FAST RECOVERY POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
3 AMPERES



STYLE 1:
PIN 1. CATHODE
2. ANODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	11.43	—	0.450
B	—	8.89	—	0.350
C	—	7.62	—	0.300
D	1.17	1.42	0.046	0.056
K	24.89	—	0.980	—

CASE 60-01
METAL

MAXIMUM RATINGS

Rating	Symbol	MR830	MR831	MR832	MR834	MR836	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100^oC$)	I_O	← 3.0 →					Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	← 100 →					Amps
Operating Junction Temperature Range	T_J	← −65 to +150 →					^oC
Storage Temperature Range	T_{stg}	← −65 to +175 →					^oC

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Forward Voltage ($I_F = 3.0$ Adc, $T_A = 25^oC$)	V_F	–	1.1	Volts
Reverse Current (rated DC Voltage) $T_A = 25^oC$	I_R		0.05	mA
$T_A = 100^oC$			1.5	

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time ($I_F = 1.0$ Amp to $V_R = 30$ Vdc)	t_{rr}	–	150	200	ns
($I_{FM} = 15$ Amp, di/dt = 25 A/μs)		–	150	300	ns
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc)	$I_{RM(REC)}$	–	–	2.0	Amp

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and leads readily solderable
POLARITY: Cathode to Case
WEIGHT: 2.4 Grams (Approximately)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR850
MR851 MR852
MR854 MR856

Designers Data Sheet

SUBMINIATURE SIZE, AXIAL LEAD MOUNTED FAST RECOVERY POWER RECTIFIERS

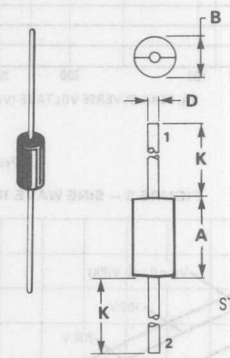
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
3 AMPERE

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MR850	MR851	MR852	MR854	MR856	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase resistive load, $T_A = 90^oC$) (1)	I_O	← 3.0 →					Amp
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	← 100 → (one cycle)					Amp
Operating and Storage Junction Temperature Range (2)	T_J, T_{stg}	← -65 to +175 →					^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Recommended Printed Circuit Board Mouting, See Note 6, Page 8)	$R_{\theta JA}$	28	$^oC/W$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage ($i_F = 9.4$ Amp, $T_J = 175^oC$)	v_F	—	0.9	1.1	Volts
Forward Voltage ($I_F = 3.0$ Amp, $T_J = 25^oC$)	V_F	—	1.04	1.25	Volts
Reverse Current (rated dc voltage) $T_J = 25^oC$	I_R	—	2.0	10	μA
$T_J = 100^oC$ MR850		—	—	150	
MR851		—	60	150	
MR852		—	—	200	
MR854		—	—	250	
MR856		—	100	300	

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time	t_{rr}				ns
($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 25)		—	150	200	
($I_F = 15$ Amp, di/dt = 10 A/μs, Figure 26)		—	200	300	
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 25)	$I_{RM(REC)}$	—	—	2.0	Amp

(1) Must be derated for reverse power dissipation. See Note 2, Page 4.
(2) Derate as shown in Figure 1

MECHANICAL CHARACTERISTICS

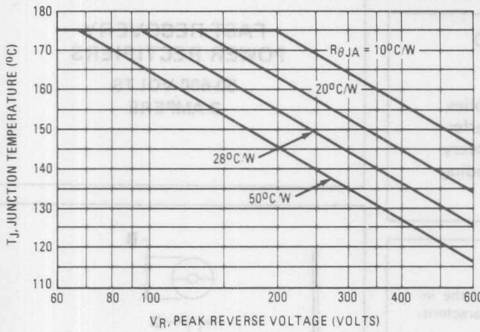
Case: Transfer Molded Plastic
Finish: External Leads are Plated, Leads are readily Solderable
Polarity: Cathode Indicated by Polarity Band
Weight: 1.1 Grams (Approximately)
Maximum Lead Temperature for Soldering Purposes:
300°C, 1/8" from case for 10 s at 5.0 lb. tension

3

3

MAXIMUM CURRENT AND TEMPERATURE RATINGS

FIGURE 1 – MAXIMUM ALLOWABLE JUNCTION TEMPERATURE



NOTE 1
MAXIMUM JUNCTION TEMPERATURE DERATING

When operating this rectifier at junction temperatures over 120°C, reverse power dissipation and the possibility of thermal runaway must be considered. The data of Figure 1 is based upon worst case reverse power and should be used to derate $T_{J(max)}$ from its maximum value of 175°C. See Note 2 for additional information on derating for reverse power dissipation.

When current ratings are computed from $T_{J(max)}$ and reverse power dissipation is also included, ratings vary with reverse voltage as shown on Figures 2 thru 5.

RESISTIVE LOAD RATINGS

Printed Circuit Board Mounting – See Note 6, Page 8

FIGURE 2 – SINE WAVE INPUT

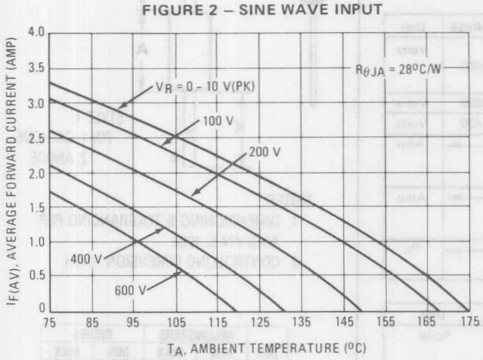


FIGURE 3 – SQUARE WAVE INPUT

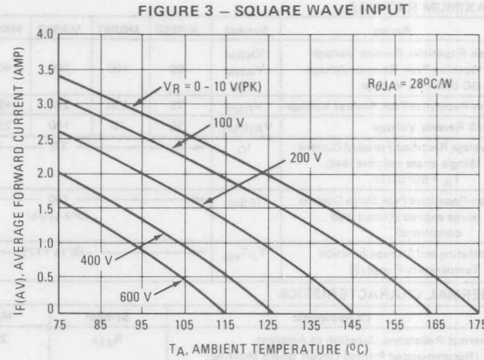


FIGURE 4 – SINE WAVE INPUT

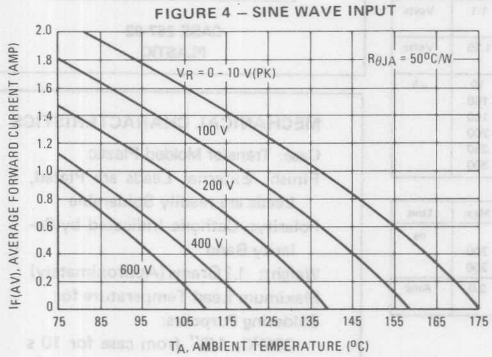
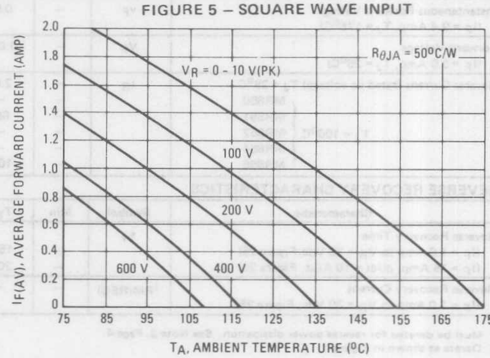


FIGURE 5 – SQUARE WAVE INPUT



MAXIMUM CURRENT RATINGS

Current derating data is based upon the thermal response data of Figure 29 and the forward power dissipation data of Figures 19 and 20. Since reverse power dissipation is not considered in Figures 6 thru 11, additional derating for reverse voltage and for junction to ambient thermal resistance must be applied. See Note 2.

SINE WAVE INPUTS

FIGURE 6 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

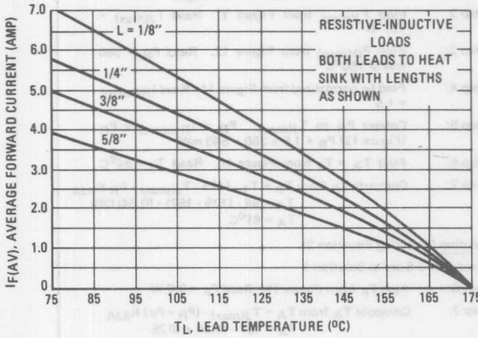


FIGURE 8 – 1/8″ LEAD LENGTH, VARIOUS LOADS

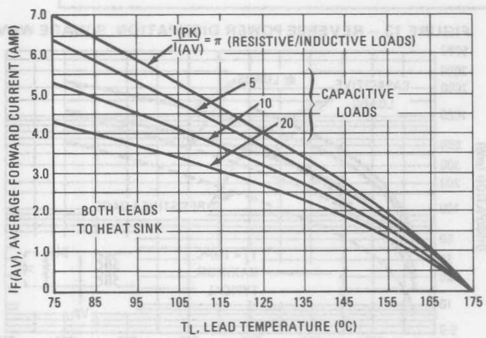
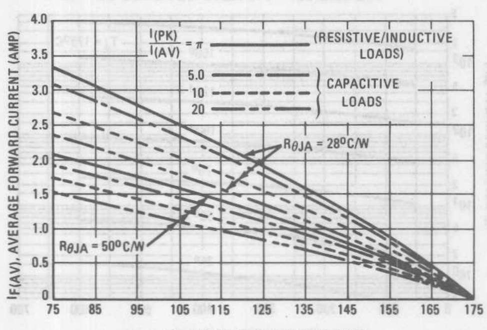


FIGURE 10 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS



SQUARE WAVE INPUTS

FIGURE 7 – EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

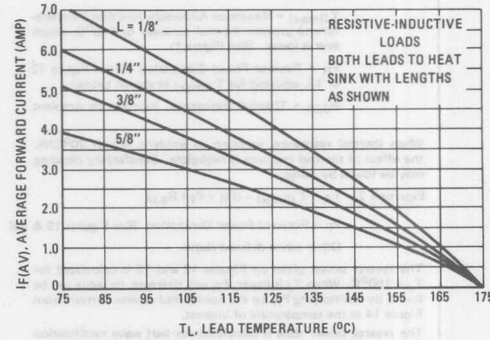


FIGURE 9 – 1/8″ LEAD LENGTH, VARIOUS LOADS

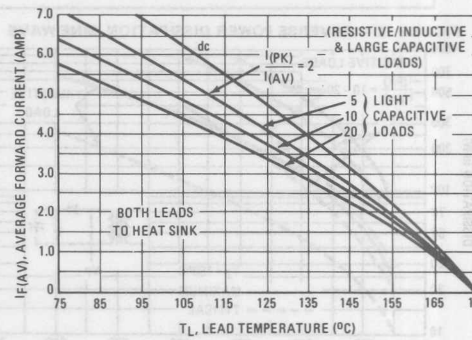
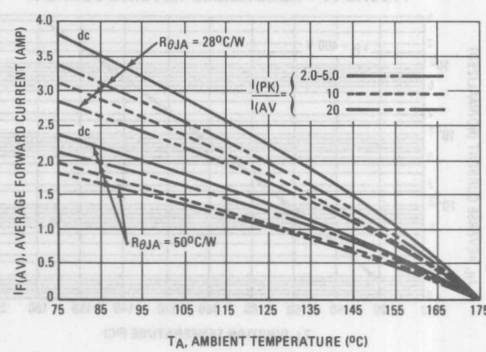


FIGURE 11 – PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS



REVERSE POWER DISSIPATION AND CURRENT

NOTE 2
DERATING FOR REVERSE POWER DISSIPATION

In this rectifier, power loss due to reverse current is generally not negligible. For reliable circuit design, the maximum junction temperature must be limited to either 175°C or the temperature which results in thermal runaway. Proper derating may be accomplished by use of equation 1 or equation 2.

Equation 1 $T_A = T_1 - (175 - T_{J(max)}) - P_R R_{\theta JA}$

Where: T_1 = Maximum Allowable Ambient Temperature neglecting reverse power dissipation (from Figures 10 or 11)

$T_{J(max)}$ = Maximum Allowable Junction Temperature to prevent thermal runaway or 175°C, which ever is lower. (See Figure 1).

P_R = Reverse Power Dissipation (From Figure 12 or 13, adjusted for $T_{J(max)}$ as shown below)

$R_{\theta JA}$ = Thermal Resistance, Junction to Ambient.

When thermal resistance, junction to ambient, is over 20°C/W, the effect of thermal response is negligible. Satisfactory derating may be found by using:

Equation 2 $T_A = T_{J(max)} - (P_R + P_F) R_{\theta JA}$

P_F = Forward Power Dissipation (See Figures 19 & 20)

Other terms defined above.

The reverse power given on Figures 12 and 13 is calculated for T_J = 150°C. When T_J is lower, P_R will decrease; its value can be found by multiplying P_R by the normalized reverse current from Figure 14 at the temperature of interest.

The reverse power data is calculated for half wave rectification circuits. For full wave rectification using either a bridge or a center-tapped transformer, the data for resistive loads is equivalent when V_P is the line to line voltage across the rectifiers. For capacitive loads, it is recommended that the dc case on Figure 13 be used, regardless of input waveform, for bridge circuits. For capacitively loaded full wave center-tapped circuits, the 20:1 data of Figure 12 should be used for sine wave inputs and the capacitive load data of Figure 13 should be used for square wave inputs regardless of $I_{(pk)}/I_{(av)}$. For these two cases, V_P is the voltage across one leg of the transformer.

Example 1 Find maximum ambient temperature for I_{AV} = 2 A, capacitive load of I_{PK}/I_{AV} = 20, Input Voltage = 60 V (rms), sine wave, $R_{\theta JA}$ = 28°C/W, half wave circuit.

Solution 1 (using Equation 1)

Step 1: Find V_P; $V_P = \sqrt{2}\,V_{in}$ = 85 V, $V_{R(pk)}$ = 170

Step 2: Find $T_{J(max)}$ from Figure 1. Read $T_{J(max)}$ = 157°C

Step 3: Find $P_{R(max)}$ from Figure 12. Read P_R = 360 mW @ 150°C

Step 4: Find I_R normalized from Figure 14. Read $I_{R(norm)}$ = 1.5

Step 5: Correct P_R to $T_{J(max)}$. $P_R = I_{R(norm)} \times P_R$ (Figure 12) P_R = 1.5 x 360 = 540 mW

Step 6: Find $T_A = T_1$ from Figure 10. Read T_1 = 94°C

Step 7: Compute T_A from $T_A = T_1 - (175 - T_{J(max)} - P_R R_{\theta JA}$
T_A = 94 - (175 - 157) - (0.54) (28)
T_A = 61°C

Solution 2 (using Equation 2)

Steps 1 thru 5 are as Solution 1

Step 6: Find P_F from Figure 19. Read P_F = 3.0 W

Step 7: Compute T_A from $T_A = T_{J(max)} - (P_R + P_F) R_{\theta JA}$
T_A = 157 - (0.54 + 3) 28
T_A = 58°C

The discrepancy occurs because thermal response is factored into solution 1, and advantage is taken of the cooling time after the power pulse and before reverse voltage achieves its maximum. 61°C is a satisfactory ambient temperature.

FIGURE 12 — REVERSE POWER DISSIPATION, SINE WAVE

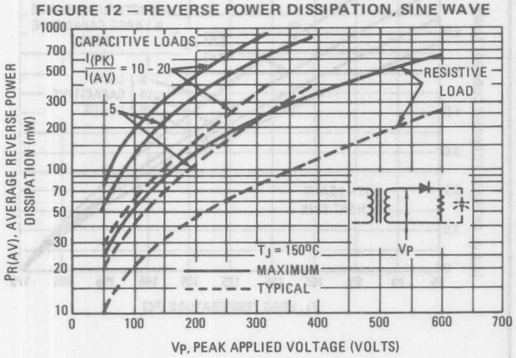


FIGURE 13 — REVERSE POWER DISSIPATION, SQUARE WAVE

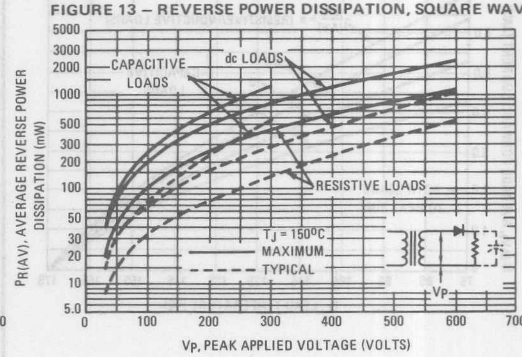


FIGURE 14 — NORMALIZED REVERSE CURRENT

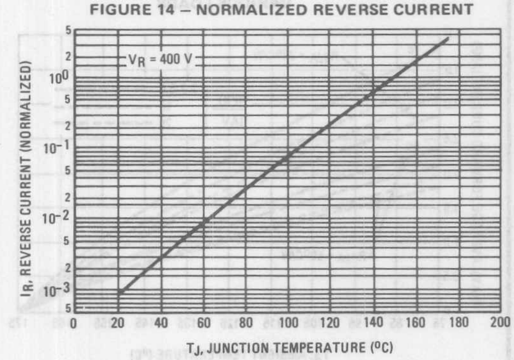
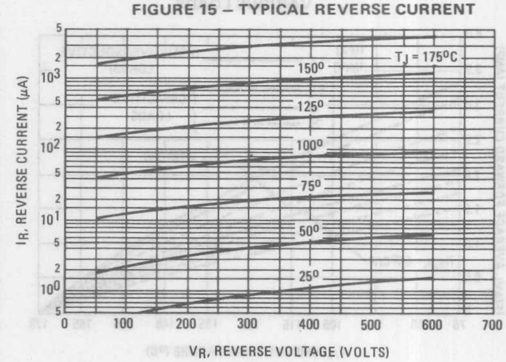


FIGURE 15 — TYPICAL REVERSE CURRENT



STATIC CHARACTERISTICS

FIGURE 16 – FORWARD VOLTAGE

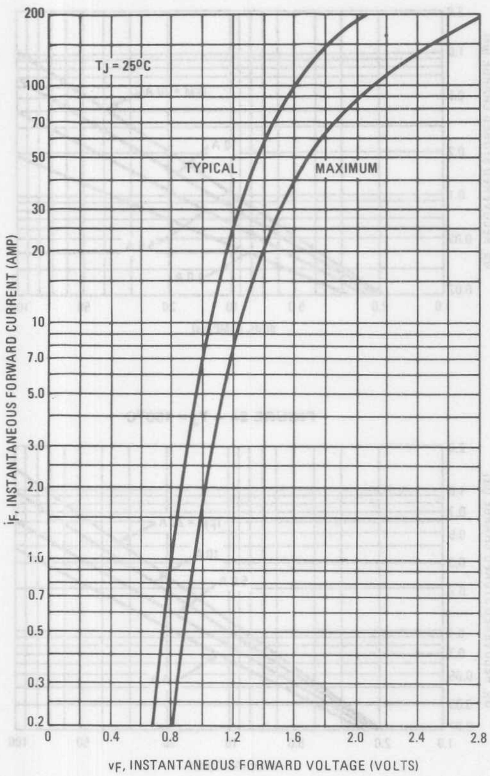


FIGURE 17 – MAXIMUM SURGE CAPABILITY

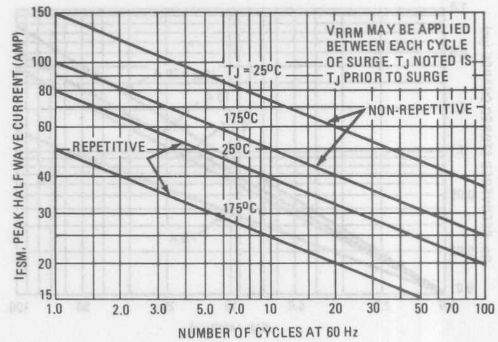
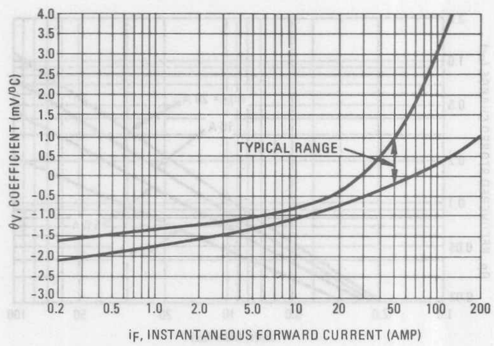
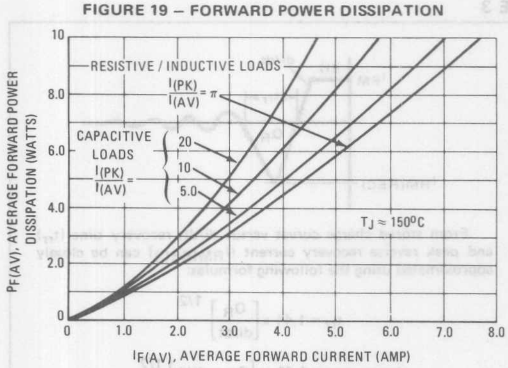


FIGURE 18 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT



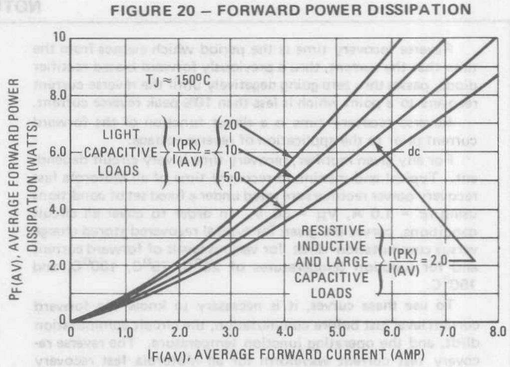
SINE WAVE INPUT

FIGURE 19 – FORWARD POWER DISSIPATION



SQUARE WAVE INPUT

FIGURE 20 – FORWARD POWER DISSIPATION



TYPICAL RECOVERED STORED CHARAGE DATA

(See Note 3)

FIGURE 21 – $T_J = 25^oC$

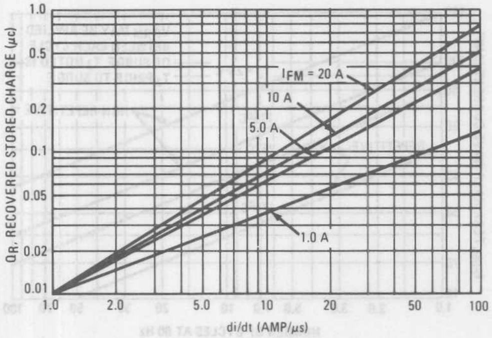


FIGURE 22 – $T_J = 75^oC$

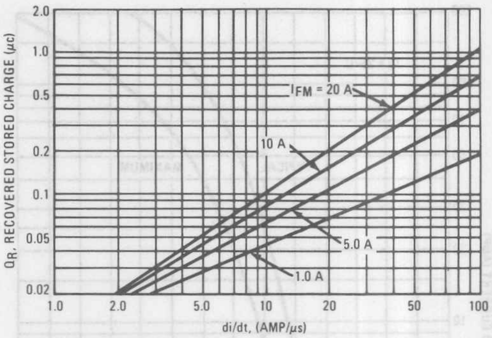


FIGURE 23 – $T_J = 100^oC$

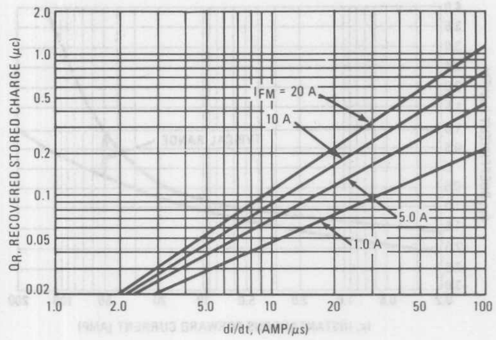
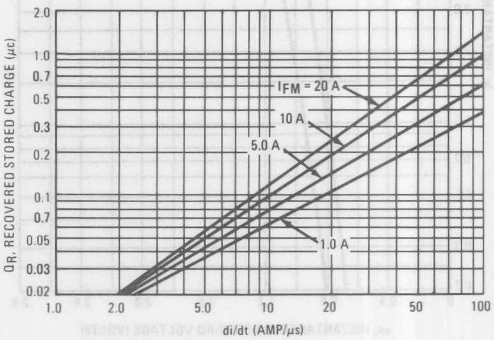


FIGURE 24 – $T_J = 150^oC$



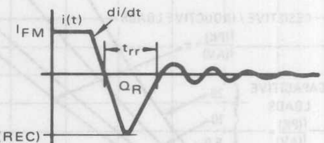
NOTE 3

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

DYNAMIC CHARACTERISTICS

FIGURE 25 — JEDEC REVERSE RECOVERY CIRCUIT

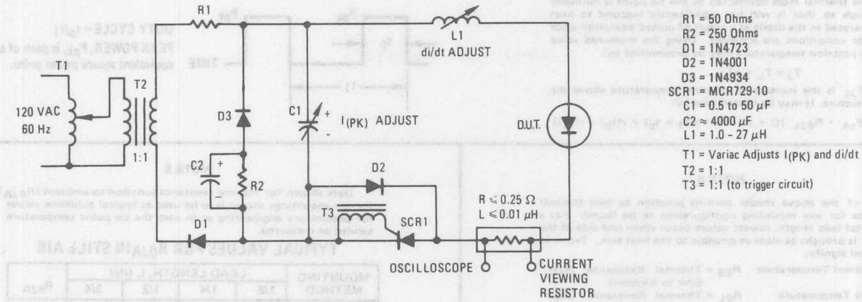


FIGURE 26 — FORWARD RECOVERY TIME

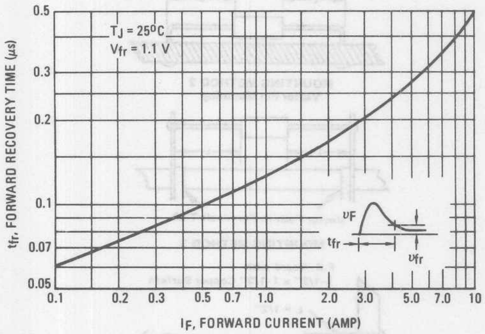


FIGURE 27 — JUNCTION CAPACITANCE

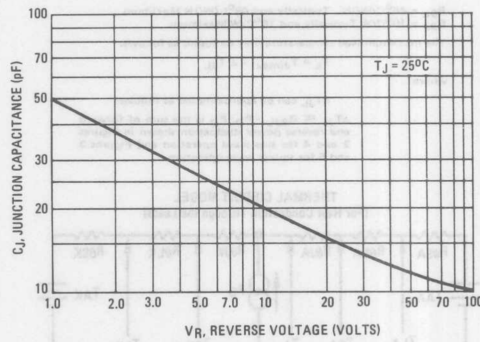


FIGURE 28 — THERMAL RESPONSE

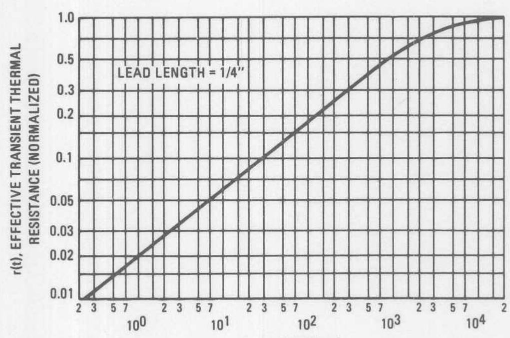
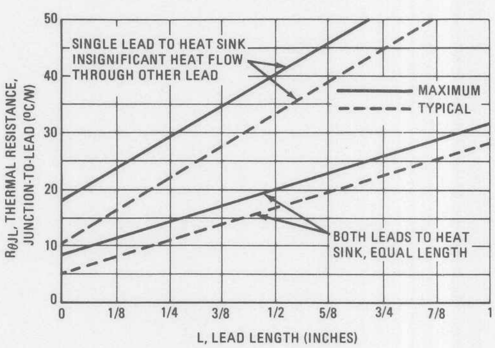


FIGURE 29 — STEADY-STATE THERMAL RESISTANCE



NOTE 4

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the lead should be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

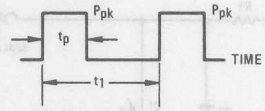
$$T_J = T_L + \Delta T_{JL}$$

where ΔT_{JL} is the increase in junction temperature above the lead temperature. It may be determined by:

$$\Delta T_{JL} = P_{pk} \cdot R_{\theta JL} \,[D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where $r(t)$ = normalized value of transient thermal resistance at time t from Figure 29, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.



DUTY CYCLE = t_p/t_1

PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

NOTE 5

Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. For a given total lead length, lowest values occur when one side of the rectifier is brought as close as possible to the heat sink. Terms in the model signify:

T_A = Ambient Temperature	$R_{\theta S}$ = Thermal Resistance, Heat Sink to Ambient
T_L = Lead Temperature	$R_{\theta L}$ = Thermal Resistance, Lead to Heat Sink
T_C = Case Temperature	$R_{\theta J}$ = Thermal Resistance, Junction to Case
T_J = Junction Temperature	P_D = Total Power Dissipation = $P_F + P_R$
	P_F = Forward Power Dissipation
	P_R = Reverse Power Dissipation

(Subscripts A and K refer to anode and cathode sides respectively.) Values for thermal resistance components are:

$R_{\theta L}$ = 46°C/W/IN. Typically and 48°C/W/IN Maximum.
$R_{\theta J}$ = 10°C/W Typically and 16°C/W Maximum.

The maximum lead temperature may be found as follows:

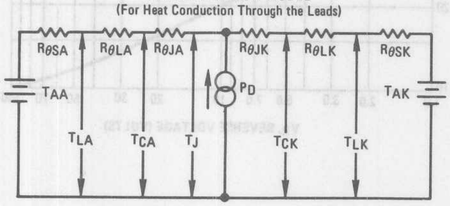
$$T_L = T_{J(max)} - \Delta T_{JL}$$

where

ΔT_{JL} can be approximated as follows:

$\Delta T_{JL} \approx R_{\theta JL} \cdot P_D$; P_D is the sum of forward and reverse power dissipation shown in Figures 2 and 4 for sine wave operation and Figures 3 and 5 for square wave operation.

THERMAL CIRCUIT MODEL
(For Heat Conduction Through the Leads)



NOTE 6

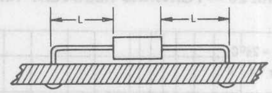
Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

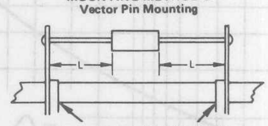
MOUNTING METHOD	LEAD LENGTH, L (IN)				$R_{\theta JA}$
	1/8	1/4	1/2	3/4	
1	50	51	53	55	°C/W
2	58	59	61	63	°C/W
3	28				°C/W

MOUNTING METHOD 1

P.C. Board Where Available Copper Surface area is small.

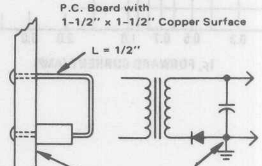


MOUNTING METHOD 2
Vector Pin Mounting



MOUNTING METHOD 3

P.C. Board with 1-1/2" x 1-1/2" Copper Surface



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR860 MR861
MR862 MR864
MR866

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

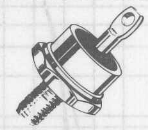
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

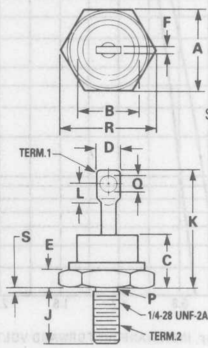
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
40 AMPERES





STYLE 1:
TERM.1. CATHODE
2. ANODE (CASE)

NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.94	17.45	0.669	0.687
B	–	16.94	–	0.667
C	–	11.43	–	0.450
D	–	9.53	–	0.375
E	2.92	5.08	0.115	0.200
F	–	2.03	–	0.080
J	10.72	11.51	0.422	0.453
K	–	25.40	–	1.000
L	3.86	–	0.156	–
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	–	20.16	–	0.794
S	–	2.26	–	0.089

CASE 257-01
DO-203AB
METAL

MAXIMUM RATINGS

Rating	Symbol	MR860	MR861	MR862	MR864	MR866	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100^oC$)	I_O	40					Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	350					Amps
Operating Junction Temperature Range	T_J	-65 to +160					^oC
Storage Temperature Range	T_{stg}	-65 to +175					^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.85	$^oC/W$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage ($i_F = 125$ Amp, $T_J = 150^oC$)	v_F	–	1.3	1.6	Volts
Forward Voltage ($I_F = 40$ Amp, $T_C = 25^oC$)	V_F	–	1.0	1.4	Volts
Reverse Current (rated dc voltage) $T_C = 25^oC$ $T_C = 100^oC$	I_R	 – –	 25 1.0	 50 2.0	 μA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 16) ($I_{FM} = 36$ Amp, $di/dt = 25$ A/μs, Figure 17)	t_{rr}	 – –	 150 200	 200 400	ns
Reverse Recovery Current ($I_F = 1.0$ Amp to $V_R = 30$ Vdc, Figure 16)	$I_{RM(REC)}$	–	2.0	3.0	Amp

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed

FINISH: All external surfaces corrosion resistant and readily solderable

POLARITY: Cathode to Case

WEIGHT: 17 Grams (Approximately)

STUD TORQUE: 25 in. lbs.

3

FIGURE 1 – FORWARD VOLTAGE

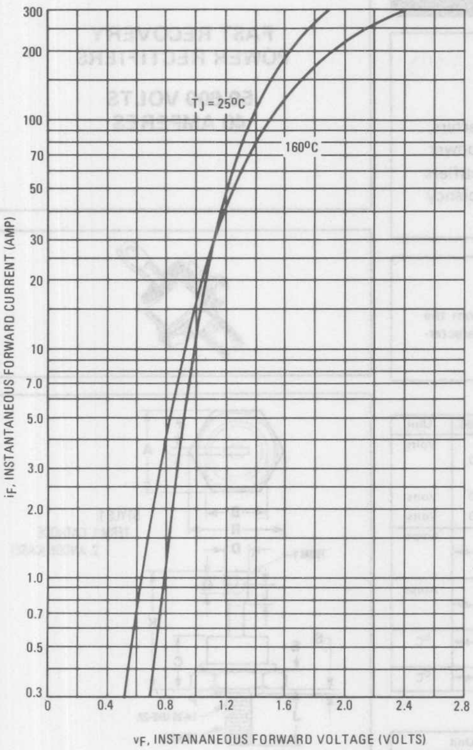
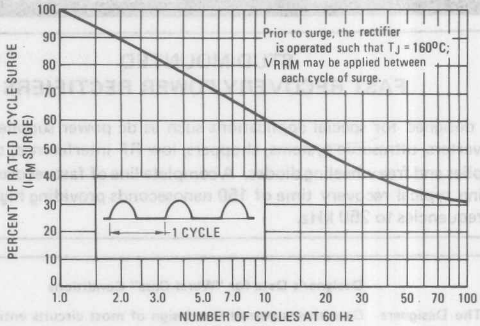
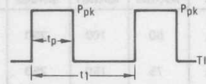


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

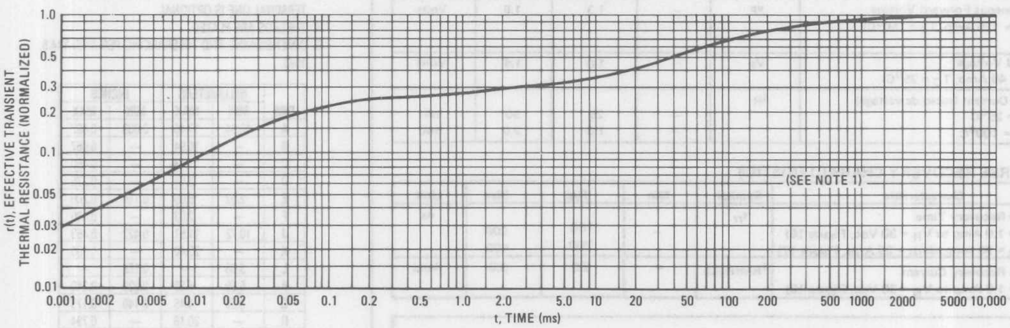
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

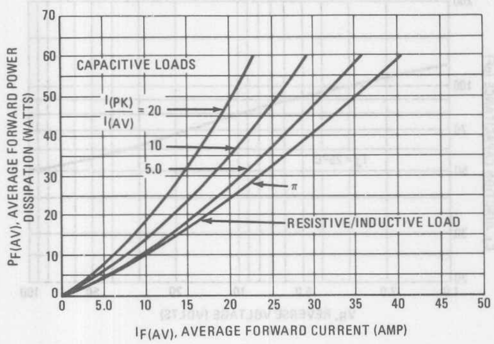
FIGURE 3 – THERMAL RESPONSE



3

SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION



SQUARE WAVE INPUT

FIGURE 5 – FORWARD POWER DISSIPATION

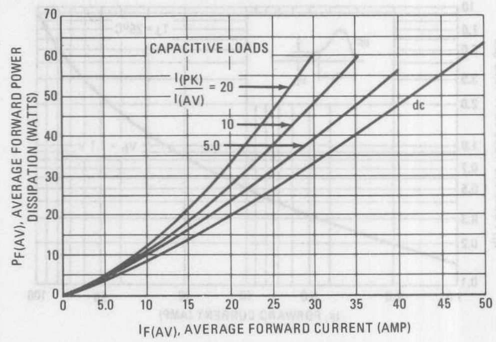


FIGURE 6 – CURRENT DERATING

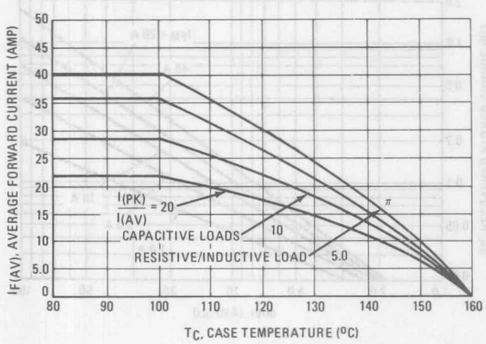


FIGURE 7 – CURRENT DERATING

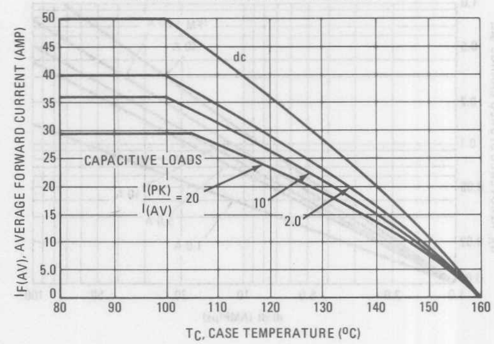


FIGURE 8 – TYPICAL REVERSE CURRENT

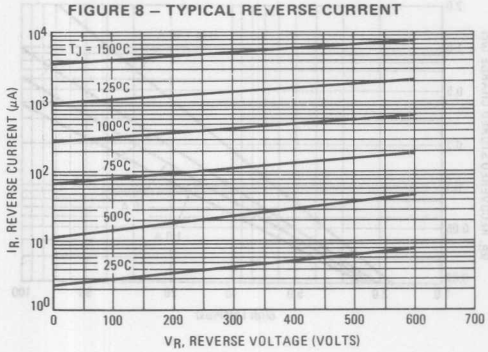
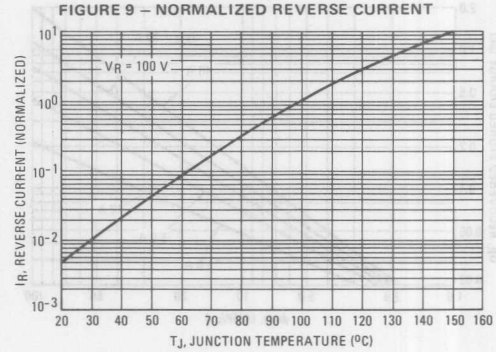


FIGURE 9 – NORMALIZED REVERSE CURRENT



3

3

FIGURE 10 – FORWARD RECOVERY TIME

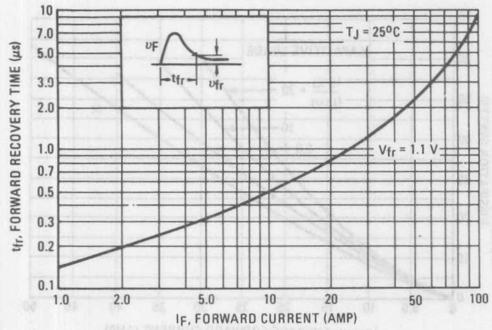
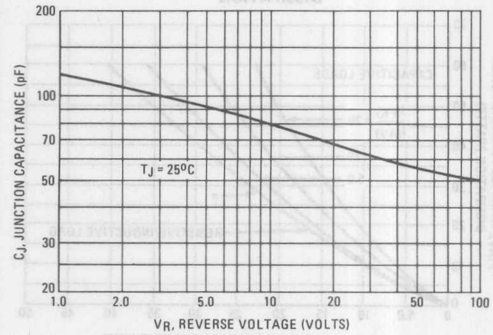


FIGURE 11 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 – $T_J = 25^oC$

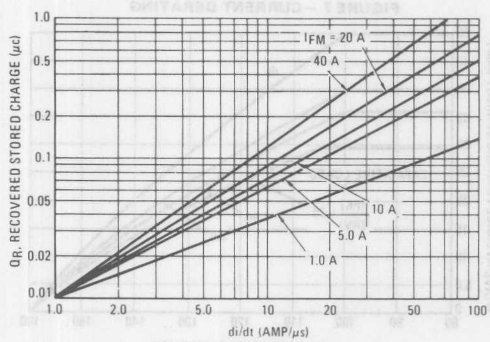


FIGURE 13 – $T_J = 75^oC$

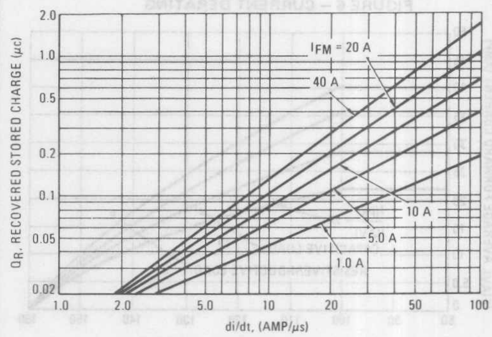


FIGURE 14 – $T_J = 100^oC$

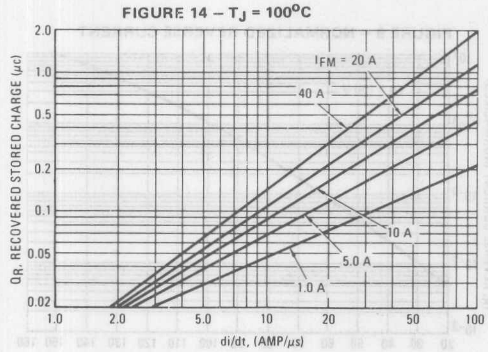


FIGURE 15 – $T_J = 150^oC$

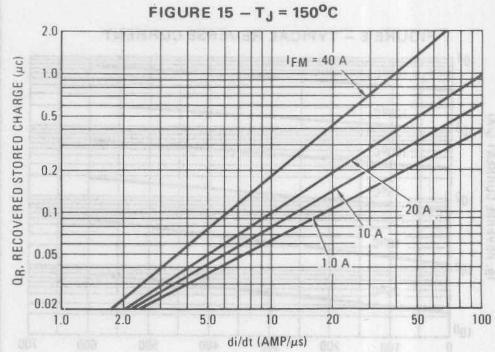
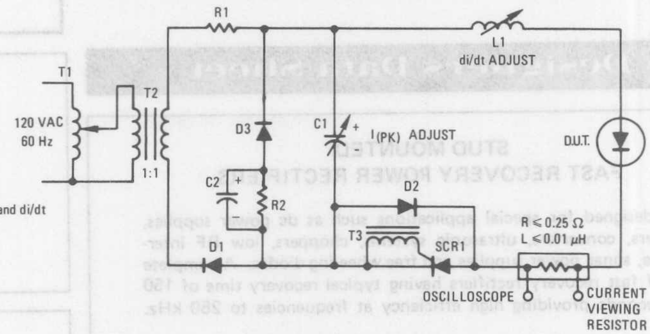


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT

R1 = 50 Ohms
R2 = 250 Ohms
D1 = 1N4723
D2 = 1N4001
D3 = 1N4933
SCR1 = MCR729-10
C1 = 0.5 to 50 μF
C2 ≈ 4000 μF
L1 = 1.0 - 27 μH
T1 = Variac Adjusts $I_{(PK)}$ and di/dt
T2 = 1:1
T3 = 1:1 (to trigger circuit)



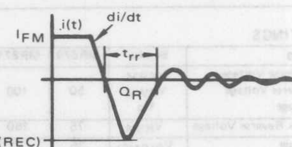
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR870 MR871
MR872 MR874
MR876

Designers Data Sheet

STUD MOUNTED
FAST RECOVERY POWER RECTIFIERS

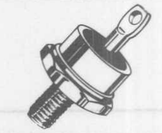
. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

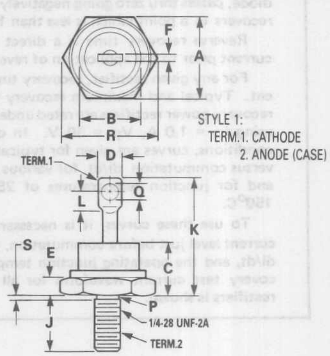
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves – representing boundaries on device characteristics – are given to facilitate "worst case" design.

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
50 AMPERES





NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.94	17.45	0.669	0.687
B	–	16.94	–	0.667
C	–	11.43	–	0.450
D	–	9.53	–	0.375
E	2.92	5.08	0.115	0.200
F	–	2.03	–	0.080
J	10.72	11.51	0.422	0.453
K	–	25.40	–	1.000
L	3.86	–	0.156	–
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	–	20.16	–	0.794
S	–	2.26	–	0.089

CASE 257-01
DO-203AB
METAL

MAXIMUM RATINGS

Rating	Symbol	MR870	MR871	MR872	MR874	MR876	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 100°C$)	I_O	← 50 →					Amps
Non-Repetitive Peak Surge Current (surge applied at rated load conditions)	I_{FSM}	← 400 →					Amps
Operating Junction Temperature Range	T_J	← -65 to +160 →					°C
Storage Temperature Range	T_{stg}	← -65 to +175 →					°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage (i_F = 157 Amp, T_J = 160°C)	v_F	–	1.3	1.6	Volts
Forward Voltage (I_F = 50 Amp, T_C = 25°C)	V_F	–	1.1	1.4	Volts
Reverse Current (rated dc voltage) T_C = 25°C T_C = 100°C	I_R	 – –	 25 1.0	 50 2.0	 μA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recovery Time (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16) (I_{FM} = 36 Amp, di/dt = 25 A/μs, Figure 17)	t_{rr}	 – –	 150 240	 200 400	ns
Reverse Recovery Current (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 16)	$I_{RM(REC)}$	–	2.0	3.0	Amp

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed
FINISH: All external surfaces corrosion resistant and readily solderable
POLARITY: Cathode to Case
WEIGHT: 17 grams (approximately)
STUD TORQUE: 25 in. lbs.

FIGURE 1 – FORWARD VOLTAGE

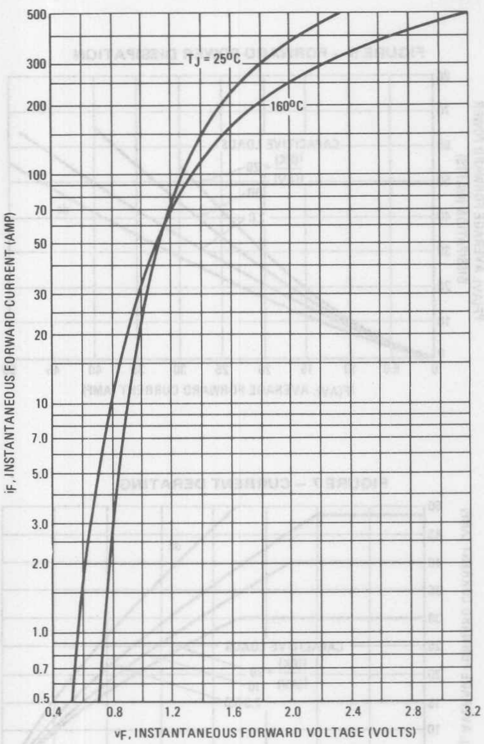
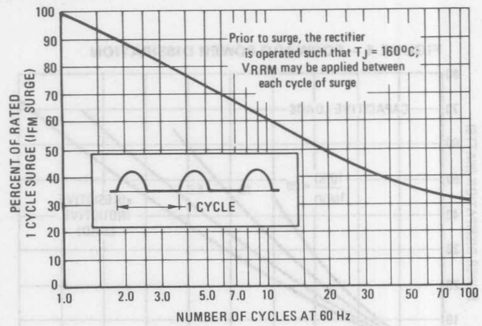
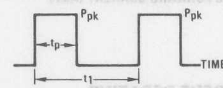


FIGURE 2 – MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see Note 3). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

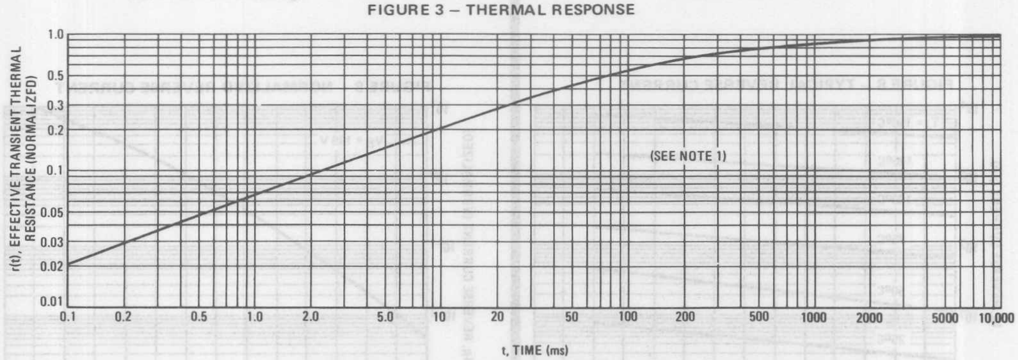
$$\Delta T_{JC} = P_{pk} \cdot R_{\theta JC} [D + (1 - D) \cdot r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 3 – THERMAL RESPONSE



3

SINE WAVE INPUT

FIGURE 4 – FORWARD POWER DISSIPATION

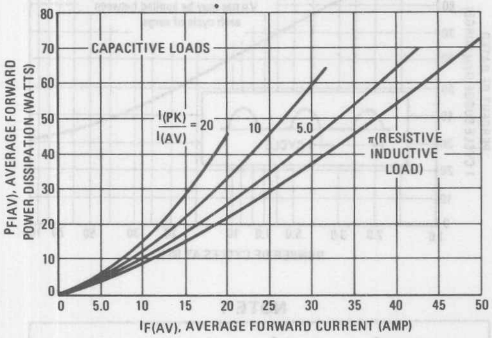


FIGURE 6 – CURRENT DERATING

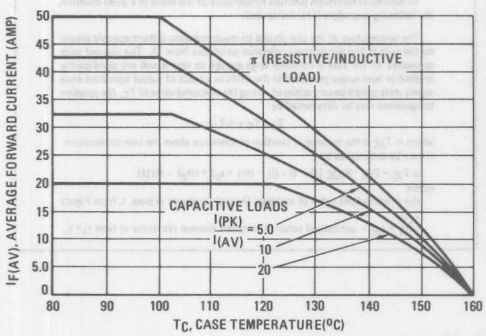
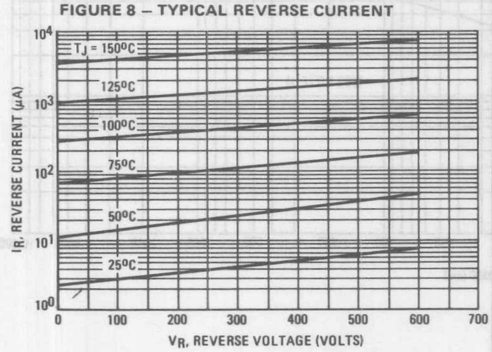


FIGURE 8 – TYPICAL REVERSE CURRENT



SQUARE WAVE INPUT

FIGURE 5 – FORWARD POWER DISSIPATION

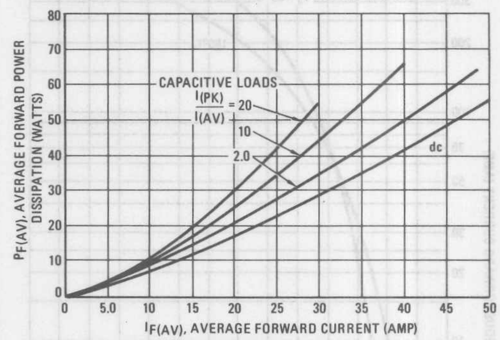


FIGURE 7 – CURRENT DERATING

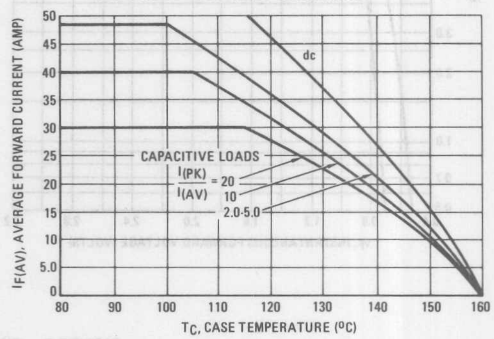
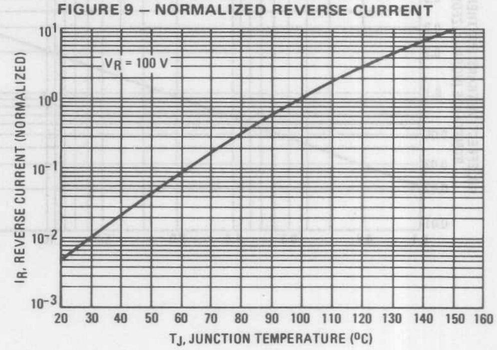


FIGURE 9 – NORMALIZED REVERSE CURRENT



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 – FORWARD RECOVERY TIME

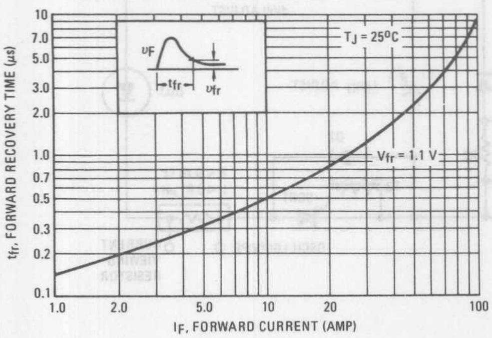
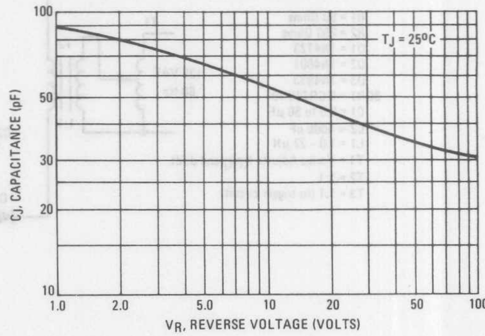


FIGURE 11 – JUNCTION CAPACITANCE



TYPICAL RECOVERED STORED CHARGE DATA

(See Note 2)

FIGURE 12 – T_J = 25°C

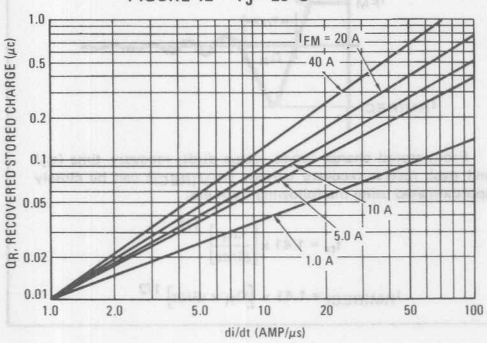


FIGURE 13 – T_J = 75°C

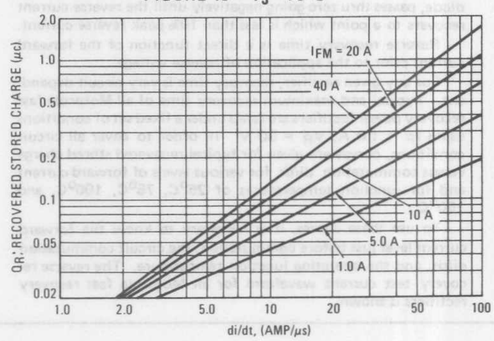


FIGURE 14 – T_J = 100°C

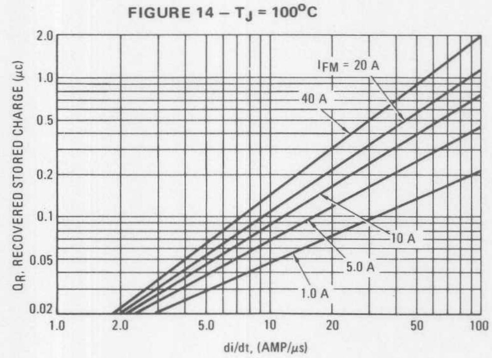


FIGURE 15 – T_J = 150°C

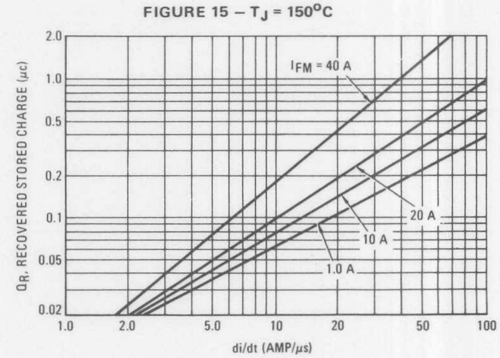
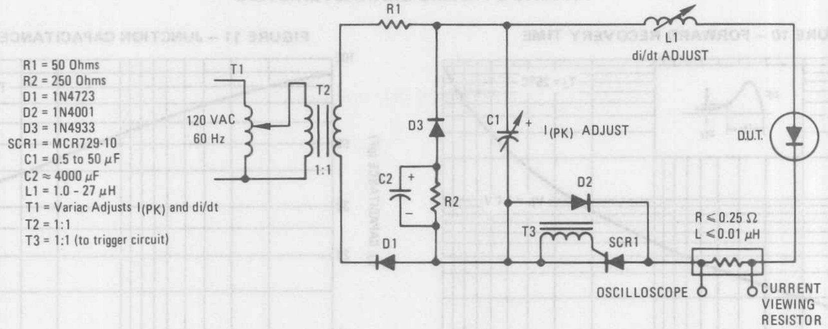


FIGURE 16 — JEDEC REVERSE RECOVERY CIRCUIT



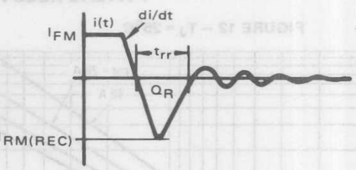
NOTE 2

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

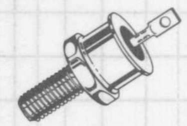
$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

3

MR1120 thru MR1126 MR1128 MR1130

MEDIUM-CURRENT SILICON RECTIFIERS

50-1000 VOLTS
12 AMPERES



MEDIUM-CURRENT SILICON RECTIFIER

Medium-current silicon rectifiers feature high surge current capacity, and low forward voltage drop.

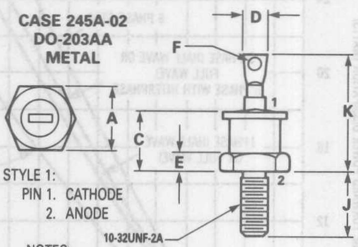
MAXIMUM RATINGS

Rating	Symbol	MR 1120	MR 1121	MR 1122	MR 1123	MR 1124	MR 1125	MR 1126	MR 1128	MR 1130	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	500	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage (one half-wave, single phase, 60 cycle peak)	V_{RSM}	100	200	300	400	500	600	720	100	1200	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	350	420	560	700	Volts
Average Rectified Forward Current (single phase, resistive load, 60 Hz, T_C = 150°C)	I_O	12									Amp
Peak Repetitive Forward Current (T_C = 150°C)	I_{FRM}	75									Amp
Non-Repetitive Peak Surge Current (superimposed on rated current at rated voltage, T_C = 150°C)	I_{FSM}	300 (for 1/2 cycle)									Amp
I^2t Rating (non-repetitive, 1 ms <t <8.3 ms)	I^2t	375									$A_{(rms)}^2s$
Maximum Junction Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +190									°C

ELECTRICAL CHARACTERISTICS (All Types)

Characteristic	Symbol	Max	Unit
Full Cycle Average Forward Voltage Drop (I_O = 12 Amps and Rated V_r, T_C = 150°C, Half Wave Rectifier)	$V_{F(AV)}$	0.55	Volts
DC Forward Voltage Drop (I_F = 12 Adc, T_C = 25°C)	V_F	1.0	Volts
Full Cycle Average Reverse Current (I_O = 12 Amps and Rated V_r, T_C = 150°C, Half Wave Rectifier)	$I_{R(AV)}$	1.5	mA
DC Reverse Current (Rated V_R, T_C = 25°C)	I_R	0.5	mA

CASE 245A-02
DO-203AA
METAL



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

3

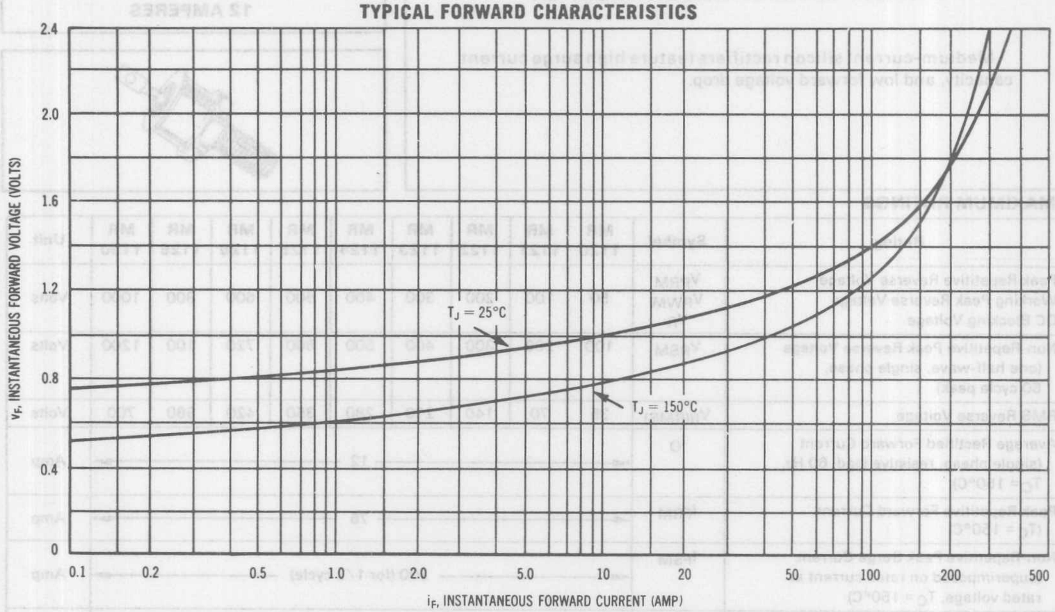
THERMAL CHARACTERISTICS

Maximum Steady State DC Thermal Resistance, $R_{\theta JC}$: 2.5°C/Watt

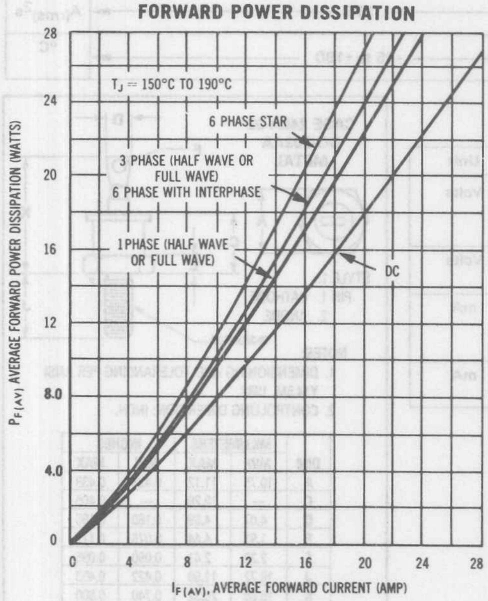
MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed construction.
FINISH: All external surfaces corrosion-resistant and the terminal lug is readily solderable.
POLARITY: CATHODE-TO-CASE (reverse polarity units are available upon request and are designated by an "R" suffix i.e. MR1120R).
MOUNTING POSITIONS: Any
STUD TORQUE: 15 in-lbs maximum.

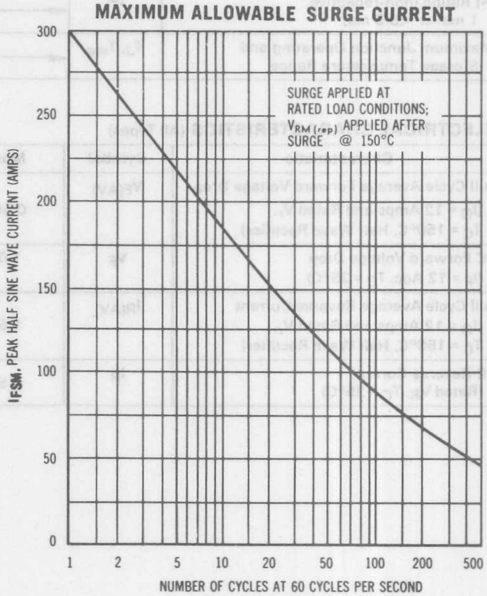
TYPICAL FORWARD CHARACTERISTICS



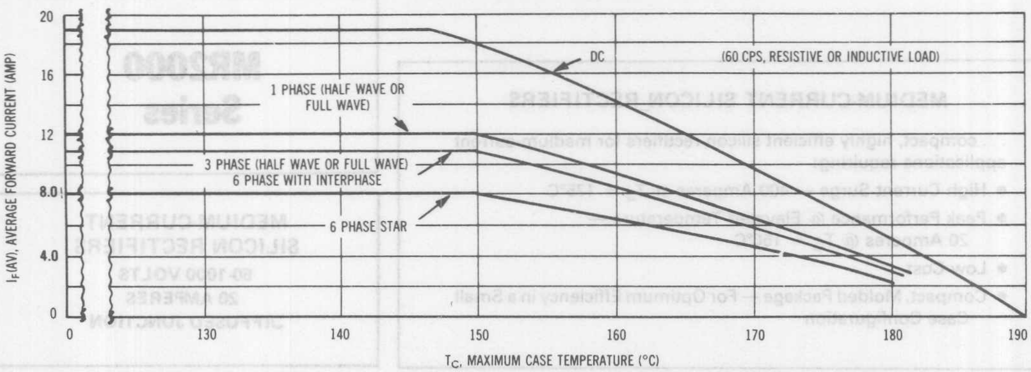
FORWARD POWER DISSIPATION



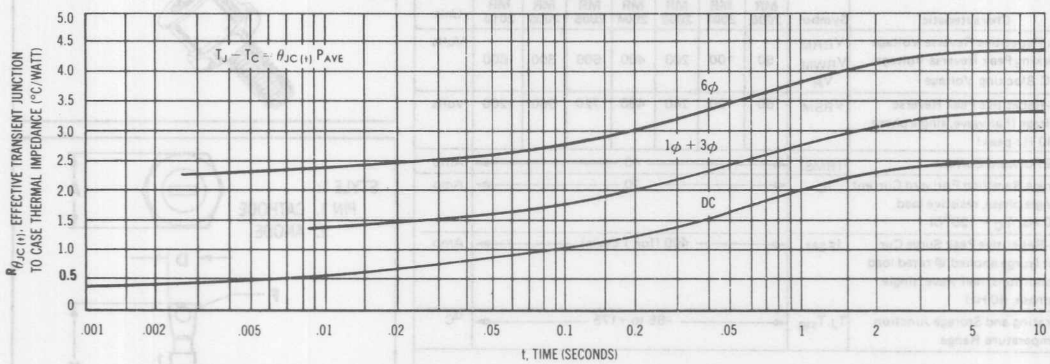
MAXIMUM ALLOWABLE SURGE CURRENT



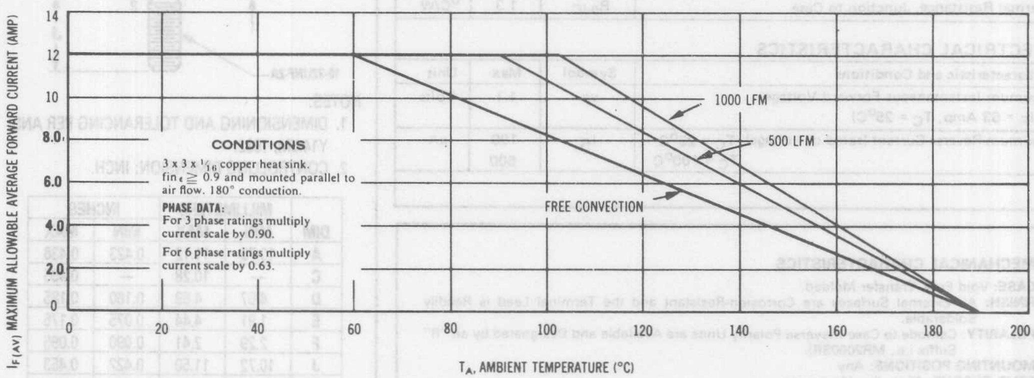
MAXIMUM CURRENT RATINGS



EFFECTIVE TRANSIENT THERMAL IMPEDANCE



CURRENT DERATING DATA



3

MR1396 See Page 3-27

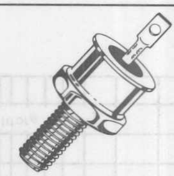
MR2000 Series

MEDIUM-CURRENT SILICON RECTIFIERS

. . . compact, highly efficient silicon rectifiers for medium-current applications requiring:

- High Current Surge — 400 Amperes @ T_J = 175°C
- Peak Performance @ Elevated Temperature — 20 Amperes @ T_C = 150°C
- Low Cost
- Compact, Molded Package — For Optimum Efficiency in a Small Case Configuration

MEDIUM-CURRENT SILICON RECTIFIERS
50-1000 VOLTS
20 AMPERES
DIFFUSED JUNCTION



MAXIMUM RATINGS

Characteristic	Symbol	MR 2000	MR 2001	MR 2002	MR 2004	MR 2006	MR 2008	MR 2010	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage (halfwave, single phase, 60 Hz peak)	V_{RSM}	60	120	240	480	720	960	1200	Volts
RMS Forward Current	$I_{(RMS)}$	← 40 →							Amp
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, T_C = 150°C)	I_O	← 20 →							Amp
Non-Repetitive Peak Surge Current (surge applied @ rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	← 400 (for 1 cycle) →							Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← −65 to +175 →							°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.3	°C/W

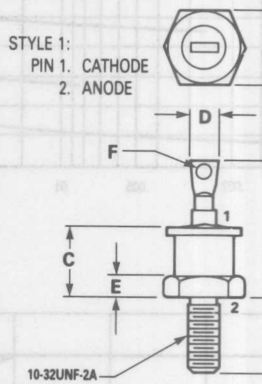
ELECTRICAL CHARACTERISTICS

Characteristic and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage (i_F = 63 Amp, T_C = 25°C)	v_F	1.1	Volts
Maximum Reverse Current (rated dc voltage) T_C = 25°C T_C = 100°C	I_R	100 500	μA

MECHANICAL CHARACTERISTICS

CASE: Void Free, Transfer Molded.
FINISH: All External Surfaces are Corrosion-Resistant and the Terminal Lead is Readily Solderable.
POLARITY: Cathode to Case (Reverse Polarity Units are Available and Designated by an "R" Suffix i.e., MR2000SR).
MOUNTING POSITIONS: Any
STUD TORQUE: 15 in. lbs. Maximum
MAXIMUM TERMINAL TEMPERATURE FOR SOLDERING PURPOSES: 275°C for 10 Seconds @ 3 Kg Tension.
WEIGHT: 6 Grams (Approximately).

STYLE 1:
PIN 1. CATHODE
2. ANODE



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

FIGURE 1 – FORWARD VOLTAGE

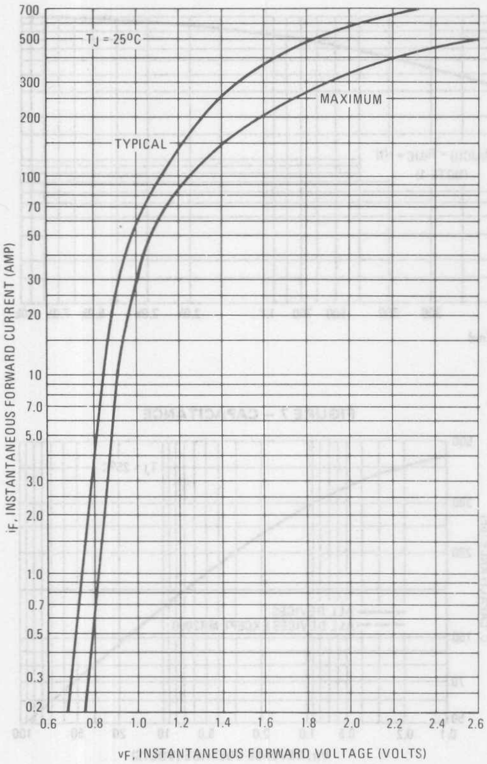


FIGURE 2 – NON-REPETITIVE SURGE CURRENT

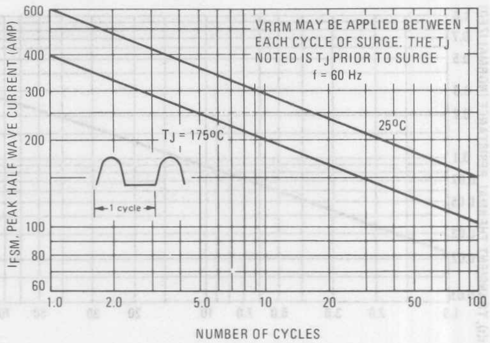


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

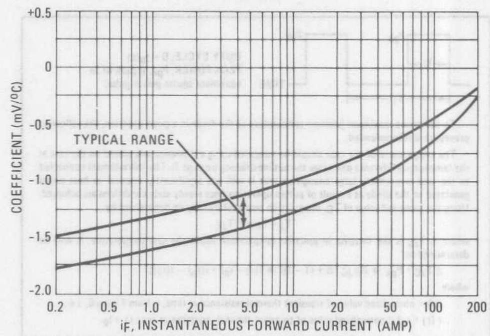


FIGURE 4 – CURRENT DERATING

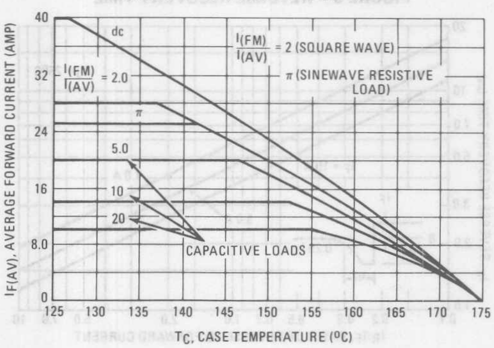


FIGURE 5 – FORWARD POWER DISSIPATION

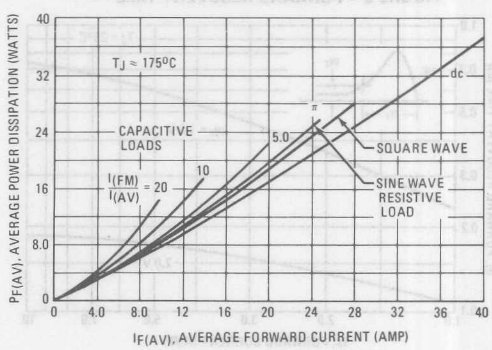


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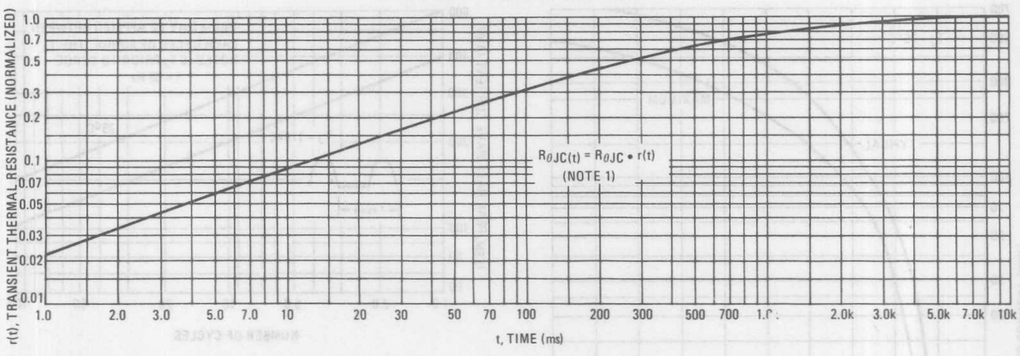
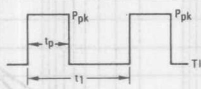
FIGURE 6 – THERMAL RESPONSE



3

NOTE 1



DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see the outline drawing on page 1). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC} [D + (1 - D) \bullet r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 6, i.e.,
$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 7 – CAPACITANCE

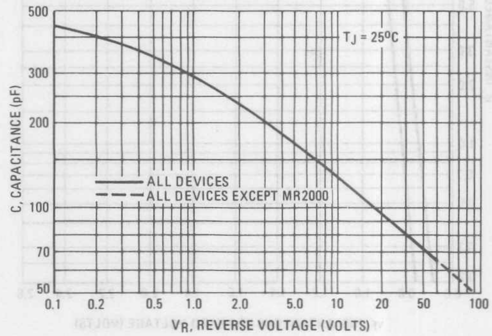


FIGURE 8 – FORWARD RECOVERY TIME

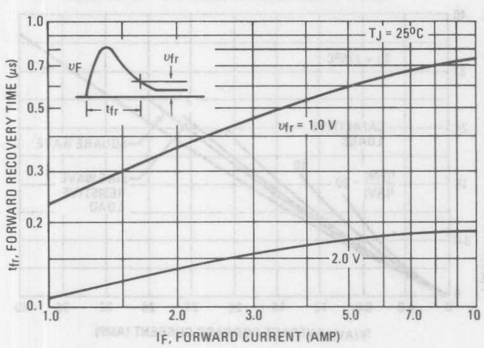


FIGURE 9 – REVERSE RECOVERY TIME

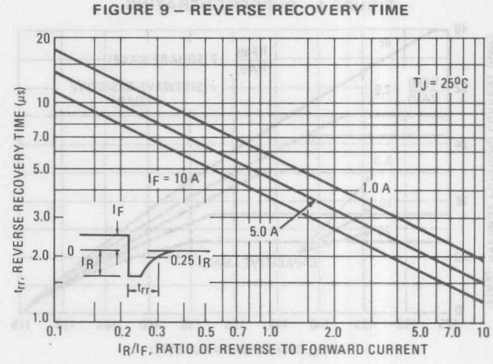
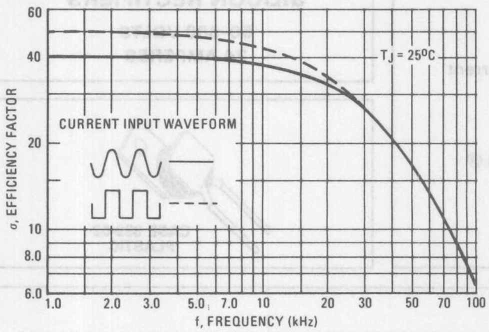
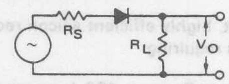


FIGURE 10 – RECTIFICATION WAVEFORM EFFICIENCY



RECTIFICATION EFFICIENCY NOTE

FIGURE 11 – SINGLE-PHASE HALF-WAVE RECTIFIER CIRCUIT



The rectification efficiency factor σ shown in Figure 10 was calculated using the formula:

$$\sigma = \frac{P_{dc}}{P_{rms}} = \frac{\dfrac{V^2{}_O(dc)}{R_L}}{\dfrac{V^2{}_O(rms)}{R_L}} \bullet 100\% = \frac{V^2{}_O(dc)}{V^2{}_O(ac) + V^2{}_O(dc)} \bullet 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assume lossless, the maximum theoretical efficiency factor becomes:

$$\sigma(\text{sine}) = \frac{\dfrac{V^2{}_m}{\pi^2 R_L}}{\dfrac{V^2{}_m}{4R_L}} \bullet 100\% = \frac{4}{\pi^2} \bullet 100\% = 40.6\% \quad (2)$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma(\text{square}) = \frac{\dfrac{V^2{}_m}{2R_L}}{\dfrac{V^2{}_m}{R_L}} \bullet 100\% = 50\% \quad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 9) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 10.

It should be emphasized that Figure 10 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_O with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 10.

TAB-MOUNTED MEDIUM-CURRENT SILICON RECTIFIERS

. . . compact, highly efficient silicon rectifiers for medium current applications requiring:

- High Current Surge — 400 Amperes @ $T_J = 175°C$
- Peak Performance @ Elevated Temperature — 24 Amperes @ $T_C = 150°C$
- Low Cost
- Same Mounting as a TO-220AB

MEDIUM-CURRENT SILICON RECTIFIERS

50-600 VOLTS
24 AMPERES

CASE 339-02
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MR2400	MR2401	MR2402	MR2404	MR2406	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Nonrepetitive Peak Reverse Voltage (half wave, single phase, 60 Hz peak)	V_{RSM}	60	120	240	480	720	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, $T_C = 150°C$)	I_O	← 24 →					Amp
Nonrepetitive Peak Surge Current (surge applied @ rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	← 400 (for 1 cycle) →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← −65 to +175 →					°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	°C/W
Thermal Resistance, Junction to Air PC Board Mount, Perpendicular to Surface	$R_{\theta JA}$	55	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage ($i_F = 75.4$ Amp, $T_C = 25°C$)	v_F	1.18	Volts
Maximum Reverse Current (rated dc voltage) $T_C = 25°C$ $T_C = 100°C$	I_R	 25 1.0	 μA mA

MECHANICAL CHARACTERISTICS

CASE: Plastic encapsulated, metal tabs.

FINISH: All external surfaces are corrosion resistant and the leads are readily solderable.

POLARITY: Cathode to tab with hole; Reverse polarity available by adding "R" Suffix, MR2402R.

MOUNTING TORQUE: 8 in-lb max.

MAXIMUM TEMPERATURE FOR SOLDERING PURPOSES: 350°C, 3/8" from case for 10 seconds.

WEIGHT: 3.6 Grams (Approximately).

FIGURE 1 – FORWARD VOLTAGE

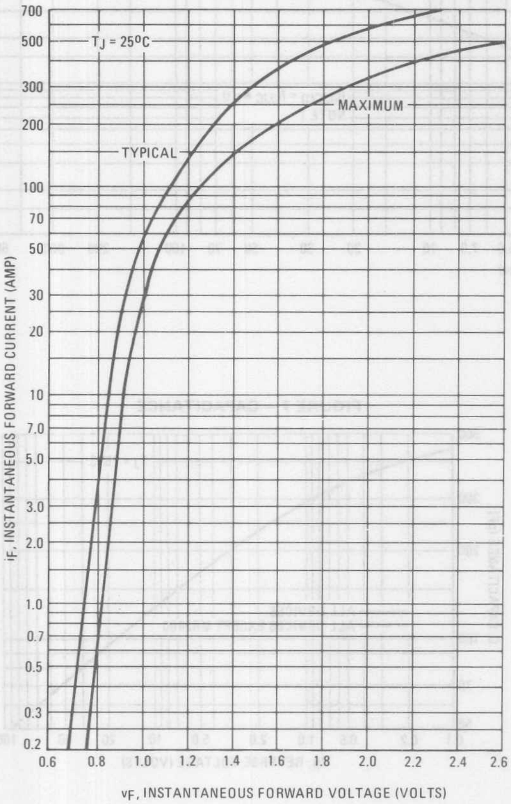


FIGURE 2 – NONREPETITIVE SURGE CURRENT

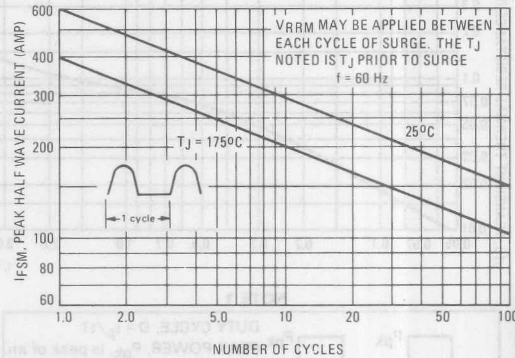


FIGURE 3 – FORWARD VOLTAGE TEMPERATURE COEFFICIENT

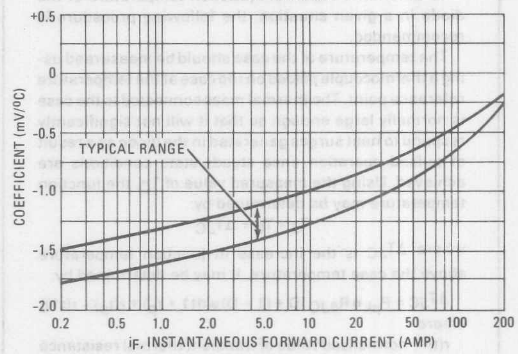


FIGURE 4 – CURRENT DERATING

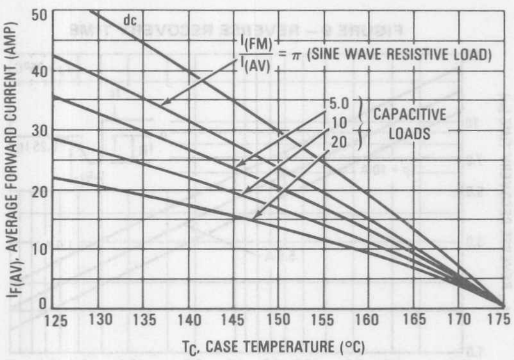


FIGURE 5 – FORWARD POWER DISSIPATION

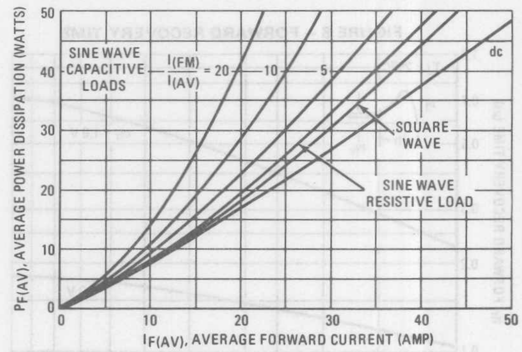
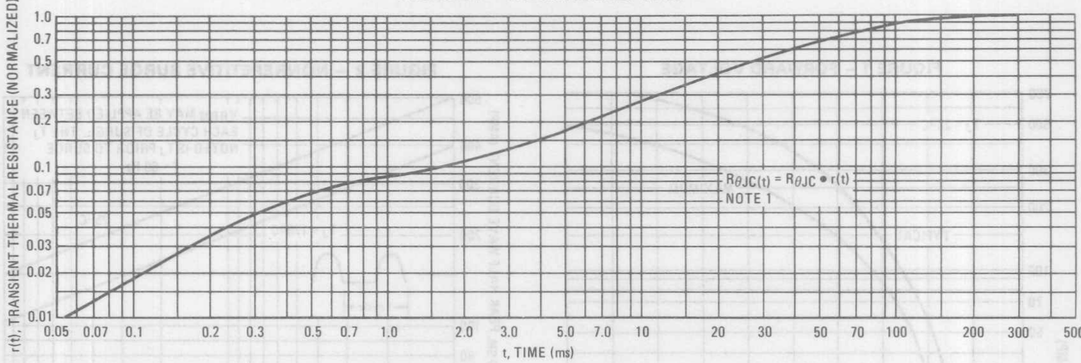
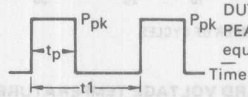


FIGURE 6 – THERMAL RESPONSE



NOTE 1



DUTY CYCLE, $D = t_p/t1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measureed using a thermocouple placed on the case at the temperature reference point. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC} \,[D + (1 - D) \bullet r(t1 + t_p) + r(t_p) - r(t1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t1 + t_p)$ = normalized value of transient thermal resistance at time $t1 + t_p$.

FIGURE 7 – CAPACITANCE

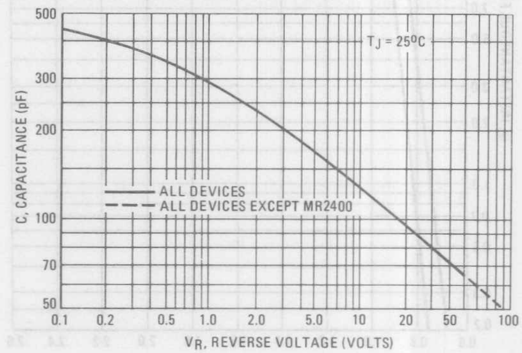


FIGURE 8 – FORWARD RECOVERY TIME

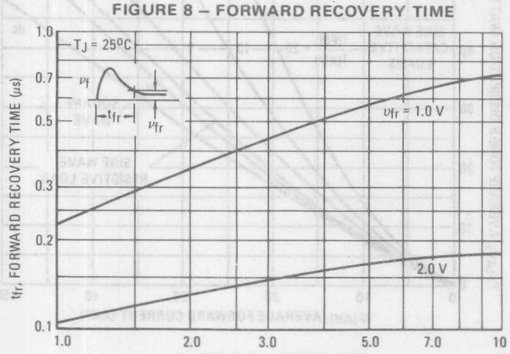


FIGURE 9 – REVERSE RECOVERY TIME

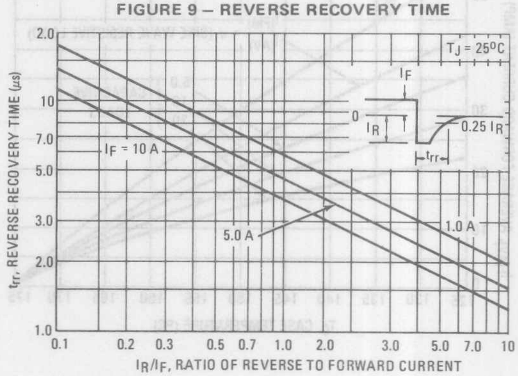
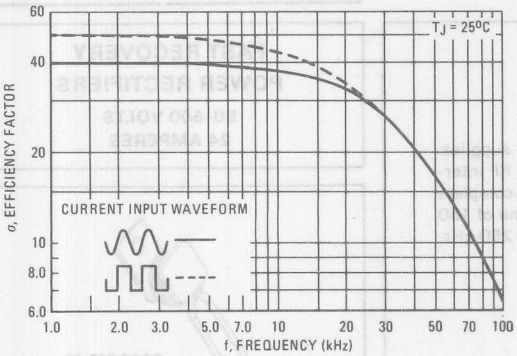
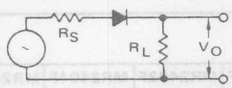


FIGURE 10 – RECTIFICATION WAVEFORM EFFICIENCY



RECTIFICATION EFFICIENCY NOTE



The rectification efficiency factor σ shown in Figure 10 was calculated using the formula:

$$\sigma = \frac{P_{dc}}{P_{rms}} = \frac{\dfrac{V^2{}_O(dc)}{R_L}}{\dfrac{V^2{}_O(rms)}{R_L}} \bullet 100\% = \frac{V^2{}_O(dc)}{V^2{}_O(ac) + V^2{}_O(dc)} \bullet 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assume lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{(sine)} = \frac{\dfrac{V^2{}_m}{\pi^2 R_L}}{\dfrac{V^2{}_m}{4R_L}} \bullet 100\% = \frac{4}{\pi^2} \bullet 100\% = 40.6\% \quad (2)$$

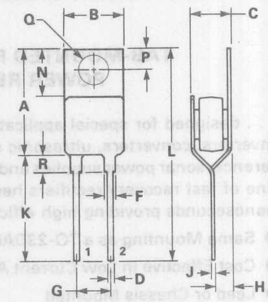
For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma_{(square)} = \frac{\dfrac{V^2{}_m}{2R_L}}{\dfrac{V^2{}_m}{R_L}} \bullet 100\% = 50\% \quad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 9) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 10.

It should be emphasized that Figure 10 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_O with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 10.



STYLE 1:
1. CATHODE
2. ANODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.22	15.88	0.560	0.625
B	9.65	10.67	0.380	0.420
C	7.21	7.87	0.284	0.310
D	0.64	1.14	0.025	0.045
F	1.52	2.29	0.060	0.090
G	4.32	5.33	0.170	0.210
H	2.03	2.92	0.080	0.115
J	0.58	0.74	0.023	0.029
K	—	14.27	—	0.562
L	—	30.15	—	1.187
N	5.84	6.86	0.230	0.270
P	2.54	3.05	0.100	0.120
Q	3.53	3.73	0.139	0.147
R	—	5.08	—	0.200

CASE 339-02
PLASTIC
(Meets TO-220AB except dimension "C")

3

3

TAB-MOUNTED FAST RECOVERY POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 250 kHz.

- Same Mounting as a TO-220AB
- Cost Effective in Low Current Applications
- Lead or Chassis Mounted
- High Surge Current Capability

FAST RECOVERY POWER RECTIFIERS

50-600 VOLTS
24 AMPERES

CASE 339-02
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MR2400F	MR2401F	MR2402F	MR2404F	MR2406F	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	75	150	250	450	650	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 125°C$)	I_O	← 24 →					Amp
Nonrepetitive Peak Surge Current (surge applied @ rated load conditions)	I_{FSM}	← 300 (for 1 cycle) →					Amp
Operating Junction Temperature Range	T_J	← −65 to +150 →					°C
Storage Temperature Range	T_{stg}	← −65 to +175 →					°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	°C/W
Thermal Resistance, Junction to Air, PC Board Mount; Perpendicular to Surface	$R_{\theta JA}$	55	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage ($I_F = 75$ Amp, $T_J = 150°C$)	v_F	—	1.15	1.29	Volts
Forward Voltage ($I_F = 24$ Amp, $T_C = 25°C$)	V_F	—	1.00	1.15	Volts
Reverse Current (rated dc voltage) $T_C = 25°C$ $T_C = 100°C$ $T_C = 150°C$	I_R	— — —	10 0.5 7.0	25 1.0 10	μA mA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Recover Time — Soft Recovery (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 19) (I_{FM} = 36 Amp, di/dt = 25 A/μs, Figure 20)	t_{rr}	— —	150 200	200 300	ns
Reverse Recovery Current (I_F = 1.0 Amp to V_R = 30 Vdc, Figure 19)	$I_{RM(REC)}$	—	—	4.0	Amp

FIGURE 1 — MAXIMUM FORWARD VOLTAGE

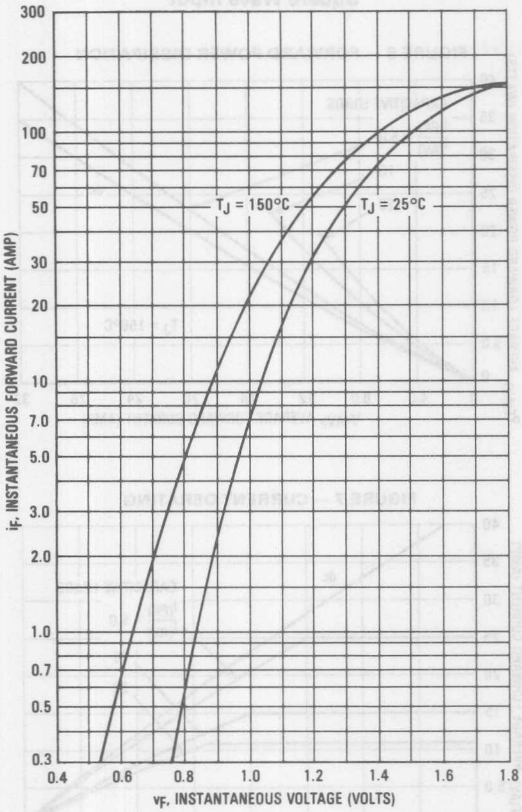
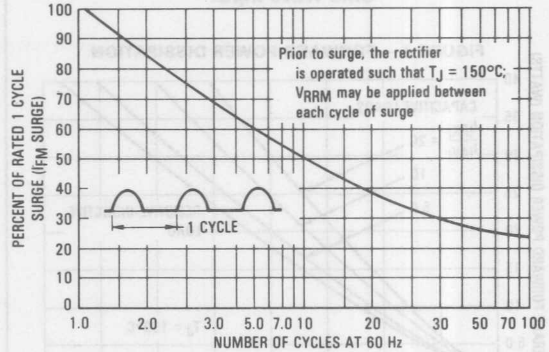
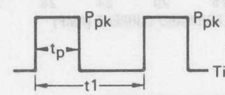


FIGURE 2 — MAXIMUM SURGE CAPABILITY



NOTE 1



DUTY CYCLE, $D = t_p/t1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measureed using a thermocouple placed on the case at the temperature reference point. The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

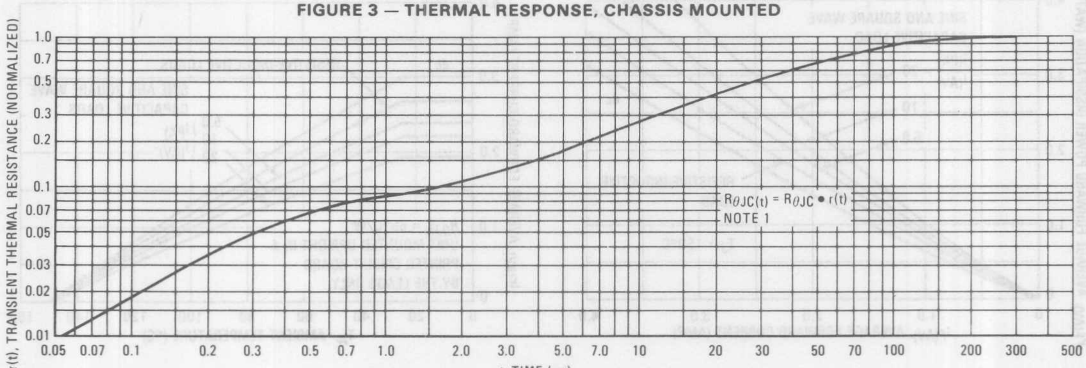
$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC} [D + (1 - D) \bullet r(t1 + t_p) + r(t_p) - r(t1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 3, i.e.:

$r(t1 + t_p)$ = normalized value of transient thermal resistance at time $t1 + t_p$.

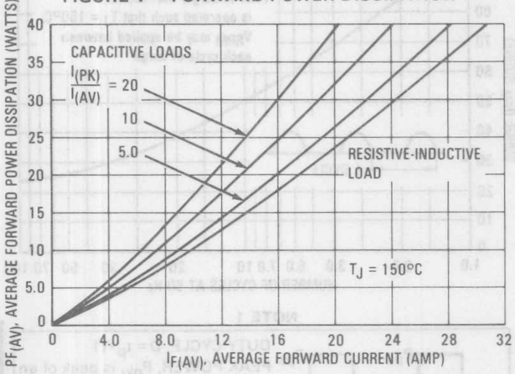
FIGURE 3 — THERMAL RESPONSE, CHASSIS MOUNTED



CHASSIS MOUNT RATING DATA

Sine Wave Input

FIGURE 4 — FORWARD POWER DISSIPATION



Square Wave Input

FIGURE 5 — FORWARD POWER DISSIPATION

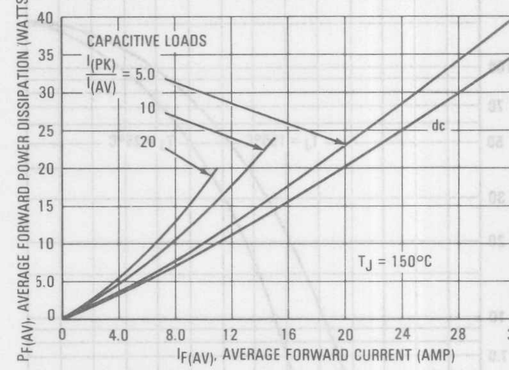


FIGURE 6 — CURRENT DERATING

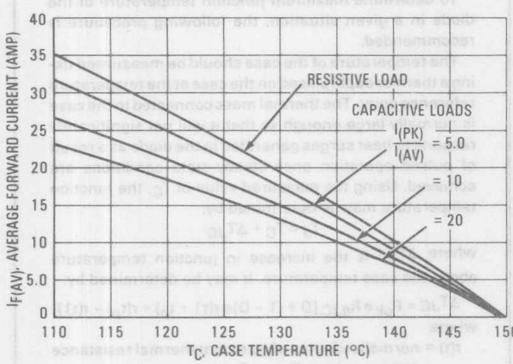
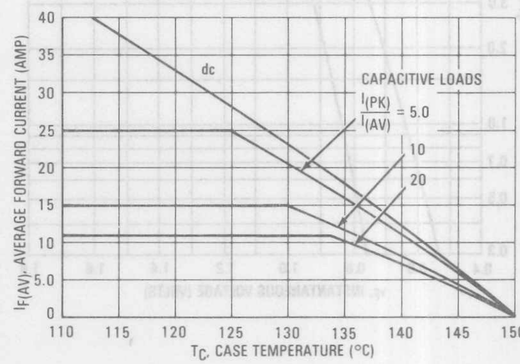


FIGURE 7 — CURRENT DERATING



PRINTED CIRCUIT BOARD RATING DATA

FIGURE 8 — FORWARD POWER DISSIPATION

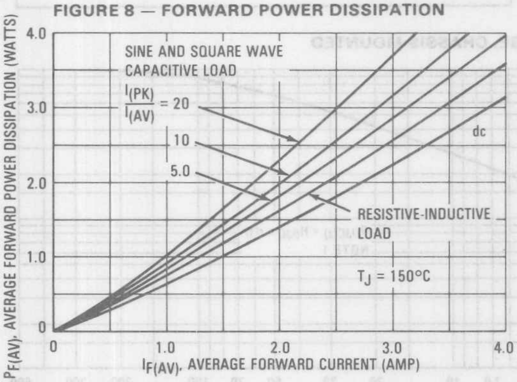
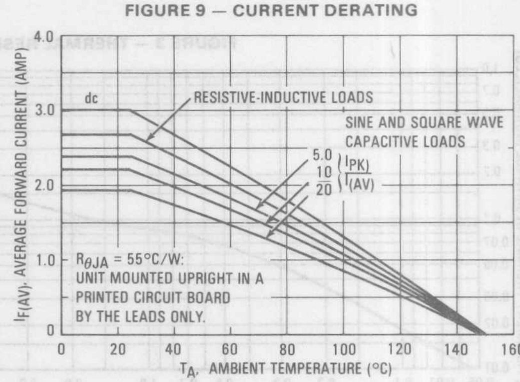


FIGURE 9 — CURRENT DERATING



TYPICAL DYNAMIC CHARACTERISTICS

FIGURE 10 — FORWARD RECOVERY TIME

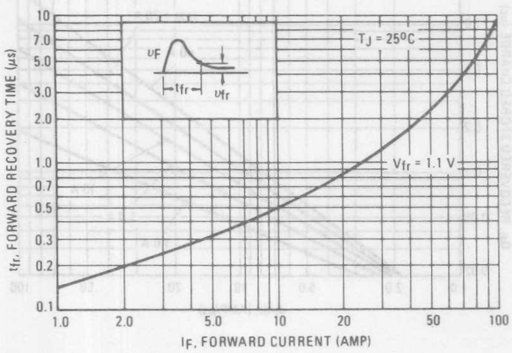


FIGURE 11 — JUNCTION CAPACITANCE

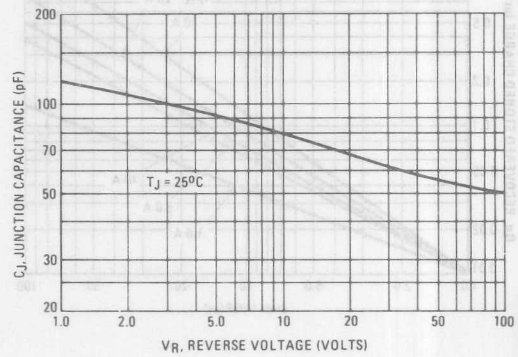


FIGURE 12 — TYPICAL REVERSE CURRENT

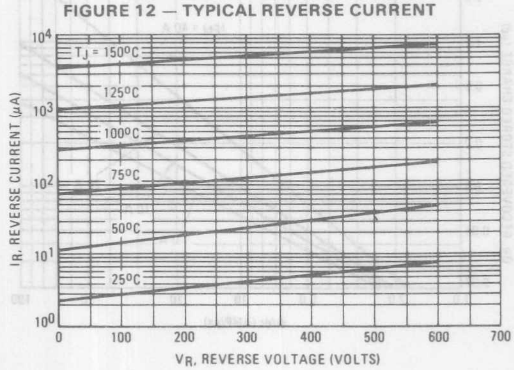
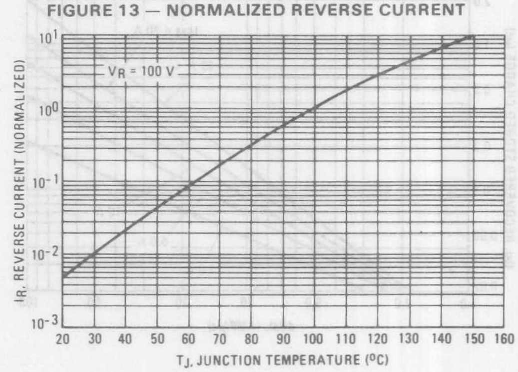
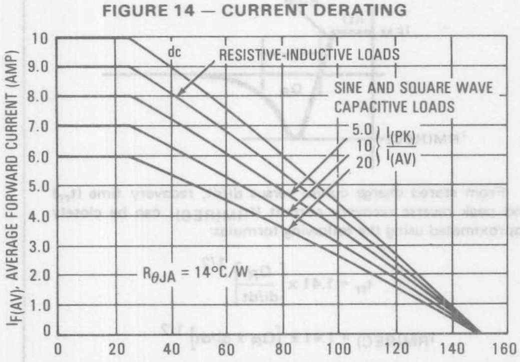


FIGURE 13 — NORMALIZED REVERSE CURRENT



TYPICAL MOUNTING DATA

FIGURE 14 — CURRENT DERATING



NOTE 2

Figure 14 shows the current carrying capability of a device mounted on a printed circuit board with a typical TO-220 type heatsink having a sink-to-air thermal resistance of 12°C/W. Allowing another 2°C/W for $R_{\theta JC}$ plus $R_{\theta CS}$ (case-to-sink) puts the total at 14°C/W as indicated. The unit and heatsink were mounted perpendicular to the printed circuit board for this data.

3

FIGURE 15 — $T_J = 25°C$

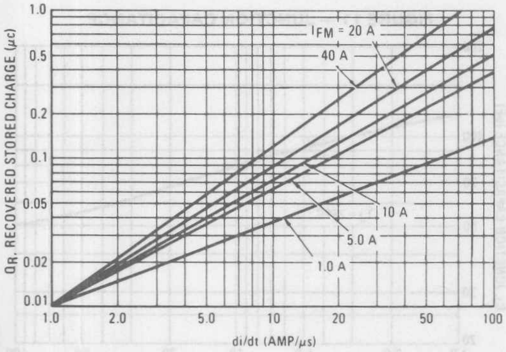
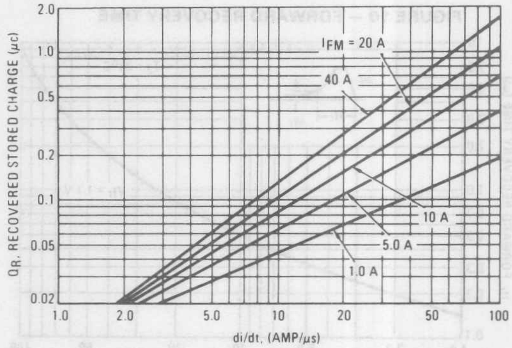


FIGURE 16 — $T_J = 75°C$



3

FIGURE 17 — $T_J = 100°C$

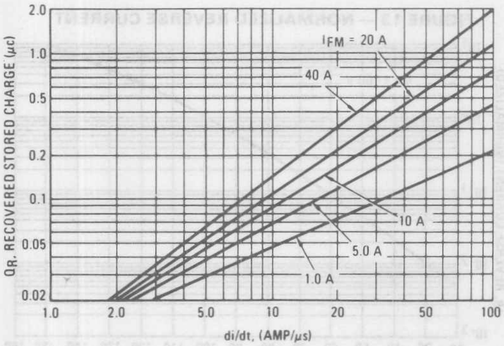
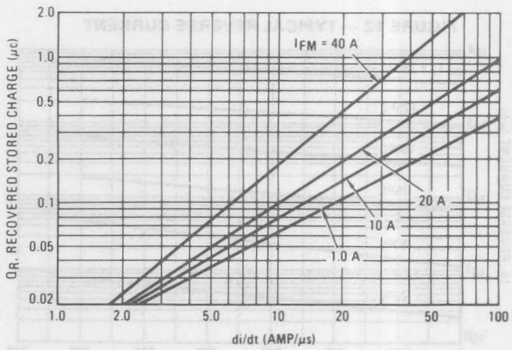


FIGURE 18 — $T_J = 150°C$



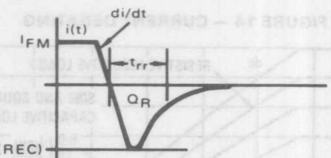
NOTE 3

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using I_F = 1.0 A, V_R = 30 V. In order to cover all circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of 25°C, 75°C, 100°C, and 150°C.

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.

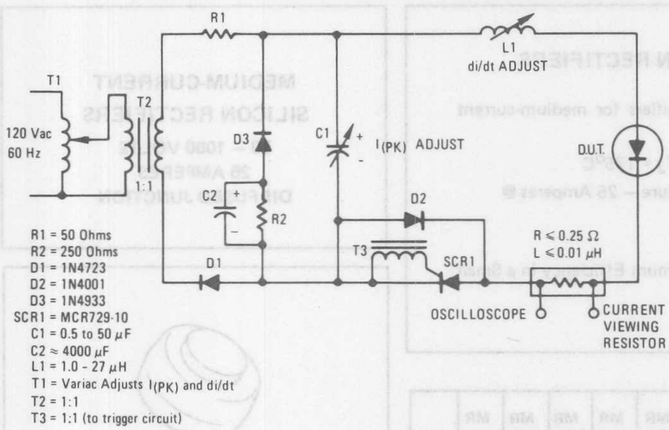


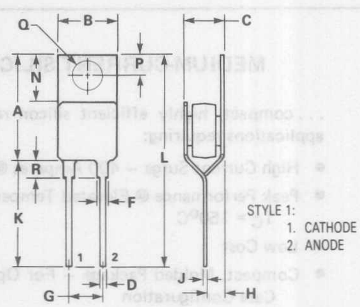
From stored charge curves versus di/dt, recovery time (t_{rr}) and peak reverse recovery current ($I_{RM(REC)}$) can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt}\right]^{1/2}$$

$$I_{RM(REC)} = 1.41 \times \left[Q_R \times di/dt\right]^{1/2}$$

FIGURE 19 — JEDEC REVERSE RECOVERY CIRCUIT

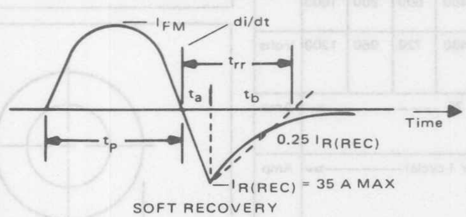




DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.22	15.88	0.560	0.625
B	9.65	10.67	0.380	0.420
C	7.21	7.87	0.284	0.310
D	0.64	1.14	0.025	0.045
F	1.52	2.29	0.060	0.090
G	4.32	5.33	0.170	0.210
H	2.03	2.92	0.080	0.115
J	0.58	0.74	0.023	0.029
K	—	14.27	—	0.562
L	—	30.15	—	1.187
N	5.84	6.86	0.230	0.270
P	2.54	3.05	0.100	0.120
Q	3.53	3.73	0.139	0.147
R	—	5.08	—	0.200

CASE 339-02
PLASTIC
(Meets TO-220AB except dimension "C")

FIGURE 20 — REVERSE RECOVERY CHARACTERISTIC



MECHANICAL CHARACTERISTICS

CASE: Plastic Encapsulated, Metal Tabs.

FINISH: All external surfaces are corrosion resistant and are readily solderable.

POLARITY: Cathode to Tab with hole; Reverse polarity available by adding "R" Suffix, MR2402FR.

WEIGHT: 3.6 Grams (Approximately).

MOUNTING TORQUE: 8 in-lbs max.

MAXIMUM TEMPERATURE FOR SOLDERING PURPOSES: 350°C, 3/8" from case for 10 seconds.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR2500 Series

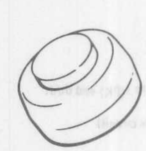
MEDIUM-CURRENT SILICON RECTIFIERS

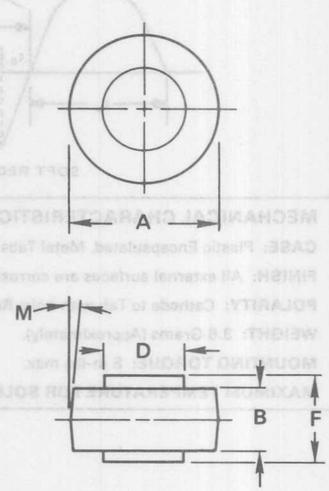
. . . compact, highly efficient silicon rectifiers for medium-current applications requiring:

- High Current Surge — 400 Amperes @ $T_J = 175^oC$
- Peak Performance @ Elevated Temperature — 25 Amperes @ $T_C = 150^oC$
- Low Cost
- Compact, Molded Package — For Optimum Efficiency in a Small Case Configuration
- Available With a Single Lead Attached

MEDIUM-CURRENT SILICON RECTIFIERS

50 — 1000 VOLTS
25 AMPERES
DIFFUSED JUNCTION





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.43	8.69	0.332	0.342
B	4.19	4.45	0.165	0.175
D	5.54	5.64	0.218	0.222
F	5.94	6.25	0.234	0.246
M	5° NOM		5° NOM	

CASE 193-04
PLASTIC

MAXIMUM RATINGS

Characteristic	Symbol	MR 2500	MR 2501	MR 2502	MR 2504	MR 2506	MR 2508	MR 2510	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	400	600	800	1000	Volts
Non-Repetitive Peak Reverse Voltage (halfwave, single phase, 60 Hz peak)	V_{RSM}	60	120	240	480	720	960	1200	Volts
Average Rectified Forward Current (Single phase, resistive load, 60 Hz, $T_C = 150^oC$)	I_O	←			25			→	Amp
Non-Repetitive Peak Surge Current (surge applied @ rated load conditions, half wave, single phase, 60 Hz)	I_{FSM}	←			400 (for 1 cycle)			→	Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	←			-65 to +175			→	^oC

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (Single Side Cooled)	$R_{\theta JC}$	1.0	$^oC/W$

ELECTRICAL CHARACTERISTICS

Characteristics and Conditions	Symbol	Max	Unit
Maximum Instantaneous Forward Voltage ($i_F = 78.5$ Amp, $T_C = 25^oC$)	v_F	1.18	Volts
Maximum Reverse Current (rated dc voltage) $T_C = 25^oC$ $T_C = 100^oC$	I_R	 100 500	μA

MECHANICAL CHARACTERISTICS

CASE: Transfer Molded Plastic

FINISH: All External Surfaces are Corrosion Resistant and the Contact Areas Readily Solderable.

POLARITY: Indicated by dot on Cathode Side

MOUNTING POSITIONS: Any

MAXIMUM TEMPERATURE FOR SOLDERING PURPOSES: 250^oC

WEIGHT: 1.8 Grams (Approximately)

FIGURE 1 — FORWARD VOLTAGE

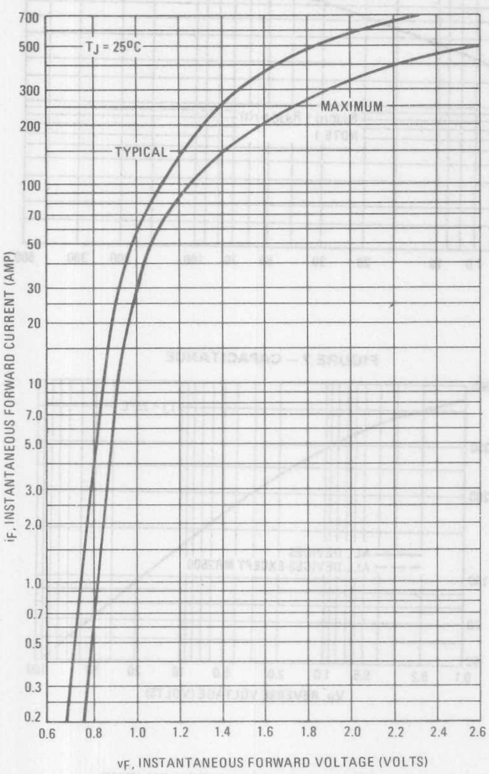


FIGURE 2 — NON-REPETITIVE SURGE CURRENT

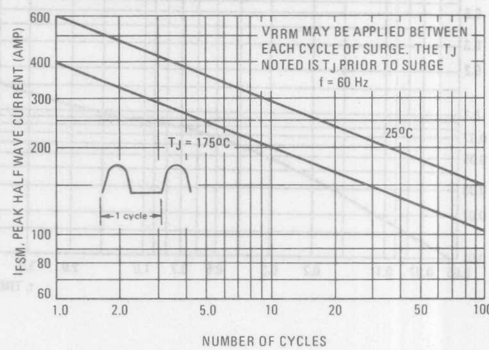


FIGURE 3 — FORWARD VOLTAGE TEMPERATURE COEFFICIENT

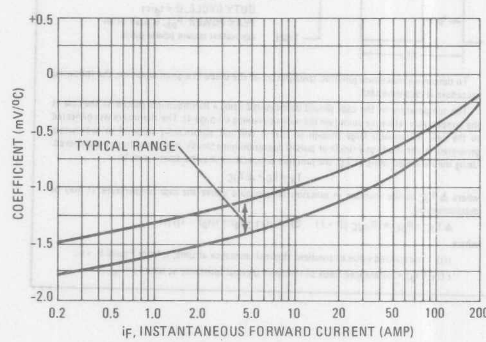


FIGURE 4 — CURRENT DERATING

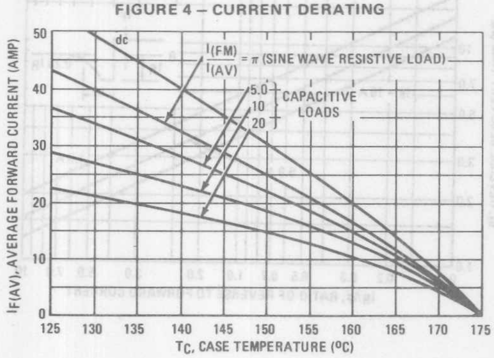


FIGURE 5 — FORWARD POWER DISSIPATION

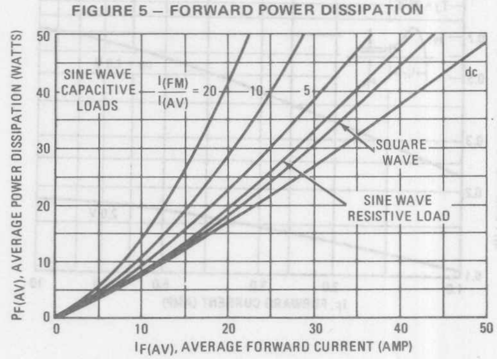
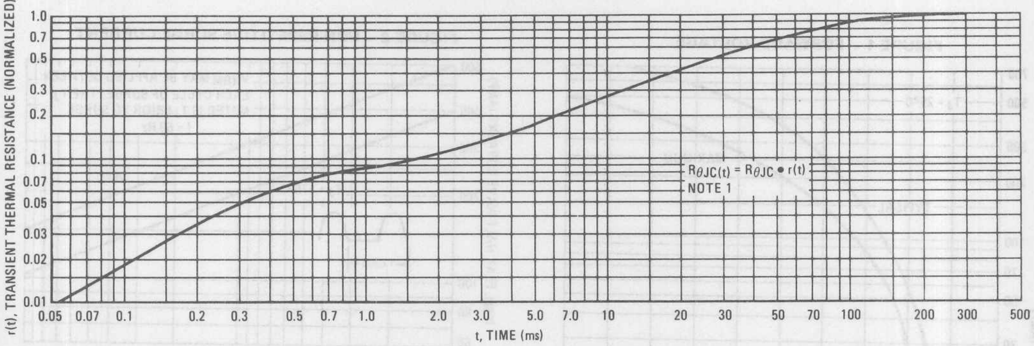
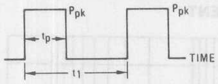


FIGURE 6 – THERMAL RESPONSE





DUTY CYCLE, $D = t_p/t_1$
PEAK POWER, P_{pk}, is peak of an equivalent square power pulse.

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended.

The temperature of the case should be measured using a thermocouple placed on the case at the temperature reference point (see the outline drawing on page 1). The thermal mass connected to the case is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}$$

where ΔT_{JC} is the increase in junction temperature above the case temperature. It may be determined by:

$$\Delta T_{JC} = P_{pk} \bullet R_{\theta JC} [D + (1 - D) \bullet r(t_1 + t_p) + r(t_p) - r(t_1)]$$

where

$r(t)$ = normalized value of transient thermal resistance at time, t, from Figure 6, i.e.,

$r(t_1 + t_p)$ = normalized value of transient thermal resistance at time $t_1 + t_p$.

FIGURE 7 – CAPACITANCE

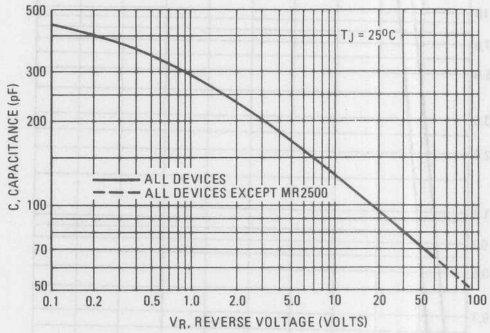


FIGURE 8 – FORWARD RECOVERY TIME

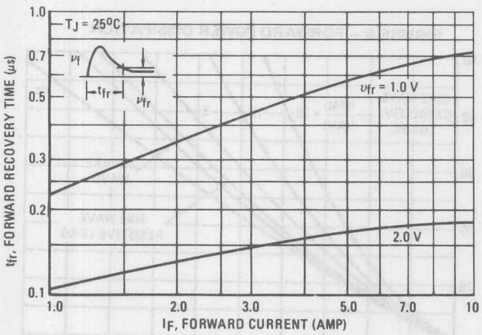


FIGURE 9 – REVERSE RECOVERY TIME

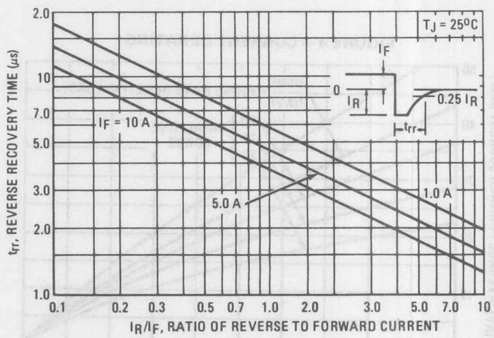
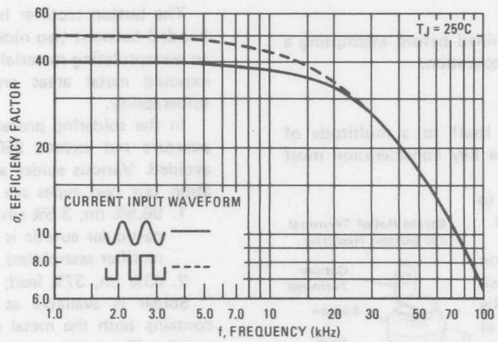
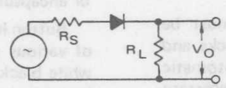


FIGURE 10 — RECTIFICATION WAVEFORM EFFICIENCY



RECTIFICATION EFFICIENCY NOTE

FIGURE 11 — SINGLE-PHASE HALF-WAVE RECTIFIER CIRCUIT



The rectification efficiency factor σ shown in Figure 10 was calculated using the formula:

$$\sigma = \frac{P_{dc}}{P_{rms}} = \frac{\frac{V^2_O(dc)}{R_L}}{\frac{V^2_O(rms)}{R_L}} \bullet 100\% = \frac{V^2_O(dc)}{V^2_O(ac) + V^2_O(dc)} \bullet 100\% \quad (1)$$

For a sine wave input $V_m \sin(\omega t)$ to the diode, assume lossless, the maximum theoretical efficiency factor becomes:

$$\sigma_{(sine)} = \frac{\frac{V^2_m}{\pi^2 R_L}}{\frac{V^2_m}{4R_L}} \bullet 100\% = \frac{4}{\pi^2} \bullet 100\% = 40.6\% \quad (2)$$

For a square wave input of amplitude V_m, the efficiency factor becomes:

$$\sigma_{(square)} = \frac{\frac{V^2_m}{2R_L}}{\frac{V^2_m}{R_L}} \bullet 100\% = 50\% \quad (3)$$

(A full wave circuit has twice these efficiencies)

As the frequency of the input signal is increased, the reverse recovery time of the diode (Figure 9) becomes significant, resulting in an increasing ac voltage component across R_L which is opposite in polarity to the forward current, thereby reducing the value of the efficiency factor σ, as shown on Figure 10.

It should be emphasized that Figure 10 shows waveform efficiency only; it does not provide a measure of diode losses. Data was obtained by measuring the ac component of V_O with a true rms ac voltmeter and the dc component with a dc voltmeter. The data was used in Equation 1 to obtain points for Figure 10.

ASSEMBLY AND SOLDERING INFORMATION

There are *two basic areas* of consideration for successful implementation of button rectifiers:

1. Mounting and Handling
2. Soldering

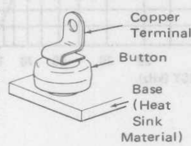
each should be carefully examined before attempting a finished assembly or mounting operation.

MOUNTING AND HANDLING

The button rectifier lends itself to a multitude of assembly arrangements but one key consideration must *always* be included:

One Side of the Connections to the Button Must Be Flexible!

Strain Relief Terminal for Button Rectifier



This stress relief to the button should also be chosen for maximum contact area to afford the best heat transfer – but not at the expense of flexibility. For an annealed copper terminal a thickness of 0.015" is suggested.

The base heat sink may be of various materials whose shape and size are a function of the individual application and the heat transfer requirements.

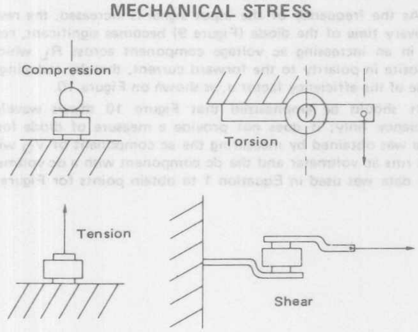
Common Materials	Advantages and Disadvantages
Steel	Low Cost; relatively low heat conductivity
Copper	High Cost; high heat conductivity
Aluminum	Medium Cost; medium heat conductivity Relatively expensive to plate and not all platers can process aluminum.

Handling of the button during assembly must be relatively gentle to minimize sharp impact shocks and avoid nicking of the plastic. Improperly designed automatic handling equipment is the worst source of unnecessary shocks. Techniques for vacuum handling and spring loading should be investigated.

The mechanical stress limits for the button diode are as follows:

Compression	32 lbs.	142.3 Newton
Tension	32 lbs.	142.3 Newton
Torsion	6-inch lbs.	0.68 Newton-meters
Shear	55 lbs.	244.7 Newton

MECHANICAL STRESS



Exceeding these recommended maximums can result in electrical degradation of the device.

SOLDERING

The button rectifier is basically a semiconductor chip bonded between two nickel-plated copper heat sinks with an encapsulating material of thermal-setting silicone. The exposed metal areas are also tin plated to enhance solderability.

In the soldering process it is important that the temperature not exceed 250°C if device damage is to be avoided. Various solder alloys can be used for this operation but two types are recommended for best results:

1. 96.5% tin, 3.5% silver; Melting point is 221°C (this particular eutetic is used by Motorola for its button rectifier assemblies).
2. 63% tin, 37% lead; Melting point 183°C (eutetic).

Solder is available as preforms or paste. The paste contains both the metal and flux and can be dispensed rapidly. The solder preform requires the application of a flux to assure good wetting of the solder. The type of flux used depends upon the degree of cleaning to be accomplished and is a function of the metals involved. These fluxes range from a mild rosin to a strong acid; e.g., Nickel plating oxides are best removed by an acid base flux while an activated rosin flux may be sufficient for tin plated parts.

Since the button is relatively light-weight, there is a tendency for it to float when the solder becomes liquid. To prevent bad joints and misalignment it is suggested that a weighting or spring loaded fixture be employed. It is also important that severe thermal shock (either heating or cooling) be avoided as it may lead to damage of the die or encapsulant of the part.

Button holding fixtures for use during soldering may be of various materials. Stainless steel has a longer use life while black anodized aluminum is less expensive and will limit heat reflection and enhance absorption. The assembly volume will influence the choice of materials. Fixture dimension tolerances for locating the button must allow for expansion during soldering as well as allowing for button clearance.

HEATING TECHNIQUES

The following four heating methods have their advantages and disadvantages depending on volume of buttons to be soldered.

1. **Belt Furnaces** readily handle large or small volumes and are adaptable to establishment of "on-line" assembly since a variable belt speed sets the run rate. Individual furnace zone controls make excellent temperature control possible.

2. **Flame Soldering** involves the directing of natural gas flame jets at the base of a heatsink as the heatsink is indexed to various loading-heating-cooling-unloading positions. This is the most economical labor method of soldering large volumes. Flame soldering offers good temperature control but requires sophisticated temperature monitoring systems such as infrared.

ASSEMBLY AND SOLDERING INFORMATION (continued)

3. **Ovens** are good for batch soldering and are production limited. There are handling problems because of slow cooling. Response time is load dependent, being a function of the watt rating of the oven and the mass of parts. Large ovens may not give an acceptable temperature gradient. Capital cost is low compared to belt furnaces and flame soldering.

4. **Hot Plates** are good for soldering small quantities of prototype devices. Temperature control is fair with overshoot common because of the exposed heating surface. Solder flow and positioning can be corrected during soldering since the assembly is exposed. Investment cost is very low.

Regardless of the heating method used, a soldering profile giving the time-temperature relationship of the particular method must be determined to assure proper soldering. Profiling must be performed on a scheduled basis to minimize poor soldering. The time-temperature relationship will change depending on the heating method used.

SOLDER PROCESS EVALUATION

Characteristics to look for when setting up the soldering process:

I **Overtemperature** is indicated by any one or all three of the following observations.
1. Remelting of the solder inside the button rectifier shows the temperature has exceeded 285^{o}C and is noted by "islands" of shiny solder and solder dewetting when a unit is broken apart.
2. Cracked die inside the button may be observed by a moving reverse oscilloscope trace when pressure is applied to the unit.
3. Cracked plastic may be caused by thermal shock as well as overtemperature so cooling rate should also be checked.

II **Cold soldering** gives a grainy appearance and solder build-up without a smooth continuous solder fillet. The temperature must be adjusted until the proper solder fillet is obtained within the maximum temperature limits.

III **Incomplete solder fillets** result from insufficient solder or parts not making proper contact.

IV **Tilted buttons** can cause a void in the solder between the heatsink and button rectifier which will result in poor heat transfer during operation. An eight degree tilt is a suggested maximum value.

V **Plating problems** require a knowledge of plating operations for complete understanding of observed deficiencies.

1. Peeling or plating separation is generally seen when a button is broken away for solder inspection. If heatsink or terminal base metal is present the plating is poor and must be corrected.
2. Thin plating allows the solder to penetrate through to the base metal and can give a poor connection. A suggested minimum plating thickness is 300 microinches.
3. Contaminated soldering surfaces may out-gas and cause non-wetting resulting in voids in the solder connection. The exact cause is not always readily apparent and can be because of:
   (a) improper plating
   (b) mishandling of parts
   (c) improper and/or excessive storage time

SOLDER PROCESS MONITORING

Continuous monitoring of the soldering process must be established to minimize potential problems. All parts used in the soldering operation should be sampled on a lot by lot basis by assembly of a controlled sample. Evaluate the control sample by break-apart tests to view the solder connections, by physical strength tests and by dimensional characteristics for part mating.

A shear test is a suggested way of testing the solder bond strength.

POST SOLDERING OPERATION CONSIDERATIONS

After soldering, the completed assembly must be unloaded, washed and inspected.

Unloading must be done carefully to avoid unnecessary stress. Assembly fixtures should be cooled to room temperature so solder profiles are not affected.

Washing is mandatory if an acid flux is used because of its ionic and corrosive nature. Wash the assemblies in agitated hot water and detergent for three to five minutes. After washing; rinse, blow off excessive water and bake 30 minutes at 150^{o}C to remove trapped moisture.

Inspection should be both electrical and physical. Any rejects can be reworked as required.

SUMMARY

The Button Rectifier is an excellent building block for specialized applications. The prime example of its use is the output bridge of the automotive alternator where millions are used each year. Although the material presented here is not all inclusive, primary considerations for use are presented. For further information, contact the nearest Motorola Sales Office or franchised distributor.

3

MR2535L
MR2540L

Advance Information

Overvoltage Transient Suppressors

MEDIUM CURRENT OVERVOLTAGE TRANSIENT SUPPRESSORS

. . . designed for applications requiring a low voltage rectifier with reverse avalanche characteristics for use as reverse power transient suppressors. Developed to suppress transients in the automotive system, these devices operate in the forward mode as standard rectifiers or reverse mode as power avalanche rectifier and will protect electronic equipment from overvoltage conditions.

- Avalanche Voltage 24 to 32 Volts
- High Power Capability
- Economical
- Increased Capacity by Parallel Operation
- Replaces MR2520L/2525L

CASE 194-01
MR2540L

CASE 194-04
MR2535L

MECHANICAL CHARACTERISTICS:

CASE: Transfer Molded Plastic
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 350°C 3/8″ from case for 10 seconds at 5 lbs. tension
FINISH: All external surfaces are corrosion-resistant, leads are readily solderable
POLARITY: Indicated by diode symbol or cathode band
WEIGHT: 2.5 Grams (approx.)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	20	Volts
Repetitive Peak Reverse Surge Current MR2535L MR2540L (Time Constant = 10 ms, Duty Cycle ≤ 1%, T_C = 25°C) (See Figure 1)	I_{RSM}	 110 150	Amps
Average Rectified Forward Current (Single Phase, Resistive Load, 60 Hz, T_C = 150°C) MR2535L MR2540L	I_O	 35 50	Amps
Non-Repetitive Peak Surge Current Surge Supplied at Rated Load Conditions Halfwave, Single Phase MR2535L MR2540L	I_{FSM}	 600 800	Amps
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

THERMAL CHARACTERISTICS

Characteristic	Lead Length	Symbol	Max	Unit
Thermal Resistance, Junction to Lead @ Both Leads to Heat Sink, Equal Length	1/4″ 3/8″ 1/2″	$R_{\theta JL}$	7.5 10 13	°C/W
Thermal Resistance Junction to Case		$R_{\theta JC}$	0.8*	°C/W

*Typical

This document contains information on a new product. Specifications and information herein are subject to change without notice.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Max	Unit
Instantaneous Forward Voltage (1) (i_F = 100 Amps, T_C = 25°C)	v_F	—	1.05	Volts
Reverse Current (V_R = 20 Vdc, T_C = 25°C)	I_R	—	200	nAdc
Breakdown Voltage (1) (I_R = 100 mAdc, T_C = 25°C)	$V_{(BR)}$	24	32	Volts
Breakdown Voltage (1) MR2535L only (I_R = 90 Amp, T_C = 150°C, PW = 80 μs)	$V_{(BR)}$	—	40	Volts
Breakdown Voltage Temperature Coefficient	$V_{(BR)TC}$	—	0.096*	%/°C
Forward Voltage Temperature Coefficient @ I_F = 10 mA	V_{FTC}	—	2*	mV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
* Typical.

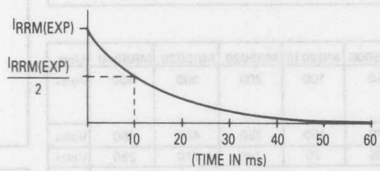
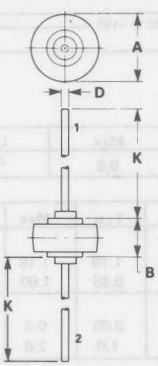


Figure 1. Surge Current Characteristics

OUTLINE DIMENSIONS



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.03	10.29	0.395	0.405
B	5.94	6.25	0.234	0.246
D	1.27	1.35	0.050	0.053
K	25.15	25.65	0.990	1.010

CASE 194-01
MR2540L

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.43	8.69	0.332	0.342
B	5.94	6.25	0.234	0.246
D	1.27	1.35	0.050	0.053
K	25.15	25.65	0.990	1.010

CASE 194-04
MR2535L

STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTE:
1. CATHODE SYMBOL ON PKG

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR5005 MR5010 MR5020 MR5030 MR5040

INDUSTRIAL PRESSFIT SILICON POWER RECTIFIERS

. . . designed for use in all medium-current applications or for higher current industrial alternators and chassis mounted power supply rectifiers.

- 50 Amp @ $T_C = 150^{\circ}C$
- 600 Amp Surge Capability
- Reverse Polarity Available
- Rugged Construction

SILICON POWER RECTIFIERS

50-400 VOLTS
50 AMPERE

3

MAXIMUM RATINGS

Rating	Symbol	MR5005	MR5010	MR5020	MR5030	MR5040	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	200	300	400	Volts
Non-Repetitive Peak Reverse Voltage	V_{RSM}	75	150	250	400	450	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	35	70	140	210	280	Volts
Average Rectified Forward Current (Single phase, resistive load, $T_C = 150^{\circ}C$	I_O	← 50 →					Amp
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	I_{FSM}	← 600 →					Amp
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +195 →					$^{\circ}C$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typ	Max	Unit
Instantaneous Forward Voltage	v_F				Volts
(i_F = 157 Amp, $T_J = 25^{\circ}C$)		–	1.10	1.18	
(i_F = 50 Amp, $T_J = 25^{\circ}C$)		–	0.95	1.00	
Reverse Current (rated dc voltage)	I_R				mA
($T_C = 25^{\circ}C$)		–	0.05	0.2	
($T_C = 150^{\circ}C$)		–	1.0	2.0	

MECHANICAL CHARACTERISTICS

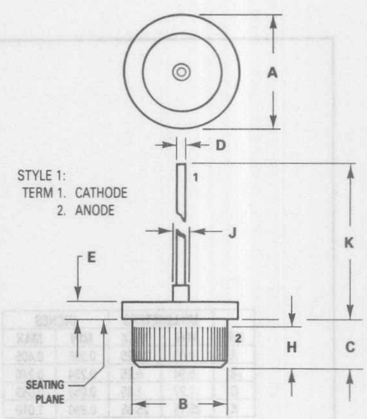
CASE: Welded hermetically sealed construction

FINISH: All external surfaces corrosion resistant, terminals readily solerable

WEIGHT: 9 grams (approx.)

POLARITY: Cathode connected to case (reverse polarity available denoted by Suffix R, i.e.: MR5030R)

MOUNTING POSITION: Any



NOTES:
1. 50 TPI STRAIGHT KNURL.
2. POLARITY, INK MARKED ON PACKAGE.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.49	16.26	0.610	0.640
B	12.73	12.83	0.501	0.505
C	5.08	6.35	0.200	0.250
D	2.46	2.62	0.097	0.103
E	2.03	4.83	0.080	0.190
H	5.08	6.35	0.200	0.250
J	–	3.56	–	0.140
K	–	15.24	–	0.600

CASE 43-04
METAL

FIGURE 1 – CURRENT DERATING

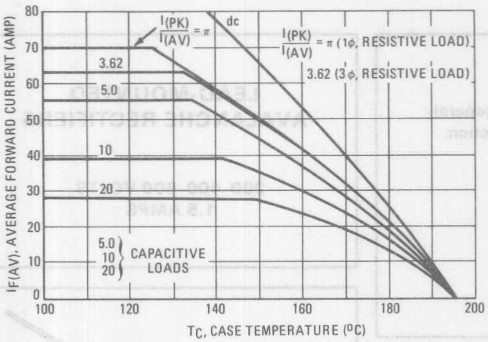


FIGURE 2 – FORWARD POWER DISSIPATION

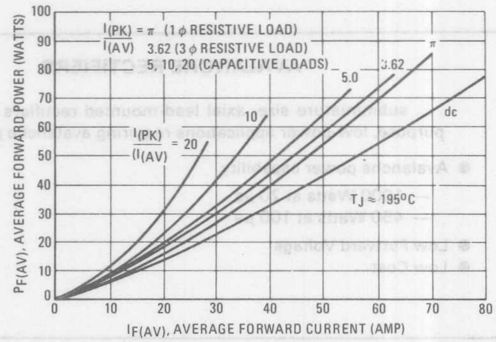


FIGURE 3 – MAXIMUM FORWARD VOLTAGE

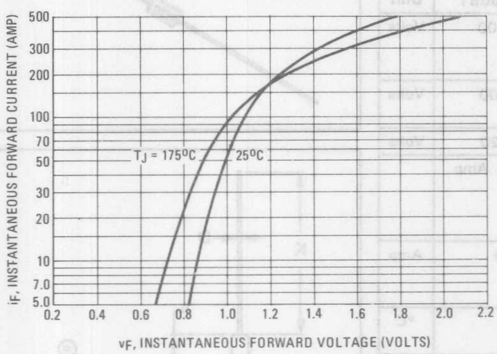


FIGURE 4 – MAXIMUM NON-REPETITIVE SURGE CAPABILITY

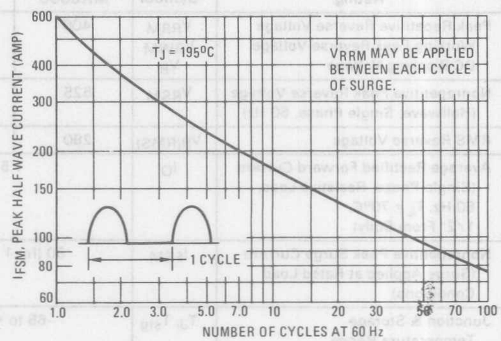
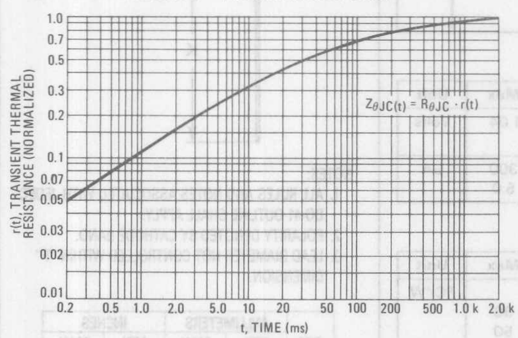
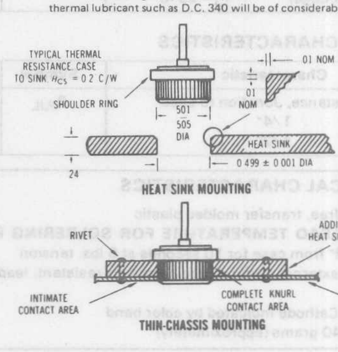


FIGURE 5 – THERMAL RESPONSE



Recommended procedures for mounting are as follows:

1. Drill a hole in the heat sink 0.499 ± 0.001 inch in diameter.
2. Break the hole edge as shown to provide a guide into the hole and prevent shearing off the knurled side of the rectifier.
3. The depth and width of the break should be 0.010 inch maximum to retain maximum heat sink surface contact.
4. To prevent damage to the rectifier during press-in, the pressing force should be applied only on the shoulder ring of the rectifier case as shown.
5. The pressing force should be applied evenly about the shoulder ring to avoid tilting or canting of the rectifier case in the hole during the press-in operation. Also, the use of a thermal lubricant such as D.C. 340 will be of considerable aid.



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MR5060
MR5061

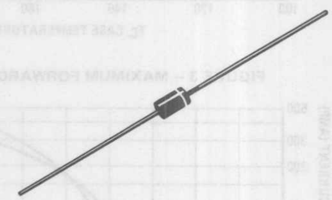
AVALANCHE RECTIFIERS

. . . subminiature size, axial lead-mounted rectifiers for general-purpose, low-power applications requiring avalanche protection.

- Avalanche power capability
  - — 1000 Watts at 20 μs
  - — 450 Watts at 100 μs
- Low Forward Voltage
- Low Cost

LEAD-MOUNTED AVALANCHE RECTIFIERS

200-400-600 VOLTS
1.5 AMPS



3

MAXIMUM RATINGS

Rating	Symbol	MR5060	MR5061	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	400	600	Volts
Nonrepetitive Peak Reverse Voltage (Halfwave, Single Phase, 60 Hz)	V_{RSM}	525	800	Volts
RMS Reverse Voltage	$V_{R(RMS)}$	280	420	Volts
Average Rectified Forward Current (Single Phase, Resistive Load, 60 Hz, T_L = 70°C, 1/2″ From Body)	I_O	1.5		Amp
Nonrepetitive Peak Surge Current (Surge Applied at Rated Load Conditions)	I_{FSM}	50 (for 1 cycle)		Amp
Junction & Storage Temperature Range	T_J, T_{stg}	-65 to +175		°C
Nonrepetitive Peak Reverse Surge Power (t = 20 μs)	P_{RM}	1000		Watts

ELECTRICAL CHARACTERISTICS

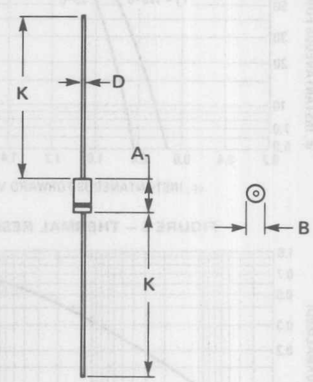
Characteristic and Conditions	Symbol	Typ	Max	Unit
Instantaneous Forward Voltage (i_f = 1.5 Amp, T_J = 25°C)	V_F	0.93	1.04	Volts
Reverse Current (Rated dc Voltage) T_J = 150°C T_J = 25°C	I_R	250 3.0	300 5.0	μA

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction to Lead 1/4″ 1/2″	$R_{\theta JL}$	 21 31	 38 50	°C/W

MECHANICAL CHARACTERISTICS

CASE: Void free, transfer molded plastic
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 240°C, 1/8″ from case for 10 seconds at 5 lbs. tension
FINISH: All external surfaces are corrosion-resistant, leads are readily solderable
POLARITY: Cathode indicated by color band
WEIGHT: 0.40 grams (approximately)



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04
PLASTIC

Dimensions Within JEDEC DO-15 Outline.

FIGURE 1 — FORWARD VOLTAGE

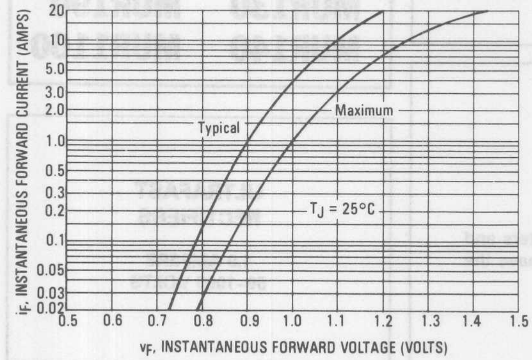


FIGURE 2 — MAXIMUM NON-REPETITIVE AVALANCHE SURGE POWER

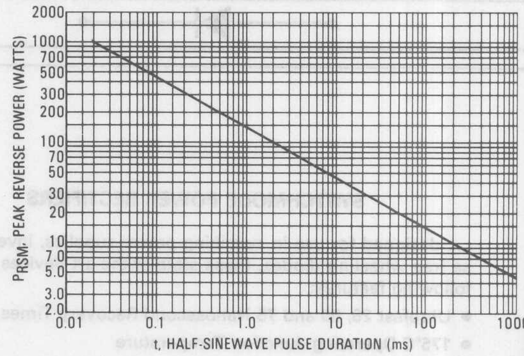


FIGURE 3 — POWER DISSIPATION

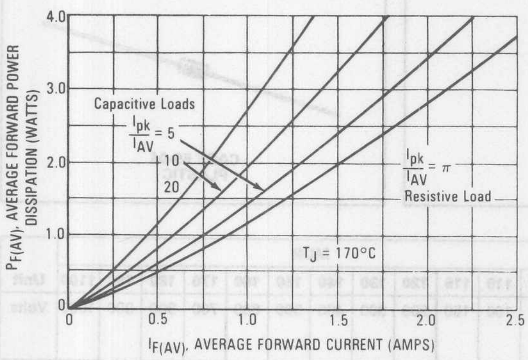


FIGURE 4 — EFFECT OF LEAD LENGTHS, RESISTIVE LOAD

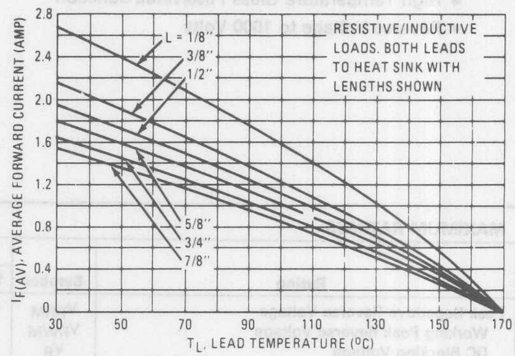
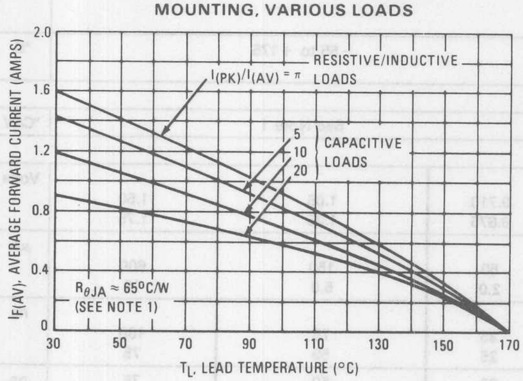


FIGURE 5 — PRINTED CIRCUIT BOARD MOUNTING, VARIOUS LOADS

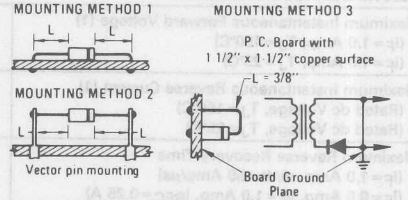


NOTE 1

Data shown for thermal resistance junction-to-ambient (θ_{JA}) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR θ_{JA} IN STILL AIR

MOUNTING METHOD	LEAD LENGTH, L (IN) 1/8	1/4	1/2	3/4	$R_{\theta JA}$
1	65	72	82	92	°C/W
2	74	81	91	101	°C/W
3		40			°C/W



MUR120 MUR180
MUR130 MUR190
MUR140 MUR1100

SWITCHMODE POWER RECTIFIERS

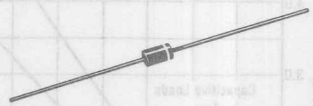
. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 25, 50 and 75 Nanosecond Recovery Times
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

3

ULTRAFAST RECTIFIERS

1.0 AMPERE
50–1000 VOLTS



CASE 59-04
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MUR 105	110	115	120	130	140	150	160	170	180	190	1100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	700	800	900	1000	Volts
Average Rectified Forward Current (Square Wave Mounting Method #3 Per Note 1)	$I_{F(AV)}$	1.0 @ T_A = 130°C			1.0 @ T_A = 120°C					1.0 @ T_A = 95°C				Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, single phase, 60 Hz)	I_{FSM}	35												Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	−65 to +175												°C

THERMAL CHARACTERISTICS

Rating	Symbol	MUR 105–1100	Unit
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	See Note 1	°C/W

ELECTRICAL CHARACTERISTICS

Rating	Symbol	MUR 105–115	MUR 120–160	MUR 170–1100	Unit
Maximum Instantaneous Forward Voltage (1) (i_F = 1.0 Amp, T_J = 150°C) (i_F = 1.0 Amp, T_J = 25°C)	v_F	 0.710 0.875	 1.05 1.25	 1.50 1.75	Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_J = 150°C) (Rated dc Voltage, T_J = 25°C)	i_R	 50 2.0	 150 5.0	 600 10	μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 A)	t_{rr}	 35 25	 75 50	 100 75	ns
Maximum Forward Recovery Time (I_F = 1.0 A, di/dt = 100 A/μs, I_{REC} to 1.0 V)	t_{fr}	25	50	75	ns

(1)Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%

MUR105, 110 AND 115

FIGURE 1 — TYPICAL FORWARD VOLTAGE

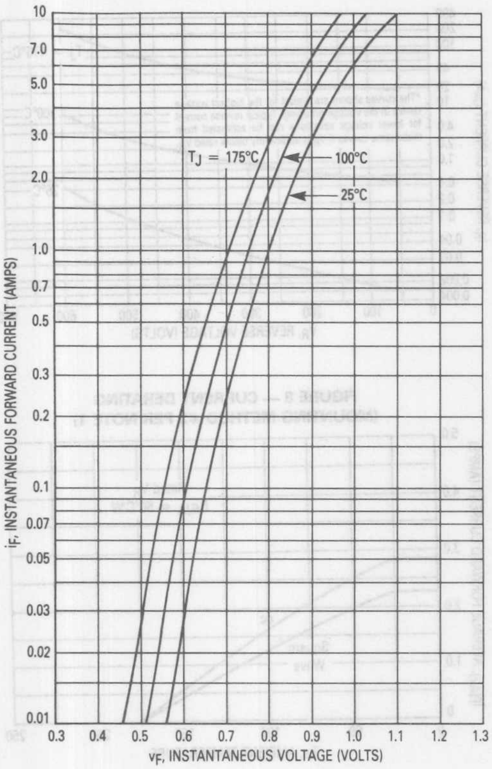


FIGURE 2 — TYPICAL REVERSE CURRENT*

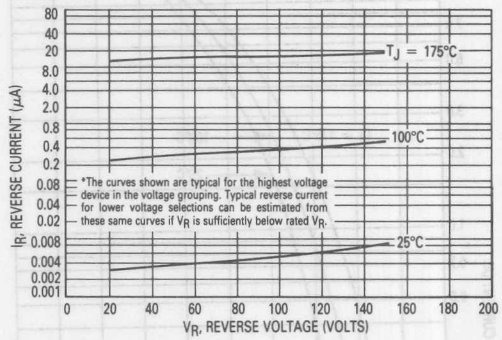


FIGURE 3 — CURRENT DERATING
(MOUNTING METHOD #3 PER NOTE 1)

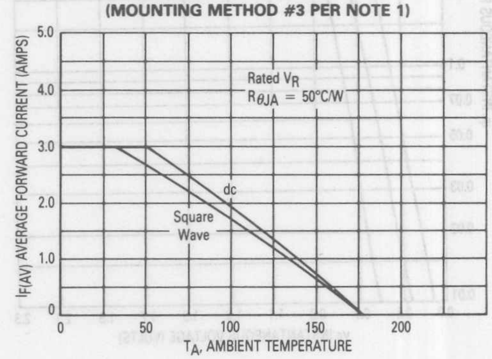


FIGURE 4 — POWER DISSIPATION

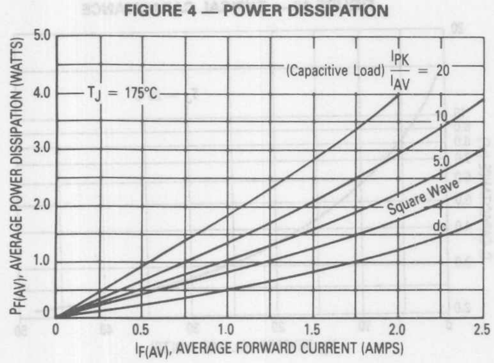
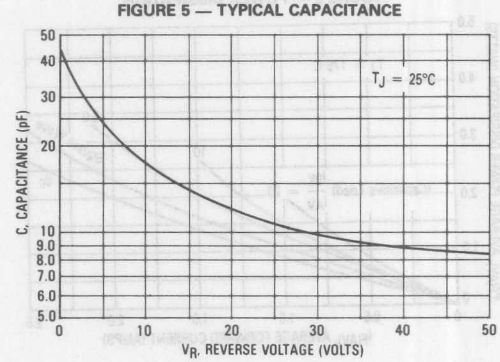


FIGURE 5 — TYPICAL CAPACITANCE



3

MUR120, 130, 140, 150, 160

FIGURE 6 — TYPICAL FORWARD VOLTAGE

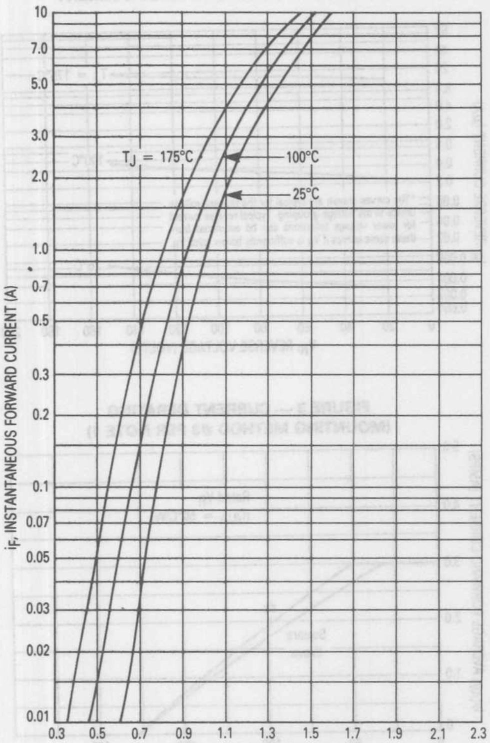


FIGURE 7 — TYPICAL REVERSE CURRENT*

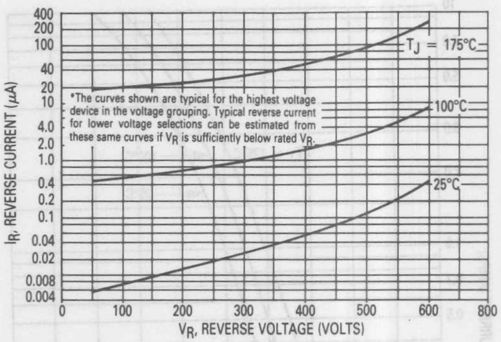


FIGURE 8 — CURRENT DERATING
(MOUNTING METHOD #3 PER NOTE 1)

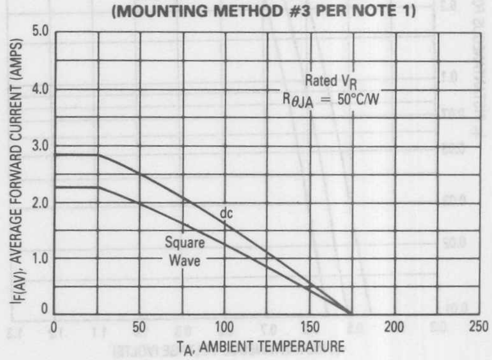


FIGURE 9 — POWER DISSIPATION

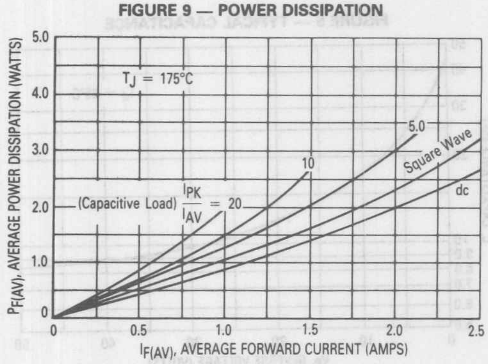


FIGURE 10 — TYPICAL CAPACITANCE

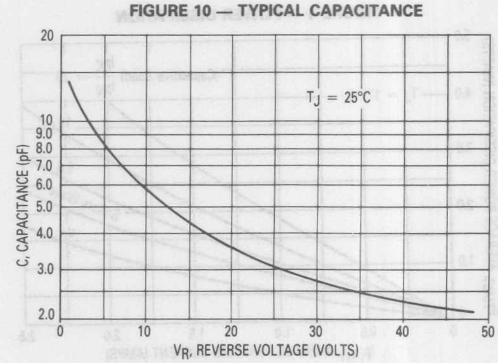


FIGURE 11 — TYPICAL FORWARD VOLTAGE

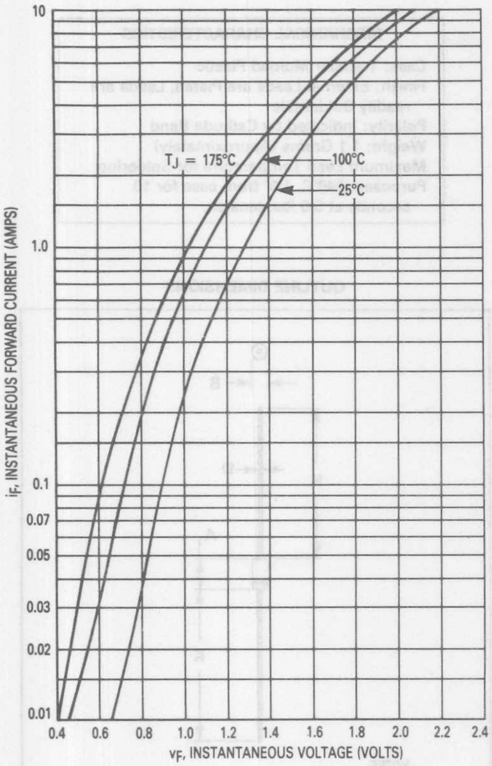
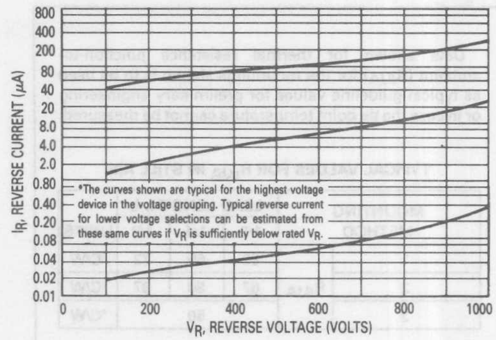


FIGURE 12 — TYPICAL REVERSE CURRENT*



3

FIGURE 13 — CURRENT DERATING (MOUNTING METHOD #3 PER NOTE 1)

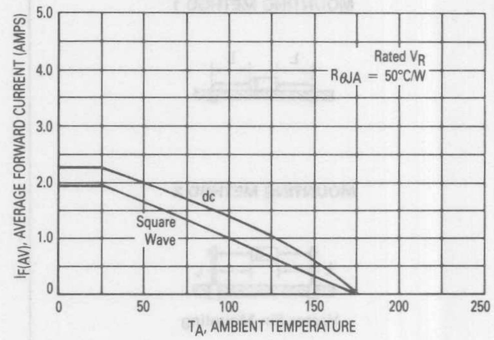


FIGURE 14 — POWER DISSIPATION

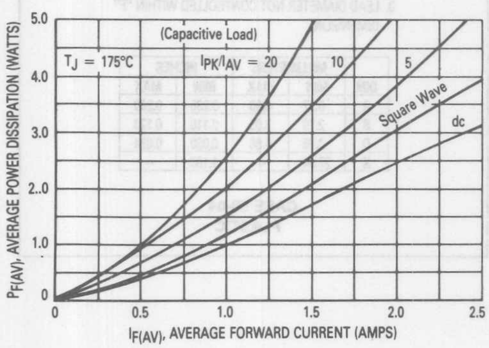
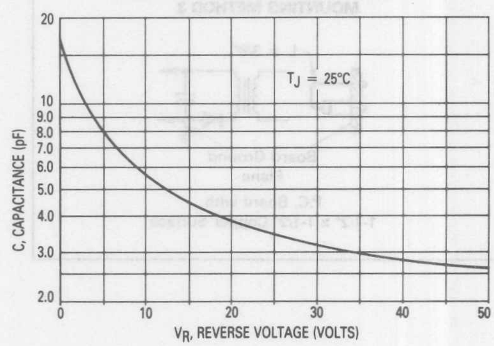


FIGURE 15 — TYPICAL CAPACITANCE

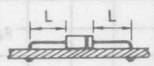


Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

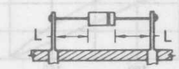
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

MOUNTING METHOD		LEAD LENGTH, L 1/8	1/4	1/2	UNITS
1	$R_{\theta JA}$	52	65	72	°C/W
2		67	80	87	°C/W
3			50		°C/W

MOUNTING METHOD 1

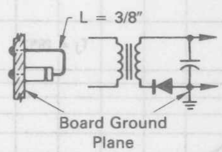


MOUNTING METHOD 2



Vector Pin Mounting

MOUNTING METHOD 3

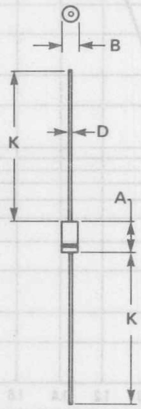


P.C. Board with
1-1/2″ x 1-1/2″ Copper Surface

MECHANICAL CHARACTERISTICS

Case: Transfer Molded Plastic
Finish: External Leads are Plated, Leads are readily Solderable
Polarity: Indicated by Cathode Band
Weight: 1.1 Grams (Approximately)
Maximum Lead Temperature for Soldering Purposes: 240°C, 1/8″ from case for 10 seconds at 5.0 lbs. tension.

OUTLINE DIMENSIONS



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MAX	INCHES MIN	MAX
A	5.97	6.60	0.235	0.260
B	2.79	3.05	0.110	0.120
D	0.76	0.86	0.030	0.034
K	27.94	—	1.100	—

CASE 59-04
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR405 MUR450 MUR410 MUR460 MUR415 MUR470 MUR420 MUR480 MUR430 MUR490 MUR440 MUR4100

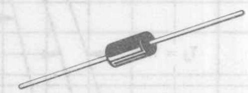
SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 25, 50 and 75 Nanosecond Recovery Times
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

ULTRAFAST RECTIFIERS

4.0 AMPERES
50–1000 VOLTS



CASE 267-02
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MUR 405	410	415	420	430	440	450	460	470	480	490	4100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	700	800	900	1000	Volts
Average Rectified Forward Current (Square Wave) (Mounting Method #3 Per Note 1)	$I_{F(AV)}$		4.0 @ T_A = 80°C				4.0 @ T_A = 40°C				4.0 @ T_A = 35°C			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}		125				70							Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}						−65 to +175							°C
THERMAL CHARACTERISTICS														
Maximum Thermal Resistance, Junction to Ambient	$R_{\theta JA}$						See Note 1							°C/W
ELECTRICAL CHARACTERISTICS														
Maximum Instantaneous Forward Voltage (1) (i_F = 3.0 Amp, T_J = 150°C) (i_F = 3.0 Amp, T_J = 25°C) (i_F = 4.0 Amp, T_J = 25°C)	v_F		 0.710 0.875 0.890				 1.05 1.25 1.28				 1.53 1.75 1.85			Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_J = 150°C) (Rated dc Voltage, T_J = 25°C)	i_R		 150 5.0				 250 10				 900 25			μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 Amp)	t_{rr}		 35 25				 75 50				 100 75			ns
Maximum Forward Recovery Time (I_F = 1.0 A, di/dt = 100 A/μs, Recovery to 1.0 V)	t_{fr}		25				50				75			ns

(1)Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%

MUR405, 410 AND 415

FIGURE 1 — TYPICAL FORWARD VOLTAGE

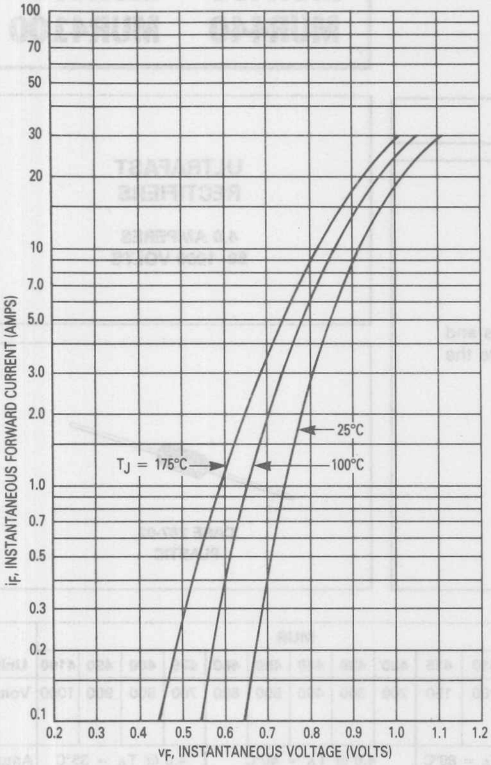


FIGURE 2 — TYPICAL REVERSE CURRENT*

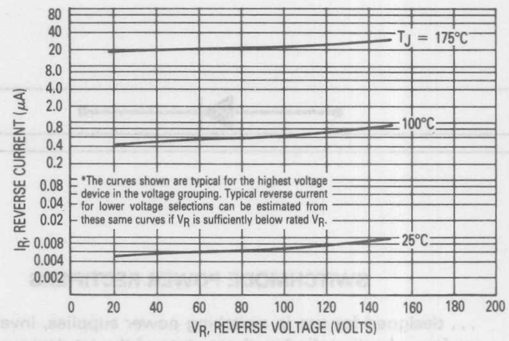


FIGURE 3 — CURRENT DERATING
(MOUNTING METHOD #3 PER NOTE 1)

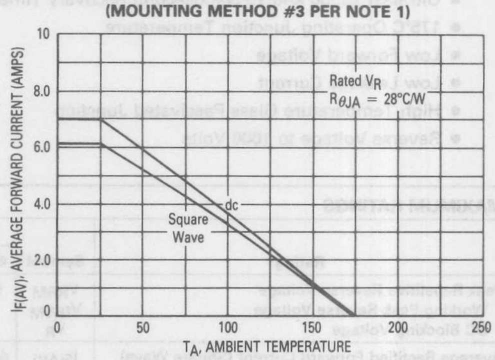


FIGURE 4 — POWER DISSIPATION

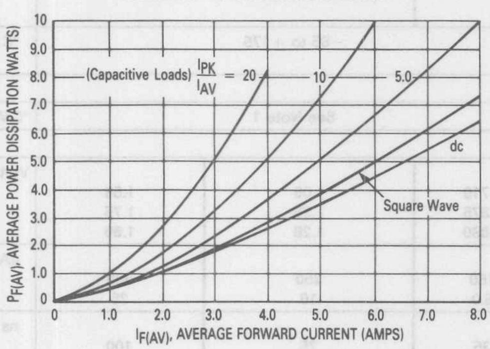
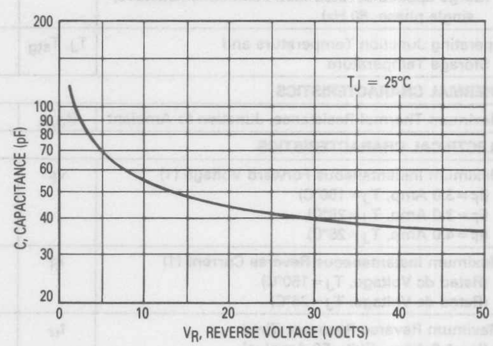


FIGURE 5 — TYPICAL CAPACITANCE



3

MUR420, 430, 440, 450 AND 460

FIGURE 6 — TYPICAL FORWARD VOLTAGE

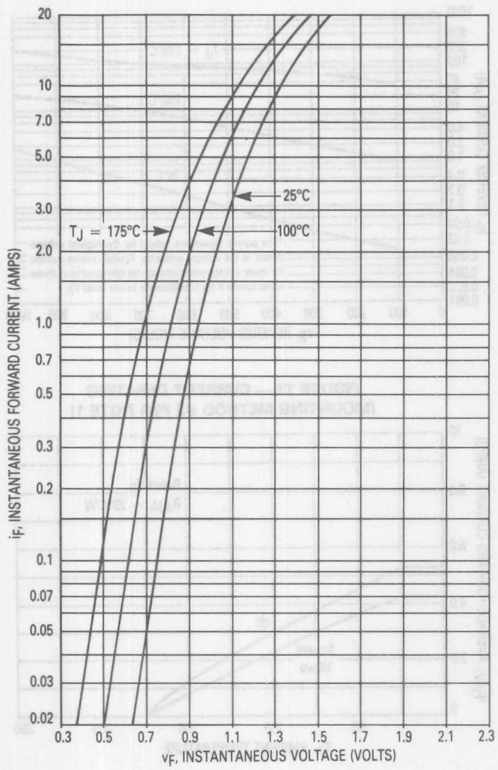


FIGURE 7 — TYPICAL REVERSE CURRENT*

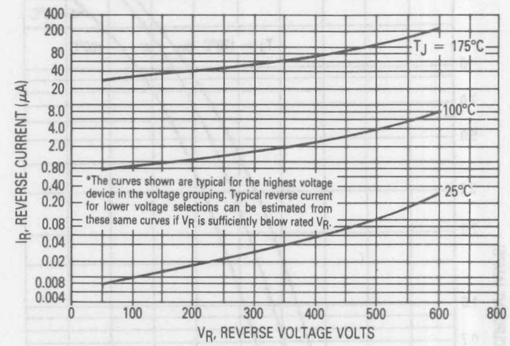


FIGURE 8 — CURRENT DERATING (MOUNTING METHOD #3 PER NOTE 1)

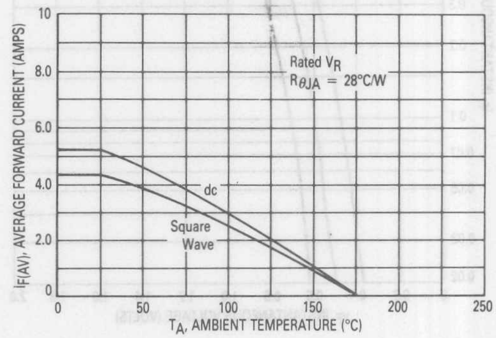


FIGURE 9 — POWER DISSIPATION

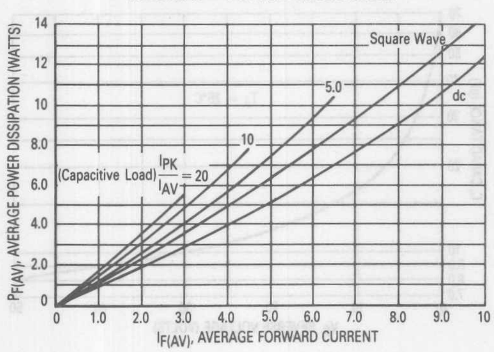
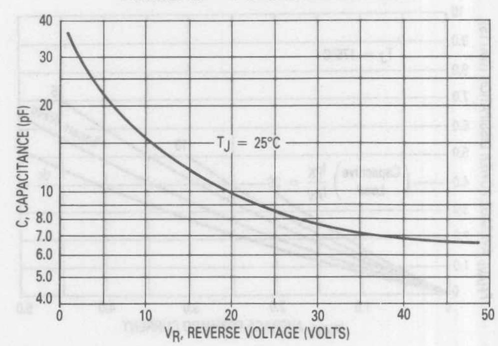


FIGURE 10 — TYPICAL CAPACITANCE



3

3

FIGURE 11 — TYPICAL FORWARD VOLTAGE

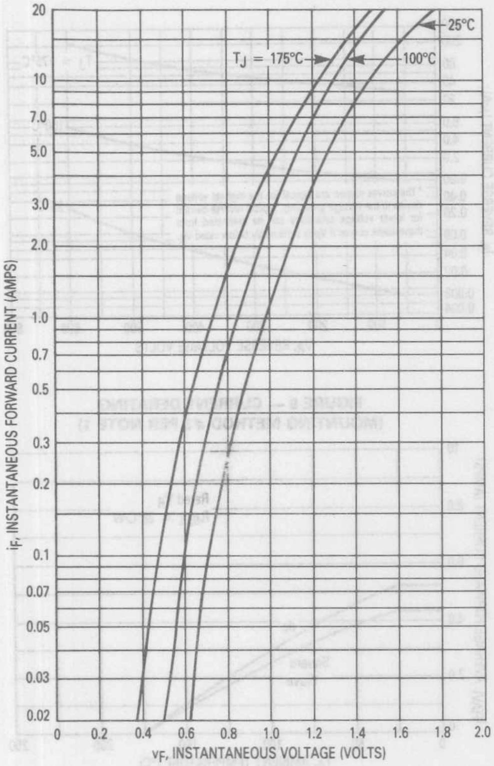


FIGURE 12 — TYPICAL REVERSE CURRENT*

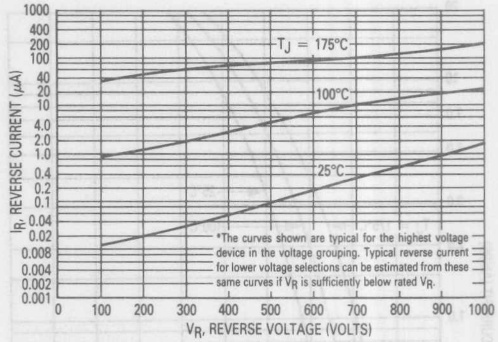


FIGURE 13 — CURRENT DERATING (MOUNTING METHOD #3 PER NOTE 1)

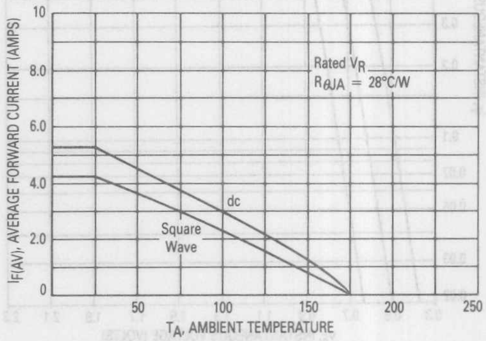


FIGURE 14 — POWER DISSIPATION

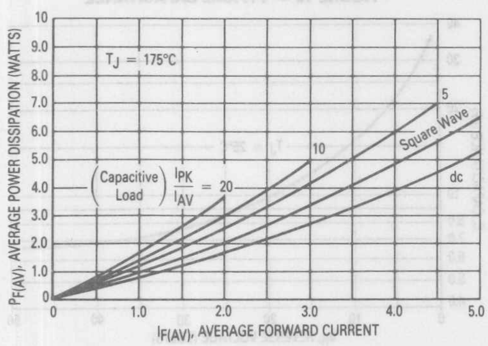
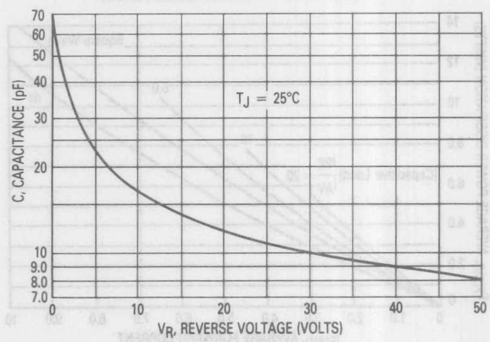


FIGURE 15 — TYPICAL CAPACITANCE



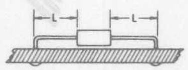
NOTE 1 — AMBIENT MOUNTING DATA

Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

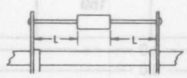
TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

MOUNTING METHOD		LEAD LENGTH, L (IN)				UNITS
		1/8	1/4	1/2	3/4	
1	$R_{\theta JA}$	50	51	53	55	°C/W
2		58	59	61	63	°C/W
3		28				°C/W

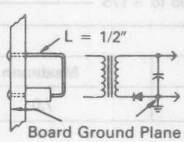
MOUNTING METHOD 1
P.C. Board Where Available Copper Surface area is small.



MOUNTING METHOD 2
Vector Push-In Terminals T-28



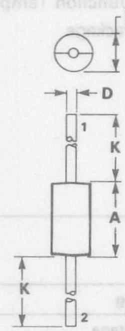
MOUNTING METHOD 3
P.C. Board with
1-1/2" x 1-1/2" Copper Surface



MECHANICAL CHARACTERISTICS

Case: Transfer Molded Plastic
Finish: External Leads are Plated, Leads are readily Solderable
Polarity: Indicated by Cathode Band
Weight: 1.1 Grams (Approximately)
Maximum Lead Temperature for Soldering Purposes:
300°C, 1/8" from case for 10 s

OUTLINE DIMENSIONS



STYLE 1:
PIN 1. CATHODE
2. ANODE

NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	9.39	—	0.370
B	—	6.35	—	0.250
D	1.22	1.32	0.048	0.052
K	25.40	—	1.000	—

CASE 267-02
PLASTIC

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR605CT
MUR610CT
MUR615CT
MUR620CT

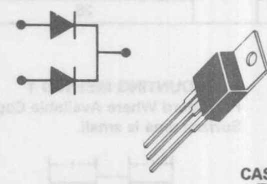
SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Popular TO-220 Package

ULTRAFAST RECTIFIERS

6 AMPERES
50–200 VOLTS



CASE 221A-04
TO-220AB
PLASTIC

3

MAXIMUM RATINGS

Rating	Symbol	MUR605CT	MUR610CT	MUR615CT	MUR620CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Average Rectified Forward Current Per Diode (Rated V_R) $T_C = 130°C$ Total Device	$I_{F(AV)}$	3.0 6.0				Amps
Peak Repetitive Forward Current Per Diode Leg (Rated V_R, Square Wave, 20 kHz) $T_C = 130°C$	I_{FRM}	6.0				Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	75				Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	−65 to +175				°C

THERMAL CHARACTERISTICS PER DIODE LEG

Rating	Symbol	Typical	Maximum	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.0–6.0	7.0	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE LEG

Instantaneous Forward Voltage (1) ($i_F = 3.0$ Amp, $T_C = 150°C$) ($i_F = 3.0$ Amp, $T_C = 25°C$)	v_F	0.80 0.94	0.895 0.975	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 150°C$) (Rated dc Voltage, $T_C = 25°C$)	i_R	2.0–10 0.01–3.0	250 5.0	μA
Reverse Recovery Time ($I_F = 1.0$ Amp, di/dt = 50 Amp/μs)	t_{rr}	20–30	35	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 1 — TYPICAL FORWARD VOLTAGE

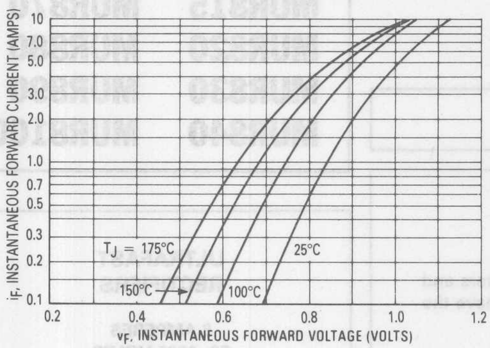


FIGURE 2 — TYPICAL REVERSE CURRENT

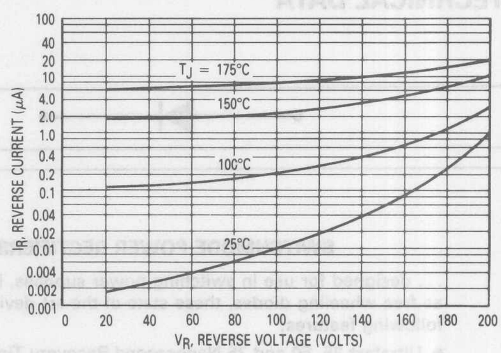


FIGURE 3 — TOTAL DEVICE CURRENT DERATING, CASE

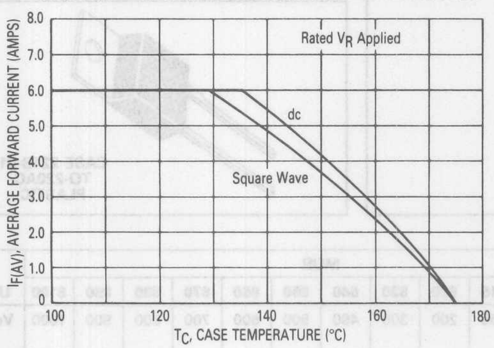


FIGURE 4 — TOTAL DEVICE CURRENT DERATING, AMBIENT

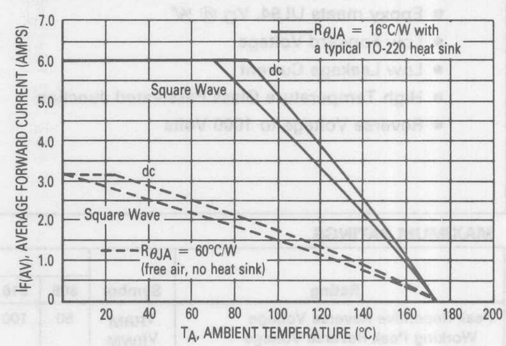
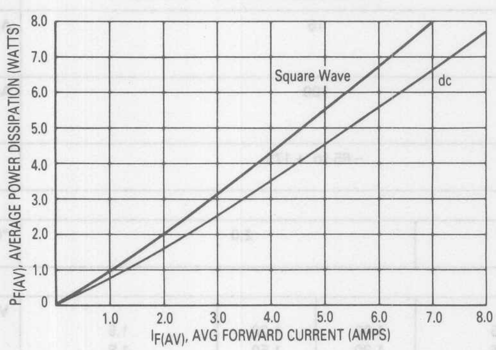
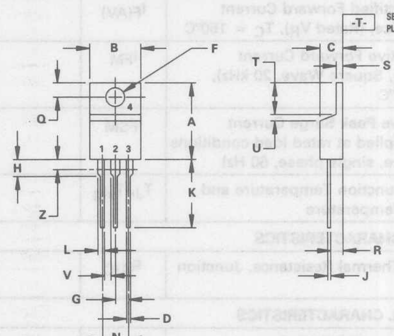


FIGURE 5 — POWER DISSIPATION





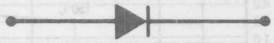
STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080

CASE 221A-04
TO-220AB
PLASTIC

MUR820 MUR880
MUR830 MUR890
MUR840 MUR8100



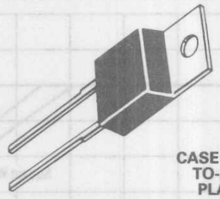
SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 25, 50 and 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Popular TO-220 Package
- Epoxy meets UL94, V_O @ 1/8″
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 Volts

ULTRAFAST RECTIFIERS

8 AMPERES
50–1000 VOLTS



CASE 221B-01
TO-220AC
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MUR 805	810	815	820	830	840	850	860	870	880	890	8100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	700	800	900	1000	Volts
Average Rectified Forward Current Total Device, (Rated V_R), T_C = 150°C	$I_{F(AV)}$	8.0												Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz), T_C = 150°C	I_{FM}	16												Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100												Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	−65 to +175												°C
THERMAL CHARACTERISTICS														
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0				2.0								°C/W
ELECTRICAL CHARACTERISTICS														
Maximum Instantaneous Forward Voltage (1) (i_F = 8.0 Amp, T_C = 150°C) (i_F = 8.0 Amp, T_C = 25°C)	v_F	0.895 0.975				1.00 1.30		1.20 1.50		1.5 1.8				Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 150°C) (Rated dc Voltage, T_C = 25°C)	i_R	250 5.0				500 10		500 10		500 25				μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 Amp)	t_{rr}	35 25				60 50				100 75				ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

MUR805, 810 AND 815

FIGURE 1 — TYPICAL FORWARD VOLTAGE

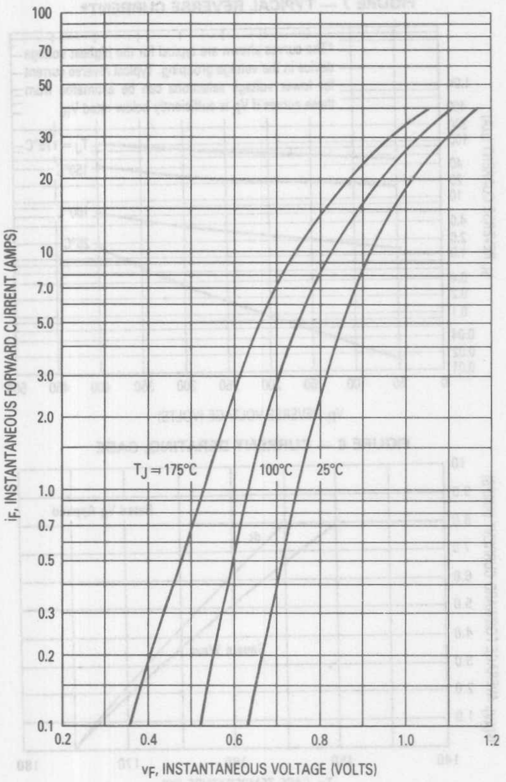


FIGURE 2 — TYPICAL REVERSE CURRENT*

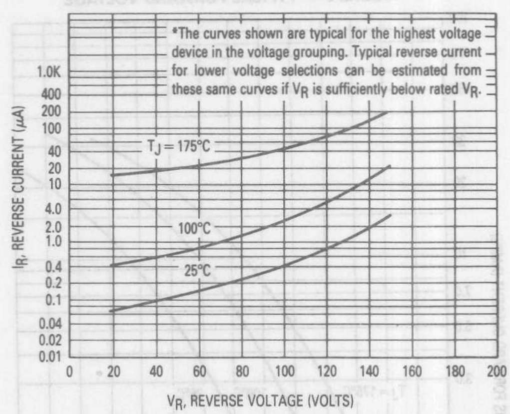


FIGURE 3 — CURRENT DERATING, CASE

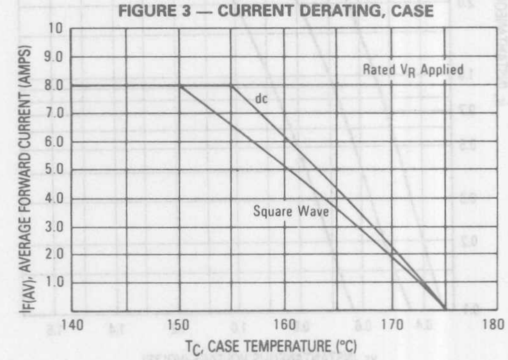


FIGURE 4 — CURRENT DERATING, AMBIENT

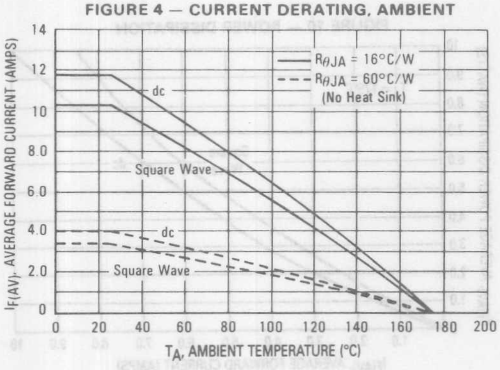
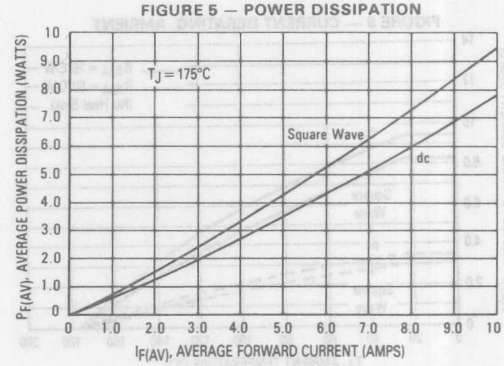


FIGURE 5 — POWER DISSIPATION



3

MUR820, 830 AND 840

FIGURE 6 — TYPICAL FORWARD VOLTAGE

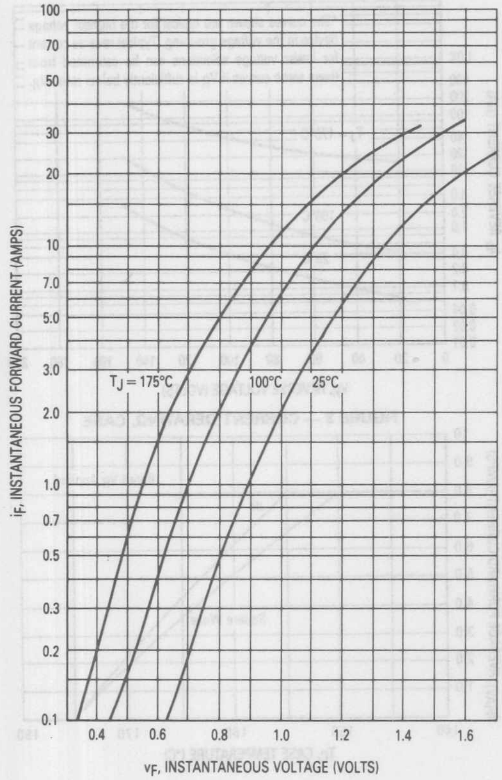


FIGURE 7 — TYPICAL REVERSE CURRENT*

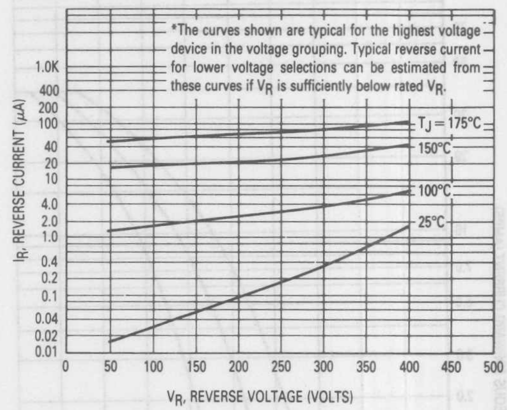


FIGURE 8 — CURRENT DERATING, CASE

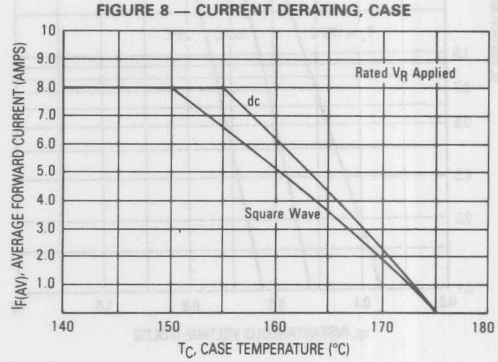


FIGURE 9 — CURRENT DERATING, AMBIENT

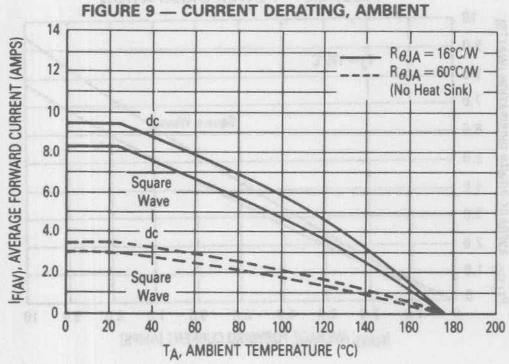
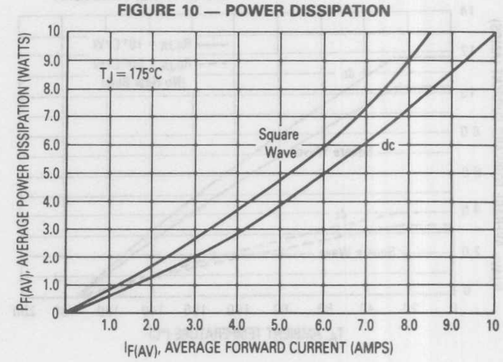


FIGURE 10 — POWER DISSIPATION



MUR850 AND 860

FIGURE 11 — TYPICAL FORWARD VOLTAGE

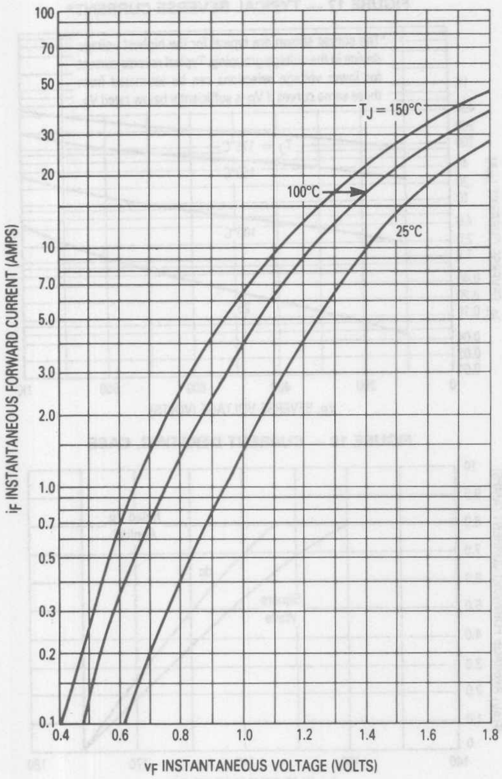


FIGURE 12 — TYPICAL REVERSE CURRENT*

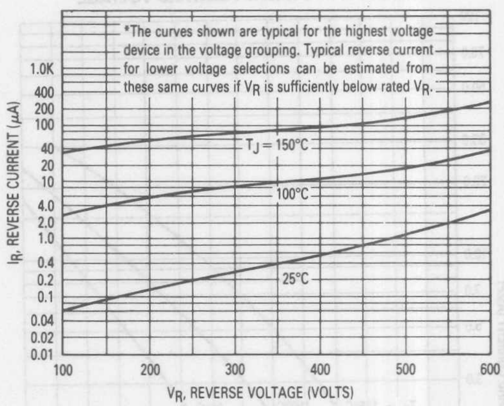


FIGURE 13 — CURRENT DERATING, CASE

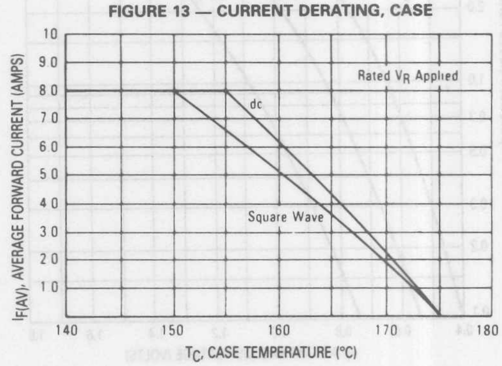


FIGURE 14 — CURRENT DERATING, AMBIENT

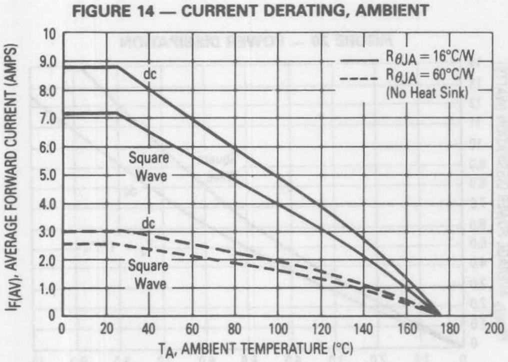


FIGURE 15 — POWER DISSIPATION

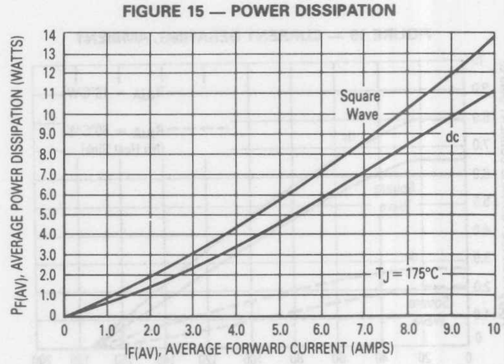


FIGURE 16 — TYPICAL FORWARD VOLTAGE

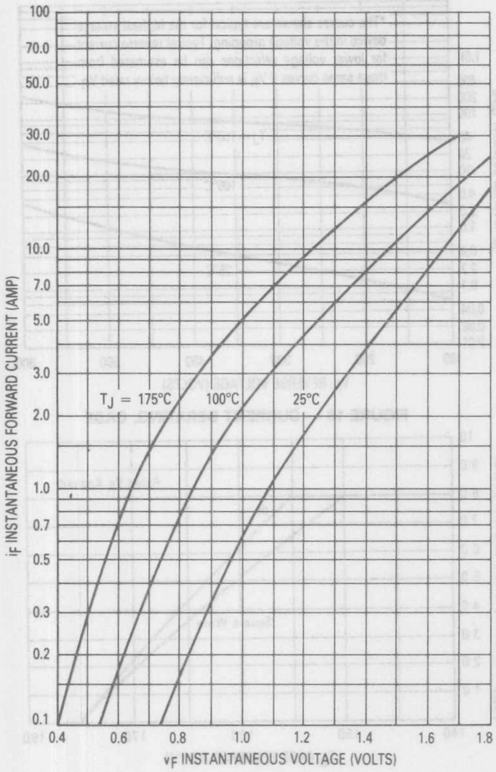


FIGURE 17 — TYPICAL REVERSE CURRENT*

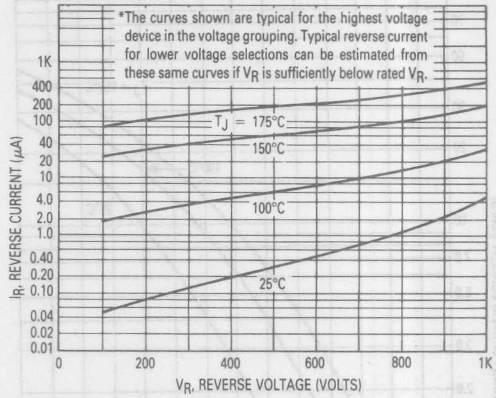


FIGURE 18 — CURRENT DERATING, CASE

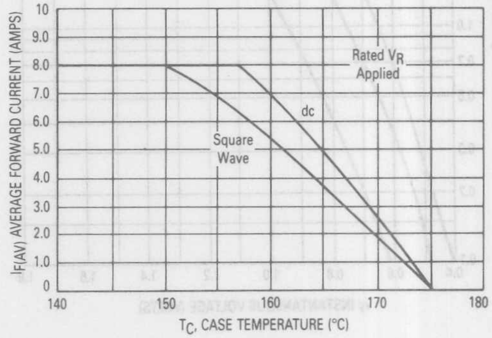


FIGURE 19 — CURRENT DERATING, AMBIENT

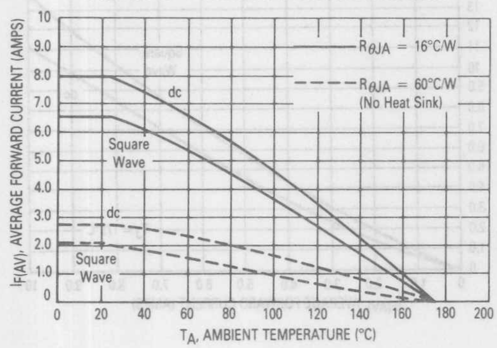


FIGURE 20 — POWER DISSIPATION

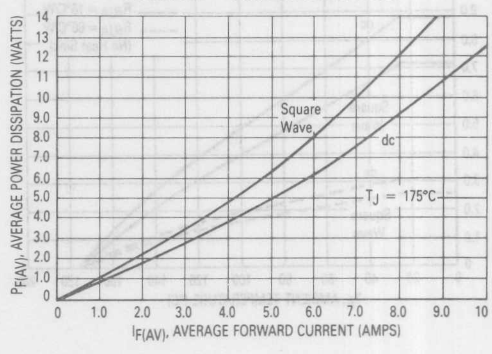


FIGURE 21 — THERMAL RESPONSE

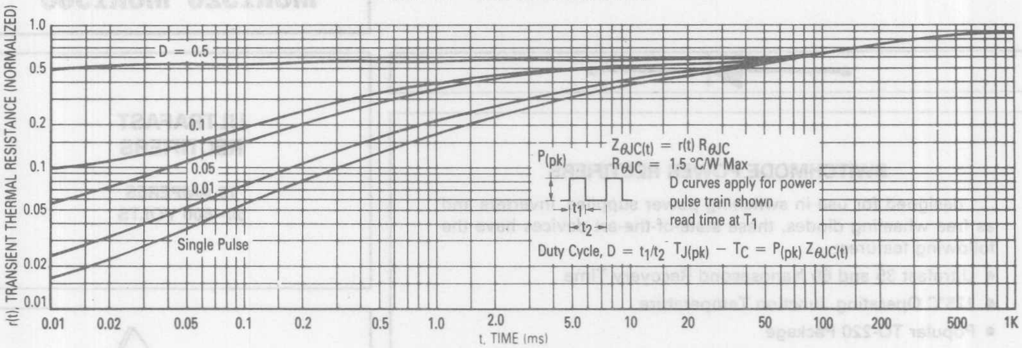


FIGURE 22 — TYPICAL CAPACITANCE

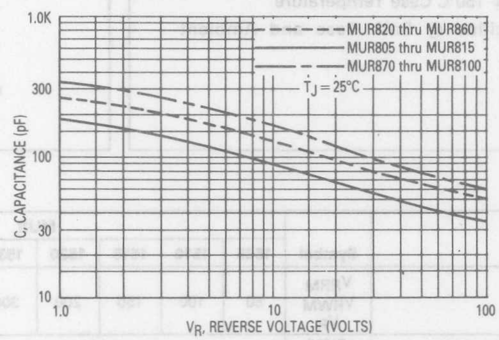
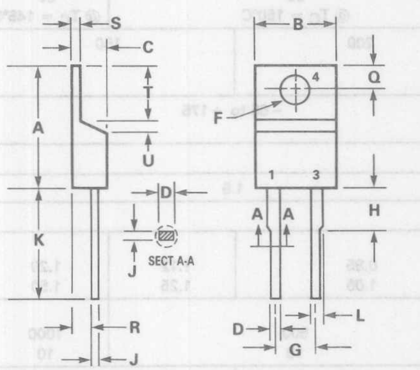


FIGURE 23 — OUTLINE DIMENSIONS



STYLE 1:
PIN 1. CATHODE
2. N/A
3. ANODE
4. CATHODE

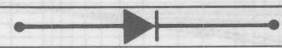
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

CASE 221B-01
TO-220AC
PLASTIC

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR1505 MUR1530
MUR1510 MUR1540
MUR1515 MUR1550
MUR1520 MUR1560



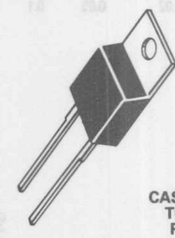
ULTRAFAST RECTIFIERS

15 AMPERES
50–600 VOLTS

SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 and 60 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Popular TO-220 Package
- High Voltage Capability to 600 Volts
- Low Forward Drop
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating Specified @ Both Case and Ambient Temperatures



CASE 221B-01
TO-220AC
PLASTIC

3

MAXIMUM RATINGS

Rating	Symbol	MUR 1505	1510	1515	1520	1530	1540	1550	1560	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	Volts
Average Rectified Forward Current (Rated V_R)	$I_{F(AV)}$	15 @ T_C = 150°C						15 @ T_C = 145°C		Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz)	I_{FRM}	30 @ T_C = 150°C						30 @ T_C = 145°C		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	200				150				Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	−65 to +175								°C
THERMAL CHARACTERISTICS										
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5								°C/W
ELECTRICAL CHARACTERISTICS										
Maximum Instantaneous Forward Voltage (1) (i_F = 15 Amp, T_C = 150°C) (i_F = 15 Amp, T_C = 25°C)	v_F	0.85 1.05				1.12 1.25		1.20 1.50		Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 150°C) (Rated dc Voltage, T_C = 25°C)	i_R	500 10						1000 10		μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs)	t_{rr}	35				60				ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

MUR1505, 1510, and 1515

FIGURE 1 — TYPICAL FORWARD VOLTAGE

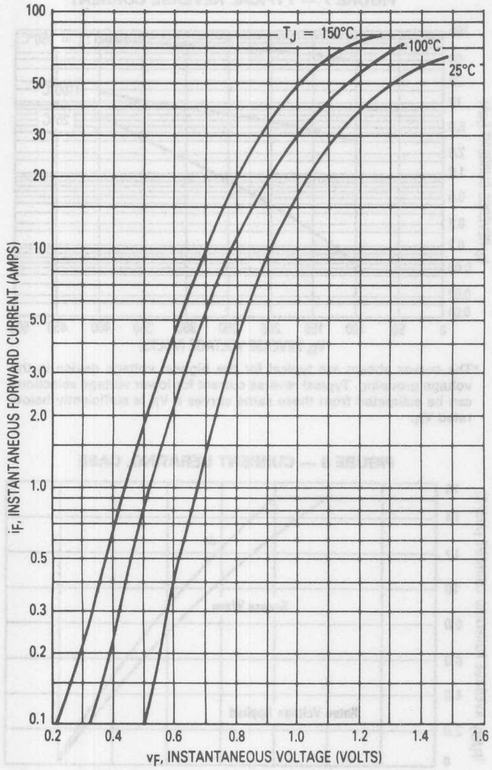
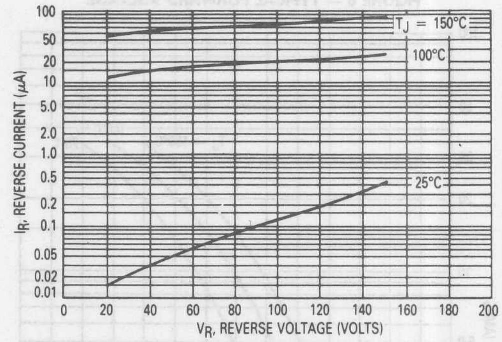


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING, CASE

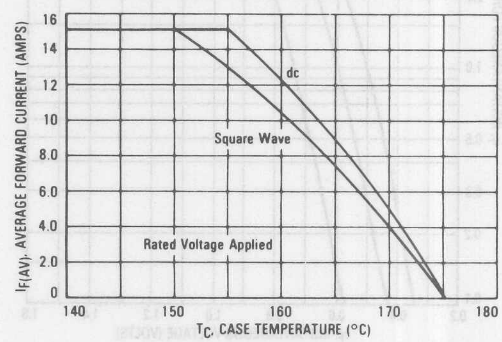


FIGURE 4 — CURRENT DERATING, AMBIENT

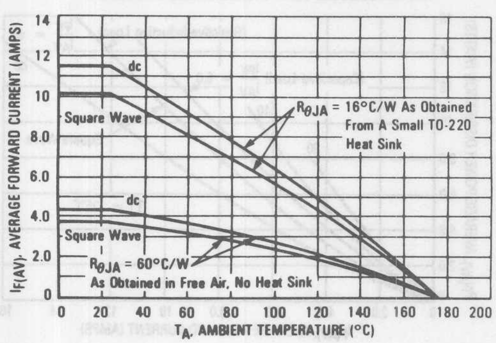
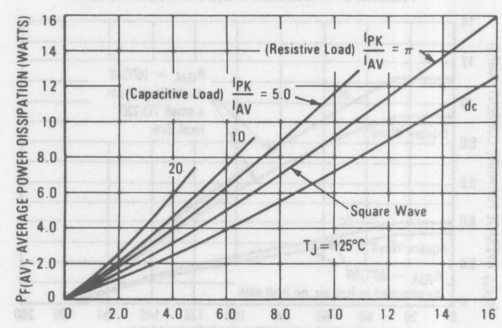


FIGURE 5 — POWER DISSIPATION



3

FIGURE 6 — TYPICAL FORWARD VOLTAGE

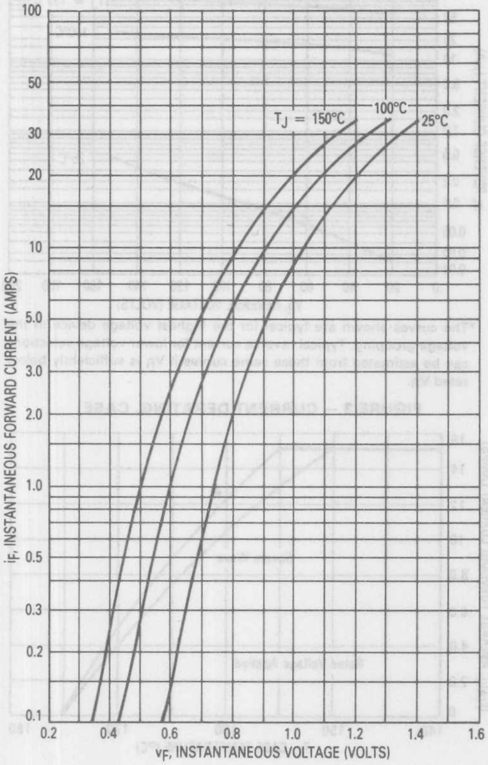
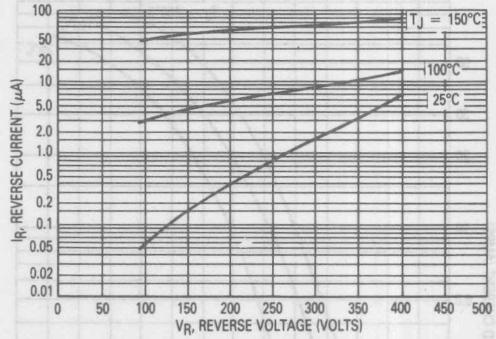


FIGURE 7 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 8 — CURRENT DERATING, CASE

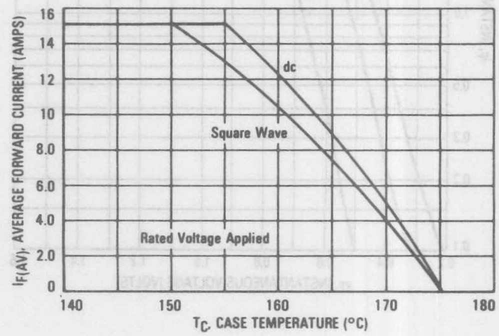


FIGURE 9 — CURRENT DERATING, AMBIENT

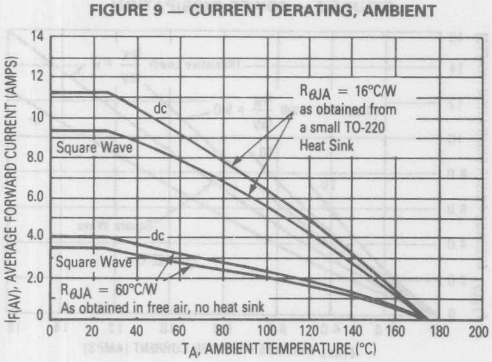
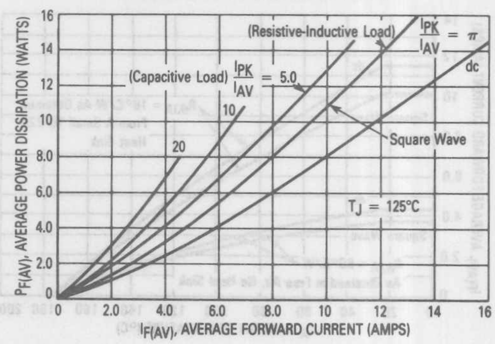


FIGURE 10 — POWER DISSIPATION



3

MUR1550, 1560

FIGURE 11 — TYPICAL FORWARD VOLTAGE

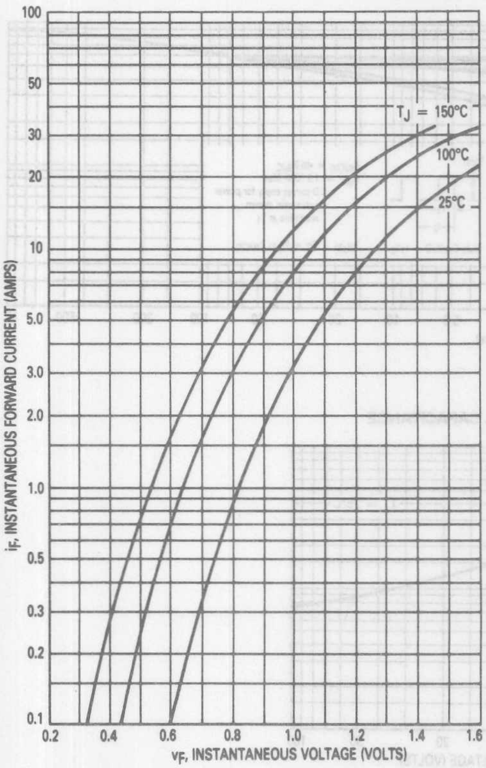
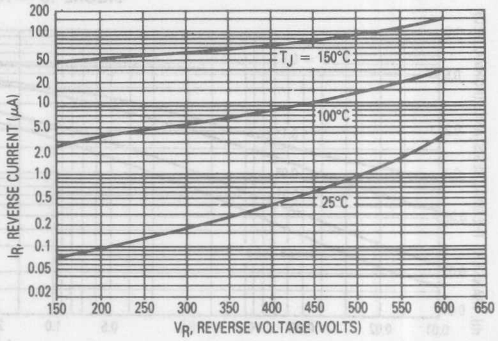


FIGURE 12 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 13 — CURRENT DERATING, CASE

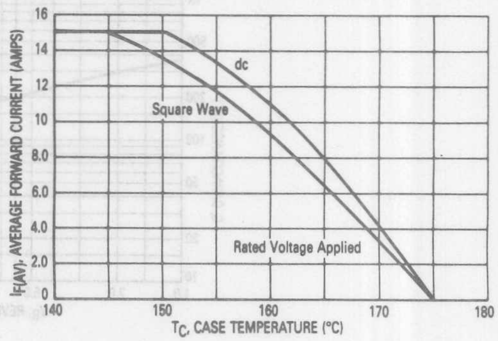


FIGURE 14 — CURRENT DERATING, AMBIENT

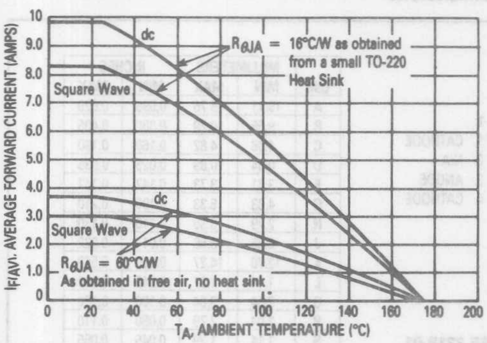


FIGURE 15 — POWER DISSIPATION

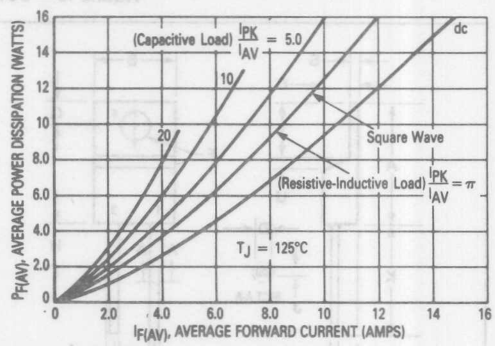


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FIGURE 16 — THERMAL RESPONSE

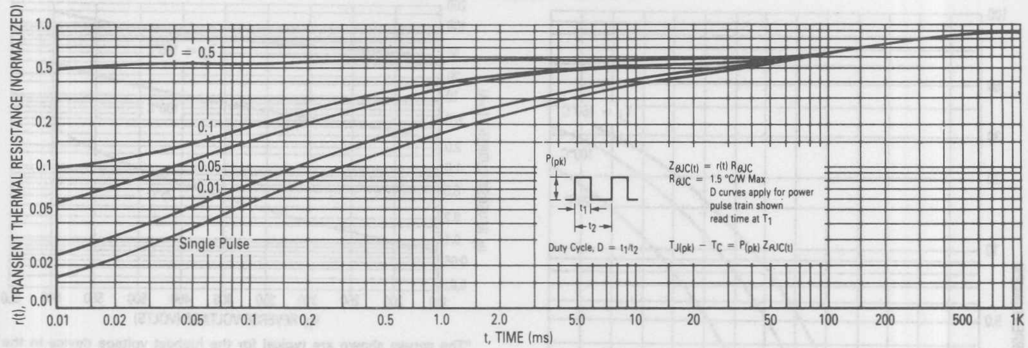


FIGURE 17 — TYPICAL CAPACITANCE

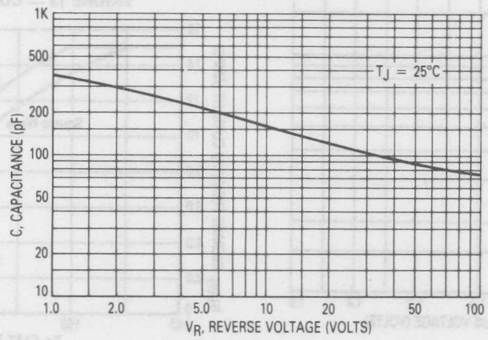
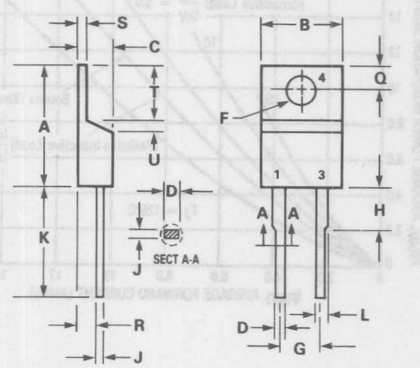


FIGURE 18 — OUTLINE DIMENSIONS



STYLE 1:
PIN 1. CATHODE
2. N/A
3. ANODE
4. CATHODE

CASE 221B-01
TO-220AC
PLASTIC

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	15.11	15.75	0.595	0.620
B	9.65	10.29	0.380	0.405
C	4.06	4.82	0.160	0.190
D	0.64	0.89	0.025	0.035
F	3.61	3.73	0.142	0.147
G	4.83	5.33	0.190	0.210
H	2.79	3.30	0.110	0.130
J	0.36	0.56	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.14	1.27	0.045	0.050
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.14	1.39	0.045	0.055
T	5.97	6.48	0.235	0.255
U	0.76	1.27	0.030	0.050

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR1605CT MUR1630CT
MUR1610CT MUR1640CT
MUR1615CT MUR1650CT
MUR1620CT MUR1660CT

SWITCHMODE POWER RECTIFIERS

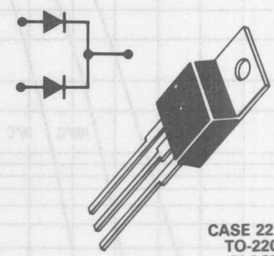
. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 and 60 Nanosecond Recovery Times
- 175°C Operating Junction Temperature
- Popular TO-220 Package
- Epoxy meets UL94, V_O @ ⅛″
- High Temperature Glass Passivated Junction
- High Voltage Capability to 600 Volts
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating @ Both Case and Ambient Temperatures

ULTRAFAST RECTIFIERS

8 AMPERES
50–600 VOLTS

3



CASE 221A-04
TO-220AB
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MUR 1605CT	1610CT	1615CT	1620CT	1630CT	1640CT	1650CT	1660CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	Volts
Average Rectified Forward Current Per Leg Total Device, (Rated V_R), T_C = 150°C Total Device	$I_{F(AV)}$	8.0 16								Amps
Peak Repetitive Forward Current Per Diode Leg (Rated V_R, Square Wave, 20 kHz), T_C = 150°C	I_{FM}	16								Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	100								Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	– 65 to + 175								°C
THERMAL CHARACTERISTICS, PER DIODE LEG										
Maximum Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0				2.0				°C/W
ELECTRICAL CHARACTERISTICS, PER DIODE LEG										
Maximum Instantaneous Forward Voltage (1) (i_F = 8.0 Amp, T_C = 150°C) (i_F = 8.0 Amp, T_C = 25°C)	v_F	0.895 0.975				1.00 1.30		1.20 1.50		Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 150°C) (Rated dc Voltage, T_C = 25°C)	i_R	250 5.0				500 10		500 10		μA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs) (I_F = 0.5 Amp, i_R = 1.0 Amp, I_{REC} = 0.25 Amp)	t_{rr}	35 25				60 50				ns

(1)Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤2.0%

FIGURE 1 — TYPICAL FORWARD VOLTAGE, PER LEG

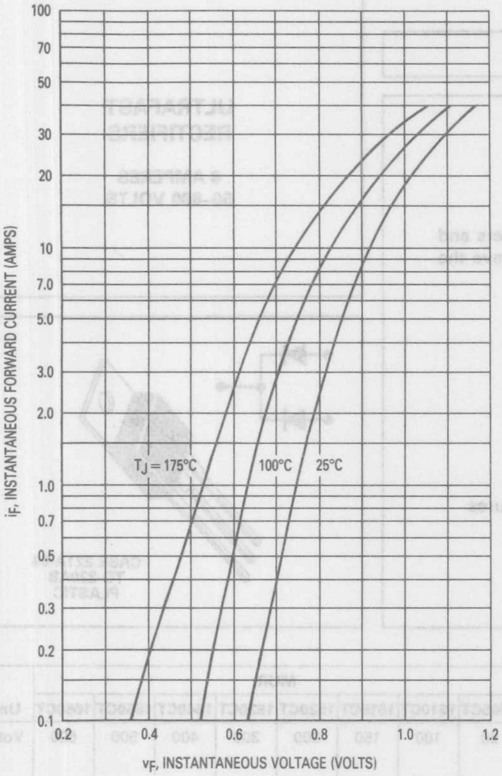


FIGURE 2 — TYPICAL REVERSE CURRENT, PER LEG*

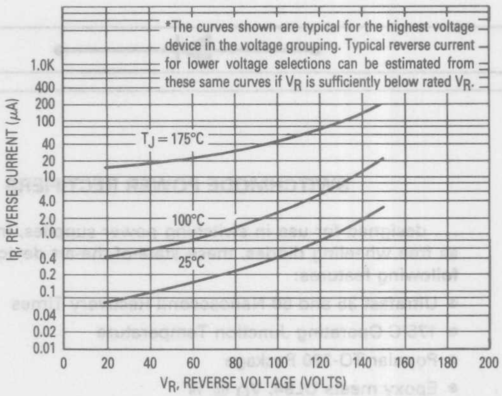


FIGURE 3 — CURRENT DERATING CASE, PER LEG

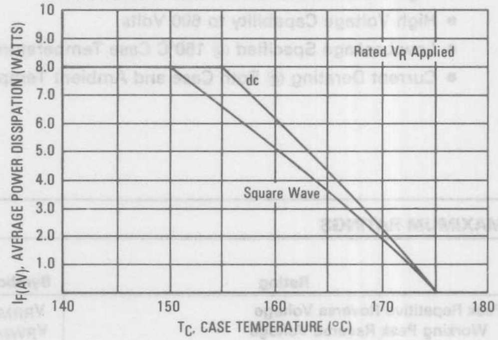


FIGURE 4 — CURRENT DERATING, AMBIENT, PER LEG

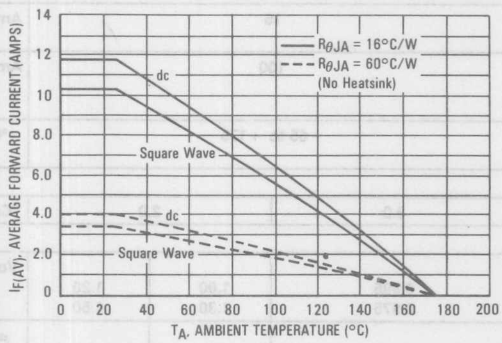
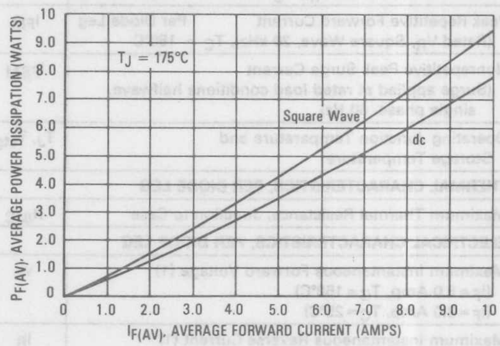


FIGURE 5 — POWER DISSIPATION, PER LEG



MUR1620CT, 1630CT AND 1640CT

FIGURE 6 — TYPICAL FORWARD VOLTAGE, PER LEG

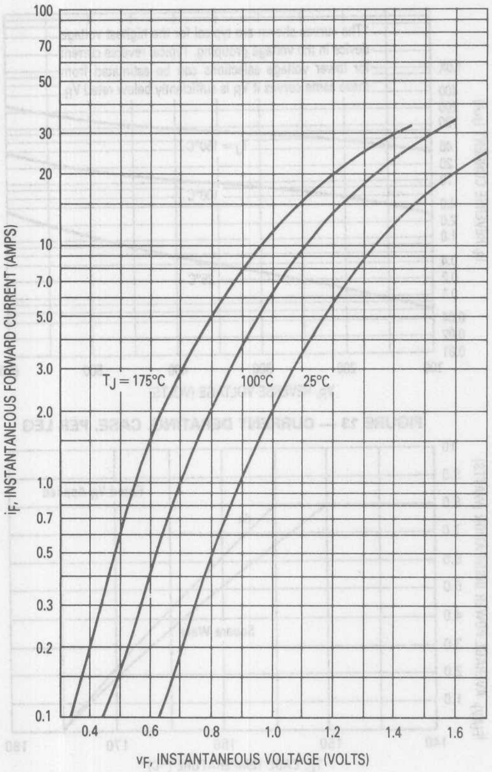


FIGURE 7 — TYPICAL REVERSE CURRENT, PER LEG*

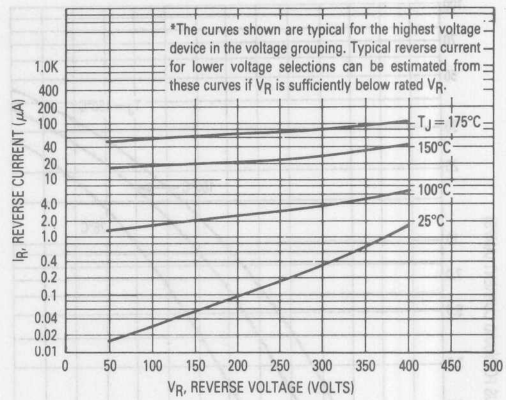


FIGURE 8 — CURRENT DERATING, CASE, PER LEG

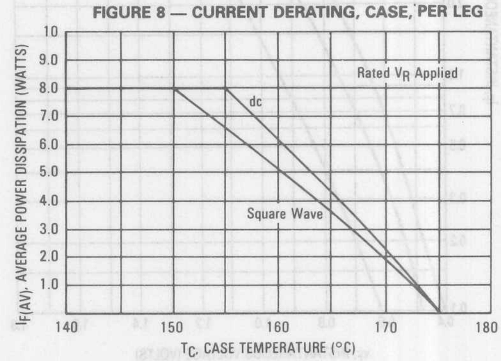


FIGURE 9 — CURRENT DERATING, AMBIENT, PER LEG

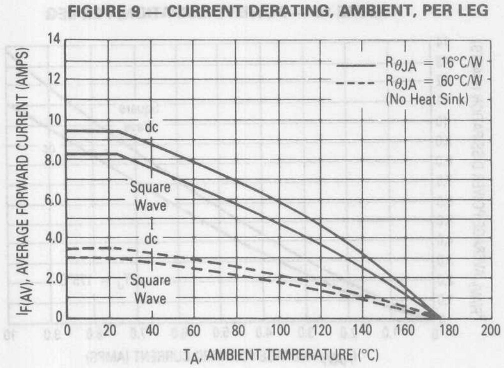
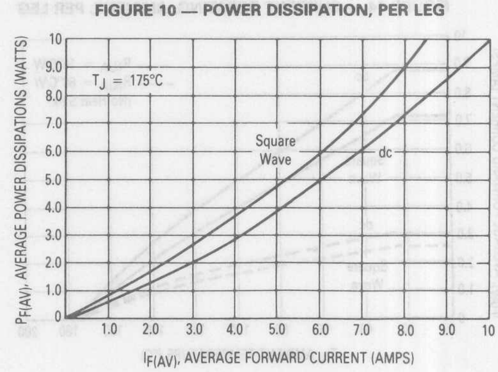


FIGURE 10 — POWER DISSIPATION, PER LEG



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MUR1650CT AND 1660CT

FIGURE 11 — TYPICAL FORWARD VOLTAGE, PER LEG

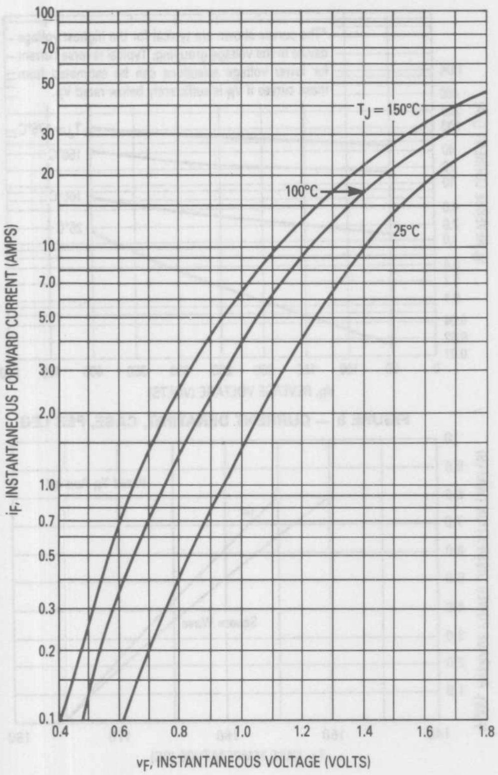


FIGURE 12 — TYPICAL REVERSE CURRENT, PER LEG*

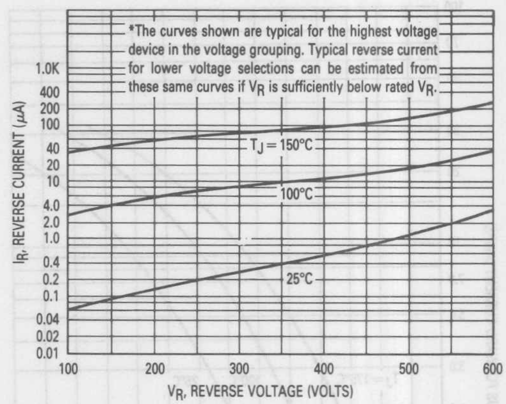


FIGURE 13 — CURRENT DERATING, CASE, PER LEG

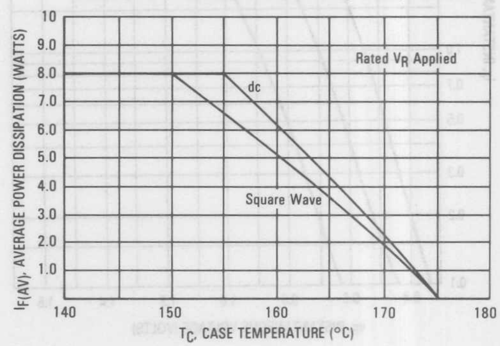


FIGURE 14 — CURRENT DERATING, AMBIENT, PER LEG

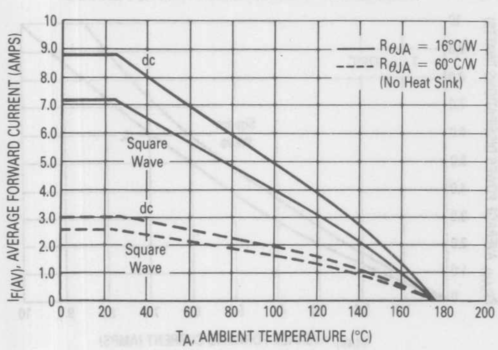


FIGURE 15 — POWER DISSIPATION, PER LEG

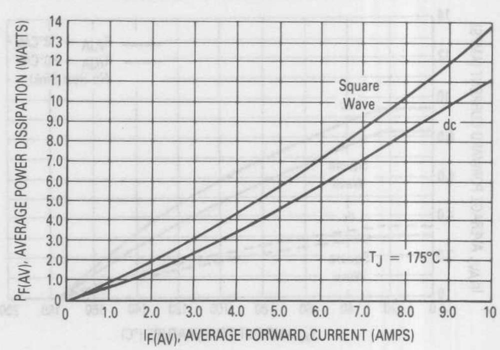


FIGURE 16 — THERMAL RESPONSE

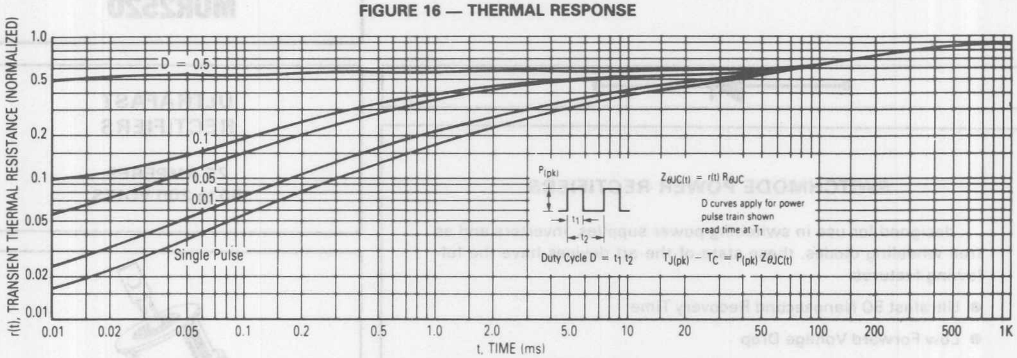
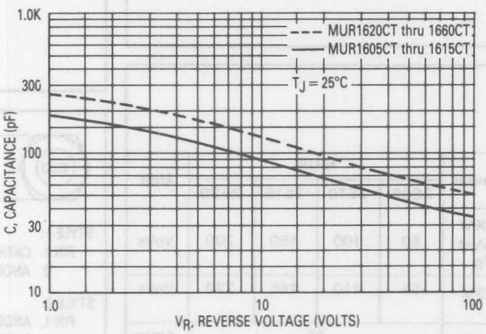
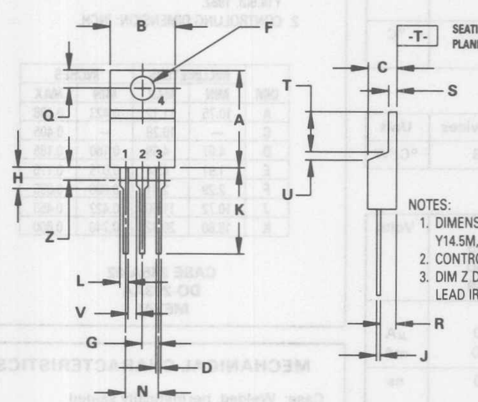


FIGURE 17 — TYPICAL CAPACITANCE, PER LEG



OUTLINE DIMENSIONS

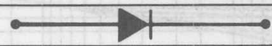


STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIM Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

CASE 221A-04
TO-220AB
PLASTIC

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	14.48	15.75	0.570	0.620
B	9.66	10.28	0.380	0.405
C	4.07	4.82	0.160	0.190
D	0.64	0.88	0.025	0.035
F	3.61	3.73	0.142	0.147
G	2.42	2.66	0.095	0.105
H	2.80	3.93	0.110	0.155
J	0.36	0.55	0.014	0.022
K	12.70	14.27	0.500	0.562
L	1.15	1.39	0.045	0.055
N	4.83	5.33	0.190	0.210
Q	2.54	3.04	0.100	0.120
R	2.04	2.79	0.080	0.110
S	1.15	1.39	0.045	0.055
T	5.97	6.47	0.235	0.255
U	0.00	1.27	0.000	0.050
V	1.15	—	0.045	—
Z	—	2.04	—	0.080



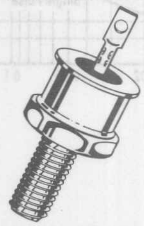
ULTRAFAST RECTIFIERS

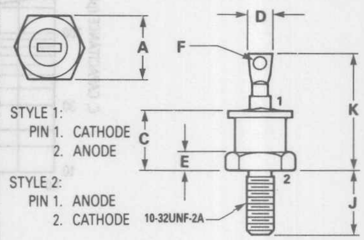
25 AMPERES
50 to 200 VOLTS

SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 50 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Hermetically Sealed Metal DO-203AA (DO-4) Package





STYLE 1:
PIN 1. CATHODE
2. ANODE

STYLE 2:
PIN 1. ANODE
2. CATHODE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	10.75	11.12	0.423	0.438
C	—	10.28	—	0.405
D	4.07	4.69	0.160	0.185
E	1.91	4.44	0.075	0.175
F	2.29	2.41	0.090	0.095
J	10.72	11.50	0.422	0.453
K	18.80	20.32	0.740	0.800

CASE 245A-02
DO-203AA
METAL

MAXIMUM RATINGS

Rating	Symbol	MUR 2505	MUR 2510	MUR 2515	MUR 2520	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	55	110	165	220	Volts
Average Forward Current $T_C = 145°C$	$I_{F(AV)}$	25				Amps
Nonrepetitive Peak Surge Forward Current (half cycle, 60 Hz, Sinusoidal Waveform)	I_{FSM}	500				Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	-65 to +175				°C

THERMAL CHARACTERISTICS

Rating	Symbol	All Devices	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.3	°C/W

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage Drop (i_F = 25 Amp, T_J = 25°C) (i_F = 25 Amp, T_J = 125°C) (i_F = 50 Amp, T_J = 125°C)	v_F	 0.95 0.80 0.88	Volts
Maximum Reverse Current @ DC Voltage (T_J = 25°C) (T_J = 125°C)	I_R	 10 1.0	 μA mA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs, V_R = 30 V, T_J = 25°C)	t_{rr}	50	ns

MECHANICAL CHARACTERISTICS

Case: Welded, hermetically sealed

Finish: All external surface corrosion resistant and terminal leads are readily solderable

Polarity: Cathode to Case

Mounting Positions: Any

Stud Torque: 15 in/lb. Max

FIGURE 1 — TYPICAL FORWARD VOLTAGE

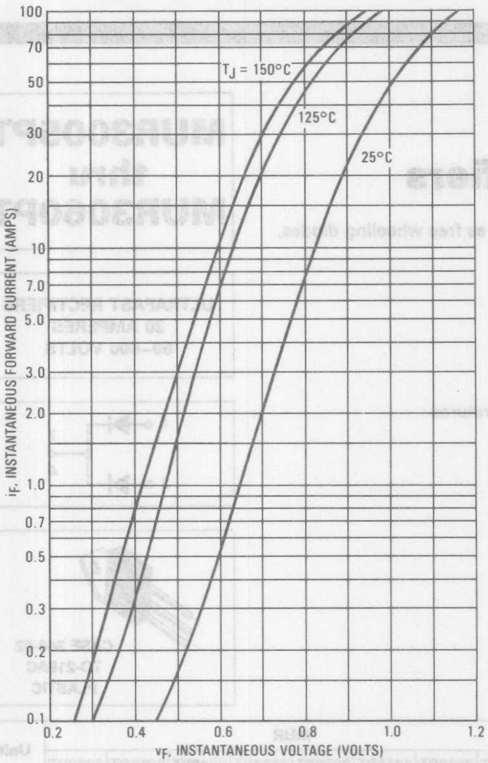
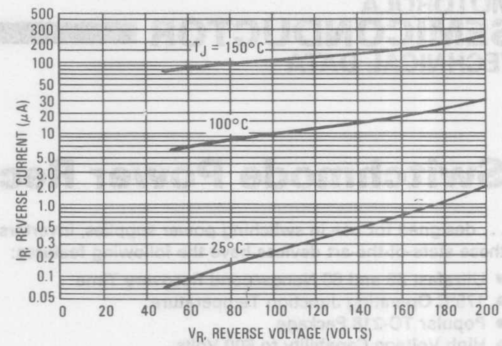


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING, CASE

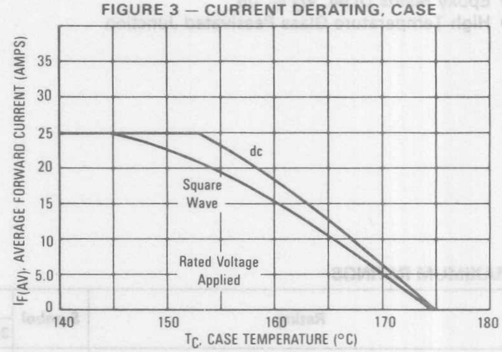


FIGURE 4 — POWER DISSIPATION

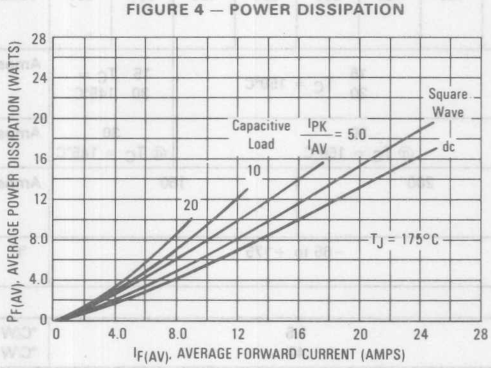


FIGURE 5 — TYPICAL CAPACITANCE

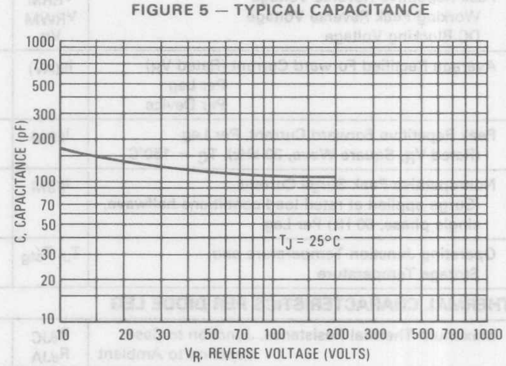
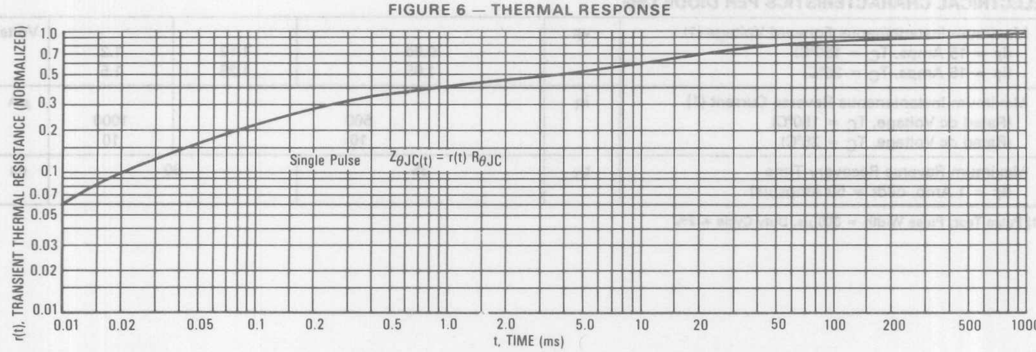


FIGURE 6 — THERMAL RESPONSE



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR3005PT thru MUR3060PT

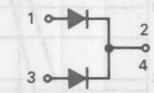
ULTRAFAST RECTIFIERS
30 AMPERES
50–600 VOLTS

Switchmode Power Rectifiers

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 and 60 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Popular TO-218 Package
- High Voltage Capability to 600 Volts
- Low Forward Drop
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating Specified @ Both Case and Ambient Temperatures
- Epoxy Meets UL94, V_O @ 1/8″
- High Temperature Glass Passivated Junction

3



CASE 340-02
TO-218AC
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MUR 3005PT	3010PT	3015PT	3020PT	3030PT	3040PT	3050PT	3060PT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	300	400	500	600	Volts
Average Rectified Forward Current (Rated V_R) Per Leg Per Device	$I_{F(AV)}$	15 30 $T_C = 150°C$						15 $T_C =$ 30 145°C		Amps
Peak Repetitive Forward Current, Per Leg (Rated V_R, Square Wave, 20 kHz), $T_C = 150°C$	I_{FRM}	30 @ $T_C = 150°C$						30 @ $T_C = 145°C$		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) Per Leg	I_{FSM}	200				150				Amps
Operating Junction Temperature and Storage Temperature	T_J, T_{stg}	−65 to +175								°C

THERMAL CHARACTERISTICS PER DIODE LEG

Maximum Thermal Resistance, Junction to Case Junction to Ambient	$R_{\theta JC}$ $R_{\theta JA}$	1.5 40	°C/W °C/W

ELECTRICAL CHARACTERISTICS PER DIODE LEG

		3005PT	3010PT	3015PT	3020PT	3030PT	3040PT	3050PT	3060PT	
Maximum Instantaneous Forward Voltage (1) (i_F = 15 Amps, $T_C = 150°C$) (i_F = 15 Amps, $T_C = 25°C$)	v_F	0.85 1.05				1.12 1.25		1.2 1.5		Volts
Maximum Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 150°C$) (Rated dc Voltage, $T_C = 25°C$)	i_R	500 10						1000 10		μA
Maximum Reverse Recovery Time (I_F = 1 Amp, di/dt = 50 Amps/μs)	t_{rr}	35				60				ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

MUR3005PT, 3010PT, and 3015PT

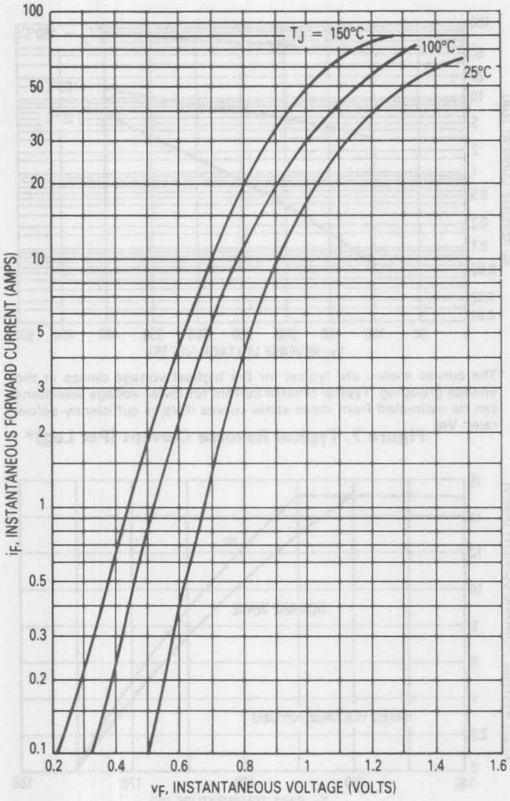
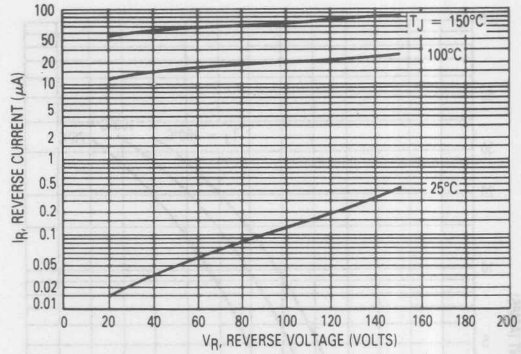


Figure 1. Typical Forward Voltage (Per Leg)



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

Figure 2. Typical Reverse Current (Per Leg)*

3

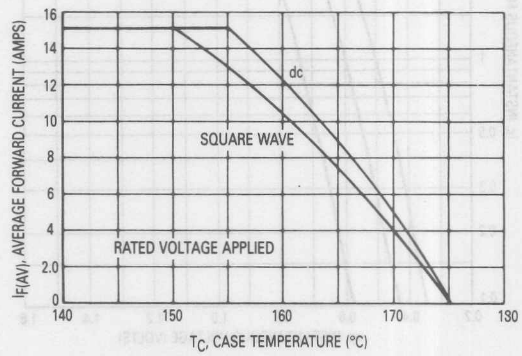


Figure 3. Current Derating, Case (Per Leg)

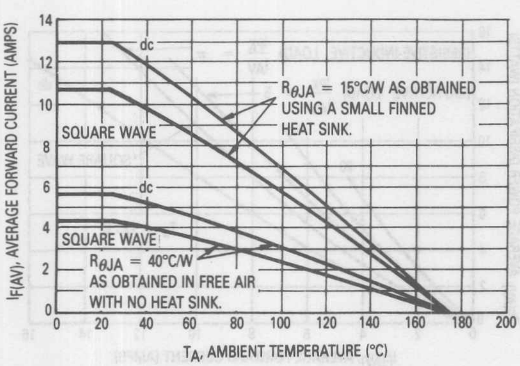


Figure 4. Current Derating, Ambient (Per Leg)

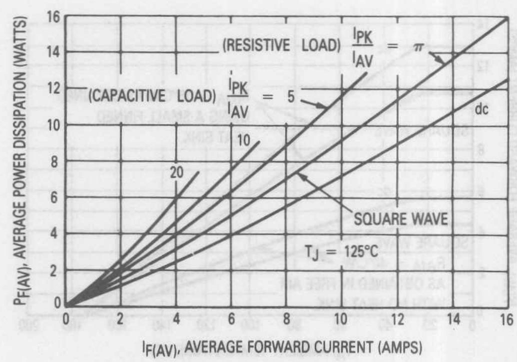


Figure 5. Power Dissipation (Per Leg)

MUR3020PT,3030PT, and 3040PT

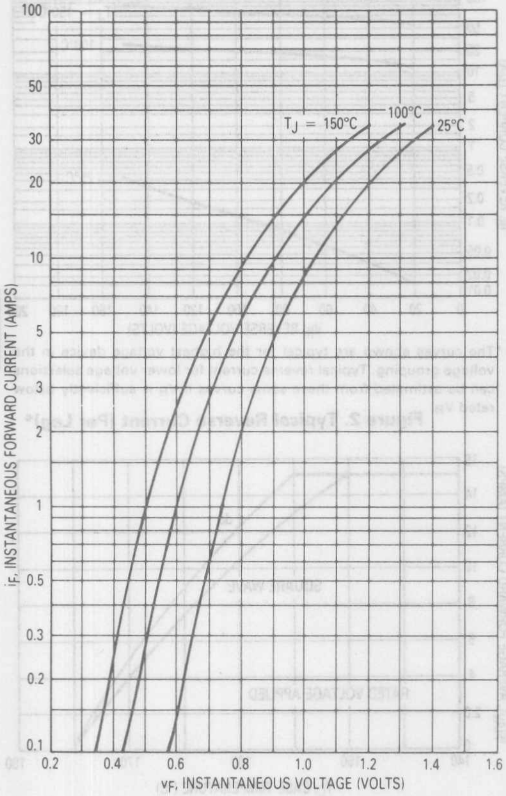
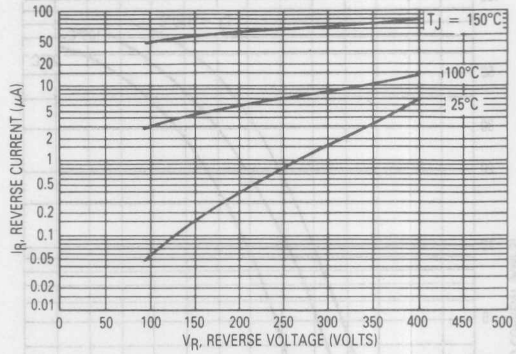


Figure 6. Typical Forward Voltage (Per Leg)



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

Figure 7. Typical Reverse Current (Per Leg)*

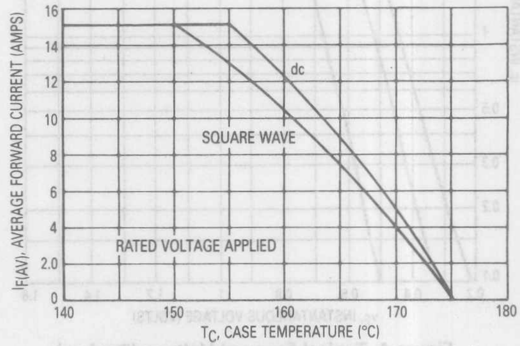


Figure 8. Current Derating, Case (Per Leg)

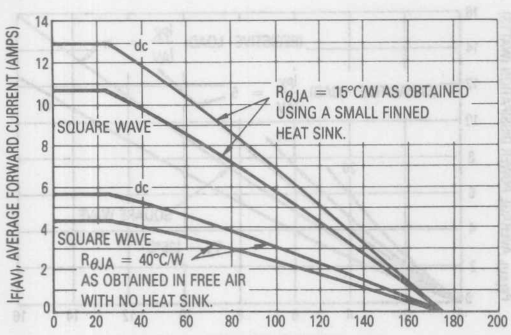


Figure 9. Current Derating, Ambient (Per Leg)

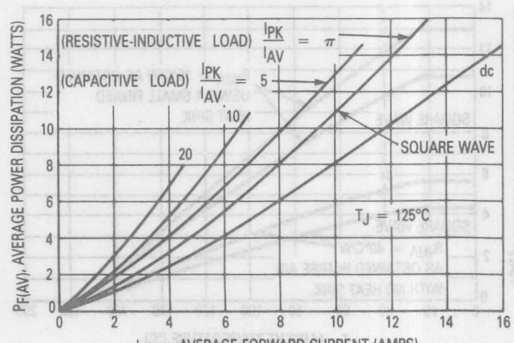


Figure 10. Power Dissipation (Per Leg)

MUR3050PT and MUR3060PT

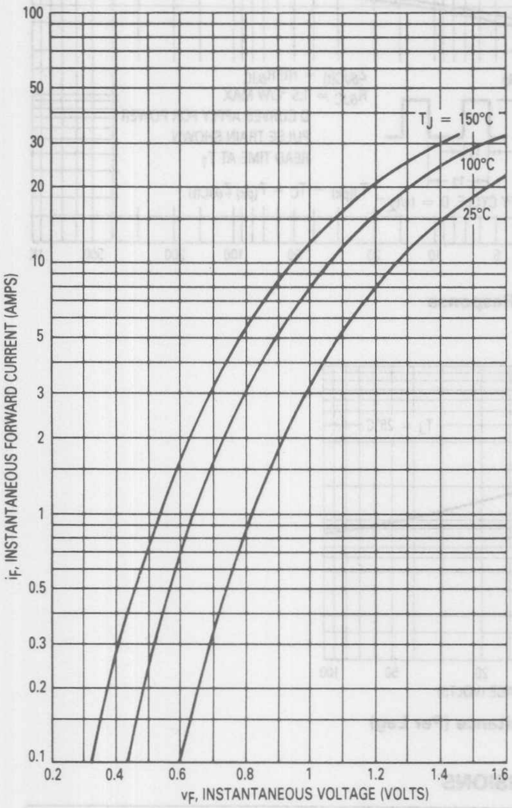
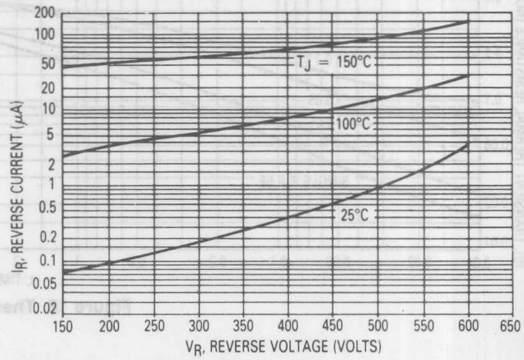


Figure 11. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

Figure 12. Typical Reverse Current*

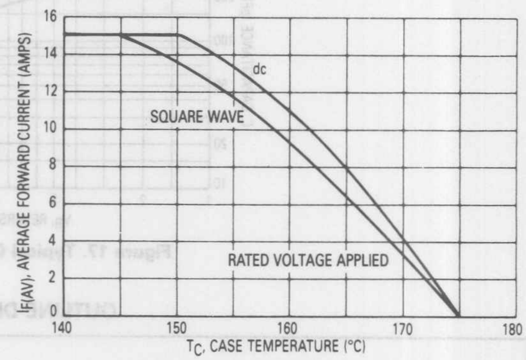


Figure 13. Current Derating, Case

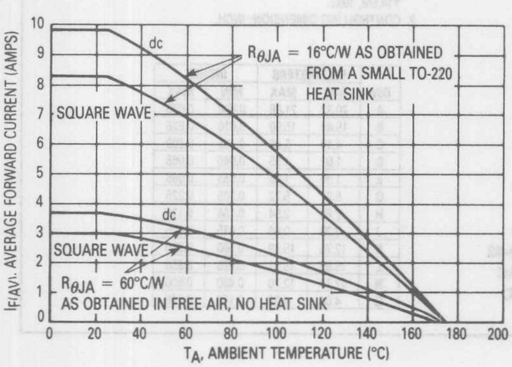


Figure 14. Current Derating, Ambient

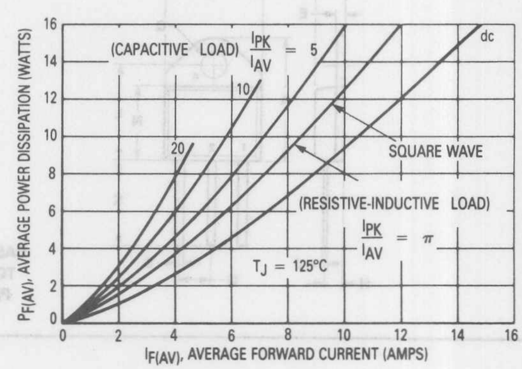


Figure 15. Power Dissipation

3

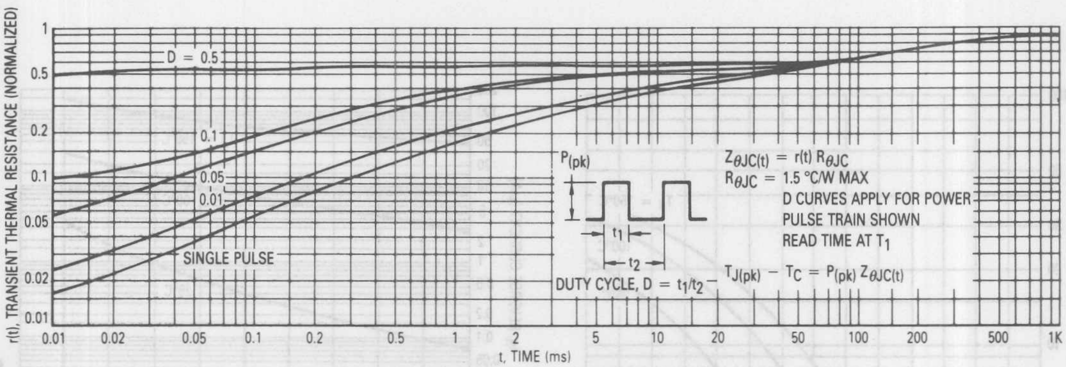


Figure 16. Thermal Response

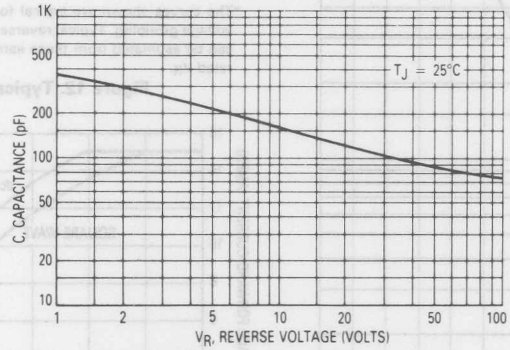
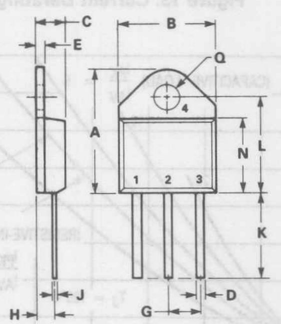


Figure 17. Typical Capacitance (Per Leg)

OUTLINE DIMENSIONS



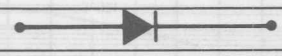
CASE 340-02
TO-218AC
PLASTIC

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	20.32	21.08	0.800	0.830
B	15.49	15.90	0.610	0.626
C	4.19	5.08	0.165	0.200
D	1.02	1.65	0.040	0.065
E	1.35	1.65	0.053	0.065
G	5.21	5.72	0.205	0.225
H	2.65	2.94	0.104	0.116
J	0.38	0.64	0.015	0.025
K	12.70	15.49	0.500	0.610
L	15.88	16.51	0.625	0.650
N	12.19	12.70	0.480	0.500
Q	4.04	4.22	0.159	0.166

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR5005
MUR5010
MUR5015
MUR5020



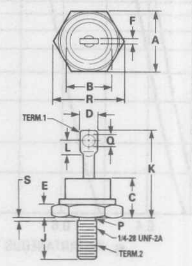
SWITCHMODE POWER RECTIFIERS

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 50 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Hermetically Sealed Metal DO-203AB Package

ULTRAFAST RECTIFIERS

50 AMPERES
50 to 200 VOLTS



NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

CASE 257-01
DO-203AB
METAL

MAXIMUM RATINGS

Rating	Symbol	MUR 5005	MUR 5010	MUR 5015	MUR 5020	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	55	110	165	220	Volts
Average Forward Current $T_C = 125°C$	$I_{F(AV)}$	50				Amps
Nonrepetitive Peak Surge Forward Current (half cycle, 60 Hz, Sinusoidal Waveform)	I_{FSM}	600				Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	-55 to +175				°C

THERMAL CHARACTERISTICS

Rating	Symbol	All Devices	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage Drop (i_F = 50 Amp, T_J = 25°C) (i_F = 50 Amp, T_J = 125°C) (i_F = 100 Amp, T_J = 125°C)	v_F	 1.15 0.95 1.10	Volts
Maximum Reverse Current @ DC Voltage (T_J = 25°C) (T_J = 125°C)	I_R	 10 1.0	 μA mA
Maximum Reverse Recovery Time (I_F = 1.0 Amp, di/dt = 50 Amp/μs, V_R = 30 V, T_J = 25°C)	t_{rr}	50	ns

MECHANICAL CHARACTERISTICS

Case: Welded, hermetically sealed

Finish: All external surface corrosion resistant and terminal leads are readily solderable

Polarity: Cathode to Case

Mounting Positions: Any

Stud Torque: 25 in/lb. Max

3

FIGURE 1 — TYPICAL FORWARD VOLTAGE

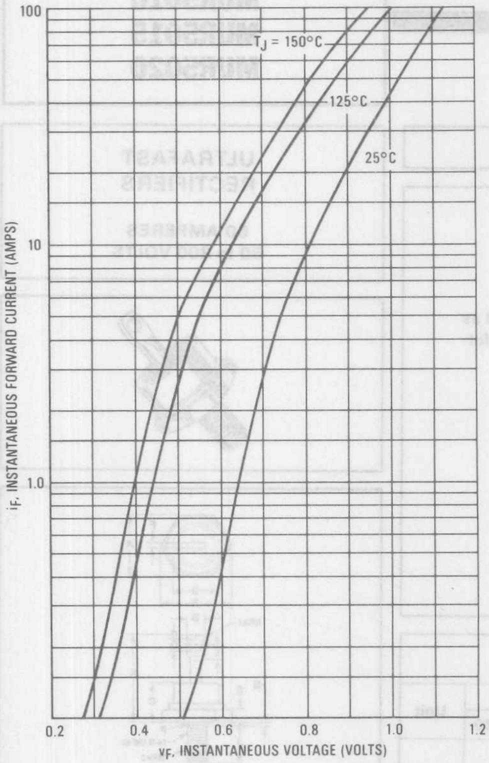
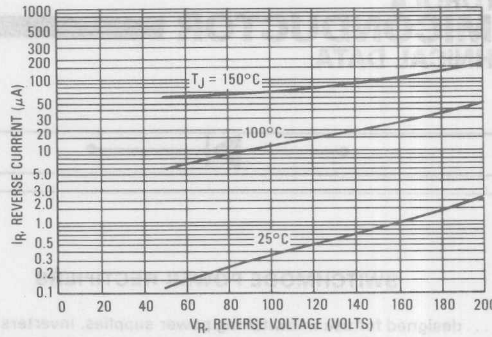


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING, CASE

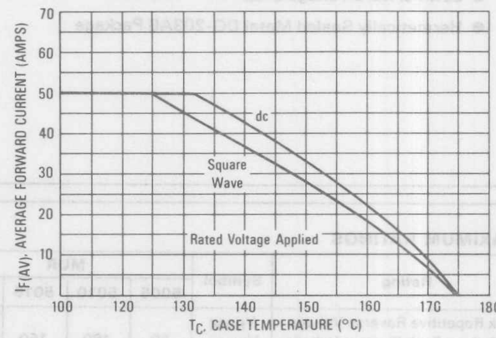


FIGURE 4 — POWER DISSIPATION

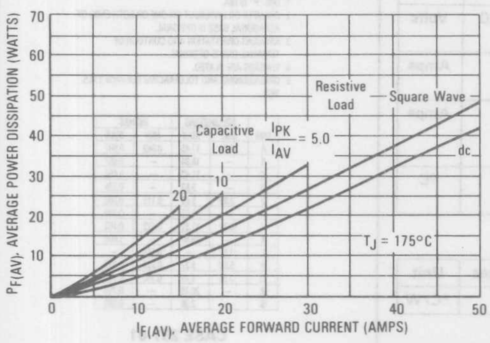


FIGURE 5 — TYPICAL CAPACITANCE

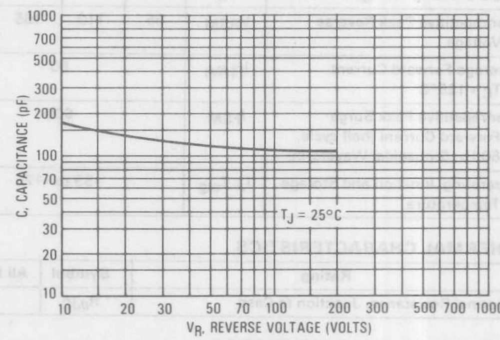
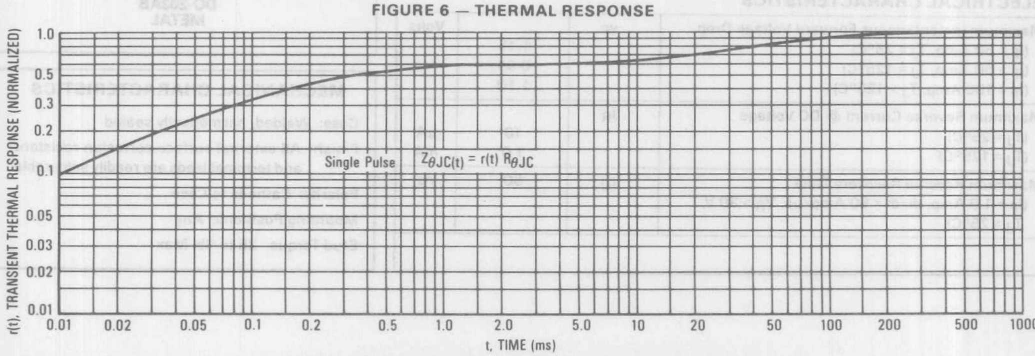


FIGURE 6 — THERMAL RESPONSE



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Switchmode Power Rectifiers

MUR7005
MUR7010
MUR7015
MUR7020

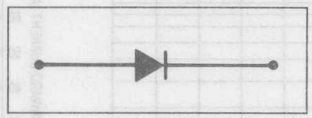
... designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

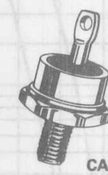
- Ultrafast 50 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Hermetically Sealed Metal DO-203AB (DO-5) Package

Mechanical Characteristics
Case: Welded, hermetically sealed
Finish: All external surface corrosion resistant and terminal leads are readily solderable
Polarity: Cathode to Case
Mounting Positions: Any
Stud Torque: 25 in./lb. Max

ULTRAFAST RECTIFIERS
70 AMPERES
50 TO 200 VOLTS

3





CASE 257-01
DO-203AB

MAXIMUM RATINGS

Rating	Symbol	MUR 7005	MUR 7010	MUR 7015	MUR 7020	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Nonrepetitive Peak Reverse Voltage	V_{RSM}	55	110	165	220	Volts
Average Forward Current $T_C = 125°C$	$I_{F(AV)}$	70				Amps
Nonrepetitive Peak Surge Forward Current (half cycle, 60 Hz, Sinusoidal Waveform)	I_{FSM}	1000				Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	−55 to +175				°C

THERMAL CHARACTERISTICS

Rating	Symbol	All Devices	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.8	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage Drop (i_F = 70 Amps, T_J = 25°C) (i_F = 70 Amps, T_J = 150°C)	v_F	 0.975 0.840	Volts
Maximum Reverse Current @ DC Voltage (T_J = 25°C) (T_J = 150°C)	I_R	 25 30	 μA mA
Maximum Reverse Recovery Time (I_F = 1 Amp, di/dt = 50 Amps/μs, V_R = 30 V, T_J = 25°C) (I_F = 0.5 Amp, i_R = 1 Amp, I_{REC} = 0.25 A, V_R = 30 V, T_J = 25°C)	t_{rr}	 60 50	ns

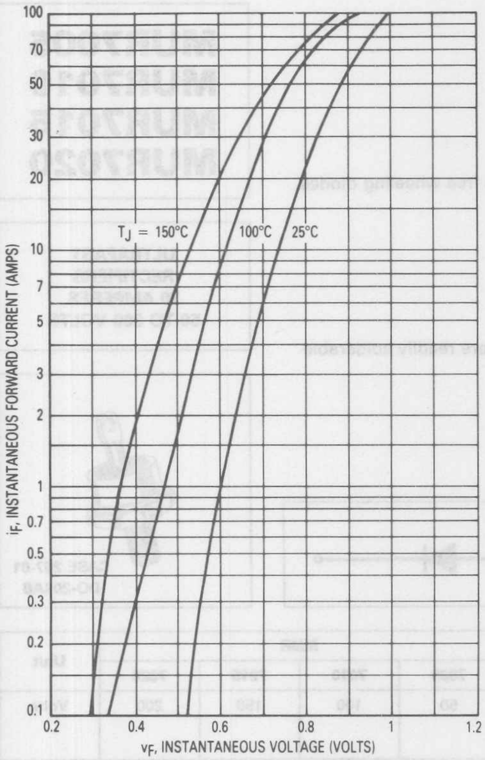


Figure 1. Typical Forward Voltage

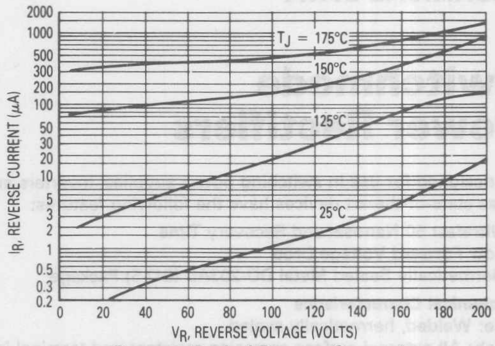


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

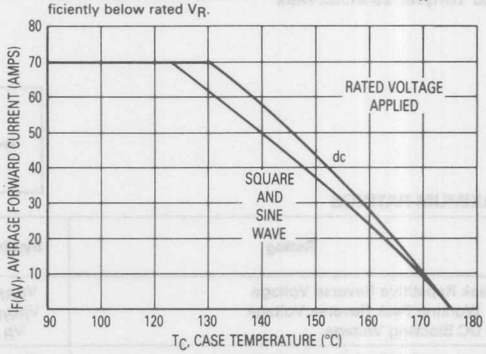


Figure 3. Current Derating, Case

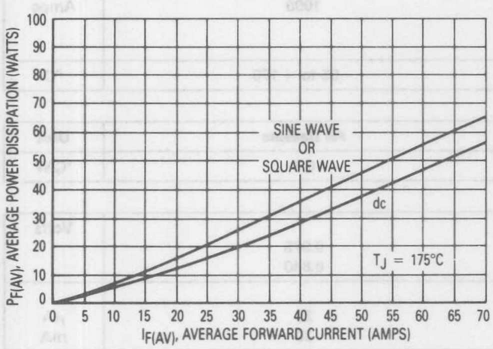


Figure 4. Average Power Dissipation

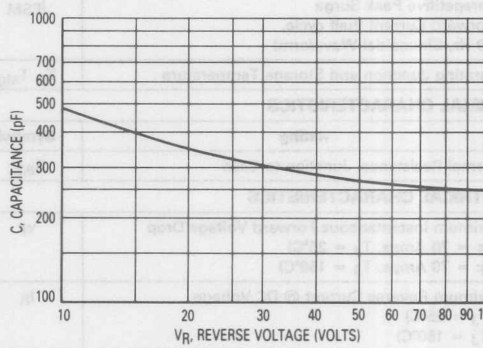


Figure 5. Typical Capacitance

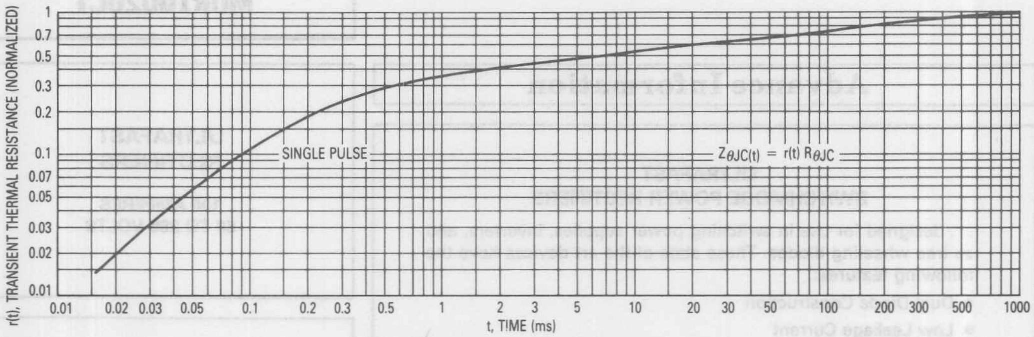
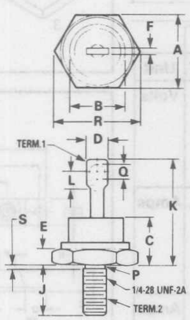


Figure 6. Thermal Response

OUTLINE DIMENSIONS



CASE 257-01
DO-203AB
(DO-5)

NOTES:
1. DIM "P" IS DIA.
2. CHAMFER OR UNDERCUT ON ONE OR BOTH ENDS OF HEXAGONAL BASE IS OPTIONAL.
3. ANGULAR ORIENTATION AND CONTOUR OF TERMINAL ONE IS OPTIONAL.
4. THREADS ARE PLATED.
5. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	16.94	17.45	0.669	0.687
B	—	16.94	—	0.667
C	—	11.43	—	0.450
D	—	9.53	—	0.375
E	2.92	5.08	0.115	0.200
F	—	2.03	—	0.080
J	10.72	11.51	0.422	0.453
K	—	25.40	—	1.000
L	3.86	—	0.156	—
P	5.59	6.32	0.220	0.249
Q	3.56	4.45	0.140	0.175
R	—	20.16	—	0.794
S	—	2.26	—	0.089

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR10005CT
MUR10010CT
MUR10015CT
MUR10020CT

Advance Information

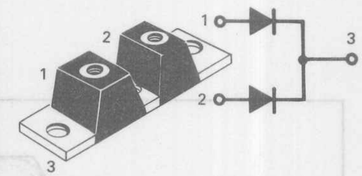
ULTRAFAST SWITCHMODE POWER RECTIFIERS

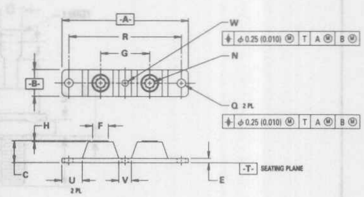
. . . designed for use in switching power supplies, inverters, and as free wheeling diodes. These state-of-the-art devices have the following features:

- Dual Diode Construction
- Low Leakage Current
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Labor Saving POWERTAP® Package

ULTRAFAST RECTIFIERS

100 AMPERES
50 TO 200 VOLTS





NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
POWER TAP

Terminal Penetration	0.300 Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

MAXIMUM RATINGS

Rating	Symbol	MUR 10005CT	MUR 10010CT	MUR 10015CT	MUR 10020CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Average Rectified Forward Current, (Rated V_R), T_C = 140°C Per Device Per Leg	$I_{F(AV)}$		100 50			Amps
Peak Repetitive Forward Current, Per Leg, (Rated V_R, Square Wave, 20 kHz), T_C = 140°C	I_{FRM}		100			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}		400			Amps
Operating Junction and Storage Temperature	T_J, T_{stg}		−65 to +175			°C

THERMAL CHARACTERISTICS PER LEG

Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Instantaneous Forward Voltage (1) (i_F = 50 Amp, T_C = 25°C)	v_F	1.10	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 250 25	μA
Maximum Reverse Recovery Time (I_F = 1.0 Amps, di/dt = 50 Amps/μs)	t_{rr}	50	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

This document contains information on a new product. Specifications and information herein are subject to change without notice.

FIGURE 1 — FORWARD VOLTAGE

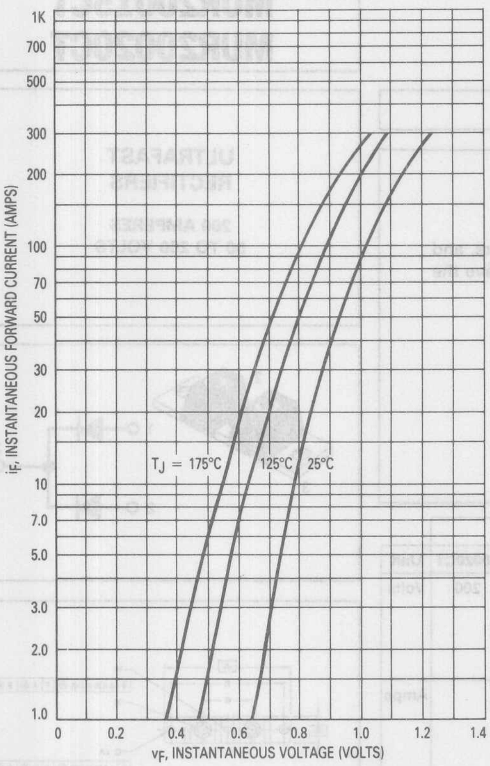
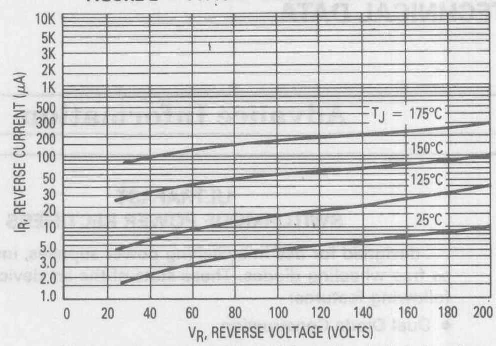


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves, if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING (PER LEG)

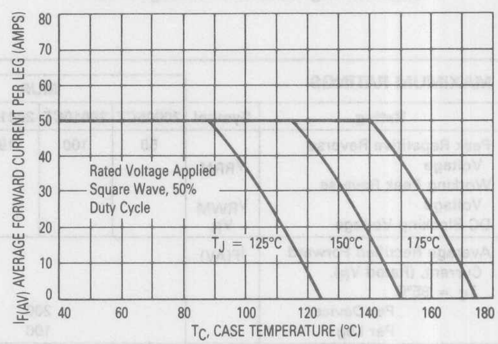


FIGURE 4 — POWER DISSIPATION (PER LEG)

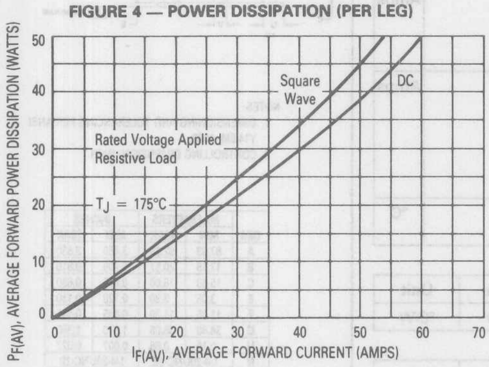
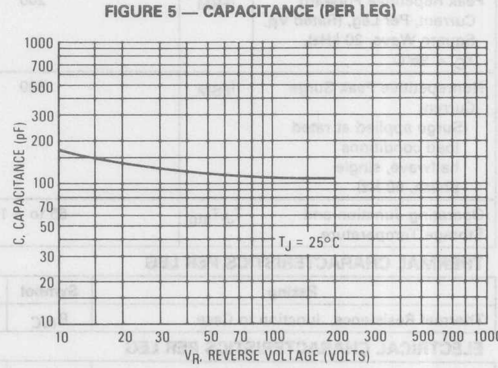


FIGURE 5 — CAPACITANCE (PER LEG)



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MUR20005CT
MUR20010CT
MUR20015CT
MUR20020CT

Advance Information

ULTRAFAST SWITCHMODE POWER RECTIFIERS

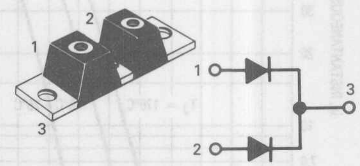
. . . designed for use in switching power supplies, inverters, and as free wheeling diodes. These state-of-the-art devices have the following features:

- Dual Diode Construction
- Low Leakage Current
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Labor Saving POWERTAP® Package

3

ULTRAFAST RECTIFIERS

200 AMPERES
50 TO 200 VOLTS



MAXIMUM RATINGS

Rating	Symbol	MUR 20005CT	MUR 20010CT	MUR 20015CT	MUR 20020CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Average Rectified Forward Current, (Rated V_R), $T_C = 95°C$ Per Device Per Leg	$I_{F(AV)}$		200 100			Amps
Peak Repetitive Forward Current, Per Leg, (Rated V_R, Square Wave, 20 kHz), $T_C = 95°C$	I_{FRM}		200			Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}		800			Amps
Operating Junction and Storage Temperature	T_J, T_{stg}		−65 to +175			°C

THERMAL CHARACTERISTICS PER LEG

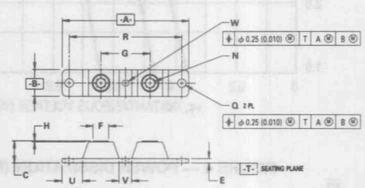
Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.70	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Instantaneous Forward Voltage (1) (i_F = 100 Amp, T_C = 25°C)	v_F	1.25	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 500 50	μA
Maximum Reverse Recovery Time (I_F = 1.0 Amps, di/dt = 50 Amps/μs)	t_{rr}	50	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

This document contains information on a new product. Specifications and information herein are subject to change without notice.



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

CASE 357C-01
POWER TAP

Terminal Penetration	0.300 Max.
Terminal Torque	25–40 lb.-in.
Mounting Base Torque	30–40 lb.-in.

FIGURE 1 — TYPICAL FORWARD VOLTAGE (PER LEG)

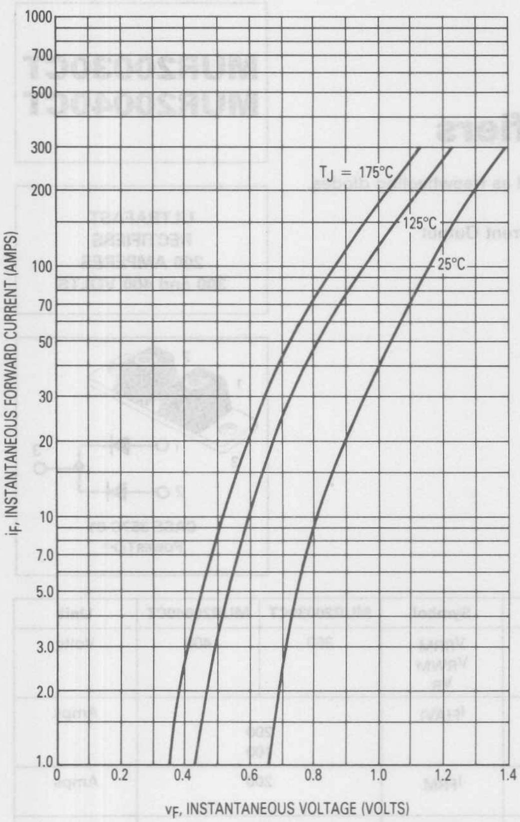
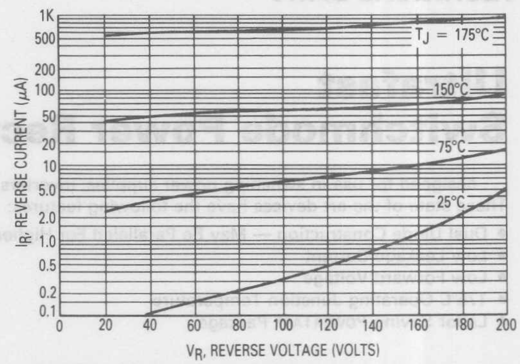


FIGURE 2 — TYPICAL REVERSE CURRENT*



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves, if V_R is sufficiently below rated V_R.

FIGURE 3 — CURRENT DERATING (PER LEG)

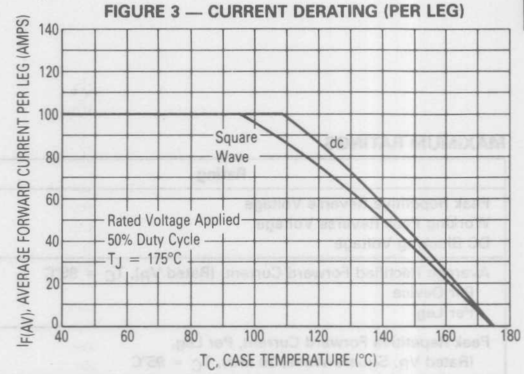


FIGURE 4 — POWER DISSIPATION (PER LEG)

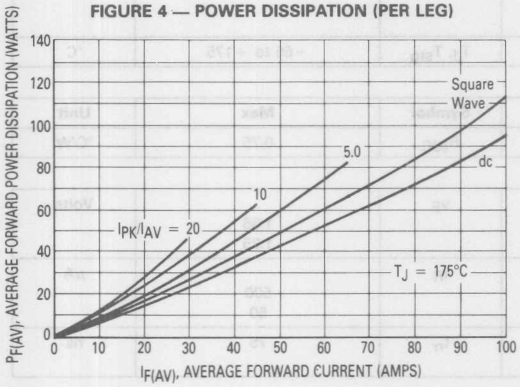
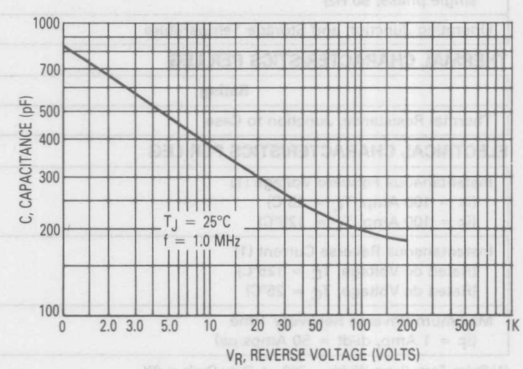


FIGURE 5 — CAPACITANCE (PER LEG)



3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

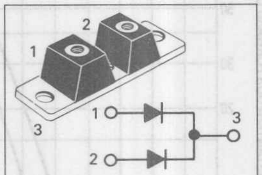
Ultrafast Switchmode Power Rectifiers

MUR20030CT
MUR20040CT

. . . designed for use in switching power supplies, inverters, and as freewheeling diodes. These state-of-the-art devices have the following features:

- Dual Diode Construction — May Be Paralleled For Higher Current Output
- Low Leakage Current
- Low Forward Voltage
- 175°C Operating Junction Temperature
- Labor Saving POWERTAP® Package

ULTRAFAST RECTIFIERS 200 AMPERES 300 and 400 VOLTS



CASE 357C-01
POWERTAP®

3

MAXIMUM RATINGS

Rating	Symbol	MUR20030CT	MUR20040CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	300	400	Volts
Average Rectified Forward Current, (Rated V_R), $T_C = 95°C$ Per Device Per Leg	$I_{F(AV)}$	200 100		Amps
Peak Repetitive Forward Current, Per Leg, (Rated V_R, Square Wave, 20 kHz), $T_C = 95°C$	I_{FRM}	200		Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	800		Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	−65 to +175		°C

THERMAL CHARACTERISTICS PER LEG

Rating	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.75	°C/W

ELECTRICAL CHARACTERISTICS PER LEG

Rating	Symbol	Max	Unit
Instantaneous Forward Voltage (1) (i_F = 100 Amp, T_C = 25°C) (i_F = 100 Amp, T_C = 125°C)	v_F	 1.35 1.25	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, T_C = 125°C) (Rated dc Voltage, T_C = 25°C)	i_R	 500 50	μA
Maximum Reverse Recovery Time (I_F = 1 Amp, di/dt = 50 Amps/μs)	t_{rr}	75	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

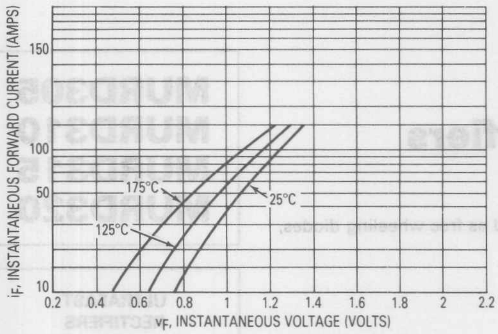


Figure 1. Typical Forward Voltage

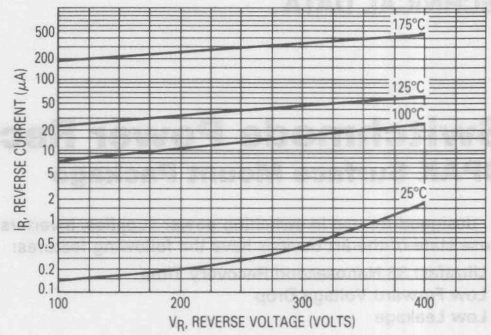


Figure 2. Typical Reverse Current

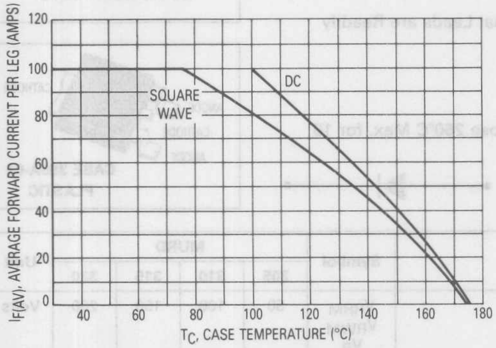


Figure 3. Current Derating (Per Leg)

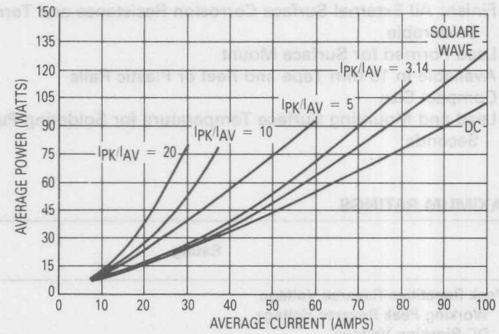


Figure 4. Average Power Dissipation and Average Current

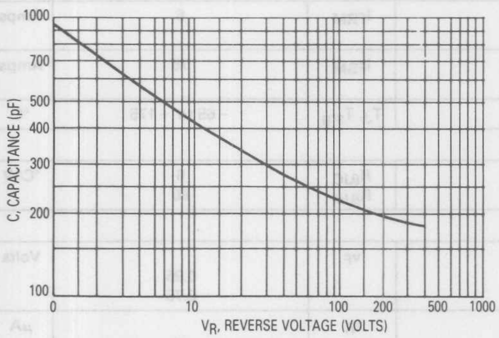
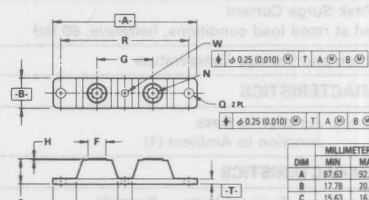


Figure 5. Capacitance (Per Leg)

OUTLINE DIMENSIONS



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	87.63	92.20	3.450	3.630
B	17.78	20.57	0.700	0.810
C	15.63	16.00	0.615	0.630
E	3.05	3.30	0.120	0.130
F	11.05	11.30	0.435	0.445
G	34.80	35.05	1.370	1.380
H	0.18	0.68	0.007	0.027
N	1/4-20UNC-2B		1/4-20UNC-2B	
Q	6.86	7.23	0.270	0.285
R	80.01 BSC		3.150 BSC	
U	15.24	16.00	0.600	0.630
V	8.39	9.52	0.330	0.375
W	4.32	4.82	0.170	0.190

TERMINAL PENETRATION	0.280 MAX
TERMINAL TORQUE	50–100 LB.-IN.
MOUNTING BASE TORQUE	30–40 LB.-IN.

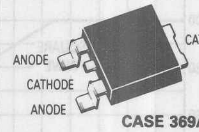
CASE 357C-01
POWERTAP®

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Switchmode Power Rectifiers
DPAK Surface Mount Package

MURD305
MURD310
MURD315
MURD320

ULTRAFAST RECTIFIERS
3 AMPERES
50 TO 200 VOLTS



CASE 369A-04
PLASTIC

. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Low Leakage

Mechanical Characteristics
- Case: Epoxy, Molded
- Finish: All External Surface Corrosion Resistance and Terminal Leads are Readily Solderable
- Lead Formed for Surface Mount
- Available in 16 mm Tape and Reel or Plastic Rails
- Compact Size
- Lead and Mounting Surface Temperature for Soldering Purpose 260°C Max. for 10 Seconds

MAXIMUM RATINGS

Rating	Symbol	MURD 305	MURD 310	MURD 315	MURD 320	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Average Rectified Forward Current (T_C = 158°C, Rated V_R)	$I_{F(AV)}$	3				Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz, T_C = 158°C)	I_{FRM}	6				Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, 60 Hz)	I_{FSM}	75				Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	−65 to +175				°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Case Junction to Ambient (1)	$R_{\theta JC}$ $R_{\theta JA}$	6 80	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage Drop (2) (i_F = 3 Amps, T_J = 25°C) (i_F = 3 Amps, T_J = 125°C)	v_F	 0.95 0.75	Volts
Maximum Instantaneous Reverse Current (2) (T_J = 25°C, Rated dc Voltage) (T_J = 125°C, Rated dc Voltage)	i_R	 5 500	μA
Maximum Reverse Recovery Time (I_F = 1 Amp, di/dt = 50 Amps/μs, V_R = 30 V, T_J = 25°C) (I_F = 0.5 Amp, i_R = 1 Amp, I_{REC} = 0.25 A, V_R = 30 V, T_J = 25°C)	t_{rr}	 35 25	ns

(1) Rating applies when surface mounted on the minimum pad sizes recommended.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

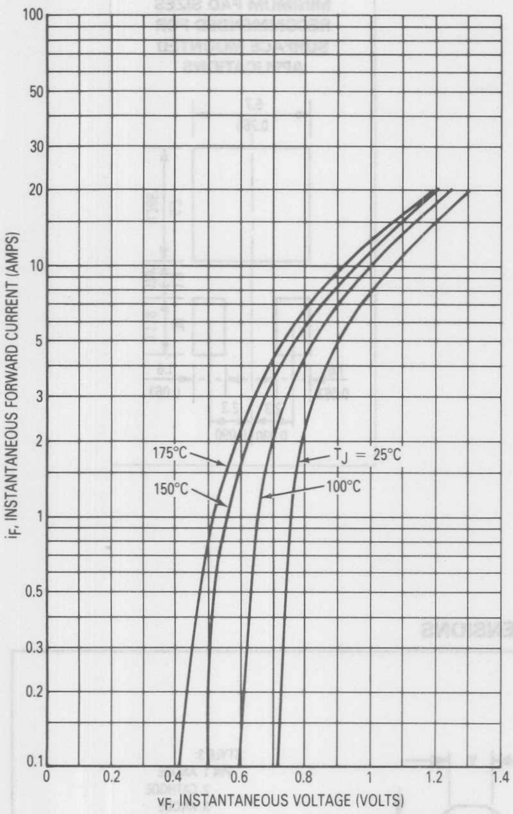
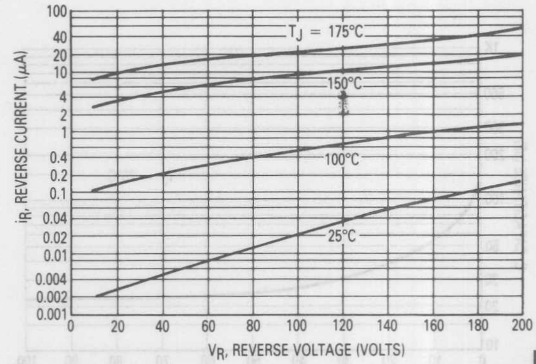


Figure 1. Typical Forward Voltage



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Reverse Current*

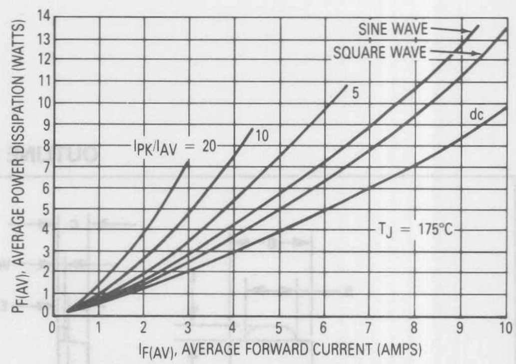


Figure 3. Average Power Dissipation

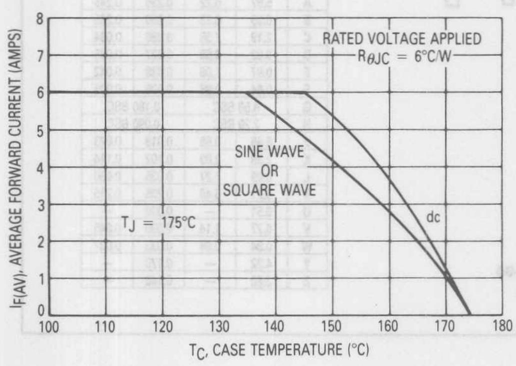


Figure 4. Current Derating, Case

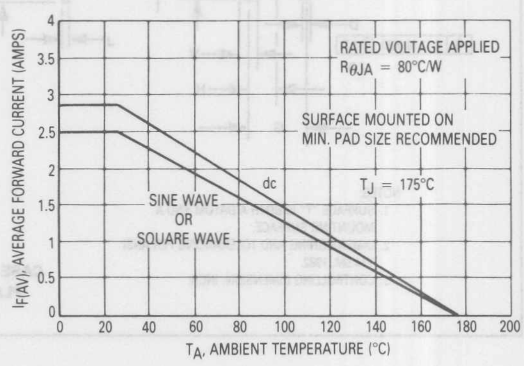


Figure 5. Current Derating, Ambient

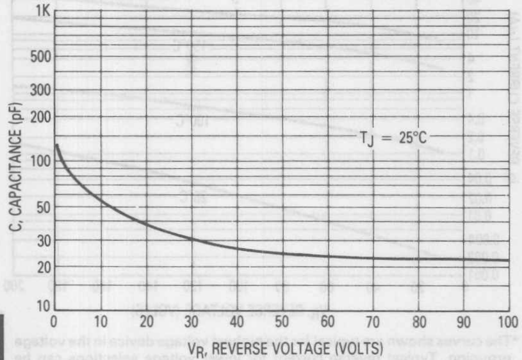
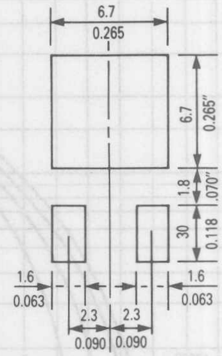
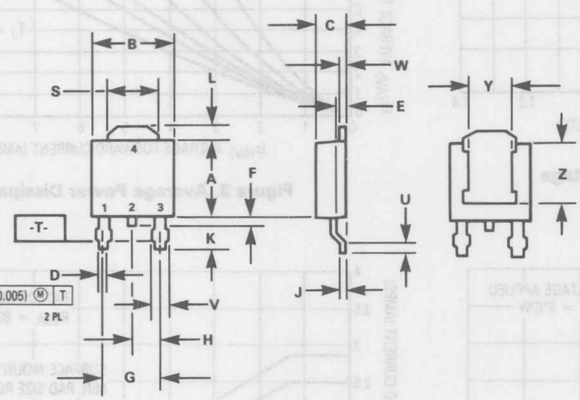


Figure 6. Typical Capacitance

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



OUTLINE DIMENSIONS



STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.69	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.88	0.025	0.035
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	6.46	0.58	0.018	0.023
K	2.59	2.89	0.102	0.114
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—
Z	3.69	—	0.145	—

NOTES:
1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

CASE 369A-04
PLASTIC

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Switchmode Power Rectifiers

DPAK Surface Mount Package

MURD605CT
MURD610CT
MURD615CT
MURD620CT

ULTRAFAST RECTIFIERS
6 AMPERES
50 TO 200 VOLTS

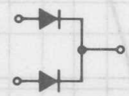
3

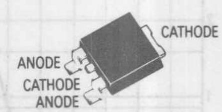
. . . designed for use in switching power supplies, inverters and as free wheeling diodes, these state-of-the-art devices have the following features:

- Ultrafast 35 Nanosecond Recovery Time
- Low Forward Voltage Drop
- Low Leakage

Mechanical Characteristics

- Case: Epoxy, Molded
- Finish: All External Surface Corrosion Resistance and Terminal Leads are Readily Solderable
- Lead Formed for Surface Mount
- Available in 16 mm Tape and Reel or Plastic Rails
- Compact Size
- Dual Rectifier Single Chip Construction
- Lead Temperature for Soldering Purpose: 260°C for 10 Seconds





CASE 369A-04
PLASTIC

MAXIMUM RATINGS

Rating	Symbol	MURD 605CT	MURD 610CT	MURD 615CT	MURD 620CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	50	100	150	200	Volts
Average Rectified Forward Voltage Per Diode (T_C = 145°C, Rated V_R) Per Device	$I_{F(AV)}$	3 6				Amps
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz, T_C = 145°C) Per Diode	I_F	6				Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions, halfwave, 60 Hz)	I_{FSM}	63				Amps
Operating Junction and Storage Temperature	T_J, T_{stg}	−65 to +175				°C

THERMAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case Junction to Ambient (1)	$R_{\theta JC}$ $R_{\theta JA}$	9 80	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage Drop (2) i_F = 3 Amps, T_C = 25°C i_F = 3 Amps, T_C = 125°C i_F = 6 Amps, T_C = 25°C i_F = 6 Amps, T_C = 125°C	v_F	 1 0.95 1.2 1.1	Volts
Maximum Instantaneous Reverse Current (2) (T_J = 25°C, Rated dc Voltage) (T_J = 125°C, Rated dc Voltage)	i_R	 5 250	μA
Maximum Reverse Recovery Time (I_F = 1 Amp, di/dt = 50 Amps/μs, V_R = 30 V, T_J = 25°C) (I_F = 0.5 Amp, i_R = 1 Amp, I_{REC} = 0.25 A, V_R = 30 V, T_J = 25°C)	t_{rr}	 35 25	ns

(1) Rating applies when surface mounted on the minimum pad size recommended.
(2) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

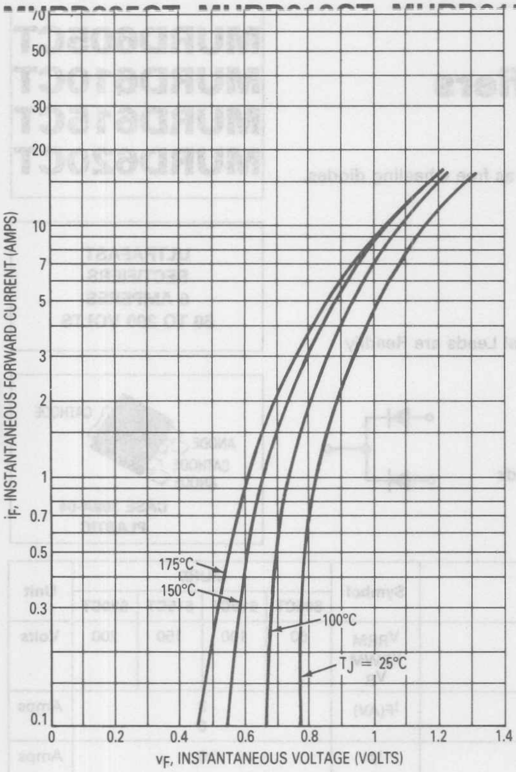
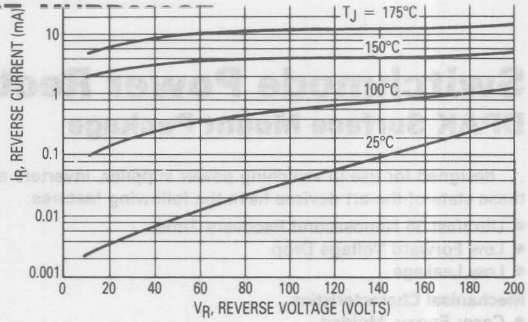


Figure 1. Typical Forward Voltage (Per Leg)



*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if V_R is sufficient below rated V_R.

Figure 2. Typical Leakage Current* (Per Leg)

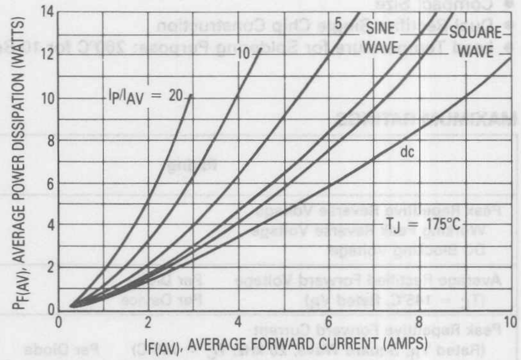


Figure 3. Average Power Dissipation (Per Leg)

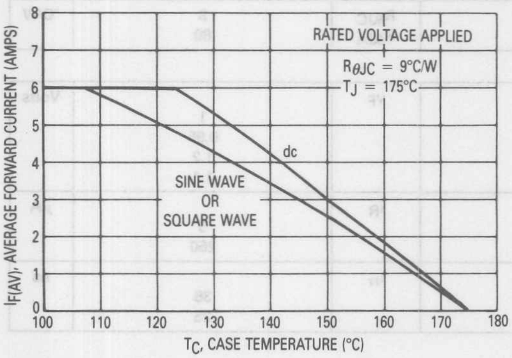


Figure 4. Current Derating, Case (Per Leg)

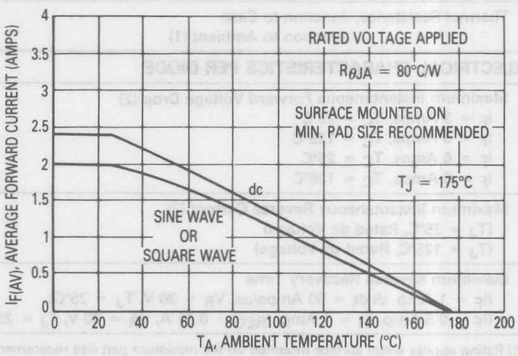


Figure 5. Current Derating, Ambient (Per Leg)

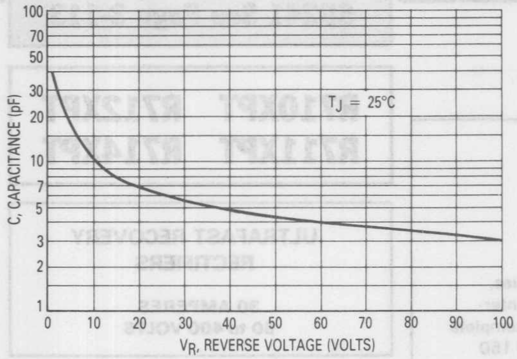
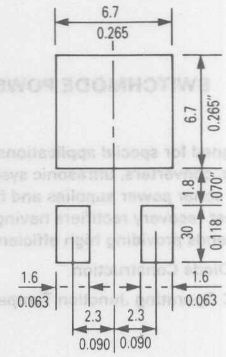
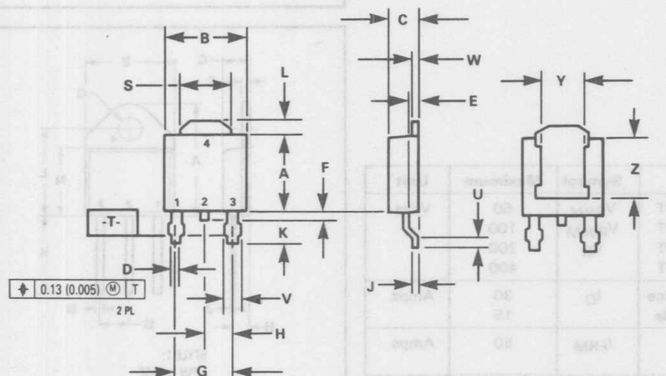


Figure 6. Typical Capacitance (Per Leg)

MINIMUM PAD SIZES RECOMMENDED FOR SURFACE MOUNTED APPLICATIONS



OUTLINE DIMENSIONS



STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.97	6.22	0.235	0.245
B	6.35	6.73	0.250	0.265
C	2.19	2.38	0.086	0.094
D	0.69	0.88	0.027	0.035
E	0.97	1.06	0.038	0.042
F	0.64	0.88	0.025	0.035
G	4.58 BSC		0.180 BSC	
H	2.29 BSC		0.090 BSC	
J	6.46	0.58	0.018	0.023
K	2.59	2.89	0.102	0.114
L	0.89	1.27	0.035	0.050
S	5.21	5.46	0.205	0.215
U	0.51	—	0.020	—
V	0.77	1.14	0.030	0.045
W	0.84	0.94	0.033	0.037
Y	4.32	—	0.170	—
Z	3.69	—	0.145	—

NOTES:
1. SURFACE "T" IS BOTH A DATUM AND A MOUNTING SURFACE.
2. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION: INCH.

CASE 369A-04
PLASTIC

3

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

SD41 See Page 3-72
SD51 See Page 3-76
SD241 See Page 3-113

R710XPT R712XPT
R711XPT R714XPT

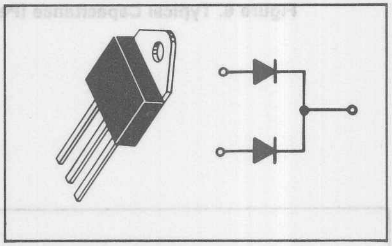
SWITCHMODE POWER RECTIFIERS

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference, sonar power supplies and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 150 nanoseconds providing high efficiency at frequencies to 50 kHz.

- Dual Diode Construction
- 150°C Operating Junction Temperature

ULTRAFAST RECOVERY RECTIFIERS

30 AMPERES
50 to 400 VOLTS



3

MAXIMUM RATINGS

Rating		Symbol	Maximum	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	R710XPT R711XPT R712XPT R714XPT	V_{RRM} V_{RWM} V_R	50 100 200 400	Volts
Average Rectified Forward Current (Rated V_R) $T_C = 100°C$	Per Device Per Diode	I_O	30 15	Amps
Peak Repetitive Forward Current, Per Diode (1 Second at 60 Hz, $T_C = 100°C$)		I_{FRM}	50	Amps
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I_{FSM}	150	Amps
Operating Junction and Storage Temperature		T_J, T_{stg}	-65 to +150	°C

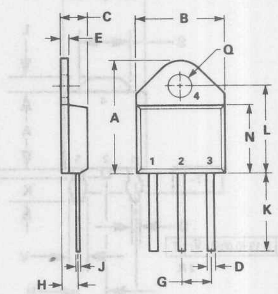
THERMAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Maximum	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE

Characteristic	Symbol	Maximum	Unit
Instantaneous Forward Voltage (1) (i_F = 15 Amp, $T_C = 25°C$)	v_F	1.30	Volts
Instantaneous Reverse Current (1) (Rated dc Voltage, $T_C = 100°C$) (Rated dc Voltage, $T_C = 25°C$)	i_R	 1.0 0.015	mA
Reverse Recovery Time (I_F = 1.0 Ampere to V_R = 30 Vdc)	t_{rr}	100	ns

(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%



STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	20.32	21.08	0.800	0.830
B	15.49	15.90	0.610	0.626
C	4.19	5.08	0.165	0.200
D	1.02	1.65	0.040	0.065
E	1.35	1.65	0.053	0.065
G	5.21	5.72	0.205	0.225
H	2.65	2.94	0.104	0.116
J	0.38	0.64	0.015	0.025
K	12.70	15.49	0.500	0.610
L	15.88	16.51	0.625	0.650
N	12.19	12.70	0.480	0.500
Q	4.04	4.22	0.159	0.166

CASE 340-02
TO-218AC
PLASTIC

FIGURE 1 — TYPICAL FORWARD VOLTAGE

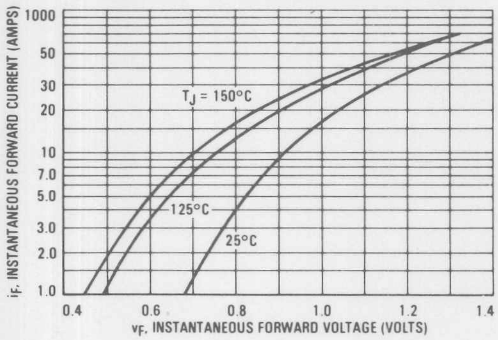


FIGURE 2 — TYPICAL REVERSE CURRENT

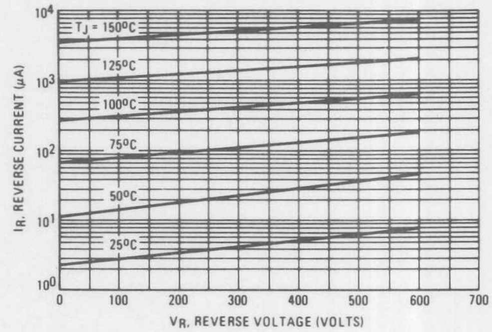


FIGURE 3 — CURRENT DERATING — TOTAL UNIT

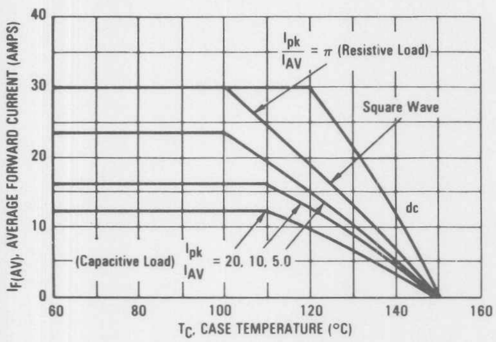


FIGURE 4 — TYPICAL CAPACITANCE

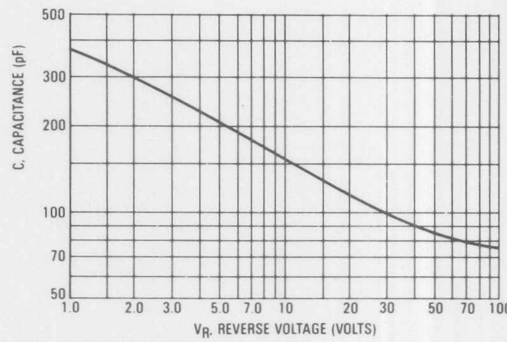


FIGURE 5 — POWER DISSIPATION — TOTAL UNIT

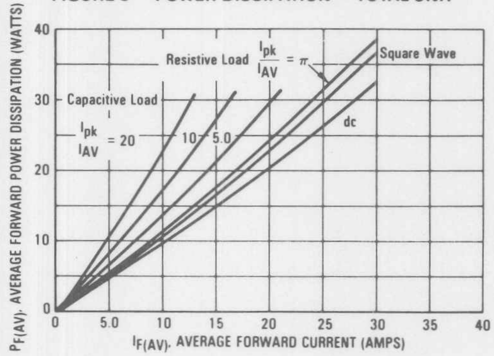
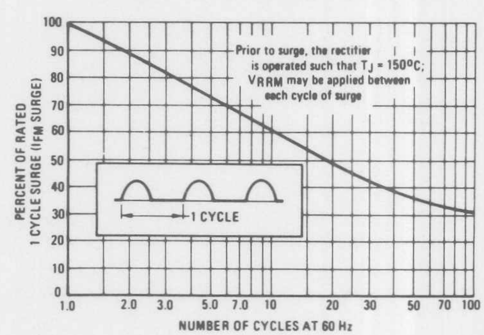


FIGURE 6 — MAXIMUM SURGE CAPABILITY



3

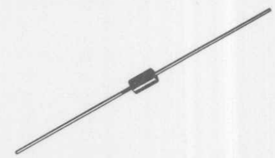
Zener Diode Data Sheets

4

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

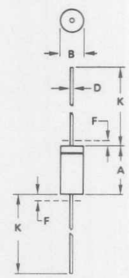
1/4M2.4AZ10 thru 1/4M105Z10

1/4 WATT
SILICON ZENER DIODES
2.4-105 VOLTS



1/4 WATT SILICON ZENER DIODES

Hermetically sealed, all-glass case with all external surfaces corrosion resistant. Cathode end, indicated by color band, will be positive with respect to anode end when operated in the zener region. These devices are in the same 400 mW glass package as the 1N746 and 1N957 Series, but designated 1/4 Watt to allow characterization at a different test current level.



NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

MAXIMUM RATINGS

Junction and Storage Temperature: −65°C to +175°C
DC Power Dissipation: 1/4 Watt (Derate 1.67 mW/°C Above 25°C)

The type numbers specified have a standard voltage (V_Z) tolerance of ±10%. For closer tolerances, add suffix "5" for ±5%, (3%, 2%, 1% tolerances also available).

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V max @ 100 mA)

Type No.	Nominal Zener Voltage @ I_{ZT} (V_Z) Volts	Test Current (I_{ZT}) mA	Maximum Zener Impedance (Z_{ZT}) @ I_{ZT} Ohms	Maximum DC Zener Current (I_{ZM}) mA	Reverse Leakage Current I_R Max (μA)	Test Voltage Vdc* V_{R1}	Test Voltage Vdc* V_{R2}
1/4M2.4AZ10	2.4	10	60	70	75	1	1
1/4M2.7AZ10	2.7	10	60	65	75	1	1
1/4M3.0AZ10	3.0	10	55	60	50	1	1
1/4M3.3AZ10	3.3	10	55	55	50	1	1
1/4M3.6AZ10	3.6	10	50	52	50	1	1

*V_{R1} — Test Voltage for 5% Tolerance Device

V_{R2} — Test Voltage for 10% Tolerance Device

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V max @ 100 mA)

Type No.	Nominal Zener Voltage @ I_{ZT} (V_Z) Volts	Test Current (I_{ZT}) mA	Maximum Zener Impedance (Z_{ZT}) @ I_{ZT} Ohms	Maximum DC Zener Current (I_{ZM}) mA	Reverse Leakage Current I_R Max (µA)	Test Voltage Vdc* V_{R1}	Test Voltage Vdc* V_{R2}
1/4M3.9AZ10	3.9	10	50	49	25	1	1
1/4M4.3AZ10	4.3	10	45	46	25	1.5	1.5
1/4M4.7AZ10	4.7	10	35	42	10	1.5	1.5
1/4M5.1AZ10	5.1	10	25	39	5	1.5	1.5
1/4M5.6AZ10	5.6	10	20	36	5	1.5	1.5
1/4M6.2AZ10	6.2	10	15	33	5	3.5	3.5
1/4M6.8Z10	6.8	9.2	7.0	33	150	5.2	4.9
1/4M7.5Z10	7.5	8.3	8.0	30	75	5.7	5.4
1/4M8.2Z10	8.2	7.6	9.0	26	50	6.2	5.9
1/4M9.1Z10	9.1	6.9	10	24	25	6.9	6.6
1/4M10Z10	10	6.3	11	21	10	7.6	7.2
1/4M11Z10	11	5.7	13	19	5	8.4	8.0
1/4M12Z10	12	5.2	15	18	5	9.1	8.6
1/4M13Z10	13	4.8	18	16	5	9.9	9.4
1/4M14Z10	14	4.5	20	15	5	10.6	10.1
1/4M15Z10	15	4.2	22	14	5	11.4	10.8
1/4M16Z10	16	3.9	24	13	5	12.2	11.5
1/4M17Z10	17	3.7	26	12.5	5	13.0	12.2
1/4M18Z10	18	3.5	28	11.5	5	13.7	13.0
1/4M19Z10	19	3.3	30	11.0	5	14.4	13.7
1/4M20Z10	20	3.1	33	10.5	5	15.2	14.4
1/4M22Z10	22	2.8	40	9.5	5	16.7	15.8
1/4M24Z10	24	2.6	46	9.0	5	18.2	17.3
1/4M25Z10	25	2.5	50	8.0	5	19.0	18.0
1/4M27Z10	27	2.3	58	7.5	5	20.6	19.4
1/4M30Z10	30	2.1	70	7.0	5	22.8	21.6
1/4M33Z10	33	1.9	85	6.5	5	25.1	23.8
1/4M36Z10	36	1.7	100	6.0	5	27.4	25.9
1/4M39Z10	39	1.6	120	5.0	5	29.7	28.1
1/4M43Z10	43	1.5	140	4.8	5	32.7	31.0
1/4M45Z10	45	1.4	150	4.5	5	34.2	32.4
1/4M47Z10	47	1.3	160	4.3	5	35.8	33.8
1/4M50Z10	50	1.2	180	4.1	5	38.0	36.0
1/4M52Z10	52	1.2	200	4.0	5	39.5	37.4
1/4M56Z10	56	1.1	230	3.8	5	42.6	40.3
1/4M62Z10	62	1.0	290	3.3	5	47.1	44.6
1/4M68Z10	68	0.92	350	3.0	5	51.7	49.0
1/4M75Z10	75	0.83	450	2.8	5	56.0	54.0
1/4M82Z10	82	0.76	550	2.5	5	62.2	59.0
1/4M91Z10	91	0.69	700	2.3	5	69.2	65.5
1/4M100Z10	100	0.63	900	2.0	5	76.0	72.0
1/4M105Z10	105	0.60	1000	1.9	5	79.8	75.6

*V_{R1} — Test Voltage for 5% Tolerance Device

V_{R2} — Test Voltage for 10% Tolerance Device

SPECIAL SELECTIONS AVAILABLE INCLUDE:

1 — Nominal zener voltages between those shown.

2 — Matches sets: (Standard Tolerances are ±5.0%, ±3.0%, ±2.0%, ±1.0%) depending on voltage per device.

a. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make possible higher zener voltages and provide lower temperature coefficients, lower dynamic impedance and greater power handling ability.

b. Two or more units matched to one another with any specified tolerance.

3 — Tight voltage tolerances: 1.0%, 2.0%, 3.0%.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1.5KE6.8,A thru 1.5KE200,A
See Page 4-71

Designers Data Sheet

500-MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

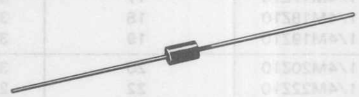
- Complete Voltage Range — 2.4 to 110 Volts
- DO-35 Package — Smaller than Conventional DO-7 Package
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die

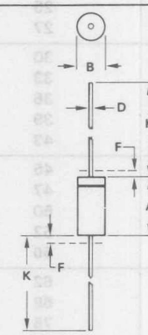
Designer's Data for "Worst Case" Conditions

The Designer's Data sheets permit the design of most circuits entirely from the information presented. Limit curves – representing boundaries on device characteristics – are given to facilitate "worst case" design.

1N746 thru 1N759
1N957A thru 1N986A
1N4370 thru 1N4372

GLASS ZENER DIODES
500 MILLIWATTS
2.4-110 VOLTS





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

4

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_L \leq 50^oC$, Lead Length = 3/8"	P_D		
*JEDEC Registration		400	mW
*Derate above $T_L = 50^oC$		3.2	$mW/^oC$
Motorola Device Ratings		500	mW
Derate above $T_L = 50^oC$		3.33	$mW/^oC$
Operating and Storage Junction Temperature Range	T_J, T_{stg}		^oC
*JEDEC Registration		-65 to +175	
Motorola Device Ratings		-65 to +200	

*Indicates JEDEC Registered Data.

MECHANICAL CHARACTERISTICS

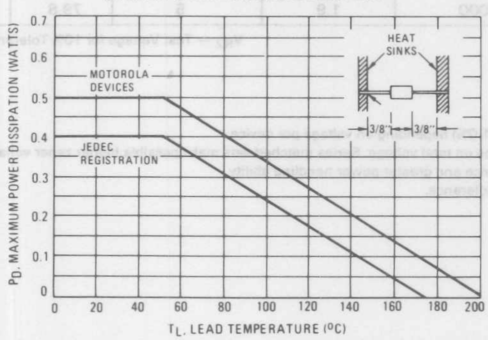
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from case for 10 seconds

FINISH: All external surfaces are corrosion resistant with readily solderable leads.

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.

MOUNTING POSITION: Any

STEADY STATE POWER DERATING



1N746 thru 1N759, 1N957A thru 1N986A, 1N4370 thru 1N4372

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V max at 200 mA for all types)

Type Number (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} (Note 2) Volts	Test Current I_{ZT} mA	Maximum Zener Impedance Z_{ZT} @ I_{ZT} (Note 3) Ohms	*Maximum DC Zener Current I_{ZM} (Note 4) mA		Maximum Reverse Leakage Current T_A = 25°C I_R @ V_R = 1 V µA	Maximum Reverse Leakage Current T_A = 150°C I_R @ V_R = 1 V µA
1N4370	2.4	20	30	150	190	100	200
1N4371	2.7	20	30	135	165	75	150
1N4372	3.0	20	29	120	150	50	100
1N746	3.3	20	28	110	135	10	30
1N747	3.6	20	24	100	125	10	30
1N748	3.9	20	23	95	115	10	30
1N749	4.3	20	22	85	105	2	30
1N750	4.7	20	19	75	95	2	30
1N751	5.1	20	17	70	85	1	20
1N752	5.6	20	11	65	80	1	20
1N753	6.2	20	7	60	70	0.1	20
1N754	6.8	20	5	55	65	0.1	20
1N755	7.5	20	6	50	60	0.1	20
1N756	8.2	20	8	45	55	0.1	20
1N757	9.1	20	10	40	50	0.1	20
1N758	10	20	17	35	45	0.1	20
1N759	12	20	30	30	35	0.1	20

Type Number (Note 1)	Nominal Zener Voltage V_Z (Note 2) Volts	Test Current I_{ZT} mA	Maximum Zener Impedance (Note 3) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	*Maximum DC Zener Current I_{ZM} (Note 4) mA		Maximum Reverse Current I_R Maximum µA	Test Voltage Vdc V_R 5%	10%
1N957A	6.8	18.5	4.5	700	1.0	47	61	150	5.2	4.9
1N958A	7.5	16.5	5.5	700	0.5	42	55	75	5.7	5.4
1N959A	8.2	15	6.5	700	0.5	38	50	50	6.2	5.9
1N960A	9.1	14	7.5	700	0.5	35	45	25	6.9	6.6
1N961A	10	12.5	8.5	700	0.25	32	41	10	7.6	7.2
1N962A	11	11.5	9.5	700	0.25	28	37	5	8.4	8.0
1N963A	12	10.5	11.5	700	0.25	26	34	5	9.1	8.6
1N964A	13	9.5	13	700	0.25	24	32	5	9.9	9.4
1N965A	15	8.5	16	700	0.25	21	27	5	11.4	10.8
1N966A	16	7.8	17	700	0.25	19	37	5	12.2	11.5
1N967A	18	7.0	21	750	0.25	17	23	5	13.7	13.0
1N968A	20	6.2	25	750	0.25	15	20	5	15.2	14.4
1N969A	22	5.6	29	750	0.25	14	18	5	16.7	15.8
1N970A	24	5.2	33	750	0.25	13	17	5	18.2	17.3
1N971A	27	4.6	41	750	0.25	11	15	5	20.6	19.4
1N972A	30	4.2	49	1000	0.25	10	13	5	22.8	21.6
1N973A	33	3.8	58	1000	0.25	9.2	12	5	25.1	23.8
1N974A	36	3.4	70	1000	0.25	8.5	11	5	27.4	25.9
1N975A	39	3.2	80	1000	0.25	7.8	10	5	29.7	28.1
1N976A	43	3.0	93	1500	0.25	7.0	9.6	5	32.7	31.0
1N977A	47	2.7	105	1500	0.25	6.4	8.8	5	35.8	33.8
1N978A	51	2.5	125	1500	0.25	5.9	8.1	5	38.8	36.7
1N979A	56	2.2	150	2000	0.25	5.4	7.4	5	42.6	40.3
1N980A	62	2.0	185	2000	0.25	4.9	6.7	5	47.1	44.6
1N981A	68	1.8	230	2000	0.25	4.5	6.1	5	51.7	49.0
1N982A	75	1.7	270	2000	0.25	1.0	5.5	5	56.0	54.0
1N983A	82	1.5	330	3000	0.25	3.7	5.0	5	62.2	59.0
1N984A	91	1.4	400	3000	0.25	3.3	4.5	5	69.2	65.5
1N985A	100	1.3	500	3000	0.25	3.0	4.5	5	76	72
1N986A	110	1.1	750	4000	0.25	2.7	4.1	5	83.6	79.2

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance Designation

The type numbers shown have tolerance designations as follows:

1N4370 series: ±10%, suffix A for ±5% units,
C for ±2%, D for ±1%.

1N746 series: ±10%, suffix A for ±5% units,
C for ±2%, D for ±1%.

1N957 series: ±10%, suffix A for ±10% units,
C for ±2%, D for ±1%,
suffix B for ±5% units,
C for ±2%, D for ±1%.

Voltage Designation

To designate units with zener voltages other than those listed, the Motorola type number should be modified as shown below. Unless otherwise specified, the electrical characteristics other than the nominal voltage (V_Z) and test voltage for leakage current will conform to the characteristics of the next higher voltage type shown in the table.

Matched Sets for Closer Tolerances or Higher Voltages

Series matched sets make zener voltages in excess of 100 volts or tolerances of less than 5% possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.

For Matched Sets or other special circuit requirements, contact your Motorola Sales Representative.

NOTE 2. ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium at the lead temperature of 30°C ± 1°C and 3/8″ lead length.

NOTE 3. ZENER IMPEDANCE (Z_Z) DERIVATION

Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac) = 0.1\ I_Z(dc)$ with the ac frequency = 60 Hz.

NOTE 4. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum zener current ratings are based on the maximum voltage of a 10% 1N746 type unit or a 20% 1N957 type unit. For closer tolerance units (10% or 5%) or units where the actual zener voltage (V_Z) is known at the operating point, the maximum zener current may be increased and is limited by the derating curve.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30-40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 1 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 3 and 4.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

FIGURE 1 – TYPICAL THERMAL RESISTANCE

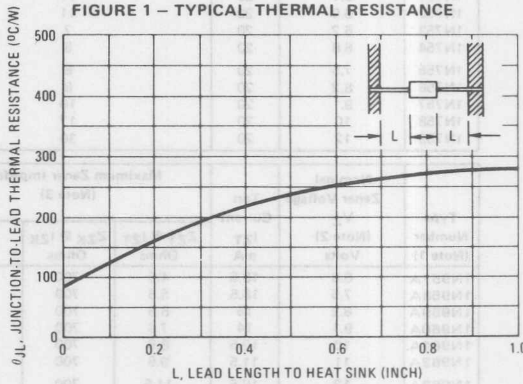


FIGURE 2 – TYPICAL LEAKAGE CURRENT

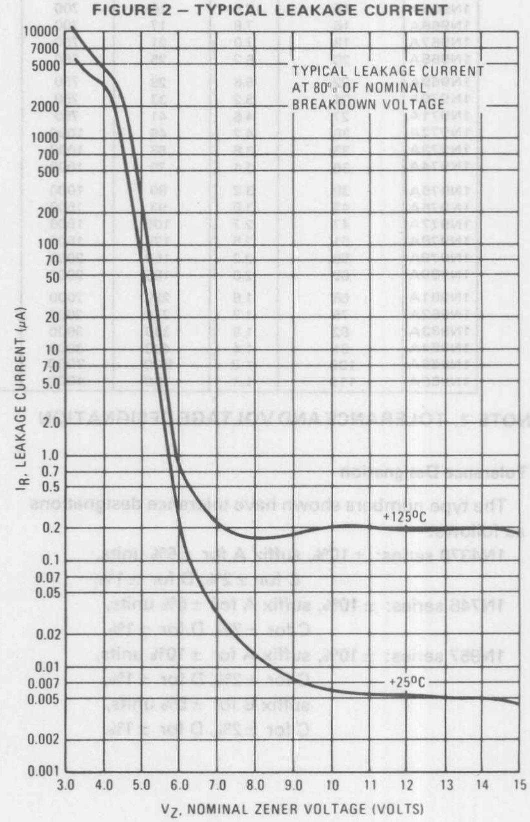
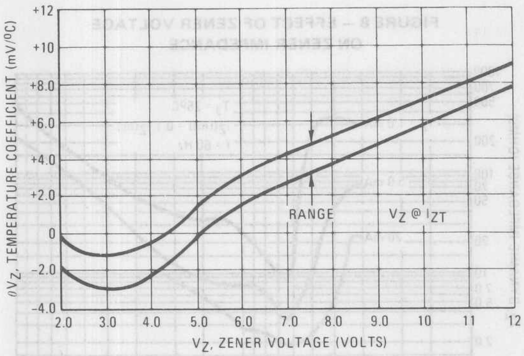


FIGURE 3 – TEMPERATURE COEFFICIENTS

(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

a – RANGE FOR UNITS TO 12 VOLTS



b – RANGE FOR UNITS 12 TO 100 VOLTS

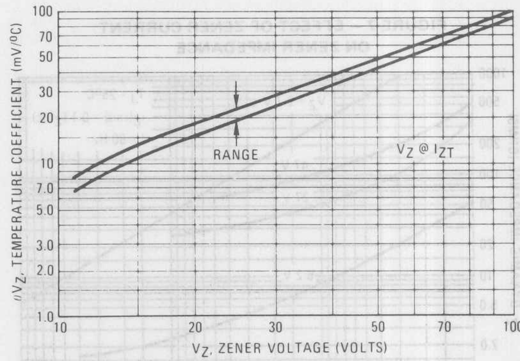


FIGURE 4 – EFFECT OF ZENER CURRENT

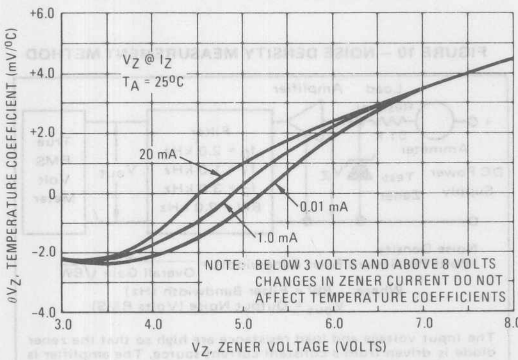


FIGURE 5 – TYPICAL CAPACITANCE

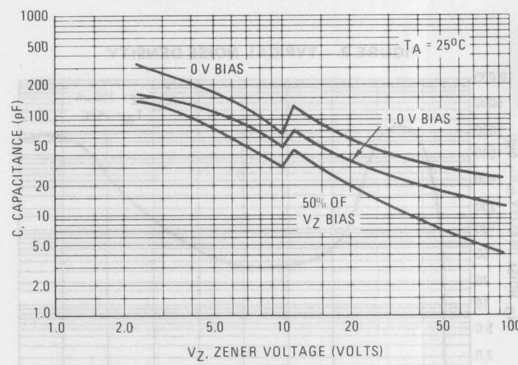
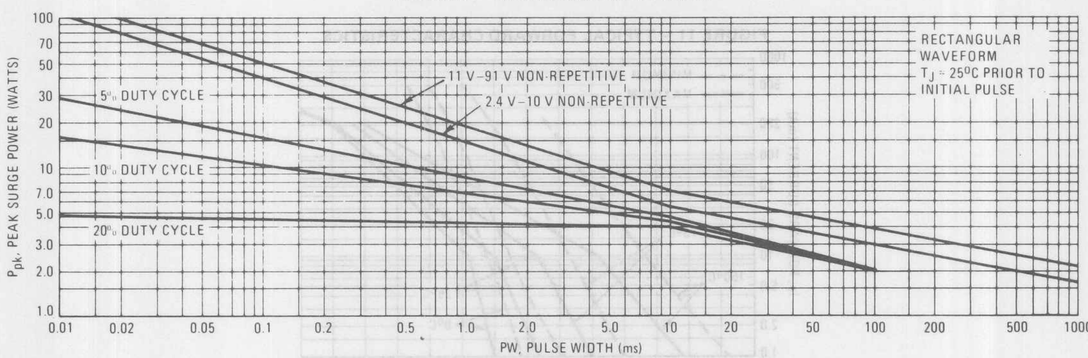


FIGURE 6 – MAXIMUM SURGE POWER



This graph represents 90 percentil data points.
For worst-case design characteristics, multiply surge power by 2/3.

FIGURE 7 – EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

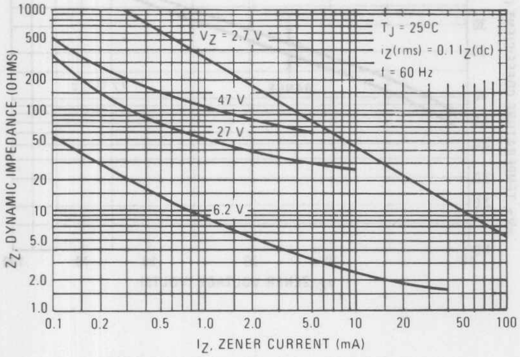


FIGURE 8 – EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

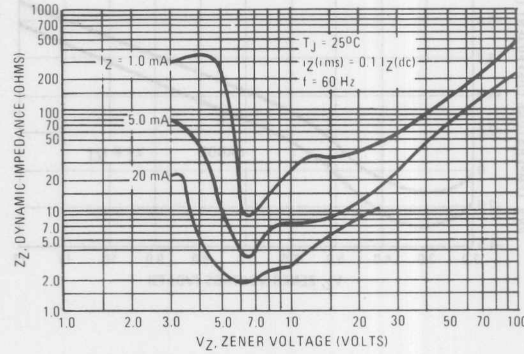


FIGURE 9 – TYPICAL NOISE DENSITY

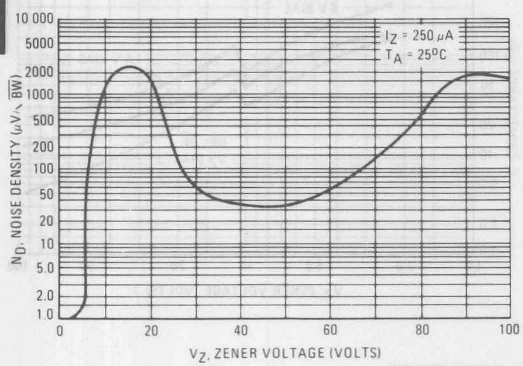
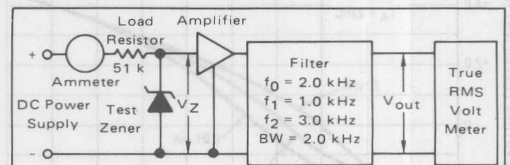


FIGURE 10 – NOISE DENSITY MEASUREMENT METHOD



$$\text{Noise Density (Volts Per Square Root Bandwidth)} = \frac{V_{out}}{\text{Overall Gain}\ \sqrt{BW}}$$

Where: BW = Filter Bandwidth (Hz)
V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

FIGURE 11 – TYPICAL FORWARD CHARACTERISTICS

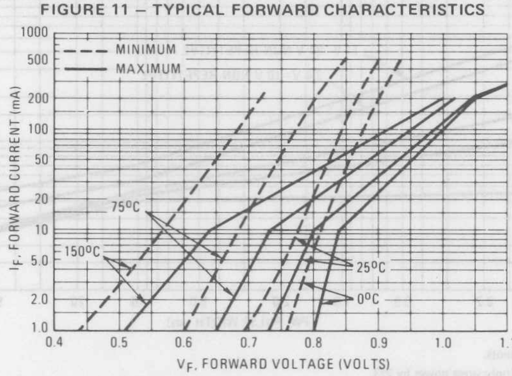


FIGURE 12 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 1 THRU 16 VOLTS

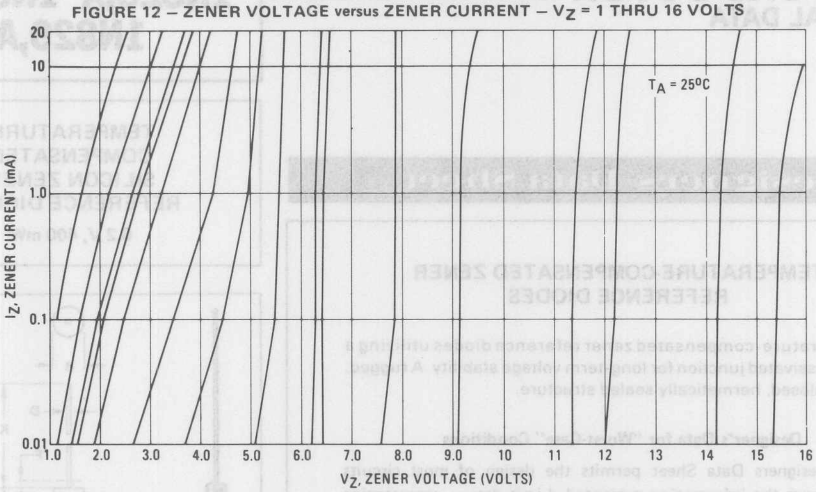


FIGURE 13 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 15 THRU 30 VOLTS

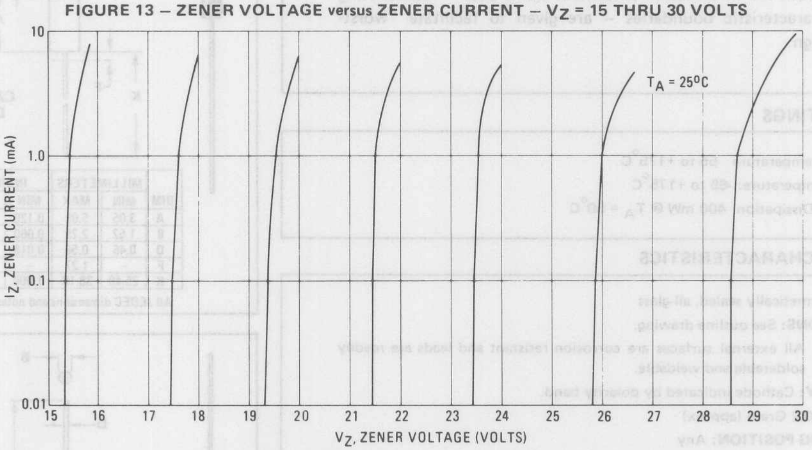
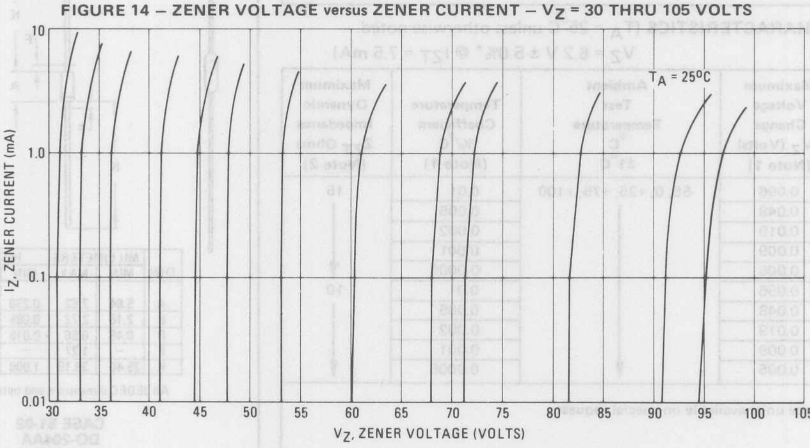


FIGURE 14 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 30 THRU 105 VOLTS



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N821,A 1N823,A 1N825,A 1N827,A 1N829,A

TEMPERATURE-COMPENSATED SILICON ZENER REFERENCE DIODES

6.2 V, 400 mW

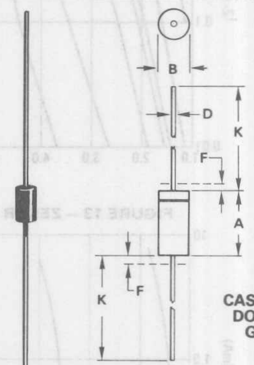
Designers Data Sheet

TEMPERATURE-COMPENSATED ZENER REFERENCE DIODES

Temperature-compensated zener reference diodes utilizing a nitride passivated junction for long-term voltage stability. A rugged, glass-enclosed, hermetically sealed structure.

Designer's Data for "Worst-Case" Conditions

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit data — representing device characteristic boundaries — are given to facilitate "worst-case" design.



CASE 299-02
DO-204AH
GLASS

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

4

MAXIMUM RATINGS

Junction Temperature -55 to +175°C
Storage Temperature: -65 to +175°C
DC Power Dissipation: 400 mW @ $T_A = 50°C$

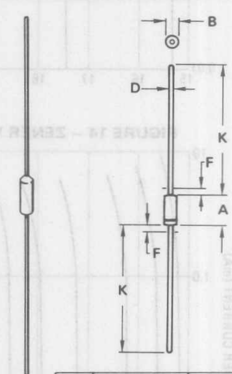
MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Gram (approx)
MOUNTING POSITION: Any

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted. $V_Z = 6.2$ V ± 5.0%* @ $I_{ZT} = 7.5$ mA)

JEDEC Type No.	Maximum Voltage Change ΔV_Z (Volts) (Note 1)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C (Note 1)	Maximum Dynamic Impedance Z_{ZT} Ohms (Note 2)
1N821	0.096	-55, 0, +25, +75, +100	0.01	15
1N823	0.048	↓	0.005	↓
1N825	0.019		0.002	
1N827	0.009		0.001	
1N829	0.005		0.0005	
1N821A	0.096		0.01	10
1N823A	0.048		0.005	↓
1N825A	0.019		0.002	
1N827A	0.009		0.001	
1N829A	0.005		0.0005	

*Tighter-tolerance units available on special request.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

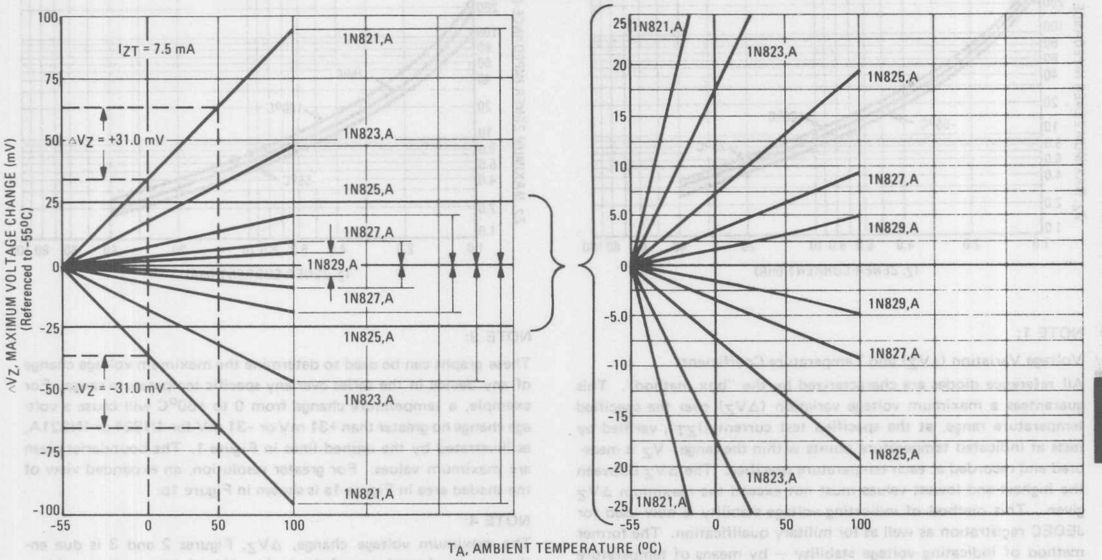
CASE 51-02
DO-204AA
GLASS
"A" SUFFIX ONLY

MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(with I_{ZT} = 7.5 mA ±0.01 mA) (See Note 3)

1N821 thru 1N829

FIGURE 1a FIGURE 1b



ZENER CURRENT versus MAXIMUM VOLTAGE CHANGE

(At Specified Temperatures)

(See Note 4)

MORE THAN 95% OF THE UNITS ARE IN THE RANGES INDICATED BY THE CURVES.

FIGURE 2 – 1N821 SERIES

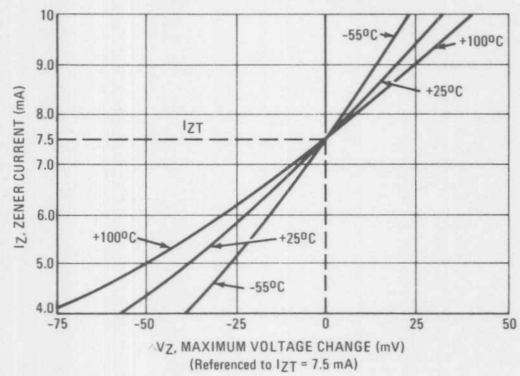
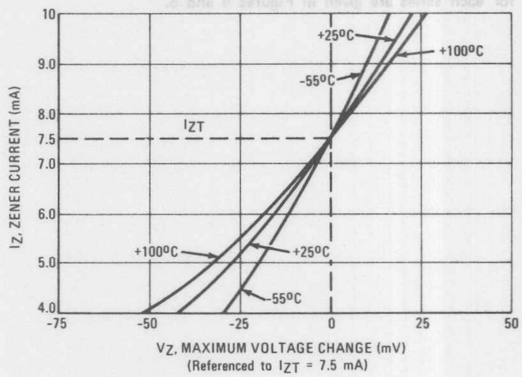


FIGURE 3 – 1N821A SERIES



MAXIMUM ZENER IMPEDANCE versus ZENER CURRENT

(See Note 2)

MORE THAN 95% OF THE UNITS ARE IN THE RANGES INDICATED BY THE CURVES.

FIGURE 4 – 1N821 SERIES

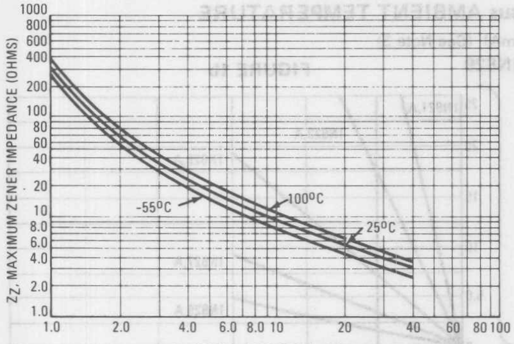
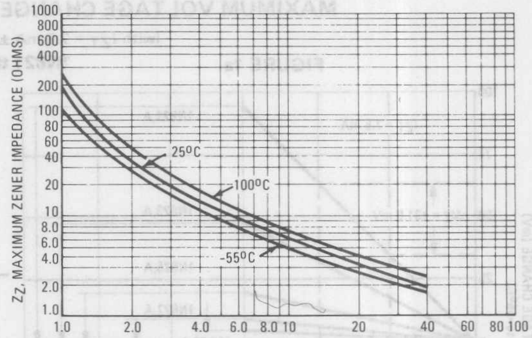


FIGURE 5 – 1N821A SERIES



NOTE 1:

Voltage Variation (ΔV_Z) and Temperature Coefficient.

All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. V_Z is measured and recorded at each temperature specified. The ΔV_Z between the highest and lowest values must not exceed the maximum ΔV_Z given. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability – by means of temperature coefficient – accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 2:

The dynamic zener impedance, Z_{ZT}, is derived from the 60-Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT}, is superimposed on I_{ZT}. Curves showing the variation of zener impedance with zener current for each series are given in Figures 4 and 5.

NOTE 3:

These graphs can be used to determine the maximum voltage change of any device in the series over any specific temperature range. For example, a temperature change from 0 to +50°C will cause a voltage change no greater than +31 mV or -31 mV for 1N821 or 1N821A, as illustrated by the dashed lines in Figure 1. The boundaries given are maximum values. For greater resolution, an expanded view of the shaded area in Figure 1a is shown in Figure 1b.

NOTE 4:

The maximum voltage change, ΔV_Z, Figures 2 and 3 is due entirely to the impedance of the device. If both temperature and I_{ZT} are varied, then the total voltage change may be obtained by graphically adding ΔV_Z in Figure 2 or 3 to the ΔV_Z in Figure 1 for the device under consideration. If the device is to be operated at some stable current other than the specified test current, a new set of characteristics may be plotted by superimposing the data in Figure 2 or 3 on Figure 1. For a more detailed explanation see AN-437 (Application Note).

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N935,A,B thru 1N939,A,B

Designers Data Sheet

TEMPERATURE-COMPENSATED ZENER REFERENCE DIODES

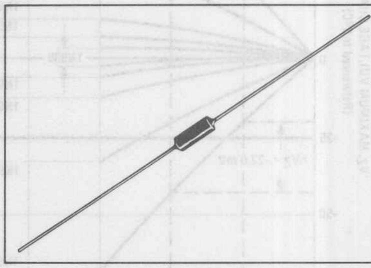
Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. A rugged, glass-enclosed, hermetically sealed structure.

Designer's Data for "Worst Case" Conditions

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit data – representing device characteristic boundaries – are given to facilitate "worst case" design.

TEMPERATURE-COMPENSATED SILICON ZENER REFERENCE DIODES

9.0 V, 500 mW



4

MAXIMUM RATINGS

Junction Temperature: -55 to +175°C
Storage Temperature: -65 to +175°C
DC Power Dissipation: 500 mW @ T_A = 25°C

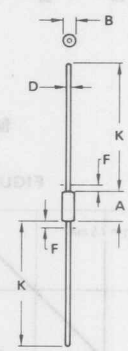
MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Gram (approx)
MOUNTING POSITION: Any

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted V_Z = 9.0 V ±5.0%* @ I_{ZT} = 7.5 mA)

JEDEC Type No. (Note 1)	Maximum Voltage Change ΔV_Z (Volts) (Note 2)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C (Note 2)	Maximum Dynamic Impedance Z_{ZT} (Ohms) (Note 3)
1N935	0.067	0, +25, +75	0.01	20
1N936	0.033		0.005	
1N937	0.013		0.002	
1N938	0.006		0.001	
1N939	0.003		0.0005	
1N935A	0.139	-55, 0, +25, +75, +100	0.01	20
1N936A	0.069		0.005	
1N937A	0.027		0.002	
1N938A	0.013		0.001	
1N939A	0.007		0.0005	
1N935B	0.184	-55, 0, +25, +75, +100, +150	0.01	20
1N936B	0.092		0.005	
1N937B	0.037		0.002	
1N938B	0.018		0.001	
1N939B	0.009		0.0005	

*Tighter-tolerance units available on special request.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

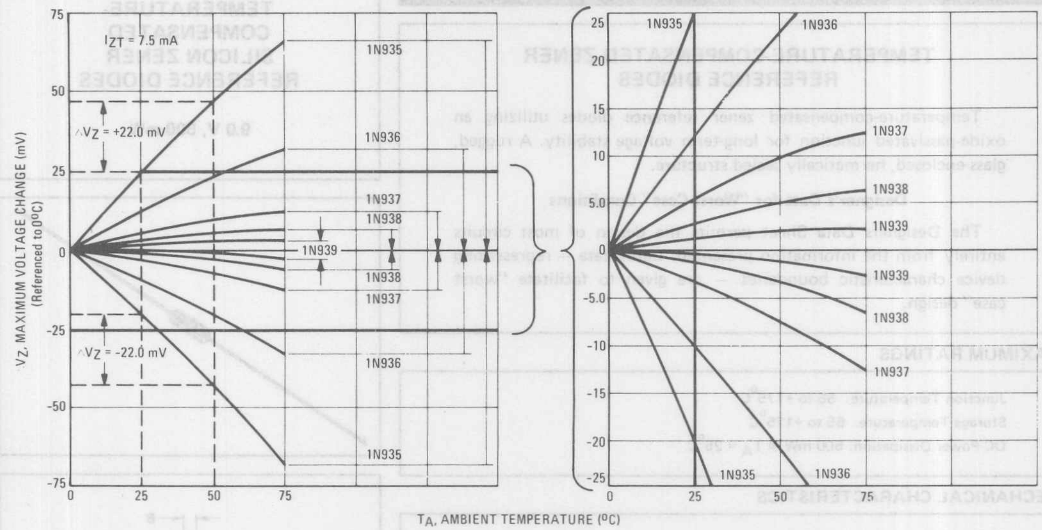
NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

MAXIMUM VOLTAGE CHANGE versus TEMPERATURE

(with I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N935 thru 1N939

FIGURE 1a **FIGURE 1b**

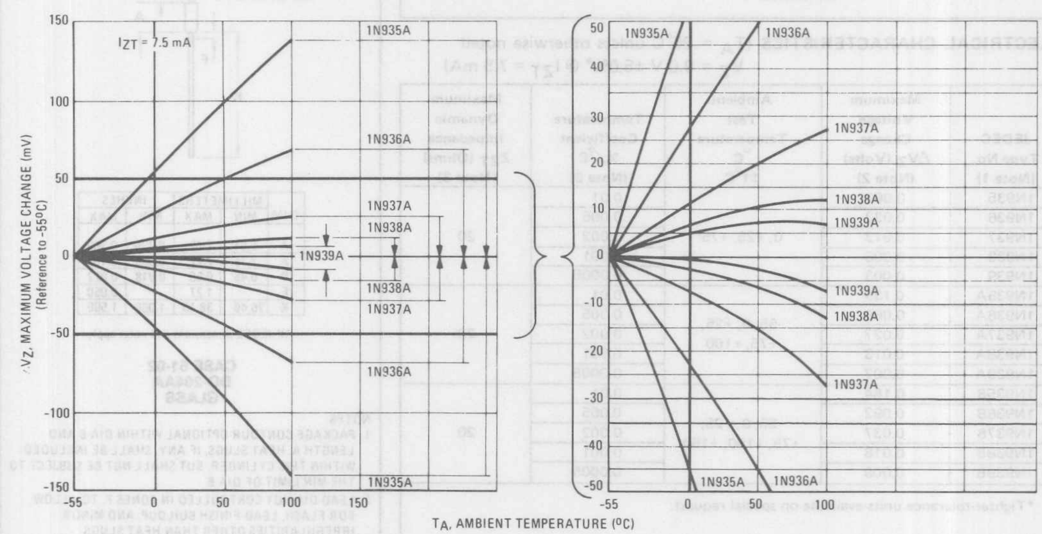


MAXIMUM VOLTAGE CHANGE versus TEMPERATURE

(with I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N935A thru 1N939A

FIGURE 2a **FIGURE 2b**



MAXIMUM VOLTAGE CHANGE versus TEMPERATURE

(with I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N935B thru 1N939B

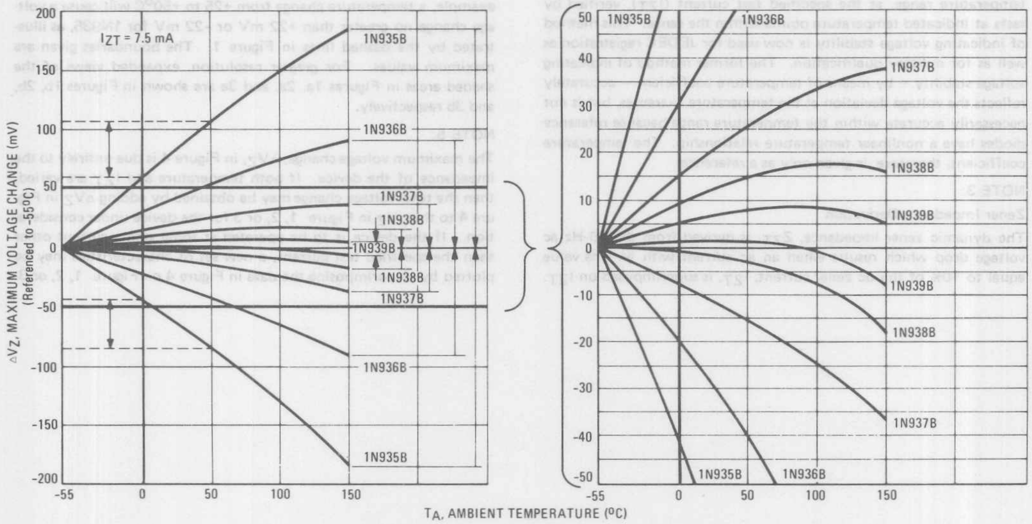


FIGURE 4 – ZENER CURRENT versus MAXIMUM VOLTAGE CHANGE (at specified temperatures)

(See Note 5)

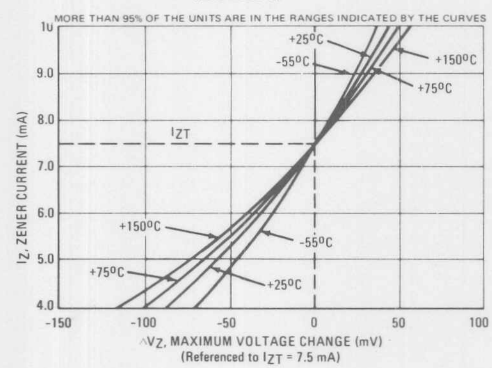
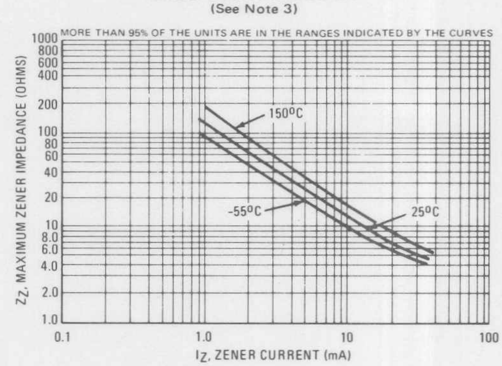


FIGURE 5 – MAXIMUM ZENER IMPEDANCE versus ZENER CURRENT

(See Note 3)



4

NOTE 1:

Types 1N935B, 1N937B, and 1N939B are available to MIL-S-19500/156 and MEG-A-LIFE II, Levels 1, 2, & 3, specifications.

NOTE 2:

Voltage Variation (ΔV_Z) and Temperature Coefficient.

All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability – by means of temperature coefficient – accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 3:

Zener Impedance Derivation

The dynamic zener impedance, Z_{ZT}, is derived from the 60-Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT}, is superimposed on I_{ZT}. Curves showing the variation of zener impedance with zener current for each series are given in Figure 5. A cathode-ray tube curve-trace test on a sample basis is used to ensure that each zener characteristic has a sharp and stable knee region.

NOTE 4:

These graphs can be used to determine the maximum voltage change of any device in the series over any specific temperature range. For example, a temperature change from +25 to +50°C will cause a voltage change no greater than +22 mV or −22 mV for 1N935, as illustrated by the dashed lines in Figure 1. The boundaries given are maximum values. For greater resolution, expanded views of the shaded areas in Figures 1a, 2a, and 3a are shown in Figures 1b, 2b, and 3b respectively.

NOTE 5:

The maximum voltage change, ΔV_Z, in Figure 4 is due entirely to the impedance of the device. If both temperature and I_{ZT} are varied, then the total voltage change may be obtained by adding ΔV_Z in Figure 4 to the ΔV_Z in Figure 1, 2, or 3 for the device under consideration. If the device is to be operated at some stable current other than the specified test current, a new set of characteristics may be plotted by superimposing the data in Figure 4 on Figure 1, 2, or 3.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N941,A,B thru 1N945,A,B

Designers Data Sheet

TEMPERATURE-COMPENSATED ZENER REFERENCE DIODES

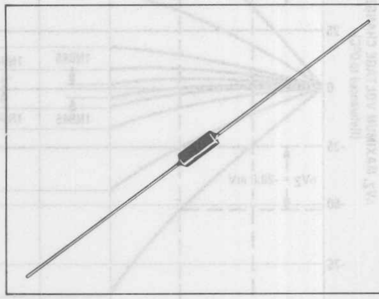
Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. A rugged, glass-enclosed, hermetically sealed structure.

Designer's Data for "Worst Case" Conditions

The Designers Data Sheet permits the design of most circuits entirely from the information presented. Limit data – representing device characteristic boundaries – are given to facilitate "worst case" design.

TEMPERATURE-COMPENSATED SILICON ZENER REFERENCE DIODES

11.7 V, 500 mW

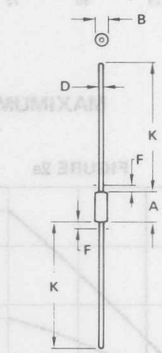


MAXIMUM RATINGS

Junction Temperature: -55 to +175°C
Storage Temperature: -65 to +175°C
DC Power Dissipation: 500 mW @ T_A = 25°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Gram (approx)
MOUNTING POSITION: Any



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted V_Z = 11.7 V ± 5.0%* @ I_{ZT} = 7.5 mA)

JEDEC Type No. (Note 1)	Maximum Voltage Change ΔV_Z (Volts) (Note 2)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C (Note 2)	Maximum Dynamic Impedance Z_{ZT} (Ohms) (Note 3)
1N941	0.088	0, +25, +75	0.01	30
1N942	0.044		0.005	
1N943	0.018		0.002	
1N944	0.009		0.001	
1N945	0.004		0.0005	
1N941A	0.181	-55, 0, +25, +75, +100	0.01	30
1N942A	0.090		0.005	
1N943A	0.036		0.002	
1N944A	0.018		0.001	
1N945A	0.009		0.0005	
1N941B	0.239	-55, 0, +25, +75, +100, +150	0.01	30
1N942B	0.120		0.005	
1N943B	0.047		0.002	
1N944B	0.024		0.001	
1N945B	0.012		0.0005	

*Tighter-tolerance units available on special request.

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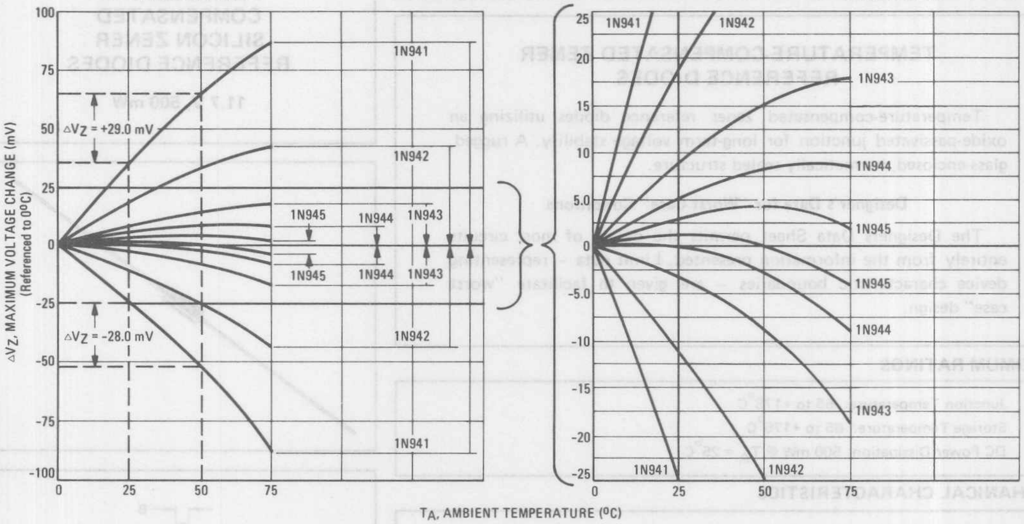
MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(With I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N941 thru 1N945

FIGURE 1a — FIGURE 1b

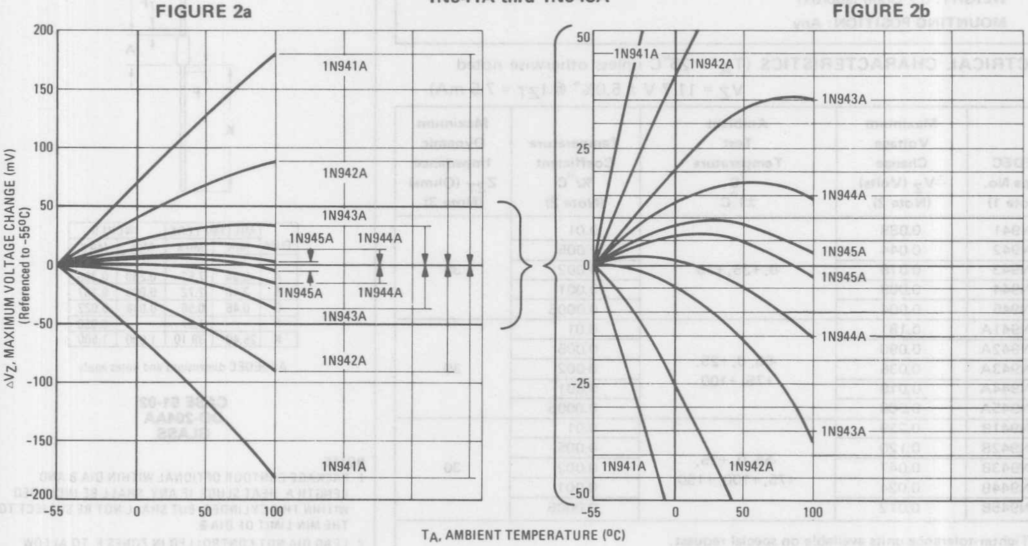


MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(With I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N941A thru 1N945A

FIGURE 2a — FIGURE 2b



MAXIMUM VOLTAGE CHANGE versus TEMPERATURE

(with I_{ZT} = 7.5 mA ±0.01 mA) (See Note 4)

1N941B thru 1N945B

FIGURE 3a   FIGURE 3b

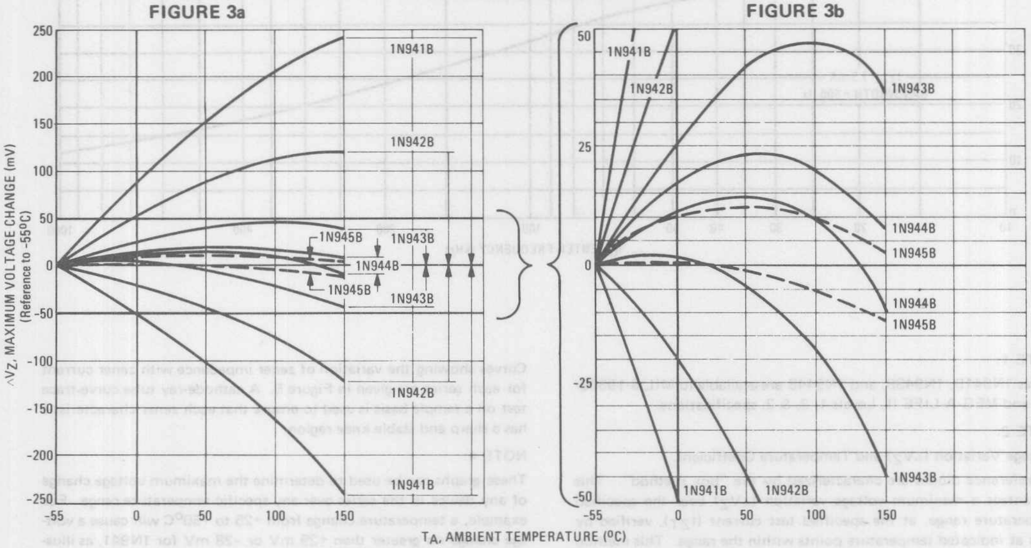


FIGURE 4 – ZENER CURRENT versus MAXIMUM VOLTAGE CHANGE (At specified temperatures)

(See Note 5)

MORE THAN 95% OF THE UNITS ARE IN THE RANGES INDICATED BY THE CURVES

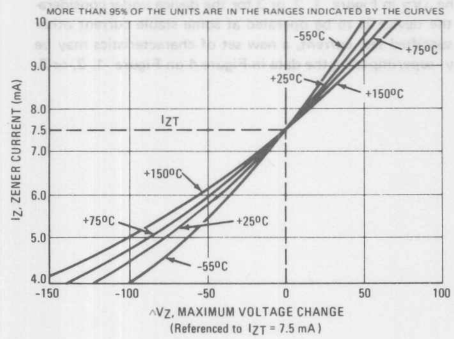


FIGURE 5 – MAXIMUM ZENER IMPEDANCE versus ZENER CURRENT

(See Note 3)

MORE THAN 95% OF THE UNITS ARE IN THE RANGES INDICATED BY THE CURVES

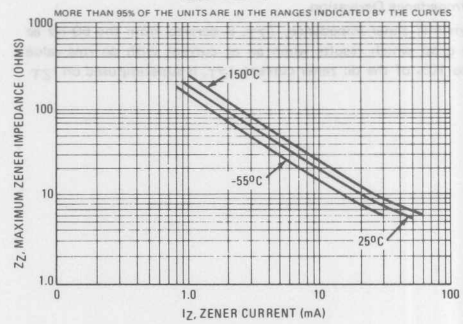
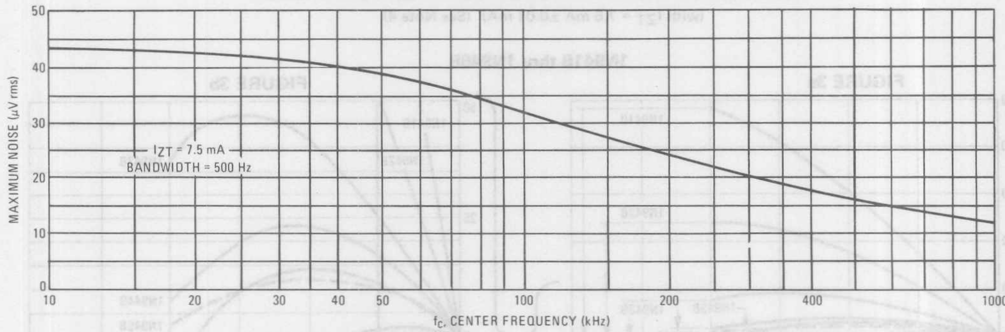


FIGURE 6 – DISTRIBUTION OF MAXIMUM GENERATED NOISE



NOTE 1:

Types 1N941B, 1N943B, and 1N944B are available to MIL-S-19500/157 and MEG-A-LIFE II, Levels 1, 2, & 3, specifications.

NOTE 2:

Voltage Variation (ΔV_Z) and Temperature Coefficient.

All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability – by means of temperature coefficient – accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 3:

Zener Impedance Derivation

The dynamic zener impedance, Z_{ZT}, is derived from the 60-Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT}, is superimposed on I_{ZT}. Curves showing the variation of zener impedance with zener current for each series are given in Figure 5. A cathode-ray tube curve-trace test on a sample basis is used to ensure that each zener characteristic has a sharp and stable knee region.

NOTE 4:

These graphs can be used to determine the maximum voltage change of any device in the series over any specific temperature range. For example, a temperature change from +25 to +50°C will cause a voltage change no greater than +29 mV or −28 mV for 1N941, as illustrated by the dashed lines in Figure 1. The boundaries given are maximum values. For greater resolution, expanded views of the shaded areas in Figures 1a, 2a, and 3a are shown in Figures 1b, 2b, and 3b respectively.

NOTE 5:

The maximum voltage change, ΔV_Z, in Figure 4 is due entirely to the impedance of the device. If both temperature and I_{ZT} are varied, then the total voltage change may be obtained by adding ΔV_Z in Figure 4 to the ΔV_Z in Figure 1, 2, or 3 for the device under consideration. If the device is to be operated at some stable current other than the specified test current, a new set of characteristics may be plotted by superimposing the data in Figure 4 on Figure 1, 2, or 3.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N957A thru 1N986A
See Page 4-4

1N987A thru 1N992A

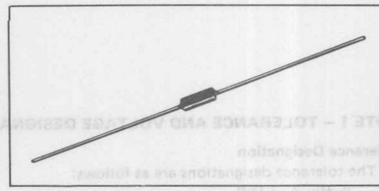
Advance Information

400-MILLIWATT

SILICON ZENER DIODES

CONSTANT-VOLTAGE REFERENCES FOR 120 thru 200-VOLT APPLICATIONS

- 400-Milliwatt
- Guaranteed Low Zener Impedance
- Guaranteed Low Leakage Current
- Controlled Forward Characteristics
- Temperature Range: −65 to +175°C
- No Heat Sink Required

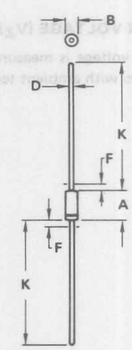


MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_L = 50°C Derate above T_L = 50°C	P_D	400 3.2	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed all glass case.
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant with readily solderable leads.
POLARITY: Cathode end indicated by color band. When operated in zener region, the cathode end will be positive with respect to anode end.
WEIGHT: 0.2 grams (approx.)
MOUNTING POSITION: Any



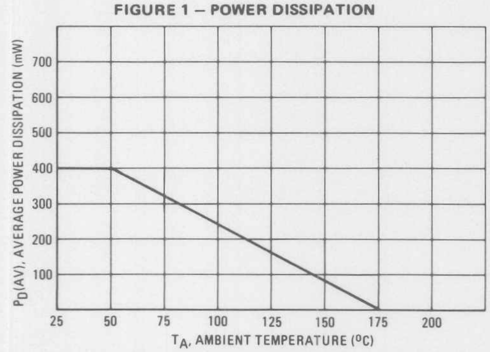
NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

FIGURE 1 – POWER DISSIPATION



This document contains information on a new product. Specifications and information herein are subject to change without notice.

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$, $V_F = 1.5$ V max at 200 mA for all types)

Type Number (Note 1)	Nominal Zener Voltage V_Z (Note 2) Volts	Test Current I_{ZT} mA	Maximum Zener Impedance (Note 3)			Maximum DC Zener Current I_{ZM} (Note 4) mA	Maximum Reverse Current (Note 5)		
			Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA		I_R Maximum μA	Test Voltage Vdc V_R 5%	10%
1N987A	120	1.0	900	4500	0.25	2.5	5.0	91.2	86.4
1N988A	130	0.95	1100	5000	0.25	2.3	5.0	98.8	93.6
1N989A	150	0.85	1500	6000	0.25	2.0	5.0	114	108
1N990A	160	0.80	1700	6500	0.25	1.9	5.0	121.6	115.2
1N991A	180	0.68	2200	7100	0.25	1.7	5.0	136.8	129.6
1N992A	200	0.65	2500	8000	0.25	1.5	5.0	152	144

4

NOTE 1 – TOLERANCE AND VOLTAGE DESIGNATION

Tolerance Designation

The tolerance designations are as follows:

Suffix A: ±10%

Suffix B: ±5%

NOTE 2 – ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium with ambient temperature of 25°C.

NOTE 3 – ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT}.

A cathode ray oscilloscope curve test is used to insure that each zener diode breakdown region begins at a low current level and that zener voltage remains nearly constant to a current level in excess of I_{ZM}.

NOTE 4 – MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum zener current ratings are based on the maximum voltage of a 20% unit. For closer tolerance units (10% or 5%) or units where the actual zener voltage (V_Z) is known at the operating point, the maximum zener current may be increased and is limited by the derating curve.

NOTE 5 – REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed only for 5% and 10% 400 mW silicon zener diodes and are measured at V_R as shown on the table.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N2804 thru 1N2846
6.8V thru 200V (Case 54-05)
1N3305 thru 1N3350
6.8V thru 200V (Case 58-01)
1N4549 thru 1N4556
3.9V thru 7.5V (Case 58-01)
1N4557 thru 1N4564
3.9V thru 7.5V (Case 54-05)

ZENER DIODES

Units are available with anode-to-case and cathode-to-case connections (standard and reverse polarity). For reverse polarity, add suffix "R" to type number.

50 WATTS
ZENER DIODES

MAXIMUM RATINGS

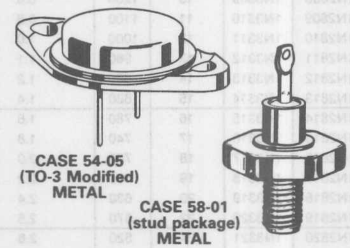
Junction and Storage Temperature: -65°C to +175°C.

DC Power Dissipation: 50 Watts. (Derate 0.5 W/°C above 75°C).

TOLERANCE DESIGNATION: The type numbers shown have a standard tolerance of ±20% on the nominal zener voltage. Add suffix "A" for ±10% units or "B" for ±5% units. (2% and 1% tolerance also available.

CASE 54 APPLICATIONS INFORMATION: If these units are used with a socket, the unregulated line should be connected to one pin through a suitable current limiting resistor and the load should be connected to the other pin. The load will now be disconnected from the line if the unit is removed from the socket.

Typical circuit connections for anode-to-case and cathode-to-case polarities (standard and reverse polarities, respectively) are shown below.



CASE 54-05
(TO-3 Modified)
METAL

CASE 58-01
(stud package)
METAL

4

ELECTRICAL CHARACTERISTICS (T_C = 30 °C unless otherwise specified, V_F = 1.5 V max @ 10 A on all types.)

50 Watt Case 54	50 Watt Case 58	Nominal Zener Voltage @ I_{ZT} (V_Z) Volts	Test Current (I_{ZT}) mA	Max Zener Impedance Z_{ZT} @ I_{ZT} ohms	Max Zener Impedance Z_{ZK} @ I_{ZK} = 5mA ohms	Max DC Zener Current 75°C Case Temp (I_{ZM})mA	Reverse* Leakage Current I_RMax (µA)	Reverse* Leakage Current V_{R1}	Reverse* Leakage Current V_{R2}	Typical Zener Voltage Temp. Coeff. %/°C
1N4557	1N4549	3.9	3200	0.16	400	11900	150	0.5	0.5	-.025
1N4558	1N4550	4.3	2900	0.16	500	10650	150	0.5	0.5	-.025
1N4559	1N4551	4.7	2650	0.12	600	9700	100	1.0	1.0	.010
1N4560	1N4552	5.1	2450	0.12	650	8900	20	1.0	1.0	.015
1N4561	1N4553	5.6	2250	0.12	900	8100	20	1.0	1.0	.030
1N4562	1N4554	6.2	2000	0.14	1000	7300	20	2.0	2.0	.040
1N2804	1N3305	6.8	1850	0.2	70	6600	150	4.5	4.3	.040
1N4563	1N4555	6.8	1850	0.16	200	6650	10	2.0	2.0	.045
1N2805	1N3306	7.5	1700	0.3	70	5900	75	5.0	4.7	.045
1N4564	1N4556	7.5	1650	0.24	100	6050	10	3.0	3.0	.053
1N2806	1N3307	8.2	1500	0.4	70	5200	50	5.4	5.2	.048
1N2807	1N3308	9.1	1370	0.5	70	4800	25	6.1	5.7	.051
1N2808	1N3309	10	1200	0.6	80	4300	10	6.7	6.3	.055
1N2809	1N3310	11	1100	0.8	80	3900	5	8.4	8.0	.060
1N2810	1N3311	12	1000	1.0	80	3600	5	9.1	8.6	.065
1N2811	1N3312	13	960	1.1	80	3300	5	9.9	9.4	.065
1N2812	1N3313	14	890	1.2	80	3000	5	10.6	10.1	.070
1N2813	1N3314	15	830	1.4	80	2800	5	11.4	10.8	.070
1N2814	1N3315	16	780	1.6	80	2650	5	12.2	11.5	.070
1N2815	1N3316	17	740	1.8	80	2500	5	13.0	12.2	.075
1N2816	1N3317	18	700	2.0	80	2300	5	13.7	13.0	.075
1N2817	1N3318	19	660	2.2	80	2200	5	14.4	13.7	.075
1N2818	1N3319	20	630	2.4	80	2100	5	15.2	14.4	.075
1N2819	1N3320	22	570	2.5	80	1900	5	16.7	15.8	.080
1N2820	1N3321	24	520	2.6	80	1750	5	18.2	17.3	.080
1N2821	1N3322	25	500	2.7	90	1550	5	19.0	18.0	.080
1N2822	1N3323	27	460	2.8	90	1500	5	20.6	19.4	.085
1N2823	1N3324	30	420	3.0	90	1400	5	22.8	21.6	.085
1N2824	1N3325	33	380	3.2	90	1300	5	25.1	23.8	.085
1N2825	1N3326	36	350	3.5	90	1150	5	27.4	25.9	.085
1N2826	1N3327	39	320	4.0	90	1050	5	29.7	28.1	.090
1N2827	1N3328	43	290	4.5	90	975	5	32.7	31.0	.090
1N2828	1N3329	45	280	4.5	100	930	5	34.2	32.4	.090
1N2829	1N3330	47	270	5.0	100	880	5	35.8	33.8	.090
1N2830	1N3331	50	250	5.0	100	830	5	38.0	36.0	.090
1N2831	1N3332	51	245	5.2	100	810	5	38.8	36.7	.090
—	1N3333	52	240	5.5	100	790	5	39.5	37.4	.090
1N2832	1N3334	56	220	6	110	740	5	42.6	40.3	.090
1N2833	1N3335	62	200	7	120	660	5	47.1	44.6	.090
1N2834	1N3336	68	180	8	140	600	5	51.7	49.0	.090
1N2835	1N3337	75	170	9	150	540	5	56.0	54.0	.090
1N2836	1N3338	82	150	11	160	490	5	62.2	59.0	.090
1N2837	1N3339	91	140	15	180	420	5	69.2	65.5	.090
1N2838	1N3340	100	120	20	200	400	5	76.0	72.0	.090
1N2839	1N3341	105	120	25	210	380	5	79.8	75.6	.095
1N2840	1N3342	110	110	30	220	365	5	83.6	79.2	.095
1N2841	1N3343	120	100	40	240	335	5	91.2	86.4	.095
1N2842	1N3344	130	95	50	275	310	5	98.8	93.6	.095
—	1N3345	140	90	60	325	290	5	106.4	100.8	.095
1N2843	1N3346	150	85	75	400	270	5	114.0	108.0	.095
1N2844	1N3347	160	80	80	450	250	5	121.6	115.2	.095
—	1N3348	175	70	85	500	230	5	133.0	126.0	.095
1N2845	1N3349	180	68	90	525	220	5	136.8	129.6	.095
1N2846	1N3350	200	65	100	600	200	5	152.0	144.0	.100

SPECIAL SELECTIONS AVAILABLE INCLUDE: (See Selector Guide for details)

*V_{R1} — Test Voltage for 5% Tolerance Device
V_{R2} — Test Voltage for 10% Tolerance Device
No Leakage Specified as 20% Tolerance Device

FIGURE 1 — TEMPERATURE CHARACTERISTICS

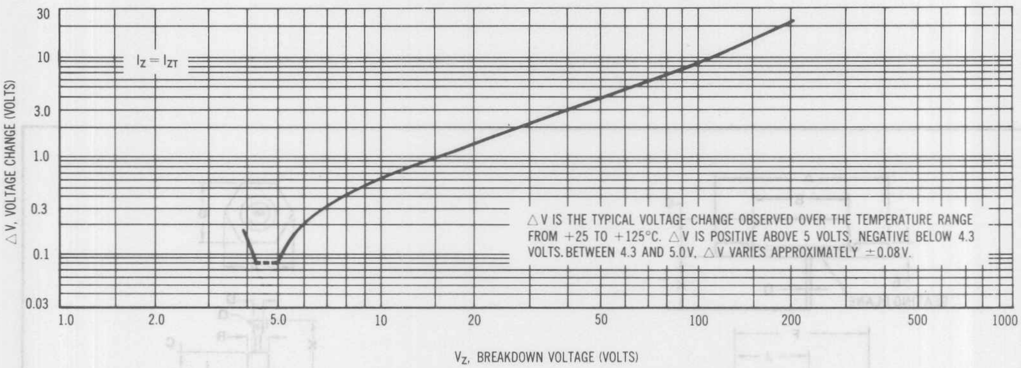


FIGURE 2 — POWER-TEMPERATURE DERATING CURVE

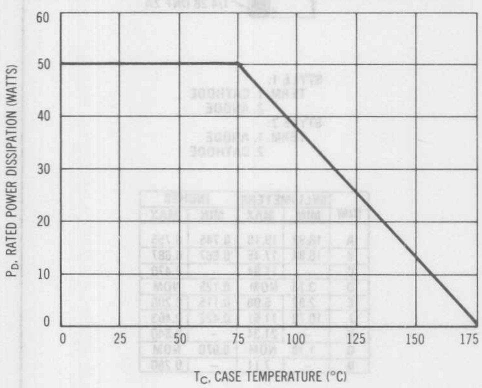


FIGURE 3 — LEAKAGE CURRENT

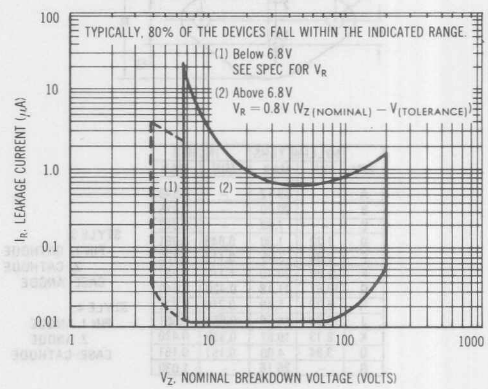
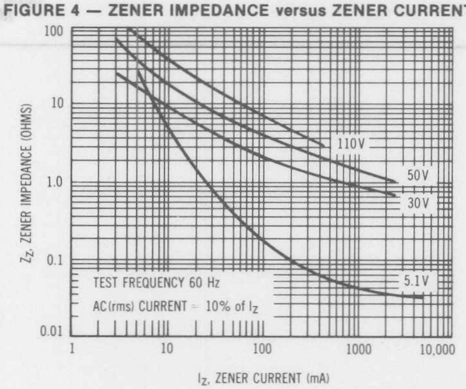
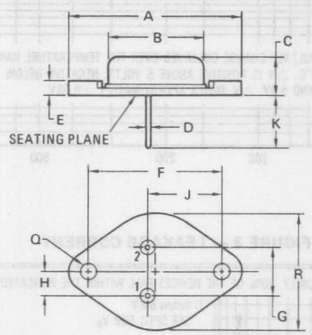


FIGURE 4 — ZENER IMPEDANCE versus ZENER CURRENT



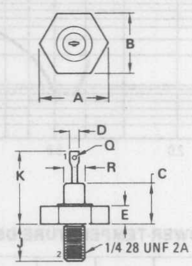


DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	–	39.12	–	1.540
B	–	20.70	–	0.815
C	–	7.92	–	0.312
D	1.22	1.30	0.048	0.051
E	2.84	3.05	0.112	0.120
F	29.90	30.40	1.177	1.197
G	10.67	11.18	0.420	0.440
H	5.33	5.59	0.210	0.220
J	16.54	16.79	0.651	0.661
K	8.13	10.67	0.320	0.420
Q	3.84	4.09	0.151	0.161
R	–	26.16	–	1.030

STYLE 3:
PIN 1. CATHODE
2. CATHODE
CASE: ANODE

STYLE 4:
PIN 1. ANODE
2. ANODE
CASE: CATHODE

CASE 54-05
(TO-3 Modified)
METAL



STYLE 1:
TERM. 1. CATHODE
2. ANODE
STYLE 2:
TERM. 1. ANODE
2. CATHODE

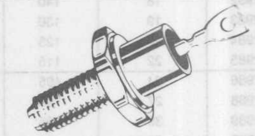
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	18.92	19.18	0.745	0.755
B	16.94	17.45	0.667	0.687
C	–	11.94	–	0.470
D	3.18	NOM	0.125	NOM
E	2.92	5.08	0.115	0.200
J	10.72	11.51	0.422	0.453
K	–	21.34	–	0.840
Q	1.78	NOM	0.070	NOM
R	–	7.11	–	0.280

CASE 58-01
(stud package)
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N2970 thru 1N3015

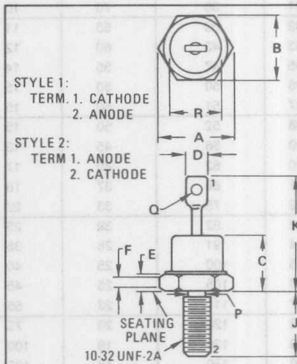
10 WATTS ZENER DIODES



ZENER DIODES

Diffused-junction zener diodes for both military and high-reliability industrial applications. Available with anode-to-case and cathode-to-case connections (standard and reverse polarity), i.e., 1N2970 and 1N2970R. Supplied with mounting hardware.

The type numbers shown have a standard tolerance of ± 20% on the nominal zener voltage. Add suffix "A" for ± 10% units or "B" for ± 5% units. (2% and 1% tolerance also available.)



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	11.94	12.83	0.470	0.505
B	10.77	11.10	0.424	0.437
C	–	10.29	–	0.405
D	–	6.35	–	0.250
E	1.91	4.45	0.075	0.175
F	1.52	–	0.060	–
J	10.72	11.51	0.422	0.453
K	–	20.32	–	0.800
P	4.14	4.80	0.163	0.189
Q	1.52	–	0.060	–
R	–	10.77	–	0.424

All JEDEC dimensions and notes apply

CASE 56-02
DO-203AA
METAL

MAXIMUM RATINGS

Junction and Storage Temperature: -65°C to +175°C.

DC Power Dissipation: 10 Watts. (Derate 83.3 mW/°C above 55°C).

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted, V_F = 1.5 V max @ I_F = 2 amp on all types.)

Type No.	Nominal Zener Voltage V_Z @ I_{ZT} Volts	Test Current I_{ZT} mA	Max Zener Impedance			Max DC Zener Current I_{ZM} mA	Max. Reverse Current*		
			Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA		I_R Max (μA)	V_{R1}	V_{R2}
1N2970	6.8	370	1.2	500	1.0	1,320	150	5.2	4.9
1N2971	7.5	335	1.3	250	1.0	1,180	75	5.7	5.4
1N2972	8.2	305	1.5	250	1.0	1,040	50	6.2	5.9
1N2973	9.1	275	2.0	250	1.0	960	25	6.9	6.6
1N2974	10	250	3	250	1.0	860	10	7.6	7.2
1N2975	11	230	3	250	1.0	780	5	8.4	8.0
1N2976	12	210	3	250	1.0	720	5	9.1	8.6
1N2977	13	190	3	250	1.0	660	5	9.9	9.4
1N2978	14	180	3	250	1.0	600	5	10.6	10.1
1N2979	15	170	3	250	1.0	560	5	11.4	10.8

*V_{R1} — Test Voltage for 5% Tolerance Device. V_{R2} — Test Voltage for 10 % Tolerance Device. No Leakage Specified as 20% Tolerance Device.

ELECTRICAL CHARACTERISTICS ($T_C = 25\,°C$ unless otherwise noted, V_F = 1.5 V max @ I_F = 2 amp on all types.)

Type No.	Nominal Zener Voltage V_Z @ I_{ZT} Volts	Test Current I_{ZT} mA	Max Zener Impedance Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Max DC Zener Current I_{ZM} mA	Max. Reverse Current* I_R Max (μA)	V_{R1}	V_{R2}
1N2980	16	155	4	250	1.0	530	5	12.2	11.5
1N2982	18	140	4	250	1.0	460	5	13.7	13.0
1N2983	19	130	4	250	1.0	440	5	14.4	13.7
1N2984	20	125	4	250	1.0	420	5	15.2	14.4
1N2985	22	115	5	250	1.0	380	5	16.7	15.8
1N2986	24	105	5	250	1.0	350	5	18.2	17.3
1N2988	27	95	7	250	1.0	300	5	20.6	19.4
1N2989	30	85	8	300	1.0	280	5	22.8	21.6
1N2990	33	75	9	300	1.0	260	5	25.1	23.8
1N2991	36	70	10	300	1.0	230	5	27.4	25.9
1N2992	39	65	11	300	1.0	210	5	29.7	28.1
1N2993	43	60	12	400	1.0	195	5	32.7	31.0
1N2995	47	55	14	400	1.0	175	5	35.8	33.8
1N2996	50	50	15	500	1.0	165	5	38.0	36.0
1N2997	51	50	15	500	1.0	163	5	38.8	36.7
1N2998	52	50	15	500	1.0	160	5	39.5	37.4
1N2999	56	45	16	500	1.0	150	5	42.6	40.3
1N3000	62	40	17	600	1.0	130	5	47.1	44.6
1N3001	68	37	18	600	1.0	120	5	51.7	49.0
1N3002	75	33	22	600	1.0	110	5	56.0	54.0
1N3003	82	30	25	700	1.0	100	5	62.2	59.0
1N3004	91	28	35	800	1.0	85	5	69.2	65.5
1N3005	100	25	40	900	1.0	80	5	76.0	72.0
1N3006	105	25	45	1,000	1.0	75	5	79.8	75.6
1N3007	110	23	55	1,100	1.0	72	5	83.6	79.2
1N3008	120	20	75	1,200	1.0	67	5	91.2	86.4
1N3009	130	19	100	1,300	1.0	62	5	98.8	93.6
1N3010	140	18	125	1,400	1.0	58	5	106.4	100.8
1N3011	150	17	175	1,500	1.0	54	5	114.0	108.0
1N3012	160	16	200	1,600	1.0	50	5	121.6	115.2
1N3014	180	14	260	1,850	1.0	45	5	136.8	129.6
1N3015	200	12	300	2,000	1.0	40	5	152.0	144.0

*V_{R1} — Test Voltage for 5% Tolerance Device. V_{R2} — Test Voltage for 10 % Tolerance Device. No Leakage Specified as 20% Tolerance Device.

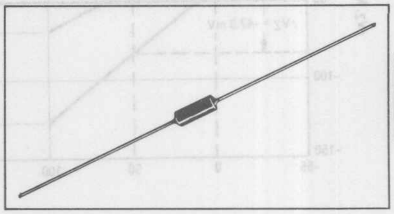
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3016 thru 1N3051
See Page 4-32

1N3154,A thru 1N3157,A

TEMPERATURE-COMPENSATED SILICON ZENER REFERENCE DIODES

8.4 V, 500 mW



TEMPERATURE-COMPENSATED SILICON ZENER REFERENCE DIODES

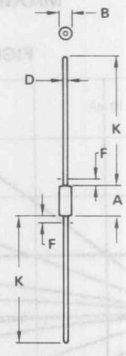
Temperature-compensated zener reference diodes utilizing an oxide-passivated junction for long-term voltage stability. A rugged, glass-enclosed, hermetically sealed structure.

MAXIMUM RATINGS

Junction Temperature: -55 to +175°C
Storage Temperature: -65 to +175°C
DC Power Dissipation: 500 mW @ T_A = 25°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all glass.
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Grams (approx)
MOUNTING POSITION: Any



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted V_Z = 8.4 V ±5.0%* @ I_{ZT} = 10 mA)

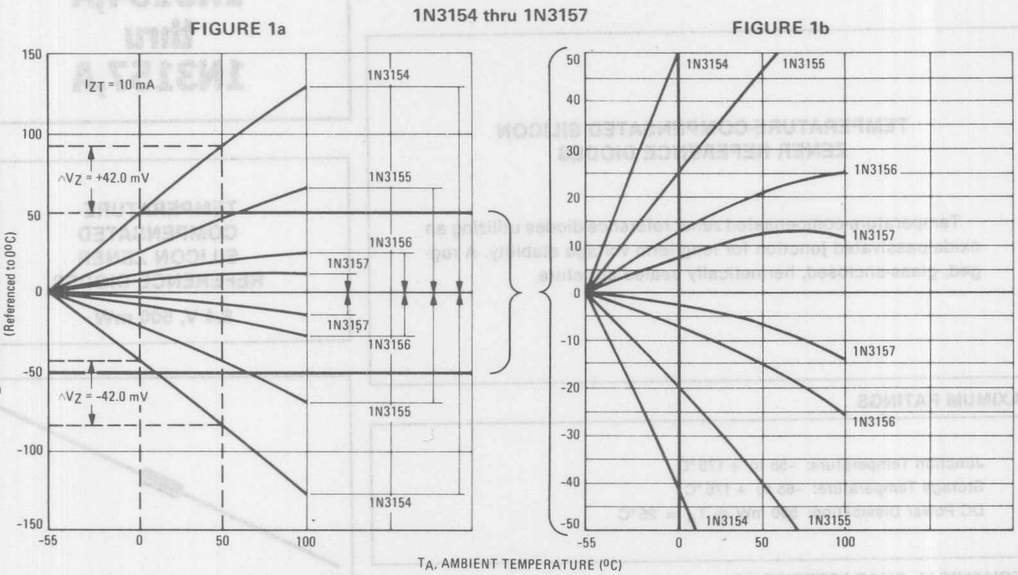
JEDEC Type No. (Note 1)	Maximum Voltage Change ΔV_Z (Volts) (Note 2)	Ambient Test Temperature °C ±1°C	Temperature Coefficient %/°C (Note 2)	Maximum Dynamic Impedance Z_{ZT} (Ohms) (Note 3)
1N3154	0.130		0.01	
1N3155	0.065	-55, 0, +25, +75, +100	0.005	15
1N3156	0.026		0.002	
1N3157	0.013		0.001	
1N3154A	0.172		0.01	
1N3155A	0.086	-55, 0, +25, +75, +100, +150	0.005	15
1N3156A	0.034		0.002	
1N3157A	0.017		0.001	

*Tighter-tolerance units available on special request.
CAPACITANCE (C) = 20 to 180 pF @ 90% of V_Z
FORWARD BREAKDOWN VOLTAGE (V_f) = 100 to 800 V

MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(with I_{ZT} = 10 mA ±0.01 mA) (See Note 4)

1N3154 thru 1N3157



MAXIMUM VOLTAGE CHANGE versus AMBIENT TEMPERATURE

(with I_{ZT} = 10 mA ±0.01 mA) (See Note 4)

1N3154A thru 1N3157A

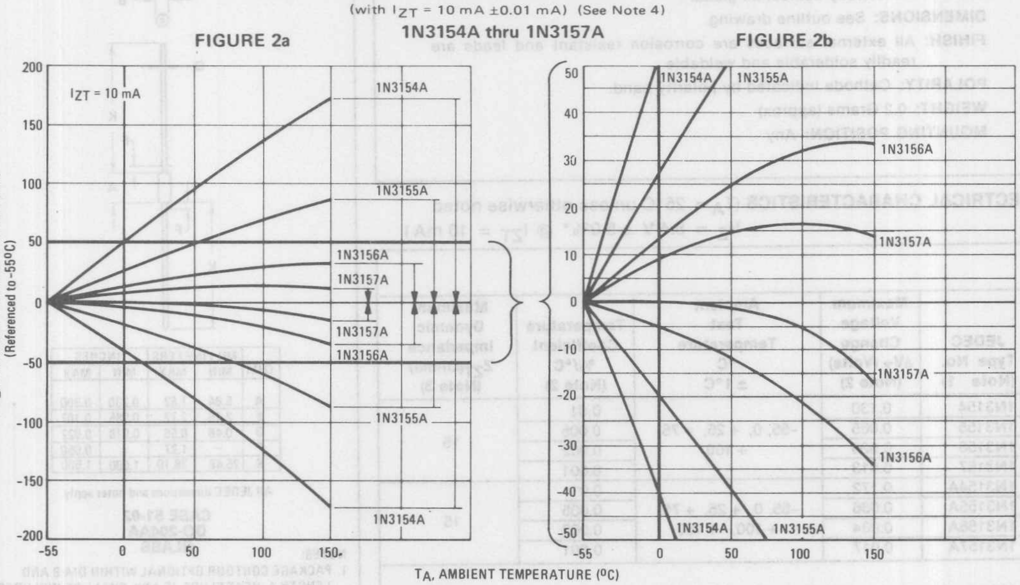


FIGURE 3 – ZENER CURRENT versus MAXIMUM VOLTAGE CHANGE (at specified temperatures)
(See Note 5)

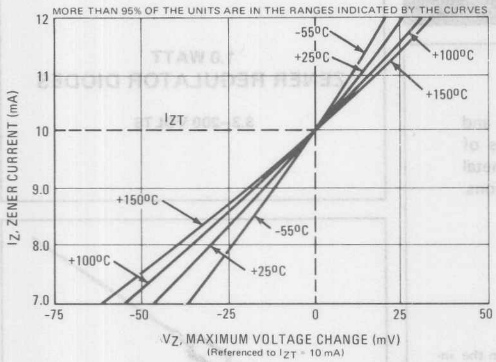


FIGURE 4 – MAXIMUM ZENER IMPEDANCE versus ZENER CURRENT
(See Note 3)

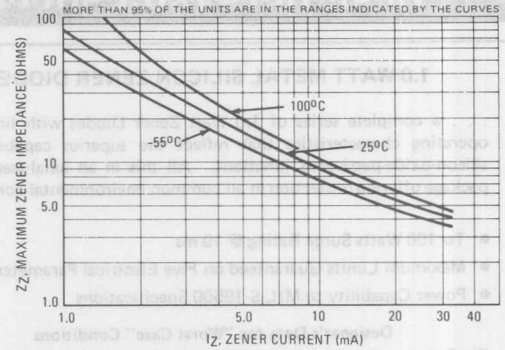
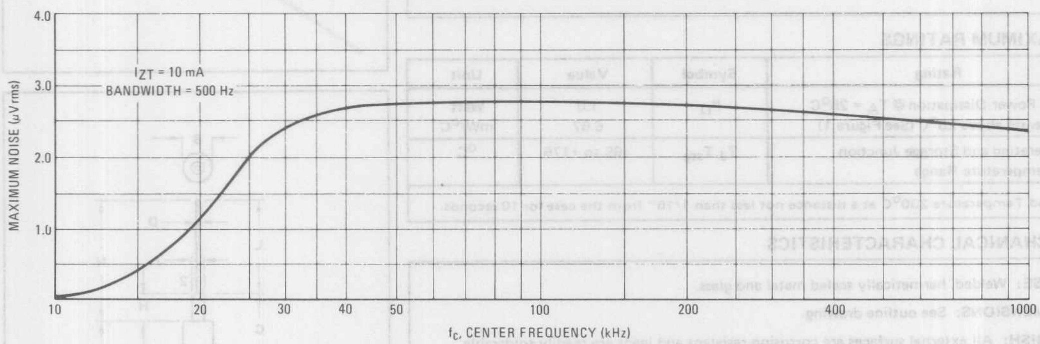


FIGURE 5 – DISTRIBUTION OF MAXIMUM GENERATED NOISE



NOTE 1:

Types 1N3154 thru 1N3157 are available to MIL-S-19500/158 and MEG-A-LIFE II, Levels 1, 2, & 3, specifications.

NOTE 2:

Voltage Variation (ΔV_Z) and Temperature Coefficient.

All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability – by means of temperature coefficient – accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 3:

Zener Impedance Derivation

The dynamic zener impedance, Z_{ZT}, is derived from the 60-Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT}, is superimposed on I_{ZT}. Curves showing the variation of zener impedance with zener current for each series are given in Figure 4. A cathode-ray tube curve-trace test on a sample basis is used to ensure that each zener characteristic has a sharp and stable knee region.

NOTE 4:

These graphs can be used to determine the maximum voltage change of any device in the series over any specific temperature range. For example, a temperature change from 0 to +50°C will cause a voltage change no greater than +42 mV or -42 mV for 1N3154, as illustrated by the dashed lines in Figure 1. The boundaries given are maximum values. For greater resolution, expanded views of the shaded areas in Figures 1a and 2a are shown in Figures 1b and 2b respectively.

NOTE 5:

The maximum voltage change, ΔV_Z, in Figure 3 is due entirely to the impedance of the device. If both temperature and I_{ZT} are varied, then the total voltage change may be obtained by adding ΔV_Z in Figure 3 to the ΔV_Z in Figure 1 or 2 for the device under consideration. If the device is to be operated at some stable current other than the specified test current, a new set of characteristics may be plotted by superimposing the data in Figure 3 on Figure 1 or 2.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3821 thru 1N3830
SERIES

1N3016 thru 1N3051
SERIES

Designers Data Sheet

1.0 WATT METAL SILICON ZENER DIODES

. . . a complete series of 1.0 Watt Zener Diodes with limits and operating characteristics that reflect the superior capabilities of silicon-oxide-passivated junctions. All this in an axial-lead, metal package offering protection in all common environmental conditions.

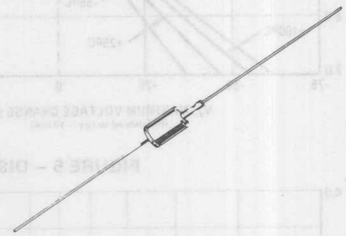
- To 100 Watts Surge Rating @ 10 ms
- Maximum Limits Guaranteed on Five Electrical Parameters
- Power Capability to MIL-S-19500 Specifications

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

1.0 WATT
ZENER REGULATOR DIODES

3.3–200 VOLTS



4

*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A = 25^oC$ Derate above 25^oC (See Figure 1)	P_D	1.0 6.67	Watt $mW/^oC$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +175	^oC
Lead Temperature 230^oC at a distance not less than 1/16" from the case for 10 seconds.			

MECHANICAL CHARACTERISTICS

CASE: Welded, hermetically sealed metal and glass.

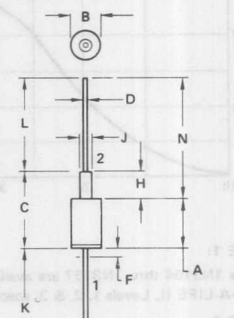
DIMENSIONS: See outline drawing.

FINISH: All external surfaces are corrosion-resistant and leads are readily solderable and weldable.

POLARITY: Cathode connected to the case. When operated in zener mode, cathode will be positive with respect to anode.

WEIGHT: 1.4 Grams (approx)

MOUNTING POSITION: Any



STYLE 1:
PIN 1. CATHODE
2. ANODE

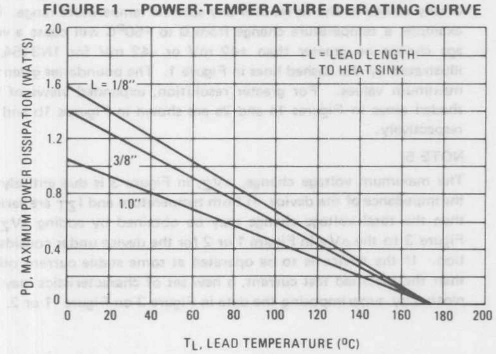
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	7.44	9.07	0.293	0.357
B	5.46	5.97	0.215	0.235
C	–	14.48	–	0.570
D	0.64	0.89	0.025	0.035
F	–	4.78	–	0.188
J	1.14	2.54	0.045	0.100
K	25.40	41.28	1.000	1.625
L	25.40	41.28	1.000	1.625

All JEDEC dimensions and notes apply

CASE 52-03
DO-13
METAL

NOTE:
1. ALL RULES AND NOTES ASSOCIATED WITH DO-13 OUTLINE SHALL APPLY.

FIGURE 1 — POWER-TEMPERATURE DERATING CURVE



*Indicates JEDEC Registered Data.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)
V_F = 1.5 V max @ I_F = 200 mA for all types

JEDEC Type No. (Flangeless)	*Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 1)	*Test Current I_{ZT} mA	*Max Zener Impedance (Note 4)			Max Reverse Current (Note 5)			*Max DC Zener Current I_{ZM} mA (Note 4)
			Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	I_R Max (μA)	V_{R1} 5%	V_{R2} 10%	
1N3821	3.3	76	10	400	1.0	*100	*1.0	1.0	276
1N3822	3.6	69	10	400	1.0	*100	*1.0	1.0	252
1N3823	3.9	64	9.0	400	1.0	*50	*1.0	1.0	238
1N3824	4.3	58	9.0	400	1.0	*10	*1.0	1.0	213
1N3825	4.7	53	8.0	500	1.0	*10	*1.0	1.0	194
1N3826	5.1	49	7.0	550	1.0	*10	*1.0	1.0	178
1N3827	5.6	45	5.0	600	1.0	*10	*2.0	2.0	162
1N3828	6.2	41	2.0	700	1.0	*10	*3.0	3.0	146
1N3829	6.8	37	1.5	500	1.0	*10	*3.0	3.0	133
1N3830	7.5	34	1.5	250	1.0	*10	*3.0	3.0	121
1N3016	6.8	37	3.5	700	1.0	10	5.2	4.9	140
1N3017	7.5	34	4.0	700	0.5	10	5.7	5.4	125
1N3018	8.2	31	4.5	700	0.5	10	6.2	5.9	115
1N3019	9.1	28	5.0	700	0.5	7.5	6.9	6.6	105
1N3020	10	25	7.0	700	0.25	5.0	7.6	7.2	95
1N3021	11	23	8.0	700	0.25	5.0	8.4	8.0	85
1N3022	12	21	9.0	700	0.25	2.0	9.1	8.6	80
1N3023	13	19	10	700	0.25	1.0	9.9	9.4	74
1N3024	15	17	14	700	0.25	1.0	11.4	10.8	63
1N3025	16	15.5	16	700	0.25	1.0	12.2	11.5	60
1N3026	18	14	20	750	0.25	0.5	13.7	13.0	52
1N3027	20	12.5	22	750	0.25	0.5	15.2	14.4	47
1N3028	22	11.5	23	750	0.25	0.5	16.7	15.8	43
1N3029	24	10.5	25	750	0.25	0.5	18.2	17.3	40
1N3030	27	9.5	35	750	0.25	0.5	20.6	19.4	34
1N3031	30	8.5	40	1000	0.25	0.5	22.8	21.6	31
1N3032	33	7.5	45	1000	0.25	0.5	25.1	23.8	28
1N3033	36	7.0	50	1000	0.25	0.5	27.4	25.9	26
1N3034	39	6.5	60	1000	0.25	0.5	29.7	28.1	23
1N3035	43	6.0	70	1500	0.25	0.5	32.7	31.0	21
1N3036	47	5.5	80	1500	0.25	0.5	35.8	33.8	19
1N3037	51	5.0	95	1500	0.25	0.5	38.8	36.7	18
1N3038	56	4.5	110	2000	0.25	0.5	42.6	40.3	17
1N3039	62	4.0	125	2000	0.25	0.5	47.1	44.6	15
1N3040	68	3.7	150	2000	0.25	0.5	51.7	49.0	14
1N3041	75	3.3	175	2000	0.25	0.5	56.0	54.0	12
1N3042	82	3.0	200	3000	0.25	0.5	62.2	59.0	11
1N3043	91	2.8	250	3000	0.25	0.5	69.2	65.5	10
1N3044	100	2.5	350	3000	0.25	0.5	76.0	72.0	9.0
1N3045	110	2.3	450	4000	0.25	0.5	83.6	79.2	8.3
1N3046	120	2.0	550	4500	0.25	0.5	91.2	86.4	8.0
1N3047	130	1.9	700	5000	0.25	0.5	98.8	93.6	6.9
1N3048	150	1.7	1000	6000	0.25	0.5	114.0	108.0	5.7
1N3049	160	1.6	1100	6500	0.25	0.5	121.6	115.2	5.4
1N3050	180	1.4	1200	7000	0.25	0.5	136.8	129.6	4.9
1N3051	200	1.2	1500	8000	0.25	0.5	152.0	144.0	4.6

* JEDEC Registered Data on 1N3821 thru 1N3830 and 1N3016 thru 1N3051

Example: 1M7.5AZZ10

NOTE 1 – ZENER VOLTAGE (V_Z) MEASUREMENT

Motorola guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature (T_L) at $30^oC \pm 1^oC$, 3/8" from the diode body.

NOTE 2 – ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK}.

NOTE 3 – REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed only for 5% and 10% zener diodes and are measured at V_R as shown in the Electrical Characteristics Table.

NOTE 4 – MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

1N3821 thru 1N3830 – Maximum zener current ratings are based on maximum voltage of 10% tolerance units.

1N3016 thru 1N3051 – Maximum zener current ratings are based on maximum voltage of 5% tolerance units.

NOTE 5 – SURGE CURRENT (i_r)

Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a specified pulse width, PW. The data presented in Figures 8 and 9 may be used to find the maximum surge current for a square wave of any pulse width between 0.01 ms and 1000 ms.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance ($^oC/W$) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30-40$^oC/W$ for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 6 for a train of power pulses (L = 3/8 inch) or from Figure 7 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Data of Figure 6 should not be used to compute surge capability. Surge limitations are given in Figure 8. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 8 be exceeded.

TEMPERATURE COEFFICIENTS AND VOLTAGE REGULATION

(90% OF THE UNITS ARE IN THE RANGES INDICATED)

FIGURE 2 – TEMPERATURE COEFFICIENT-RANGE FOR UNITS TO 12 VOLTS

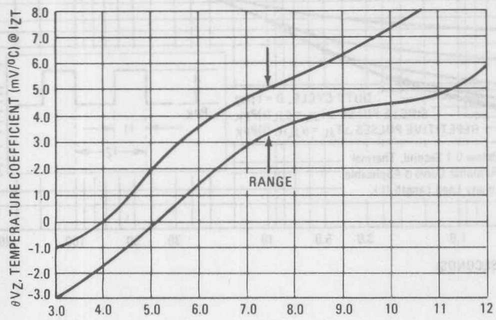


FIGURE 3 – TEMPERATURE COEFFICIENT-RANGE FOR UNITS 10 TO 220 VOLTS

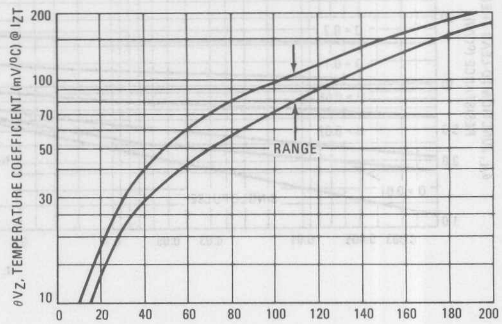


FIGURE 4 – TYPICAL VOLTAGE REGULATION

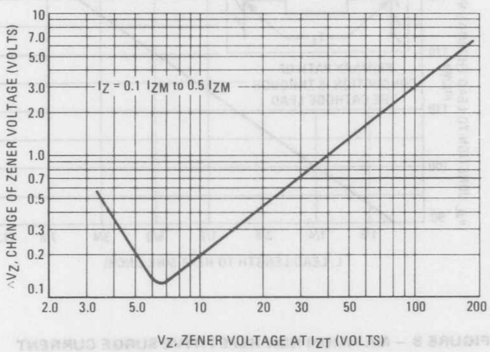


FIGURE 5 – MAXIMUM REVERSE LEAKAGE
(95% OF THE UNITS ARE BELOW THE VALUES SHOWN)

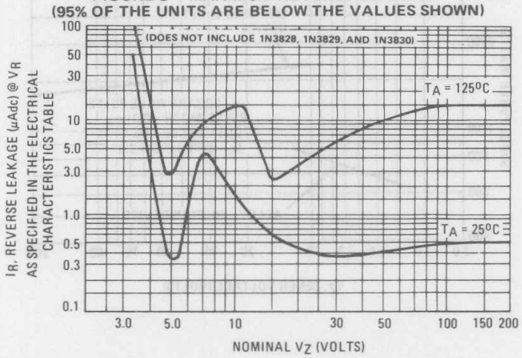


FIGURE 6 – TYPICAL THERMAL RESPONSE L, LEAD LENGTH = 3/8 INCH

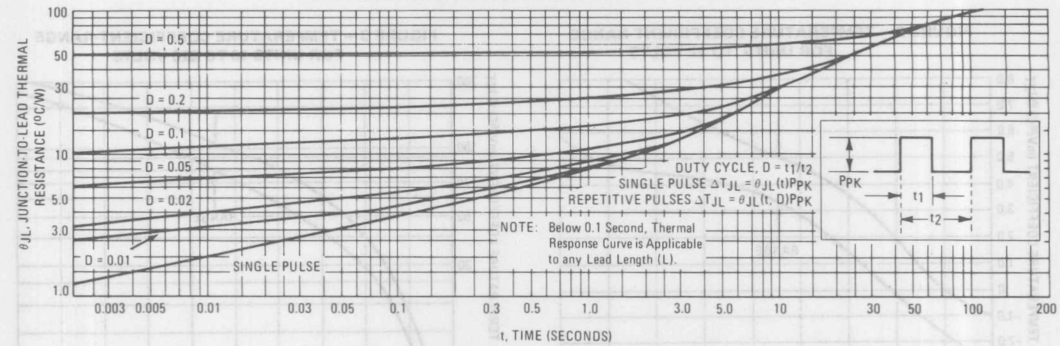


FIGURE 7 – TYPICAL THERMAL RESISTANCE

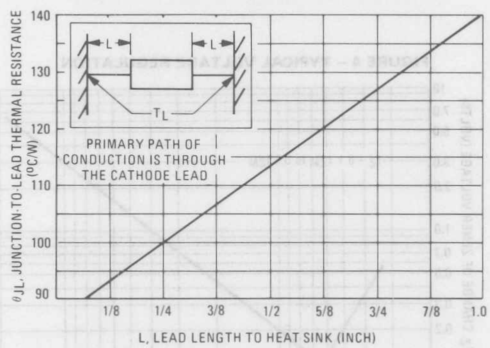
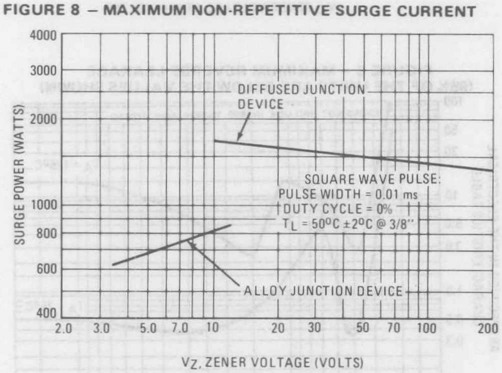


FIGURE 8 – MAXIMUM NON-REPETITIVE SURGE CURRENT



4

FIGURE 9 – SURGE POWER FACTOR

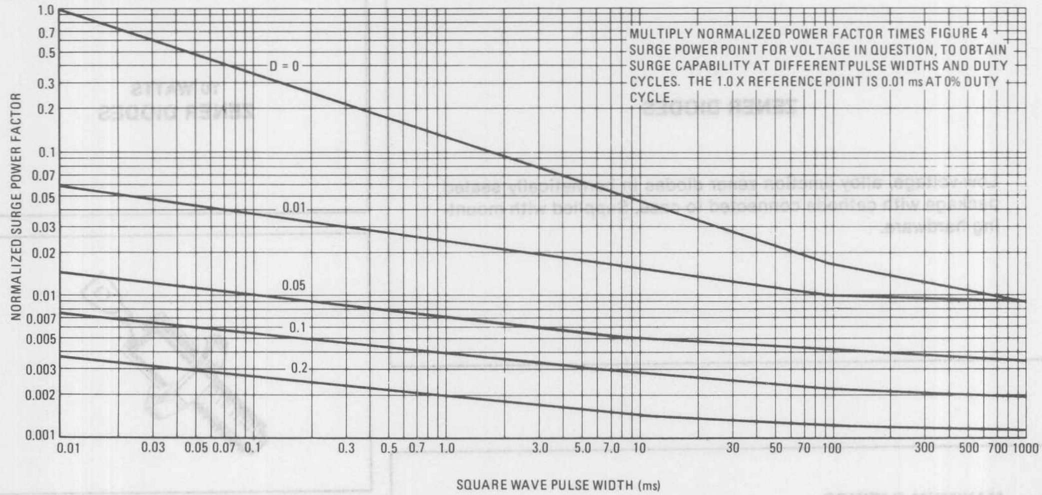
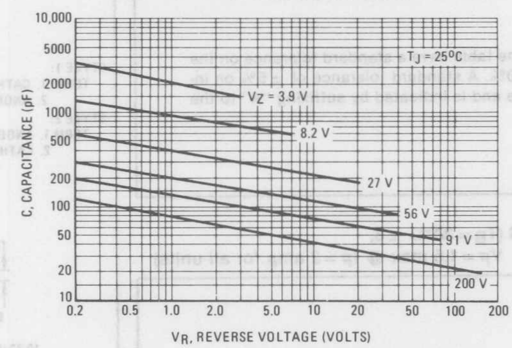


FIGURE 10 – TYPICAL CAPACITANCE



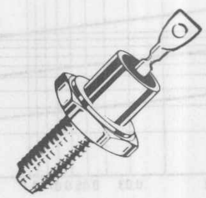
MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N3993 THRU 1N4000

ZENER DIODES

Low-voltage, alloy-junction zener diodes in hermetically sealed package with cathode connected to case. Supplied with mounting hardware.

10 WATTS ZENER DIODES



4

MAXIMUM RATINGS

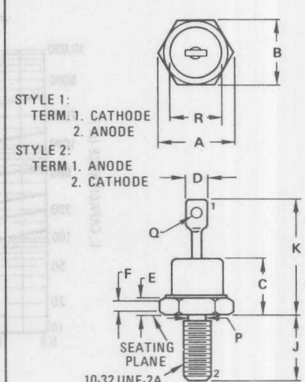
Junction and Storage Temperature: −65°C to +175°C.
DC Power Dissipation: 10 Watts. (Derate 83.3 mW/°C above 55°C).

The type numbers shown in the table have a standard tolerance on the nominal zener voltage of ±10%. A standard tolerance of ±5% on individual units is also available and is indicated by suffixing "A" to the standard type number.

ELECTRICAL CHARACTERISTICS ($T_B = 30°C \pm 3$, $V_F = 1.5$ max @ $I_F = 2$ amp for all units)

Type No.	Nominal Zener Voltage V_Z @ I_{ZT} Volts	Test Current I_{ZT} mA	Max Zener Impedance Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ $I_{ZK} = 1.0$ mA Ohms	Max DC Zener Current I_{ZM} mA	Reverse Leakage Current I_R μA	V_R Volts
1N3993	3.9	640	2.0	400	2380	100	0.5
1N3994	4.3	580	1.5	400	2130	100	0.5
1N3995	4.7	530	1.2	500	1940	50	1.0
1N3996	5.1	490	1.1	550	1780	10	1.0
1N3997	5.6	445	1.0	600	1620	10	1.0
1N3998	6.2	405	1.1	750	1460	10	2.0
1N3999	6.8	370	1.2	500	1330	10	2.0
1N4000	7.5	335	1.3	250	1210	10	3.0

SPECIAL SELECTIONS AVAILABLE INCLUDE: (See Selector Guide for details)



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	11.94	12.83	0.470	0.505
B	10.77	11.10	0.424	0.437
C	–	10.29	–	0.405
D	–	6.35	–	0.250
E	1.91	4.45	0.075	0.175
F	1.52	–	0.060	–
J	10.72	11.51	0.422	0.453
K	–	20.32	–	0.800
P	4.14	4.80	0.163	0.189
Q	1.52	–	0.060	–
R	–	10.77	–	0.424

All JEDEC dimensions and notes apply

CASE 56-02
DO-203AA
METAL

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4099 thru 1N4135
1N4614 thru 1N4627

LOW-LEVEL SILICON PASSIVATED ZENER DIODES

. . . designed for 250 mW applications requiring low leakage, low impedance, and low noise.

- Voltage Range from 1.8 to 100 Volts
- First Zener Diode Series to Specify Noise — 50% Lower than Conventional Diffused Zeners
- Zener Impedance and Zener Voltage Specified for Low-Level Operation at $I_{ZT} = 250\ \mu A$
- Low Leakage Current — I_R from 0.01 to 10 μA over Voltage Range

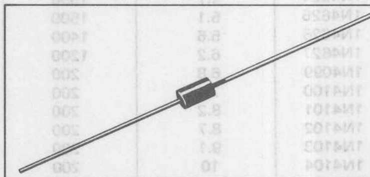
SILICON ZENER DIODES

($\pm$5.0% TOLERANCE)

250 MILLIWATTS

1.8-100 VOLTS

SILICON OXIDE PASSIVATED JUNCTION



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	250 1.43	mW mW/°C
Junction and Storage Temperature Range	T_J, T_{stg}	-65 to +200	°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass.

DIMENSIONS: See outline drawing.

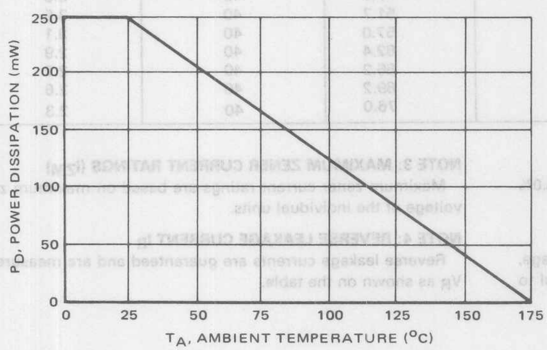
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.

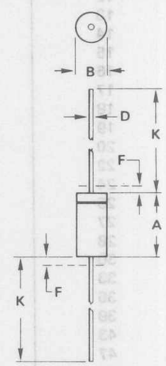
POLARITY: Cathode indicated by polarity band.

WEIGHT: 0.2 gram (approx.)

MOUNTING POSITION: Any

POWER TEMPERATURE DERATING CURVE





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

ELECTRICAL CHARACTERISTICS

(At 25°C Ambient temperature unless otherwise specified) I_{ZT} = 250 μA and V_F = 1.0 V max @ I_F = 200 mA on all Types

Type Number (Note 1)	Nominal Zener Voltage V_Z (Note 1) (Volts)	Max Zener Impedance Z_{ZT} (Note 2) (Ohms)	Max Reverse Current I_R (μA)	@ (Note 4)	Test Voltage V_R (Volts)	Max Noise Density At I_{ZT} = 250 μA N_D (Fig 1) (micro-volts per Square Root Cycle)	Max Zener Current I_{ZM} (Note 3) (mA)
1N4614	1.8	1200	7.5		1.0	1.0	120
1N4615	2.0	1250	5.0		1.0	1.0	110
1N4616	2.2	1300	4.0		1.0	1.0	100
1N4617	2.4	1400	2.0		1.0	1.0	95
1N4618	2.7	1500	1.0		1.0	1.0	90
1N4619	3.0	1600	0.8		1.0	1.0	85
1N4620	3.3	1650	7.5		1.5	1.0	80
1N4621	3.6	1700	7.5		2.0	1.0	75
1N4622	3.9	1650	5.0		2.0	1.0	70
1N4623	4.3	1600	4.0		2.0	1.0	65
1N4624	4.7	1550	10		3.0	1.0	60
1N4625	5.1	1500	10		3.0	2.0	55
1N4626	5.6	1400	10		4.0	4.0	50
1N4627	6.2	1200	10		5.0	5.0	45
1N4099	6.8	200	10		5.2	40	35
1N4100	7.5	200	10		5.7	40	31.8
1N4101	8.2	200	1.0		6.3	40	29.0
1N4102	8.7	200	1.0		6.7	40	27.4
1N4103	9.1	200	1.0		7.0	40	26.2
1N4104	10	200	1.0		7.6	40	24.8
1N4105	11	200	0.05		8.5	40	21.6
1N4106	12	200	0.05		9.2	40	20.4
1N4107	13	200	0.05		9.9	40	19.0
1N4108	14	200	0.05		10.7	40	17.5
1N4109	15	100	0.05		11.4	40	16.3
1N4110	16	100	0.05		12.2	40	15.4
1N4111	17	100	0.05		13.0	40	14.5
1N4112	18	100	0.05		13.7	40	13.2
1N4113	19	150	0.05		14.5	40	12.5
1N4114	20	150	0.01		15.2	40	11.9
1N4115	22	150	0.01		16.8	40	10.8
1N4116	24	150	0.01		18.3	40	9.9
1N4117	25	150	0.01		19.0	40	9.5
1N4118	27	150	0.01		20.5	40	8.8
1N4119	28	200	0.01		21.3	40	8.5
1N4120	30	200	0.01		22.8	40	7.9
1N4121	33	200	0.01		25.1	40	7.2
1N4122	36	200	0.01		27.4	40	6.6
1N4123	39	200	0.01		29.7	40	6.1
1N4124	43	250	0.01		32.7	40	5.5
1N4125	47	250	0.01		35.8	40	5.1
1N4126	51	300	0.01		38.8	40	4.6
1N4127	56	300	0.01		42.6	40	4.2
1N4128	60	400	0.01		45.6	40	4.0
1N4129	62	500	0.01		47.1	40	3.8
1N4130	68	700	0.01		51.7	40	3.5
1N4131	75	700	0.01		57.0	40	3.1
1N4132	82	800	0.01		62.4	40	2.9
1N4133	87	1000	0.01		66.2	40	2.7
1N4134	91	1200	0.01		69.2	40	2.6
1N4135	100	1500	0.01		76.0	40	2.3

NOTE 1: TOLERANCE AND VOLTAGE DESIGNATION

The type numbers shown have a standard tolerance of ±5.0% on the nominal zener voltage. C for ±2.0%, D for ±1%.

NOTE 2: ZENER IMPEDANCE (Z_{ZT}) DERIVATION

The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT}.

NOTE 3: MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum zener current ratings are based on maximum zener voltage of the individual units.

NOTE 4: REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed and are measured at V_R as shown on the table.

ZENER NOISE DENSITY

A zener diode generates noise when it is biased in the zener direction. A small part of this noise is due to the internal resistance associated with the device. A larger part of zener noise is a result of the zener breakdown phenomenon and is called microplasma noise. This microplasma noise is generally considered "white" noise with equal amplitude for all frequencies from about zero cycles to approximately 200,000 cycles. To eliminate the higher frequency components of noise a small shunting capacitor can be used. The lower frequency noise generally must be tolerated since a capacitor required to eliminate the lower frequencies would degrade the regulation properties of the zener in many applications.

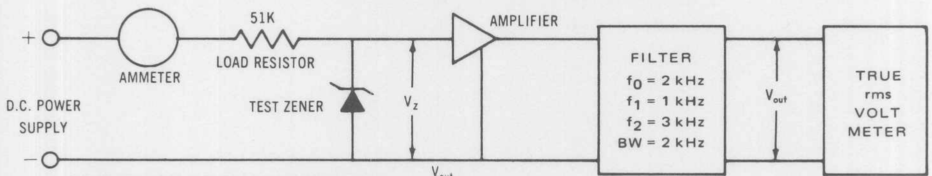
Motorola is rating this series with a maximum noise density at 250 microamperes. The rating of microvolts RMS per square root cycle enables calculation of the maximum RMS noise for any bandwidth.

Noise density decreases as zener current increases. This can be seen by the graph in Figure 2 where a typical noise density is plotted as a function of zener current.

The junction temperature will also change the zener noise levels. Thus the noise rating must indicate bandwidth, current level and temperature.

The block diagram given in Figure 1 shows the method used to measure noise density. The input voltage and load resistance is high so that the zener is driven from a constant current source. The amplifier must be low noise so that the amplifier noise is negligible compared to the test zener. The filter bandpass is known so that the noise density in volts RMS per square root cycle can be calculated.

FIGURE 1 – NOISE DENSITY MEASUREMENT METHOD



$$\text{NOISE DENSITY (VOLTS PER SQUARE ROOT CYCLE)} = \frac{V_{out}}{\text{OVERALL GAIN}\sqrt{BW}}$$

WHERE: BW = FILTER BANDWIDTH (CYCLES)

V_{out} = OUTPUT NOISE (VOLTS RMS)

FIGURE 2 – TYPICAL NOISE DENSITY versus ZENER CURRENT

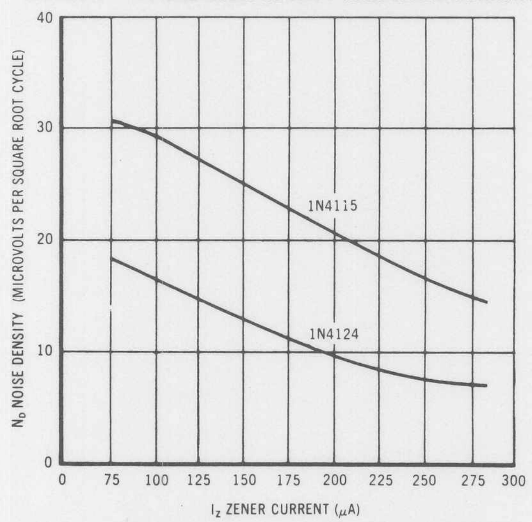


FIGURE 3 – TYPICAL CAPACITANCE

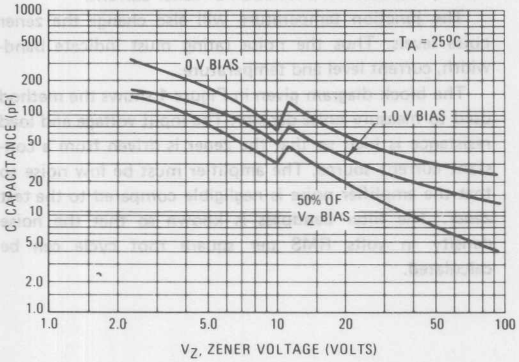
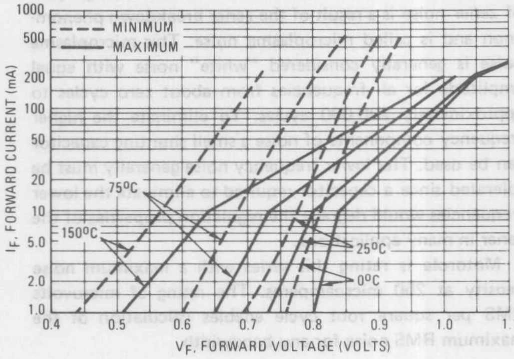


FIGURE 4 – TYPICAL FORWARD CHARACTERISTICS



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4370 thru 1N4372
See Page 4-4

1N4549 thru 1N4564
See Page 4-23

1N4565 thru 1N4584
1N4765 thru 1N4784

REFERENCE DIODES

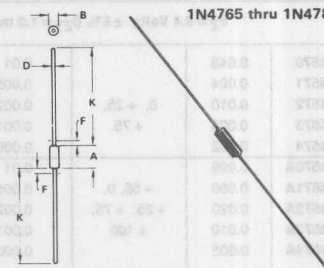
LOW LEVEL
TEMPERATURE-COMPENSATED
ZENER

LOW-LEVEL TEMPERATURE-COMPENSATED ZENER REFERENCE DIODES

Highly reliable reference sources utilizing a nitride/oxide-passivated junction for long-term voltage stability. Glass construction provides a rugged, hermetically sealed structure.

- **Low Power Drain Devices Specified @ 0.5 mA, 1.0 mA, 2.0 mA, and 4.0 mA**
- Maximum Voltage Change Specified over Test Temperature Range
- Temperature Compensation Guaranteed over Two Standard Operating Temperature Ranges:
  0 to 75°C
  −55 to 100°C

1N4765 thru 1N4784



NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

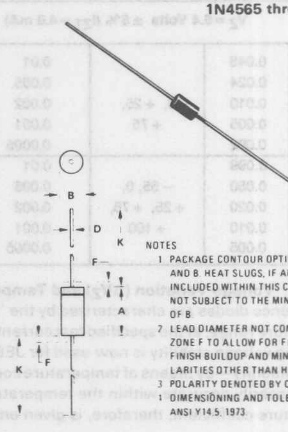
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A = 50°C$	P_D	400	mW
Derate above 50°C		3.2	mW/°C
Junction and Storage Temperature Range	T_J, T_{stg}	−65 to +175	°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass.
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 gram (approx.)
MOUNTING POSITION: Any

1N4565 thru 1N4584



NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F		1.27		0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

1N4565 thru 1N4584, 1N4775 thru 1N4784, 1N4765 thru 1N4774

4

TYPE	ΔV_Z (Note 1) Volts Max	@ Test Temperature °C	Temperature Coefficient for Reference %/°C (Note 1)	Dynamic Imped. Ohms Max (Note 2)
$V_Z = 6.4$ Volts ±5% ($I_{ZT} = 0.5$ mA)				
1N4565	0.048		0.01	
1N4566	0.024		0.005	
1N4567	0.010	0, +25, +75	0.002	200
1N4568	0.005		0.001	
1N4569	0.002		0.0005	
1N4565A	0.099		0.01	
1N4566A	0.050		0.005	
1N4567A	0.020	−55, 0, +25, +75, +100	0.002	200
1N4568A	0.010		0.001	
1N4569A	0.005		0.005	
$V_Z = 6.4$ Volts ±5% ($I_{ZT} = 1.0$ mA)				
1N4570	0.048		0.01	
1N4571	0.024		0.005	
1N4572	0.010	0, +25, +75	0.002	100
1N4573	0.005		0.001	
1N4574	0.002		0.0005	
1N4570A	0.099		0.01	
1N4571A	0.050		0.005	
1N4572A	0.020	−55, 0, +25, +75, +100	0.002	100
1N4573A	0.010		0.001	
1N4574A	0.005		0.0005	
$V_Z = 6.4$ Volts ±5% ($I_{ZT} = 2.0$ mA)				
1N4575	0.048		0.01	
1N4576	0.024		0.005	
1N4577	0.010	0, +25, +75	0.002	50
1N4578	0.005		0.001	
1N4579	0.002		0.0005	
1N4575A	0.099		0.01	
1N4576A	0.050		0.005	
1N4577A	0.020	−55, 0, +25, +75, +100	0.002	50
1N4578A	0.010		0.001	
1N4579A	0.005		0.0005	
$V_Z = 6.4$ Volts ±5% ($I_{ZT} = 4.0$ mA)				
1N4580	0.048		0.01	
1N4581	0.024		0.005	
1N4582	0.010	0, +25, +75	0.002	25
1N4583	0.005		0.001	
1N4584	0.002		0.0005	
1N4580A	0.099		0.01	
1N4581A	0.050		0.005	
1N4582A	0.020	−55, 0, +25, +75, +100	0.002	25
1N4583A	0.010		0.001	
1N4584A	0.005		0.0005	

TYPE	ΔV_Z (Note 1) Volts Max	@ Test Temperature °C	Temperature Coefficient for Reference %/°C (Note 1)	Dynamic Imped. Ohms Max (Note 2)
$V_Z = 8.5$ Volts ±5% ($I_{ZT} = 0.5$ mA)				
1N4775	0.064		0.01	
1N4776	0.032		0.005	
1N4777	0.013	0, +25, +75	0.002	200
1N4778	0.006		0.001	
1N4779	0.003		0.0005	
1N4775A	0.132		0.01	
1N4776A	0.066		0.005	
1N4777A	0.026	−55, 0, +25, +75, +100	0.002	200
1N4778A	0.013		0.001	
1N4779A	0.007		0.0005	
$V_Z = 8.5$ Volts ±5% ($I_{ZT} = 1.0$ mA)				
1N4780	0.064		0.01	
1N4781	0.032		0.005	
1N4782	0.013	0, +25, +75	0.002	100
1N4783	0.006		0.001	
1N4784	0.003		0.0005	
1N4780A	0.132		0.01	
1N4781A	0.066		0.005	
1N4782A	0.026	−55, 0, +25, +75, +100	0.002	100
1N4783A	0.013		0.001	
1N4784A	0.007		0.0005	
$V_Z = 9.1$ Volts ±5% ($I_{ZT} = 0.5$ mA)				
1N4765	0.068		0.01	
1N4766	0.034		0.005	
1N4767	0.014	0, +25, +75	0.002	350
1N4768	0.007		0.001	
1N4769	0.003		0.0005	
1N4765A	0.141		0.01	
1N4766A	0.070		0.005	
1N4767A	0.028	−55, 0, +25, +75, +100	0.002	350
1N4768A	0.014		0.001	
1N4769A	0.007		0.0005	
$V_Z = 9.1$ Volts ±5% ($I_{ZT} = 1.0$ mA)				
1N4770	0.068		0.01	
1N4771	0.034		0.005	
1N4772	0.014	0, +25, +75	0.002	200
1N4773	0.007		0.001	
1N4774	0.003		0.0005	
1N4770A	0.141		0.01	
1N4771A	0.070		0.005	
1N4772A	0.028	−55, 0, +25, +75, +100	0.002	200
1N4773A	0.014		0.001	
1N4774A	0.007		0.0005	

NOTE 1: Voltage Variation (ΔV_Z) and Temperature Coefficient.
All reference diodes are characterized by the "box method". This guarantees a maximum voltage variation (ΔV_Z) over the specified temperature range, at the specified test current (I_{ZT}), verified by tests at indicated temperature points within the range. This method of indicating voltage stability is now used for JEDEC registration as well as for military qualification. The former method of indicating voltage stability—by means of temperature coefficient—accurately reflects the voltage deviation at the temperature extremes, but is not necessarily accurate within the temperature range because reference diodes have a nonlinear temperature relationship. The temperature coefficient, therefore, is given only as a reference.

NOTE 2:
The dynamic zener impedance, Z_{ZT}, is derived from the 60 Hz ac voltage drop which results when an ac current with an rms value equal to 10% of the dc zener current, I_{ZT} is superimposed on I_{ZT}. A cathode-ray tube curve-trace test on a sample basis is used to ensure that the zener has a sharp and stable knee region.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4614 thru 1N4627
See Page 4-39

1N4678 thru 1N4717

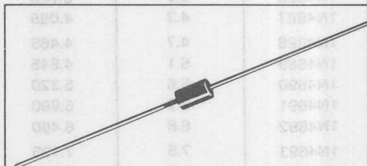
ZENER REGULATOR DIODES

Low level oxide passivated zener diodes for applications requiring extremely low operating currents, low leakage, and sharp breakdown voltage.

- Zener Voltage Specified @ I_{ZT} = 50 μA
- Maximum Delta V_Z Given from 10 to 100 μA

ZENER REGULATOR DIODES

250 MILLIWATTS



ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_A = 50°C Derate above T_A = 50°C	P_D	250 1.67	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed all glass case.

DIMENSIONS: See outline drawing.

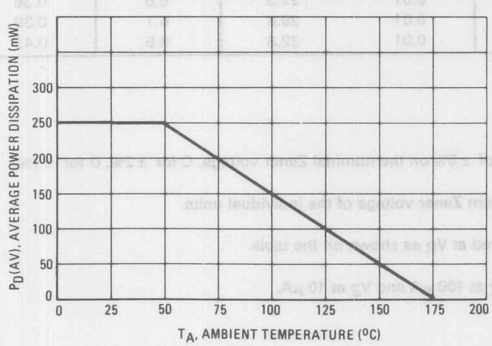
FINISH: All external surfaces are corrosion resistant with readily solerable leads.

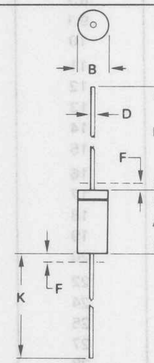
POLARITY: Cathode end indicated by color band. When operated in zener region, the cathode end will be positive with respect to anode end.

WEIGHT: 0.2 grams (approx.)

MOUNTING POSITION: Any.

FIGURE 1 – POWER TEMPERATURE DERATING CURVE





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

4

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$, $V_F = 1.5$ V max at $I_F = 100$ mA for all types)

Type Number (Note 1)	Zener Voltage V_Z @ $I_{ZT} = 50\ \mu A$ Volts			Maximum Reverse Current I_R µA	Test Voltage V_R Volts	Maximum Zener Current I_{ZM} mA (Note 2)	Maximum Voltage Change ΔV_Z Volts (Note 4)
	Nom (Note 1)	Min	Max	(Note 3)			
1N4678	1.8	1.710	1.890	7.5	1.0	120	0.70
1N4679	2.0	1.900	2.100	5.0	1.0	110	0.70
1N4680	2.2	2.090	2.310	4.0	1.0	100	0.75
1N4681	2.4	2.280	2.520	2.0	1.0	95	0.80
1N4682	2.7	2.565	2.835	1.0	1.0	90	0.85
1N4683	3.0	2.850	3.150	0.8	1.0	85	0.90
1N4684	3.3	3.135	3.465	7.5	1.5	80	0.95
1N4685	3.6	3.420	3.780	7.5	2.0	75	0.95
1N4686	3.9	3.705	4.095	5.0	2.0	70	0.97
1N4687	4.3	4.085	4.515	4.0	2.0	65	0.99
1N4688	4.7	4.465	4.935	10	3.0	60	0.99
1N4689	5.1	4.845	5.355	10	3.0	55	0.97
1N4690	5.6	5.320	5.880	10	4.0	50	0.96
1N4691	6.2	5.890	6.510	10	5.0	45	0.95
1N4692	6.8	6.460	7.140	10	5.1	35	0.90
1N4693	7.5	7.125	7.875	10	5.7	31.8	0.75
1N4694	8.2	7.790	8.610	1.0	6.2	29.0	0.50
1N4695	8.7	8.265	9.135	1.0	6.6	27.4	0.10
1N4696	9.1	8.645	9.555	1.0	6.9	26.2	0.08
1N4697	10	9.500	10.50	1.0	7.6	24.8	0.10
1N4698	11	10.45	11.55	0.05	8.4	21.6	0.11
1N4699	12	11.40	12.60	0.05	9.1	20.4	0.12
1N4700	13	12.35	13.65	0.05	9.8	19.0	0.13
1N4701	14	13.30	14.70	0.05	10.6	17.5	0.14
1N4702	15	14.25	15.75	0.05	11.4	16.3	0.15
1N4703	16	15.20	16.80	0.05	12.1	15.4	0.16
1N4704	17	16.15	17.85	0.05	12.9	14.5	0.17
1N4705	18	17.10	18.90	0.05	13.6	13.2	0.18
1N4706	19	18.05	19.95	0.05	14.4	12.5	0.19
1N4707	20	19.00	21.00	0.01	15.2	11.9	0.20
1N4708	22	20.90	23.10	0.01	16.7	10.8	0.22
1N4709	24	22.80	25.20	0.01	18.2	9.9	0.24
1N4710	25	23.75	26.25	0.01	19.0	9.5	0.25
1N4711	27	25.65	28.35	0.01	20.4	8.8	0.27
1N4712	28	26.60	29.40	0.01	21.2	8.5	0.28
1N4713	30	28.50	31.50	0.01	22.8	7.9	0.30
1N4714	33	31.35	34.65	0.01	25.0	7.2	0.33
1N4715	36	34.20	37.80	0.01	27.3	6.6	0.36
1N4716	39	37.05	40.95	0.01	29.6	6.1	0.39
1N4717	43	40.85	45.15	0.01	32.6	5.5	0.43

NOTES: 1. TOLERANCING AND VOLTAGE DESIGNATION (V_Z)

The type numbers shown have a standard tolerance of ±5% on the nominal Zener voltage, C for ±2%, D for ±1%.

2. MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum Zener current ratings are based on maximum Zener voltage of the individual units.

3. REVERSE LEAKAGE CURRENT (I_R)

Reverse leakage currents are guaranteed and measured at V_R as shown on the table.

4. MAXIMUM VOLTAGE CHANGE (ΔV_Z)

Voltage change is equal to the difference between V_Z at 100 µA and V_Z at 10 µA.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N4728,A thru 1N4764,A

Designers Data Sheet

ONE WATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

- Complete Voltage Range — 3.3 to 100 Volts
- DO-41 Package — Smaller than Conventional DO-7 Package
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die

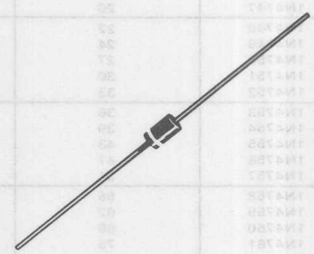
Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

1.0 WATT

ZENER REGULATOR DIODES

3.3–100 VOLTS



*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A = 50^oC$ Derate above 50^oC	P_D	1.0 6.67	Watt $mW/^oC$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	^oC

MECHANICAL CHARACTERISTICS

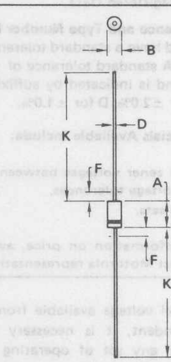
CASE: Double slug type, hermetically sealed glass

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from case for 10 seconds

FINISH: All external surfaces are corrosion resistant with readily solderable leads.

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.

MOUNTING POSITION: Any

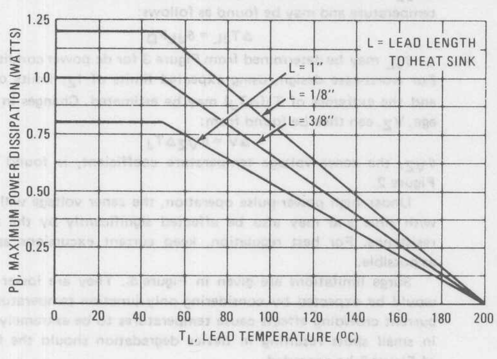


DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	–	1.27	–	0.050
K	27.94	–	1.100	–

CASE 59-03
DO-41
GLASS

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

FIGURE 1 — POWER TEMPERATURE DERATING CURVE



*Indicates JEDEC Registered Data

***ELECTRICAL CHARACTERISTICS** ($T_A = 25^oC$ unless otherwise noted) $V_F = 1.2$ V max, $I_F = 200$ mA for all types.

JEDEC Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Notes 2 and 3)	Test Current I_{ZT} mA	Maximum Zener Impedance (Note 4) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Leakage Current I_R μA Max	V_R Volts	Surge Current @ $T_A = 25^oC$ i_r – mA (Note 5)
1N4728	3.3	76	10	400	1.0	100	1.0	1380
1N4729	3.6	69	10	400	1.0	100	1.0	1260
1N4730	3.9	64	9.0	400	1.0	50	1.0	1190
1N4731	4.3	58	9.0	400	1.0	10	1.0	1070
1N4732	4.7	53	8.0	500	1.0	10	1.0	970
1N4733	5.1	49	7.0	550	1.0	10	1.0	890
1N4734	5.6	45	5.0	600	1.0	10	2.0	810
1N4735	6.2	41	2.0	700	1.0	10	3.0	730
1N4736	6.8	37	3.5	700	1.0	10	4.0	660
1N4737	7.5	34	4.0	700	0.5	10	5.0	605
1N4738	8.2	31	4.5	700	0.5	10	6.0	550
1N4739	9.1	28	5.0	700	0.5	10	7.0	500
1N4740	10	25	7.0	700	0.25	10	7.6	454
1N4741	11	23	8.0	700	0.25	5.0	8.4	414
1N4742	12	21	9.0	700	0.25	5.0	9.1	380
1N4743	13	19	10	700	0.25	5.0	9.9	344
1N4744	15	17	14	700	0.25	5.0	11.4	304
1N4745	16	15.5	16	700	0.25	5.0	12.2	285
1N4746	18	14	20	750	0.25	5.0	13.7	250
1N4747	20	12.5	22	750	0.25	5.0	15.2	225
1N4748	22	11.5	23	750	0.25	5.0	16.7	205
1N4749	24	10.5	25	750	0.25	5.0	18.2	190
1N4750	27	9.5	35	750	0.25	5.0	20.6	170
1N4751	30	8.5	40	1000	0.25	5.0	22.8	150
1N4752	33	7.5	45	1000	0.25	5.0	25.1	135
1N4753	36	7.0	50	1000	0.25	5.0	27.4	125
1N4754	39	6.5	60	1000	0.25	5.0	29.7	115
1N4755	43	6.0	70	1500	0.25	5.0	32.7	110
1N4756	47	5.5	80	1500	0.25	5.0	35.8	95
1N4757	51	5.0	95	1500	0.25	5.0	38.8	90
1N4758	56	4.5	110	2000	0.25	5.0	42.6	80
1N4759	62	4.0	125	2000	0.25	5.0	47.1	70
1N4760	68	3.7	150	2000	0.25	5.0	51.7	65
1N4761	75	3.3	175	2000	0.25	5.0	56.0	60
1N4762	82	3.0	200	3000	0.25	5.0	62.2	55
1N4763	91	2.8	250	3000	0.25	5.0	69.2	50
1N4764	100	2.5	350	3000	0.25	5.0	76.0	45

*Indicates JEDEC Registered Data.

NOTE 1 — Tolerance and Type Number Designation. The JEDEC type numbers listed have a standard tolerance on the nominal zener voltage of ±10%. A standard tolerance of ±5% on individual units is also available and is indicated by suffixing "A" to the standard type number. C for ±2.0%, D for ±1.0%.

NOTE 2 – Specials Available Include:

A. Nominal zener voltages between the voltages shown and tighter voltage tolerances,

B. Matched sets.

For detailed information on price, availability, and delivery, contact your nearest Motorola representative.

NOTE 3 – Zener Voltage (V_Z) Measurement. Motorola guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature (T_L) at $30^oC \pm 1^oC$, 3/8" from the diode body.

NOTE 4 – Zener Impedance (Z_Z) Derivation. The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK}.

NOTE 5 – Surge Current (i_r) Non-Repetitive. The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current, I_{ZT}, per JEDEC registration; however, actual device capability is as described in Figure 5.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from

$$T_L = \theta_{LA}P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance ($^oC/W$) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to $40^oC/W$ for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found as follows:

$$\Delta T_{JL} = \theta_{JL}P_D$$

θ_{JL} may be determined from Figure 3 for dc power conditions. For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ}\Delta T_J$$

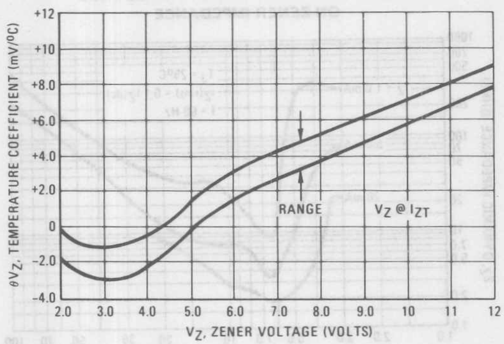
θ_{VZ}, the zener voltage temperature coefficient, is found from Figure 2.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 5. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 5 be exceeded.

FIGURE 2 – TEMPERATURE COEFFICIENTS
($-55^{\circ}C$ to $+150^{\circ}C$ temperature range; 90% of the units are in the ranges indicated.)

a – RANGE FOR UNITS TO 12 VOLTS



b – RANGE FOR UNITS 12 TO 100 VOLTS

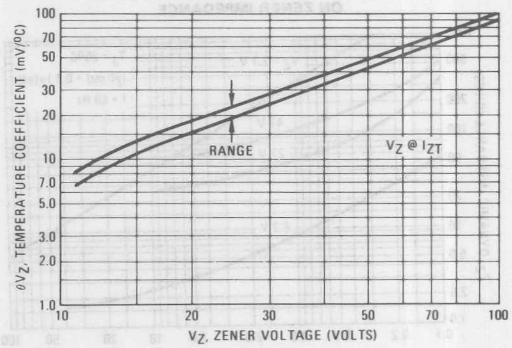


FIGURE 3 – TYPICAL THERMAL RESISTANCE versus LEAD LENGTH

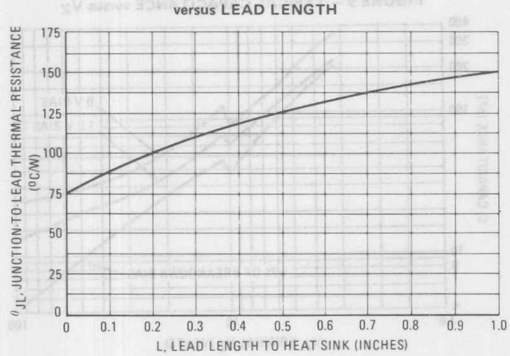


FIGURE 4 – EFFECT OF ZENER CURRENT

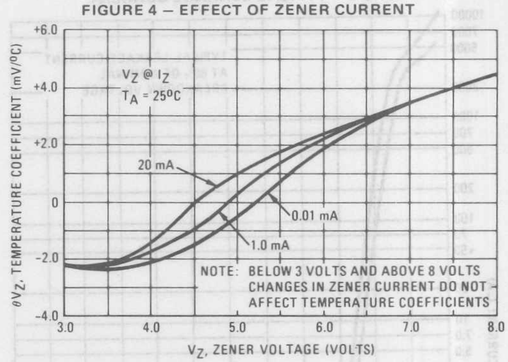
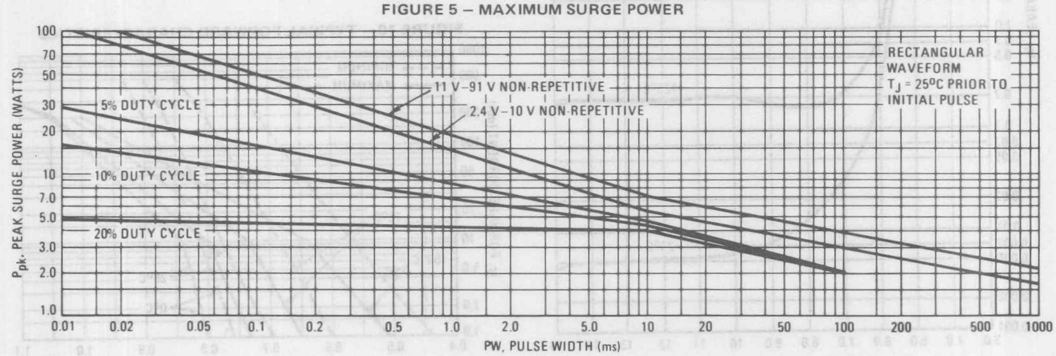


FIGURE 5 – MAXIMUM SURGE POWER



This graph represents 90 percentile data points.
For worst-case design characteristics, multiply surge power by 2/3.

FIGURE 6 – EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

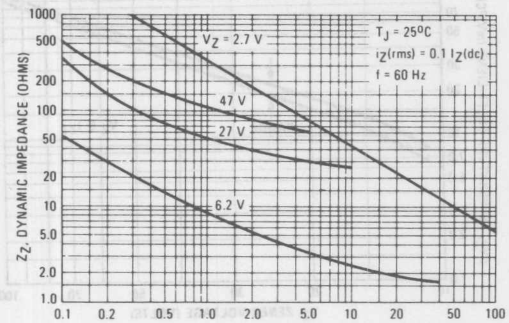


FIGURE 7 – EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

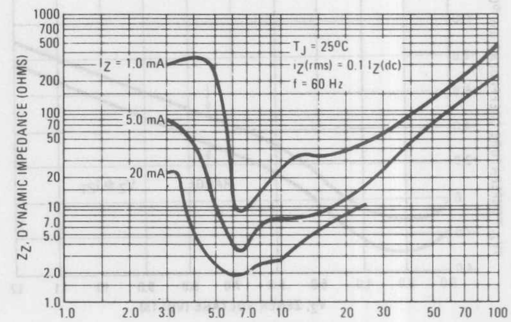


FIGURE 8 – TYPICAL LEAKAGE CURRENT

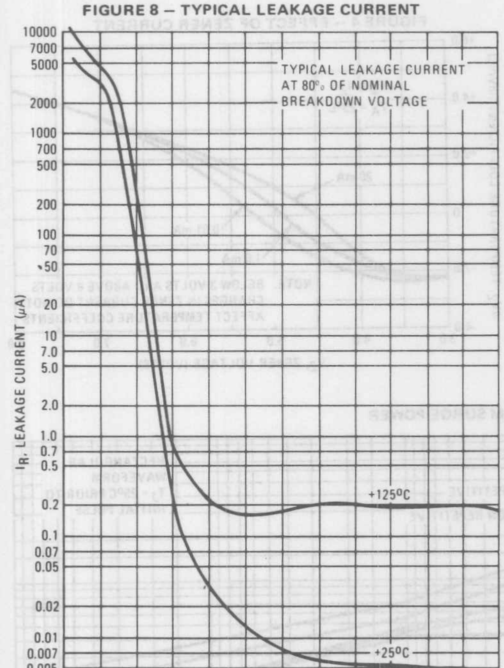


FIGURE 9 – TYPICAL CAPACITANCE versus V_Z

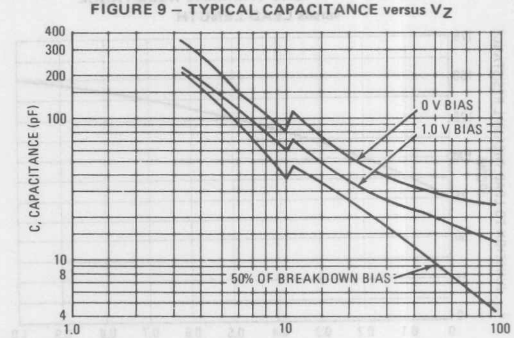
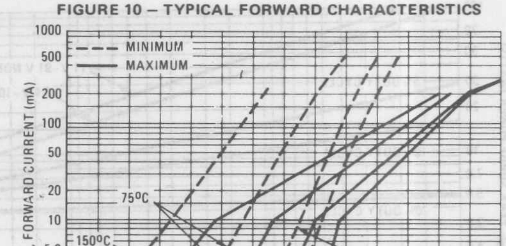


FIGURE 10 – TYPICAL FORWARD CHARACTERISTICS



4

1N4765 thru 1N4784
See Page 4-45

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5221A thru 1N5272A

Designers Data Sheet

500 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

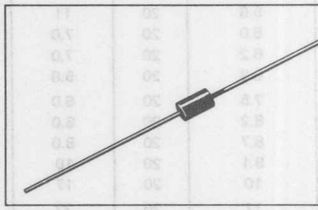
- Complete Voltage Range — 2.4 to 110 Volts**
- DO-35 Package — Smaller than Conventional DO-7 Package
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die

Designer's Data for "Worst Case" Conditions

The Designer's Data sheets permit the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

GLASS ZENER DIODES

500 MILLIWATTS
2.4-110 VOLTS



*MAXIMUM RATINGS

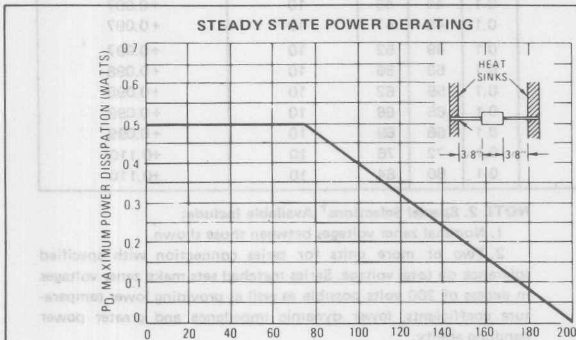
Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_L \leq 75^{\circ}C$ Lead Length = 3/8" Derate above $T_L = 75^{\circ}C$	P_D	500 4.0	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

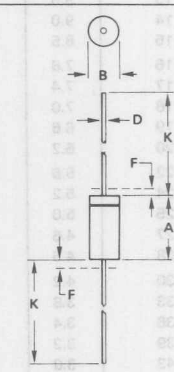
*Indicates JEDEC Registered Data
**See 1N5273 thru 1N5281 for devices > 110 volts.

MECHANICAL CHARACTERISTICS

CASE: Double slug type, hermetically sealed glass
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from case for 10 seconds
FINISH: All external surfaces are corrosion resistant with readily solderable leads
POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode
MOUNTING POSITION: Any

STEADY STATE POWER DERATING





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

4

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted. Based on dc measurements at thermal equilibrium; lead length = 3/8"; thermal resistance of heat sink = 30°C/W) V_F = 1.1 max @ I_F = 200 mA for all types.

JEDEC Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max Zener Impedance A and B Suffix only: Z_{ZT} @ I_{ZT} Ohms	Max Zener Impedance A and B Suffix only: Z_{ZK} @ I_{ZK} = 0.25 mA Ohms	Max Reverse Leakage Current, A and B Suffix only: I_R µA	@ V_R Volts A	@ V_R Volts B	Max Reverse Leakage Current, Non-Suffix: I_R @ V_R Used for Suffix A µA	Max Zener Voltage Temperature Coeff. (A and B Suffix only) θ_{VZ} (%/°C) (Note 3)
1N5221A	2.4	20	30	1200	100	0.95	1.0	200	−0.085
1N5222A	2.5	20	30	1250	100	0.95	1.0	200	−0.085
1N5223A	2.7	20	30	1300	75	0.95	1.0	150	−0.080
1N5224A	2.8	20	30	1400	75	0.95	1.0	150	−0.080
1N5225A	3.0	20	29	1600	50	0.95	1.0	100	−0.075
1N5226A	3.3	20	28	1600	25	0.95	1.0	100	−0.070
1N5227A	3.6	20	24	1700	15	0.95	1.0	100	−0.065
1N5228A	3.9	20	23	1900	10	0.95	1.0	75	−0.060
1N5229A	4.3	20	22	2000	5.0	0.95	1.0	50	±0.055
1N5230A	4.7	20	19	1900	5.0	1.9	2.0	50	±0.030
1N5231A	5.1	20	17	1600	5.0	1.9	2.0	50	±0.030
1N5232A	5.6	20	11	1600	5.0	2.9	3.0	50	+0.038
1N5233A	6.0	20	7.0	1600	5.0	3.3	3.5	50	+0.038
1N5234A	6.2	20	7.0	1000	5.0	3.8	4.0	50	+0.045
1N5235A	6.8	20	5.0	750	3.0	4.8	5.0	30	+0.050
1N5236A	7.5	20	6.0	500	3.0	5.7	6.0	30	+0.058
1N5237A	8.2	20	8.0	500	3.0	6.2	6.5	30	+0.062
1N5238A	8.7	20	8.0	600	3.0	6.2	6.5	30	+0.065
1N5239A	9.1	20	10	600	3.0	6.7	7.0	30	+0.068
1N5240A	10	20	17	600	3.0	7.6	8.0	30	+0.075
1N5241A	11	20	22	600	2.0	8.0	8.4	30	+0.076
1N5242A	12	20	30	600	1.0	8.7	9.1	10	+0.077
1N5243A	13	9.5	13	600	0.5	9.4	9.9	10	+0.079
1N5244A	14	9.0	15	600	0.1	9.5	10	10	+0.082
1N5245A	15	8.5	16	600	0.1	10.5	11	10	+0.082
1N5246A	16	7.8	17	600	0.1	11.4	12	10	+0.083
1N5247A	17	7.4	19	600	0.1	12.4	13	10	+0.084
1N5248A	18	7.0	21	600	0.1	13.3	14	10	+0.085
1N5249A	19	6.6	23	600	0.1	13.3	14	10	+0.086
1N5250A	20	6.2	25	600	0.1	14.3	15	10	+0.086
1N5251A	22	5.6	29	600	0.1	16.2	17	10	+0.087
1N5252A	24	5.2	33	600	0.1	17.1	18	10	+0.088
1N5253A	25	5.0	35	600	0.1	18.1	19	10	+0.089
1N5254A	27	4.6	41	600	0.1	20	21	10	+0.090
1N5255A	28	4.5	44	600	0.1	20	21	10	+0.091
1N5256A	30	4.2	49	600	0.1	22	23	10	+0.091
1N5257A	33	3.8	58	700	0.1	24	25	10	+0.092
1N5258A	36	3.4	70	700	0.1	26	27	10	+0.093
1N5259A	39	3.2	80	800	0.1	29	30	10	+0.094
1N5260A	43	3.0	93	900	0.1	31	33	10	+0.095
1N5261A	47	2.7	105	1000	0.1	34	36	10	+0.095
1N5262A	51	2.5	125	1100	0.1	37	39	10	+0.096
1N5263A	56	2.2	150	1300	0.1	41	43	10	+0.096
1N5264A	60	2.1	170	1400	0.1	44	46	10	+0.097
1N5265A	62	2.0	185	1400	0.1	45	47	10	+0.097
1N5266A	68	1.8	230	1600	0.1	49	52	10	+0.097
1N5267A	75	1.7	270	1700	0.1	53	56	10	+0.098
1N5268A	82	1.5	330	2000	0.1	59	62	10	+0.098
1N5269A	87	1.4	370	2200	0.1	65	68	10	+0.099
1N5270A	91	1.4	400	2300	0.1	66	69	10	+0.099
1N5271A	100	1.3	500	2600	0.1	72	76	10	+0.110
1N5272A	110	1.1	750	3000	0.1	80	84	10	+0.110

NOTE 1. Tolerance — The JEDEC type numbers shown indicate a tolerance of ±10% with guaranteed limits on only V_Z, I_R and V_F as shown in the electrical characteristics table. Units with guaranteed limits on all six parameters are indicated by suffix "A" for ±10% tolerance and suffix "B" for ±5.0% units, C for ±2%, D for ±1%.

†For more information on special selections contact your nearest Motorola representative.

NOTE 2. Special Selections† Available Include:

1. Nominal zener voltages between those shown.
2. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.
3. Nominal voltages at non-standard test currents.

NOTE 3. Temperature Coefficient (θ_{VZ}) — Test conditions for temperature coefficient are as follows:

a. I_{ZT} = 7.5 mA, T_1 = 25°C,
T_2 = 125°C (1N5221A,B through 1N5242A,B).

b. I_{ZT} = Rated I_{ZT}, T_1 = 25°C,
T_2 = 125°C (1N5243A,B through 1N5272A, B).

Device to be temperature stabilized with current applied prior to reading breakdown voltage at the specified ambient temperature.

NOTE 4. Zener Voltage (V_Z) Measurement — Nominal zener voltage is measured with the device junction in thermal equilibrium at the lead temperature of 30°C ± 1°C and 3/8" lead length.

NOTE 5. Zener Impedance (Z_Z) Derivation — Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for I_Z(ac) = I_Z(dc) with the ac frequency = 60 Hz.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA}P_D + T_A.$$

θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30 to 40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}.$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 1 for dc power:

$$\Delta T_{JL} = \theta_{JL}P_D.$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ}\Delta T_J.$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 3 and 4.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

FIGURE 1 — TYPICAL THERMAL RESISTANCE

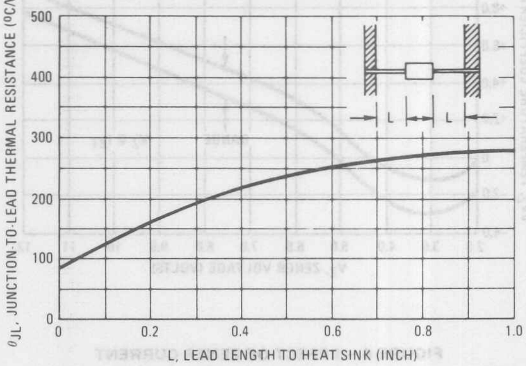


FIGURE 2 — TYPICAL LEAKAGE CURRENT

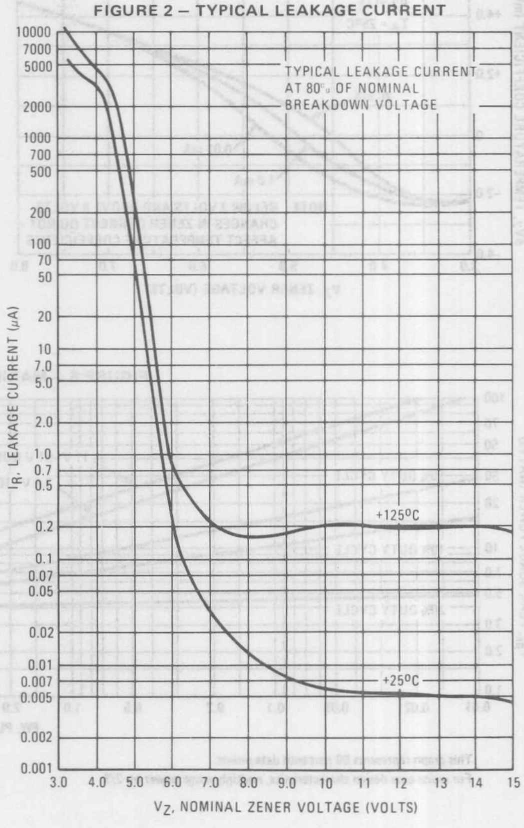
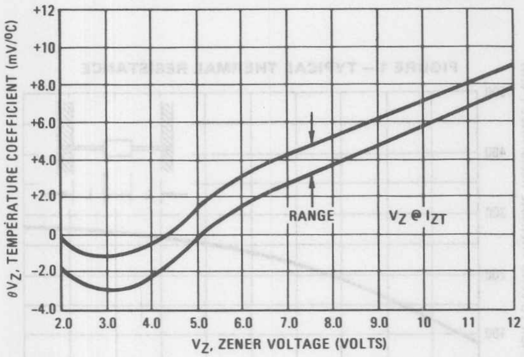


FIGURE 3 — TEMPERATURE COEFFICIENTS

(−55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

a — RANGE FOR UNITS TO 12 VOLTS



b — RANGE FOR UNITS 12 TO 100 VOLTS

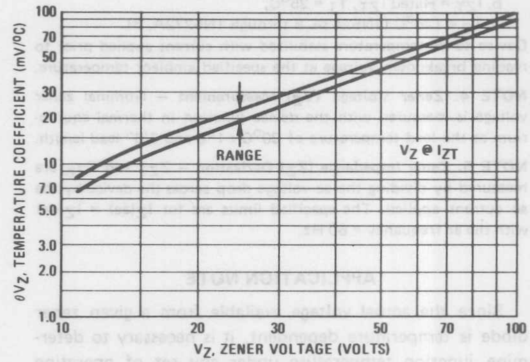


FIGURE 4 — EFFECT OF ZENER CURRENT

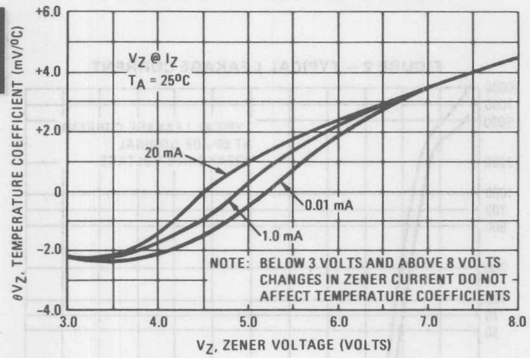


FIGURE 5 — TYPICAL CAPACITANCE

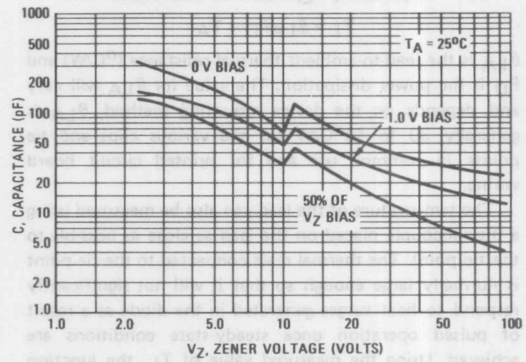
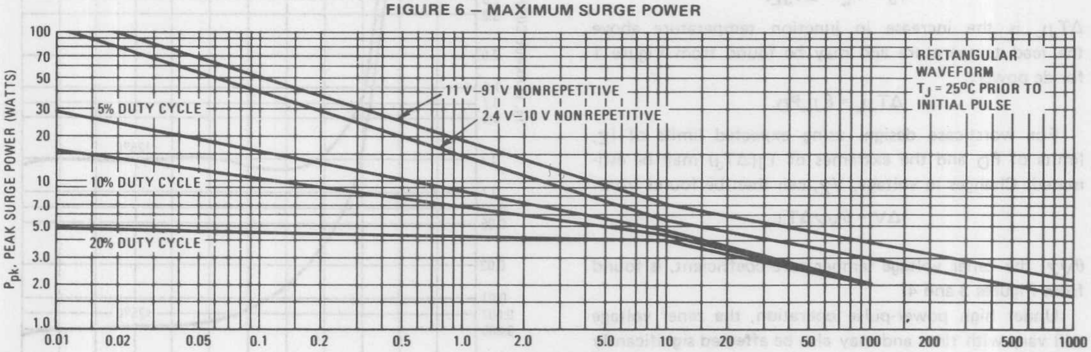


FIGURE 6 — MAXIMUM SURGE POWER



This graph represents 90 percentil data points.
For worst-case design characteristics, multiply surge power by 2/3.

FIGURE 7 – EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

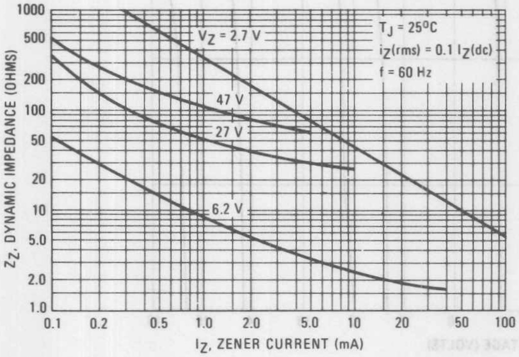


FIGURE 8 – EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

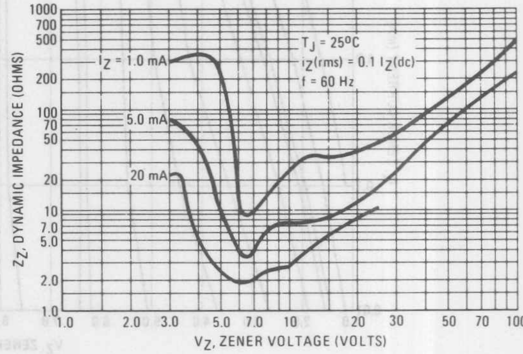


FIGURE 9 – TYPICAL NOISE DENSITY

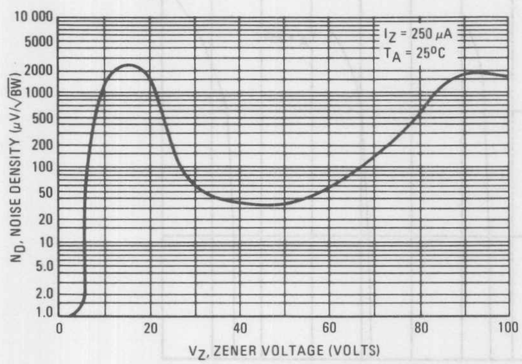
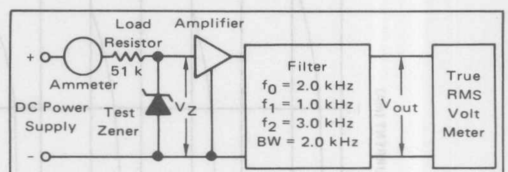


FIGURE 10 – NOISE DENSITY MEASUREMENT METHOD



Noise Density (Volts Per Square Root Bandwidth) = $\frac{V_{out}}{\text{Overall Gain } \sqrt{BW}}$

Where: BW = Filter Bandwidth (Hz)
V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

4

FIGURE 11 – TYPICAL FORWARD CHARACTERISTICS

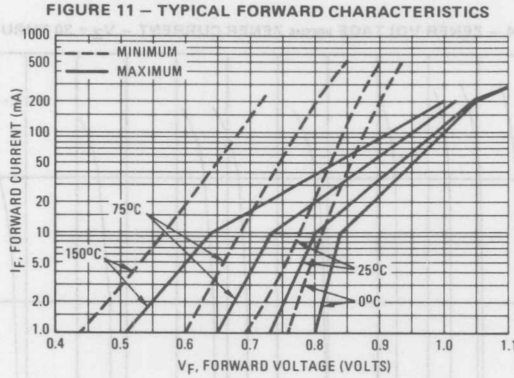


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FIGURE 12 – ZENER VOLTAGE versus ZENER CURRENT – V_Z = 1 THRU 16 VOLTS

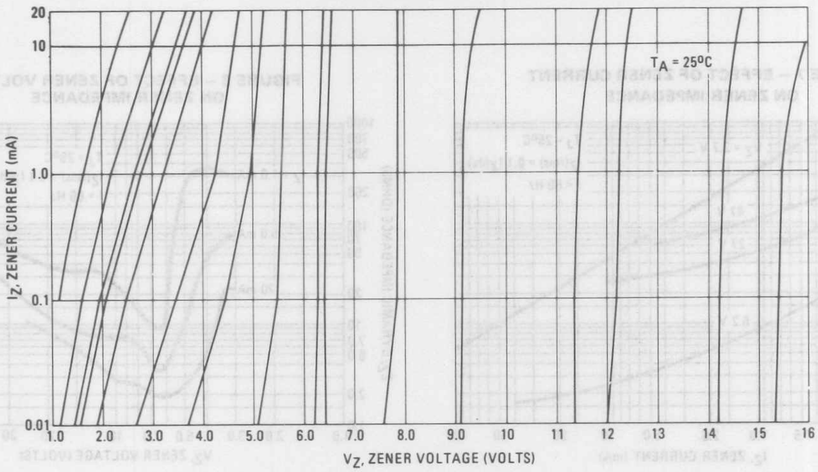


FIGURE 13 – ZENER VOLTAGE versus ZENER CURRENT – V_Z = 15 THRU 30 VOLTS

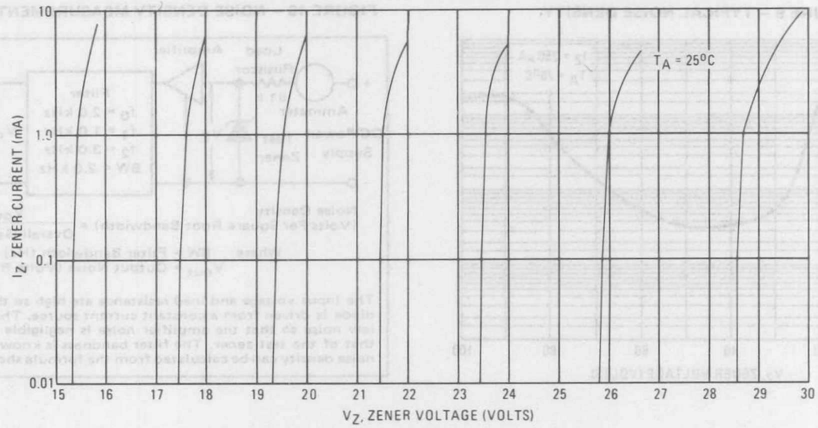
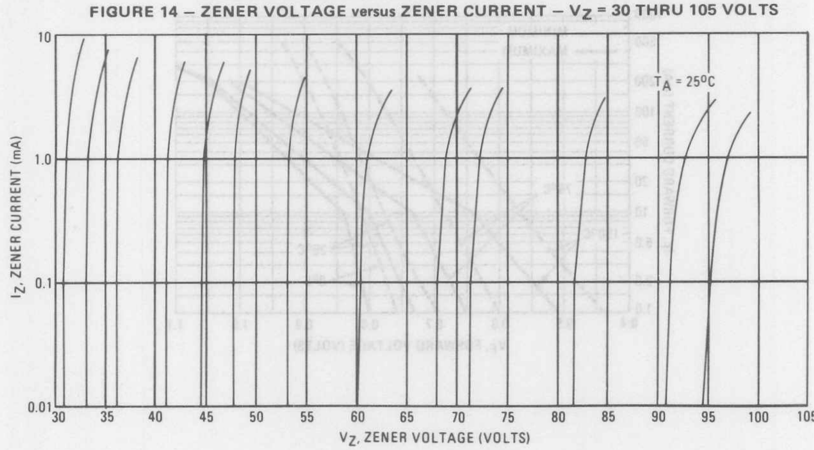


FIGURE 14 – ZENER VOLTAGE versus ZENER CURRENT – V_Z = 30 THRU 105 VOLTS



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5273 thru 1N5281

Advance Information

500 MILLIWATT SURMETIC 20 SILICON ZENER DIODES
(SILICON OXIDE PASSIVATED)

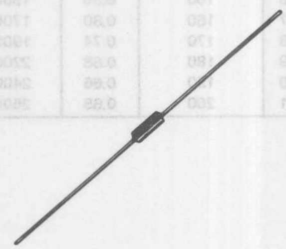
. . . in answer to the Circuit Design and Component Engineers' many requests — A complete new series of Zener Diodes in the popular DO-204AA case with higher ratings, tighter limits, better operating characteristics and a full set of designers' curves that reflect the superior capabilities of silicon-oxide-passivated junctions. All this in an axial-lead, transfer-molded plastic package offering protection in all common environmental conditions.

- Proven Capability to MIL-S-19500 Specifications
- 10 Watt Surge Rating
- Weldable Leads
- Maximum Limits Guaranteed on Six Electrical Parameters

500 MILLIWATT

ZENER REGULATOR DIODES

120-200 VOLTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_L = 75^oC$, Lead Length = 3/8" Derate above $T_L = 75^oC$	P_D	500 4.0	mW mW/^oC
Surge Power (Non-Recurrent Square Wave @ PW = 8.3 ms, $T_J = 55^oC$)	—	10	Watts
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to +200	^oC
Lead Temperature not less than 1/16" from the case for 10 seconds: 230^oC.			

MECHANICAL CHARACTERISTICS

CASE: Void free, transfer molded, thermosetting plastic.

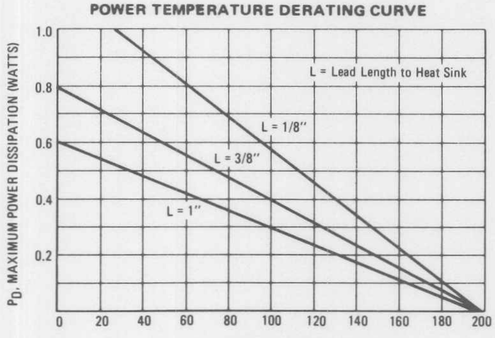
FINISH: All external surfaces are corrosion resistant. Leads are readily solderable and weldable.

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.

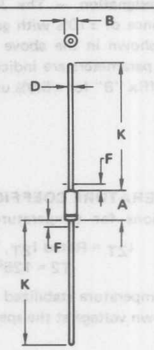
MOUNTING POSITION: Any.

WEIGHT: 0.18 gram (approximately).

POWER TEMPERATURE DERATING CURVE



This document contains information on a new product. Specifications and information herein are subject to change without notice.



NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

4

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted. Based on dc measurements at thermal equilibrium; lead length = 3/8"; thermal resistance of heat sink = 30°C/W). V_F = 1.1 max @ I_F = 200 mA for all types.

JEDEC Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Notes 2 & 4)	Test Current I_{ZT} mA	Max Zener Impedance A and B Suffix Only Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} = 0.25 mA Ohms	Max Reverse Leakage Current A and B Suffix Only I_R µA	@ V_R Volts A	V_R Volts B	Non-Suffix I_R @ V_R Used For Suffix A µA	Max Zener Voltage Temperature Coefficient (A and B Suffix Only) θ_{VZ} (%/°C) (Note 3)
1N5273	120	1.0	900	4000	0.1	86	91	10	+0.110
1N5274	130	0.95	1100	4500	0.1	94	99	10	+0.110
1N5275	140	0.90	1300	4500	0.1	101	106	10	+0.110
1N5276	150	0.85	1500	5000	0.1	108	114	10	+0.110
1N5277	160	0.80	1700	5500	0.1	116	122	10	+0.110
1N5278	170	0.74	1900	5500	0.1	116	129	10	+0.110
1N5279	180	0.68	2200	6000	0.1	130	137	10	+0.110
1N5280	190	0.66	2400	6500	0.1	137	144	10	+0.110
1N5281	200	0.65	2500	7000	0.1	144	152	10	+0.110

NOTE 1. TOLERANCE AND VOLTAGE DESIGNATION

Tolerance Designation — The JEDEC type numbers shown indicate a tolerance of ±10% with guaranteed limits on only V_Z, I_R, and V_F as shown in the above table. Units with guaranteed limits on all six parameters are indicated by suffix "A" for ±10% tolerance and suffix "B" for ±5.0% units.

NOTE 3. TEMPERATURE COEFFICIENT (θ_{VZ})

Test conditions for temperature coefficient are as follows:

I_{ZT} = Rated I_{ZT}, T1 = 25°C,
T2 = 125°C.

Device to be temperature stabilized with current applied prior to reading breakdown voltage at the specified ambient temperature.

NOTE 2. SPECIAL SELECTIONS AVAILABLE INCLUDE:

1. Nominal zener voltages between those shown.
2. Matched sets (standard tolerances are ±5.0%, ±2.0%, ±1.0%).

   a. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.

   b. Two or more units matched to one another with any specified tolerance.
3. Tight voltage tolerances: 1.0%, 2.0%, 3.0%.

NOTE 4. ZENER VOLTAGE (V_Z) MEASUREMENT

Motorola guarantees the zener voltage when measured at 90 seconds while maintaining the lead temperature (T_L) at 30°C ±1°C, 3/8" from the diode body.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5283 thru 1N5314

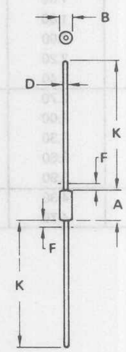
CURRENT REGULATOR DIODES

CURRENT REGULATOR DIODES

Field-effect current regulator diodes are circuit elements that provide a current essentially independent of voltage. These diodes are especially designed for maximum impedance over the operating range. These devices may be used in parallel to obtain higher currents.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Operating Voltage ($T_J = -55°$ C to $+200°$C)	POV	100	Volts
Steady State Power Dissipation @ $T_L = 75°$C Derate above $T_L = 75°$C Lead Length = 3/8″ (Forward or Reverse Bias)	P_D	600 4.8	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200	°C



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

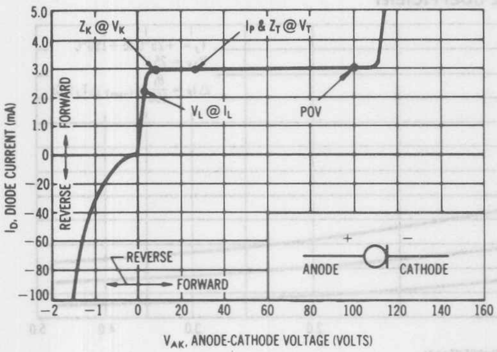
NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

4

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Type No.	Regulator Current I_P (mA) @ $V_T = 25$ V nom	min	max	Minimum Dynamic Impedance @ $V_T = 25$ V Z_T (MΩ)	Minimum Knee Impedance @ $V_K = 6.0$ V Z_K (MΩ)	Maximum Limiting Voltage @ $I_L = 0.8$ I_P (min) V_L (Volts)
1N5283	0.22	0.198	0.242	25.0	2.75	1.00
1N5284	0.24	0.216	0.264	19.0	2.35	1.00
1N5285	0.27	0.243	0.297	14.0	1.95	1.00
1N5286	0.30	0.270	0.330	9.0	1.60	1.00
1N5287	0.33	0.297	0.363	6.6	1.35	1.00
1N5288	0.39	0.351	0.429	4.10	1.00	1.05
1N5289	0.43	0.387	0.473	3.30	0.870	1.05
1N5290	0.47	0.423	0.517	2.70	0.750	1.05
1N5291	0.56	0.504	0.616	1.90	0.560	1.10
1N5292	0.62	0.558	0.682	1.55	0.470	1.13
1N5293	0.68	0.612	0.748	1.35	0.400	1.15
1N5294	0.75	0.675	0.825	1.15	0.335	1.20
1N5295	0.82	0.738	0.902	1.00	0.290	1.25
1N5296	0.91	0.819	1.001	0.880	0.240	1.29
1N5297	1.00	0.900	1.100	0.800	0.205	1.35
1N5298	1.10	0.990	1.210	0.700	0.180	1.40
1N5299	1.20	1.08	1.32	0.640	0.155	1.45
1N5300	1.30	1.17	1.43	0.580	0.135	1.50
1N5301	1.40	1.26	1.54	0.540	0.115	1.55
1N5302	1.50	1.35	1.65	0.510	0.105	1.60
1N5303	1.60	1.44	1.76	0.475	0.092	1.65
1N5304	1.80	1.62	1.98	0.420	0.074	1.75
1N5305	2.00	1.80	2.20	0.395	0.061	1.85
1N5306	2.20	1.98	2.42	0.370	0.052	1.95
1N5307	2.40	2.16	2.64	0.345	0.044	2.00
1N5308	2.70	2.43	2.97	0.320	0.035	2.15
1N5309	3.00	2.70	3.30	0.300	0.029	2.25
1N5310	3.30	2.97	3.63	0.280	0.024	2.35
1N5311	3.60	3.24	3.96	0.265	0.020	2.50
1N5312	3.90	3.51	4.29	0.255	0.017	2.60
1N5313	4.30	3.87	4.73	0.245	0.014	2.75
1N5314	4.70	4.23	5.17	0.235	0.012	2.90

FIGURE 1 — TYPICAL CURRENT REGULATOR CHARACTERISTICS



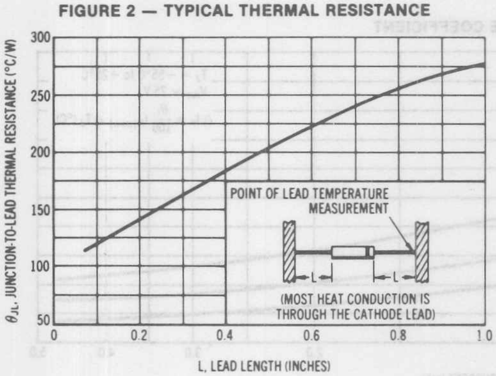
SYMBOLS AND DEFINITIONS

I_D — Diode Current.
I_L — Limiting Current: 80% of I_P minimum used to determine Limiting voltage, V_L.
I_P — Pinch-off Current: Regulator current at specified Test Voltage, V_T.
POV — Peak Operating Voltage: Maximum voltage to be applied to device.
θ_I — Current Temperature Coefficient.
V_{AK} — Anode-to-cathode Voltage.
V_K — Knee Impedance Test Voltage: Specified voltage used to establish Knee Impedance, Z_K.
V_L — Limiting Voltage: Measured at I_L. V_L, together with Knee AC Impedance, Z_K, indicates the Knee characteristics of the device.
V_T — Test Voltage: Voltage at which I_P and Z_T are specified.
Z_K — Knee AC Impedance at Test Voltage: To test for Z_K, a 90 Hz signal v_K with RMS value equal to 10% of test voltage, V_K, is superimposed on V_K:

$$Z_K = v_K / i_K$$

where i_K is the resultant ac current due to v_K
To provide the most constant current from the diode, Z_K should be as high as possible; therefore, a minimum value of Z_K is specified.
Z_T — AC Impedance at Test Voltage: Specified as a minimum value. To test for Z_T, a 90 Hz signal with RMS value equal to 10% of Test Voltage, V_T, is superimposed on V_T.

FIGURE 2 — TYPICAL THERMAL RESISTANCE



APPLICATION NOTE

As the current available from the diode is temperature dependent, it is necessary to determine junction temperature, T_J, under specific operating conditions to calculate the value of the diode current. The following procedure is recommended:

Lead Temperature, T_L, shall be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

where θ_{LA} is lead-to-ambient thermal resistance
and P_D is power dissipation.

θ_{LA} is generally 30-40°C/W for the various clips and tie points in common use, and for printed circuit-board wiring.

Junction Temperature, T_J, shall be calculated from:

$$T_J = T_L + \theta_{JL} P_D$$

where θ_{JL} is taken from Figure 2.

For circuit design limits of V_{AK}, limits of P_D may be estimated and extremes of T_J may be computed. Using the information on Figures 4 and 5, changes in current regulation may be found. To improve current regulation, keep V_{AK} low to reduce P_D and keep the leads short, especially the cathode lead, to reduce θ_{JL}.

FIGURE 3 — TYPICAL FORWARD CHARACTERISTICS

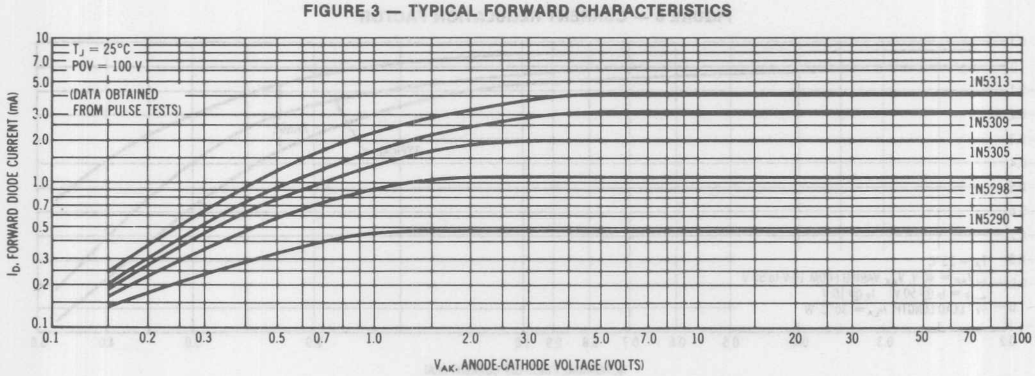


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FIGURE 4 — TEMPERATURE COEFFICIENT

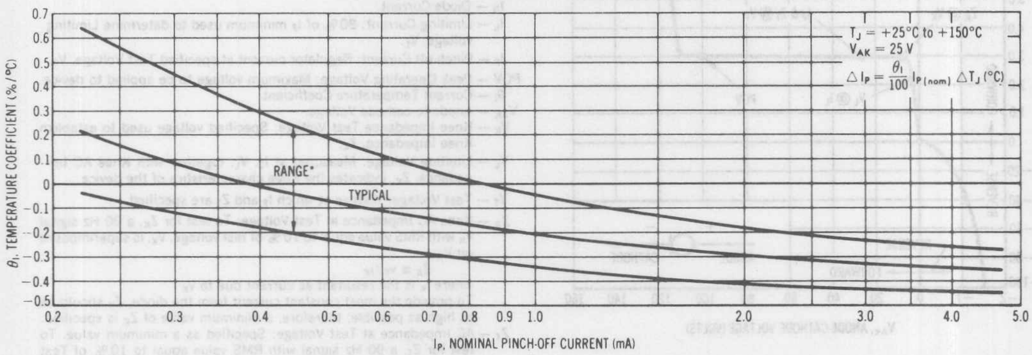


FIGURE 5 — TEMPERATURE COEFFICIENT

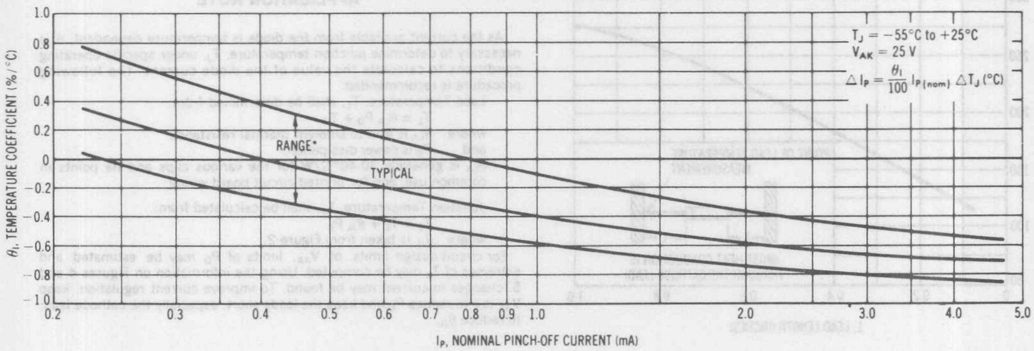
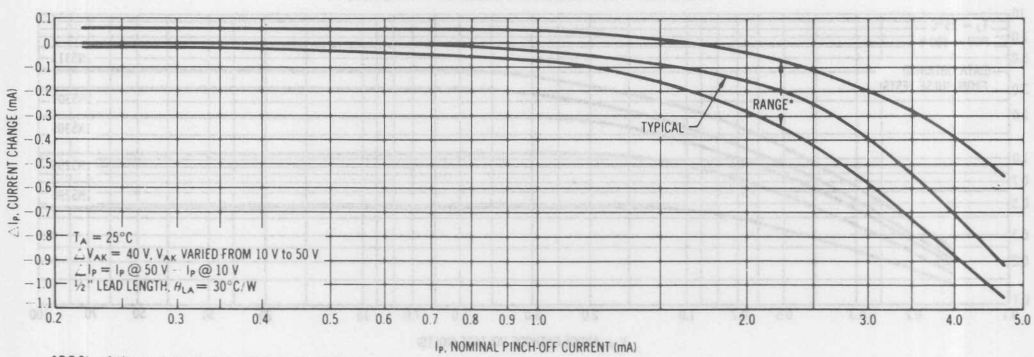


FIGURE 6 — CURRENT REGULATION FACTOR



*90% of the units will be in the ranges shown.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

Designer's Data Sheet

5-Watt Surmetic 40 Silicon Zener Diodes

1N5333A,B,C,D thru 1N5388A,B,C,D

5-WATT ZENER REGULATOR DIODES 3.3–200 VOLTS

. . . a complete series of 5 Watt Zener Diodes with tight limits and better operating characteristics that reflect the superior capabilities of silicon-oxide-passivated junctions. All this in an axial-lead, transfer-molded plastic package offering protection in all common environmental conditions.

- Up to 180 Watt Surge Rating @ 8.3 ms
- Maximum Limits Guaranteed on Seven Electrical Parameters
- Offered in 10%, 5%, 2% and 1% V_Z Tolerance

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic
FINISH: All external surfaces are corrosion resistant and leads are readily solderable
POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode
MOUNTING POSITION: Any
WEIGHT: 0.7 gram (approx)

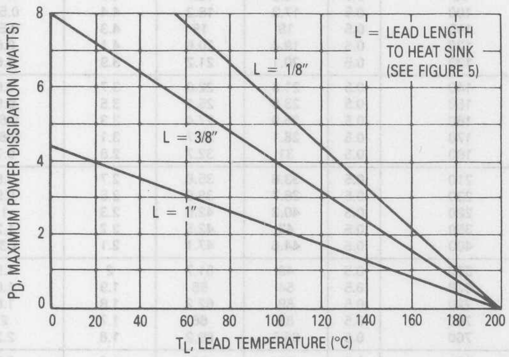
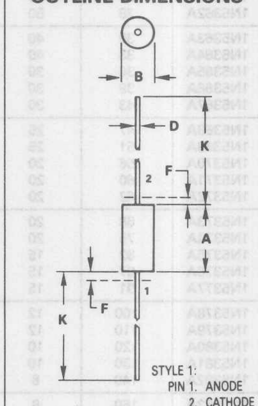


Figure 1. Power-Temperature Derating Curve

OUTLINE DIMENSIONS



NOTE:
1. LEAD DIAMETER & FINISH NOT CONTROLLED WITHIN DIM "F".

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.38	8.89	0.330	0.350
B	3.30	3.68	0.130	0.145
D	0.94	1.09	0.037	0.043
F	—	1.27	—	0.050
K	25.40	31.75	1.000	1.250

CASE 17-02 GLASS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_L = 75°C Lead Length = 3/8" Derate above 75°C	P_D	5 40	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, V_F = 1.2 Max @ I_F = 1 A for all types)

JEDEC Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max Zener Impedance A & B Suffix Only		Max Reverse Leakage Current			Applies to all Suffix	A & B Suffix Only	Maximum Regulator Current I_{ZM} mA (Note 5)
			Z_{ZT} @ I_{ZT} Ohms (Note 2)	Z_{ZK} @ I_{ZK} = 1 mA Ohms (Note 2)	I_R μA	@ V_R Volts Non & A Suffix	V_R Volts B-Suffix	Max Surge Current i_r, Amps (Note 3)	Max Voltage Regulation ΔV_Z, Volts (Note 4)	
1N5333A	3.3	380	3	400	300	1	1	20	0.85	1440
1N5334A	3.6	350	2.5	500	150	1	1	18.7	0.8	1320
1N5335A	3.9	320	2	500	50	1	1	17.6	0.54	1220
1N5336A	4.3	290	2	500	10	1	1	16.4	0.49	1100
1N5337A	4.7	260	2	450	5	1	1	15.3	0.44	1010
1N5338A	5.1	240	1.5	400	1	1	1	14.4	0.39	930
1N5339A	5.6	220	1	400	1	2	2	13.4	0.25	865
1N5340A	6	200	1	300	1	3	3	12.7	0.19	790
1N5341A	6.2	200	1	200	1	4	3	12.4	0.1	765
1N5342A	6.8	175	1	200	10	4.9	5.2	11.5	0.15	700
1N5343A	7.5	175	1.5	200	10	5.4	5.7	10.7	0.15	630
1N5344A	8.2	150	1.5	200	10	5.9	6.2	10	0.2	580
1N5345A	8.7	150	2	200	10	6.3	6.6	9.5	0.2	545
1N5346A	9.1	150	2	150	7.5	6.6	6.9	9.2	0.22	520
1N5347A	10	125	2	125	5	7.2	7.6	8.6	0.22	475
1N5348A	11	125	2.5	125	5	8	8.4	8	0.25	430
1N5349A	12	100	2.5	125	2	8.6	9.1	7.5	0.25	395
1N5350A	13	100	2.5	100	1	9.4	9.9	7	0.25	365
1N5351A	14	100	2.5	75	1	10.1	10.6	6.7	0.25	340
1N5352A	15	75	2.5	75	1	10.8	11.5	6.3	0.25	315
1N5353A	16	75	2.5	75	1	11.5	12.2	6	0.3	295
1N5354A	17	70	2.5	75	0.5	12.2	12.9	5.8	0.35	280
1N5355A	18	65	2.5	75	0.5	13	13.7	5.5	0.4	265
1N5356A	19	65	3	75	0.5	13.7	14.4	5.3	0.4	250
1N5357A	20	65	3	75	0.5	14.4	15.2	5.1	0.4	237
1N5358A	22	50	3.5	75	0.5	15.8	16.7	4.7	0.45	216
1N5359A	24	50	3.5	100	0.5	17.3	18.2	4.4	0.55	198
1N5360A	25	50	4	110	0.5	18	19	4.3	0.55	190
1N5361A	27	50	5	120	0.5	19.4	20.6	4.1	0.6	176
1N5362A	28	50	6	130	0.5	20.1	21.2	3.9	0.6	170
1N5363A	30	40	8	140	0.5	21.6	22.8	3.7	0.6	158
1N5364A	33	40	10	150	0.5	23.8	25.1	3.5	0.6	144
1N5365A	36	30	11	160	0.5	25.9	27.4	3.3	0.65	132
1N5366A	39	30	14	170	0.5	28.1	29.7	3.1	0.65	122
1N5367A	43	30	20	190	0.5	31	32.7	2.8	0.7	110
1N5368A	47	25	25	210	0.5	33.8	35.8	2.7	0.8	100
1N5369A	51	25	27	230	0.5	36.7	38.8	2.5	0.9	93
1N5370A	56	20	35	280	0.5	40.3	42.6	2.3	1	86
1N5371A	60	20	40	350	0.5	43	42.5	2.2	1.2	79
1N5372A	62	20	42	400	0.5	44.6	47.1	2.1	1.35	76
1N5373A	68	20	44	500	0.5	49	51.7	2	1.5	70
1N5374A	75	20	45	620	0.5	54	56	1.9	1.6	63
1N5375A	82	15	65	720	0.5	59	62.2	1.8	1.8	58
1N5376A	87	15	75	760	0.5	63	66	1.7	2	54.5
1N5377A	91	15	75	760	0.5	65.5	69.2	1.6	2.2	52.5
1N5378A	100	12	90	800	0.5	72	76	1.5	2.5	47.5
1N5379A	110	12	125	1000	0.5	79.2	83.6	1.4	2.5	43
1N5380A	120	10	170	1150	0.5	86.4	91.2	1.3	2.5	39.5
1N5381A	130	10	190	1250	0.5	93.6	98.8	1.2	2.5	36.6
1N5382A	140	8	230	1500	0.5	101	106	1.2	2.5	34
1N5383A	150	8	330	1500	0.5	108	114	1.1	3	31.6
1N5384A	160	8	350	1650	0.5	115	122	1.1	3	29.4
1N5385A	170	8	380	1750	0.5	122	129	1	3	28
1N5386A	180	5	430	1750	0.5	130	137	1	4	26.4
1N5387A	190	5	450	1850	0.5	137	144	0.9	5	25
1N5388A	200	5	480	1850	0.5	144	152	0.9	5	23.6

NOTES:

(1) TOLERANCE AND VOLTAGE DESIGNATION — The JEDEC type numbers shown indicate a tolerance of ±10% with guaranteed limits on only V_Z, I_R, i_r, and V_F as shown in the electrical characteristics table. Units with guaranteed limits on all seven parameters are indicated by suffix "A" for ±10% tolerance and suffix "B" for ±5%, C for ±2% and D for ±1%.

(2) ZENER VOLTAGE (V_Z) AND IMPEDANCE (Z_{ZT} & Z_{ZK}) — Test conditions for Zener voltage and impedance are as follows: I_Z is applied 40 ± 10 ms prior to reading. Mounting contacts are located 3/8″ to 1/2″ from the inside edge of mounting clips to the body of the diode. (T_A = 25°C $^{+8}_{-2}$°C).

(3) SURGE CURRENT (i_r) — Surge current is specified as the maximum allowable peak, non-recurrent square-wave current with a pulse width, PW, of 8.3 ms. The data given in Figure 6 may be used to find the maximum surge current for a square wave of any pulse width between 1 ms and 1000 ms by plotting the applicable points on logarithmic paper. Examples of this, using the 3.3 V and 200 V zeners, are shown in Figure 7. Mounting contact located as specified in Note 3. (T_A = 25°C $^{+8}_{-2}$°C).

(4) VOLTAGE REGULATION (ΔV_Z) — Test conditions for voltage regulation are as follows: V_Z measurements are made at 10% and then at 50% of the I_Z max value listed in the electrical characteristics table. The test currents are the same for the 5% and 10% tolerance devices. The test current time duration for each V_Z measurement is 40 ± 10 ms. (T_A = 25°C $^{+8}_{-2}$°C). Mounting contact located as specified in Note 2.

(5) MAXIMUM REGULATOR CURRENT (I_{ZM}) — The maximum current shown is based on the maximum voltage of a 5% type unit, therefore, it applies only to the B-suffix device. The actual I_{ZM} for any device may not exceed the value of 5 watts divided by the actual V_Z of the device. T_L = 75°C at 3/8″ maximum from the device body.

TEMPERATURE COEFFICIENTS

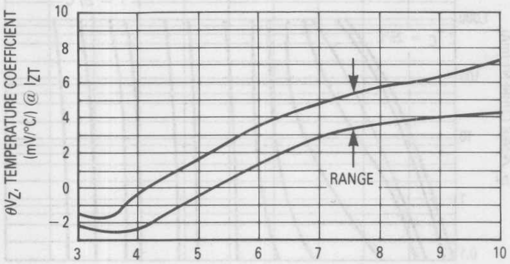


Figure 2. Temperature Coefficient-Range for Units 3 to 10 Volts

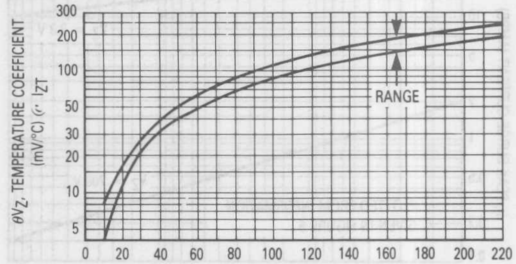


Figure 3. Temperature Coefficient-Range for Units 10 to 220 Volts

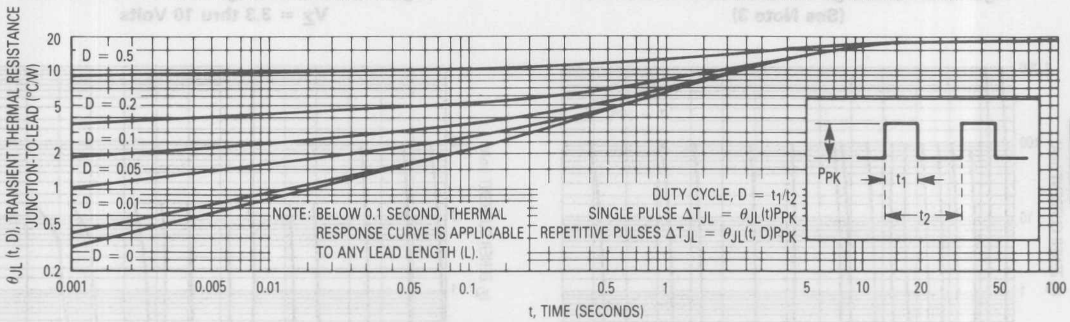


Figure 4. Typical Thermal Response L, Lead Length = 3.8 Inch

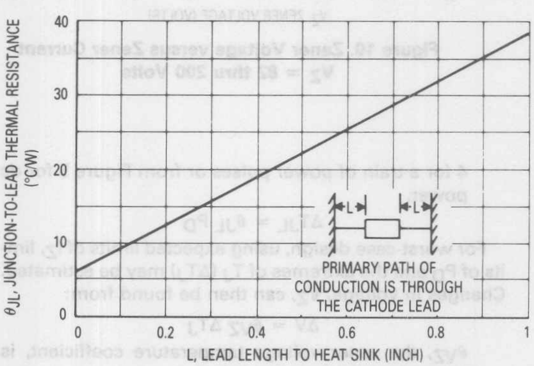


Figure 5. Typical Thermal Resistance

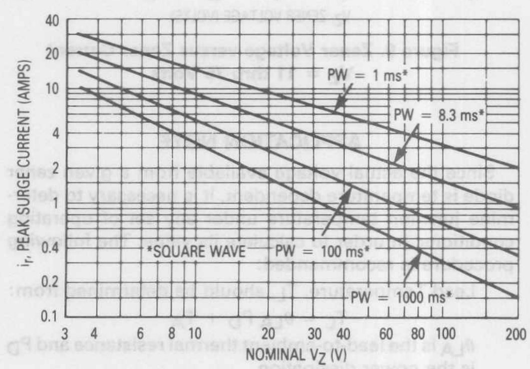


Figure 6. Maximum Non-Repetitive Surge Current versus Nominal Zener Voltage (See Note 3)

Data of Figure 4 should not be used to compute surge capability. Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 6 be exceeded.

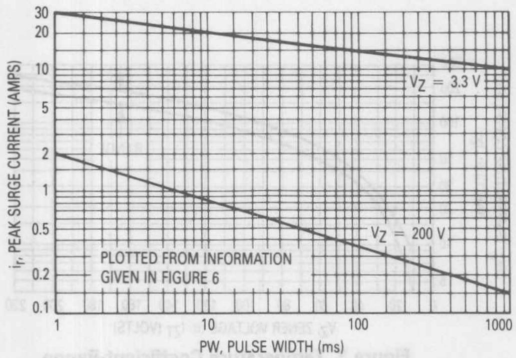


Figure 7. Peak Surge Current versus Pulse Width (See Note 3)

ZENER VOLTAGE versus ZENER CURRENT
(Figures 8, 9 and 10)

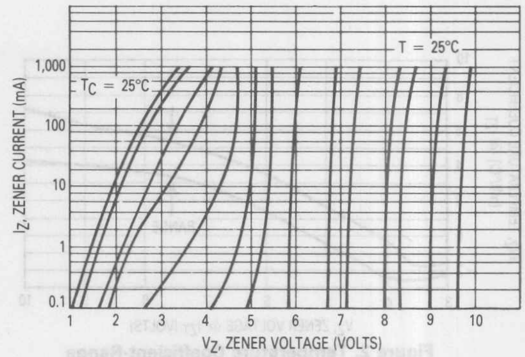


Figure 8. Zener Voltage versus Zener Current
V_Z = 3.3 thru 10 Volts

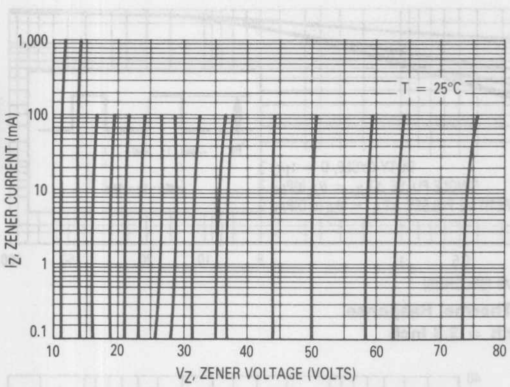


Figure 9. Zener Voltage versus Zener Current
V_Z = 11 thru 75 Volts

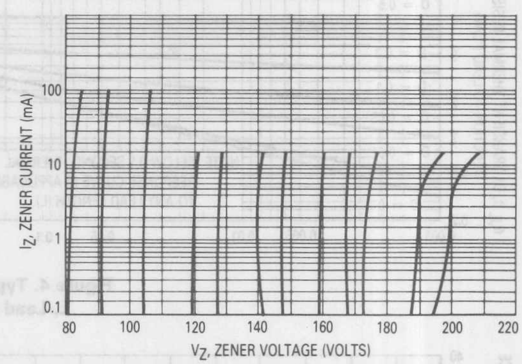


Figure 10. Zener Voltage versus Zener Current
V_Z = 82 thru 200 Volts

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions, in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance and P_D is the power dissipation.

Junction Temperature, T_J, may be found from:

$$T_J = T_L + \Delta T_{JL}$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 4 for a train of power pulses or from Figure 5 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of T_J (ΔT_J) may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

1N5518A,B thru 1N5546A,B

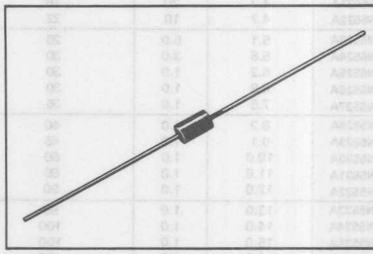
LOW VOLTAGE AVALANCHE SILICON OXIDE PASSIVATED ZENER REGULATOR DIODES

Highly reliable silicon regulators utilizing an oxide-passivated junction for long-term voltage stability. Double slug construction provides a rugged, glass-enclosed, hermetically sealed structure.

- Low Zener Noise Specified
- Low Maximum Regulation Factor
- Low Zener Impedance
- Low Leakage Current
- Controlled Forward Characteristics
- Temperature Range: -65 to +200°C

LOW VOLTAGE AVALANCHE ZENER DIODES

400 MILLIWATTS
3.3 THRU 33 VOLTS



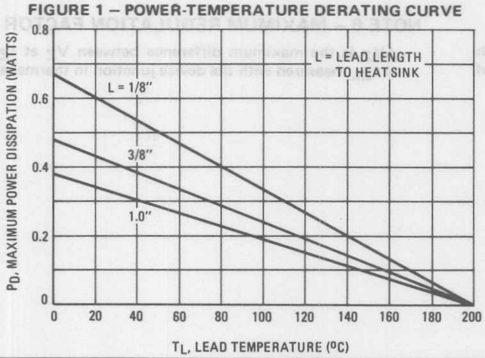
MAXIMUM RATINGS

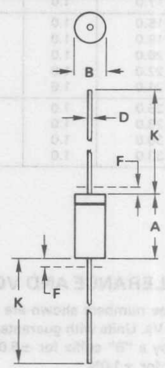
Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A = 50^oC$ Derate above 50°C	P_D	400 3.2	mW mW/°C
DC Power Dissipation @ $T_L = 50^oC$ Lead Length = 1/8" Derate above 50°C (Figure 1)	P_D	500 3.3	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

MECHANICAL CHARACTERISTICS

CASE: Hermetically sealed, all-glass
DIMENSIONS: See outline drawing.
FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable.
POLARITY: Cathode indicated by polarity band.
WEIGHT: 0.2 Gram (approx)
MOUNTING POSITION: Any

FIGURE 1 – POWER-TEMPERATURE DERATING CURVE





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

4

ELECTRICAL CHARACTERISTICS ($T_A = 25^oC$ unless otherwise noted. Based on dc measurements at thermal equilibrium; $V_F = 1.1$ Max @ $I_F = 200$ mA for all types)

JEDEC Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mAdc	Max Zener Impedance B-C-D Suffix Z_{ZT} @ I_{ZT} Ohms (Note 3)	Max Reverse Leakage Current I_R µAdc (Note 4)	V_R – Volts Non & A-Suffix	V_R – Volts B-C-D Suffix	B-C-D Suffix Maximum DC Zener Current I_{ZM} mAdc (Note 5)	B-C-D Suffix Max Noise Density at $I_Z = 250\ \mu A$ N_D (Figure 1) (micro-volts per square root cycle)	Regulation Factor ΔV_Z Volts (Note 6)	Low V_Z Current I_{ZL} mAdc
1N5518A	3.3	20	26	5.0	0.90	1.0	115	0.5	0.90	2.0
1N5519A	3.6	20	24	3.0	0.90	1.0	105	0.5	0.90	2.0
1N5520A	3.9	20	22	1.0	0.90	1.0	98	0.5	0.85	2.0
1N5521A	4.3	20	18	3.0	1.0	1.5	88	0.5	0.75	2.0
1N5522A	4.7	10	22	2.0	1.5	2.0	81	0.5	0.60	1.0
1N5523A	5.1	5.0	26	2.0	2.0	2.5	75	0.5	0.65	0.25
1N5524A	5.6	3.0	30	2.0	3.0	3.5	68	1.0	0.30	0.25
1N5525A	6.2	1.0	30	1.0	4.5	5.0	61	1.0	0.20	0.01
1N5526A	6.8	1.0	30	1.0	5.5	6.2	56	1.0	0.10	0.01
1N5527A	7.5	1.0	35	0.5	6.0	6.8	51	2.0	0.05	0.01
1N5528A	8.2	1.0	40	0.5	6.5	7.5	46	4.0	0.05	0.01
1N5529A	9.1	1.0	45	0.1	7.0	8.2	42	4.0	0.05	0.01
1N5530A	10.0	1.0	60	0.05	8.0	9.1	38	4.0	0.10	0.01
1N5531A	11.0	1.0	80	0.05	9.0	9.9	35	5.0	0.20	0.01
1N5532A	12.0	1.0	90	0.05	9.5	10.8	32	10	0.20	0.01
1N5533A	13.0	1.0	90	0.01	10.5	11.7	29	15	0.20	0.01
1N5534A	14.0	1.0	100	0.01	11.5	12.6	27	20	0.20	0.01
1N5535A	15.0	1.0	100	0.01	12.5	13.5	25	20	0.20	0.01
1N5536A	16.0	1.0	100	0.01	13.0	14.4	24	20	0.20	0.01
1N5537A	17.0	1.0	100	0.01	14.0	15.3	22	20	0.20	0.01
1N5538A	18.0	1.0	100	0.01	15.0	16.2	21	20	0.20	0.01
1N5539A	19.0	1.0	100	0.01	16.0	17.1	20	20	0.20	0.01
1N5540A	20.0	1.0	100	0.01	17.0	18.0	19	20	0.20	0.01
1N5541A	22.0	1.0	100	0.01	18.0	19.8	17	20	0.25	0.01
1N5542A	24.0	1.0	100	0.01	20.0	21.6	16	20	0.30	0.01
1N5543A	25.0	1.0	100	0.01	21.0	22.4	15	20	0.35	0.01
1N5544A	28.0	1.0	100	0.01	23.0	25.2	14	20	0.40	0.01
1N5545A	30.0	1.0	100	0.01	24.0	27.0	13	20	0.45	0.01
1N5546A	33.0	1.0	100	0.01	28.0	29.7	12	20	0.50	0.01

NOTE 1 – TOLERANCE AND VOLTAGE DESIGNATION

The JEDEC type numbers shown are ±10% with guaranteed limits for V_Z, I_R, and V_F. Units with guaranteed limits for all six parameters are indicated by a "B" suffix for ±5.0% units, "C" suffix for ±2.0% and "D" suffix for ±1.0%.

NOTE 2 – ZENER VOLTAGE (V_Z) MEASUREMENT

Nominal zener voltage is measured with the device junction in thermal equilibrium with ambient temperature of 25°C.

NOTE 3 – ZENER IMPEDANCE (Z_Z) DERIVATION

The zener impedance is derived from the 60 Hz ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT}.

NOTE 4 – REVERSE LEAKAGE CURRENT (I_R)

Reverse leakage currents are guaranteed and are measured at V_R as shown on the table.

NOTE 5 – MAXIMUM REGULATOR CURRENT (I_{ZM})

The maximum current shown is based on the maximum voltage of a 5.0% type unit, therefore, it applies only to the "B" suffix device. The actual I_{ZM} for any device may not exceed the value of 400 milliwatts divided by the actual V_Z of the device.

NOTE 6 – MAXIMUM REGULATION FACTOR (ΔV_Z)

ΔV_Z is the maximum difference between V_Z at I_{ZT} and V_Z at I_{ZL} measured with the device junction in thermal equilibrium.

ZENER NOISE DENSITY

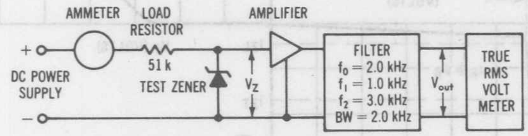
A zener diode generates noise when it is biased in the zener direction. A small part of this noise is due to the internal resistance associated with the device. A larger part of zener noise is a result of the zener breakdown phenomenon and is called microplasma noise. To eliminate the higher frequency components of noise a small shunting capacitor can be used. The lower frequency noise generally must be tolerated since a capacitor required to eliminate the lower frequencies would degrade the regulation properties of the zener in many applications.

Motorola is rating this series with a maximum noise density at 250 microamperes, a bandwidth of 2.0 kHz and a center frequency of 2.0 kHz.

Noise density decreases as zener current increases. The junction temperature will also change the zener noise levels, thus the noise rating must indicate frequency, bandwidth, current level and temperature.

The block diagram shown in Figure 2 represents the method used to measure noise density. The input voltage and load resistance is high so that the zener is driven from a constant current source. The amplifier must be low noise so that the amplifier noise is negligible compared to the test zener. The filter frequency and bandpass is known so that the noise density in volts RMS per square root cycle can be calculated.

FIGURE 2 – NOISE DENSITY MEASUREMENT METHOD



$$\text{NOISE DENSITY (VOLTS PER SQUARE ROOT BANDWIDTH)} = \frac{V_{out}}{\text{OVERALL GAIN}\sqrt{BW}}$$

WHERE: BW = FILTER BANDWIDTH (Hz)
V_{out} = OUTPUT NOISE (VOLTS RMS)

FIGURE 3 – TYPICAL CAPACITANCE

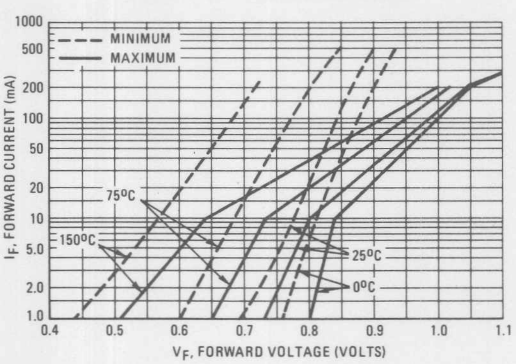


FIGURE 4 – TYPICAL FORWARD CHARACTERISTICS

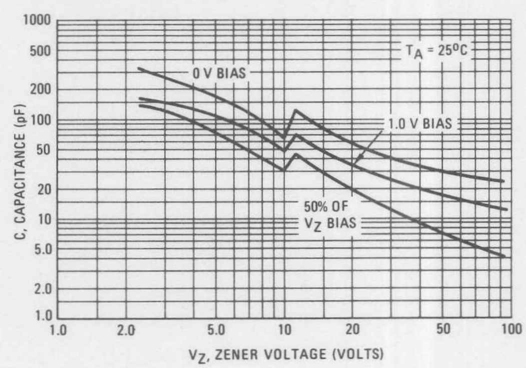
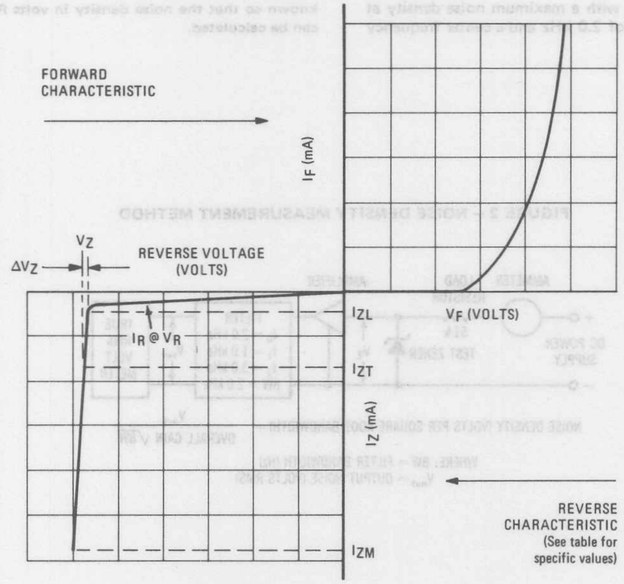


FIGURE 5 – ZENER DIODE CHARACTERISTICS AND SYMBOL IDENTIFICATION



4

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5908
1N6373/ICTE-5, C
MPTE-5, C
thru
1N6389/ICTE-45, C
MPTE-45, C
1N6267, A/1.5KE6.8, A
thru
1N6303, A/1.5KE200, A

ZENER OVERVOLTAGE TRANSIENT SUPPRESSOR

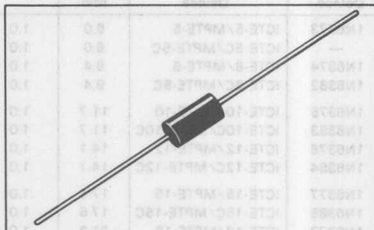
Mosorb devices are designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. These devices are Motorola's exclusive, cost-effective, highly reliable Surmetic axial leaded package and are ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications, to protect CMOS, MOS and Bipolar integrated circuits.

SPECIFICATION FEATURES

- Standard Voltage Range — 5.0 to 200 V
- Peak Power — 1500 Watts @ 1.0 ms
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA above 10 V
- Standard Back to Back Versions Available

MOSORBS
ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS

5.0-200 VOLT
1500 WATT PEAK POWER
5.0 WATTS STEADY STATE



4

MAXIMUM RATINGS

Rating	Symbol	Value	Units
Peak Power Dissipation (1) @ $T_L \leq 25°C$	P_{PK}	1500	Watts
Steady State Power Dissipation @ $T_L \leq 75°C$, Lead Length = 3/8″ Derated above $T_L = 75°C$	P_D	5.0 50	Watts mW/°C
Forward Surge Current (2) @ $T_A = 25°C$	I_{FSM}	200	Amps
Operating and Storage Temperature Range	T_J, T_{stg}	-65 to +175	°C

Lead Temperature not less than 1/16″ from the case for 10 seconds: 230°C

MECHANICAL CHARACTERISTICS

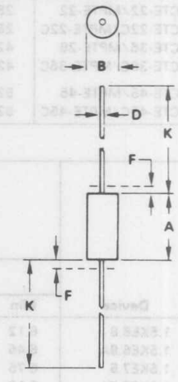
CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable

POLARITY: Cathode indicated by polarity band. When operated in zener mode, will be positive with respect to anode

MOUNTING POSITION: Any

NOTES: 1. Nonrepetitive Current Pulse per Figure 4 and Derated above $T_A = 25°C$ per Figure 2.
2. 1/2 Square Wave (or equivalent), PW = 8.3 ms, Duty Cycle = 4 Pulses per minute maximum.



NOTE:
1. LEAD FINISH AND DIA UNCONTROLLED IN AREA "F".

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	9.14	9.52	0.360	0.375
B	4.83	5.21	0.190	0.205
D	0.97	1.07	0.038	0.042
F	–	1.27	–	0.050
K	27.94	–	1.100	–

CASE 41-11
GLASS

***ELECTRICAL CHARACTERISTICS** (T_A = 25°C unless otherwise noted) V_F# = 3.5 V max, I_F** = 100 A

Device	Breakdown Voltage V_{BR} (Volts) Min	Breakdown Voltage @ I_T (mA)	Maximum Reverse Stand-Off Voltage V_{RWM}*** (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Voltage @ I_{RSM}† = 120 A (Clamping Voltage) V_{RSM} (Volts)	Clamping Voltage: Peak Pulse Current @ I_{pp1}† = 30 A V_{C1} (Volts max)	Clamping Voltage: Peak Pulse Current @ I_{pp2}† = 60 A V_{C2} (Volts max)
1N5908	6.0	1.0	5.0	300	8.5	7.6	8.0

ELECTRICAL CHARACTERISTIC (T_A = 25°C unless otherwise noted) V_F# = 3.5 V max, I_F** = 100 A) (C suffix denotes standard back to back versions. Test both polarities)

JEDEC Device	Device	Breakdown Voltage V_{BR} Volts Min	Breakdown Voltage @ I_T (mA)	Maximum Reverse Stand-Off Voltage V_{RWM}*** (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM}† (Clamping Voltage) V_{RSM}(Volts)	Clamping Voltage: Peak Pulse Current @ I_{pp1}† = 1.0 A V_{C1} (Volts max)	Clamping Voltage: Peak Pulse Current @ I_{pp2}† = 10 A V_{C2} (Volts max)
1N6373	ICTE-5/MPTE-5	6.0	1.0	5.0	300	160	9.4	7.1	7.5
—	ICTE-5C/MPTE-5C	6.0	1.0	5.0	300	160	9.4	8.1	8.3
1N6374	ICTE-8/MPTE-8	9.4	1.0	8.0	25	100	15.0	11.3	11.5
1N6382	ICTE-8C/MPTE-8C	9.4	1.0	8.0	25	100	15.0	11.4	11.6
1N6375	ICTE-10/MPTE-10	11.7	1.0	10	2.0	90	16.7	13.7	14.1
1N6383	ICTE-10C/MPTE-10C	11.7	1.0	10	2.0	90	16.7	14.1	14.5
1N6376	ICTE-12/MPTE-12	14.1	1.0	12	2.0	70	21.2	16.1	16.5
1N6384	ICTE-12C/MPTE-12C	14.1	1.0	12	2.0	70	21.2	16.7	17.1
1N6377	ICTE-15/MPTE-15	17.6	1.0	15	2.0	60	25.0	20.1	20.6
1N6385	ICTE-15C/MPTE-15C	17.6	1.0	15	2.0	60	25.0	20.8	21.4
1N6378	ICTE-18/MPTE-18	21.2	1.0	18	2.0	50	30.0	24.2	25.2
1N6386	ICTE-18C/MPTE-18C	21.2	1.0	18	2.0	50	30.0	24.8	25.5
1N6379	ICTE-22/MPTE-22	25.9	1.0	22	2.0	40	37.5	29.8	32.0
1N6387	ICTE-22C/MPTE-22C	25.9	1.0	22	2.0	40	37.5	30.8	32.0
1N6380	ICTE-36/MPTE-26	42.4	1.0	36	2.0	23	65.2	50.6	54.3
1N6388	ICTE-36C/MPTE-36C	42.4	1.0	36	2.0	23	65.2	50.6	54.3
1N6381	ICTE-45/MPTE-45	52.9	1.0	45	2.0	19	78.9	63.3	70.0
1N6389	ICTE-45C/MPTE-45C	52.9	1.0	45	2.0	19	78.9	63.3	70.0

JEDEC Device	Device	Breakdown Voltage V_{BR} Volts Min	Breakdown Voltage V_{BR} Volts Nom	Breakdown Voltage V_{BR} Volts Max	@ I_T (mA)	Working Peak Reverse Voltage V_{RWM} (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM} (Clamping Voltage) V_{RSM} (Volts)	Maximum Temperature Coefficient of V_{BR} (%/°C)
1N6267	1.5KE6.8	6.12	6.8	7.48	10	5.50	1000	139	10.8	0.057
1N6267A	1.5KE6.8A	6.45	6.8	7.14	10	5.80	1000	143	10.5	0.057
1N6268	1.5KE7.5	6.75	7.5	8.25	10	6.05	500	128	11.7	0.061
1N6268A	1.5KE7.5A	7.13	7.5	7.88	10	6.40	500	132	11.3	0.061
1N6269	1.5KE8.2	7.38	8.2	9.02	10	6.63	200	120	12.5	0.065
1N6269A	1.5KE8.2A	7.79	8.2	8.61	10	7.02	200	124	12.1	0.065
1N6270	1.5KE9.1	8.19	9.1	10.0	1.0	7.37	50	109	13.8	0.068
1N6270A	1.5KE9.1A	8.65	9.1	9.55	1.0	7.78	50	112	13.4	0.068
1N6271	1.5KE10	9.00	10	11	1.0	8.10	10	100	15.0	0.073
1N6271A	1.5KE10A	9.50	10	10.5	1.0	8.55	10	103	14.5	0.073
1N6272	1.5KE11	9.90	11	12.1	1.0	8.92	5.0	93.0	16.2	0.075
1N6272A	1.5KE11A	10.5	11	11.6	1.0	9.40	5.0	96.0	15.6	0.075

***ELECTRICAL CHARACTERISTICS** (Continued)

JEDEC Device	Device	Breakdown Voltage V_{BR} Volts Min	Nom	Max	@ I_T (mA)	Working Peak Reverse Voltage V_{RWM} (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM} (Clampling Voltage) V_{RSM} (Volts)	Maximum Temperature Coefficient of V_{BR} (%/°C)
1N6273	1.5KE12	10.8	12	13.2	1.0	9.72	5.0	87.0	17.3	0.078
1N6273A	1.5KE12A	11.4	12	12.6	1.0	10.2	5.0	90.0	16.7	0.078
1N6274	1.5KE13	11.7	13	14.3	1.0	10.5	5.0	79.0	19.0	0.081
1N6274A	1.5KE13A	12.4	13	13.7	1.0	11.1	5.0	82.0	18.2	0.081
1N6275	1.5KE15	13.5	15	16.5	1.0	12.1	5.0	68.0	22.0	0.084
1N6275A	1.5KE15A	14.3	15	15.8	1.0	12.8	5.0	71.0	21.2	0.084
1N6276	1.5KE16	14.4	16	17.6	1.0	12.9	5.0	64.0	23.5	0.086
1N6276A	1.5KE16A	15.2	16	16.8	1.0	13.6	5.0	67.0	22.5	0.086
1N6277	1.5KE18	16.2	18	19.8	1.0	14.5	5.0	56.5	26.5	0.088
1N6277A	1.5KE18A	17.1	18	18.9	1.0	15.3	5.0	59.5	25.2	0.088
1N6278	1.5KE20	18.0	20	22.0	1.0	16.2	5.0	51.5	29.1	0.090
1N6278A	1.5KE20A	19.0	20	21.0	1.0	17.1	5.0	54.0	27.7	0.090
1N6279	1.5KE22	19.8	22	24.2	1.0	17.8	5.0	47.0	31.9	0.092
1N6279A	1.5KE22A	20.9	22	23.1	1.0	18.8	5.0	49.0	30.6	0.092
1N6280	1.5KE24	21.6	24	26.4	1.0	19.4	5.0	43.0	34.7	0.094
1N6280A	1.5KE24A	22.8	24	25.2	1.0	20.5	5.0	45.0	33.2	0.094
1N6281	1.5KE27	24.3	27	29.7	1.0	21.8	5.0	38.5	39.1	0.096
1N6281A	1.5KE27A	25.7	27	28.4	1.0	23.1	5.0	40.0	37.5	0.096
1N6282	1.5KE30	27.0	30	33.0	1.0	24.3	5.0	34.5	43.5	0.097
1N6282A	1.5KE30A	28.5	30	31.5	1.0	25.6	5.0	36.0	41.4	0.097
1N6283	1.5KE33	29.7	33	36.3	1.0	26.8	5.0	31.5	47.7	0.098
1N6283A	1.5KE33A	31.4	33	34.7	1.0	28.2	5.0	33.0	45.7	0.098
1N6284	1.5KE36	32.4	36	39.6	1.0	29.1	5.0	29.0	52.0	0.099
1N6284A	1.5KE36A	34.2	36	37.8	1.0	30.8	5.0	30.0	49.9	0.099
1N6285	1.5KE39	35.1	39	42.9	1.0	31.6	5.0	26.5	56.4	0.100
1N6285A	1.5KE39A	37.1	39	41.0	1.0	33.3	5.0	28.0	53.9	0.100
1N6286	1.5KE43	38.7	43	47.3	1.0	34.8	5.0	24.0	61.9	0.101
1N6286A	1.5KE43A	40.9	43	45.2	1.0	36.8	5.0	25.3	59.3	0.101
1N6287	1.5KE47	42.3	47	51.7	1.0	38.1	5.0	22.2	67.8	0.101
1N6287A	1.5KE47A	44.7	47	49.4	1.0	40.2	5.0	23.2	64.8	0.101
1N6288	1.5KE51	45.9	51	56.1	1.0	41.3	5.0	20.4	73.5	0.102
1N6288A	1.5KE51A	48.5	51	53.6	1.0	43.6	5.0	21.4	70.1	0.102
1N6289	1.5KE56	50.4	56	61.6	1.0	45.4	5.0	18.6	80.5	0.103
1N6289A	1.5KE56	53.2	56	58.8	1.0	47.8	5.0	19.5	77.0	0.103
1N6290	1.5KE62	55.8	62	68.2	1.0	50.2	5.0	16.9	89.0	0.104
1N6290A	1.5KE62A	58.9	62	65.1	1.0	53.0	5.0	17.7	85.0	0.104
1N6291	1.5KE68	61.2	68	74.8	1.0	55.1	5.0	15.3	98.0	0.104
1N6291A	1.5KE68A	64.6	68	71.4	1.0	58.1	5.0	16.3	92.0	0.104
1N6292	1.5KE75	67.5	75	82.5	1.0	60.7	5.0	13.9	108.0	0.105
1N6292A	1.5KE75A	71.3	75	78.8	1.0	64.1	5.0	14.6	103.0	0.105
1N6293	1.5KE82	73.8	82	90.2	1.0	66.4	5.0	12.7	118.0	0.105
1N6293A	1.5KE82A	77.9	82	86.1	1.0	70.1	5.0	13.3	113.0	0.105
1N6294	1.5KE91	81.9	91	100.0	1.0	73.7	5.0	11.4	131.0	0.106
1N6294A	1.5KE91A	86.5	91	95.50	1.0	77.8	5.0	12.0	125.0	0.106
1N6295	1.5KE100	90.0	100	110.0	1.0	81.0	5.0	10.4	144.0	0.106
1N6295A	1.5KE100A	95.0	100	105.0	1.0	85.5	5.0	11.0	137.0	0.106
1N6296	1.5KE110	99.0	110	121.0	1.0	89.2	5.0	9.5	158.0	0.107
1N6296A	1.5KE110A	105.0	110	116.0	1.0	94.0	5.0	9.9	152.0	0.107
1N6297	1.5KE120	108.0	120	132.0	1.0	97.2	5.0	8.7	173.0	0.107
1N6297A	1.5KE120A	114.0	120	126.0	1.0	102.0	5.0	9.1	165.0	0.107
1N6298	1.5KE130	117.0	130	143.0	1.0	105.0	5.0	8.0	187.0	0.107
1N6298A	1.5KE130A	124.0	130	137.0	1.0	111.0	5.0	8.4	179.0	0.107
1N6299	1.5KE150	135.0	150	165.0	1.0	121.0	5.0	7.0	215.0	0.108
1N6299A	1.5KE150A	143.0	150	158.0	1.0	128.0	5.0	7.2	207.0	0.108
1N6300	1.5KE160	144.0	160	176.0	1.0	130.0	5.0	6.5	230.0	0.108
1N6300A	1.5KE160A	152.0	160	168.0	1.0	136.0	5.0	6.8	219.0	0.108

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*ELECTRICAL CHARACTERISTICS (Continued)

JEDEC Device	Device	Breakdown Voltage V_{BR} Volts Min	Nom	Max	@ I_T (mA)	Working Peak Reverse Voltage V_{RWM} (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM} (Clampling Voltage) V_{RSM} (Volts)	Maximum Temperature Coefficient of V_{BR} (%/°C)
1N6301	1.5KE170	153.0	170	187.0	1.0	138.0	5.0	6.2	244.0	0.108
1N6301A	1.5KE170A	162.0	170	179.0	1.0	145.0	5.0	6.4	234.0	0.108
1N6302	1.5KE180	162.0	180	198.0	1.0	146.0	5.0	5.8	258.0	0.108
1N6302A	1.5KE180A	171.0	180	189.0	1.0	154.0	5.0	6.1	246.0	0.108
1N6303	1.5KE200	180.0	200	220.0	1.0	162.0	5.0	5.2	287.0	0.108
1N6303A	1.5KE200A	190.0	200	210.0	1.0	171.0	5.0	5.5	274.0	0.108

†Surge Current Waveform per Figure 4 and Derate per Figure 2.
*Indicates JEDEC Registered Data.
**1/2 Square Equivalent Sine Wave, PW = 8.3 ms, Duty Cycle = 4 Pulses per Minute maximum.
***A Transient Suppressor is normally selected according to the maximum reverse stand-off voltage (V_{RWM}), which should be equal to or greater than the dc or continuous peak operating voltage level.
#V_F applies to Non-C suffix devices only.
C suffix denotes standard back-to-back versions. Test both polarities.

To order clipper-bidirectional device in 1N6267 series, add a "C" suffix to 1.5KE device title, i.e., 1.5KE7.5C or 1.5KE7.5CA.

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FIGURE 1 — PULSE RATING CURVE

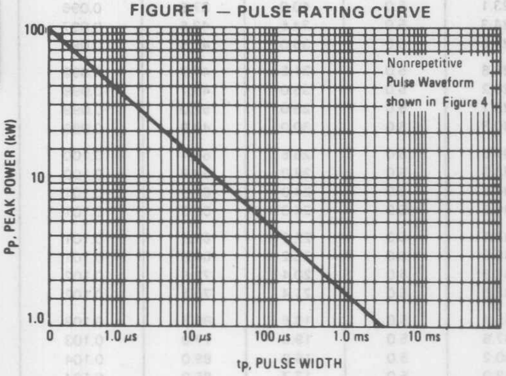


FIGURE 2 — PULSE DERATING CURVE

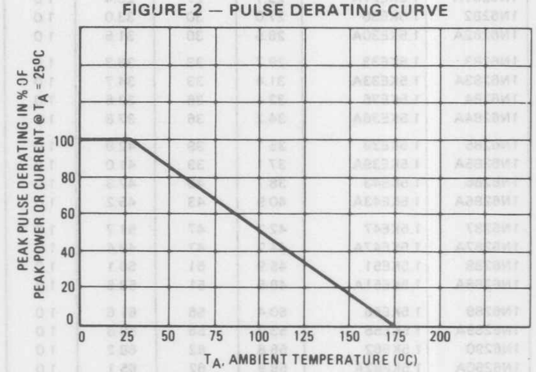
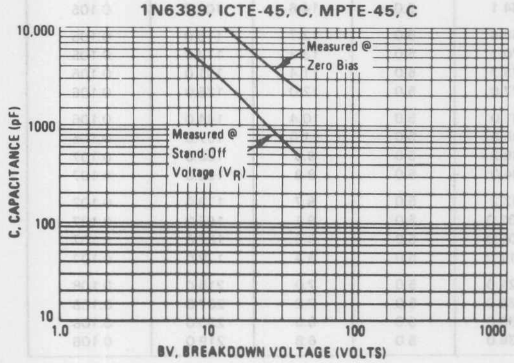


FIGURE 3 — CAPACITANCE versus BREAKDOWN VOLTAGE

1N6373, ICTE-5, C, MPTE-5, C
thru
1N6389, ICTE-45, C, MPTE-45, C



1N6267, A/1.5KE6.8, A
thru
1N6303, A/1.5KE200, A

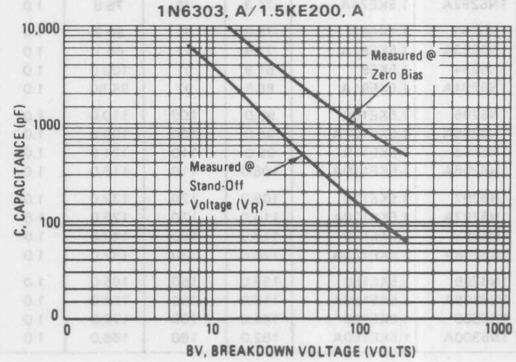


FIGURE 4 — STEADY STATE POWER DERATING

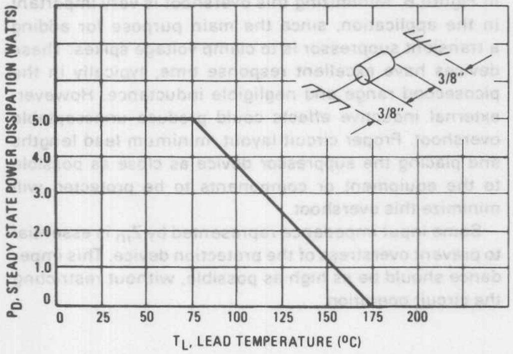


FIGURE 5 — PULSE WAVEFORM

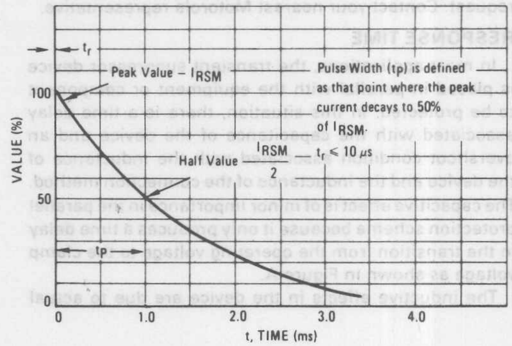
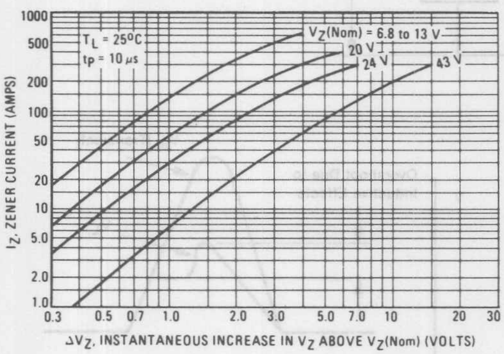
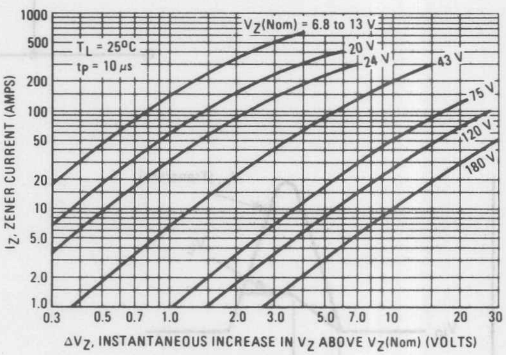


FIGURE 6 — DYNAMIC IMPEDANCE

1N6373, ICTE-5, C, MPTE-5, C
thru
1N6389, ICTE-45, C, MPTE-45, C



1N6267, A/1.5KE6.8, A
thru
1N6303, A/1.5KE200, A



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APPLICATION NOTES

SPECIAL DEVICES

Matched sets and back-to-back configurations for bidirectional applications can be ordered upon special request. Contact your nearest Motorola representative.

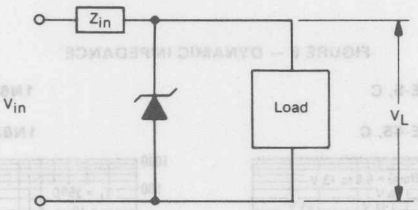
RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure A.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure B. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. These devices have excellent response time, typically in the picosecond range and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

TYPICAL PROTECTION CIRCUIT



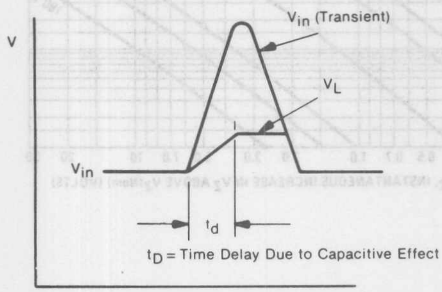


FIGURE A

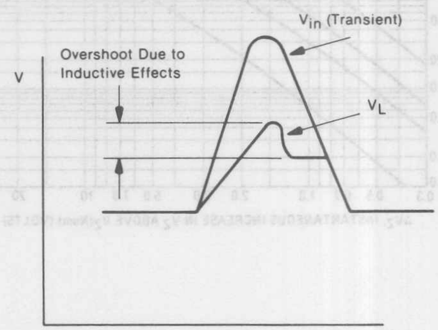


FIGURE B

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N5913A thru 1N5956A

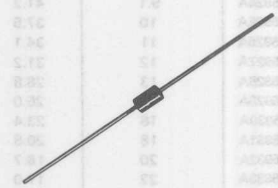
1.5 WATT SURMETIC 30 SILICON ZENER DIODES

. . . A complete line of 1.5-Watt Zener Diodes offering the following advantages:

- Complete Voltage Range – 3.3 to 200 Volts
- DO-41 Package – Smaller than Conventional Metal Devices
- Metallurgically Bonded Construction
- JEDEC Registered Parameters
- Oxide Passivated Diode

1.5 WATTS ZENER DIODES

3.3 – 200 VOLTS



*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_L = 75°C, Lead Length = 3/8'' Derate above 75°C	P_D	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +200	°C

*Indicates JEDEC Registered Data.

MECHANICAL CHARACTERISTICS

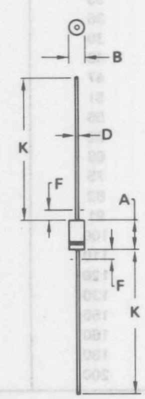
CASE: Surmetic 30 void-free, transfer-molded, thermosetting-plastic

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, 1/16" from case for 10 seconds

FINISH: All external surfaces are corrosion resistant with readily solderable leads

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.

MOUNTING POSITION: Any



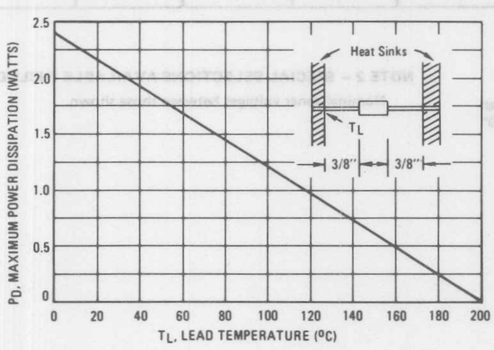
DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	–	1.27	–	0.050
K	27.94	–	1.100	–

All JEDEC dimensions and notes apply.

CASE 59-03
DO-41
GLASS

NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

FIGURE 1 – STEADY STATE POWER DERATING



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***ELECTRICAL CHARACTERISTICS** (T_L = 30°C unless otherwise noted. V_F = 1.5 Volts Max @ I_F = 200 mAdc for all types.)

Motorola Type Number (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max. Zener Impedance Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} Ohms	@ I_{ZK} mA	Max. Reverse Leakage Current I_R μA	@ V_R Volts	Maximum DC Zener Current I_{ZM} mAdc
1N5913A	3.3	113.6	10	500	1.0	100	1.0	454
1N5914A	3.6	104.2	9.0	500	1.0	75	1.0	416
1N5915A	3.9	96.1	7.5	500	1.0	25	1.0	384
1N5916A	4.3	87.2	6.0	500	1.0	5.0	1.0	348
1N5917A	4.7	79.8	5.0	500	1.0	5.0	1.5	319
1N5918A	5.1	73.5	4.0	350	1.0	5.0	2.0	294
1N5919A	5.6	66.9	2.0	250	1.0	5.0	3.0	267
1N5920A	6.2	60.5	2.0	200	1.0	5.0	4.0	241
1N5921A	6.8	55.1	2.5	200	1.0	5.0	5.2	220
1N5922A	7.5	50.0	3.0	400	0.5	5.0	6.8	200
1N5923A	8.2	45.7	3.5	400	0.5	5.0	6.5	182
1N5924A	9.1	41.2	4.0	500	0.5	5.0	7.0	164
1N5925A	10	37.5	4.5	500	0.25	5.0	8.0	150
1N5926A	11	34.1	5.5	550	0.25	1.0	8.4	136
1N5927A	12	31.2	6.5	550	0.25	1.0	9.1	125
1N5928A	13	28.8	7.0	550	0.25	1.0	9.9	115
1N5929A	15	25.0	9.0	600	0.25	1.0	11.4	100
1N5930A	16	23.4	10	600	0.25	1.0	12.2	93
1N5931A	18	20.8	12	650	0.25	1.0	13.7	83
1N5932A	20	18.7	14	650	0.25	1.0	15.2	75
1N5933A	22	17.0	17.5	650	0.25	1.0	16.7	68
1N5934A	24	15.6	19	700	0.25	1.8	18.2	62
1N5935A	27	13.9	23	700	0.25	1.0	20.6	55
1N5936A	30	12.5	26	750	0.25	1.0	22.8	50
1N5937A	33	11.4	33	800	0.25	1.0	25.1	45
1N5938A	36	10.4	38	850	0.25	1.0	27.4	41
1N5939A	39	9.6	45	900	0.25	1.0	29.7	38
1N5940A	43	8.7	53	950	0.25	1.0	32.7	34
1N5941A	47	8.0	67	1000	0.25	1.0	35.8	31
1N5942A	51	7.3	70	1100	0.25	1.0	38.8	29
1N5943A	56	6.7	86	1300	0.25	1.0	42.6	26
1N5944A	62	6.0	100	1500	0.25	1.0	47.1	24
1N5945A	68	5.5	120	1700	0.25	1.0	51.7	22
1N5946A	75	5.0	140	2000	0.25	1.0	56.0	20
1N5947A	82	4.6	160	2500	0.25	1.0	62.2	18
1N5948A	91	4.1	200	3000	0.25	1.0	69.2	16
1N5949A	100	3.7	250	3100	0.25	1.0	76.0	15
1N5950A	110	3.4	300	4000	0.25	1.0	83.6	13
1N5951A	120	3.1	380	4500	0.25	1.0	91.2	12
1N5952A	130	2.9	450	5000	0.25	1.0	98.8	11
1N5953A	150	2.5	600	6000	0.25	1.0	114	10
1N5954A	160	2.3	700	6500	0.25	1.0	121.6	9.0
1N5955A	180	2.1	900	7000	0.25	1.0	136.8	8.0
1N5956A	200	1.9	1200	8000	0.25	1.0	152	7.0

*Indicates JEDEC Registered Data.

NOTE 1 – TOLERANCE AND VOLTAGE DESIGNATION

Tolerance designation — Device tolerances of ±10% are indicated by an "A" suffix, ±5% by a "B" suffix, ±2% by a "C" suffix, ±1% by a "D" suffix.

NOTE 2 – SPECIAL SELECTIONS AVAILABLE INCLUDE:

Nominal zener voltages between those shown.

TYPICAL CHARACTERISTICS

TEMPERATURE COEFFICIENTS (-55°C to +150°C temperature range)

FIGURE 2 – ZENER VOLTAGE – TO 12 VOLTS

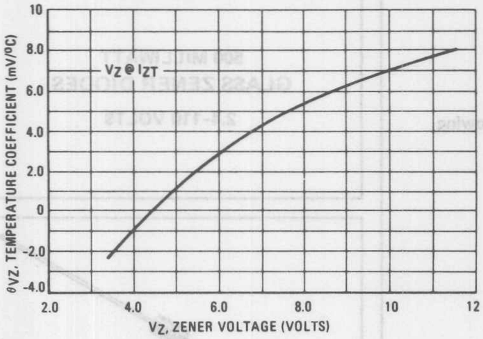
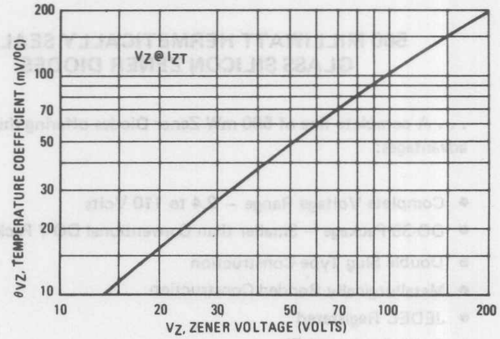


FIGURE 3 – ZENER VOLTAGE – 14 TO 200 VOLTS



ZENER IMPEDANCE

FIGURE 4 – EFFECT OF ZENER CURRENT

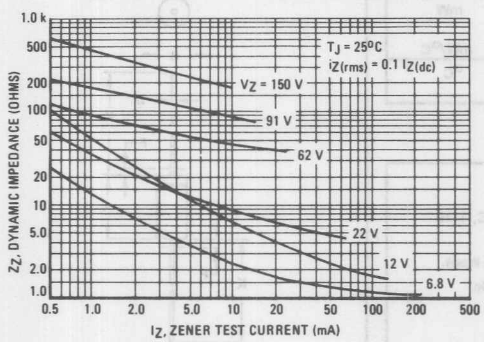
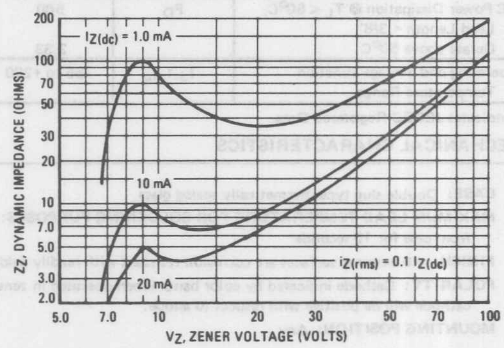


FIGURE 5 – EFFECT OF ZENER VOLTAGE



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

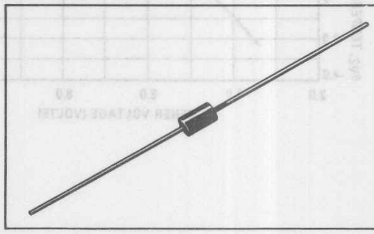
1N5985A thru 1N6025A

500 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

. . . A complete line of 500 mW Zener Diodes offering the following advantages:

- Complete Voltage Range — 2.4 to 110 Volts
- DO-35 Package — Smaller than Conventional DO-7 Package
- Double Slug Type Construction
- Metallurgically Bonded Construction
- JEDEC Registered
- Oxide Passivated Die

500 MILLIWATT GLASS ZENER DIODES
2.4–110 VOLTS



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*MAXIMUM RATINGS

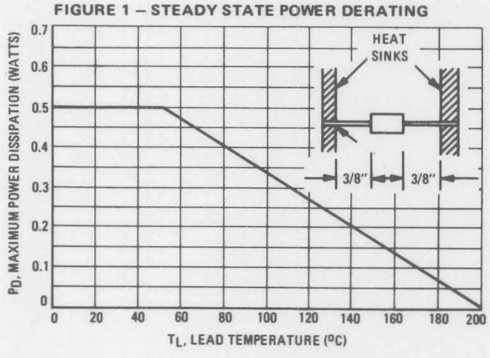
Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_L \leq 50^oC$, Lead Length = 3/8"	P_D	500	mW
Derate above 50^oC		3.33	$mW/^oC$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +200	^oC

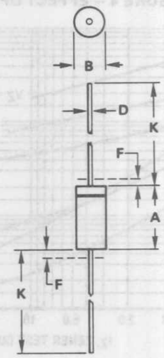
*Indicates JEDEC Registered Data.

MECHANICAL CHARACTERISTICS

CASE: Double slug type, hermetically sealed glass
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230^oC, 1/16" from case for 10 seconds
FINISH: All external surfaces are corrosion resistant with readily solderable leads.
POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode.
MOUNTING POSITION: Any

FIGURE 1 — STEADY STATE POWER DERATING





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN A AND B. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT NOT SUBJECT TO THE MINIMUM LIMIT OF B.
2. LEAD DIAMETER NOT CONTROLLED IN ZONE F TO ALLOW FOR FLASH, LEAD FINISH BUILDUP AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.
3. POLARITY DENOTED BY CATHODE BAND.
4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5, 1973.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	3.05	5.08	0.120	0.200
B	1.52	2.29	0.060	0.090
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply.

CASE 299-02
DO-204AH
GLASS

***ELECTRICAL CHARACTERISTICS** (T_L = 30°C unless otherwise noted.) (V_F = 1.5 Volts Max @ I_F = 100 mAdc for all types.)

Motorola Type Number (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max. Zener Impedance (Note 4) Z_{ZT} @ I_{ZT} Ohms B Suffix	Z_{ZT} @ I_{ZT} Ohms A, Non-Suffix	Z_{ZK} @ I_{ZK} = 0.25 mA Ohms B Suffix	Z_{ZK} @ I_{ZK} = 0.25 mA Ohms A, Non-Suffix	Max. Reverse Leakage Current I_R μA B Suffix	I_R μA A, Non-Suffix	@ V_R volts B Suffix	@ V_R volts A, Non-Suffix	Max. DC Zener Current I_{ZM} (Note 3)
1N5985A	2.4	5.0	100	110	1800	2000	100	100	1.0	0.5	208
1N5986A	2.7	5.0	100	110	1900	2200	75	100	1.0	0.5	185
1N5987A	3.0	5.0	95	100	2000	2300	50	100	1.0	0.5	167
1N5988A	3.3	5.0	95	100	2200	2400	25	75	1.0	0.5	152
1N5989A	3.6	5.0	90	95	2300	2500	15	50	1.0	0.5	139
1N5990A	3.9	5.0	90	95	2400	2500	10	25	1.0	1.0	128
1N5991A	4.3	5.0	88	90	2500	2500	5.0	15	1.0	1.0	116
1N5992A	4.7	5.0	70	90	2200	2500	3.0	10	1.5	1.0	106
1N5993A	5.1	5.0	50	88	2050	2500	2.0	5.0	2.0	1.0	98
1N5994A	5.6	5.0	25	70	1800	2200	2.0	3.0	3.0	1.5	89
1N5995A	6.2	5.0	10	50	1300	2050	1.0	2.0	4.0	2.0	81
1N5996A	6.8	5.0	8.0	25	750	1800	1.0	2.0	5.2	3.0	74
1N5997A	7.5	5.0	7.0	10	600	1300	0.5	1.0	6.0	4.0	67
1N5998A	8.2	5.0	7.0	15	600	750	0.5	1.0	6.5	5.2	61
1N5999A	9.1	5.0	10	18	600	600	0.1	0.5	7.0	6.0	55
1N6000A	10	5.0	15	22	600	600	0.1	0.5	8.0	6.5	50
1N6001A	11	5.0	18	25	600	600	0.1	0.1	8.4	7.0	45
1N6002A	12	5.0	22	32	600	600	0.1	0.1	9.1	8.0	42
1N6003A	13	5.0	25	36	600	600	0.1	0.1	9.9	8.4	38
1N6004A	15	5.0	32	42	600	600	0.1	0.1	11	9.1	33
1N6005A	16	5.0	36	48	600	600	0.1	0.1	12	9.9	31
1N6006A	18	5.0	42	55	600	600	0.1	0.1	14	11	28
1N6007A	20	5.0	48	62	600	600	0.1	0.1	15	12	25
1N6008A	22	5.0	55	70	600	600	0.1	0.1	17	14	23
1N6009A	24	5.0	62	78	600	600	0.1	0.1	18	15	21
1N6010A	27	5.0	70	88	600	700	0.1	0.1	21	17	19
1N6011A	30	5.0	78	95	600	700	0.1	0.1	23	18	17
1N6012A	33	5.0	88	110	700	800	0.1	0.1	25	21	15
1N6013A	36	5.0	95	130	700	900	0.1	0.1	27	23	14
1N6014A	39	2.0	130	170	800	1000	0.1	0.1	30	25	13
1N6015A	43	2.0	150	180	900	1100	0.1	0.1	33	27	12
1N6016A	47	2.0	170	200	1000	1300	0.1	0.1	36	30	11
1N6017A	51	2.0	180	225	1300	1400	0.1	0.1	39	33	9.8
1N6018A	56	2.0	200	240	1400	1600	0.1	0.1	43	36	8.9
1N6019A	62	2.0	225	265	1400	1700	0.1	0.1	47	39	8.0
1N6020A	68	2.0	240	280	1600	2000	0.1	0.1	52	43	7.4
1N6021A	75	2.0	265	300	1700	2300	0.1	0.1	56	47	6.7
1N6022A	82	2.0	280	350	2000	2600	0.1	0.1	62	52	6.1
1N6023A	91	2.0	300	400	2300	3000	0.1	0.1	69	56	5.5
1N6024A	100	1.0	500	800	2600	4000	0.1	0.1	76	62	5.0
1N6025A	110	1.0	650	950	3000	4500	0.1	0.1	84	69	4.5

*Indicates JEDEC Registered Data.

NOTE 1 – TOLERANCE AND VOLTAGE DESIGNATION

Tolerance designation – Device tolerances of ±10% are indicated by an "A" suffix, ±5% by a "B" suffix, ±2% by a "C" suffix, ±1% by a "D" suffix.

NOTE 2 – SPECIAL SELECTIONS AVAILABLE INCLUDE:

(a) Nominal Zener voltages between those shown.

(b) Matched sets: (Standard Tolerances are ±5.0%, ±2.0%, ±1.0%)

a. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability

b. Two or more units matched to one another with any specified tolerance.

NOTE 3:

This data was calculated using nominal voltages. In order to determine the maximum current handling capability on a worst case basis the following formula must be used:

$$I_{zm}(\text{worst case}) = \frac{500\text{ mW}}{V_z(\text{nom}) + \text{tolerance}}$$

NOTE 4:

Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac) = 0.1\ I_Z(dc)$ with the ac frequency = 1.0 kHz.

4

TYPICAL CHARACTERISTICS

TEMPERATURE COEFFICIENTS (-55°C to +150°C temperature range)

FIGURE 2A – ZENER VOLTAGE 2.4 to 12 VOLTS

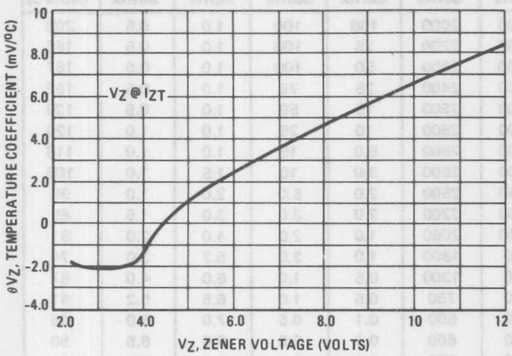


FIGURE 2B – ZENER VOLTAGE 12 to 200 VOLTS

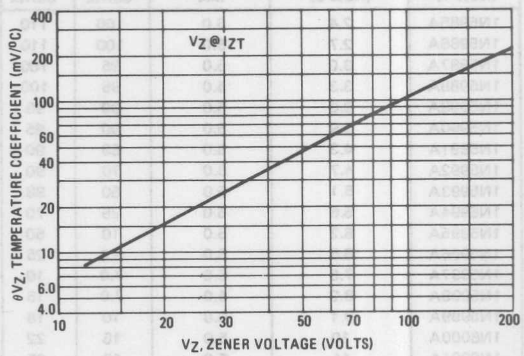


FIGURE 3 – EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

FIGURE 3A

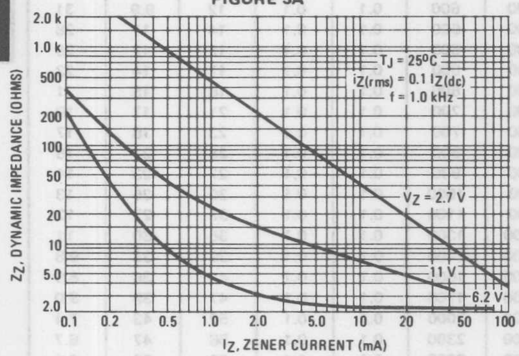


FIGURE 3B

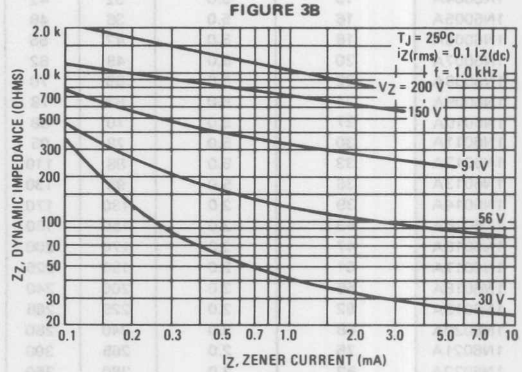
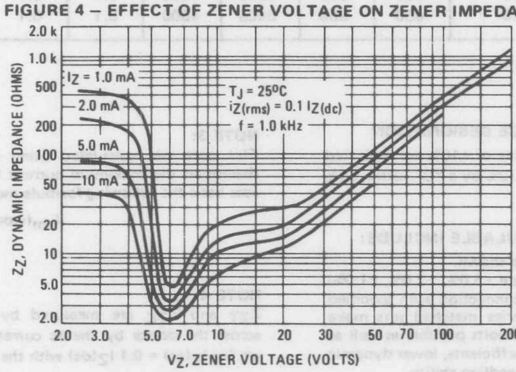


FIGURE 4 – EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

3EZ3.9D5 thru 3EZ200D5

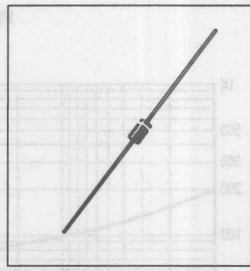
Designer's Data Sheet

3-Watt Surmetic 30 Silicon Zener Diodes

. . . a complete series of 3 Watt Zener Diodes with limits and operating characteristics that reflect the superior capabilities of silicon-oxide-passivated junctions. All this in an axial-lead, transfer-molded plastic package offering protection in all common environmental conditions.

- Surge Rating of 98 Watts @ 1 ms
- Maximum Limits Guaranteed on Six Electrical Parameters
- Package No Larger Than the Conventional 1 W Package

3-WATT ZENER REGULATOR DIODES 3.9–200 VOLTS



Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable

POLARITY: Cathode indicated by polarity band. When operated in zener mode, cathode will be positive with respect to anode

MOUNTING POSITION: Any

WEIGHT: 0.4 gram (approx)

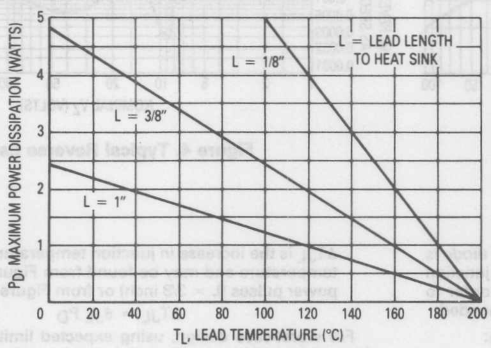
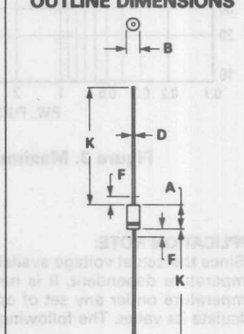


Figure 1. Power-Temperature Derating Curve

OUTLINE DIMENSIONS



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	—	1.27	—	0.050
K	27.94	—	1.100	—

CASE 59-03 (DO-41)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_L = 75°C Lead Length = 3/8" Derate above 75°C	P_D	3 24	Watts mW/°C
DC Power Dissipation @ T_A = 50°C Derate above 50°C	P_D	1 6.67	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

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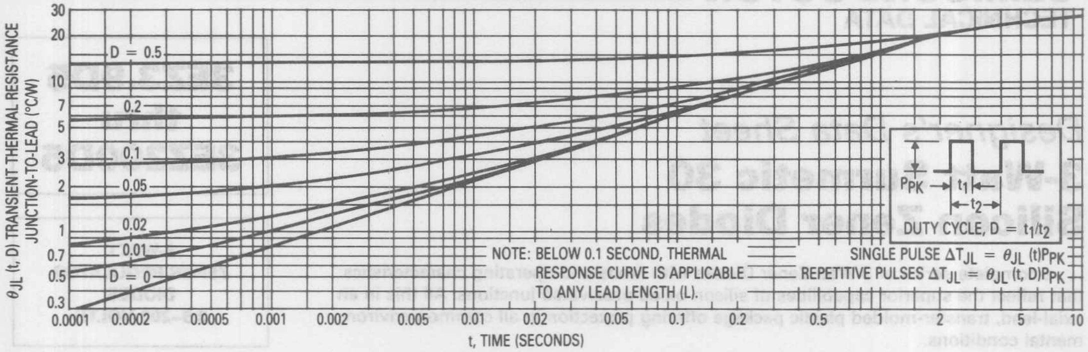

Figure 2. Typical Thermal Response L, Lead Length = 3/8 Inch

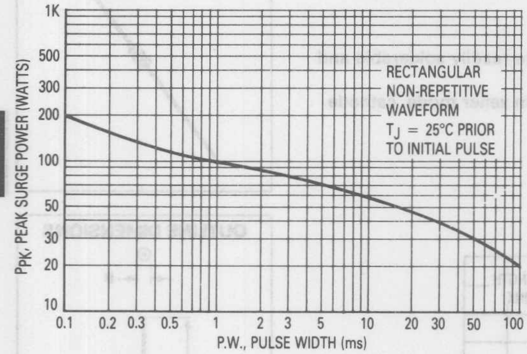

Figure 3. Maximum Surge Power

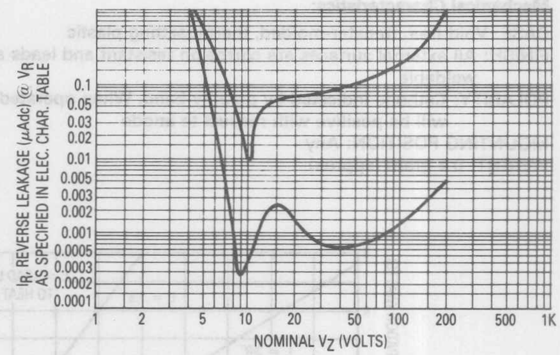

Figure 4. Typical Reverse Leakage

APPLICATION NOTE:

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Lead Temperature, T_L, should be determined from:

$$T_L = \theta_{LA} P_D + T_A$$

θ_{LA} is the lead-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{LA} will vary and depends on the device mounting method. θ_{LA} is generally 30–40°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the lead can also be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_L, the junction temperature may be determined by:

$$T_J = T_L + \Delta T_{JL}$$

ΔT_{JL} is the increase in junction temperature above the lead temperature and may be found from Figure 2 for a train of power pulses (L = 3/8 inch) or from Figure 10 for dc power.

$$\Delta T_{JL} = \theta_{JL} P_D$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of T_J (ΔT_J) may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 5 and 6.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Data of Figure 2 should not be used to compute surge capability. Surge limitations are given in Figure 3. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots resulting in device degradation should the limits of Figure 3 be exceeded.

TEMPERATURE COEFFICIENT RANGES

(90% of the Units are in the Ranges Indicated)

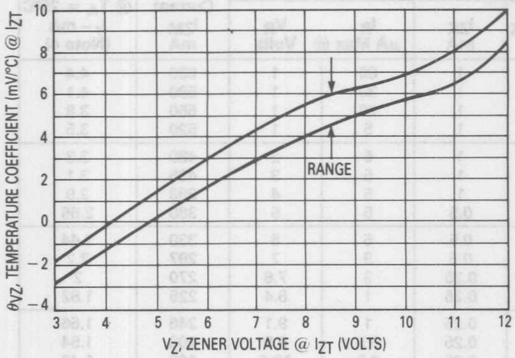

Figure 5. Units To 12 Volts

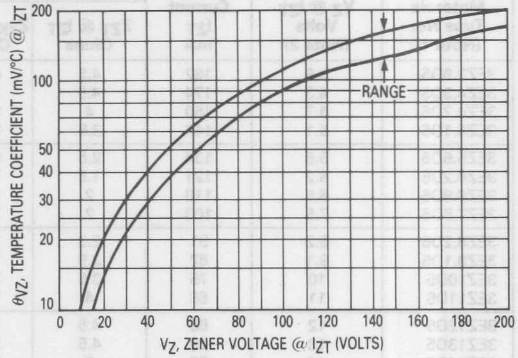

Figure 6. Units 10 To 200 Volts

ZENER VOLTAGE versus ZENER CURRENT

(Figures 7, 8 and 9)

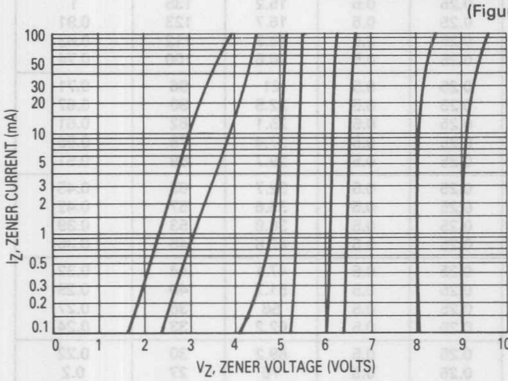

Figure 7. V_Z = 3.9 thru 10 Volts

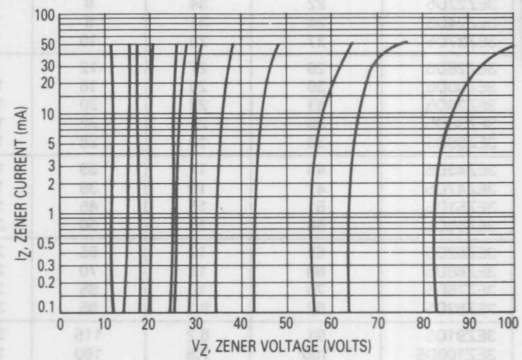

Figure 8. V_Z = 12 thru 82 Volts

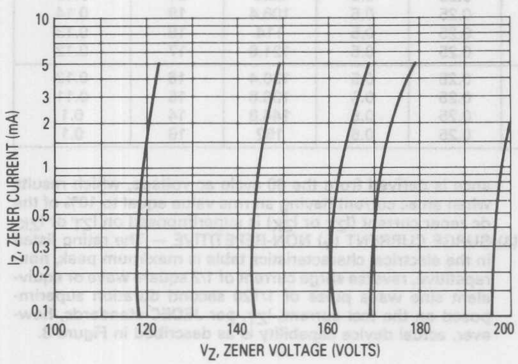

Figure 9. V_Z = 100 thru 200 Volts

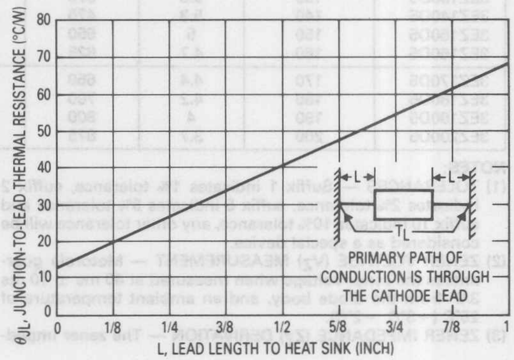

Figure 10. Typical Thermal Resistance

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) V_F = 1.5 V max, I_F = 200 mA for all types)

Motorola Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max Zener Impedance (Note 3) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Leakage Current I_R μA Max @	V_R Volts	Maximum Zener Current I_{ZM} mA	Surge Current @ T_A = 25°C i_r – mA (Note 4)
3EZ3.9D5	3.9	192	4.5	400	1	80	1	630	4.4
3EZ4.3D5	4.3	174	4.5	400	1	30	1	590	4.1
3EZ4.7D5	4.7	160	4	500	1	20	1	550	3.8
3EZ5.1D5	5.1	147	3.5	550	1	5	1	520	3.5
3EZ5.6D5	5.6	134	2.5	600	1	5	2	480	3.3
3EZ6.2D5	6.2	121	1.5	700	1	5	3	435	3.1
3EZ6.8D5	6.8	110	2	700	1	5	4	393	2.9
3EZ7.5D5	7.5	100	2	700	0.5	5	5	360	2.66
3EZ8.2D5	8.2	91	2.3	700	0.5	5	6	330	2.44
3EZ9.1D5	9.1	82	2.5	700	0.5	3	7	297	2.2
3EZ10D5	10	75	3.5	700	0.25	3	7.6	270	2
3EZ11D5	11	68	4	700	0.25	1	8.4	225	1.82
3EZ12D5	12	63	4.5	700	0.25	1	9.1	246	1.66
3EZ13D5	13	58	4.5	700	0.25	0.5	9.9	208	1.54
3EZ14D5	14	53	5	700	0.25	0.5	10.6	193	1.43
3EZ15D5	15	50	5.5	700	0.25	0.5	11.4	180	1.33
3EZ16D5	16	47	5.5	700	0.25	0.5	12.2	169	1.25
3EZ17D5	17	44	6	750	0.25	0.5	13	150	1.18
3EZ18D5	18	42	6	750	0.25	0.5	13.7	159	1.11
3EZ19D5	19	40	7	750	0.25	0.5	14.4	142	1.05
3EZ20D5	20	37	7	750	0.25	0.5	15.2	135	1
3EZ22D5	22	34	8	750	0.25	0.5	16.7	123	0.91
3EZ24D5	24	31	9	750	0.25	0.5	18.2	112	0.83
3EZ27D5	27	28	10	750	0.25	0.5	20.6	100	0.74
3EZ28D5	28	27	12	750	0.25	0.5	21	96	0.71
3EZ30D5	30	25	16	1000	0.25	0.5	22.5	90	0.67
3EZ33D5	33	23	20	1000	0.25	0.5	25.1	82	0.61
3EZ36D5	36	21	22	1000	0.25	0.5	27.4	75	0.56
3EZ39D5	39	19	28	1000	0.25	0.5	29.7	69	0.51
3EZ43D5	43	17	33	1500	0.25	0.5	32.7	63	0.45
3EZ47D5	47	16	38	1500	0.25	0.5	35.6	57	0.42
3EZ51D5	51	15	45	1500	0.25	0.5	38.8	53	0.39
3EZ56D5	56	13	50	2000	0.25	0.5	42.6	48	0.36
3EZ62D5	62	12	55	2000	0.25	0.5	47.1	44	0.32
3EZ68D5	68	11	70	2000	0.25	0.5	51.7	40	0.29
3EZ75D5	75	10	85	2000	0.25	0.5	56	36	0.27
3EZ82D5	82	9.1	95	3000	0.25	0.5	62.2	33	0.24
3EZ91D5	91	8.2	115	3000	0.25	0.5	69.2	30	0.22
3EZ100D5	100	7.5	160	3000	0.25	0.5	76	27	0.2
3EZ110D5	110	6.8	225	4000	0.25	0.5	83.6	25	0.18
3EZ120D5	120	6.3	300	4500	0.25	0.5	91.2	22	0.16
3EZ130D5	130	5.8	375	5000	0.25	0.5	98.8	21	0.15
3EZ140D5	140	5.3	475	5000	0.25	0.5	106.4	19	0.14
3EZ150D5	150	5	550	6000	0.25	0.5	114	18	0.13
3EZ160D5	160	4.7	625	6500	0.25	0.5	121.6	17	0.12
3EZ170D5	170	4.4	650	7000	0.25	0.5	130.4	16	0.12
3EZ180D5	180	4.2	700	7000	0.25	0.5	136.8	15	0.11
3EZ190D5	190	4	800	8000	0.25	0.5	144.8	14	0.1
3EZ200D5	200	3.7	875	8000	0.25	0.5	152	13	0.1

NOTES:

(1) TOLERANCES — Suffix 1 indicates 1% tolerance, suffix 2 indicates 2% tolerance, suffix 5 indicates 5% tolerance and suffix 10 indicates 10% tolerance, any other tolerance will be considered as a special device.

(2) ZENER VOLTAGE (V_Z) MEASUREMENT — Motorola guarantees the zener voltage when measured at 40 ms ± 10 ms 3/8″ from the diode body, and an ambient temperature of 25°C (+8°C, −2°C).

(3) ZENER IMPEDANCE (Z_Z) DERIVATION — The zener impedance is derived from the 60 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT} or I_{ZK}) is superimposed on I_{ZT} or I_{ZK}.

(4) SURGE CURRENT (i_r) NON-REPETITIVE — The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current, I_{ZT}, per JEDEC standards, however, actual device capability is as described in Figure 3.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

1N6267,A thru 1N6303,A
1N6373 thru 1N6389
ICTE-5,C
thru
ICTE-45,C
See Page 4-71

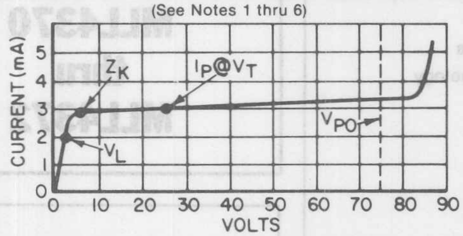
MCL1300 thru MCL1304

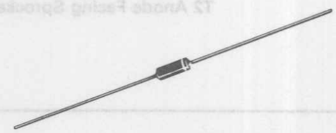
CURRENT LIMITING DIODES

CURRENT LIMITING DIODES

Field-effect current limiting diodes designed for applications requiring a current reference or a constant current over a specified voltage range.

CURRENT-LIMITER CHARACTERISTICS AND SYMBOL IDENTIFICATION
(See Notes 1 thru 6)





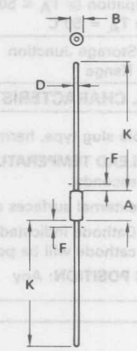
MAXIMUM RATINGS ($T_A = 25\,°C$ unless otherwise noted)

Junction and Storage Temperature: $-65\,°C$ to $+200\,°C$
Peak Operating Voltage: See Table

ELECTRICAL CHARACTERISTICS ($T_A = 25\,°C$ unless otherwise noted)

Type Number	Nominal Pinch-Off Current Note 1 I_P (mA)	Tol. (mA)	Test Volt. Note 2 V_T (Volts)	Limiter Imped. Note 3 Z_T (min) (Megohms)	Knee Imped. at 6 V Note 4 Z_K (min) (Megohms)	Limiting Voltage Note 5 V_L (max) (Volts)	Peak Operating Voltage Note 6 V_{PO} (Volts)
MCL1300	0.5	± 0.3	25	4.000	0.500	1.0	75
MCL1301	1.0	± 0.6	25	0.800	0.200	1.5	75
MCL1302	2.0	± 0.6	25	0.400	0.100	2.0	75
MCL1303	3.0	± 0.6	25	0.300	0.050	2.0	75
MCL1304	4.0	± 0.6	25	0.250	0.025	2.5	75

These specifications are preliminary. Selections may be made to obtain nominal currents between those shown, as well as tighter tolerance units.



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

SYMBOL DEFINITIONS:

NOTE 1 I_P – The pinch-off current is the guaranteed current at a specified V_T. I_P is specified as a nominal with a tolerance.

NOTE 2 V_T – The test voltage for measurement of I_P.

NOTE 3 Z_T – The impedance at the test voltage, V_T, specified. To provide the most constant current Z_T should be as high as possible; thus a minimum Z_T is specified. Z_T is derived from the 90 cycle per second current which results when an AC voltage having an RMS value equal to 10% of the test voltage (V_T) is superimposed on V_T.

NOTE 4 Z_K – Knee impedance is specified as a minimum also since again the highest value is desired. V_K is established as 6.0 V for convenience.

NOTE 5 V_L – Limiting Voltage. This specification is provided with Z_K to indicate the sharp knee of the device. The specification is analogous to I_R and Z_K of a zener diode. V_L a maximum specification is measured at 80% on I_P tolerance.

NOTE 6 V_{PO} – The peak-operating voltage is provided and indicates the maximum voltage to be applied to the device. The specification is necessary since the device is either power limited or breakdown limited beyond this specified voltage.

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MLL746 thru MLL759

MLL957A thru MLL986A

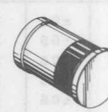
MLL4370 thru MLL4372

500 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

- Complete Voltage Range — 2.4 to 110 Volts
- Leadless Package for Surface Mount Technology
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Nitride Passivated Die
- Available in 8 mm Tape and Reel
  T1 Cathode Facing Sprocket Holes
  T2 Anode Facing Sprocket Holes

LEADLESS GLASS ZENER DIODES

500 MILLIWATTS
2.4–110 VOLTS



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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A \le 50°C$ Derate above $T_A = 50°C$	P_D	500 3.3	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

MECHANICAL CHARACTERISTICS

CASE: Double slug type, hermetically sealed glass

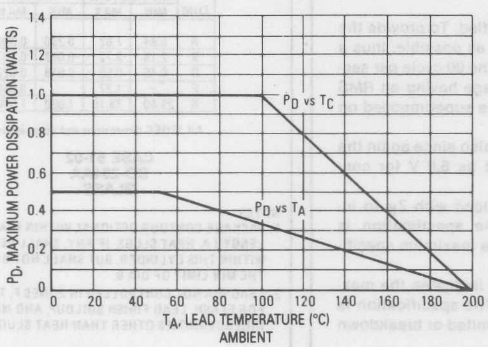
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, for 10 seconds

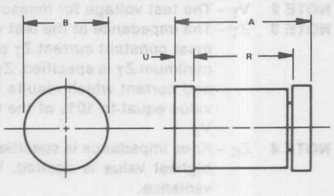
FINISH: All external surfaces are corrosion resistant and readily solderable

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode

MOUNTING POSITION: Any

STEADY STATE POWER DERATING





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

CASE 362-01
GLASS

ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V Max @ 200 mA for all types)

Type Number (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} (Notes 1,2,3) Volts	Test Current I_{ZT} (Note 2) mA	Maximum Zener Impedance Z_{ZT} @ I_{ZT} (Note 4) Ohms	Maximum DC Zener Current I_{ZM} mA		Maximum Reverse Leakage Current T_A = 25°C I_R @ V_R = 1 V µA	T_A 150°C I_R @ V_R = 1 V µA
MLL4370	2.4	20	30	150	190	100	200
MLL4371	2.7	20	30	135	165	75	150
MLL4372	3.0	20	29	120	150	50	100
MLL746	3.3	20	28	110	135	10	30
MLL747	3.6	20	24	100	125	10	30
MLL748	3.9	20	23	95	115	10	30
MLL749	4.3	20	22	85	105	2	30
MLL750	4.7	20	19	75	95	2	30
MLL751	5.1	20	17	70	85	1	20
MLL752	5.6	20	11	65	80	1	20
MLL753	6.2	20	7	60	70	0.1	20
MLL754	6.8	20	5	55	65	0.1	20
MLL755	7.5	20	6	50	60	0.1	20
MLL756	8.2	20	8	45	55	0.1	20
MLL757	9.1	20	10	40	50	0.1	20
MLL758	10	20	17	35	45	0.1	20
MLL759	12	20	30	30	35	0.1	20

Type Number (Note 1)	Nominal Zener Voltage V_Z (Notes 1,2,3) Volts	Test Current I_{ZT} (Note 2) mA	Maximum Zener Impedance (Note 4) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Maximum DC Zener Current I_{ZM} mA		Maximum Reverse Current I_R Maximum µA	Test Voltage Vdc V_R 5%	10%
MLL957A	6.8	18.5	4.5	700	1.0	47	61	150	5.2	4.9
MLL958A	7.5	16.5	5.5	700	0.5	42	55	75	5.7	5.4
MLL959A	8.2	15	6.5	700	05	38	50	50	6.2	5.9
MLL960A	9.1	14	7.5	700	0.5	35	45	25	6.9	6.6
MLL961A	10	12.5	8.5	700	0.25	32	41	10	7.6	7.2
MLL962A	11	11.5	9.5	700	0.25	28	37	5	8.4	8.0
MLL963A	12	10.5	11.5	700	0.25	26	34	5	9.1	8.6
MLL964A	13	9.5	13	700	0.25	24	32	5	9.9	9.4
MLL965A	15	8.5	16	700	0.25	21	27	5	11.4	10.8
MLL966A	16	7.8	17	700	0.25	19	37	5	12.2	11.5
MLL967A	18	7.0	21	750	0.25	17	23	5	13.7	13.0
MLL968A	20	6.2	25	750	0.25	15	20	5	15.2	14.4
MLL969A	22	5.6	29	750	0.25	14	18	5	16.7	15.8
MLL970A	24	5.2	33	750	0.25	13	17	5	18.2	17.3
MLL971A	27	4.6	41	750	0.25	11	15	5	20.6	19.4
MLL972A	30	4.2	49	1000	0.25	10	13	5	22.8	21.6
MLL973A	33	3.8	58	1000	0.25	9.2	12	5	25.1	23.8
MLL974A	36	3.4	70	1000	0.25	8.5	11	5	27.4	25.9
MLL975A	39	3.2	80	1000	0.25	7.8	10	5	29.7	28.1
MLL976A	43	3.0	93	1500	0.25	7.0	9.6	5	32.7	31.0
MLL977A	47	2.7	105	1500	0.25	6.4	8.8	5	35.8	33.8
MLL978A	51	2.5	125	1500	0.25	5.9	8.1	5	38.8	36.7
MLL979A	56	2.2	150	2000	0.25	5.4	7.4	5	42.6	40.3
MLL980A	62	2.0	185	2000	0.25	4.9	6.7	5	47.1	44.6
MLL981A	68	1.8	230	2000	0.25	4.5	6.1	5	51.7	49.0
MLL982A	75	1.7	270	2000	0.25	1.0	5.5	5	56.0	54.0
MLL983A	82	1.5	330	3000	0.25	3.7	5.0	5	62.2	59.0
MLL984A	91	1.4	400	3000	0.25	3.3	4.5	5	69.2	65.5
MLL985A	100	1.3	500	3000	0.25	3.0	4.5	5	76	72
MLL986A	110	1.1	750	4000	0.25	2.7	4.1	5	83.6	79.2

4

NOTE 1. Tolerance Designation — The type numbers shown have tolerance designations as follows:

MLL4370 series: ±10%, suffix A for ±5% units.
MLL746 series: ±10%, suffix A for ±5% units.
MLL957 series: suffix A for ±10% units, suffix B for ±5% units.

NOTE 2. Special Selections† Available Include:

1. Nominal zener voltages between those shown.
2. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.
3. Nominal voltages at non-standard test currents.

NOTE 3. Zener Voltage (V_Z) Measurement — Nominal zener voltage is measured with the device junction in thermal equilibrium at the case temperature of 30°C ±1°C.

NOTE 4. Zener Impedance (Z_Z) Derivation — Z_{ZT} is measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac) = 0.1 \times I_Z(dc)$ with the ac frequency = 1.0 kHz.

†For more information on special selections contact your nearest Motorola representative.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Case Temperature, T_C, should be determined from:

$$T_C = \theta_{CA}P_D + T_A.$$

θ_{CA} is the case-to-ambient thermal resisstance (°C/W) and P_D is the power dissipation. The value for θ_{CA} will vary and depends on the device mounting method. θ_{CA} is generally 200°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the case can also be measured using a thermocouple placed at the case end as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}.$$

ΔT_{JC} is the increase in junction temperature above the case temperature and may be found by using:

$$\Delta T_{JC} = \theta_{JC}P_D.$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ}\Delta T_J.$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 2 and 3.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

FIGURE 1 — TYPICAL LEAKAGE CURRENT

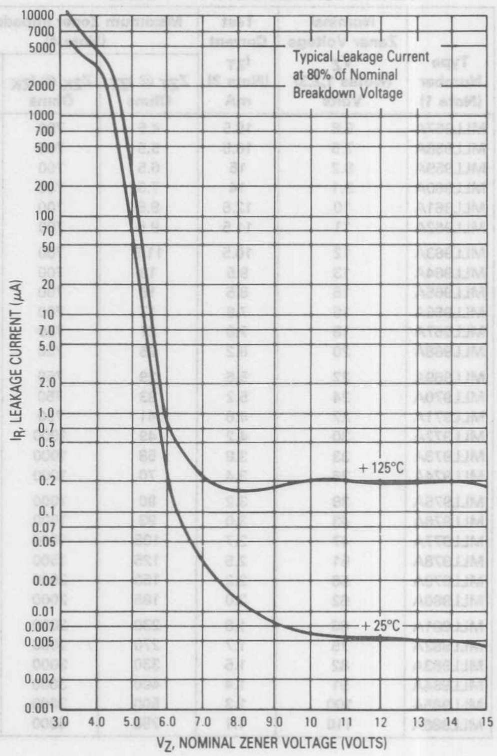


FIGURE 2 — TEMPERATURE COEFFICIENTS
(−55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

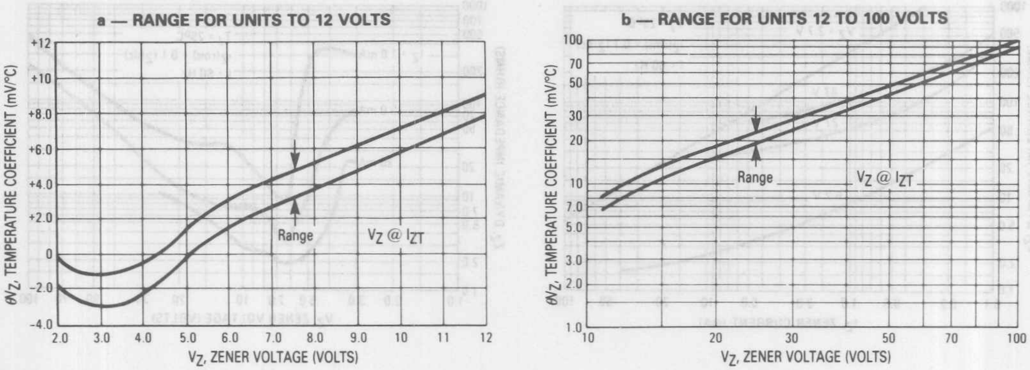


FIGURE 3 — EFFECT OF ZENER CURRENT

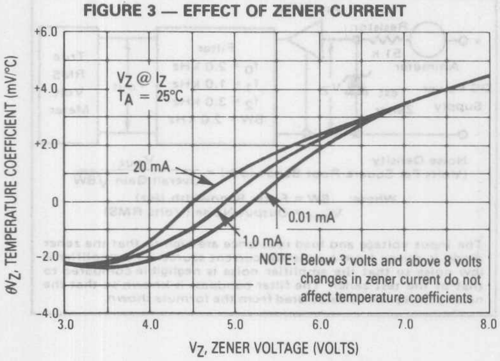


FIGURE 4 — TYPICAL CAPACITANCE

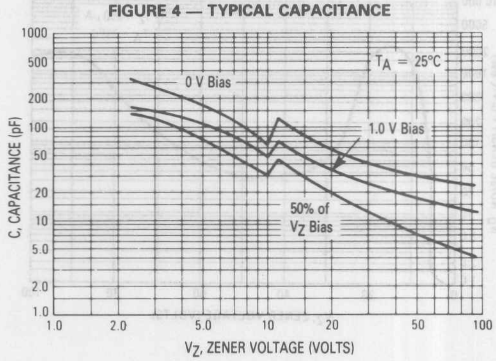
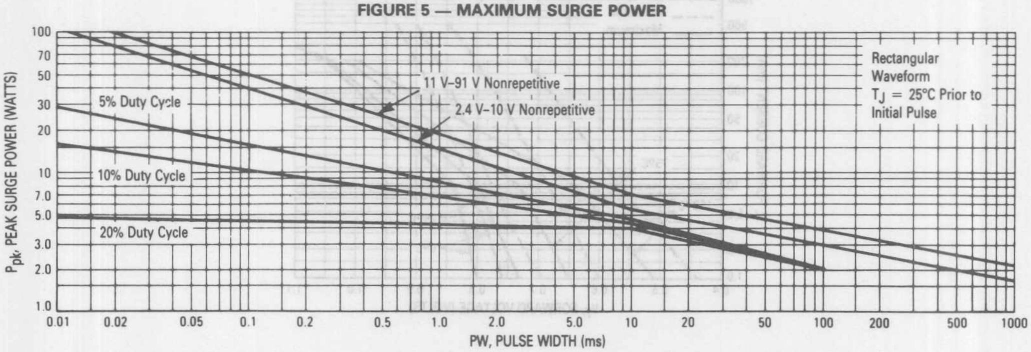


FIGURE 5 — MAXIMUM SURGE POWER



This graph represents 90 percentil data points.
For worst-case design characteristics, multiply surge power by 2/3.

FIGURE 6 — EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

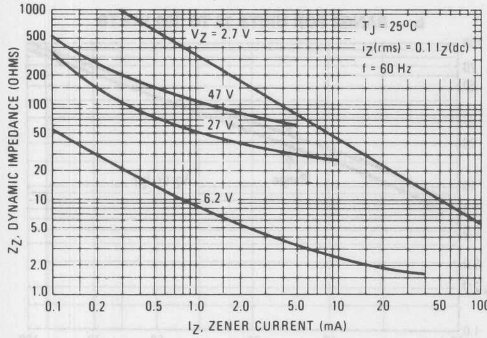


FIGURE 7 — EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

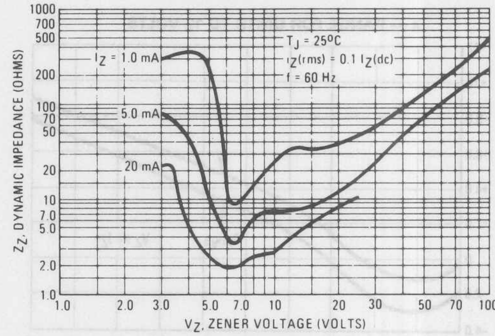


FIGURE 8 — TYPICAL NOISE DENSITY

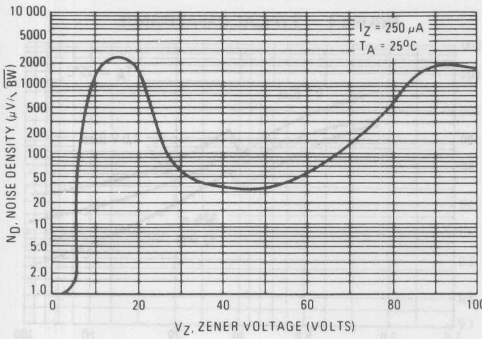
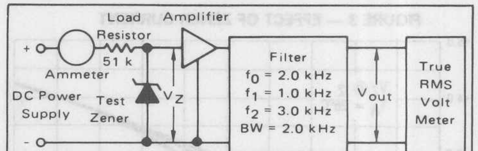


FIGURE 9 — NOISE DENSITY MEASUREMENT METHOD

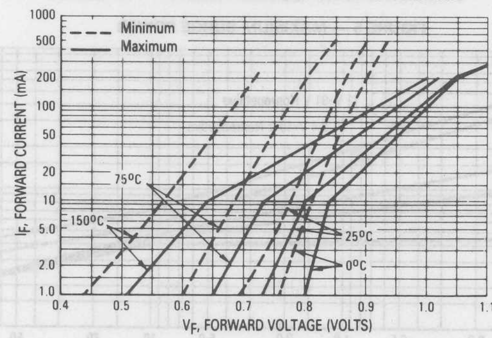


$$\text{Noise Density (Volts Per Square Root Bandwidth)} = \frac{V_{out}}{\text{Overall Gain}\ \sqrt{BW}}$$

Where: BW = Filter Bandwidth (Hz)
V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

FIGURE 10 — TYPICAL FORWARD CHARACTERISTICS



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MLL4099–MLL4135
MLL4614–MLL4627

LOW NOISE LEVEL SILICON PASSIVATED ZENER DIODES

. . . designed for 250 mW applications requiring low leakage, low impedance, and low noise.

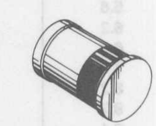
- Leadless Package for Surface Mount Technology
- Voltage Range from 1.8 to 100 Volts
- First Leadless Zener Diode Series to Specify Noise — 50% Lower than Conventional Diffused Zeners
- Zener Impedance and Zener Voltage Specified for Low-Level Operation at I_{ZT} = 250 μA
- Low Leakage Current — I_R from 0.01 to 10 μA over Voltage Range
- Available in 8mm Tape and Reel
  T1 Cathode Facing Sprocket Holes
  T2 Anode Facing Sprocket Holes

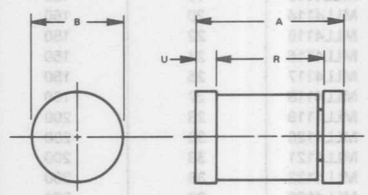
SILICON LEADLESS GLASS ZENER DIODES

(±5.0% TOLERANCE)

250 MILLIWATTS
1.8–100 VOLTS

SILICON NITRIDE PASSIVATED JUNCTION





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

CASE 362-01
GLASS

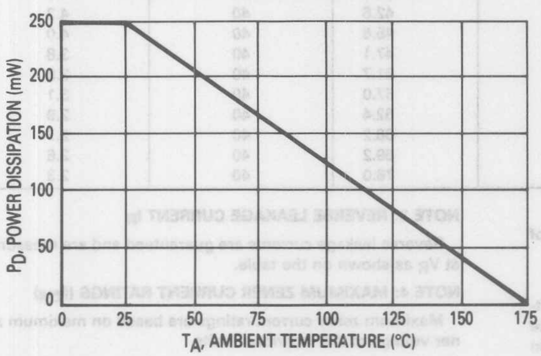
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_A = 25°C Derate above 25°C	P_D	250 1.43	mW mW/°C
Junction and Storage Temperature Range	T_J, T_{stg}	−65 to +200	°C

MECHANICAL CHARACTERISTICS

CASE: Double slug, hermetically sealed glass
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C for 10 seconds
FINISH: All external surfaces are corrosion resistant and readily solderable
POLARITY: Cathode indicated by color band. When operated in the zener mode, cathode will be positive with respect to anode
MOUNTING POSITION: Any

POWER TEMPERATURE DERATING CURVE



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4

ELECTRICAL CHARACTERISTICS

(At 25°C Ambient temperature unless otherwise specified) I_{ZT} = 250 μA and V_F = 1.0 V max @ I_F = 200 mA on all Types

Type Number (Note 1)	Nominal Zener Voltage V_Z (Note 1) (Volts)	Max Zener Impedance Z_{ZT} (Note 2) (Ohms)	Max Reverse Current I_R (μA)	(Note 3)	Test Voltage V_R (Volts)	Max Noise Density At I_{ZT} = 250 μA N_D (Fig 1) (micro-volts per Square Root Cycle)	Max Zener Current I_{ZM} (Note 4) (mA)
MLL4614	1.8	1200	7.5		1.0	1.0	120
MLL4615	2.0	1250	5.0		1.0	1.0	110
MLL4616	2.2	1300	4.0		1.0	1.0	100
MLL4617	2.4	1400	2.0		1.0	1.0	95
MLL4618	2.7	1500	1.0		1.0	1.0	90
MLL4619	3.0	1600	0.8		1.0	1.0	85
MLL4620	3.3	1650	7.5		1.5	1.0	80
MLL4621	3.6	1700	7.5		2.0	1.0	75
MLL4622	3.9	1650	5.0		2.0	1.0	70
MLL4623	4.3	1600	4.0		2.0	1.0	65
MLL4624	4.7	1550	10		3.0	1.0	60
MLL4625	5.1	1500	10		3.0	2.0	55
MLL4626	5.6	1400	10		4.0	4.0	50
MLL4627	6.2	1200	10		5.0	5.0	45
MLL4099	6.8	200	10		5.2	40	35
MLL4100	7.5	200	10		5.7	40	31.8
MLL4101	8.2	200	1.0		6.3	40	29.0
MLL4102	8.7	200	1.0		6.7	40	27.4
MLL4103	9.1	200	1.0		7.0	40	26.2
MLL4104	10	200	1.0		7.6	40	24.8
MLL4105	11	200	0.05		8.5	40	21.6
MLL4106	12	200	0.05		9.2	40	20.4
MLL4107	13	200	0.05		9.9	40	19.0
MLL4108	14	200	0.05		10.7	40	17.5
MLL4109	15	100	0.05		11.4	40	16.3
MLL4110	16	100	0.05		12.2	40	15.4
MLL4111	17	100	0.05		13.0	40	14.5
MLL4112	18	100	0.05		13.7	40	13.2
MLL4113	19	150	0.05		14.5	40	12.5
MLL4114	20	150	0.01		15.2	40	11.9
MLL4115	22	150	0.01		16.8	40	10.8
MLL4116	24	150	0.01		18.3	40	9.9
MLL4117	25	150	0.01		19.0	40	9.5
MLL4118	27	150	0.01		20.5	40	8.8
MLL4119	28	200	0.01		21.3	40	8.5
MLL4120	30	200	0.01		22.8	40	7.9
MLL4121	33	200	0.01		25.1	40	7.2
MLL4122	36	200	0.01		27.4	40	6.6
MLL4123	39	200	0.01		29.7	40	6.1
MLL4124	43	250	0.01		32.7	40	5.5
MLL4125	47	250	0.01		35.8	40	5.1
MLL4126	51	300	0.01		38.8	40	4.6
MLL4127	56	300	0.01		42.6	40	4.2
MLL4128	60	400	0.01		45.6	40	4.0
MLL4129	62	500	0.01		47.1	40	3.8
MLL4130	68	700	0.01		51.7	40	3.5
MLL4131	75	700	0.01		57.0	40	3.1
MLL4132	82	800	0.01		62.4	40	2.9
MLL4133	87	1000	0.01		66.2	40	2.7
MLL4134	91	1200	0.01		69.2	40	2.6
MLL4135	100	1500	0.01		76.0	40	2.3

NOTE 1: TOLERANCE AND VOLTAGE DESIGNATION

The type numbers shown have a standard tolerance of ±5.0% on the nominal zener voltage.

NOTE 2: ZENER IMPEDANCE (Z_{ZT}) DERIVATION

The zener impedance is derived from the 1000 cycle ac voltage, which results when an ac current having an rms value equal to 10% of the dc zener current (I_{ZT}) is superimposed on I_{ZT}.

NOTE 3: REVERSE LEAKAGE CURRENT I_R

Reverse leakage currents are guaranteed and are measured at V_R as shown on the table.

NOTE 4: MAXIMUM ZENER CURRENT RATINGS (I_{ZM})

Maximum zener current ratings are based on maximum zener voltage of the individual units.

ZENER NOISE DENSITY

A zener diode generates noise when it is biased in the zener direction. A small part of this noise is due to the internal resistance associated with the device. A larger part of zener noise is a result of the zener breakdown phenomenon and is called microplasma noise. This microplasma noise is generally considered "white" noise with equal amplitude for all frequencies from about zero cycles to approximately 200,000 cycles. To eliminate the higher frequency components of noise a small shunting capacitor can be used. The lower frequency noise generally must be tolerated since a capacitor required to eliminate the lower frequencies would degrade the regulation properties of the zener in many applications.

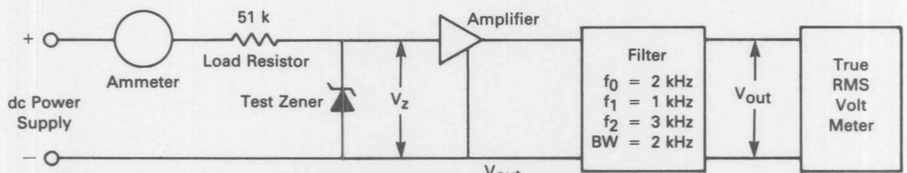
Motorola is rating this series with a maximum noise density at 250 microamperes. The rating of microvolts RMS per square root cycle enables calculation of the maximum RMS noise for any bandwidth.

Noise density decreases as zener current increases. This can be seen by the graph in Figure 2 where a typical noise density is plotted as a function of zener current.

The junction temperature will also change the zener noise levels. Thus the noise rating must indicate bandwidth, current level and temperature.

The block diagram given in Figure 1 shows the method used to measure noise density. The input voltage and load resistance is high so that the zener is driven from a constant current source. The amplifier must be low noise so that the amplifier noise is negligible compared to the test zener. The filter bandpass is known so that the noise density in volts RMS per square root cycle can be calculated.

FIGURE 1 — NOISE DENSITY MEASUREMENT METHOD



$$\text{Noise Density (volts per square root cycle)} = \frac{V_{out}}{\text{Overall Gain } \sqrt{BW}}$$

Where: BW = Filter Bandwidth (Cycles)

V_{out} = Output Noise (Volts RMS)

FIGURE 2 — TYPICAL NOISE DENSITY versus ZENER CURRENT

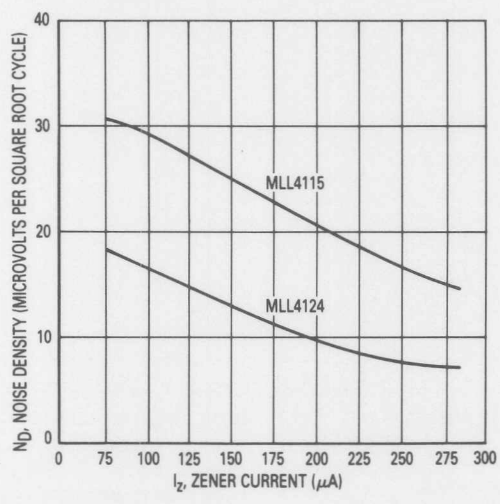


FIGURE 3 — TYPICAL CAPACITANCE

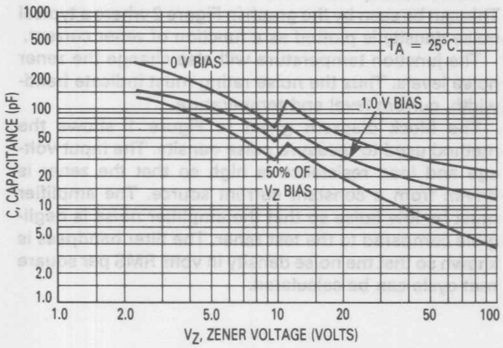
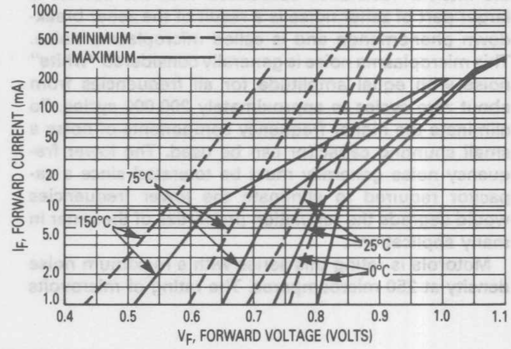


FIGURE 4 — TYPICAL FORWARD CHARACTERISTICS



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MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MLL4678 thru MLL4717

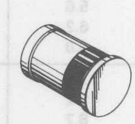
250 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

Low level nitride passivated zener diodes for applications requiring extremely low operating currents, low leakage, and sharp breakdown voltage.

- Complete Voltage Range — 1.8 to 43 Volts
- Zener Voltage Specified @ I_{ZT} = 50 μA
- Leadless Package for Surface Mount Technology
- Maximum Delta V_Z Given from 10 to 100 μA
- Available in 8 mm Tape and Reel
  T1 Cathode Facing Sprocket Holes
  T2 Anode Facing Sprocket Holes

LEADLESS GLASS ZENER DIODES

250 MILLIWATTS

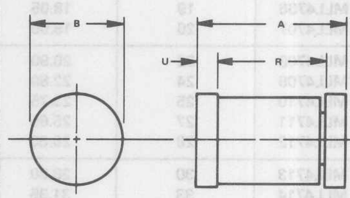


ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ T_A = 50°C Derate above T_A = 50°C	P_D	250 1.67	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +175	°C

MECHANICAL CHARACTERISTICS

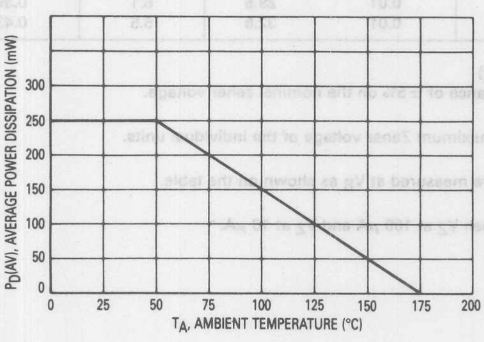
CASE: Double slug, hermetically sealed glass
MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C for 10 seconds
FINISH: All external surfaces are corrosion resistant and readily solderable
POLARITY: Cathode end indicated by color band. When operated in zener mode, the cathode will be positive with respect to anode
MOUNTING POSITION: Any



	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

CASE 362-01 GLASS

FIGURE 1 — POWER TEMPERATURE DERATING CURVE



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ELECTRICAL CHARACTERISTICS (T_A = 25°C, V_F = 1.5 V max at I_F = 100 mA for all types)

Type Number (Note 1)	Zener Voltage V_Z @ I_{ZT} = 50 μA Volts			Maximum Reverse Current I_R μA (Note 3)	Test Voltage V_R Volts (Note 3)	Maximum Zener Current I_{ZM} mA (Note 2)	Maximum Voltage Change ΔV_Z Volts (Note 4)
	Nom (Note 1)	Min	Max				
MLL4678	1.8	1.710	1.890	7.5	1.0	120	0.70
MLL4679	2.0	1.900	2.100	5.0	1.0	110	0.70
MLL4680	2.2	2.090	2.310	4.0	1.0	100	0.75
MLL4681	2.4	2.280	2.520	2.0	1.0	95	0.80
MLL4682	2.7	2.565	2.835	1.0	1.0	90	0.85
MLL4683	3.0	2.850	3.150	0.8	1.0	85	0.90
MLL4684	3.3	3.135	3.465	7.5	1.5	80	0.95
MLL4685	3.6	3.420	3.780	7.5	2.0	75	0.95
MLL4686	3.9	3.705	4.095	5.0	2.0	70	0.97
MLL4687	4.3	4.085	4.515	4.0	2.0	65	0.99
MLL4688	4.7	4.465	4.935	10	3.0	60	0.99
MLL4689	5.1	4.845	5.355	10	3.0	55	0.97
MLL4690	5.6	5.320	5.880	10	4.0	50	0.96
MLL4691	6.2	5.890	6.510	10	5.0	45	0.95
MLL4692	6.8	6.460	7.140	10	5.1	35	0.90
MLL4693	7.5	7.125	7.875	10	5.7	31.8	0.75
MLL4694	8.2	7.790	8.610	1.0	6.2	29.0	0.50
MLL4695	8.7	8.265	9.135	1.0	6.6	27.4	0.10
MLL4696	9.1	8.645	9.555	1.0	6.9	26.2	0.08
MLL4697	10	9.500	10.50	1.0	7.6	24.8	0.10
MLL4698	11	10.45	11.55	0.05	8.4	21.6	0.11
MLL4699	12	11.40	12.60	0.05	9.1	20.4	0.12
MLL4700	13	12.35	13.65	0.05	9.8	19.0	0.13
MLL4701	14	13.30	14.70	0.05	10.6	17.5	0.14
MLL4702	15	14.25	15.75	0.05	11.4	16.3	0.15
MLL4703	16	15.20	16.80	0.05	12.1	15.4	0.16
MLL4704	17	16.15	17.85	0.05	12.9	14.5	0.17
MLL4705	18	17.10	18.90	0.05	13.6	13.2	0.18
MLL4706	19	18.05	19.95	0.05	14.4	12.5	0.19
MLL4707	20	19.00	21.00	0.01	15.2	11.9	0.20
MLL4708	22	20.90	23.10	0.01	16.7	10.8	0.22
MLL4709	24	22.80	25.20	0.01	18.2	9.9	0.24
MLL4710	25	23.75	26.25	0.01	19.0	9.5	0.25
MLL4711	27	25.65	28.35	0.01	20.4	8.8	0.27
MLL4712	28	26.60	29.40	0.01	21.2	8.5	0.28
MLL4713	30	28.50	31.50	0.01	22.8	7.9	0.30
MLL4714	33	31.35	34.65	0.01	25.0	7.2	0.33
MLL4715	36	34.20	37.80	0.01	27.3	6.6	0.36
MLL4716	39	37.05	40.95	0.01	29.6	6.1	0.39
MLL4717	43	40.85	45.15	0.01	32.6	5.5	0.43

NOTES:
1. **TOLERANCE AND VOLTAGE DESIGNATION (V_Z)**
   The type numbers shown have a standard tolerance of ±5% on the nominal zener voltage.
2. **MAXIMUM ZENER CURRENT RATINGS (I_{ZM})**
   Maximum Zener current ratings are based on maximum Zener voltage of the individual units.
3. **REVERSE LEAKAGE CURRENT (I_R)**
   Reverse leakage currents are guaranteed and are measured at V_R as shown on the table.
4. **MAXIMUM VOLTAGE CHANGE (ΔV_Z)**
   Voltage change is equal to the difference between V_Z at 100 μA and V_Z at 10 μA.

4

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

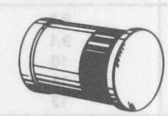
MLL4728 thru MLL4764

1.0 WATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

- Complete Voltage Range — 3.3 to 100 Volts
- Leadless Package for Surface Mount Technology
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die
- Available in 12 mm Tape and Reel
  T1 Cathode Facing Sprocket Holes
  T2 Anode Facing Sprocket Holes

LEADLESS GLASS ZENER DIODES

1.0 WATT
3.3–100 VOLTS



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A \leq 50°C$ Derate above $T_A = 50°C$	P_D	1.0 6.67	W mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200	°C

MECHANICAL CHARACTERISTICS

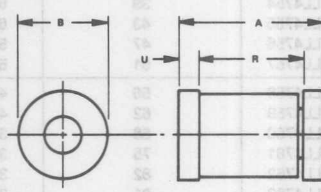
CASE: Double slug type, hermetically sealed glass

MAXIMUM TEMPERATURE FOR SOLDERING PURPOSES: 230°C, for 10 seconds

FINISH: All external surfaces are corrosion resistant and readily solderable

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode

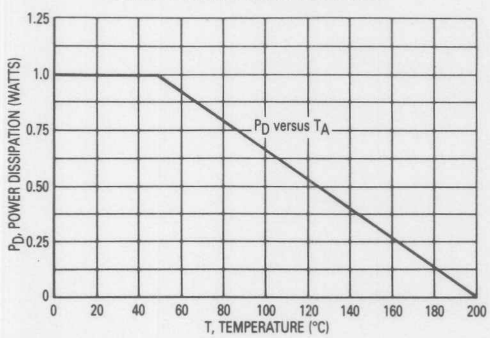
MOUNTING POSITION: Any



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.20	0.189	0.205
B	2.39	2.59	0.094	0.102
R	3.68	4.54	0.145	0.179
U	0.30	0.55	0.012	0.022

CASE 362B-01
GLASS

STEADY STATE POWER DERATING



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MLL4728 thru MLL4764

(T_A = 25°C unless otherwise noted. Based on dc measurements at thermal equilibrium; case temperature maintained at 30±2°C. V_F = 1.2 V max @ I_F = 200 mA for all types.)

Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Notes 2 and 3)	Test Current I_{ZT} mA	Maximum Zener Impedance (Note 4) Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} Ohms	I_{ZK} mA	Leakage Current I_R µA Max	V_R Volts	Surge Current @ T_A = 25°C i_r – mA (Note 5)
MLL4728	3.3	76	10	400	1.0	100	1.0	1380
MLL4729	3.6	69	10	400	1.0	100	1.0	1260
MLL4730	3.9	64	9.0	400	1.0	50	1.0	1190
MLL4731	4.3	58	9.0	400	1.0	10	1.0	1070
MLL4732	4.7	53	8.0	500	1.0	10	1.0	970
MLL4733	5.1	49	7.0	550	1.0	10	1.0	890
MLL4734	5.6	45	5.0	600	1.0	10	2.0	810
MLL4735	6.2	41	2.0	700	1.0	10	3.0	730
MLL4736	6.8	37	3.5	700	1.0	10	4.0	660
MLL4737	7.5	34	4.0	700	0.5	10	5.0	605
MLL4738	8.2	31	4.5	700	0.5	10	6.0	550
MLL4739	9.1	28	5.0	700	0.5	10	7.0	500
MLL4740	10	25	7.0	700	0.25	10	7.6	454
MLL4741	11	23	8.0	700	0.25	5.0	8.4	414
MLL4742	12	21	9.0	700	0.25	5.0	9.1	380
MLL4743	13	19	10	700	0.25	5.0	9.9	344
MLL4744	15	17	14	700	0.25	5.0	11.4	304
MLL4745	16	15.5	16	700	0.25	5.0	12.2	285
MLL4746	18	14	20	750	0.25	5.0	13.7	250
MLL4747	20	12.5	22	750	0.25	5.0	15.2	225
MLL4748	22	11.5	23	750	0.25	5.0	16.7	205
MLL4749	24	10.5	25	750	0.25	5.0	18.2	190
MLL4750	27	9.5	35	750	0.25	5.0	20.6	170
MLL4751	30	8.5	40	1000	0.25	5.0	22.8	150
MLL4752	33	7.5	45	1000	0.25	5.0	25.1	135
MLL4753	36	7.0	50	1000	0.25	5.0	27.4	125
MLL4754	39	6.5	60	1000	0.25	5.0	29.7	115
MLL4755	43	6.0	70	1500	0.25	5.0	32.7	110
MLL4756	47	5.5	80	1500	0.25	5.0	35.8	95
MLL4757	51	5.0	95	1500	0.25	5.0	38.8	90
MLL4758	56	4.5	110	2000	0.25	5.0	42.6	80
MLL4759	62	4.0	125	2000	0.25	5.0	47.1	70
MLL4760	68	3.7	150	2000	0.25	5.0	51.7	65
MLL4761	75	3.3	175	2000	0.25	5.0	56.0	60
MLL4762	82	3.0	200	3000	0.25	5.0	62.2	55
MLL4763	91	2.8	250	3000	0.25	5.0	69.2	50
MLL4764	100	2.5	350	3000	0.25	5.0	76.0	45

NOTE 1. Tolerance and Type Number Designation — The type numbers listed have a standard tolerance on the nominal zener voltage of ±10%. A standard tolerance of ±5% on individual units is also available and is indicated by suffixing "A" to the standard type number.

NOTE 2. Special Selections† Available Include:

1. Nominal zener voltages between those shown.
2. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.
3. Nominal voltages at non-standard test currents.

NOTE 3. Zener Voltage (V_Z) Measurement — Nominal zener voltage is measured with the device junction in thermal equilibrium at the case temperature of 30°C ±2°C.

NOTE 4. Zener Impedance (Z_Z) Derivation — Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac) = 0.1 \times I_Z(dc)$ with the ac frequency = 1.0 kHz.

†For more information on special selections contact your nearest Motorola representative.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Case Temperature, T_C, should be determined from:

$$T_C = \theta_{CA} P_D + T_A.$$

θ_{CA} is the case-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{CA} will vary and depends on the device mounting method. θ_{CA} is generally 200°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the case can also be measured using a thermocouple placed at the case end as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}.$$

ΔT_{JC} is the increase in junction temperature above the case temperature and may be found by using:

$$\Delta T_{JC} = \theta_{JC} P_D.$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ} \Delta T_J.$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 3 and 4.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

NOTE 5. Surge Current (i_r) Nonrepetitive — The rating listed in the electrical characteristics table is maximum peak, non-repetitive, reverse surge current of 1/2 square wave or equivalent sine wave pulse of 1/120 second duration superimposed on the test current, I_{ZT}, per JEDEC registration; however, actual device capability is as described in Figures 4 and 6.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

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FIGURE 1 — TYPICAL LEAKAGE CURRENT

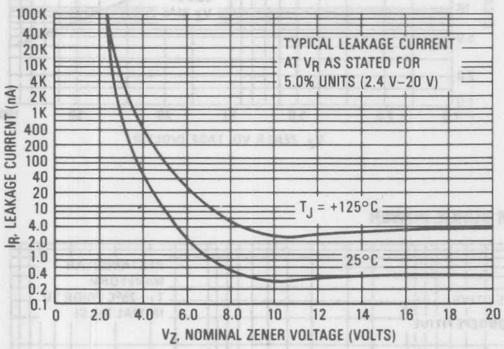


FIGURE 2 — TYPICAL LEAKAGE CURRENT

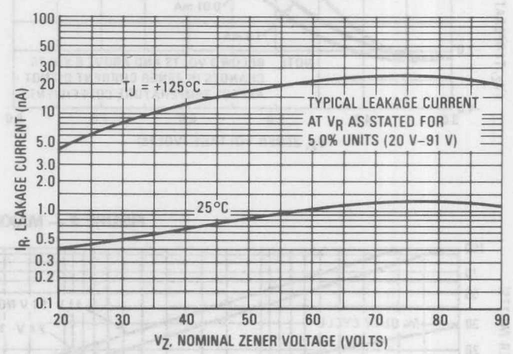
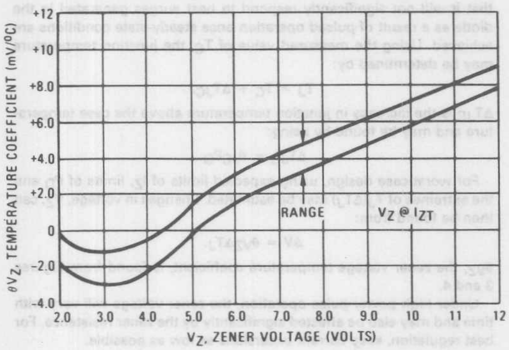


FIGURE 3 — TEMPERATURE COEFFICIENTS @ I_{ZT}

(−55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

a — RANGE FOR UNITS TO 12 VOLTS



b — RANGE FOR UNITS 12 TO 100 VOLTS

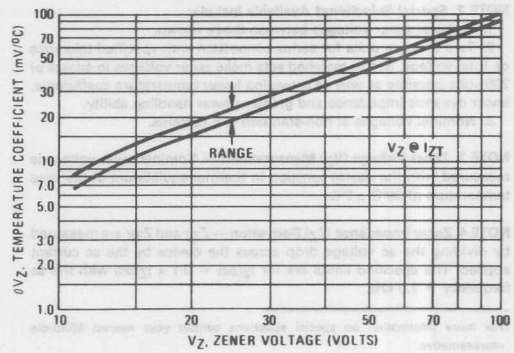


FIGURE 4 — EFFECT OF ZENER CURRENT

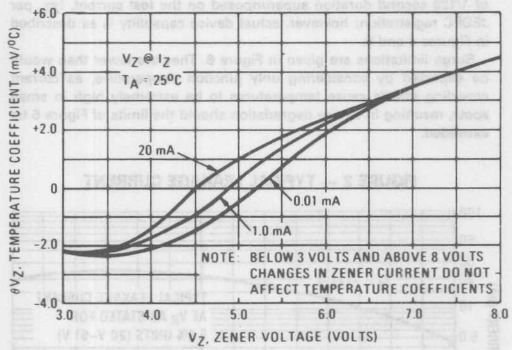


FIGURE 5 — TYPICAL CAPACITANCE

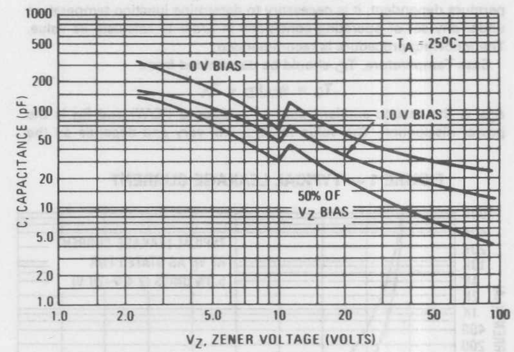
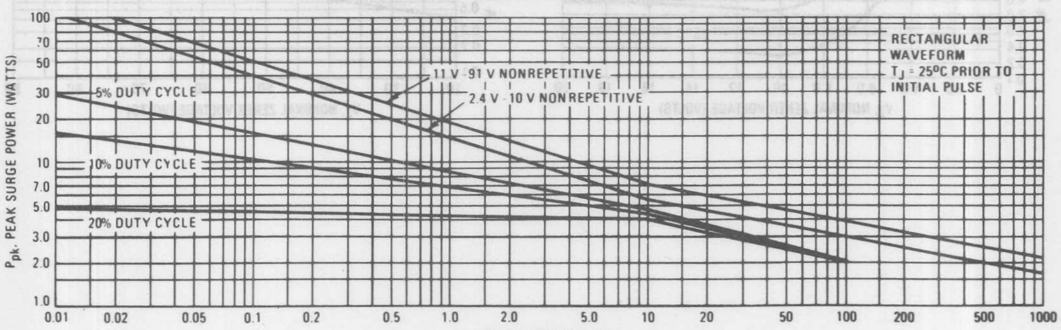


FIGURE 6 — MAXIMUM SURGE POWER



This graph represents 90 percentil data points.
For worst-case design characteristics, multiply surge power by 2/3.

FIGURE 7 — EFFECT OF ZENER CURRENT ON ZENER IMPEDANCE

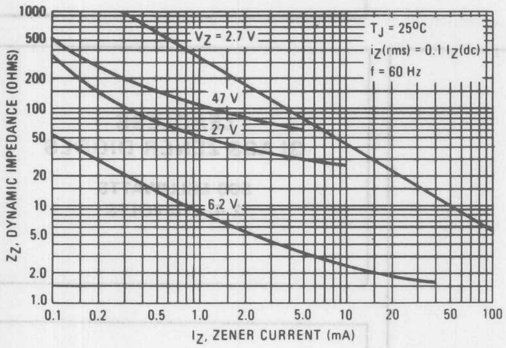


FIGURE 8 — EFFECT OF ZENER VOLTAGE ON ZENER IMPEDANCE

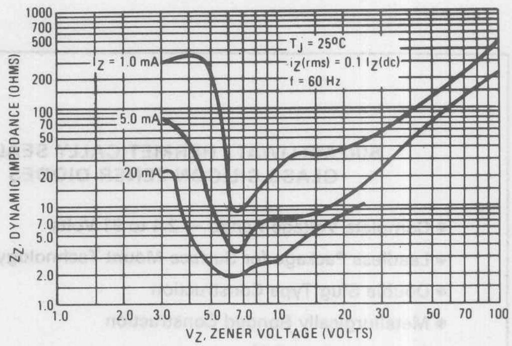


FIGURE 9 — TYPICAL NOISE DENSITY

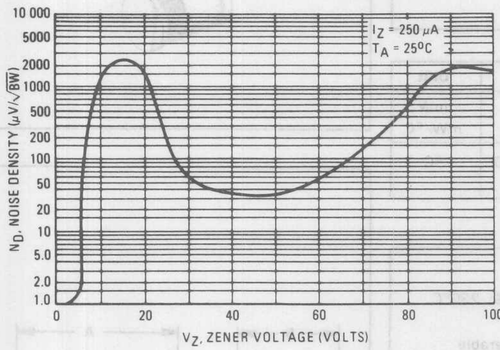
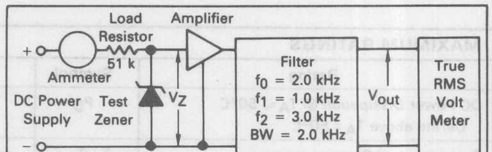


FIGURE 10 — NOISE DENSITY MEASUREMENT METHOD



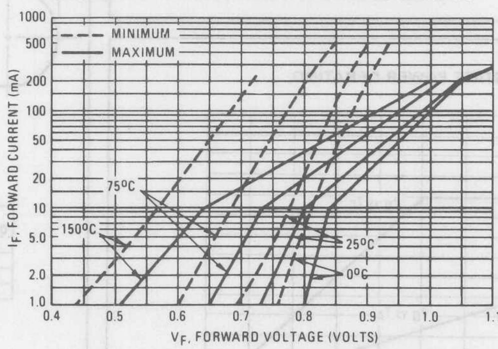
Noise Density (Volts Per Square Root Bandwidth) $= \dfrac{V_{out}}{\text{Overall Gain}\ \sqrt{BW}}$

Where: BW = Filter Bandwidth (Hz)

V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

FIGURE 11 — TYPICAL FORWARD CHARACTERISTICS



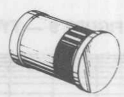
4

LEADLESS GLASS ZENER DIODES

500 MILLIWATTS
2.4-110 VOLTS

500 MILLIWATT HERMETICALLY SEALED GLASS SILICON ZENER DIODES

- Complete Voltage Range — 2.4 to 91 Volts
- Leadless Package for Surface Mount Technology
- Double Slug Type Construction
- Metallurgically Bonded Construction
- Oxide Passivated Die



MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_A \leq 50°C$ Derate above $T_A = 50°C$	P_D	500 3.3	mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

MECHANICAL CHARACTERISTICS

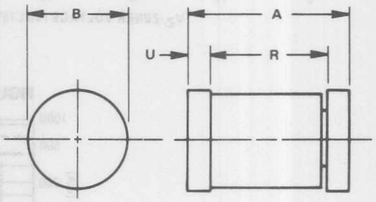
CASE: Double slug type, hermetically sealed glass

MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 230°C, for 10 seconds

FINISH: All external surfaces are corrosion resistant and readily solderable

POLARITY: Cathode indicated by color band. When operated in zener mode, cathode will be positive with respect to anode

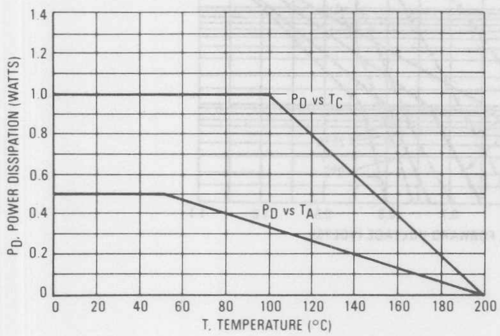
MOUNTING POSITION: Any



DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	3.30	3.70	0.130	0.146
B	1.60	1.70	0.063	0.067
R	2.49	2.59	0.098	0.102
U	0.41	0.55	0.016	0.022

CASE 362-01
GLASS

STEADY STATE POWER DERATING



ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted. Based on dc measurements at thermal equilibrium; case temperature maintained at 30±2°C. V_F = 1.1 max @ I_F = 200 mA for all types.)

Type No. (Note 1)	Nominal Zener Voltage V_Z @ I_{ZT} Volts (Note 2)	Test Current I_{ZT} mA	Max Zener Impedance A and B Suffix only		Max Reverse Leakage Current				Max Zener Voltage Temperature Coeff. (A and B Suffix only) θ_{VZ} (%/°C) (Note 3)
			Z_{ZT} @ I_{ZT} Ohms	Z_{ZK} @ I_{ZK} = 0.25 mA Ohms	A and B Suffix only: I_R µA	@ V_R Volts A	V_R Volts B	Non-Suffix: I_R @ V_R Used for Suffix A µA	
MLL5221A	2.4	20	30	1200	100	0.95	1.0	200	−0.085
MLL5222A	2.5	20	30	1250	100	0.95	1.0	200	−0.085
MLL5223A	2.7	20	30	1300	75	0.95	1.0	150	−0.080
MLL5224A	2.8	20	30	1400	75	0.95	1.0	150	−0.080
MLL5225A	3.0	20	29	1600	50	0.95	1.0	100	−0.075
MLL5226A	3.3	20	28	1600	25	0.95	1.0	100	−0.070
MLL5227A	3.6	20	24	1700	15	0.95	1.0	100	−0.065
MLL5228A	3.9	20	23	1900	10	0.95	1.0	75	−0.060
MLL5229A	4.3	20	22	2000	5.0	0.95	1.0	50	±0.055
MLL5230A	4.7	20	19	1900	5.0	1.9	2.0	50	±0.030
MLL5231A	5.1	20	17	1600	5.0	1.9	2.0	50	±0.030
MLL5232A	5.6	20	11	1600	5.0	2.9	3.0	50	+0.038
MLL5233A	6.0	20	7.0	1600	5.0	3.3	3.5	50	+0.038
MLL5234A	6.2	20	7.0	1000	5.0	3.8	4.0	50	+0.045
MLL5235A	6.8	20	5.0	750	3.0	4.8	5.0	30	+0.050
MLL5236A	7.5	20	6.0	500	3.0	5.7	6.0	30	+0.058
MLL5237A	8.2	20	8.0	500	3.0	6.2	6.5	30	+0.062
MLL5238A	8.7	20	8.0	600	3.0	6.2	6.5	30	+0.065
MLL5239A	9.1	20	10	600	3.0	6.7	7.0	30	+0.068
MLL5240A	10	20	17	600	3.0	7.6	8.0	30	+0.075
MLL5241A	11	20	22	600	2.0	8.0	8.4	30	+0.076
MLL5242A	12	20	30	600	1.0	8.7	9.1	10	+0.077
MLL5243A	13	9.5	13	600	0.5	9.4	9.9	10	+0.079
MLL5244A	14	9.0	15	600	0.1	9.5	10	10	+0.082
MLL5245A	15	8.5	16	600	0.1	10.5	11	10	+0.082
MLL5246A	16	7.8	17	600	0.1	11.4	12	10	+0.083
MLL5247A	17	7.4	19	600	0.1	12.4	13	10	+0.084
MLL5248A	18	7.0	21	600	0.1	13.3	14	10	+0.085
MLL5249A	19	6.6	23	600	0.1	13.3	14	10	+0.086
MLL5250A	20	6.2	25	600	0.1	14.3	15	10	+0.086
MLL5251A	22	5.6	29	600	0.1	16.2	17	10	+0.087
MLL5252A	24	5.2	33	600	0.1	17.1	18	10	+0.088
MLL5253A	25	5.0	35	600	0.1	18.1	19	10	+0.089
MLL5254A	27	4.6	41	600	0.1	20	21	10	+0.090
MLL5255A	28	4.5	44	600	0.1	20	21	10	+0.091
MLL5256A	30	4.2	49	600	0.1	22	23	10	+0.091
MLL5257A	33	3.8	58	700	0.1	24	25	10	+0.092
MLL5258A	36	3.4	70	700	0.1	26	27	10	+0.093
MLL5259A	39	3.2	80	800	0.1	29	30	10	+0.094
MLL5260A	43	3.0	93	900	0.1	31	33	10	+0.095
MLL5261A	47	2.7	105	1000	0.1	34	36	10	+0.095
MLL5262A	51	2.5	125	1100	0.1	37	39	10	+0.096
MLL5263A	56	2.2	150	1300	0.1	41	43	10	+0.096
MLL5264A	60	2.1	170	1400	0.1	44	46	10	+0.097
MLL5265A	62	2.0	185	1400	0.1	45	47	10	+0.097
MLL5266A	68	1.8	230	1600	0.1	49	52	10	+0.097
MLL5267A	75	1.7	270	1700	0.1	53	56	10	+0.098
MLL5268A	82	1.5	330	2000	0.1	59	62	10	+0.098
MLL5269A	87	1.4	370	2200	0.1	65	68	10	+0.099
MLL5270A	91	1.4	400	2300	0.1	66	69	10	+0.099

4

4

NOTE 1. Tolerance — Units with guaranteed limits on all six parameters are indicated by suffix "A" for ±10% tolerance and suffix "B" for ±5.0% units.

NOTE 2. Special Selections† Available Include:
1. Nominal zener voltages between those shown.
2. Two or more units for series connection with specified tolerance on total voltage. Series matched sets make zener voltages in excess of 200 volts possible as well as providing lower temperature coefficients, lower dynamic impedance and greater power handling ability.
3. Nominal voltages at non-standard test currents.

NOTE 3. Temperature Coefficient (θ_{VZ}) — Test conditions for temperature coefficient are as follows:
a. I_{ZT} = 7.5 mA, T_1 = 25°C,
T_2 = 125°C (MLL5221A,B through MLL5242A,B).
b. I_{ZT} = Rated I_{ZT}, T_1 = 25°C,
T_2 = 125°C (MLL5243A, B through MLL5270A,B).
Device to be temperature stabilized with current applied prior to reading breakdown voltage at the specified ambient temperature.

NOTE 4. Zener Voltage (V_Z) Measurement — Nominal zener voltage is measured with the device junction in thermal equilibrium at the case temperature of 30°C ±1°C.

NOTE 5. Zener Impedance (Z_Z) Derivation — Z_{ZT} and Z_{ZK} are measured by dividing the ac voltage drop across the device by the ac current applied. The specified limits are for $I_Z(ac)$ = 0.1 × $I_Z(dc)$ with the ac frequency = 1.0 kHz.

† For more information on special selections contact your nearest Motorola representative.

APPLICATION NOTE

Since the actual voltage available from a given zener diode is temperature dependent, it is necessary to determine junction temperature under any set of operating conditions in order to calculate its value. The following procedure is recommended:

Case Temperature, T_C, should be determined from:

$$T_C = \theta_{CA}P_D + T_A.$$

θ_{CA} is the case-to-ambient thermal resistance (°C/W) and P_D is the power dissipation. The value for θ_{CA} will vary and depends on the device mounting method. θ_{CA} is generally 200°C/W for the various clips and tie points in common use and for printed circuit board wiring.

The temperature of the case can also be measured using a thermocouple placed at the case end as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of T_C, the junction temperature may be determined by:

$$T_J = T_C + \Delta T_{JC}.$$

ΔT_{JC} is the increase in junction temperature above the case temperature and may be found by using:

$$\Delta T_{JC} = \theta_{JC}P_D.$$

For worst-case design, using expected limits of I_Z, limits of P_D and the extremes of $T_J(\Delta T_J)$ may be estimated. Changes in voltage, V_Z, can then be found from:

$$\Delta V = \theta_{VZ}\Delta T_J.$$

θ_{VZ}, the zener voltage temperature coefficient, is found from Figures 3 and 4.

Under high power-pulse operation, the zener voltage will vary with time and may also be affected significantly by the zener resistance. For best regulation, keep current excursions as low as possible.

Surge limitations are given in Figure 6. They are lower than would be expected by considering only junction temperature, as current crowding effects cause temperatures to be extremely high in small spots, resulting in device degradation should the limits of Figure 6 be exceeded.

FIGURE 1 — TYPICAL LEAKAGE CURRENT

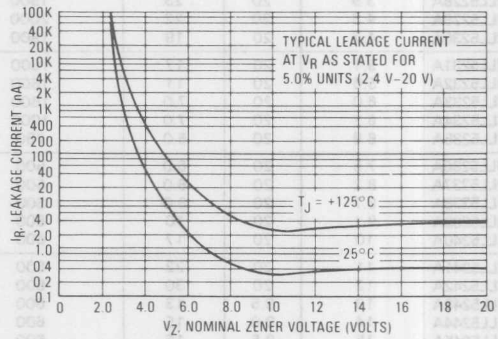


FIGURE 2 — TYPICAL LEAKAGE CURRENT

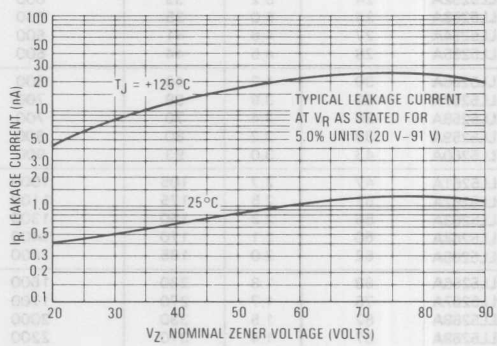
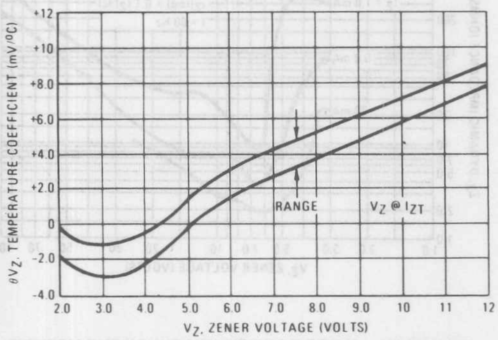


FIGURE 3 — TEMPERATURE COEFFICIENTS

(-55°C to +150°C temperature range; 90% of the units are in the ranges indicated.)

a – RANGE FOR UNITS TO 12 VOLTS



b – RANGE FOR UNITS 12 TO 100 VOLTS

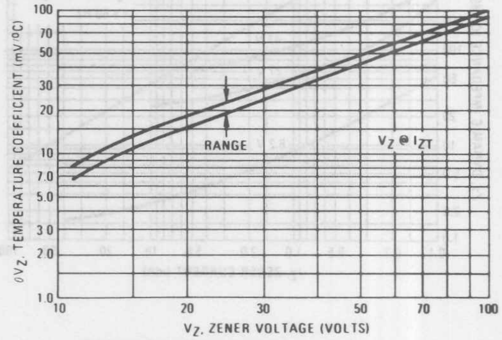


FIGURE 4 — EFFECT OF ZENER CURRENT

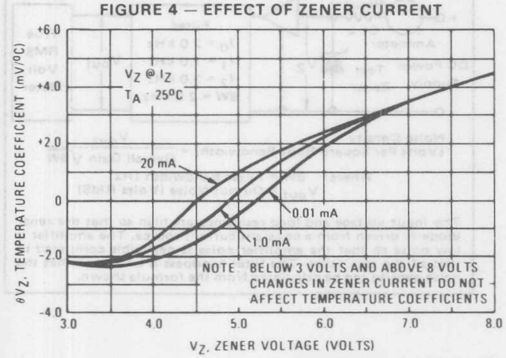


FIGURE 5 — TYPICAL CAPACITANCE

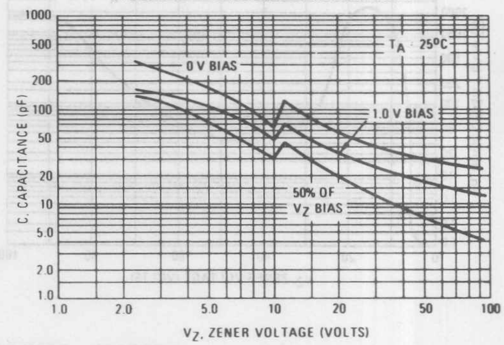
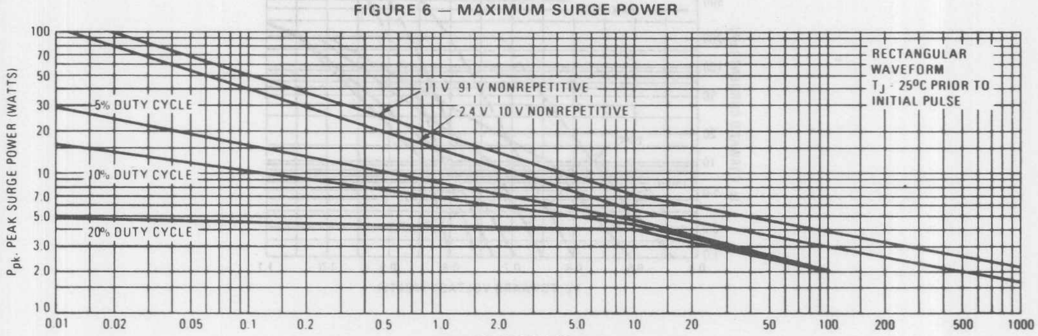
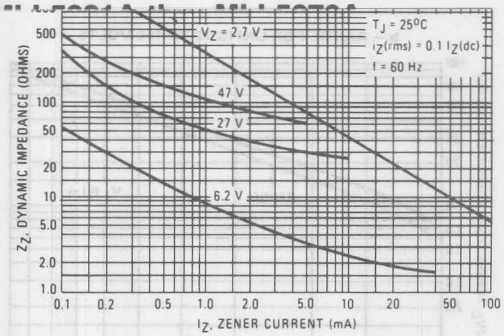


FIGURE 6 — MAXIMUM SURGE POWER



This graph represents 90 percentil data points.

For worst-case design characteristics, multiply surge power by 2/3.



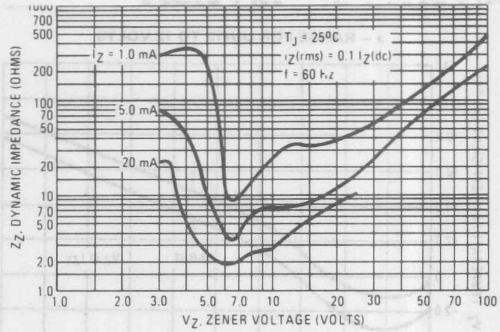


FIGURE 9 — TYPICAL NOISE DENSITY

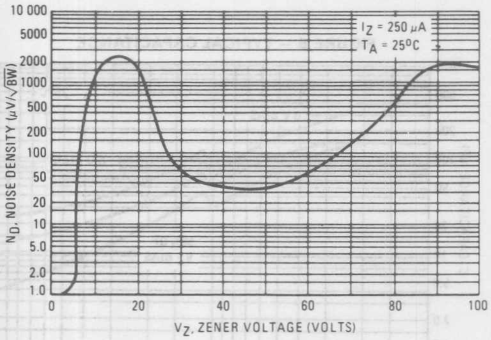
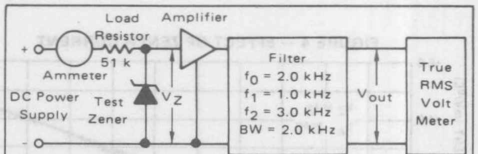


FIGURE 10 — NOISE DENSITY MEASUREMENT METHOD



$$\text{Noise Density (Volts Per Square Root Bandwidth)} = \frac{V_{out}}{\text{Overall Gain}\sqrt{BW}}$$

Where: BW = Filter Bandwidth (Hz)
V_{out} = Output Noise (Volts RMS)

The input voltage and load resistance are high so that the zener diode is driven from a constant current source. The amplifier is low noise so that the amplifier noise is negligible compared to that of the test zener. The filter bandpass is known so that the noise density can be calculated from the formula shown.

FIGURE 11 — TYPICAL FORWARD CHARACTERISTICS

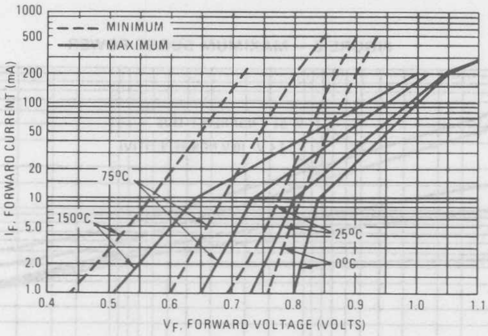


FIGURE 12 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 1 THRU 16 VOLTS

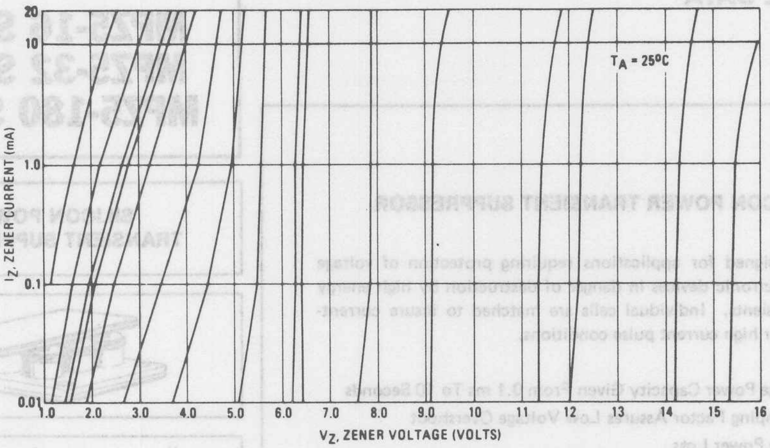


FIGURE 13 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 15 THRU 30 VOLTS

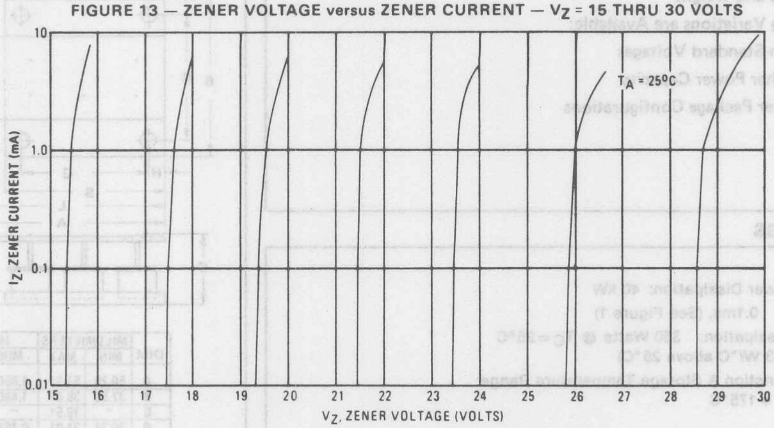
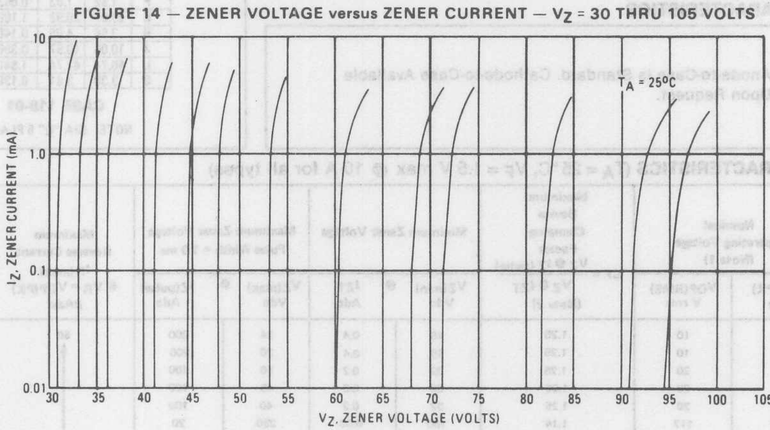


FIGURE 14 — ZENER VOLTAGE versus ZENER CURRENT — V_Z = 30 THRU 105 VOLTS



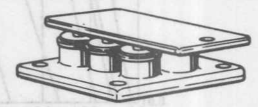
4

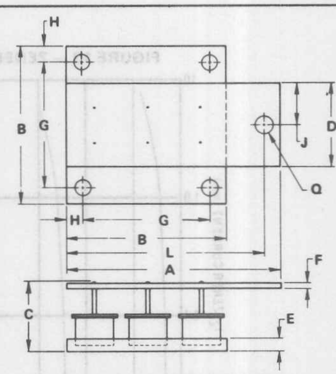
MPTE-5,C thru MPTE-45,C
See Page 4-71

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MPZ5-16 Series
MPZ5-32 Series
MPZ5-180 Series

SILICON POWER TRANSIENT SUPPRESSOR





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	50.29	51.31	1.980	2.020
B	37.59	38.61	1.480	1.520
C	–	16.51	–	0.650
D	20.24	21.01	0.797	0.827
E	2.92	3.43	0.115	0.135
F	1.32	1.83	0.052	0.072
G	29.97	30.99	1.180	1.220
H	3.56	4.06	0.140	0.160
J	10.06	10.57	0.396	0.416
L	46.74	47.74	1.840	1.860
Q	3.30	3.81	0.130	0.150

CASE 119-01

NOTE: DIA "Q" 5 PLACES

SILICON POWER TRANSIENT SUPPRESSOR

. . . designed for applications requiring protection of voltage sensitive electronic devices in danger of destruction by high energy voltage transients. Individual cells are matched to insure current-sharing under high current pulse conditions.

- Peak Surge Power Capacity Given From 0.1 ms To 10 Seconds
- Low Clamping Factor Assures Low Voltage Overshoot
- Negligible Power Loss
- Small Size and Weight
- Following Variations are Available:
  - Non-Standard Voltages
  - Higher Power Capacity
  - Other Package Configurations

4

MAXIMUM RATINGS

Transient Power Dissipation: 40 kW
Pulse Width: 0.1ms, (See Figure 1)
DC Power Dissipation: 350 Watts @ $T_C = 25°C$
(Derate 2.33 W/°C above 25°C)
Operating Junction & Storage Temperature Range:
−65°C to +175°C

MECHANICAL CHARACTERISTICS

POLARITY: Anode-to-Case is Standard. Cathode-to-Case Available Upon Request.

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$, $V_F = 1.5$ V max @ 10 A for all types)

Type	Nominal Operating Voltage (Note 1) $V_{OP(PK)}$ Vdc	Nominal Operating Voltage (Note 1) $V_{OP(RMS)}$ V rms	Maximum Device Clamping Factor $CF = \frac{V_Z @ I_{Z(pulse)}}{V_Z @ I_{ZT}}$ (Note 2)	Minimum Zener Voltage $V_{Z(min)}$ Vdc	@ I_{ZT} Adc	Maximum Zener Voltage Pulse Width = 1.0 ms $V_{Z(max)}$ Vdc	@ $I_{Z(pulse)}$ Adc	Maximum Reverse Current $I_{R(max)}$ @ $V_R = V_{OP(PK)}$ µAdc	Typical Capacitance C (typ) @ $V_R = V_{OP(PK)}$ µF
MPZ5-16A	14	10	1.25	16	0.4	24	200	50	0.025
-16B	14	10	1.25	16	0.4	20	200		0.025
-32A	28	20	1.25	32	0.2	50	100		0.011
-32B	28	20	1.25	32	0.2	45	100		0.011
-32C	28	20	1.25	32	0.2	40	100		0.011
-180A	165	117	1.14	180	0.03	250	20		0.0012
-180B	165	117	1.14	180	0.03	225	20		0.0012
-180C	165	117	1.14	180	0.03	205	20	50	0.0012

FIGURE 1 – MAXIMUM NON-REPETITIVE SURGE POWER
(RECTANGULAR WAVEFORM)

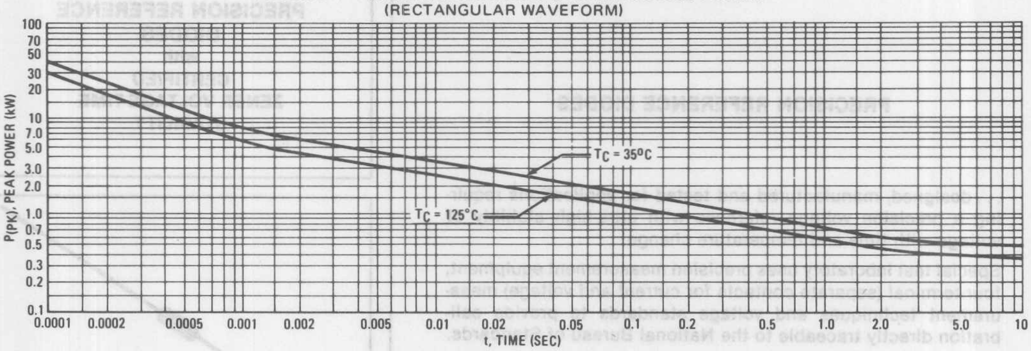
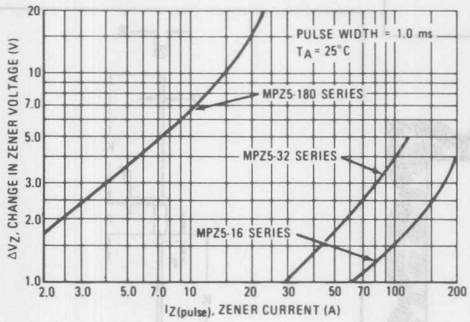


FIGURE 2 – TYPICAL DYNAMIC ZENER VOLTAGE CHARACTERISTICS (Note 2)



NOTE 1: Nominal operating voltage is defined as normal input voltage to device for non-operating condition. If non-sinusoidal wave or dc input is present, peak voltage input values $V_{OP(PK)}$ should be used to select device type.

NOTE 2: The maximum device clamping factor C_F is a ratio of V_Z measured at I_Z (pulse) given in the Electrical Characteristics Table divided by V_Z measured at I_{ZT} under steady state conditions. This value guarantees the sharpness of the voltage breakdown of individual devices. Figure 2 demonstrates the typical sharpness of the breakdown, and indicates the voltage regulation over a wide range of currents.

$$\Delta V_Z = V_Z @ I_{Z(pulse)} - V_Z @ I_{ZT}$$

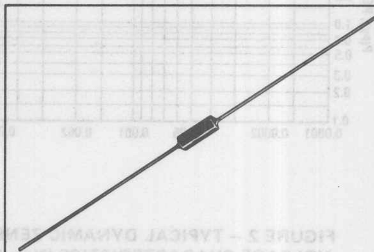
4

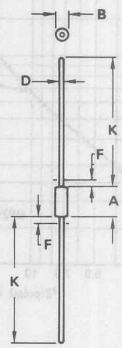
PRECISION REFERENCE DIODES

. . . designed, manufactured and tested for applications requiring a precision voltage reference with ultra-high stability of voltage with time and temperature change.

Special test laboratory uses precision measurement equipment, four-terminal (separate contacts for current and voltage) measurement techniques and voltage standards to provide calibration directly traceable to the National Bureau of Standards.

PRECISION REFERENCE DIODES with CERTIFIED ZENER VOLTAGE-TIME STABILITY





NOTES:
1. PACKAGE CONTOUR OPTIONAL WITHIN DIA B AND LENGTH A. HEAT SLUGS, IF ANY, SHALL BE INCLUDED WITHIN THIS CYLINDER, BUT SHALL NOT BE SUBJECT TO THE MIN LIMIT OF DIA B.
2. LEAD DIA NOT CONTROLLED IN ZONES F, TO ALLOW FOR FLASH, LEAD FINISH BUILDUP, AND MINOR IRREGULARITIES OTHER THAN HEAT SLUGS.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	5.84	7.62	0.230	0.300
B	2.16	2.72	0.085	0.107
D	0.46	0.56	0.018	0.022
F	–	1.27	–	0.050
K	25.40	38.10	1.000	1.500

All JEDEC dimensions and notes apply

CASE 51-02
DO-204AA
GLASS

Certified TEST DATA

Every Precision Reference Diode is individually serialized and its test data recorded on a Certificate of Precision that accompanies the device when shipped. This data shows:

- Actual device voltage at 168 hour intervals during verification test
- Voltage stability throughout the entire 1000 hour test period
- Certification of Precision
- All diodes are marked with the device type number and polarity band

OPERATING TEMPERATURE RANGE:* 25 to 100°C.

MZ600 SERIES (Voltage 6.2V ±5%, $I_{ZT} = 7.5$ mAdc†, $\Delta V_Z = 2.5$ mVdc**)

Type No.	Voltage-Time Stability (μV/1000 Hours)	Parts Per Million Change (ppm/1000 Hours)
MZ605	31 Maximum	< 5
MZ610	62 Maximum	<10
MC620	124 Maximum	<20
MZ640	248 Maximum	<40

DYNAMIC IMPEDANCE: 10 Ohms at $I_{ZT} = 7.5$ mAdc, $I_{ac} = 0.75$ mA.

NOTES

†TEST CURRENT

For certification testing of time stability, Motorola maintains I_{ZT} constant and repeatable to ±0.05 μA tolerance. For voltage tolerance, impedance and voltage temperature stability I_{ZT} needs to be held to 0.01 tolerance only.

*Maximum limits for use as a precision reference device. Limits are well below the maximum thermal limits.

**VOLTAGE-TEMPERATURE STABILITY: Maximum allowable voltage change between voltages recorded at 25, 75 and 100°C ambient.

VOLTAGE-TIME STABILITY
(ΔV_Z/1000 Hours).

The device voltage is read and recorded initially and at 168 hour intervals through 1000 hours. The maximum change of voltage between readings, taken at any of the seven points, must be less than the maximum voltage change per 1000 hour specified as Voltage-Time Stability.

TURN-ON CHARACTERISTICS

Precision Reference Diodes have been tested to determine the behavior of the device under interrupted power operation. To insure specified performance, adequate time must be allowed for the device and its environment to reach thermal equilibrium. "Warm-up" time may range from 8 to 24 hours. Thermal equilibrium is reached when the chamber is cycling at the required temperature with the device energized.

After this "'warm-up" period, the device voltage will be between the minimum and the maximum voltage of those recorded at the seven points of the Voltage-Time Stability certification.

MOUNTING

Excellent results have been obtained by using a mechanical mounting. If necessary, the device may be soldered into a circuit using a heat sink between the heat source and the body of the diode. A low thermal EMF solder is recommended.

SPECIAL NOTE

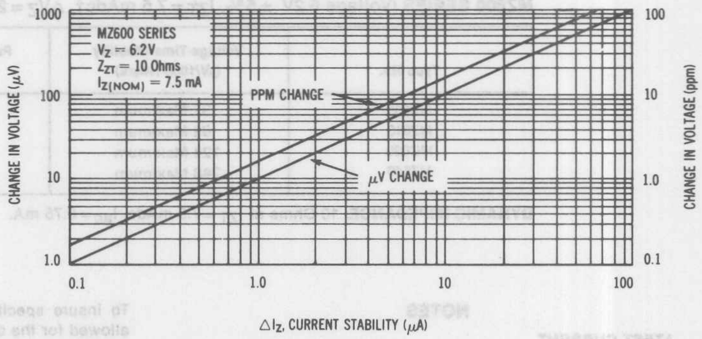
Voltage tolerance less than 5.0% is available upon special request.

Precision Reference Diodes capable of meeting special requirements for standard voltages regardless of required test current, temperature range, or test temperatures are available. Custom requirements of particular devices for specific applications are also available.

VOLTAGE-CURRENT STABILITY CHARACTERISTICS

For verification of time stability, and for repeatable operation, I_{ZT} should be maintained with a tolerance of ± 0.1 μA. Figure 1 will assist in design where the supply current stability cannot be maintained to better than 0.2 μA deviation.

FIGURE 1 — MAXIMUM VOLTAGE CHANGE, IN μV AND PPM, DUE TO CURRENT SUPPLY STABILITY



VOLTAGE-TEMPERATURE CHARACTERISTICS

CHOICE OF OPERATING TEMPERATURE

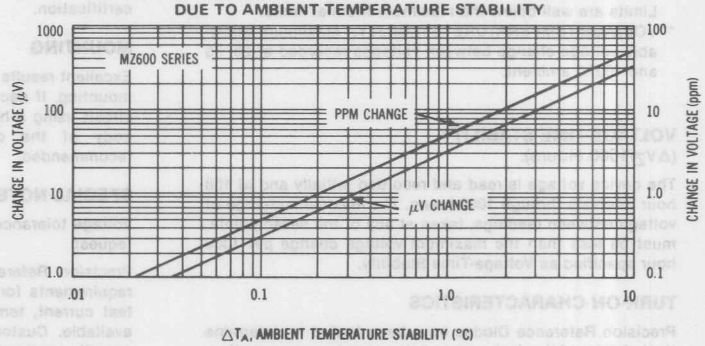
The stability certification is performed at 65°C ± 0.02°C. The operating temperature can be selected within the operating temperature range. If the desired temperature is not 65°C, the precise voltage of the device will be different but the certified stability will still be observed.

VOLTAGE TEMPERATURE STABILITY

For verification of time stability and/or repeatable operation, the ambient temperature should be controlled to ± 0.1°C.

Figure 2 will assist in designs where ambient temperature cannot be controlled to better than 0.2°C deviation.

FIGURE 2 — TYPICAL VOLTAGE CHANGE, IN μV AND PPM, DUE TO AMBIENT TEMPERATURE STABILITY



MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

MZ2360
MZ2361

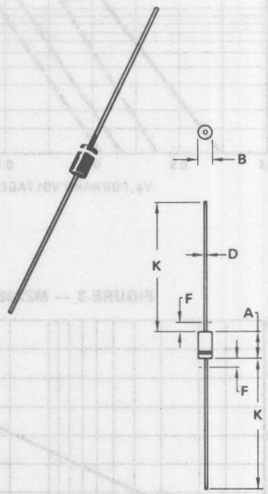
FORWARD REFERENCE DIODES

STABISTORS

CONSTANT-VOLTAGE REFERENCE DIODES FOR LOW-VOLTAGE APPLICATIONS

. . . high-conductance silicon diodes designed as a stable forward reference source for biasing transistor amplifiers and similar applications.

- Guaranteed Forward Voltage Range
- Temperature Effects Provided



NOTES:
1. ALL RULES AND NOTES ASSOCIATED WITH JEDEC DO-41 OUTLINE SHALL APPLY.
2. POLARITY DENOTED BY CATHODE BAND.
3. LEAD DIAMETER NOT CONTROLLED WITHIN "F" DIMENSION.

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	4.07	5.20	0.160	0.205
B	2.04	2.71	0.080	0.107
D	0.71	0.86	0.028	0.034
F	–	1.27	–	0.050
K	27.94	–	1.100	–

CASE 59-03
DO-41
GLASS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
DC Power Dissipation @ $T_L = 30°C \pm 3°C$, Lead Length = 3/8″	P_D	1.5	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	− 65 to + 175	°C

MECHANICAL CHARACTERISTICS

CASE: Surmetic

DIMENSIONS: See outline drawing

FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable

POLARITY: Cathode indicated by polarity band. Cathode negative for forward reference application.

MOUNTING POSITIONS: Any

ELECTRICAL CHARACTERISTICS ($T_A = 25°C$ unless otherwise noted)

Type Number	Forward Reference Voltage (1) V_F Volts Min/Max	@ I_F mA	Reverse Leakage Current (Max) I_R µA	@ V_R Volts	Package	Case
MZ2360	0.63/0.71	10	10	5.0	Surmetic	59-03
MZ2361	1.24/1.38	10	10	5.0	Surmetic	59-03

(1) Motorola guarantees the forward reference voltage when measured at 90 seconds while maintaining the lead temperature (T_L) at 30°C ± 1°C, 3/8″ from the diode body.

4

TYPICAL FORWARD VOLTAGE CHARACTERISTICS

FIGURE 1 — MZ2360

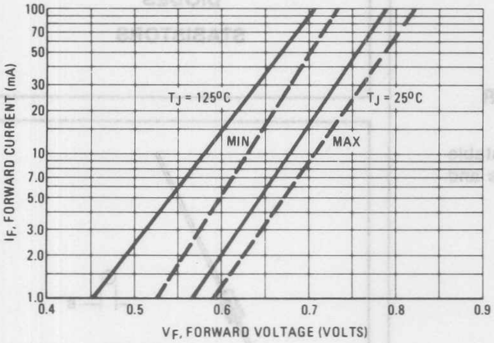
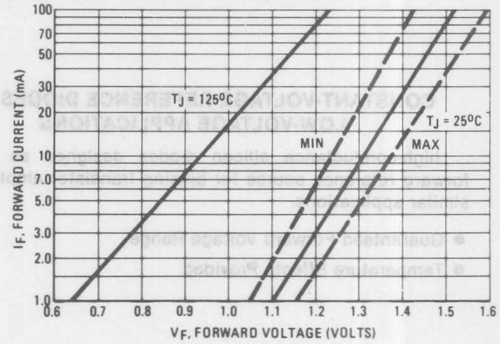


FIGURE 2 — MZ2361



TYPICAL TEMPERATURE COEFICIENT

FIGURE 3 — MZ2360

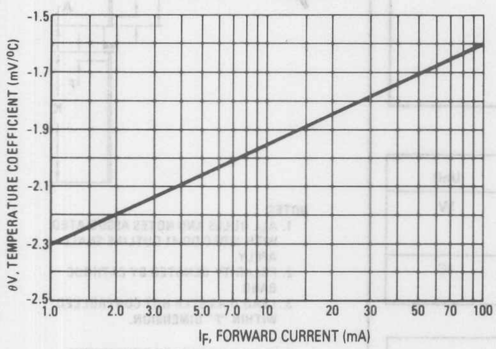
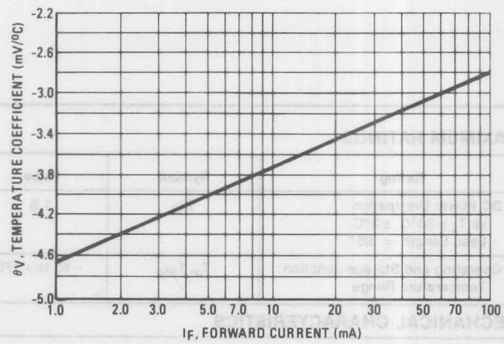


FIGURE 4 — MZ2361

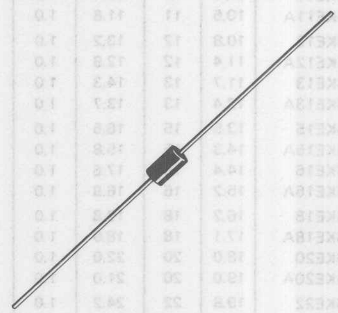


MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

P6KE6.8,A thru P6KE200,A

ZENER OVERVOLTAGE TRANSIENT SUPPRESSORS

6.8-200 VOLT
600 WATT PEAK POWER
5.0 WATTS STEADY STATE



ZENER OVERVOLTAGE TRANSIENT SUPPRESSOR

The P6KE6.8 series is designed to protect voltage sensitive components from high voltage, high energy transients. They have excellent clamping capability, high surge capability, low zener impedance and fast response time. The P6KE6.8 series is supplied in Motorola's exclusive, cost-effective, highly reliable surmetic axial leaded package and is ideally-suited for use in communication systems, numerical controls, process controls, medical equipment, business machines, power supplies and many other industrial/consumer applications.

SPECIFICATION FEATURES

- Standard Zener Voltage Range — 6.8 to 200 V
- Peak Power — 600 Watts @ 1.0 ms
- Maximum Clamp Voltage @ Peak Pulse Current
- Low Leakage < 5.0 μA above 10 V
- Maximum Temperature Coefficient Specified

MAXIMUM RATINGS

Rating	Symbol	Value	Units
Peak Power Dissipation (1) @ $T_L \leq 25^oC$	P_{PK}	600	Watts
Steady State Power Dissipation @ $T_L \leq 75^oC$, Lead Length = 3/8" Derated above $T_L = 75^oC$	P_D	5.0 50	Watts mW/^oC
Forward Surge Current (2) @ $T_A = 25^oC$	I_{FSM}	100	Amps
Operating and Storage Temperature Range	T_J, T_{stg}	−65 to +175	^oC

Lead Temperature not less than 1/16" from the case for 10 seconds: 230°C

MECHANICAL CHARACTERISTICS

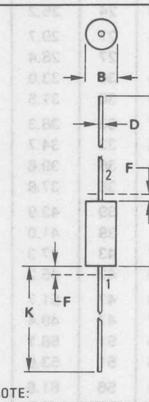
CASE: Void-free, transfer-molded, thermosetting plastic

FINISH: All external surfaces are corrosion resistant and leads are readily solderable and weldable

POLARITY: Cathode indicated by polarity band. When operated in zener mode, will be positive with respect to anode

MOUNTING POSITION: Any

NOTES: 1. Non-Repetitive Current Pulse per Figure 4 and Derated above $T_A = 25^oC$ per Figure 2.
2. 1/2 Square Wave (or equivalent), PW = 8.3 ms, Duty Cycle = 4 Pulses per Minute maximum.



NOTE:
1. LEAD DIAMETER & FINISH NOT CONTROLLED WITHIN DIM "F".

STYLE 1:
PIN 1. ANODE
2. CATHODE

DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	8.38	8.89	0.330	0.350
B	3.30	3.68	0.130	0.145
D	0.94	1.09	0.037	0.043
F	–	1.27	–	0.050
K	25.40	31.75	1.000	1.250

CASE 17-02 GLASS

4

4

ELECTRICAL CHARACTERISTIC (T_A = 25°C unless otherwise noted) V_F = 3.5 V max, I_F** = 50 A for all types.

Device	Breakdown Voltage * V_{BR} (Volts) Min	Nom	Max	@ I_T (mA)	Working Peak Reverse Voltage V_{RWM} (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM} (Clamping Voltage) V_{RSM} (Volts)	Maximum Temperature Coefficient of V_{BR} (%/°C)
P6KE6.8	6.12	6.8	7.48	10	5.50	1000	56	10.8	0.057
P6KE6.8A	6.45	6.8	7.14	10	5.80	1000	57	10.5	0.057
P6KE7.5	6.75	7.5	8.25	10	6.05	500	51	11.7	0.061
P6KE7.5A	7.13	7.5	7.88	10	6.40	500	53	11.3	0.061
P6KE8.2	7.38	8.2	9.02	10	6.63	200	48	12.5	0.065
P6KE8.2A	7.79	8.2	8.61	10	7.02	200	50	12.1	0.065
P6KE9.1	8.19	9.1	10.0	1.0	7.37	50	44	13.8	0.068
P6KE9.1A	8.65	9.1	9.55	1.0	7.78	50	45	13.4	0.068
P6KE10	9.00	10	11.0	1.0	8.10	10	40	15.0	0.073
P6KE10A	9.50	10	10.5	1.0	8.55	10	41	14.5	0.073
P6KE11	9.90	11	12.1	1.0	8.92	5.0	37	16.2	0.075
P6KE11A	10.5	11	11.6	1.0	9.40	5.0	38	15.6	0.075
P6KE12	10.8	12	13.2	1.0	9.72	5.0	35	17.3	0.078
P6KE12A	11.4	12	12.6	1.0	10.2	5.0	36	16.7	0.078
P6KE13	11.7	13	14.3	1.0	10.5	5.0	32	19.0	0.081
P6KE13A	12.4	13	13.7	1.0	11.1	5.0	33	18.2	0.081
P6KE15	13.5	15	16.5	1.0	12.1	5.0	27	22.0	0.084
P6KE15A	14.3	15	15.8	1.0	12.8	5.0	28	21.2	0.084
P6KE16	14.4	16	17.6	1.0	12.9	5.0	26	23.5	0.086
P6KE16A	15.2	16	16.8	1.0	13.6	5.0	27	22.5	0.086
P6KE18	16.2	18	19.8	1.0	14.5	5.0	23	26.5	0.088
P6KE18A	17.1	18	18.9	1.0	15.3	5.0	24	25.2	0.088
P6KE20	18.0	20	22.0	1.0	16.2	5.0	21	29.1	0.090
P6KE20A	19.0	20	21.0	1.0	17.1	5.0	22	27.7	0.090
P6KE22	19.8	22	24.2	1.0	17.8	5.0	19	31.9	0.092
P6KE22A	20.9	22	23.1	1.0	18.8	5.0	20	30.6	0.092
P6KE24	21.6	24	26.4	1.0	19.4	5.0	17	34.7	0.094
P6KE24A	22.8	24	25.2	1.0	20.5	5.0	18	33.2	0.094
P6KE27	24.3	27	29.7	1.0	21.8	5.0	15	39.1	0.096
P6KE27A	25.7	27	28.4	1.0	23.1	5.0	16	37.5	0.096
P6KE30	27.0	30	33.0	1.0	24.3	5.0	14	43.5	0.097
P6KE30A	28.5	30	31.5	1.0	25.6	5.0	14.4	41.4	0.097
P6KE33	29.7	33	36.3	1.0	26.8	5.0	12.6	47.7	0.098
P6KE33A	31.4	33	34.7	1.0	28.2	5.0	13.2	45.7	0.098
P6KE36	32.4	36	39.6	1.0	29.1	5.0	11.6	52.0	0.099
P6KE36A	34.2	36	37.8	1.0	30.8	5.0	12	49.9	0.099
P6KE39	35.1	39	42.9	1.0	31.6	5.0	10.6	56.4	0.100
P6KE39A	37.1	39	41.0	1.0	33.3	5.0	11.2	53.9	0.100
P6KE43	38.7	43	47.3	1.0	34.8	5.0	9.6	61.9	0.101
P6KE43A	40.9	43	45.2	1.0	36.8	5.0	10.1	59.3	0.101
P6KE47	42.3	47	51.7	1.0	38.1	5.0	8.9	67.8	0.101
P6KE47A	44.7	47	49.4	1.0	40.2	5.0	9.3	64.8	0.101
P6KE51	45.9	51	56.1	1.0	41.3	5.0	8.2	73.5	0.102
P6KE51A	48.5	51	53.6	1.0	43.6	5.0	8.6	70.1	0.102
P6KE56	50.4	56	61.6	1.0	45.4	5.0	7.4	80.5	0.103
P6KE56A	53.2	56	58.8	1.0	47.8	5.0	7.8	77.0	0.103
P6KE62	55.8	62	68.2	1.0	50.2	5.0	6.8	89.0	0.104
P6KE62A	58.9	62	65.1	1.0	53.0	5.0	7.1	85.0	0.104
P6KE68	61.2	68	74.8	1.0	55.1	5.0	6.1	98.0	0.104
P6KE68A	64.6	68	71.4	1.0	58.1	5.0	6.5	92.0	0.104
P6KE75	67.5	75	82.5	1.0	60.7	5.0	5.5	108.0	0.105
P6KE75A	71.3	75	78.8	1.0	64.1	5.0	5.8	103.0	0.105
P6KE82	73.8	82	90.2	1.0	66.4	5.0	5.1	118.0	0.105
P6KE82A	77.9	82	86.1	1.0	70.1	5.0	5.3	113.0	0.105
P6KE91	81.9	91	100.0	1.0	73.7	5.0	4.8	131.0	0.106
P6KE91A	86.5	91	95.50	1.0	77.8	5.0	4.8	125.0	0.106

ELECTRICAL CHARACTERISTICS (continued)

Device	Breakdown Voltage V_{BR} (Volts) Min	Nom	Max	@ I_T (mA)	Working Peak Reverse Voltage V_{RWM} (Volts)	Maximum Reverse Leakage @ V_{RWM} I_R (μA)	Maximum Reverse Surge Current I_{RSM}† (Amps)	Maximum Reverse Voltage @ I_{RSM} (Clamping Voltage) V_{RSM} (Volts)	Maximum Temperature Coefficient of V_{BR} (%/°C)
P6KE100	90.0	100	110.0	1.0	81.0	5.0	4.2	144.0	0.106
P6KE100A	95.0	100	105.0	1.0	85.5	5.0	4.4	137.0	0.106
P6KE110	99.0	110	121.0	1.0	89.2	5.0	3.8	158.0	0.107
P6KE110A	105.0	110	116.0	1.0	94.0	5.0	4.0	152.0	0.107
P6KE120	108.0	120	132.0	1.0	97.2	5.0	3.5	173.0	0.107
P6KE120A	114.0	120	126.0	1.0	102.0	5.0	3.6	165.0	0.107
P6KE130	117.0	130	143.0	1.0	105.0	5.0	3.2	187.0	0.107
P6KE130A	124.0	130	137.0	1.0	111.0	5.0	3.3	179.0	0.107
P6KE150	135.0	150	165.0	1.0	121.0	5.0	2.8	215.0	0.108
P6KE150A	143.0	150	158.0	1.0	128.0	5.0	2.9	207.0	0.108
P6KE160	144.0	160	176.0	1.0	130.0	5.0	2.6	230.0	0.108
P6KE160A	152.0	160	168.0	1.0	136.0	5.0	2.7	219.0	0.108
P6KE170	153.0	170	187.0	1.0	138.0	5.0	2.5	244.0	0.108
P6KE170A	162.0	170	179.0	1.0	145.0	5.0	2.6	234.0	0.108
P6KE180	162.0	180	198.0	1.0	146.0	5.0	2.3	258.0	0.108
P6KE180A	171.0	180	189.0	1.0	154.0	5.0	2.4	246.0	0.108
P6KE200	180.0	200	220.0	1.0	162.0	5.0	2.1	287.0	0.108
P6KE200A	190.0	200	210.0	1.0	171.0	5.0	2.2	274.0	0.108

†Surge Current Waveform per Figure 4 and Derate per Figure 2.

**1/2 Square or Equivalent Sine Wave, PW = 8.3 ms, Duty Cycle = 4 Pulses per Minute maximum.

*V_{BR} measured after I_T applied for 300 μs, I_T = Square Wave Pulse or equivalent.

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FIGURE 1 – PULSE RATING CURVE

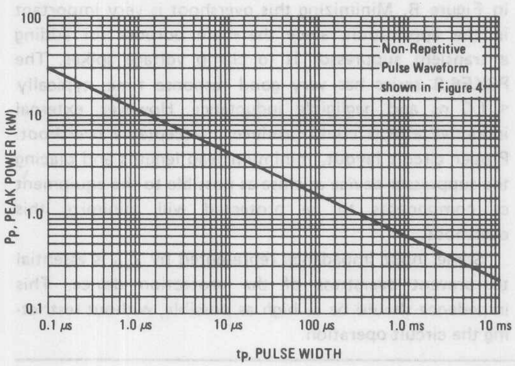


FIGURE 2 – PULSE DERATING CURVE

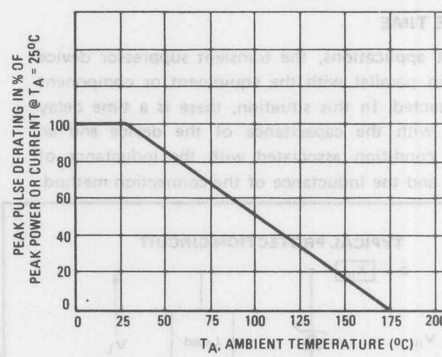


FIGURE 3 – CAPACITANCE versus BREAKDOWN VOLTAGE

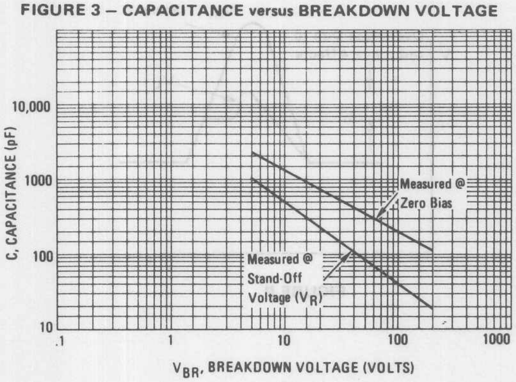


FIGURE 4 – PULSE WAVEFORM

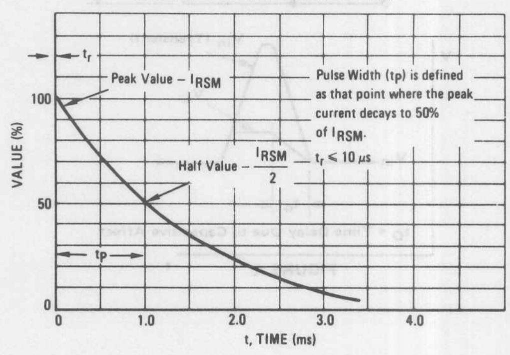
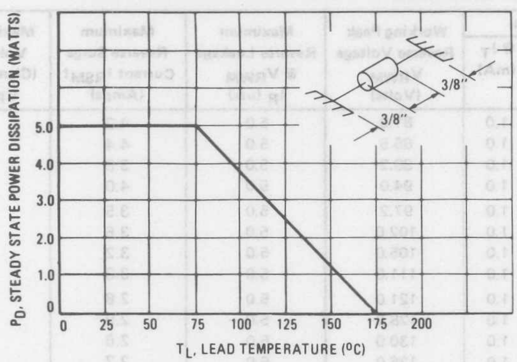


FIGURE 5 – STEADY STATE POWER DERATING



APPLICATION NOTES

SPECIAL DEVICES

Matched sets and back-to-back configurations for bidirectional applications can be ordered upon special request. Contact your nearest Motorola representative.

For a bidirectional device use a C or CA suffix (i.e. P6KE10CA). Electrical characteristics apply in both directions except for V_F. Available for all P/N's except P6KE6.8,A.

RESPONSE TIME

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method.

The capacitive affect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure A.

The inductive affects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive affect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure B. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The P6KE6.8 series has very good response time, typically < 1.0 ns and negligible inductance. However, external inductive affects could produce unacceptable overshoot. Proper circuit layout, minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by Z_{in} is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

TYPICAL PROTECTION CIRCUIT

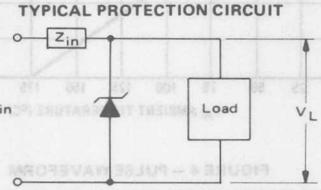


FIGURE A

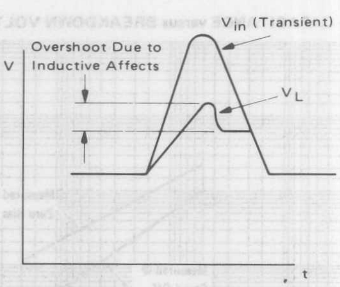


FIGURE B